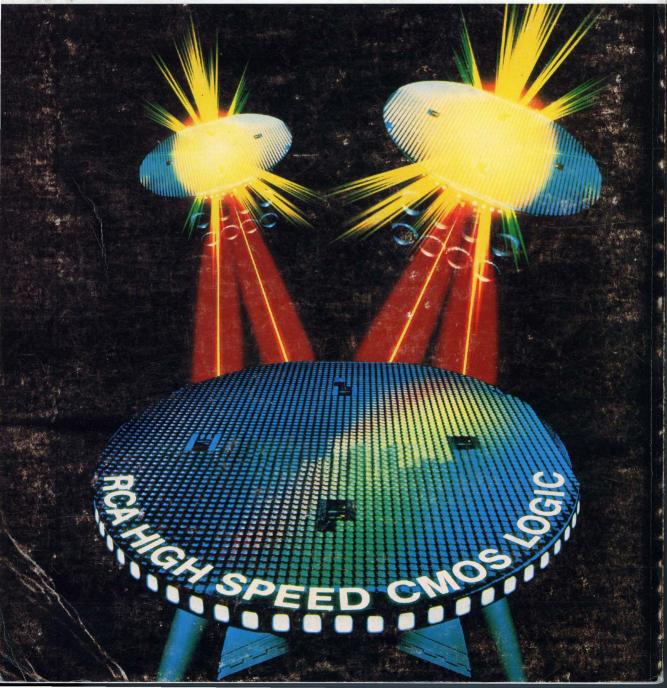


DATABOOK



RCA High-Speed CMOS Logic Integrated Circuits

The RCA HC/HCT series of high-speed CMOS logic integrated circuits include an extensive line of products that are pin compatible with many existing bipolar 54/74 LSTTL and CMOS 4000 series of digital logic types. The new HC/HCT series IC's provide high-speed CMOS replacements for the most popular LSTTL devices in existing designs and also offer low-power all-CMOS designs for new digital systems. Key family features of the RCA HC/HCT types include:

- Speeds equivalent to LSTTL types with typical gate delays of 8 ns.
- Fanout to 10 74 LSTTL loads; 15 loads using Bus Driver 54/74 types.
- Operating frequencies equivalent to LSTTL types, typically 50 MHz.
- The high voltage noise immunity characteristic of CMOS, typically 45 percent of Vcc, a two to three times improvement over LSTTL. (HC-Series types.)
- Wide range of power supply operating voltages, 2 to 6 volts.
- CMOS low static power consumption, typically less than 1 microwatt.

With the broad line of CMOS MSI function types currently available, together with performance offered by the RCA HC/HCT series of high-speed CMOS integrated circuits, the designer need not sacrifice speed for power consumption. Add the other classical advantages of CMOS, including high noise immunity and wide power supply and temperature ranges, and the decision to use high-speed CMOS logic is the choice for the 80's. This family provides for the design of more cost-effective systems to serve high-speed market applications.

The RCA product line consists of CD54/74HC-series types, which feature CMOS input voltage level compatibility and CD54/74HCT-series types, which are input voltage level compatible with LSTTL devices. The line also includes a limited number of single-stage, unbuffered inverter types (CD54/74HCU-series) for added versatility in oscillator and amplifier applications.

A general information section defines the distinguishing characteristics of each product series and provides characteristic data and classification and selection charts.

The data pages include a description, special features, truth tables and/or timing diagrams, and significant dynamic electrical characteristics.

The data sections are followed by a Dimensional Outlines section.

Product Selectors Technical Overview **High-Speed CMOS Macrocells Technical Data** Preview Data **Advanced CMOS Logic Application Notes Dimensional Outlines**

RCA Sales Offices, Authorized Distributors

and Manufacturers' Representatives

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When incorporating RCA Solid State Devices in equipment, it is recommended that the designer refer to "Operating Considerations for RCA Solid State Devices," Form No. 1CE-402, available on request from RCA Solid State Division, Box 3200, Somerville, N.J. 08876.

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Product Selectors

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D74HC395E,M D74HC365E,M D74HC365E,M D74HC365E,M D74HC366E,M D74HC367E,M D74HC367E,M D74HC377E,M D74HC377E,M D74HC379E,M D74HC393E,M D74HC393E,M D74HC393E,M D74HC534E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M	CD54HC299F CD54HC356F CD54HC356F CD54HC366F CD54HC366F CD54HC366F CD54HC368F CD54HC373F CD54HC377F CD54HC377F CD54HC377F CD54HC390F CD54HC423F CD54HC533F CD54HC533F CD54HC534F CD54HC534F CD54HC541F CD54HC541F CD54HC541F	CD74HCT297E,M CD74HCT299E,M CD74HCT356E,M CD74HCT356E,M CD74HCT366E,M CD74HCT366E,M CD74HCT367E,M CD74HCT367E,M CD74HCT378E,M CD74HCT377E,M CD74HCT377E,M CD74HCT399E,M CD74HCT399E,M CD74HCT393E,M CD74HCT439E,M CD74HCT533E,M CD74HCT533E,M	CD54HCT297F CD54HCT299F CD54HCT354F CD54HCT356F CD54HCT365F CD54HCT366F CD54HCT366F CD54HCT367F CD54HCT377F CD54HCT377F CD54HCT377F CD54HCT377F CD54HCT390F CD54HCT399F CD54HCT399F CD54HCT399F CD54HCT3938F CD54HCT3938F	363 370 370 380 380 385 385 390 396 401 407 413	Digital Phase-Locked Loop Filter 8-Bit Universal Shift Register, 3-State 8-Input Multiplexer/Register, 3-State 8-Input Multiplexer/Register, 3-State Hex Buffer/Line Driver, 3-State Hex Buffer/Line Driver, 3-State, Inverting Hex Buffer/Line Driver, 3-State Hex Buffer/Line Driver, 3-State, Inverting Octal Transparent Latch, 3-State Octal D-Tippe Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	20 20 16 16 16 16 20 20 20
D74HC395E,M D74HC365E,M D74HC365E,M D74HC365E,M D74HC366E,M D74HC367E,M D74HC367E,M D74HC377E,M D74HC377E,M D74HC379E,M D74HC393E,M D74HC393E,M D74HC393E,M D74HC534E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M D74HC548E,M	CD54HC299F CD54HC356F CD54HC356F CD54HC366F CD54HC366F CD54HC366F CD54HC368F CD54HC373F CD54HC377F CD54HC377F CD54HC377F CD54HC390F CD54HC423F CD54HC533F CD54HC533F CD54HC534F CD54HC534F CD54HC541F CD54HC541F CD54HC541F	CD74HCT299E,M CD74HCT356E,M CD74HCT365E,M CD74HCT365E,M CD74HCT366E,M CD74HCT367E,M CD74HCT367E,M CD74HCT377E,M CD74HCT377E,M CD74HCT377E,M CD74HCT393E,M CD74HCT393E,M CD74HCT393E,M CD74HCT393E,M CD74HCT533E,M CD74HCT534E,M CD74HCT534E,M	CD54HCT299F CD54HCT356F CD54HCT365F CD54HCT365F CD54HCT365F CD54HCT367F CD54HCT367F CD54HCT373F CD54HCT374F CD54HCT377F CD54HCT377F CD54HCT399F CD54HCT399F CD54HCT399F CD54HCT399F	363 370 370 380 380 385 385 390 396 401 407 413	B-Bit Universal Shift Register, 3-State B-Input Multiplexer/Register, 3-State B-Input Multiplexer/Register, 3-State Hex Buffer/Line Driver, 3-State Hex Buffer/Line Driver, 3-State, Inverting Hex Buffer/Line Driver, 3-State, Inverting Octal Transparent Latch, 3-State Octal D Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	20 20 16 16 16 16 20 20 20
2D74HC354E,M 2D74HC365E,M 2D74HC365E,M 2D74HC365E,M 2D74HC365E,M 2D74HC368E,M 2D74HC37E,M 2D74HC37E,M 2D74HC377E,M 2D74HC377E,M 2D74HC393E,M 2D74HC439E,M 2D74HC439E,M 2D74HC534E,M 2D74HC534E,M 2D74HC54DE,M 2D74HC54E,M 2D74HC54E,M 2D74HC56E,M 2D74HC56E,M 2D74HC56E,M 2D74HC56E,M 2D74HC56E,M 2D74HC56E,M 2D74HC56E,M 2D74HC56E,M 2D74HC56E,M	CD54HC354F CD54HC356F CD54HC366F CD54HC366F CD54HC368F CD54HC374F CD54HC373F CD54HC377F CD54HC390F CD54HC390F CD54HC390F CD54HC429F CD54HC533F CD54HC540F CD54HC540F CD54HC541F CD54HC541F CD54HC541F CD54HC563F	CD74HCT354E,M CD74HCT356E,M CD74HCT366E,M CD74HCT366E,M CD74HCT367E,M CD74HCT367E,M CD74HCT373E,M CD74HCT374E,M CD74HCT379E,M CD74HCT399E,M CD74HCT393E,M CD74HCT333E,M CD74HCT533E,M CD74HCT533E,M	CD54HCT354F CD54HCT356F CD54HCT366F CD54HCT366F CD54HCT367F CD54HCT367F CD54HCT373F CD54HCT377F CD54HCT377F CD54HCT397F CD54HCT390F CD54HCT390F CD54HCT393F CD54HCT393F	370 380 380 385 385 390 396 401 407 413	8-Input Multiplexer/Register, 3-State 8-Input Multiplexer/Register, 3-State Hex Buffer/Line Driver, 3-State Hex Buffer/Line Driver, 3-State, Inverting Hex Buffer/Line Driver, 3-State, Inverting Hex Buffer/Line Driver, 3-State, Inverting Octal Transparent Latch, 3-State Octal D Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	20 16 16 16 16 20 20 20
D74HC356E,M D74HC365E,M D74HC365E,M D74HC367E,M D74HC367E,M D74HC373E,M D74HC373E,M D74HC374E,M D74HC393E,M D74HC393E,M D74HC393E,M D74HC533E,M D74HC54B,M D74HC54B,M D74HC54B,M D74HC54B,M D74HC54B,M D74HC56B,M D74HC56B,M	CD54HC356F CD54HC366F CD54HC366F CD54HC367F CD54HC373F CD54HC377F CD54HC377F CD54HC390F CD54HC390F CD54HC390F CD54HC533F CD54HC534F CD54HC534F CD54HC54F CD54HC54F CD54HC54F CD54HC54F CD54HC554F CD54HC564F CD54HC564F CD54HC564F	CD74HCT356E,M CD74HCT366E,M CD74HCT366E,M CD74HCT367E,M CD74HCT367E,M CD74HCT377E,M CD74HCT377E,M CD74HCT377E,M CD74HCT393E,M CD74HCT393E,M CD74HCT433E,M CD74HCT533E,M CD74HCT534E,M	CD54HCT356F CD54HCT365F CD54HCT366F CD54HCT367F CD54HCT367F CD54HCT373F CD54HCT377F CD54HCT377F CD54HCT390F CD54HCT390F CD54HCT390F CD54HCT3938F CD54HCT3938F	380 385 385 385 390 396 401 407 413	8-Input Multiplexer/Register, 3-State Hex Buffer/Line Driver, 3-State Hex Buffer/Line Driver, 3-State, Inverting Hex Buffer/Line Driver, 3-State, Inverting Hex Buffer/Line Driver, 3-State, Inverting Octal Transparent Latch, 3-State Octal D Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	16 16 16 16 20 20 20
D74HC365E,M D74HC366E,M D74HC367E,M D74HC367E,M D74HC373E,M D74HC374E,M D74HC377E,M D74HC399E,M D74HC393E,M D74HC439E,M D74HC534E,M D74HC540E,M D74HC540E,M D74HC54E,M D74HC54E,M D74HC54E,M D74HC564E,M D74HC564E,M D74HC564E,M D74HC563E,M	CD54HC365F CD54HC366F CD54HC367F CD54HC376F CD54HC377F CD54HC377F CD54HC377F CD54HC390F CD54HC390F CD54HC393F CD54HC533F CD54HC534F CD54HC540F CD54HC540F CD54HC541F CD54HC541F	CD74HCT365E,M CD74HCT366E,M CD74HCT367E,M CD74HCT368E,M CD74HCT377E,M CD74HCT377E,M CD74HCT377E,M CD74HCT399E,M CD74HCT399E,M CD74HCT439E,M CD74HCT439E,M CD74HCT534E,M CD74HCT534E,M	CD54HCT365F CD54HCT366F CD54HCT367F CD54HCT367F CD54HCT373F CD54HCT377F CD54HCT377F CD54HCT390F CD54HCT399F CD54HCT393F CD54HCT423F	380 385 385 385 390 396 401 407 413	Hex Buffer/Line Driver, 3-State Hex Buffer/Line Driver, 3-State, Inverting Hex Buffer/Line Driver, 3-State Hex Buffer/Line Driver, 3-State, Inverting Octal Transparent Latch, 3-State Octal D Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	16 16 16 16 20 20 20
D74HC366E,M D74HC367E,M D74HC373E,M D74HC373E,M D74HC377E,M D74HC377E,M D74HC393E,M D74HC393E,M D74HC433E,M D74HC533E,M D74HC534E,M D74HC540E,M D74HC540E,M D74HC540E,M D74HC541E,M	CD54HC366F CD54HC368F CD54HC373F CD54HC377F CD54HC377F CD54HC377F CD54HC390F CD54HC393F CD54HC533F CD54HC533F CD54HC533F CD54HC541F CD54HC541F CD54HC541F	CD74HCT366E,M CD74HCT367E,M CD74HCT373E,M CD74HCT373E,M CD74HCT377E,M CD74HCT397E,M CD74HCT399E,M CD74HCT393E,M CD74HCT438E,M CD74HCT533E,M CD74HCT534E,M	CD54HCT366F CD54HCT367F CD54HCT368F CD54HCT373F CD54HCT374F CD54HCT377F CD54HCT390F CD54HCT393F CD54HCT423F	380 385 385 390 396 401 407 413	Hex Buffer/Line Driver, 3-State, Inverting Hex Buffer/Line Driver, 3-State, Hex Buffer/Line Driver, 3-State, Dottal Transparent Latch, 3-State Octal Drip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	16 16 10 20 20 20
D74HC367E,M D74HC373E,M D74HC373E,M D74HC377E,M D74HC399E,M D74HC399E,M D74HC4033E,M D74HC533E,M D74HC533E,M D74HC54E,M D74HC54E,M D74HC54E,M D74HC54E,M D74HC54E,M	D54HC36FF CD54HC36FF CD54HC373F CD54HC377F CD54HC390F CD54HC390F CD54HC390F CD54HC533F CD54HC533F CD54HC540F CD54HC540F CD54HC541F CD54HC563F CD54HC563F	CD74HCT367E,M CD74HCT368E,M CD74HCT373E,M CD74HCT377E,M CD74HCT397E,M CD74HCT393E,M CD74HCT393E,M CD74HCT423E,M CD74HCT533E,M CD74HCT533E,M	CD54HCT367F CD54HCT378F CD54HCT373F CD54HCT377F CD54HCT390F CD54HCT393F CD54HCT393F	385 385 390 396 401 407 413	Hex Buffer/Line Driver, 3-State Hex Buffer/Line Driver, 3-State, Inverting Octal Transparent Latch, 3-State Octal D Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	16 16 20 20 20
2D74HC368E,M 2D74HC373E,M 2D74HC377E,M 2D74HC397E,M 2D74HC399E,M 2D74HC393E,M 2D74HC533E,M 2D74HC534E,M 2D74HC540E,M 2D74HC540E,M 2D74HC540E,M 2D74HC564E,M 2D74HC564E,M 2D74HC564E,M 2D74HC563E,M	CD54HC373F CD54HC377F CD54HC377F CD54HC377F CD54HC390F CD54HC393F CD54HC533F CD54HC533F CD54HC534F CD54HC541F CD54HC541F CD54HC541F	CD74HCT368E,M CD74HCT373E,M CD74HCT377E,M CD74HCT377E,M CD74HCT390E,M CD74HCT393E,M CD74HCT438E,M CD74HCT533E,M CD74HCT533E,M	CD54HCT368F CD54HCT373F CD54HCT374F CD54HCT377F CD54HCT390F CD54HCT393F CD54HCT423F	385 390 396 401 407 413	Hex Buffer/Line Driver, 3-State, Inverting Octal Transparent Latch, 3-State Octal D Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	11 21 21 11
2D74HC373E,M 2D74HC377E,M 2D74HC377E,M 2D74HC39DE,M 2D74HC393E,M 2D74HC4393E,M 2D74HC533E,M 2D74HC534E,M 2D74HC54DE,M 2D74HC54DE,M 2D74HC54DE,M 2D74HC564E,M 2D74HC564E,M 2D74HC564E,M	CD54HC373F CD54HC374F CD54HC377F CD54HC390F CD54HC393F CD54HC533F CD54HC533F CD54HC534F CD54HC541F CD54HC541F CD54HC561F	CD74HCT373E,M CD74HCT374E,M CD74HCT377E,M CD74HCT390E,M CD74HCT393E,M CD74HCT423E,M CD74HCT533E,M CD74HCT534E,M	CD54HCT373F CD54HCT374F CD54HCT377F CD54HCT390F CD54HCT393F CD54HCT423F	390 396 401 407 413	Octal Transparent Latch, 3-State Octal D Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	2i 2i 2i
D74HC374E,M D74HC377E,M D74HC399E,M D74HC393E,M D74HC533E,M D74HC533E,M D74HC534E,M D74HC544E,M D74HC541E,M D74HC564E,M D74HC564E,M D74HC564E,M	CD54HC374F CD54HC377F CD54HC390F CD54HC390F CD54HC393F CD54HC543F CD54HC540F CD54HC540F CD54HC540F CD54HC540F CD54HC540F	CD74HCT374E,M CD74HCT377E,M CD74HCT390E,M CD74HCT393E,M CD74HCT423E,M CD74HCT533E,M CD74HCT534E,M	CD54HCT374F CD54HCT377F CD54HCT390F CD54HCT393F CD54HCT423F	396 401 407 413	Octal D Flip-Flop, 3-State Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	2i 2i 1i
D74HC377E,M D74HC390E,M D74HC4393E,M D74HC533E,M D74HC533E,M D74HC540E,M D74HC540E,M D74HC540E,M D74HC564E,M D74HC564E,M D74HC564E,M	CD54HC377F CD54HC390F CD54HC393F CD54HC533F CD54HC533F CD54HC534F CD54HC540F CD54HC540F	CD74HCT377E,M CD74HCT390E,M CD74HCT393E,M CD74HCT423E,M CD74HCT533E,M CD74HCT534E,M	CD54HCT377F CD54HCT390F CD54HCT393F CD54HCT423F	401 407 413	Octal D-Type Flip-Flop with Data Enable Dual Decade Ripple Counter	1
D74HC390E,M D74HC423E,M D74HC533E,M D74HC533E,M D74HC534E,M D74HC540E,M D74HC540E,M D74HC564E,M D74HC564E,M	CD54HC390F CD54HC393F CD54HC423F CD54HC533F CD54HC534F CD54HC540F CD54HC541F CD54HC541F	CD74HCT390E,M CD74HCT393E,M CD74HCT423E,M CD74HCT533E,M CD74HCT534E,M	CD54HCT390F CD54HCT393F CD54HCT423F	407 413	Dual Decade Ripple Counter	1
2D74HC393E,M 2D74HC423E,M 2D74HC533E,M 2D74HC534E,M 2D74HC540E,M 2D74HC541E,M 2D74HC563E,M 2D74HC564E,M 2D74HC564E,M 2D74HC563E,M	CD54HC393F CD54HC423F CD54HC533F CD54HC534F CD54HC540F CD54HC541F CD54HC563F	CD74HCT393E,M CD74HCT423E,M CD74HCT533E,M CD74HCT534E,M	CD54HCT393F CD54HCT423F	413		
D74HC423E,M D74HC533E,M D74HC534E,M D74HC540E,M D74HC543E,M D74HC563E,M D74HC563E,M D74HC563E,M	CD54HC423F CD54HC533F CD54HC534F CD54HC540F CD54HC541F CD54HC563F	CD74HCT423E,M CD74HCT533E,M CD74HCT534E,M	CD54HCT423F			
CD74HC533E,M CD74HC534E,M CD74HC540E,M CD74HC541E,M CD74HC563E,M CD74HC564E,M CD74HC564E,M CD74HC573E,M	CD54HC533F CD54HC534F CD54HC540F CD54HC541F CD54HC563F	CD74HCT533E,M CD74HCT534E,M			Dual 4-Bit Binary Ripple Counter	1
CD74HC533E,M CD74HC534E,M CD74HC540E,M CD74HC541E,M CD74HC563E,M CD74HC564E,M CD74HC564E,M CD74HC573E,M	CD54HC533F CD54HC534F CD54HC540F CD54HC541F CD54HC563F	CD74HCT533E,M CD74HCT534E,M			· ·	
CD74HC534E,M CD74HC540E,M CD74HC541E,M CD74HC563E,M CD74HC564E,M CD74HC564E,M	CD54HC534F CD54HC540F CD54HC541F CD54HC563F	CD74HCT534E,M	CD54HC1533F	149	Dual Retriggerable Monostable Multivibrator with Reset	10
D74HC540E,M D74HC541E,M D74HC563E,M D74HC564E,M D74HC573E,M	CD54HC540F CD54HC541F CD54HC563F			418	Octal Transparent Latch, 3-State, Inverting	2
D74HC541E,M D74HC563E,M D74HC564E,M D74HC573E,M	CD54HC541F CD54HC563F	LCD74HCT540F M I	CD54HCT534F	424	Octal D Flip-Flop, 3-State, Inverting	2
D74HC563E,M D74HC564E,M D74HC573E,M	CD54HC563F		CD54HCT540F	429	Octal Buffer Line Driver, 3-State, Inverting	20
D74HC564E,M D74HC573E,M		CD74HCT541E,M	CD54HCT541F	429	Octal Buffer Line Driver, 3-State	2
D74HC564E,M D74HC573E,M		СD74НСТ563Е,М	CD54HCT563F	418	Octal Transparent Latch, 3-State, Inverting	2
D74HC573E,M	CD54HC564F	CD74HCT564E,M	CD54HCT564F	424	Octal D Flip-Flop, 3-State, Inverting	2
	CD54HC573F	CD74HCT573E,M	CD54HCT573F	390	Octal Transparent Latch, 3-State	2
	CD54HC573F CD54HC574F	CD74HCT573E,M	CD54HCT573F	396	Octal D Flip-Flop, 3-State	2
D74HC583E,M	CD54HC574F CD54HC583F	CD74HCT583E,M	CD54HCT583F	434	4-Bit BCD Full Adder w/Fast Carry	1
					-	- 1
D74HC597E,M	CD54HC597F	CD74HCT597E,M	CD54HCT597F	636	8-Bit Shift Register with Input Storage	1
D74HC640E,M	CD54HC640F	CD74HCT640E,M	CD54HCT640F	439	Octal Bus Transceiver, 3-State, Inverting	2
D74HC643E,M	CD54HC643F	CD74HCT643E,M	CD54HCT643F	439	Octal Bus Transceiver, 3-State, True/Inverting	2
D74HC646E,M	CD54HC646F	CD74HCT646E,M	CD54HCT646F	444	Octal Bus Transceiver/Register, 3-State	2
D74HC648E,M	CD54HC648F	CD74HCT648E,M	CD54HCT648F	444	Octal Bus Transceiver/Register, 3-State, Inverting	2
D74HC670E,M	CD54HC670F	CD74HCT670E,M	CD54HCT670F	451	4 x 4 Register File, 3-State	1
D74HC688E,M	CD54HC688F	CD74HCT688E,M	CD54HCT688F	458	8-Bit Magnitude Comparator	2
D74HC4002E,M	CD54HC4002F	CD74HCT4002E,M	CD54HCT4002F	462	Dual 4-Input NOR Gate	1
D74HC4015E,M	CD54HC4015F	CD74HCT4015E,M	CD54HCT4015F	466	Dual 4-Stage Static Shift Register	1
D74HC4016E,M	CD54HC4016F	CD74HCT4016E,M	CD54HCT4016F	637	Quad Bilateral Switch	1
D74HC4017E,M	CD54HC4017F	CD74HCT4017E,M	CD54HCT4017F	472	Decade Counter/Divider with 10 Decoded Outputs	1
D74HC4020E,M	CD54HC4020F	CD74HCT4020E.M	CD54HCT4020F	478	14-Stage Binary Ripple Counter	1 1
D74HC4024E,M	CD54HC4024F	CD74HCT4024E,M	CD54HCT4024F	483	7-Stage Binary Ripple Counter	1 1
D74HC4040E,M	CD54HC4040F	CD74HCT4040E,M	CD54HCT4040F	488	12-Bit Binary Counter	1
D74HC4046AE,M	CD54HC4046AF	CD74HCT4046AE,M	CD54HCT4046AF	493	Phase-Locked Loop with VCO	1
		OD/411014040AL,WI	CD3411C14040A1			1
D74HC4049E,M	CD54HC4049F	-	_	510	Hex Inverting HIGH-to-LOW Level Shifter	1 10
D74HC4050E,M	CD54HC4050F		_	510	Hex HIGH-to-LOW Level Shifter	1
D74HC4051E,M	CD54HC4051F	CD74HCT4051E,M	CD54HCT4051F	514	8-Channel Analog Multiplexer/Demultiplexer	1
D74HC4052E,M	CD54HC4052F	CD74HCT4052E,M	CD54HCT4052F	514	Dual 4-Channel Analog Multiplexer/Demultiplexer	1
D74HC4053E,M	CD54HC4053F	CD74HCT4053E,M	CD54HCT4053F	514	Triple 2-Channel Analog Multiplexer/Demultiplexer	1 1
D74UC40505 M	CDEALICAGEGE	ODZALIOTACCOE NA	0054110740505	-nn		١.
D74HC4059E,M	CD54HC4059F	CD74HCT4059E,M	CD54HCT4059F	523	Programmable Divide by "N" Counter	2.
D74HC4060E,M	CD54HC4060F	CD74HCT4060E,M	CD54HCT4060F	530	14-Stage Binary Counter w/Oscillator	1
D74HC4066E,M	CD54HC4066F	CD74HCT4066E,M	CD54HCT4066F	536	Quad Bilateral Switch	1
D74HC4067E,M	CD54HC4067F	CD74HCT4067E,M	CD54HCT4067F	542	16-Channel Analog Multiplexer/Demultiplexer	2
D74HC4075E,M	CD54HC4075F	CD74HCT4075E,M	CD54HCT4075F	548	Triple 3-Input OR Gate	1
D74HC4094E,M	CD54HC4094F	CD74HCT4094E,M	CD54HCT4094F	552	8-Stage Shift-and-Store Bus Register	1
D74HC4316E,M	CD54HC4316F	CD74HCT4316E,M		638	Quad Analog Switch	1 1
D74HC4351E,M	CD54HC4351F	CD74HCT4351E,M		638	Analog MUX w/Latch	2
D74HC4352E,M	CD54HC4352F	CD74HCT4352E,M	CD54HCT4352F	639	Analog MUX w/Latch	2
D74HC4353E,M	CD54HC4353F	CD74HCT4353E,M	CD54HCT4353F	639	Analog MUX w/Latch	2
					-	
D74HC4510E,M	CD54HC4510F	CD74HCT4510E,M	CD54HCT4510F	559	Up/Down Counter, BCD	1
D74HC4511E,M	CD54HC4511F	CD74HCT4511E,M		569	BCD-to-7-Segment Latch/Decoder/Driver	1
D74HC4514E,M	CD54HC4514F	CD74HCT4514E,M	CD54HCT4514F	574	4-to-16-Line Decoder/Demultiplexer w/Input Latch	2
D74HC4515E,M	CD54HC4515F	CD74HCT4515E,M	CD54HCT4515F	574	4-to-16-Line Decoder with Input Latches	2
D74HC4516E,M	CD54HC4516F	CD74HCT4516E,M	CD54HCT4516F	559	Up/Down Counter, Binary	1
D74HC4518E,M	CD54HC4518F	CD74HCT4518E.M	CD54HCT4518F	580	Dual Synchronous BCD Counter	1 1
D74HC4520E,M	CD54HC4520F	CD74HCT4518E,M		580	Dual 4-Bit Synchronous Binary Counter	1
D74HC4520E,M	CD54HC4520F CD54HC4538F	CD74HCT4520E,M CD74HCT4538E,M	CD54HCT4520F	586	Dual Precision Monostable Multivibrator	
D74HC4538E,M	CD54HC4538F CD54HC4543F			594		1
D74HC4543E,M D74HC7030E	CD34FIC4543F	CD74HCT4543E,M	CD54HCT4543F		BCD-to-7-Segment Latch/Decoder/Driver for LCDs	1
D14001030E	_	CD74HCT7030E	_	640	9-Bit x 64 Word FIFO Register, 3-State	2
D74HC7038E,M	CD54HC7038F	CD74HCT7038E,M	CD54HCT7038F	641	9-Bit Bus Transceiver w/Latch	2
D74HC7046E,M	CD54HC7046F	CD74HCT7046E,M	CD54HCT7046F	641	Phase-Locked Loop with In-Lock Detection	1
D74HC7266E,M	CD54HC7266F	_		600	Quad Exclusive NOR Gate	1
D74HC40102E,M	CD54HC40102F	CD74HCT40102E,M	CD54HCT40102F	604	8-Bit Synchronous BCD Down Counter	li
D74HC40103E,M	CD54HC40103F	CD74HCT40102E,M	CD54HCT40102F	604	8-Bit Binary Down Counter	1
		1			-	
D74HC40104E,M	CD54HC40104F	CD74HCT40104E,M	CD54HCT40104F	613	4-Bit Bidrectional Universal Shift Register, 3-State	1
D74HC40105E,M D74HCU04E,M	CD54HC40105F CD54HCU04F	CD74HCT40105E,M	CD54HCT40105F	619 628	4 Bits x 16 Words FIFO Register Hex Inverter (Unbuffered)	1

Note: Add package suffix code to part number on all orders.

E = Dual-In-Line Plastic Package — Temp. Range = -40° to + 85° C.

F = Dual-In-Line Frit-Seal Ceramic Package (CERDIP) — Temp. Range = -55° to + 125° C.

H = Chip — Temp. Range = -55° C to 125° C.

M = Dual-In-Line Surface Mounted Package — Temp. Range = -40° to + 85° C.

Product Selection Guide

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Туре	Function/Description	Classification	Page
CD54/74	NAND/NOR Gates		
HC/HCT00	Quad 2-Input NAND Gate	SSI	48
HC/HCT02	Quad 2-Input NOR Gate	SSI	52
HC/HCT03	Quad 2-Input NAND Gate with Open Drain	SSI	56
HC/HCT10	Triple 3-Input NAND Gate	SSI	68
HC/HCT20	Dual 4-Input NAND Gate	SSI	80
HC/HCT27	Triple 3-Input NOR Gate	SSI	88
HC/HCT30	8-Input NAND Gate	SSI	92
HC/HCT4002	Dual 4-Input NOR Gate	SSI	462
	AND/OR/EXCLUSIVE-OR Gates		
HC/HCT08	Quad 2-Input AND Gate	SSI	64
HC/HCT11	Triple 3-Input AND Gate	SSI	72
HC/HCT21	Dual 4-Input AND Gate	SSI	84
HC/HCT32	Quad 2-Input OR Gate	SSI	96
HC/HCT86 HC/HCT4075	Quad 2-Input EXCLUSIVE-OR Gate Triple 3-Input OR Gate	SSI SSI	125 548
HC7266	Quad Exclusive NOR Gate	SSI	600
	Inverters/Buffers/Bus Drivers		000
HC/HCT04	Hex Inverter/Buffer	SSI	60
HCU04 HC/HCT125*	Hex Inverter (Unbuffered) Quad 3-State Buffer	SSI MSI	628
HC/HCT126*	Quad 3-State Buffer	MSI	155 160
HC/HCT240*	Octal Buffer/Line Driver: 3-State: Inverting	MSI	298
HC/HCT241*	Octal Buffer/Line Driver; 3-State	MSI	298
HC/HCT244*	Octal Buffer/Line Driver; 3-State	MSI	298
HC/HCT365*	Hex Buffer/Line Driver; 3-State	MSI	380
HC/HCT366*	Hex Buffer/Line Driver; 3-State Inverting	MSI	380
HC/HCT367*	Hex Buffer/Line Driver; 3-State	MSI	385
HC/HCT368*	Hex Buffer/Line Driver; 3-State; Inverting	MSI	385
HC/HCT540* HC/HCT541*	Octal Buffer/Line Driver; 3-State; Inverting Octal Buffer/Line Driver; 3-State	MSI MSI	429 429
HC4049	Hex Inverting HIGH-to-LOW Level Shifter	SSI	510
HC4050	Hex HIGH-to-LOW Level Shifter	SSI	510
	Flip-Flops		
HC/HCT73	Dual JK Flip-Flop with Reset; Negative-Edge Trigger	FF	104
HC/HCT74	Dual D-Type Flip-Flop with Set and Reset; Positive-Edge Trigger	FF	109
HC/HCT107	Dual JK Flip-Flop with Reset; Negative-Edge Trigger	FF	134
HC/HCT109	Dual JK Flip-Flop with Set and Reset; Positive-Edge Trigger	FF	139
HC/HCT112	Dual JK Flip-Flop with Set and Reset, Negative-Edge Trigger	FF	144
HC/HCT173* HC/HCT174	Quad D-Type Flip-Flop with Set and Reset; Positive-Edge Trigger; 3-State	MSI MSI	232 238
HC/HCT175	Hex D-Type Flip-Flop with Reset; Positive-Edge Trigger Quad D-Type Flip-Flop with Reset; Positive-Edge Trigger	MSI	238 243
HC/HCT273	Octal D-Type Flip-Flop with Reset; Positive-Edge Trigger	MSI	342
HC/HCT374*	Octal D-Type Flip-Flop; Positive-Edge Trigger; 3-State	MSI	396
HC/HCT377	Octal D-Type Flip-Flop with Data Enable; Positive-Edge Trigger	MSI	401
HC/HCT534*	Octal D-Type Flip-Flop; Positive-Edge Trigger; 3-State; Inverting	MSI	424
HC/HCT564*	Octal D-Type Flip-Flop; Positive-Edge Trigger; 3-State; Inverting	MSI	424
HC/HCT574*	Octal D-Type Flip-Flop; Positive-Edge; 3-State	MSI	396
	Shift/FIFO Buffer/Multiport Registers		
HC/HCT164	8-Bit Serial-In/Parallel-Out Shift Register	MSI	215
HC/HCT165	8-Bit Parallel-In/Serial-Out Shift Register	MSI	220
HC/HCT166	8-Bit Parallel/Serial-In Serial-Out Shift Register	MSI	226
HC/HCT194	4-Bit Bidirectional Universal Shift Register	MSI	279
HC/HCT195 HC/HCT299*	4-Bit Parallel Access Shift Register 8-Bit Universal Shift Register; 3-State	MSI MSI	285 363
HC/HCT597	8-Bit Shift Register with Input Storage	MSI	636
HC/HCT670*	4 x 4 Register File; 3-State	MSI	451
HC/HCT4015	Dual 4-Stage Static Shift Register	MSI	466
HC/HCT4094	8-Stage Shift-and-Store Bus Register; 3-State	MSI	552
HC/HCT7030*	9-Bit x 64 Word FIFO Register; 3-State	MSI	640
HC/HCT40104*	4-Bit Bidirectional Universal Shift Register; 3-State	MSI	613
HC/HCT40105	4 Bits x 16 Words FIFO Register	MSI	619
	Let a continue to the second		

^{*}Types with a bus driver output stage.

Product Selection Guide (Cont'd)

Туре	Function/Description	Classification	Page
CD54/74	Arithmetic Circuits		
HC/HCT85	4-Bit Magnitude Comparator	MSI	119
HC/HCT181	4-Bit Arithmetic Logic Unit	MSI	248
HC/HCT182	Look-Ahead Carry Generator	MSI	254
HC/HCT280	9-Bit Odd/Even Parity Generator/Checker	MSI	347
HC/HCT283	4-Bit Full Adder with Fast Carry	MSI	351
HC/HCT583	4-Bit BCD Full Adder with Fast Carry	MSI	434
HC/HCT688	8-Bit Magnitude Comparator	MSI	458
	Counters		
HC/HCT93	4-Bit Binary Ripple Counter	MSI	129
HC/HCT160	Presettable Synchronous BCD Decade Counter; Asynchronous Reset	MSI	205
HC/HCT161	Presettable Synchronous 4-Bit Binary Counter, Asynchronous Reset	MSI	205
HC/HCT162	Presettable Synchronous BCD Decade Counter; Synchronous Reset	MSI	205
HC/HCT163	Presettable Synchronous 4-Bit Binary Counter; Synchronous Reset	MSI	205
HC/HCT190	Presettable Synchronous BCD Decade Up/Down Counter	MSI	260
HC/HCT191	Presettable Synchronous 4-Bit Binary Up/Down Counter	MSI	260
HC/HCT192	Presettable Synchronous BCD Decade Up/Down Counter	MSI	269
HC/HCT193	Presettable Synchronous 4-Bit Binary Up/Down Counter	MSI	269
HC/HCT390	Dual Decade Ripple Counter	MSI	407
HC/HCT393	Dual 4-Bit Binary Ripple Counter	MSI	413
HC/HCT4017	Decade Counter/Divider with 10 Decoded Outputs	MSI	472
HC/HCT4020	14-Stage Binary Ripple Counter	MSI	478
HC/HCT4024	7-Stage Binary Ripple Counter	MSI	483
HC/HCT4040	12-Stage Binary Ripple Counter	MSI	488
HC/HCT4059	Programmable Divide by "N" Counter	MSI	523
HC/HCT4060	14-Stage Binary Ripple Counter with Oscillator	MSI	530
HC/HCT4510 HC/HCT4516	Up/Down Counter, BCD	MSI MSI	559 559
	Up/Down Counter, Binary Dual Synchronous BCD Counter	MSI	580
HC/HCT4518 HC/HCT4520		MSI	580
HC/HCT40102	Dual 4-Bit Synchronous Binary Counter 8-Bit Synchronous BCD Down Counter	MSI	604
HC/HCT40102	8-Bit Binary Down Counter	MSI	604
110/110140103	•	WIOI	004
	Analog and Digital Multiplexers/Demultiplexers		
HC/HCT151	8-Input Multiplexer	MSI	184
HC/HCT153	Dual 4-Input Multiplexer	MSI	189
HC/HCT157	Quad 2-Input Multiplexer	MSI MSI	200 200
HC/HCT158 HC/HCT251	Quad 2-Input Multiplexer; Inverting 8-Input Multiplexer; 3-State	MSI	315
HC/HCT253*	Dual 4-Input Multiplexer; 3-State	MSI	321
HC/HCT257*	Quad 2-Input Multiplexer; 3-State; Non-Inverting Outputs	MSI	326
HC/HCT258	Quad 2-Input Multiplexer; 3-State; Inverting Outputs	MSI	330
HC/HCT354*	8-Input Multiplexer/Register; 3-State	MSI	370
HC/HCT356*	8-Input Multiplexer/Register; 3-State	MSI	370
HC/HCT4051	8-Channel Analog Multiplexer/Demultiplexer	MSI	514
HC/HCT4052	Dual 4-Channel Analog Multiplexer/Demultiplexer	MSI	514
HC/HCT4053	Triple 2-Channel Analog Multiplexer/Demultiplexer	MSI	514
HC/HCT4067	16-Channel Analog Multiplexer/Demultiplexer	MSI	542
HC/HCT4351	Analog Multiplexer with Latch	MSI	638
HC/HCT4352	Analog Multiplexer with Latch	MSI	639
HC/HCT4353	Analog Multiplexer with Latch	MSI	639
	Decoders/Encoders		
HC/HCT42	BCD to Decimal Decoder (1-of-10)	MSI	100
HC/HCT137	3-to-8 Line Decoder with Latch; Inverting	MSI	634
HC/HCT138	3-to-8 Line Decoder/Demultiplexer; Inverting	MSI	169
HC/HCT139	Dual 2-to-4 Line Decoder/Demultiplexer	MSI	174
HC/HCT147	10-to-4-Line Priority Encoder	MSI	179
HC/HCT154	4-to-16-Line Decoder/Demultiplexer	MSI	194
HC/HCT237	3-to-8-Line Decoder/Demultiplexer with Address Latches	MSI	635
HC/HCT238	3-to-8-Line Decoder/Demultiplexer	MSI	169
HC/HCT4511	BCD-to-7-Segment Latch/Decoder/Driver	MSI	569
HC/HCT4514	4-to-16-Line Decoder/Demultiplexer with Input Latches	MSI	574
HC/HCT4515	4-to-16-Line Decoder/Demultiplexer with Input Latches	MSI MSI	574 594
HC/HCT4543	BCD-to-7-Segment Latch/Decoder/Driver for LCDs	IVIOI	594
*Types with a bus	driver output stage.		

^{*}Types with a bus driver output stage.

Product Selection Guide (Cont'd)

Туре	Function/Description	Classification	Page
CD54/74	Analog Switches		
HC/HCT4016 HC/HCT4066 HC/HCT4316	Quad Bilateral Switch Quad Bilateral Switch Quad Analog Switch	SSI SSI MSI	637 536 638
	Bus Transceivers		
HC/HCT242* HC/HCT243* HC/HCT245* HC/HCT640* HC/HCT6443* HC/HCT646* HC/HCT648* HC/HCT7038*	Quad Bus Transceiver; 3-State; Inverting Quad Bus Transceiver; 3-State Octal Bus Transceiver; 3-State Octal Bus Transceiver; 3-State Inverting Octal Bus Transceiver; 3-State True/Inverting Octal Bus Transceiver; 3-State Octal Bus Transceiver; 3-State; Inverting 9-Bit Bus Transceiver with Latch	MSI MSI MSI MSI MSI MSI MSI MSI	304 304 310 439 439 444 444 641
	Schmitt Triggers		
HC/HCT14 HC/HCT132	Hex Inverting Schmitt Trigger Quad 2-Input NAND Schmitt Trigger	SSI SSI	76 165
	Latches		
HC/HCT75 HC/HCT259 HC/HCT373* HC/HCT533* HC/HCT563* HC/HCT573*	Dual 2-Input Bistable Transparent Latch 8-Bit Addressable Latch Octal Transparent Latch; 3-State Octal Transparent Latch; 3-State; Inverting Octal Transparent Latch; 3-State; Inverting Octal Transparent Latch; 3-State	FF MSI MSI MSI MSI MSI	114 335 390 418 418 390
	One-Shot Multivibrators		
HC/HCT123 HC/HCT221 HC/HCT423 HC/HCT4538	Dual Retriggerable Monostable Multivibrator with Reset Dual Monostable Multivibrator with Reset Dual Retriggerable Monostable Multivibrator with Reset Dual Retriggerable Precision Monostable Multivibrator	MSI MSI MSI MSI	149 291 149 586
	Phase-Locked Loops (PLL)		
HC/HCT297 HC/HCT4046A HC/HCT7046	Digital Phase-Locked Loop Filter Phase-Locked Loop with VCO Phase-Locked Loop with In-Lock Detection	MSI MSI MSI	356 493 641

^{*}Types with a bus driver output stage.

Product Classification Chart

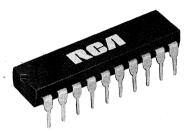
				GAT	res								MULTI	/IBRATORS
	Single-level	,					Multi-le	evel					Flip-Flo	ps/Latches
NOR/NAND OR/AND					us vers	Multi- function AO1		Decoders/ Encoders		Schmitt Trigger		Flip-Flops	Latches	
(CD54/74HC/HC1						CD54/74/H	IC/HCT					CD54/	74HC/HCT
HC/HCT02	HC/HCT00	НС/НСТ08	HC/	HCT240●	HC/H	CT125	нс/нст	86	НС/НСТ4	2	HC/HCT14		НС/НСТ73	HC/HCT75
нс/нстоз∳	HC/HCT10	HC/HCT11	HC/	HCT241●	нс/н	CT126	HC7266		нс/нст1	37	HC/HCT132	2	HC/HCT74	HC/HCT259
HC/HCT27	HC/HCT20	HC/HCT21	HC/	HCT244●	нс/н	CT241			нс/нст1	38		- 1	HC/HCT107	HC/HCT373●
HC/HCT4002	HC/HCT30	НС/НСТ32	HC/	HCT365●	нс/н	CT244			нс/нст1	39		-	HC/HCT109	HC/HCT533●
		HC/HCT4075	HC/	HCT366●	HC/H	CT365			HC/HCT1	17			HC/HCT112	HC/HCT563●
			l	HCT367●		CT366			HC/HCT1	- 1			HC/HCT173	HC/HCT573•
				HCT368●		CT367			HC/HCT2	- 1			HC/HCT174	
			1	HCT540●		CT368			HC/HCT2				HC/HCT175	
			HC/	HCT541●		CT540			HC/HCT4			1	HC/HCT273	Monostable
			<u> </u>	Level	нс/н	CT541			HC/HCT45			ı	HC/HCT374 HC/HCT377	HC/HCT123
				hifters	Inve	rters			HC/HC14	,15			HC/HCT534	HC/HCT423
				IC 4049	нс/н	CT04						- 1	HC/HCT564•	HC/HCT4538
			1	C 4050	HCU					1			HC/HCT574	
	REGISTER	3 3			COUN	TERS				Γ',	PHASE	Г		[
Chim	FIFO			Binar	у	Cumak		l	IGITAL IPLEXERS	1	OCKED		BILATERAL SWITCHES	CIRCUITS
Shift	Buffer	Multipor		Rippl	е	Synch	ronous			ı	OOPS			0000
	CD54/74HC/F	ст		CD54/74HC/HCT								CD54/74	нс/нст	
HC/HCT164	HC/HCT4010	5 HC/HCT67	0	нс/нст	3	нс/нс	T160	HC/F	ICT151	HC/I	HCT279	н	C/HCT4016 ▲	Bus
HC/HCT165	HC/HCT7030)	Ì	нс/нста	ł					1CT4046A		C/HCT4066 ▲	Transceivers	
HC/HCT166				нс/нста		HC/HC				HC/I	ļ		C/HCT4316 ▲	HC/HCT242●
HC/HCT194				нс/нст4		нс/нс	*		1CT158				Analog //ultiplexers/	HC/HCT243•
HC/HCT195				HC/HCT4		нс/нс			1CT251		(emultiplexers	HC/HCT245● HC/HCT640●
HC/HCT299• HC/HCT597				HC/HCT4		HC/HC			HCT253 HCT257◆				C/HCT4051	HC/HCT643•
HC/HCT4015				HC/HCT4		нс/нс			1CT257				C/HCT4051	HC/HCT646•
HC/HCT4094	1					HC/HC			1CT354•				C/HCT4053	HC/HCT648•
HC/HCT40104•						нс/нс	T4510	HC/F	HCT356●			н	C/HCT4067	HC/HCT7038•
	İ					нс/нс	T4516					н	C/HCT4351	
						нс/нс	T4518					н	C/HCT4352	
						нс/нс	T4520					н	C/HCT4353	
	1					нс/нс	T40102							
	AR	ITHMETIC CIRCU	ITS							DI	SPLAY DRIVI	ERS		
Adders/		ALU/Rate			Parity	i					For			or
Comparato		Multipliers			nerator/ hecker						LCD Drive			.ED
	l		1		necker)rive
HC/HCT05	T	CD54/74HC/HCT	Т	нель-							D54/74HC/H			/HCT4511
HC/HCT85		HCT181		HC/HCT2	:60						HC/HCT454: See Decoders		"	711014311
HC/HCT182											See Decoders	5 /	l	

Open Drain

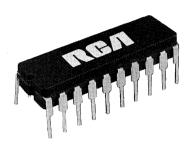
[▲] Quad type

With Bus Driver output stage

Typical Dual-In-Line Plastic Package



Typical Dual-In-Line Frit-Seal Ceramic (CERDIP) Package



Typical SO (Small Outline) Plastic Package





HC/HCT Family Description

The RCA HC/HCT series of high-speed CMOS integrated circuits (QMOS) includes a functionally complete set of LSTTL equivalent types and selected equivalent CMOS CD4000 series types. The CD4000 series types selected are unique to the CMOS process. These types are readily produced by the highly versatile CMOS technology, but cannot be implemented by the more restrictive bipolar technology. Each CMOS circuit function is offered in two basic logic series, as follows:

- CD54/74HCTXXXX-series types feature LSTTL input-voltage-level compatibility and provide highspeed CMOS direct drop-in replacements of LSTTL devices.
- CD54/74HCXXXX-series types feature CMOS input-voltage-level compatibility and are intended for use in new second-generation all-CMOS systems.

In addition, RCA offers a third category, **CD54/74HCUXX**, which includes unbuffered types intended for linear or high-speed oscillator applications.

The HC/HCT family consists of a comprehensive set of buffers, transceivers, and registers that are popular in computer systems. A wide variety of popular logic, MUX's, encoders/decoders, counters, arithmetic units, mulitvibrators, display drivers, and phase-lock loops complete the family.

Shown below is a breakdown of the HC/HCT family by logic function:

The HC/HCT Family

Device Function	Number of Types
Inverters/Buffers/Bus Drivers	14
Flip-Flops/Latches	20
Bus Transceivers	8
Registers	13
Counters	23
Decoders/Encoders	12
Multiplexers (Analog & Digital)	17
Multivibrators	4
Schmitt Triggers	2
Phase-Lock Loops	3
Bilateral Switches	3
Arithmetic Circuits	7
Gates	15

NOTE: Each function is available in both an HCT and HC version.

HC/HCT Family Features

- Functionally and pin compatible with industry 54 and 74 LSTTL-series and CD4000B-series types.
- CMOS outputs for maximum noise margins.
- Fan-out (over temperature):
 Standard Outputs 10 LSTTL loads
 Bus-Driver Outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT/HCU: -40 to +85°C CD54HC/HCT/HCU: -55 to +125°C
- Balanced propagation and transition times.
- Significant power reduction compared to LSTTL logic.
- Alternate source Philips/Signetics

Series Features

CD54HCXXXX and CD74HCXXXX Series

- · 2 to 6V operation.
- High noise immunity: N_{IL} = 30%, N_{IH} = 30% at V_{CC} = 5V.

CD54HCTXXXX and CD74HCTXXXX Series

- 4.5 to 5.5V operation.
- Direct LSTTL input logic compatibility V_{IL} = 0.8V(max), V_{IH} = 2.0V (min)
- CMOS input compatibility
 I_{IL}, I_{IH} ≤IuA at V_{OL}, V_{OH}

Quantitative Comparison of HC/HCT and LSTTL Logic Types

RCA's HC and HCT logic types have many outstanding advantages when compared with the conventional high-current LSTTL logic types which these types can replace in existing and new equipment designs that require devices operating at frequencies in the 20-30 MHz range. Table I compares significant operating characteristics of the HC/HCT vs. LSTTL logic families.

Table I — Quantitative Comparison of HC/HCT and LSTTL Logic Types

Characteris	tic	-	4 Series IC/HCT	74 Series LSTTL			
Quiescent Power -per Gate -per FF -4 Stage Counter -per Transceiver/Buffer			0.025mW 0.05mW 0.4mW 0.1mW	5.5mW 10mW 95mW 60mW			
2. Operatin	g Power	Freque	nov	Eron	iency		
	0.1MHz	1MHz	10MHz	0.1 to	10MHz		
-per Gate -per FF	0.2mW 0.15mw	2mW 1.5mW	20mW 15mW	1MHz 5.5mW 10mW	20mW 15mW		
-4 Stage Counter -per Trans- ceiver/	0.24mW	2.4mW	24mW	95mW	120mW		
Buffer	0.25mW	2.5mW	25mW	60mW	90mW		
3. Operatir Voltage	3. Operating Supply Voltage		CT) 4.5V to V C) 2V to 6V	4.75V t	o 5.25V		
4. Operatir Tempera Range		-40	°C to +85°C	0°C to	+70°C		
5. Noise Margin @ 5V LS to LS HC to HC HCT to HCT		OW)	 1.4V/1.4V 2.9V/0.7V	0.7V/0.4V 			
6. Input Sv Voltage Variation	vitching n with Ten	ιρ. ∨	s \pm 60mV	Vs ± 2	200 mV		

Table I — Cont'd	74 Series HC/HCT	74 Series LSTTL
7. Output Drive Current		
 a) Source Current at V_{OH} = 2.4V b) Sink Current 	-8mA	-400uA
Std. Logic (V _{OL}) BUS Logic (V _{OL}) V _{OL} =0.5V	4mA (0.33V) 6mA (0.33V) 12mA	4mA (0.4V) 12mA (0.4V) 24mA
8. Typ. Output Transition Time*		
t _{TLH} t _{THL}	6ns 6ns	15ns 6ns
9. Typical Gate Propagat Delay*: t _{PHL} /t _{PLH} V _{CC} = 5V, C _L = 15pF	ion 8ns/8ns	8ns/11ns
10. Typical FF Propagation $V_{CC} = 5V, C_{L} = 15pF$	on Delay:	
tern tehr	14ns 14ns	15ns 22ns
11. Typ. Clock Rate of an FF	50MHz	33MHz
12. Input Current	-luA luA	-0.4. to -0.8mA 40uA
13. 3-State Output Leakage Current	±5uA	±20uA
14. Reliability %/1000 hours at 60% Confidence	.0019 (RCA Report)	.008 (RADC Report)

*Loading coefficient = 0.055ns/pF (both HC/HCT and LSTTL)

HC/HCT IC Structure

The high speeds and low quiescent power dissipation that characterize the RCA HC/HCT family are made possible by utilizing a three-micron, self-aligned silicon gate CMOS process. The three-micron process minimizes the internal parasitic capacitances of the circuit, which results in increased switching speed.

The polysilicon gates of the transistors are deposited over a thin gate oxide before the source and drain diffusions are defined. Ion implantation is then used to form the source and drain areas, with the polysilicon gates acting as a mask for the implantation. The source and drain are automatically aligned to the gate, hence the expression "self-aligned-gate" process. In this manner, gate-to-source and gate-to-drain capacitances are minimized. Junction capacitances, which are proportional to the junction area, are also reduced because of the shallower diffusions. Fig. 1 shows the parasitic capacitances in a CMOS inverter.

In contrast, the source and drain areas in a metal-gate CMOS process are formed before the gate is deposited.

Moreover, the metal gate must overlap the source and drain to allow for alignment tolerances. These conditions result in higher overlap capacitances than those present in QMOS devices. The metal-gate process also employs deeper diffusions than those in the QMOS process and, consequently, has larger junction capacitances.

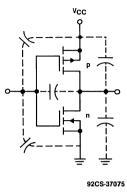


Fig. 1 - Parasitic capacitances in a CMOS inverter

The QMOS structure features a three-micron gate length; the CD4000 series structure has a gate length of seven microns. The equation for the drain current of a MOSFET is:

 $I_{DS} = K' \frac{\text{width}}{\text{length}} [\text{ (gate voltage)} - (\text{threshold voltage)}]^2$

where K' is the "beta" of the MOSFET. Therefore, a shortter gate length results in higher drive capability, which in turn increases the speed at which a transistor can charge or discharge capacitance.

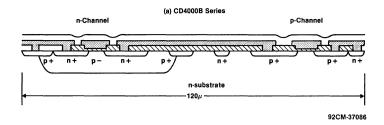
The polysilicon in a silicon-gate process is also an interconnect layer, thus, there are three levels of interconnect (diffusion, polysilicon, and metal) instead of the two layers (diffusion and metal) present in a metal-gate process. This situation aids in making a more compact die. Fig. 2 compares the cross sections of the seven-micron metal-gate CMOS structure and the three-micron QMOS structure.

Input Characteristics

The inputs of QMOS devices are voltage-level sensitive, and do not require current, except for input leakage. The definitive switching characteristics for the HC and HCT versions are illustrated in Figs. 3 and 4, respectively.

System designers require the actual MIN/MAX range of expected input switching voltage over the temperature range of -55°C to +125°C. This vital information is contained in the curves of Figs. 5 and 6 for the HC and HCT families, respectively.

The unbuffered HCU04 hex inverter has one stage of active inverting logic from input to output and, therefore, is a special case for input switching voltage as shown in Fig. 7.



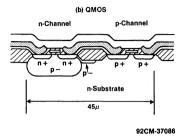


Fig. 2 - Crossectional view of (a) the seven-micron CD4000B Series structure and (b) threemicron QMOS structure

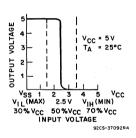


Fig. 3 - Typical switching characteristics of RCA HC series types

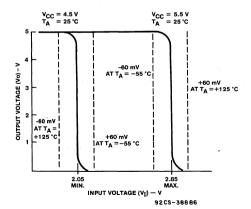


Fig. 5 - Actual Min/Max switching characteristics of RCA HC series types

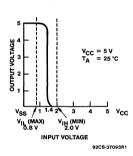


Fig. 4 - Typical switching characteristics of RCA HCT series types

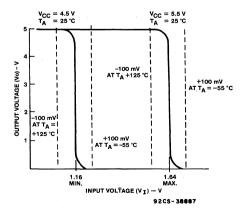


Fig. 6 - Actual Min/Max switching characteristics of RCA HCT series types

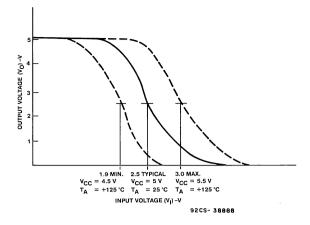


Fig. 7 Actual Min/Max and typical switching characteristics of the HCU04 Unbuffered Hex Inverter

Noise Immunity and Noise Margin

Table II shows the HC, HCT, and HCU input noise immunity and noise margin for use in those applications where like members of the HC, HCT, and HCU families interface with each other at a nominal supply voltage of 5V. Output voltages are also shown.

Table II(a): Noise Immunity and Noise Margin (V_{CC} = 5V).

	HC	HCT	HCU
V _{IL} max.	1.5V	V8.0	1V
V _{IH} min.	3.5V	2V	4V
V _{o∟} max.	0.1V	0.1V	0.5V
V _{он} min.	4.9V	4.9V	4.5V
Noise Margin Low (V _{NML})	1.4V	0.7V	0.5V
Noise Margin High (V _{NMH})	1.4V	2.9V	0.5V

Table II(b) shows noise immunity and noise margin voltages for standard HCT devices interfacing with LSTTL logic types with a fully loaded HCT or LSTTL output at $V_{\rm CC} = 4.5V$, and a temperature range of 0°C to +70°C. This

limited LSTTL temperature range is the only convenient temperature range when using LSTTL characteristics.

Whenever the HCT output drives either an LS or HCT input, there is an improvement in noise margin over the LSTTL family driving itself or driving HCT. This improvement is especially true for noise margin high where the superior output sourcing current of the rail-to-rail QMOS output swing is far superior to the limited totem-pole pull-up output voltage of LSTTL

Input Current

Fig. 8 is a plot of typical HC/HCT device input current vs. temperature for a $V_{\rm CC}$ of 6V. This actual performance of under 1.5nA over the temperature range of -55°C to +125°C contrasts with maximum family and JEDEC standard input leakage current limit of 100nA for T = -55°C to +25°C, and a limit of 1 $\mu{\rm a}$ at $T_{\rm A}=85^{\circ}{\rm C}$ and +125°C. The reason for this difference in performance vs. ratings is high-speed testing limitations associated with test system resolution and the measurement of settling time. A secondary reason is that the limits are end-of-life, thus allowing some leakage current shift due to minor externally introduced foreign material or moisture.

Table II(b) - Noise Immunity and Noise Margin for HCT and LS Device Interfacing

	нст	LSTTL	HCT → LS	LS HCT	LS - LS	HCT → HCT
VIL MAX	0.8V	0.8V	_	_		_
VIH MIN	2V	2V		_	_	_
V _{OL} MAX	0.33V	0.4V	_	_	_	_
Von MIN	4.4V	2.7V	_	_	_	_
V _{NML}	_	_	0.47V	0.4V	0.4V	0.7V
V _{NMH}	_	_	2.4V	0.7V	0.7V	2.4V

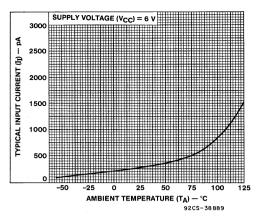


Fig. 8 - Typical HC/HCT input current Vs. temperature

Input Termination

The very low HC/HCT input current and hence, high input resistance is primarily due to low-level leakage currents of the input ESD protection diodes shown in Fig. 9. This excellent input buffering characteristic of CMOS logic IC's is fundamental to the wide range of very low power applications from pure logic to wide range RC oscillators, high Q crystal oscillators, etc. However, in no situation should this high input resistance be left floating or unterminated. Inputs may be tied directly to $V_{\rm CC}$ or GND via resistors of up to 1Mohm; the upper limit is only related to ac noise immunity, i.e., pick up.

Comparing HC/HCT unused input terminations to LSTTL logic, puts the flexibility of QMOS into a very positive light. It is a stated LSTTL design rule that unused inputs be terminated to $V_{\rm CC}$ via a 1.2kohm resistor and not tied directly to GND or $V_{\rm CC}$ nor left floating.

One additional note on HC/HCT input terminations. There are several bidirectional (transceiver) logic types in the QMOS family with common I/O pins. These I/O pins do not have the input poly resistor (R) of Fig. 9. Hence, these pins cannot be terminated directly to V_{CC} or GND. A terminating resistor to V_{CC} or GND of 10kohm is recommended.

Input/Output ESD Protection

HC/HCT device inputs have a resistor-diode protection network, shown in Fig. 9, that protects the gate oxide from electrostatic discharge (ESD) damage. The network provides protection to levels typically greater then 2kV in all modes pertaining to the input, as shown in Fig. 10. The 2kV figure was arrived at by testing devices in the ESD test circuit shown in Fig. 11 while conforming to the MIL-STD-38510 requirements.

The recommended handling practices for QMOS devices are similar to those described in RCA Application Note ICAN-6525, "Guide to Better Handling and Operation of CMOS Integrated Circuits".

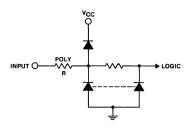


Fig. 9 - Resistor-diode protection network used on inputs of HC/HCT devices to protect device gate oxide from electrostatic discharge damage(ESD).

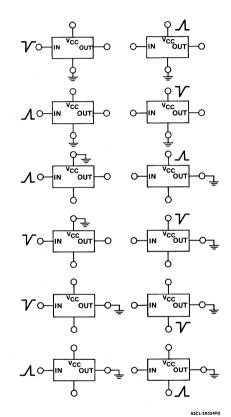
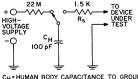


Fig. 10 - HC/HCT ESD test modes



CH=HUMAN BODY CAPACITANCE TO GROUND Rs=BODY SOURCE RESISTANCE

92CS -37074

Fig. 11 - Test circuit used to measure electrostatic discharge (ESD) in HC/HCT circuits. The rise time at the output terminal should be 13 \pm 2nS.

Input Interaction

Another effect of the input-protection network is the imposition of a parasitic transistor between adjacent input pins. Fig. 12 shows this transistor.

92CA-37078R1

Fig. 12 - Parasitic transistor caused by input-protection network.

This parasitic transistor may cause undesirable interaction between adjacent inputs if the input level is greater than Vcc+Vdiode. RCA QMOS devices minimize the alpha (∝ =I_E/I_C) to less than 0.05. This feature of RCA QMOS inputs permits proper logic operation in the presence of transients and also allows high-to-low voltage translation via series input resistors. The typical value of ∝ for QMOS ICs is .001. Fig. 13 illustrates how control of ∝ in RCA QMOS devices provides for safe conversion of 12V control logic levels to 5V HC system logic simply by insertion of a 100k ohm resistor in each input. The only disadvantage is that logic signals are delayed by 1-2uS and therefore, this scheme works well only with rather slow 12V control logic as for example, in automotive applications. When the input diodes are used as clamps for logic level translation, the input current should be kept to 2mA or less.

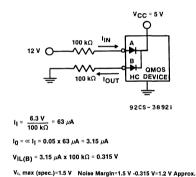


Fig. 13 - 12V-to-5V logic-level conversion at HC inputs using 100kOhm series resistors

Input-Voltage Considerations and Maximum Forward-Diode Input Current Limits

As a general rule, CMOS logic devices employing input clamp diodes (Fig. 9) to minimize ESD effects should be operated between the power supply rails. If the input series polysilicon resistor shown in Fig. 9 is not considered, then the rule is:

$$-0.5V \le V_{IN} \le (V_{CC} + 0.5V)$$

This rule is the industry standard (JEDEC Std. No 7) and is intended to keep users from damaging devices because the devices of some HC/HCT device manufacturers the devices do not have the built-in input series polysilicon resistor. RCA HC/HCT data sheets continue to show the conservative rating established by JEDEC. However, RCA HC/HCT device inputs are capable of meeting the following rating: -1.5V≤V_{IN}≤V_{CC} +1.5V.

Furthermore, RCA devices, except for special cases such as transceivers and analog switches or multiplexer signal inputs, can reliably operate with the $\pm 1.5 V$ rule without logic errors. Beyond $\pm 1.5 V$, maximum forward current poses a second limitation with respect to the V_{CC} and GND rail. This QMOS and JEDEC rating is $\pm 20 mA$ of transient current maximum forced into inputs or outputs.

Latch-Up

Definition

Latch-up within CMOS IC structures may be initiated or triggered by voltage overshoot or undershoot at inputs, outputs, or supply terminals. A high transient voltage or current at any one or combination of these terminals may initiate turn-on of an SCR-type 4-layer diode parasitic bipolar device, as shown in the simplified diagram of Fig. 14. This parasitic structure, when triggered on, keeps the supply voltage below the $V_{\rm CC}$ voltage and thus permits a high supply current of several hundred mA to flow (see Fig. 14). The resistor values of $r_{\rm c}$, $r_{\rm bb}{}^{\prime 1}$ and $r_{\rm bb}{}^{\prime 2}$ are dependent on circuit layout geometry and p+ and n+ doping levels.

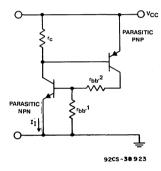


Fig. 14 - Simplified diagram of CMOS 4-layer diode structure

The lower the value of these resistors, the less voltage drop that will occur. A much higher trigger current, therefore, will be required to induce turn on of the SCR structure shown in Fig. 14.

Also important are established layout rules and process parameters that minimize the current gain (Beta) of the parasitic NPN and PNP transistors shown in Fig. 14.

Latch-Up Capability

The trigger current that could potentially trigger latch-up of QMOS ICs is typically $\pm 80 \text{mA}$ at any input or output terminal. Measurements are made at all terminals (see next section for preferred measurement technique), so that these terminals have a minimum acceptable latch current of $\pm 40 \text{mA}$. The absolute maximum rating in the QMOS data sheet and in the industry JEDEC Standard No. 7 is $\pm 20 \text{mA}$. The possibility for transient currents in applications are more likely to appear at input terminals where interfaces could cause voltage transients. The voltage required to induce the $\pm 40 \text{mA}$ measured capability and the $\pm 80 \text{mA}$ typical capability of QMOS ICs as illustrated in Fig. 15, is established by the QMOS built-in 120 ohm minimum current-limiting polysilicon resistor at logic inputs.

Equations:

$$\begin{array}{lll} V_T = I_TR + V_D + V_{CC} & R = 120 \text{ ohms} \\ & V_D = 0.7V \\ -V_T = -I_TR & -V_D & V_{CC} = 4.5V \end{array} \label{eq:vt}$$

Values:

 $V_T = 40 \text{mA} \times 0.12 \text{k ohms} + 0.7 \text{V} + 4.5 \text{V} = 10 \text{V min.} \\ V_T = 80 \text{mA} \times 0.12 \text{k ohms} + 0.7 \text{V} + 4.5 \text{V} = 14.8 \text{V typ.} \\ -V_T = -40 \text{mA} \times 0.12 \text{k ohms} - 0.7 \text{V} = -5.2 \text{V min.} \\ -V_T = -80 \text{mA} \times 0.12 \text{k ohms} - 0.7 \text{V} = -10.3 \text{V typ.} \\ \end{array}$

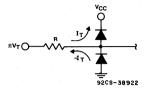


Fig. 15 Input latch transient voltage determination

As developed in Fig. 15, the minimum and typical $\pm V_T$ transient input voltages required to induce either ±40mA or ±80mA are relatively large, and far greater than the transients induced in 5V systems where 2 or 3 volts of ringing transients can be induced via wiring inductance effects. This ±40mA QMOS capability is truly a "latch-up free" condition for operation in a 2V to 6V system. If transients are induced in a particular application beyond +10V/-5.2V, then the use of external series-limiting resistors are advised to keep transient currents below +40mA. Another consideration is unused inputs. If unused QMOS inputs are tied to a V_{CC} of +5.5V and the V_{CC} of the QMOS IC is temporarily grounded, for example, in a 2-power supply system, or when PC cards are replaced with power on, no possibility of latch-up will exist because the input current will be limited to ±40mA via the built-in 120-ohm polysilicon series resistor.

Measuring Latch-Up Sensitivity Caution

The test methods that follow can damage devices if the following precautions are not strictly observed.

- Apply currents for 1ms (min) to 5 seconds (max).
- Limit power supply currents to 200mA.
- Allow a cool-down period between successive tests to be equal to or greater than the time that is required to apply trigger current.
- These tests may be safely adapted to bench-testing with meters or use of a curve tracer
- Static Input or Output Triggering for Latch-up

V_{cc} supply to 200mA

For input triggering connect other inputs to V_{cc} or GND

All valid logic conditions are subject to test.

For Output Triggering (Figs. 16c/d):

- -lo Active outputs must be set low
- +lo Active outputs must be set high
- 3-State outputs Also set output to highimpedance state

Apply trigger current first (Fig. 17)

- Apply $\pm l_1$ or $\pm l_0$ (Fig. 16)
- Raise V_{CC to} ±V_{CC} max.
- After the trigger duration, reduce trigger current to zero
- If I_{CC} is less than its quiescent value, the device is not latched.

If the quiescent value of I_{CC} is out of specification, the input and output structure should be electrically checked to determine if the I/O circuitry is damaged and latch-up did not occur. Further device analysis may be required to verify if latch-up did indeed occur.

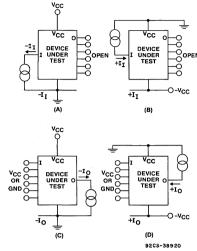


Fig. 16 - Test set-up for positive and negative trigger current

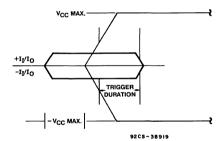


Fig. 17 - Latch test waveforms

2. V_{cc} Triggered Latch-Up Test by Over-Voltage on V_{cc} (Fig. 18)

Latch-up can occur if the voltage of the power supply is raised above the absolute maximum supply voltage rating.

Apply a V_{CC} overvoltage of 2X V_{CC} max. referenced to GND using a 100-mA limited supply.

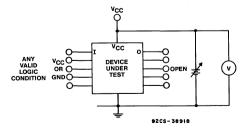


Figure 18: Test set-up for $V_{\text{\tiny C}}$ over-voltage latch trigger

Measure the V_{CC} voltage. If it is less than V_{CC} max., the part has latched.

Output Characteristics

QMOS outputs make use of a complementary symmetry transistor configuration, which is different from the LSTTL totem-pole output; both outputs are shown in Fig. 19. QMOS outputs meet the voltage-level requirements necessary to interface to QMOS inputs, and the drive and current requirements needed to interface to bipolar inputs; i.e., TTL, LS, ALS, AS, FAST, etc.

The outputs of the QMOS devices are classified into two categories: standard and bus drive. The two outputs differ in the output transistor widths needed to meet JEDEC standard drive and current requirements. Both standard outputs and bus drive outputs may be active (2-state) or 3-state with a high-impedance mode added and where both the PMOS and NMOS transistors are off. Another type of QMOS output is the open-drain output of the HC/HCT 03 Quad NAND gate shown in Fig. 20. This output has no intrinsic or added diode connected to $V_{\rm CC}$ at the output. The output of this device may be connected to an external load terminated at up to 10V. Thus, outputs can be pulled up above a nominal 5V supply for up-level voltage conversion.

The HC/HCT03 is the only QMOS gate type whose outputs can be used for a "wired OR" arrangement.

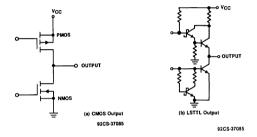


Fig. 19 - Comparison of HC/HCT (a) and LSTTL (b)

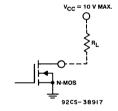


Fig. 20 - HC/HCT 03 output circuit

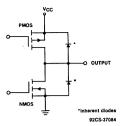


Fig. 21 - Inherent diodes protecting HC/HCT outputs.

Output Protection

The outputs in a QMOS device are protected from ESD damage by diodes. Figure 21 shows these diodes. These intrinsic diodes are effective because of the large geometries (widths) of the output transistors. These diodes are the drain to n-substrate junction of the p device and the drain to p-well junction of the n device. This network provides protection to voltage levels typically greater than 3kV in all ESD discharge modes pertaining to the output (see Fig. 9).

Output Currents

QMOS outputs are specified for both CMOS and LSTTL loads. CMOS inputs are voltage sensitive and the only current is leakage current. The output voltage test for CMOS interfacing is specified for l_0 at $\pm 20 \text{uA}$ (20 CMOS loads). The outputs are also specified at $l_0=4 \text{mA}$ (10 LSTTL loads) and 6mA (15 LSTTL loads) for standard and bus-drive outputs, respectively. The corresponding V_{OL} (max) and V_{OH} (min) for the outputs, are illustrated in Table III.

The maximum current per output pin (I_0) is \pm 25mA and \pm 35mA for standard and bus-drive outputs, respectively. This maximum current rating is specified when the outputs are in their active regions: -0.5V<Vo<Vo<+0.5V. The maximum current rating per power pin, Vcc or ground, is 50mA and 70 mA, respectively, for standard or bus-drive outputs.

When the output voltage exceeds $V_{\rm CC}$ or is below ground by greater than 500mV, the output protection diodes turn on and conduct current. The maximum diode transient current, $I_{\rm CK}$, should not exceed ± 40 mA to avoid latch-up as described earlier.

Table III - Output Drive Specifications

	Te	est Cond	ditions/Limits	(V _{CC} =4.5V)	
Characteristic	lo	25°C	-40 to 85° C	-55 to 125°C	Unit
High-Level Output Voltage, V _{он} (min)	-20uA -4mA -6mA (Bus)	4.4 3.98 3.98	4.4 3.84 3.84	4.4 3.7 3.7	V V V
Low-Level Output Voltage, V _{o∟} (max)	20uA 4mA 6mA (Bus)	0.1 0.26 0.26	0.1 0.33 0.33	0.1 0.4 0.4	V V V

Output-Current and Interfacing Capability

A comparison of the output drive capabilities for QMOS with those of LSTTL is as follows:

LSTTL capability is usually expressed in unit loads (ULs) where the load is specified to be an input of the same family. This specification assures that the worst case low and high input thresholds will be met and the existing margins of noise immunity preserved.

QMOS capability is expressed as source/sink current at a specified output voltage. Since QMOS requires virtually no input current, the unit load concept does not apply.

With a specified output drive of 0.4mA at 0.4V, the QMOS-to-QMOS interface capability exceeds 1000 ULs, and with a 20uA/0.1V specification, the QMOS capability is 20ULs. Each standard QMOS output has a drive capability of ten LSTTL loads and maintains a V_{OL} of 0.4V over the full temperature range. Bus driver outputs can drive 15 LSTTL loads under the same conditions.

The output drive capabilities of QMOS expressed in LSTTL unit loads are shown in Table IV.

Output Curves

Output current derating versus temperature is shown in Fig. 22 and is valid for all types of output. Output source and sink drives at $V_{\rm CC}=2$, 4.5, and 6V are given in Figs. 23 to 26 which show output currents versus output voltages. These curves indicate the typical output current at 25°C and minimum output currents that can be expected at 25°C, 85°C, and +125°C, and can also serve as a design aid in interface applications and for calculating transmission line effects on charging highly capacitive loads.

Note to Figs. 22 to 25: The expected minimum curves are included as an aid to equipment designers, and are tested only at the points indicated on device data sheets.

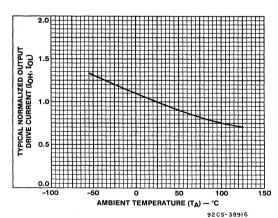
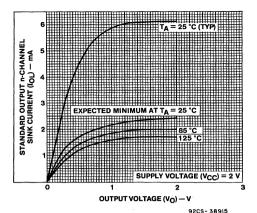
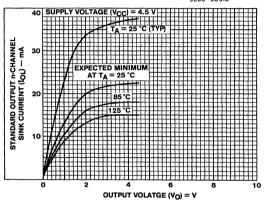


Fig. 22: Output current derating vs. ambient temperature.

Table IV: Comparison of Output Drive Capabilities





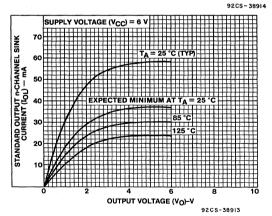
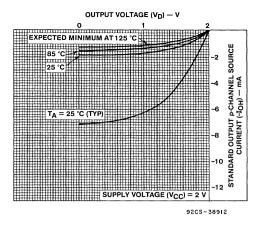
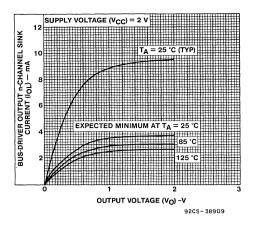


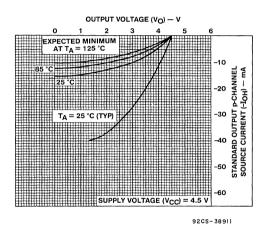
Fig. 23: Standard output n-channel sink current (I_{OL}) for V_{CC} =2V, 4.5V, and 6V.

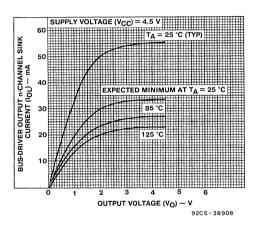
LS Device	Output Drive	HC/HCT Equivalent	Output Type	Output	Drive
74LS00	4 mA 10 UL	74HC00	Standard	4 mA	10 UL
74LS138	4 mA 10 UL	74HC138	Standard	4 mA	10 UL
74LS245	12 mA 30 UL	74HC245	Bus	6 mA	15 UL
74LS374	12 mA 30 UL	74HC374	Bus	6 mA	15 UL

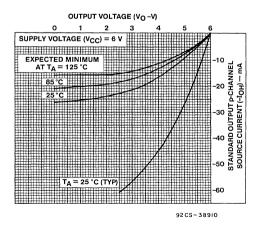
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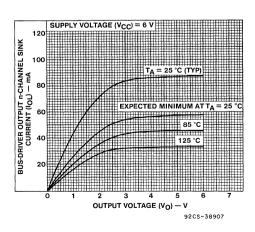
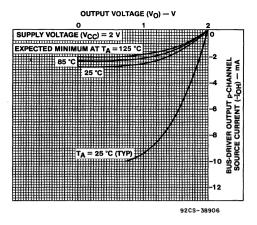
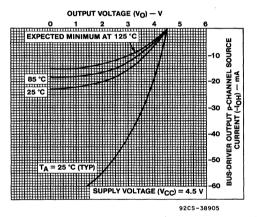


Fig. 24: Standard output p-channel source current (-I $_{OH}$) for V $_{CC}$ =2V, 4.5V, and 6V.

Fig. 25: Bus-driver output n-channel sink current (I_{0L}) for V_{CC} =2V, 4.5V, and 6V.





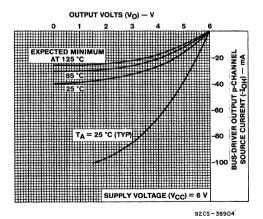


Fig. 26: Bus-driver output p-channel source current (- I_{OH}) for V_{CC} =2V, 4.5V, and 6V.

Dynamic Characteristics

The RCA QMOS family is designed to meet the dynamic switching speeds and operating frequency of low-power Schottky TTL. When compared to metal-gate CD4000 and 74C series CMOS, QMOS shows a 10 to 1 improvement in ac performance. QMOS types feature balanced propagation delays and transition times specified at conditions similar to LSTTL at a nominal $V_{\rm CC}=5V$ and $C_{\rm L}=15pF$, so that the user can relate to the equivalent LSTTL specification. Switching speed limits for QMOS are given at a more realistic $V_{\rm CC}$ of 4.5V and a $C_{\rm L}$ of 50pF. Test waveforms for the HC and HCT types are shown at the end of this section.

Capacitive Load (C_L) Determination

The external capacitive loading (C_L) seen by a QMOS output is required to calculate the propagation delay and operating power dissipation of a logic function. The three components of C_L at a logic node are:

- 1. n C_{IN} where n is the fan-out.
- 2. m C_{OUT} where m is the number of three-state outputs on a logic bus.
- C_{STRAY} which is the effective wiring and interconnect capacitance.

$$C_L = n C_{IN} + (m-1) C_{OUT} + C_{STRAY}$$
 (1)

 $C_{\rm IN}$ is shown in Fig. 27 for typical HCT and HC type inputs. Note that $C_{\rm IN}$ has peak values at the respective switch points of HCT (1.4V) and HC(2.5V). Capacitance on either side of the peak is a summation of package, lead-frame, reverse-biased input diode, and CMOS gate-to-source/drain capacitance. The peak capacitance results from the Miller multiplication of C gate-to-drain in the high-gain linear-transition region. The values of $C_{\rm IN}$ that most typically represent the average loading effect are 4pF for HCT inputs and 3pF for HC inputs. $C_{\rm IN}$ for HCT inputs is higher than that for HC inputs because of the required large gate-to-source/drain capacitance of the large NMOS device widths.

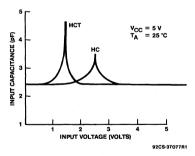


Fig. 27: Cin as a function of Vin.

Output capacitance (C_{OUT}) is typically 10pF for both HCT and HC-type bus-driver outputs when these versions are in their high-impedance state, the only state where C_{OUT} loading is a factor.

The wiring and interconnect capacitance (C_{STRAY}) is determined by estimates of interconnect capacitance and wiring capacitance. These capacitances are highly variable because of differences in interwiring techniques. An often used high-speed wiring technique utilizes strip line with 100-ohm characteristic impedance. C_{STRAY} in this case, is typically 20pF per foot. Capacitances of sockets and connectors are available from their manufacturers.

In a bus system, C_{STRAY} is the largest single C_L component, as the following example illustrates:

 $\begin{array}{ll} \text{Bus Specification:} & \text{No. of fan-outs (n)} = 10 \\ \text{No. of bus drivers (m)} = 5 \\ \text{From Equation (1):} & \text{$C_L = 10 \times 2.5 pF} + 4 \times 10 pF + 7 \times 20 pF} \\ & = 25 pF + 40 pF + 140 pF = 205 pF \end{array}$

Propagation Delays

Propagation Delays Vs. Supply Voltage

The dynamic performance of a CMOS device is related to its drain characteristics. The drain characteristics are related to the thresholds and gate-to-source voltage potential, Vgs. The Vgs voltage is equal to the power supply voltage, V_{CC} . Therefore, a reduction in V_{CC} adversely affects the drain characteristics which, in turn increases the propagation delays. An increase in V_{CC} decreases the propagation delays.

The voltage range of the HCT version is 5V \pm 10%. Over this range, the effects of propagation delays on performance are minimal. However, the voltage range recommended for the HC version is 2 to 6V. Over such a wide range, the effects on dynamic performance of propagation delay and operating frequency (See Fig. 28) are appreciable.

Propagation Delay Vs. Capacitance

Propagation delay vs. capacitance for the RCA family of HC/HCT types is similar to that of LSTTL types which HC/HCT types may replace in present or new applications.

To determine a propagation delay maximum limit at any value of capacitive loading up to 300pF, the following equation is used:

$$t_{PD}(C_L) = t_{PD}(50pF) + t(C_L)[C_L - 50pF]$$
 (2)

Where:

 $t_{\text{PD}}(C_L) = \text{maximum}$ propagation delay at the desired C_L $t_{\text{PD}}(\text{SOpF}) = \text{maximum}$ propagation delay from device data sheet at 2V, 4.5V, or 6V (See Table V). $t(C_L)$ Maximum (ns/pF) multiplying factor from the following table:

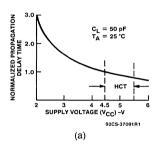
	t(C _L) (nS/pF)
\mathbf{v}_{cc}	Std. Output	Bus Output
2V	0.272	0.187
4.5V	0.102	0.068
6V	0.082	0.056

Propagation Delay Vs. Temperature

Because an increase in temperature causes a decrease in electron and hole mobilities, a temperature increase will cause an increase in propagation delays. Correspondingly, ac performance improves with lower temperatures. Typically, speeds derate linearly from 25°C at about -0.3%/°C.

The propagation delay, therefore, can be computed at any temperature between -55° C and +125° C by using the following relationship:

$$t_{PD}(T) = t_{PD}(25^{\circ}C) + [(T(^{\circ}C)-25) (0.003 \text{ns/}^{\circ}C)]$$
 (3)



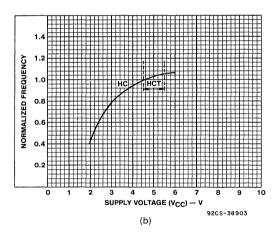


Fig. 28: Typical switching speed characteristic versus supply voltage normalized to 4.5V.

Output Transition Times

Table V shows the RCA standard and maximum ratings for output transition times applicable to all standard and bus-driver outputs. Typical values are approximately one-half the maximum values. Practical unspecified minimum values are one-fourth the limit values.

Table V - Output Transition Time Limits for $C_L = 50pF$

			Maximum Outp				
Output	V _{cc} (V)	T _A = 25°C	T _A = 85°C	T _A = 125°C			
Standard	2 4.5* 6	75 15 13	95 19 16	110 22 19			
Bus Driver	2 4.5* 6	60 12 10	75 15 13	90 18 15			

^{*}Specification for CD54HCT and CD74HCT types.

Output Transition Time Vs. Capacitive Loading

To determine the maximum output transition time on any capacitive loading up to 300pF, the following formula is used:

$$t_T(C_L) = t_T(50pF) + t'(C_L) [C_L - 50 pF] (4)$$

Where:

$$\begin{split} t_T(C_L) &= \text{maximum transition time at the desired } C_L \\ t_T(50pF) &= \text{limit at 2V, 4.5V, or 6V(Table V)} \\ t_TN(C_L) &= (\text{ns/pF}) \text{ multiplying factor from the following table:} \end{split}$$

	t'(C _L) (ns	/pF)
Vcc	Std. Output	Bus Output
2V	0.544	0.374
4.5V	0.204	0.131
6V	0.170	0.110

Transition Time Vs. Temperature

Transition time at HC/HCT outputs typically changes by -0.3%/°C. Equation (3) used to compute increase in propagation delay with temperature (see above), can also be used to compute transition time at any temperature by simply substituting t_T for t_{PD}.

Clock Pulse Considerations

All HC/HCT flip-flops and counters contain master-slave devices with level-sensitive clock inputs. As the voltage at the clock input reaches the threshold level of the device, data in the master (input) section is transferred to the slave (output) section. The use of voltage threshold levels for clocking is an improvement over ac-coupled clock inputs, however, these levels make these devices somewhat sensitive to clock-edge rates. The threshold level is typically 50% of V $_{\rm CC}$ for HC devices, and 28% of V $_{\rm CC}$ for HCT devices (1.4V at V $_{\rm CC}=5$ V). Temperature has little effect on the clock threshold levels.

When clocking occurs, the internal gates and output circuits of the device dump current to ground. This condition results in a noise transient that is equal to the algebraic sum of internal and external gound plane noise. When a number of loaded outputs change at the same time, it is possible for the **chip** ground reference level (and therefore, the clock reference level) to rise by as much as 500 mV. If the clock input of a positive-edge triggered device is at or near its threshold during a noise transient period, multiple triggering can occur. To prevent this condition, the rise and fall times of the clock inputs should be less than 500 ns at $V_{\text{CC}} = 4.5 \text{V}$, the data sheet maximum value.

In the HC/HCT family, several flip-flops have a Schmitt-trigger circuit at their clock input. This circuit increases the maximum permissable rise/fall time on the clock waveform. The RCA flip-flop types HC/HCT 73, 74, 107, 109 and 112, have special Schmitt-trigger circuits which increase their tolerance to slow rise/fall times and to high levels of ground noise.

Maximum permissible input-clock pulse-frequency ratings on each clocked device type data sheet requires a 50% duty cycle input clock. At these rated frequencies, the outputs will swing rail-to-rail, assuming no dc load on the outputs. This feature is a very conservative and highly reliable method of rating clock-input-frequency limits which for HC/HCT devices, equal or exceed LSTTL ratings.

Power Consumption

The power consumption of a HC/HCT device is composed of two components: one static, the other dynamic. The static component is the result of quiescent current caused principally by reverse junction leakage. The dynamic component results from transient currents required to charge and discharge the capacitive loads on logic elements, that is, transient currents caused by internal and external capacitance, and transients resulting from the overlapping of active p and n transistors. Internal chip power consumption is represented by the value CPD.

Two equations are used to compute the total IC power consumption. The first equation (A) is applicable to an HC or HCT device when the inputs are driven from GND to V_{CC} (rail-to-rail), as follows:

Equation (A):

P = PDC + PAC

 $P = I_{CC}V_{CC} + C_{PD}V_{CC}^2 f_1 + \sum C_L V_{CC}^2 f_0$

Where

Icc = Quiescent Current (Ref. Table VI)

V_{cc} = Supply Voltage

f_i = Input Frequency

fo = Output Frequency

C_{PD} = Device Equivalent Capacitance

C_L = Load Capacitance

The second equation (B) is applicable only to an HCT device where specific input pins are driven at LSTTL levels defined as $V_{IN} = V_{CC} - 2.1V$:

Equation (B):

 $P = P_{DC} + P_{AC}$

 $P = I_{CC}V_{CC} + \Delta I_{CC}V_{CC}D + C_{PD}V_{CC}^2f_I + \Sigma C_LV_{CC}^2f_O$

Where.

 Δ I_{cc} = Added dc current when V_{IN} = V_{cc} -2.1V

(LSTTL level)

D = Duty cycle of clock (% of time HIGH)

Table VI - Temperature - Dependent Ratings

				LIN	AIT.		
			T _A = 2	25° C	-40 to +85° C	-55 to +125° C	
	VIN	V _{cc}	typ	max	74HCT MAX	54HCT MAX	Units
ΔI _{cc} additive dc current per input pin (1-Unit)	V _{cc} - 2.1V	4.5V to 5.5V	100	360	450	490	uA

Table VII HC/HCT and LSTTL Maximum Quiescent Current at $V_{\rm CC} = 5V$

Device		HC/I	HCT		LSTTL
Complexity	Typical		Limit		125°C
,	25°C	25° C	85° C	125° C	
SSI	2 nA	2 uA	20 uA	40 uA	4.4 mA
FF	4 nA	4 uA	40 uA	80 uA	8 mA
MSI	8 nA	8 uA	80 uA	160 uA	10 mA
					to
					95 mA

The temperature dependent ratings for I_{CC} are given in the table below:

HCT load table by type shown on each data sheet:

Example: Input Unit Multiplier

All X 0.6

The dynamic power due to outputs is the sum of the ac power at each output. The user must independently determine the $C_{\rm L}$ and the average frequency at each output. The latter requires estimating the average freguency of data nodes in a logic system. For example, for HC/HCT counter types, each output is inherently operating at different frequencies.

The source of the C_{PD} or device equivalent-power-dissipation capacitance is made up of 2 sources of internal device power consumption:

- Power consumed by charge and discharge of internal device capacitance.
- Power consumed through current switching transients.

Fig. 29 illustrates the typical I_{CC} vs. V_{IN} characteristic of HC type devices Note that when $V_{IN}=0.1V$ or (V_{CC} -0.1V), zero current flows. Thus, no ΔI_{CC} component is required for computing the power consumption of HC device types. However, the transient switching components of an IC consume power and are a part of the C_{PD} value.

Fig. 30 illustrates the typical I_{CC} vs. V_{IN} characteristic of HCT type devices. Again, if input voltages are 0.1V or $(V_{CC}$ -0.1V), no ΔI_{CC} value exists. Also for $V_{IN}=0.4$ V, ΔI_{CC} is zero. If V_{IN} , however, is an LSTTL logic high level of $(V_{CC}$ -2.1V) or approximately 3V for $V_{CC}=5$ V, then **significant** ΔI_{CC} does exit and is indicated in equation (B) as the ΔI_{CC} component.

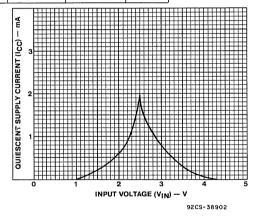


Fig. 29: Icc vs. V_{IN} for RCA HC types

The special input design of RCA's HCT types greatly reduces the value of Δl_{CC} such that the added power is very small; for example, RCA's HCT power is minimal compared to LSTTL power. If this special input circuitry were not used, the Δl_{CC} values would be relatively high as demonstrated by the dashed line in Fig. 30, and the HCT type would not have very low power when compared to LSTTL.

NOTE: The low value of I_{CC} is due to a special input design that provides a true low-power HCT capability.

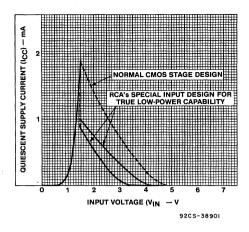


Fig. 30: Icc vs. V_{IN} for HCT types

Because appreciable current flows during device input switching as shown in Figs. 29 and 30, it is important to maintain fast input rise and fall times. The JEDEC and RCA recommended maximum input rise and fall times are:

1000 ns for
$$V_{CC} = 2V$$

500 ns for $V_{CC} = 4.5V$
400 ns for $V_{CC} = 6V$

Since maximum output transition times are 15ns for the standard logic types and 12ns for bus drivers, a designer must only be concerned with exceeding the rise and fall times shown above for interfacing or linear mode operation in applications such as RC oscillators, crystal oscillators, and amplifiers using the HCU04 types.

When Schmitt-trigger types HC/HCT14 and 132 are used for either shaping up slow signals or as RC oscillators, power is increased due to prolonged through-current. For further information on oscillators and their power consumption, refer to RCA Application Note (ICAN-7337), "Astable Multivibrator Design Using High-Speed QMOS IC's".

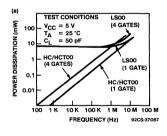
The adverse effects of power transitions is another reason to maintain input rise and fall times under the recommended limits. Longer transitions may cause oscillations of logic circuits (and hence, logic errors) or premature triggering depending on system V_{CC} and GND noise, which are amplified when input signals hover near the switching voltages illustrated in Figs. 29 and 30. To reduce the effects of slower transitions, the use of Schmitt trigger types is recommended.

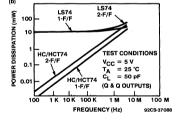
Comparison to LSTTL Power

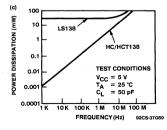
The dynamic power consumption of HC/HCT devices is frequency dependent, but it should be noted that LSTTL power consumption is also frequency dependent at frequencies greater than 1MHz. At frequencies less than 1MHz, the dynamic component is negligible compared to the static component. The average power consumption of HC/HCT and LSTTL equivalents is illustrated in Fig. 31 for four device types. Because all of the functions in a multifunctional LSTTL device are biased when power is applied, the HC/HCT device characteristics are plotted for a single function and for the total package for the purposes of comparison.

Some observations from Fig. 31 are:

- 1) For SSI gate types, the HC/HCT power approaches LSTTL power at about 1MHz.
- For higher complexity types such as the RCA HC/ HCT 138 3-of-8 line decoder/demultiplexer shown in Fig. 31(c), HC/HCT power approaches LSTTL power at above 10MHz.







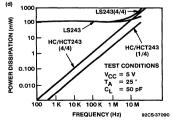


Fig. 31 - Power versus frequency graphs for the (a) LS/HC/HCT00, (b) LS/HC/HCT74, (c) LS/HC/HCT138, and (d) LS/HC/HCT243.

3) Fig. 31 implies continuous operation at the frequencies shown, however, most practical applications of logic in microcomputer systems have variable operation or data/address signal rates. The average operating frequency is much below the peak operating frequency — particularly in the 100KHz region where power savings over LSTTL are several orders of magnitude.

Power-Supply Considerations

Power-Supply Voltages

The RCA HC and HCU versions have a power supply range of 2 to 6V; the absolute maximum voltage rating is 7V. The ability to use RCA's HC types with a 2V supply makes these devices particularly useful in battery-operated equipment, especially systems including memories that feature 2V standby operation. The absolute maximum supply or ground current, per pin, is $\pm 50 \text{mA}$ for types with standard output drive, and $\pm 70 \text{mA}$ for types with bus driver outputs.

The operating supply-voltage range for RCA's CD74HCT types is 4.5V to 5.5V, 5V \pm 10%. These figures indicate that there is more tolerance in the regulation of the low-current system supply than is the case with other technologies. The maximum voltage indicated for HC and HCU versions also applies to HCT versions. The advantages of using HC/HCT/HCU with its wider voltage supply range are illustrated in Fig. 32.

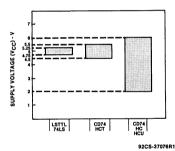


Fig. 32: Power-supply ranges for CD74HCT, CD74HC and CD74HCU versions of the RCA family of devices and 74LS series types.

Battery Back-Up

Battery back-up can be easily implemented in systems of RCA's HC/HCU devices. An example of this arrangement is shown in Fig. 33. The minimum battery voltage required is only 2V plus one diode drop.

In the example, RCA's High-to-Low Level Shifters (HC4049 or HC4050) are used to prevent the flow of positive input currents into the system due to input voltage levels greater than one diode drop above $V_{\rm CC}$. If the circuit design is such that input voltages can exceed $V_{\rm CC}$, then external resistors should be included to limit input currents to 2mA. External resistors may also be necessary in the output circuits to limit currents to 2mA, if the output can be pulled above $V_{\rm CC}$ or below GND. These currents are due to inherent $V_{\rm CC}/GND$ diodes that are present in all outputs, including three-state outputs.

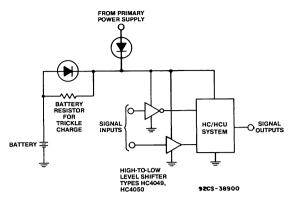


Fig. 33 - Example of an HC/HCU system with battery back-up.

Power Supply Regulation and Decoupling

The wide power supply range of 2 to 6V may suggest that voltage regulation is not necessary, but it must be realized that a changing supply voltage affects system speed, noise immunity and power consumption. Because noise immunity, and even the correct operation of the circuit, can be affected by noise spikes on the supply lines, therefore, matched decoupling is always necessary in dynamic systems.

Both HC and HCT types have the same power supply regulation and decoupling requirement. The best method of minimizing spiking on the supply lines is by implementing good power supply and ground bussing and having low ac impedances from the $V_{\rm CC}$ and GND pins of each device. Because the minimum value of a decoupling capacitor depends on the voltage spikes that can be allowed, it is a general rule to restrict ground and $V_{\rm CC}$ noise peaks to 400mV. A local voltage regulator on the printed-circuit board can be decoupled using an electrolytic capacitor of 10 to 50 uF.

Localized decoupling of devices can be provided by a 22nF capacitor for every two to five packages, and a 1uF tantalum capacitor for every ten packages. The $V_{\rm CC}$ line of bus driver circuits and level sensitive devices can be effectively decoupled from instantaneous loads by a 22 nF ceramic capacitor connected as close to the package as possible.

A practical example of determining the value of a decoupling capacitor is as follows: assume that a buffer output sees a 100-ohm dynamic load and that the output low-to-high transition is 5V, then the current demand is 50 mA per output. For an octal buffer, the current demand would be 0.4A per package, in approximately 6 nS.

The following formula can also be used to determine the value of a decoupling capacitor:

The term Q = CV is differentiated to obtain
$$\frac{\Delta Q}{\Delta t} = C \frac{\Delta V}{\Delta t}$$

Since
$$\frac{\Delta Q}{\Delta t}$$
 = I, the equation becomes I = C $\frac{\Delta V}{\Delta t}$.

Hence:
$$C = \frac{I\Delta t}{\Delta V}$$

For an octal buffer, assuming a change in V_{CC} or GND of 0.4V, then:

$$C = \frac{0.4 \text{ A X 6 X } 10^{-9} \text{S}}{0.4 \text{ V}} = 6 \text{ X } 10^{-9} \text{ F} = 6 \text{ nF}.$$

For further information on power-supply regulation and decoupling, refer to RCA Application Note ICAN7329, "Power-Supply Distribution and Decoupling for QMOS High-Speed IC's."

Interfacing

Because of the characteristics of the CMOS output, the HC/HCT family is very versatile in interfacing between different logic families. This capability including the corresponding fanout is illustrated in Fig. 34.

Note that the fanout to CMOS devices is limited only by the input rise and fall times, which are dependent on the capacitive loading, C_L. This dependence can be computed by the following relationship:

$$t_{B_1} t_F = 2.2 RC_L$$
 (5)

where R is the impedance of the output.

Fanout From:	Te	o Co	rrespo	nding l	ogic F	amilies:
нс/нст	TTL	LS	ALS	FAST	S/AS	4000, 74C
Standard Types	2	10	20	6	2	See
Bus Drivers	3	15	30	10	3	Text

Fig. 34 - HC/HCT interfacing capability and corresponding fanout to other logic families

RCA's HC types cannot be driven from any of the TTL families because the TTL output voltage high, V_{OH} (min), does not satisfy the HC input voltage high, V_{HH} (min) specification. The HCT types can be directly interfaced to the TTL families because the HCT input voltage high, V_{OH} (min) is less than the TTL output voltage high, V_{OH} (min). To meet minimum V_{HH} requirements, HC types can use a pull-up resistor as illustrated in Fig. 35.

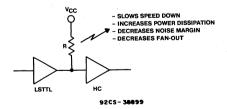


Fig 35 - Use of pull-up resistor to interface TTL and HC devices.

However, the use of a pull-up resistor will not give optimum performance because as noted in Fig. 35, the resistor tends to slow down system speed, increase power dissipation, decrease noise margin, and decrease fan-out.

For further information on interfacing, refer to RCA Application Note ICAN7325, "Interfacing HC/HCT QMOS Logic with Other Families and Various Types of Loads."

Logic-Level Conversion

The HC/HCT family contains logic-level conversion types necessary to interface high-voltage logic levels (up to 15V common in control and automation systems) to low voltage levels (down to 2V) as shown in Fig. 36.

Fig. 36 - High-to-low logic level conversion

B) HEX NON-INVERTING

92CS-38898

The Quad open-drain NAND gate (HC/HCT03) is used to convert from HC (2V to 6V) or HCT (TTL or CMOS) logic levels up to 10V output logic levels as shown in Fig. 37 R_L can be a very wide range of values. For design of this output interface, use

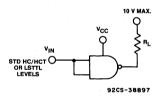


Fig 37 - Low-to-high logic-level conversion

the output N-MOS transistor characteristics of Fig. 23. The minimum value of R_L is that necessary to keep the output current below the 25mA HC/HCT family maximum rating. A large value of R_L will prolong the output rise time.

System (Parallel) Clocking

When utilizing the HC/HCT family in synchronously clocked systems the following guidelines should be followed. Because of variations in switching points between devices, a slow clock edge could cause a logic error. If data in one of the synchronously clocked circuits changes before the switching point of the next sequential circuit is reached, a logic error will occur. This situation is illustrated in Fig. 38.

VS1 = Switching point, device 1
VS2 = Switching point, device 2
tp = Propagation delay

Because of variations in input threshold voltages among RCA's HC-version devices, the maximum clock-pulse rise or fall time should adhere to the following relationship:

$$t_{r_{t}} t_{f} (max) < 2t_{p} (max) \tag{6}$$

In a system where HC, HCT, and TTL-type families are mixed, the maximum clock pulse rise or fall times should adhere to the following relationship:

$$t_R$$
, t_F (max) $< t_P$ (max) (7)

It is recommended that a Schmitt-trigger circuit be utilized if wave-shaping is required.

The maximum rise or fall time into any RCA HC or HCT device must be limited to 1000, 500, and 400 nS at 2, 4.5, and 6 volts, respectively. If these limits are exceeded, noise on the input or power supply may cause the outputs to oscillate during transition. This oscillation could cause logic errors and unnecessary power consumption.

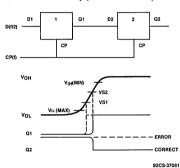


Fig. 38 - Result of changing data in one synchonously clocked circuit before the switching point of the next sequential circuit is reached.

Drop-In Replacement

The use of RCA HCT family devices make it unnecessary to sacrifice noise margins, speed, and quiescent power dissipation in constructing interfaces to achieve mixed-technology designs. This performance is possible because HCT devices are TTL compatible and can directly replace LSTTL counterparts without the addition of pull-up resistors at the LSTTL outputs.

Fan-out capabilities should be taken into account when an HCT device is used to replace a TTL part. TTL fan-out is usually expressed in unit loads (ULs) and the load is specified to be an input of the same family. In fact, TTL fan-out is determined by the ability of the outputs to sink current (a TTL input usually sources current). The outputs of HCT devices are classified in two categories: standard and busdriver. Table VIII shows the fan-out for the different TTL families.

For further information on drop-in replacements, refer to RCA Application Note ICAN7330, "Replacing LSTTL with QMOS High-Speed Logic IC's".

The fan-out values shown in Table VIII are derived at a voltage drop of maximum 0.4V (V_{OL}). In the "74" TTL ser-

ies, an extended V_{OL} value is often seen, e.g., 8 mA at 0.5V voltage drop for LSTTL. If this value is used in determining the fan-out of the TTL part, it can result in a higher fan-out than is possible with QMOS. This condition can be resolved by replacing as many of the driven TTL parts as possible by HCT devices to reduce the sink current requirement (the HCT input current is neglegible). Furthermore, the use of HCT devices results in a substantial reduction in power dissipation.

Devices of the HCT family are power-saving, virtually drop-in replacements for LSTTL parts. The total power consumed by a system depends largely on the number of gates switching at any time and on the switching frequency, but in most systems only about 30% of all circuits switch at the maximum system frequency; 70% operate at far lower rates. Thus, even in systems using ALS, AS, S and FAST, the HCT family can be used with consequent power-savings and good reliability improvement in mixed technology designs.

Conversion of LSTTL Test to HCT Test

A simplified technique to convert an LSTTL test program to one that properly tests an HCT type is explained in RCA application note ICAN-7323 "Modification of LSTTL Test Programs to Test HCT High-Speed CMOS Logic IC's".

Bus Systems

Bus systems are commonly used in microcomputer applications. RCA CMOS devices are being increasingly used in these applications, for example, several CMOS versions of popular NMOS processors have recently been introduced.

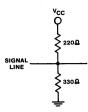
There are several constraints imposed on microprocessor systems in industrial applications, such as electrically noisy environments, battery stand-by requirements and sealed, gas-tight enclosures. QMOS bus systems, e.g., the proposed CMOS STD bus (a non-proprietary CMOS bus proposed standard) provides a low power solution to virtually all of these problems. In comparison with older bipolar digital IC Bus standards, QMOS bus systems offer superior noise immunity, equal operating speed, lower power dissipation, wider supply voltage range, extended temperature range, and enhanced reliability.

In order to optimize results with QMOS, particularly in circuits which communicate directly with the bus, the use of only HC devices is recommended, because HC QMOS optimizes input-signal noise immunity with HC QMOS a new low-power bus termination can be introduced (see Fig. 39 (b)) which, unlike the conventional high-current TTL bus termination of Fig 39a, draws no heavy dc current and is more suited to QMOS outputs. Both HC and HCT QMOS have the identical rail-to-rail output drive.

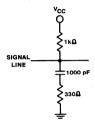
The wider supply voltage range of HC type QMOS together with its lower power dissipation virtually eliminates problems caused by voltage drops along power

Table VIII: Fan-Out of HCT to TTL Elements

нст	TTL	LS	ALS	FAST	S & AS
Standard Bus-Driver	2 3	10 15	20 30	6 10	2 3



(a) Conventional terminations for TTL buses - 0.25 W per line or 2 W per octal drive and termination.



(b) Proposed low-power termination for CMOS STD bus equivalents.

Fig. 39 - Bus Terminations

buses between cards in a system. It is possible for a circuit to pick up severe noise spikes or differential voltages via the card edge-input protection circuit. Such

pick-up can exceed the CMOS input current maximum ratings if the input current is not limited by a 10k-ohm series resistor in the QMOS logic line. This series resistor will limit transient current to ± 20 mA for external voltages of up to $\pm 200V$. However, for correct functioning, the dc input current should be kept below 2 mA. This type of card edge input protection is shown in Fig. 40.

In the circuit of Fig. 40, if the input diode current exceeds 2mA, a QMOS high-to-low level shifter should be used (e.g., HC4049, or HC4050).

Because QMOS bus-drivers do not have built-in hysteresis, slowly rising pulses should be avoided or devices with Schmitt-trigger action should be used, such as the QMOS flip-flop series HC/HCT73, 74, 107, 109, 112, or the dedicated Schmitt-trigger types HC/HCT14 and 132. The rise and fall times can be derived from the information given in the section, "Propagation Delays and Transition Times".

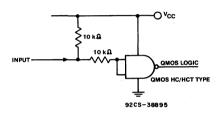


Fig. 40: Example of the card edge-input-protection circuit.

Standardized Capacitance Power Dissipation (CPD) Test Procedure

The purpose of the CPD number is to allow the user to estimate the actual power consumption of his system. Therefore, the table has been set up to exercise each device in the same manner as it would usually be used. Devices which are separable into independent sections are measured on a "per section" basis, the remaining are measured on a "per device" basis. Each part number's unique setup is listed in the "Pin Condition Table." The following paragraphs describe the generic set up for each class of devices:

All part numbers: Measurements are to be made at $T_A = 25$ °C, $V_{CC} = 5$ V, and 3-state outputs both enabled and disabled.

Gates: Switch one input. Bias the remaining inputs such that the output switches.

Latches: Toggle as in a flip-flop.

Flip-flops: Switch the clock pin while changing "D" (or biasing "J" and "K") such that the output(s) change each clock cycle. For part numbers with common clocks, exercise the "D", "J", or "K" inputs of only one flip-flop. Set the inputs of the remaining flip-flops so they do not change state.

Decoders / Demultiplexers: Switch one address pin, which changes two outputs.

Data Selectors / Multiplexers: Switch one address input, with the corresponding data inputs at opposite logic levels, so that the output switches.

Counters: Switch the clock pin, with other inputs biased, such that the device counts.

Shift Registers: Switch the clock, adjust the data inputs such that the shift register fills with alternate 1's and 0's.

Transceivers: Switch one data input. For bi-directional

transceivers enable only one direction.

One Shots: TO BE DETERMINED Parity Generators: Switch one input.

Priority Encoders: Switch the lowest priority input.

Rams: TO BE DETERMINED

Display Drivers: Switch one input such that approximately

half the outputs change state.

ALUs / Adders: Switch one least significant input bit, bias the remaining inputs so that the device is alternately adding 0000 (binary) or 0001 (binary) to 1111 (binary).

Since CPD is a measure of device power consumption, and not that of the driven load, each output would ideally be unloaded. However, this is impractical with automatic testers which often have 30 to 40 pF hanging on each pin. Therefore, each output which is switching should be loaded with the standard 50 pF. The equivalent load capacitance, based on the number of outputs switching and their frequency, is then subtracted from the measured gross CPD number to obtain the device's actual CPD value.

If a device is tested at a high enough frequency, static supply current will contribute a negligible amount to power consumption and can be ignored. Thus, it is recommended that power consumption be measured at 1 MHz and the following formula be used to calculate CPD:

$$CPD = \frac{(I_{CC})}{(V_{CC})(1E6)} - (equivalent load capacitance)$$

than the V_{CC} supply

B = both R and C

EXPLANATION OF SYMBOLS Key V = V_{CC} (+5 V) G = ground H = logic 1 (V_{CC}) — inputs at V_{CC} for HC types; 3.5 V for HCT types L = logic 0 (ground) D = don't care — either H or L but not switching C = a 50 pF load to ground O = an open pin; 50 pF to ground is allowed P = input pulse (see illustration) O = half frequency pulse (see illustration) R = 1 kΩ pull-up resistor to an additional 5 V supply other

Pin Condition Table for CPD Tests

	Equiv-														Pin	Nur	nbe	r											
HC/ HCT	alent Load																												
Types	(pF)	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28
00	50	Р	н	C	D	D	o	G	0	D	D	0	D	D	٧	_	_	_	_	_	_	_	_	_	_	_	_	_	-
02	50	С	P	L	0	D	D	G	D	D	0	D	D	0	ν	_		_	_		_		_	_	_		_	_	_
03	0	Р	Н	В	D	D	0	G	0	D	D	0	D	D	٧	_	_		_	_		_	_	_	_	_	_	_	_
04 :	50	Ρ	_		-	_	_	_	-	D	-	D	0	D	٧	_	_	_	_	_	_	_	_		_	_	_ ,	_	_
U04	50	Ρ	С	D	0	D	0	G	0	D	0	D	0	D	٧	_	-		-	_	-	_	_	-	_	_	_	_	_
08	50	P	н	Ċ	D	D	0	G	0	D	D.	0	D	D	٧	_	_	_	_	_	_		_		_	_	-	_	_
10	50	Ρ	Н	D	D	D	0	G	0	D	D	D	С	Н	ν	_	_	_	_	_	_	_	_	_	_	_	_	_	_
11	50	Ρ	Н	D	D	D	0	G	0	D	D	D	С	Н	ν	_	-		_	_	_	_	_	-	_		-	_	_
14	50	P								D		D	0	D	٧	_	_		_	_	_	_	_	_	_	_	_	-	_
20	50	Ρ	Н	0	Н	Н	С	G	0	D	D	0	D	D	٧	_	_	_	_	_	_	_	_	_	_	_		-	_
21	50	Ρ	Н	0	Н	Н	С	G	0	D	D.	0	D	D	ν	_	_	_	-	_	_	_	_	_	_	_	_	_	_
27	50	P	L	D	D	D	0	G	0	D	D	D	С	L	٧	_	_	_	_	_	_	_	_	_	_	_	_	_	_
30	50	P							-	0	-	Н	Н	0	ν		_	_	_	-		-	_	_	_	_	-	_	_
32	50	Ρ								D		0	D	D	ν	- ,	_		-	-	_	-	_	-	_	-	-	-	-
42	100	С	С	0	0	0	0	0	G	0	0	0	L	L	L	Р	٧	-	_	-	-	-	_	-			-	-	_
58	50	Ρ	D	D	D	D	О	G	0	L	L	L	Н	Н	٧	_	_	_	_	_	_	_	_	_	_	_	_	_	_
73	50	Р	Н	Н	٧	D	D	D	0	0	D	G	С	С	Н	_	_	_	_	_	_	_	_	_	_	_	_	_	_
74	50		Q							0		D	D	D	٧	_	_	_	_	_	_	_	_	_	_	-	_	-	_
75	50									0		0	G	Р	0	0	С	-	-	_	-	_	_	-		_	_	_	_
85	50	L	Н	P	Н	0	С	0	G	L	L	L	L	L	L	L	٧	_	-	_	_	-	_	_	_	_	_	-	_
86	50	P	L	С	D	D	0	G	0	D	D	0	D	D	V		_	_	_	_	_	_	_	_	_	_	_	_	_
93	47	Q	L	L	D	٧	D	D	С	С	G	С	С	D	Ρ	_	_		_	_	_	_	_	_	_	_	_		_
107	50	Н	С	С						D		D	P	H	٧		_	_	-	_	_	_	_	_			-	_	_
109	50	Н	Н							0		D	D.	D	D	D	٧	_	_	_	-	-	_	-	_	-	_	-	_
112	50	Р	Н	Н	Н	С	С	0	G	0	D	D	D	D	D	Н	٧	-	-	-	_	-	_	_	-	-	_	-	_
123	100	L	Н	Ρ	С	0	0	0	G	D	D	D	0	С	0	R	٧	_	_	· <u>-</u>	_	_	_	_	_	_	_	_	_
125	50	L	P	С	D	D	0	G	0	D	D	0	D	D	٧	_	_	_	_	_	_	-	_	_	_	_	'	_	_
126	50	Н	Р				-	_	_	D	_	0	D	D	٧	-	_	_	-	_		_	_	_	-	-		_	-
132	50	Ρ	Н				_		_	D	_	0	D.	D	٧	_	-	-	-	-	-	_	· —	_	-	-	-	-	_
137	100	Ρ	L	L	L	L	Н	О	G	О	0	О	О	0	С	С	V	_	-	-	_	-	_	-	-	_	_	_	_

Pin Condition Table (Cont'd)

	Equiv-												Pin	Nun	nbei												
HC/ HCT Types	alent Load (pF)	1 2	3	4	5	6 7	78	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28
138 139 147 151 153 154 157 158 160	100 100 50 100 50 100 50 50 50		L H L D O H H	C H H D O C C	C H C L O L L	0 0 H 0 L	0 L C O O		0 0 C H L L	O O P P D O L L C	О О Н D D G О О С	O D H D D O L L C	C D O D P O L L C	C D O D O L L C	>	- - - - 0 - -	- - - - L -	- - - - - L	- - - - - L	- - - - - L -	- - - - - L	- - - - P -	- - - - v - -	- - - - - - -	- - - - - -	- - - - - -	
161 162 163 164 165 166	50 55 50 200 50 25	H P H P Q H H P Q D	D D C D	D C D	D D C D	D D C D L	H G C P	G H G H G G	Q H D	CCCDD	C C C D D	CCCCCC	C C C V D D	C C C - L H	V V V V	- - - -	- - - -	- - - -		- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - - -
173 174 175 181 182	25 25 50 250 150	H C H C P H H L	C Q	D Q L	O D L	D O H	О О Н	G F G F L (o c	D O C C	D O D G C	D D C P	Q D O B H	C C L	V V C V	_ _ C _	_ _ L _	— — Н	_ _ L	— — Н	_ _ L	— Н	- - V -	_ _ _ _	- - -	- - - -	- - - -
190 191 192 193 194	60 53 60 50 100	D C D C D C H Q	C C	L H H	L P P	С С С	C C	G [G [G [D D D D	Н Н Н Н	C C C C	C C C C	P L L C	D D D C	V V V V V	- - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -		- - - -	- - - -	- - - -	- - - -
195 221 237 238 240	125 100 100 100 50	H H L H P L P L L P	P L L	C L L	0 L L	0 H H	0	G (D D	C D O O D	0 0 0	C O O D	C O C C	C R C C	v v v o	- - - D	- - - c	- - - D	- - - v	- - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -
241 242 243 244 245	50 50 50 50 50	L P L O L O L P H P	Р Р О	D D D	D D O	D D D	G G O	0 (0 (0 (0 G 0 O 0 G 0 G	D C C D	0 0 0 0	D L L D	0 V V 0	D - - D 0	0 - - 0	D - - D 0	C - c c	H - D L	v - - v v	- - -	- - -		- - - -	- - - -	- - -	- - - -	- - - -
251 253B 257 258 259	100 50 50 50 50 25		D H H	D C C	L D D	H D D	0 0	G (G (P D D D	D D O O	D D D Q	D P D D	D D L L	> > > >	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -	- - - -
7266 273 280 283 297	50 25 100 250 12	P L H C L L C H H H	Q O L	D L C	O C P	0 C H	D G L	D (P I G (O G L L C C	O P L H O	D C L C	D L C D	V D V L	— О Н Н	- 0 - v v	_ D _ _	_ D _ _	- 0 - -	- V - -	- - - -		- - - -	- - - -	- - - -	- - - -	- - - -	- - - -

Pin Condition Table (Cont'd)

HC/	Equiv-														Pin	Nun	nber	•			-					-			
HC/ HCT Types	alent Load (pF)	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28
299 354	250 100	D	D	LDD	D	D	D	L	Н		G	Q L	P L	C	C P	C	C	СН	D C	C	v v	_ ·	_	_	_	_	-	_	_
356 365 366	50 50 50	L	Р	C	D	0	D	О	G	P O O		0 0	L D D	0 0	D D	L L	L V	H 	C -	C -	V -	_	_	_	_	_	_	_	_
367	50	L								0		0	Ď	0	D	L	v	_	_	_	_	_	_	_	_	_	_	_	_
368 373	50 25	L		Q	D		0	D	D	0	G	O P	D 0	. O D	D D	0	0	_ D	_ D	0	- V	-	_	-	_	-	_	-	-
374 377	25 25	L	С		D	0	0	D	D	0	G	P P	0	D D	D D	0	0	D D	D D	0	V V	_	_	_	_	_	_	_	_
390 393 423	50 47 100	P P L	L L P	С	С	С С О	С	G	0	0 0 D	0	0 0 D	D D O	0 D C	D V O	D - R	V - V	_	_	_	_	-	_	-	-		_		
533 534	25 25		С	Q	D	0	0	D	D	0	G	P P	0	D D	D D	0	0	D D	D D	0	V V	_	<u>-</u> .	<u>-</u> .	_	_	_	-	_
540 541	50 50	L L	P P			D D			D D	D D		0	0	0	0	0	0	0	C C	L L	V V	_	_ 	_	_	_	_	-	_
563 564	25 25	L L	Q	D D	D	D	D	D	D	D D		P P	0 0	0	0	0 0	0 0	0 0	0 0	C C	V V	_	_	- -	<u>-</u>	-	- -	_	_
573 574	25 25	L	P Q	D	D		D	D	D	D D	G	H P	0	0	0	0	0	0	0	c c	V V	_	_	_	_	_	_	- -	_
583 597 7597	250 25 25	D	H D D	D	D	D	D	D	G	CCC	Н	C P	H D D	P H H	L Q	L D D	V V V	_	_	-	_	-	_		_	_	_	_	_
640	50	Н	P	D	D	D	D	D	D	D	G	0	О	0	0	0	0	0	C	L	V	_	_		_	-	_	_	_
643 646 648 670	50 50 50 100	D D	L Q	H H Q	P P L	D D P	D D C	D D C	D D G	D C	D D C	O D D L	O G L	0 0 0 L	0 0 0 P	0 0 0 0	0 0 0 V	0 0 0	0 0 -	0 0 L	v c c	L L	D D	D D	v v -	- 1 -	- - -	- - -	- - -
688 4002 4015	50 50 100		P P C	L	L	L	o	G	0	L D D	D	L D C	L D C	С С	L V L	L - Q	_ V	L _	L - -	c - -	v -	-	- -	<u> </u>	-	-	- -	_	_
4016 4017 4020	0 55 48	C	_	0	0 C	D C	D C	G C	O G	o	0 C	O C L	D C C	P L C	V P C	L C	· _ v	_	_	_	-	-	-	_	_	_	_	_	_
4024 4040	48 48	P	L	С	С	С	С	G	0	C	o	C	C	0	v c	- C	- V	_	_	_	_	_	_	_	_	_		_ _ _	_ _
4046A 4049 4050	50 50 50	٧	CCC	L P	0	H D	0	O D	G G	0 D D	0 0	O D D	0	0	P D D	0	V 0 0	<u>-</u> -	- -	<u>-</u> -	- -	<u>-</u> -	-	-	- -	-	- -	- -	-
4051 4052 4053	0 0 0	0		0	0	0	L	G G	G G	L		P O P	0	0 0	0	0 0	V V	<u>-</u> ,	- -	_	_	_	_	_	-	<u>-</u>	_	_	-
4053 4059 4060	17 106	Р	D	Н	L	L	L	L	G L G	L	L	H P	G	H	Н	C L	V L V	L -	L –	L -	L –	L –	L –	с -	v -	- -	_	_	- -

Pin Condition Table (Cont'd)

HC/ HCT Types	Equiv-														Pin	Nu	mbe	r								-			
	Load (pF)	1	2	3	4	5	6	7	8	9	10	11	12	13	14	15	16	17	18	19	20	21	22	23	24	25	26	27	28
4066	0	0	0	0	0	D	D	G	0	О	0	0	D	Р	ν	_	_	_	_	_	_	_	_	_	_	_	_	_	_
4067	0	0	0	0	0	0	0	0	0	0	Р	L	G	L	L	L	0	0	0	0	0	0	0	0	V	_	_	-	_
4075	50	Ρ	L	D	D	D	0	G	L	С	0	D	D	D	٧	_	_	_	_	_	_	_		_	_	_	_	_	_
4094	250	Н	Q	Ρ	С	С	С	С	G	С	С	С	С	С	С	Н	٧	_	_	_	_	_	_	-	-	-	-	_	-
4316	0	0	0	0	0	Ρ	D	L	G	G	0	0	0	О	D	D	٧	_	_	_	_	_	-	-	_	_	_	-	-
4351	0	0	0	0	0	0	0	L	н	G	G	н	P	L	0	L	0	0	0	0	V	_	_	_	_	_	_	_	_
4352	0	0	0	0	0	0	0	L	Н	G	G	н	Р	L	0	0	0	0	0	0	V	_	_		_	_	_	_	_
4353	0	0	0	0	0	0	0	L	Н	G	G	Н	Р	L	0	L	0	О	0	0	V	_	_	_	_	_	_		_
4510	55	L	С	D	D	L	С	C	G	L	Н	С	D	D	С	Ρ	٧	_	_	_	_	_	_	_	_		_	_	_
4511	200	L	L	Н	Н	L	L	Ρ	G	С	С	0	0	С	0	С	٧	_	_	_	-	_	_	_	_	_	_	_	-
4514	100	н	Р	L	0	0	0	0	0	С	0	С	G	0	0	0	0	0	o	0	0	L	L	L	V	_	_	_	_
4515	100	Н	P	L	0			o			0	C	G	O	0	O	0	o	0	0	0	L	L	L	V	_	_	_	_
4516	50	L	С	D	D	L	С	С	G	L	H٠	С	D	D	С	Р	٧	_	_	_	_		_	_	_	_	_		_
4518	50	Р	Н	С	С	С	С	L	G	D	D	0	0	0	0	D	٧	_	_	_		_		_	_			_	_
4520	47	Ρ	Н	С	С	С	С	L	G	D	D	0	0	0	0	D	٧	_	_	_	-	_	_	_	_	-	_	-	_
4538	100	G	R	н	Р	н	С	С	G	0	0	D	D	L	0	G	v	_	_	_	_			_	_	_	_	_	_
4543	50	Н			Н		_	_	_	c	_	C	C	C	Ċ	Ċ	٧	_	_	_	_	_	_	_	_	_	_	_	_
7030	325	G	G	С	Ρ	Q	Q	Q	Q	Q	Q	Q	Q	Q	G	L	С	С	С	С	С	С	С	С	С	С	Ρ	Н	٧
7046A	50	0	С	L	0	Н	0	0	G	0	0	0	0	0	Р	0	٧	_	_	_	_	_	_	_		_	_	_	_
40102	5	P	Н	L	L	L	L	L	G	Н	L	L	L	L	С	Н	٧	-	_	-	-	-	_	_	_	_	_		_
40103	3	Р	н	L	L	L	L	Ĺ	G	н	L	L	L	L	С	н	٧	_	_	_	_	_		_	_	_	_	_	_
40104	100	Н	Q	D	D	D	D	D	_			P	c	c	Ċ	C	٧	_			_	_	_	_	_	_	_	_	_
40105	200	L	С	Р	Q	Q	a	Q	G	L	С	С	С	С	C	P	V	_	_	_	_	_	_	_	_	_	_	_	_

RCA Standardized Maximum Ratings and Recommended Operating Conditions for CD54/74HC, CD54/74HCT, and CD54/74HCU Integrated Circuits

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V).	
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Voc + 0.5 V):	
STANDARD OUTPUT	±25 mA
BUS DRIVER OUTPUT	±35 mA
DC Vcc OR GROUND CURRENT, (Icc):	
STANDARD OUTPUT	±50 mA
BUS DRIVER OUTPUT	±70 mA
POWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +60°C (PACKAGE TYPE M)	300 mW
For T _A = +60 to +85°C (PACKAGE TYPE M)	Derate Linearly at 5 mW/°C to 175 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tstg)	
LEAD TEMPERATURE (DURING SOLDERING) :	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

CHARACTERISTIC	LIN	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNIIS
Supply-Voltage Range (For TA=Full Package Temperature Range) Vcc:*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _i , V _o	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r ,t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

Static Electrical Characteristics for CD74HC/CD54HC Types

(Table 1-JEDEC Standard No. 7A)

				Tem	peratur	ө°С								
Symb	Parameter	Vcc	54HC/ 2		74 – 40	HC to 85	541 55 1	HC to 125	U n i	Test Conditions				
		v	min	max	min	max	min	max	t					
VIH	High Level	2.0	1.5		1.5		1.5		v					
	Input Voltage	4.5	3.15		3.15		3.15		v					
		6.0	4.2		4.2		4.2		٧					
VIL	Low Level	2.0		0.3		0.3		0.3	٧					
	Input Voltage	4.5		0.9		0.9		0.9	v					
		6.0		1.2		1.2		1.2	v					
										٧ _I	STD	I _O BUS	Unit	
VOH	High Level Output Voltage	2.0	1.9		1.9		1.9		٧		- 20.0	- 20.0	μΑ	
Note 1		4.5	4.4	1	4.4		4.4		v		- 20.0	- 20.0	μΑ	
Note		6.0	5.9	{	5.9		5.9		٧	V _{IH} or	- 20.0	- 20.0	μA	
		4.5	3.98		3.84		3.7		\ v	VIL	- 4.0	- 6.0	mA	
		6.0	5.48		5.34		5.2		٧		- 5.2	- 7.8	mA	
v_{OL}	Low Level Output Voltage	2.0		0.1		0.1		0.1	v		20.0	20.0	μА	
	Catput Voltage	4.5		0.1		0.1		0.1	v		20.0	20.0	μА	
	i	6.0		0.1		0.1		0.1	v	V _{IH} or	20.0	20.0	μΑ	
		4.5		0.26	}	0.33		0.4	v	VIL	4.0	6.0	mA	
		6.0		0.26		0.33		0.4	v		5.2	7.8	mA	
l _I Note 2	Input Leakage Current	6.0		± 0.1		± 1.0		± 1.0	μА	$V_I = V_{C_I}$	C or GND			
lOZ Note 3	3-state Output Off-State Current	6.0		±0.5		± 5.0		± 10.0	μА	$V_I = V_{IH}$ or V_{IL} $V_O = V_{CC}$ or GND				
lcc	Quiescent Supply Current									,, ,,	01/5			
	ssı	6.0		2.0		20.0		40.0	μА	\ \1 = \C	C or GND			
	FF	6.0		4.0		40.0		80.0	μА	10=0				
	мѕі	6.0		8.0		80.0		160.	μА					

Notes:

- Not applicable to open drain outputs.
 For digital I/O pins use I_{OZ} limits
- 3. Also applicable to open drain outputs.

Static Electrical Characteristics for CD74HCT/CD54HCT Types

(Table 2-JEDEC Standard No. 7A)

				Temp	eratur	в°С							
Symb	Parameter	vcc		7/74HCT 25		<u>HCT</u>) to 85	-	iHCT i to 125	U n i	Т	est Co	nditions	•
		v	min	max	min	max	min	max	t				
v _{IH}	High Level Input Voltage	4.5 to 5.5	2.0	·	2.0		2.0		\ v \				
, V _{IL}	Low Level Input Voltage	4.5 to 5.5		0.8		0.8		0.8	v				
										VI	STD	I _O BUS DRIVER	Unit
V _{OH} Note 1	High Level Output Voltage	4.5 4.5	4.4 3.98		4.4 3.84		4.4 3.7		v v	V _{IH} or V _{IL}	-20.0 -4.0	-20.0 -6.0	μA mA
V _{OL}	Low Level Output Voltage	4.5 4.5		0.1 0.26		0.1 0.33		0.1 0.4	v	V _{IH} or V _{IL}	20.0	20.0	μA mA
l _l Note 2	Input Leakage Current	5.5	,	± 0.1		± 1.0		± 1.0	μΑ	VI = VCC	or GNE)	
I _{OZ} Note 3	3-state Output Off-State Current	5.5		± 0.5		± 5.0		± 10.0	μΑ	V _I = V _{IH}		D	
ICC	Quiescent Supply Current												
	SSI	5.5		2.0		20.0		40.0	μА	$V_1 = V_{CC}$	or GNE)	
	FF	5.5		4.0		40.0		80.0	μА	$I_O = 0$			
	MSI	5.5		8.0		80.0		160.	μA				
Δlcc	Additional Worst Case Supply Current Note 4	5.5		2.7		2.9		3.0	mA	Per input-pir V _I = 2.4	n∙ Iii	other nputs: t V _{CC} or	

Notes:

- 1. Not applicable to open drain outputs.
- 2. For digital I/O pins use I_{OZ} limits
- 3. Also applicable to open drain outputs.
- 4. Total supply current = $I_{CC} + \Sigma \Delta I_{CC}$.

Dynamic Electrical Characteristics

Definitions

Characteristic	Symbol	Lin	nits	Notes	
	•	Max.	Min.		
Propagation Delay:					
Outputs going high to low	t _{PHL}	X			
Outputs going low to high	t _{PLH}) ×			
Output Transition Time: Outputs going high to low Outputs going low to high	t _{тнь} t _{тьн}	x x			
Pulse Width-Set, Reset, Preset Enable, Disable, Strobe, Clock	twL or twH		x	1	
Clock Input Frequency	f _{CL}	x		1,2	
Clock Input Rise and Fall Time	t_{rCL} , t_{rCL}	x			
Set-Up Time	t _{su}		X	1	
Hold Time	t _H		X	1	
Removal Time - Set, Reset, Preset-Enable	t _{REM}		X	1	
Three State Disable Delay Times: High level to high impedance High impedance to low level Low level to high impedance High impedance to high level	tpHz tpzL tpLz tpzH	X X X			

NOTE: (1) By placing a defining min. or max. in front of definition, the limits can change from min. to max., or vice versa.

(2) Clock input waveform should have a 50% duty cycle and be such as to cause the outputs to be switching from 10% Vcc to 90% Vcc in accordance with the device truth table.

OPERATING AND HANDLING CONSIDERATIONS

1. Handling

All inputs and outputs of RCA CMOS devices have a network for electrostatic protection during handling. Recommended handling practices for CMOS devices are described in ICAN-6525. "Guide to Better Handling and Operation of CMOS Integrated Circuits."

2. Operating

Operating Voltage

During operation near the maximum supply voltage limit, care should be taken to avoid or suppress power supply turn-on and turn-off transients, power supply ripple, or ground noise; any of these conditions must not cause V_{CC} — Gnd to exceed the absolute maximum rating.

Input Signals

To prevent damage to the input protection circuit, input signals should never be greater than $V_{\rm CC}$ nor less than Gnd. Input currents must not exceed 20 mA even when the power supply is off.

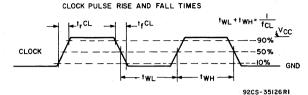
Unused Inputs

A connection must be provided at every input terminal. All unused input terminals must be connected to either V_{CC} or Gnd, whichever is appropriate.

Output Short Circuits

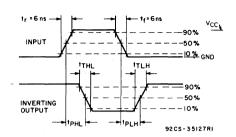
Shorting of outputs to V_{CC} or Gnd may damage CMOS devices by exceeding the maximum device dissipation.

Switching Waveforms for CD54/74HC and CD54/74HCU Integrated Circuits

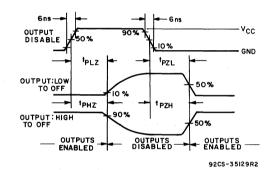


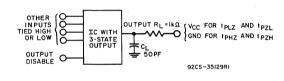
Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{max} , input duty cycle=50%.

Clock-pulse rise and fall times and pulse width.

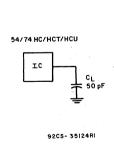


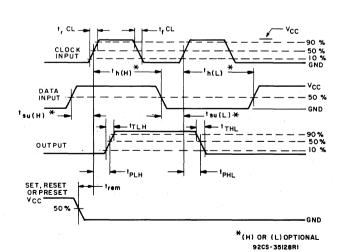
Transition times and propagation delay times, combination logic.





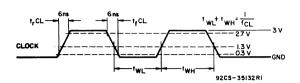
Three-state propagation delay wave shapes and test circuit.





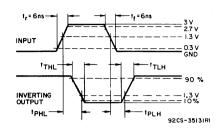
Setup times, hold times, removal time, and propagation delay times for edge triggered sequential logic circuits.

Switching Waveforms for CD54/74HCT Integrated Circuits

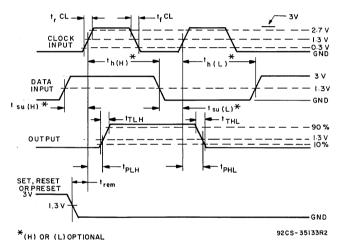


Outputs should be switching from 10% V_{CC} to 90% V_{CC} in accordance with device truth table. For f_{max} , input duty cycle=50%.

Clock-pulse rise and fall times and pulse width.



Transition times and propagation delay times, combination logic.



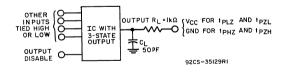
1C CL 50 pF

54/74 HC/HCT/HCU

Setup times, hold times, removal time, and propagation delay times for edge triggered sequential logic circuits.

6 ns OUTPUT 2.7 -1.3GND PLZ †PZL OUTPUT: LOW TO OFF 1.3 V 10% ^{- †}PHZ †PZH OUTPUT: HIGH OUTPUTS OUTPUTS OUTPUTS ENABLED ENABLED 92CS-35130R2

Three-state propagation delay wave shapes and test circuit.



Note:

Open drain waveforms t_{PLZ} and t_{PZL} are the same as those for three-state shown on the left. The test circuit is Output $R_L=1k\Omega$ to V_{CC} , $C_L=50$ pF.

Enhanced Product

The need to achieve the enhanced reliability resulting from burn-in screening must be determined by careful analysis of system design and application.

How many IC's are incorporated into the total system?

How many devices on each board?

Is the proper device being used for the application?

What are the reliability goals?

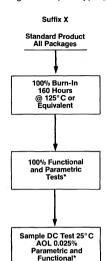
What failure rates are being experienced without screening?

Cost-effectiveness of using enhanced CMOS can be determined by mutual analysis of the economic trade-offs made possible by the following features of the program:

- Available in both plastic and frit-seal ceramic packages.
- Offered on the industry's broadest line of circuit functions.
- 0.025% AQL cumulative.
- Reduction in PC board reworking through fewer line rejects.
- Lower warranty requirements through the elimination of infant mortality failures.
- Reduced incoming inspection cost by reduction or complete elimination of test procedures.
- Reduction of system failures and related service expenses and customer complaints.

Screening

Digital IC's (CD Types)



"X" Product

*For the High-Speed CD54/74HC/HCT/HCU products. AC parameters are tested by selecting certain critical propagation delays (which vary from part to part) as indicators of proper AC performance and sample tested to an AQL of 0.025%.

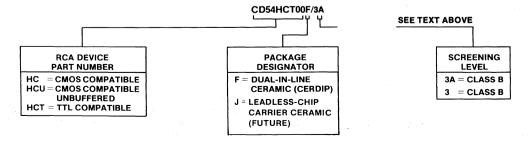
RCA MIL-STD-883 Slash-Series HC/HCT ICs

RCA high-reliability slash-series products are available in both CD54HCXXXX-series and CD54HCTXXXX-series types. These devices are supplied in hermetic dual-in-line frit packages. The CD54HC/HCT (Slash series) types are provided to screening level /3 that corresponds to MIL-STD-883, Method 5004, Class B requirements. This /3 is a non-compliant part using glass die attach. Product is also available as a level /3A which is a fully compliant part using gold eutectic die attach.

Detailed information pertaining to the screening performed can be found in the RCA "High-Reliability Integrated Circuits" DATABOOK, SSD-230B.

Contact your RCA representative for specific timing and availability.

Guide to the Reliability Class and Package of RCA High-Reliability 54HC/HCT Integrated Circuits





High-Speed CMOS (HC/HCT) Macro Cells for RCA Silicon Circuit Board ASIC Design Program

RCA offers a unified Computer-Aided Engineering (CAE) system that supports the high-speed CMOS (HC/HCT QMOS) library of standard logic functions defined as Macro Cells. The system provides not only automatic placement and routing but also the interactive editing of a mixture of CMOS standard cells and rectangular Macro Cells of different sizes.

The HC/HCT Macro Cells are equivalent in performance to the high-speed CMOS HC/HCT series of standard devices as specified in this DATABOOK; only the bond pads have been removed and large drivers down-sized. The Macro Cells are fully characterized and behaviorally described over the operating voltage and temperature ranges. These capabilities provide the system designer a fast, predictable, integration path from a PC board designed with high-speed CMOS or LSTTL, SSI/MSI discrete devices to a single Application-Specific Integrated Circuit (ASIC) that meets all criteria for PC board design.

The Silicon Circuit Board approach to ASIC design is distinctive because it allows the system engineer to develop a circuit using large, predesigned, fully characterized Macros. The characterization data for these Macros provide the engineer with the performance information needed to evaluate the feasibility of differing design approaches quickly and efficiently. The Macros have been developed to provide the optimum performance available within a given technology and are guaranteed to meet these performance specifications over the stated voltage and temperature ranges. All HC/HCT logic functions specified in RCA's QMOS family are included in the Silicon Circuit Board family of logic Macro Cells.

Features of the RCA Silicon Circuit Board and Related User Benefits.

Features:

- Works with 137 high-speed CMOS (QMOS-HC/HCT) standard logic Macro Cells
- Also works with RCA's new ACL standard part Macro Cells
- Intermixes Macros and standard logic function elements providing high-density designs
- Uses double-level metal technology with a polysilicon level option
- Uses fully characterized Macro Cells behaviorally described over the operating voltage and temperature ranges
- Provides simulation based on performance of characterized parts
- Provides fully automatic placement and routing plus interactive editing
- Provides automatic generation of test patterns for use in manufacture
- Integrates with RCA Semicustom FASTRACK system for Standard Cells and Gate Arrays

Renefits:

- Provides high probability of first-time success
- Reduces design development time
- Converts existing HCMOS/TTL boards to CMOS ASICs
- · Reduces simulation costs
- · Reduces parts costs
- Logic speed increase to x3 or more with high-speed process and ACL Macro Cells

How to Benefit from the RCA Modular Approach to CMOS ASIC Design and Fabrication

The RCA Silicon Circuit Board addresses the most difficult areas in the development of ASICs. These areas are performance, development time, and costs. If the following questions are part of your work assignment in the design of Application-Specific Integrated Circuits, the answers given here will be of significant interest to you.

1. Will the RCA ASIC approach work in my design?

The advantages of the RCA Silicon Circuit Board approach in a specific application can best be determined by a nocost consultation with our technical staff. We can help you make a reasoned decision whether the RCA modular approach will work in your design. And, if that is the route selected, we will help you save engineering development time and money by working with you on the entire program through to final manufacturing and performance tests.

2. How long will the design take?

The overall development time will be equal to or less than the time normally required for the development of SSI/MSI designs. The RCA Silicon Circuit Board achieves a shortened development time because it incorporates into a design a large number of cells containing from a handful to thousands of gates. Not only is the actual design time reduced, but simulation times also are substantially diminished by the utilization of behavioral modeling of these larger functional levels.

3. Will it work the first time?

The Silicon Circuit Board uses tried and tested high-speed CMOS cells that are fully characterized and behaviorally described. These cells have been developed to provide the optimum performance available within a given technology and are guaranteed to meet those performance specifications over the stated voltage and temperature ranges. Furthermore, RCA will provide any specialized support necessary to assure first-time success.

4. How much will it cost?

This program, involving newly available CAE software and a modular approach, can provide considerable cost savings (as much as 60%) in combined development and die costs. By providing a substantially more efficient methodology for ASIC design, RCA's Silicon Circuit Board greatly reduces engineering development costs. Additionally, the optimized layout of the Macro Cells provides for a significant reduction in the cost of manufacturing the ASIC chip.

How Do I Interface with RCA in Designing a Silicon Circuit Board?

The interface between the RCA Silicon Circuit Board Program and the customer's system engineer is very flexible and can be tailored to fit the specific needs, capabilities, and resources of the customer. Regardless of where the customer enters the system—and it can be anywhere in the flow of the program, as shown in the chart of Fig. 1—RCA will provide the support necessary to assure first-time success in the ASIC design. Following are examples of different interface choices.

One choice is to supply RCA with an SSI/MSI-level schematic, a description of how your circuit works, and timing information so that we can verify its operation in silicon and generate test programs. RCA will handle simulation, placement, routing, mask tooling, and prototype production.

Another choice is for your systems engineer to capture the schematic on a supported popular workstation using a generic SSI/MSI library. Supply RCA with a copy of the schematic, extracted net list, circuit description, and pattern files on magnetic tape or a floppy disk. RCA will then handle the rest.

A third choice is for your system engineer to do all the initial design work on RCA equipment at an RCA Design Center utilizing the assistance and guidance of an RCA applications engineer skilled in ASIC development. Again, RCA will handle the rest.

A fourth choice is for RCA to supply you with the RCA ASIC Design System software tools that will enable you to take your design through the layout step.

For more information on interfacing the RCA Silicon Circuit Board and on the additional benefits this advanced design technology can provide you, contact RCA ASIC Product Marketing at (201) 685-6585 or (201) 685-7119.

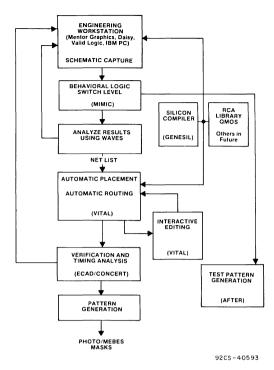
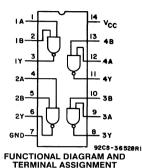


Fig. 1 — Flow Chart of RCA Silicon Circuit Board Design Process

Technical Data

High-Speed CMOS Logic



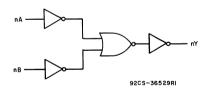
Quad 2-Input NAND Gate

Type Features:

- Buffered inputs
- Typical propagation delay = 7 ns @ V_{CC} = 5V C_L = 15 pF, T_A = 25 $^\circ$ C

The RCA-CD54/74HC00 and CD54/74HCT00 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC00 and CD54HCT00 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC00 and CD74HCT00 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



LOGIC DIAGRAM

Family Features:

- Fanout (Over Temperature Range):
 Standard Outputs 10 LSTTL Loads
 Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT/: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL}=30%, N_{IH}=30% of V_{CC} @ V_{CC}=5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL}=0.8 V Max., V_{IH}=2 V Min. CMOS Input Compatibility

 $I_1 \leq 1 \mu A @ V_{OL}, V_{OH}$

TRUTH TABLE

INP	UTS	OUTPUTS
nA	nB	nY
L	L	Н
L	Н	Н
Н	L	Н
Н	Н	L

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, $I_{i\kappa}$ (FOR $V_i < -0.5 \text{ V OR } V_i > V_{cc} + 0.5 \text{V}$)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5V)	
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V)	
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F. H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (T _{stg})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. \dots	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

CHARACTERISTIC	LIN	NITS	UNITS
CHARACTERISTIC	MIN.	MAX.	JUNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _{in} , V _{out}	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r ,t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD74	HC00.	/CD5	4HC00	0				CD74HCT00/CD54HCT00									
CHARACTERISTIC	TEST CONDITIONS			74HC/54HC 74HC TYPES TYPES			54HC TYPES		TEST CONDITIONS		1	CT/54 TYPES		74F		ı	ICT PES			
CHARACTERISTIC	V ₁ I _o		V _{cc}	+25°C		;	-40/ +85° C		-55/ +125°C		V,	V _{cc}	+25°		;	-40/ +85° C		-55/ +125° C		UNITS
	V	mA		Min	Тур	Max	Min	Max	Min	Max	1 1	Min	Тур	Max	Min	Max	Min	Max		
High-Level			2	1.5	-	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15		3.15	_	-	to	2	-	-	2	-	2	-	v
			6	4.2	_	-	4.2	_	4.2	-		5.5								
Low-Level			2	_	_	0.5	_	0.5		0.5		4.5								
Input Voltage V _{IL}			4.5		_	1.35	_	1.35	_	1.35	-	to	l – ,	-	0.8	-	0.8	-	0.8	V .
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	V _{1L}			-						
Output Voltage V _{он}	or	-0.02	4.5	4.4		_	4.4	_	4.4	_	or	4.5	4.4	_	-	4.4	_	4.4	-	v
CMOS Loads	V _{IH}	,	6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	VIL										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_		3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7		v
·	V _{IH}	-5.2	6	5.48	_	-	5.34	_	5.2	_	V _{IH}									
Low-Level	VIL		2	_	_	0.1	_	0.1	-	0.1	VIL									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1		0.1		0.1	V _{IH}									
	V_{IL}										V _{rL}									l i
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6		_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I	or		6	-	-	±0.1	-	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1		±1	μΑ
	Gnd				L_						& Gnd									
Quiescent	V _{cc}	}									Vcc									
Device	or	0	6	-	-	2	-	20	-	40	or	5.5	-	-	2	-	20	-	40	μΑ
Current I _{cc}	Gnd				<u></u>						Gnd -						-		_	
Additional Quiescent Device Current per input pin:											V _{cc} -2.1	4.5 to 5.5	-	100	360		450	-	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
nA	1.8
nB	1.1

*Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$, Input t_r , $t_t = 6 \text{ ns}$)

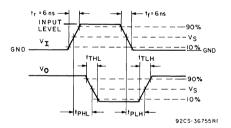
CHARACTERICTIC	CVMPOL	Tyl	pical	Units
CHARACTERISTIC	SYMBOL	HC HCT		Units
Propagation Delay, Data Input to Output Y (Fig. 1) (C _L =15 pf)	t _{PLH} t _{PHL}	7	8	ns
Power Dissipation Capacitance*	C _{PD}	25	25	pF

^{*} C_{PD} is used to determine the dynamic power consumption, per gate. PD = V_{cc}^2 fi $(C_{PD} + C_L)$ where f,=input frequency

C_L = output load capacitance Vcc = supply voltage.

SWITCHING CHARACTERISTICS (C, =50 pF, Input t, t,=6 ns)

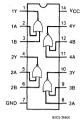
				25	°C		-4	0°C to	o +85°	C	-55				
CHARACTERISTIC	SYMBOL	Vcc	Vcc H		Н	HCT		74HC		74HCT		НС	54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.]
Propagation Delay	t _{PLH}	2	_	90	_	_	_	115		_	_	135	_	_	
Input to Output	t _{PHL}	4.5	<u> </u>	18	l —	20	-	23		25	_	27	-	30	ns
(Figure 1)	}	6	<u> </u>	15		_	_	20				23		_	
Transition Times	t _{TLH}	2	_	75	_	_	_	95	Γ=	_	_	110	_	_	
(Figure 1)	t _{THL}	4.5	_	15	l —	15	_	19	-	19	-	22	_	22	ns
		6	—	13	l —		l –	16				19		_	
Input Capacitance	C,	_		10		10		10		10		10		10	pF



	54/74HC	54/74HCT
INPUT LEVEL	V _{cc}	3V
V _S	50% V _{CC}	1.3V

Fig. 1 - Transition times and propagation delay times.

High-Speed CMOS Logic



Quad 2-Input NOR Gate

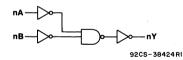
Type Features:

- Buffered Inputs
- Typical Propagation Delay = 7ns @ V_{CC} = 5v, C_L= 15pF, T_A = 25° C

FUNCTIONAL DIAGRAM and TERMINAL ASSIGNMENT

The RCA-CD54/74HC02 and CD54/74HCT02 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The CD54/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC02 and CD54HCT02 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC02 and CD74HCT02 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



LOGIC DIAGRAM

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V ■ CD54HCT/CD74HCT Types:
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ Vo_L, V_{OH}

TRUTH TABLE								
nA	nB	nY						
L	L	Н						
L	Н	L						
Н	L	L						
Н	Н	L						

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, $I_{i\kappa}$ (FOR $V_i < -0.5$ V OR $V_i > V_{cc} + 0.5$ V)	±20mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V)	±25mA
DC Vcc OR GROUND CURRENT (Icc)	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mV
For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mV
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	-40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

CHARACTERISTIC	LIN	LIMITS				
CHARACTERISTIC	MIN.	MAX.	UNITS			
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*						
CD54/74HC Types	2	6	V			
CD54/74HCT Types	4.5	5.5	V			
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V			
Operating Temperature T _A :						
CD74 Types	-40	+85	°c			
CD54 Types	-55	+125				
Input Rise and Fall Times t _r , t _f						
at 2 V	0	1000				
at 4.5 V	0	500	ns			
at 6 V	0	400				

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		CD74	HC02/	CD54	4HC0:	2				CD74HCT02/CD54HCT02										
			ı									1		74HCT SERIES		54HCT SERIES		UNITS		
V ,	I₀ m∆	V _{cc}	•	+25° C	;			l		V,				+25° C	;					UNITS
			Min	Тур	Max	Min	Max	Min	Max	'	ľ	Min	Тур	Max	Min	Max	Min	Max		
		2	1.5	_	_	1.5	_	1.5	_		4.5									
		4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	-	2	-	2	-	v	
		6	4.2	_		4.2	_	4.2	_		5.5				ĺ					
		2		_	0.5	_	0.5	_	0.5		4.5									
		4.5		_	1.35		1.35	_	1.35	_	to	-	-	0.8	-	0.8	-	0.8	v	
		6	_	_	1.8		1.8	_	1.8		5.5									
V _{IL}		2	1.9	_	_	1.9	_	1.9	_	VIL										
or	-0.02	4.5	4.4	_		4.4	_	4.4	_	or	4.5	4.4	-	_	4.4	-	4.4	-	v	
V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}										
V _{IL}										V _{IL}	į									
or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v	
V _{IH}	-5.2	6	5.48	_	<u>-</u>	5.34	_	5.2	_	V _{IH}								ļ		
V _{IL}		2	_	_	0.1	_	0.1		0.1	V _{IL}										
or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v	
V _{IH}		6	_	_	0.1	_	0.1	-	0.1	V _{IH}										
VIL										V _{IL}		Ì								
or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v	
V _{IH}	5.2	6	_	_	0.26	_	0.33		0.4	V _{IH}										
V _{cc}										Any										
or		6	-	-	±0.1	-	±1	-	±1	Between	5.5	-	_	±0.1	_	±1	-	±1	μΑ	
Gnd										& Gnd										
V _{cc}										Vcc										
or	0	6	-	_	2		20	_	40	or	5.5	-	_	2	_	20	-	40	μΑ	
Gnd									<u> </u>	Gnd	<u> </u>			<u> </u>				<u></u>		
										V _{cc} -2.1	4.5 to	_	100	360	_	450	_	490	μΑ	
	V _I , V V _{IL} or V _{IH} V _{IL} or V _{IH} V _{IL} or V _{IH} V _{IC} or V _{IH} V _{IC} or Cand V _{CC} or	Vi	TEST CONDITIONS V ₁ l ₀ V _{cc} V A 5 6 2 4.5 6 V _{1t} 2 0 4.5 6 V _{1t} 0 -0.02 4.5 6 V _{1t} 0 -5.2 6 V _{1t} 0 -5.2 6 V _{1t} 0 6	TEST CONDITIONS Vi lo MA Vcc V Min 2 1.5 4.5 3.15 6 4.2 2 4.5 6 Vil 2 1.9 or -0.02 4.5 4.4 6 5.9 Vil 3.98 Vil 4.5 Vil 3.98 Vil 3.98 Vil 4.5 Vil 4	TEST CONDITIONS V ₁ V MIn Typ 2 1.5 — 4.5 3.15 — 6 4.2 — 4.5 — 4.5 — 4.5 — 7 4 4.5 — 7 5.2 — 7 6 —	TEST CONDITIONS V, Io MA Vcc V Min Typ Max 2 1.5 — — 4.5 3.15 — — 6 4.2 — — 2 1.5 — — 1.35 6 — — 1.35 6 — — 1.8 V _{IL} or —0.02 4.5 4.4 — — V _{IL} or —4 4.5 3.98 — — OLD V _{IL} or —4 4.5 3.98 — — V _{IL} or —4 4.5 3.98 — — OLD V _{IL} or —4 4.5 3.98 — — OLD V _{IL} or —6 5.2 6 5.48 — — OLD V _{IL} or —7 0.1 V _{IL} or —8 0.1 V _{IL} or —9 0.1 OLD V _{IL} or —9 0.26 V _{IL} or —9 0.26 V _{IL} or —9 0.1 Gnd V _{IL} OR OR OR OR OR OR OR OR OR O	V₁ V₁ NA I₀ MA Vcc V +25° C -485 Min V₁ NIM	TEST CONDITIONS V, Voc MIN Typ Max MIN Max 2 1.5 1.5 1.5 4.2 4.5 1.35 1.35 1.35 1.35 1.35 - 1.35	TEST CONDITIONS V ₁ V NA V ₂ V NA V ₃ V ₄ V NA V ₄ V NA V ₄ V ₄ NA V ₄ V ₄ NA TEST CONDITIONS T4HC/54HC SERIES SERIES SERIES SERIES SERIES SERIES SERIES	TEST CONDITIONS 74HC/54HC SERIES SAHC SERIES CONDITIONS SERIES SERIES CONDITIONS Test Conditions Te	TEST CONDITIONS V_i	TEST CONDITIONS 74HC/54HC SERIES 74HC SERIES 74BC SERI	TEST CONDITIONS 74HC/54HC SERIES SERIES SERIES SERIES SERIES TAHCT/54 SERIES TOMITOM TOM TOM TOM TOM TOM TOM TOM TOM TOM	TEST CONDITIONS Table 10 Series Table 20 Ser	TEST CONDITIONS T4HC/54HC SERIES SERIES SERIES SERIES SERIES SERIES SERIES SERIES SERIES T4HC7/54HCT SERIES T4HC7/5	Test Conditions	TEST CONDITIONS 74HC/54HC SERIES SERIES SERIES SERIES SERIES SERIES SERIES SERIES SERIES TANCT/54HCT SERIES TANCT/54HCT SERIES SERIES TANCT/54HCT SERIES SERIES SERIES TANCT/54HCT SERIES SERIES SERIES TANCT/54HCT SERIES SERIES SERIES SERIES SERIES SERIES TANCT/54HCT SERIES SERIES SERIES SERIES SERIES SERIES SERIES TANCT/54HCT SERIES SERIES SERIES SERIES SERIES TANCT/54HCT SERIES SERIES SERIES SERIES SERIES SERIES SERIES SERIES SERIES TANCT/54HCT SERIES TANCT/54HCT SERIES SERIES SERIES SERIES SERIES TANCT/54HCT SERIES SERIES SERIES SERIES SERIES SERIES SERIES TANCT/54HCT SERIES SER	TEST CONDITIONS TAHC/SHC SERIES TAHC/S		

^{*}For dual-supply systems theoretical worst case (V_i = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
All	1.5

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

CHARACTERISTIC		SYMBOL	TYP	CAL	UNITS	
CHARACTERISTIC	(pF)	STWIBOL	HC	HCT	ONITS	
Propagation Delay, Data Input to Output Y (Fig. 1)	15	t _{PLH} t _{PHL}	7	8	ns	
Power Dissipation Capacitance*	-	C _{PD}	26	26	pF	

^{*}CPD is used to determine the dynamic power consumption, per gate.

 $PD = V_{CC}^2 f_i (C_{PD} + C_L)$

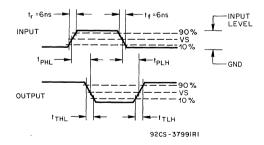
f, = input frequency

C_L = output load capacitance

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (CL = 50 pF, Input tr, tr = 6 ns)

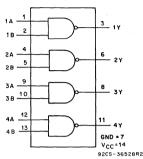
				25	°C		-4	0°C t	o +85°	C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	СТ	74	нс	741	ICT	54	нС	54H	ICT	UNITS
	i i		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	
Propagation Delay,	t _{PLH}	2		90		_		115		_		135			
Input to Output	t _{PHL}	4.5		18		21	Ì	23	}	26	ł	27	ļ	32	ns
(Fig. 1)	ĺ	6	Ì	15		—		20		l —		23		_	
Transition Times	t _{TLH}	2		75		_		95		T —		110		_	
(Fig. 1)	t _{THL}	4.5		15		15	İ	19		19	ĺ	22		22	ns
		6		13		_		16		_		19			
Input				10		10		10		10		10		10	pF
Capacitance	Cı			10		10		10		10		10		10	ρr



	•	
	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, Vs	50% V _{CC}	1.3 V

Fig. 1 - Transition times and propagation delay times.

High-Speed CMOS Logic



Quad 2-Input NAND Gate With Open Drain

Type Features:

- Buffered inputs
- Typical propagation delay = 8 ns @ Vcc = 5 V, CL = 15 pF, TA = 25° C
- Output pull-up to 10 V

FUNCTIONAL DIAGRAM

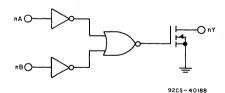
The RCA-CD54/74HC03 and CD54/74HCT03 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

These open-drain NAND gates can drive into resistive loads to output voltages as high as 10 V. Minimum values of R_L required vs. load voltage are shown in Fig. 2.

The CD54HC03 and CD54HCT03 are supplied in 14-lead dual-in-line frit-seal ceramic packages (F suffix). The CD74HC03 and CD74HCT03 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High noise immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- Of Vcc, @ Vcc = 5 V
 CD54HCT/CD74HCT Types:
 4.5 to 5.5 V Operation
 Direct LSTTL input logic compatibility
 V_{IL} = 0.8 V max., V_{IH} = 2 V Min.
 CMOS input compatibility
 I₁ ≤ 1 μA @ Vo_L, Vo_H



LOGIC DIAGRAM

TRUTH TABLE

A	В	١	,
L	L	Z #	н*
Н .	L	Z #	н*
L	• н	Z #	н*
н	н	ı	_

- * Requires pull-up (R_L to V_L)
- # Without pull-up (high impedance)

MAXIMUM RATINGS, Absolute-Maximum Values:

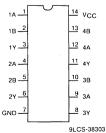
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5 \text{ V OR } V_i > V_{CC} + 0.5 \text{ V}$)	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V)	20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo)	25 mA
DC V _{cc} OR GROUND CURRENT (I _{cc})	±50 mA
POWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Lineary at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tatg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

	LIM		
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} : *			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input Voltage V ₁	0	V _{cc}	V
DC Load Voltage V _L	0	10 #	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _l			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*} Unless otherwise specified, all voltages are referenced to Ground.

[#] With pull-up resistor whose value limits output current to 25 mA.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

	_		CD74HC03/CD54HC03									CD74HCT03/CD54HCT03												
CHARACTERIS	TIC	TEST CONDITIONS		1 ' ''	74HC/54HC TYPES		' '	74HC TYPES		HC PES	TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS				
CHARACTERIS	110	v,	lo	V _{cc}		+25° C	;	-40/ +85° C		-55/ +125°C		V _I	Vcc		+25° C		-40/ +85° C		-55/ +125°C					
		V	mA	٧	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max				
High-Level				2	1.5	=	-	1.5	_	1.5	_		4.5											
Input Voltage	VIH			4.5	3.15	_	_	3.15		3.15	_	_	to	2	-	-	2	—	2	-	V			
				6	4.2	_	_	4.2	_	4.2	_		5.5				<u> </u>		_					
Low-Level				2			0.5		0.5	_	0.5		4.5] .					ļ	1				
Input Voltage	VIL			4.5			1.35	<u> </u>	1.35	_	1.35	_	to	-	-	0.8	-	0.8	-	0.8	V			
				6	<u> </u>	_	1.8	_	1.8	_	1.8		5.5		ļ	-		L	_	L_				
Low-Level		VIL	ļ	2	-	_	0.1	_	0.1	_	0.1	VIL		ļ										
Output Voltage	V_{OL}	or :	0.02	4.5	<u> </u>	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V			
CMOS Loads		V _{IH}		6	_	<u> </u>	0.1	_	0.1	_	0.1	V _{IH}	<u> </u>	<u> </u>	L		<u> </u>	<u> </u>		├				
		VIL		├	-	_		<u> </u>				VIL		1				l						
TTL Loads		or	4	4.5		<u> </u>	0.26	Ι=_	0.33	_	0.4	or	4.5	-	-	0.26		0.33	_	0.4	V			
		V _{IH}	5.2	6		_	0.26	<u> </u>	0.33	_	0.4	V _{IH}		<u> </u>	<u> </u>		<u> </u>	├	_	<u> </u>				
Input Leakage		Vcc		l								Any		l				l						
Current	h	or	l	6	l –	_	±0.1	_	±1	_	±1	Voltage	5.5		i —	±0.1	_	±1	l –	±1	μΑ			
		Gnd		}					1		l	Between		ł		ľ		1						
Quiescent		Vcc		-		-	-	-	 -	_	-	V _{cc} & Gnd V _{cc}	_	 -	├	-	 	\vdash	_					
Device Current	lcc	or	0	6			2		20		40	or	5.5	_	_	2		20	_	40	μΑ			
Device Current	ICC	Gnd	"	ľ	-	_		-	20	_	**	Gnd	3.5			* .	_	20	_	40	μΛ			
Additional		Gild	L		<u></u>	L	L	Щ.	Ь	Ь	Ь	Gild		-	\vdash	-	<u> </u>	+-	+	_				
Quiescent Device					* 1								4.5	İ		1	}	ļ						
Current per input												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ			
pin: 1 unit load	Δlcc*												5.5	1		ļ.			l					
Output Leakage			Vo=	ΤĖ	Γ	T	Г	Г	Г	Γ-		V _I = V _{IL}						†		1				
Current	loz		10 V				1					Vo = 10 V							1				1	
		VIL	thru	6	-	-	0.5	-	5	-	10	thru	5.5	-	-	0.5	-	5	-	10	μA			
			1 ΚΩ	1]	١.	1)	1 ΚΩ		1].	1] .				

^{*}For dual-supply systems theoretical worst case (V_{I} = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
nA, nB	# 1

^{*} Unit Load is Δt_{cc} fimit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25°C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, \text{ Input } t_r, t_f = 6 \text{ ns}$)

			TYPICAL	VALUES	UNITS
CHARACTERISTIC		C∟ (pF)	нс	нст	UNITS
Propagation Delay, (Fig. 1)	t _{PZL} , t _{PLZ}	15	8	9	ns
Power Dissipation Capacitance *	CPD		6.4	9	pF

* C_{PD} is used to determine the dynamic power consumption, per gate.

 $P_D = C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 f_o) + \Sigma (V_L^2 / R_L)$ (Duty Factor "Low")

where fi = input frequency

Duty factor "low" = percent of time output is "low" V_L = output voltage

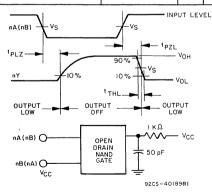
fo = output frequency C_L = output load capacitance

V_{cc} = supply voltage

R_L = pull-up resistor

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

		LIMITS												
011404075010710	TEST		25	°C		-4	0°C to	+85°	,c	-55	5°C to	+125	°C	LINUTO
CHARACTERISTIC	CONDITIONS	н	С	н	СТ	74	нс	74F	ICT	541	нс	54H	НСТ	UNITS
	V _{cc}	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay t _{PLZ} Output Low to t _{PZL} High Impedance and High Impedance to Output Low	2 4.5 6		100 20 17		 24 		125 25 21		_ 30 _	_ _ _	150 30 26		_ 36 _	ns
Transition Times t _{THL} (Figure 1)	2 4.5 6		75 15 13		_ 15 _	_	95 19 16	_ _ _	— 19 —	_	110 22 19	_ _ _	_ 22 _	ns
Input Capacitance C _I		_	10	_	10	_	10	_	10	_	10	_	10	pF



	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

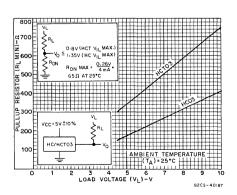
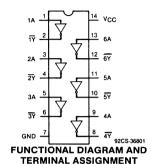


Fig. 2 - Minimum resistive load vs load voltage.

High-Speed CMOS Logic



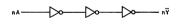
Hex Inverter

Type Features:

- Input and Output are both buffered
- Typical propagation delay = 6 ns @ V_{CC} = 5V, C_L = 15 pF, T_A = 25° C

The RCA-CD54/74HC04 and CD54/74HCT04 hex inverter utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC04 and CD54HCT04 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC04 and CD74HCT04 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



92CS-36947RI

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: NIL = 30%, NIH = 30% of VCC; @ VCC = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility VIL = 0.8 V Max., VIH = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ Vol. Vol.

LOGIC DIAGRAM

TRUTH TABLE

INPUTS	OUTPUTS
nA	nY ,
L	Н
Н	L

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, I_{iK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)	
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I_o) (FOR -0.5 V $<$ V $_o$ $<$ V $_c$ + 0.5V)	
DC V _{cc} OR GROUND CURRENT (I _{cc})	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	-40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79 \text{ mm})$ from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C
3 ,	

RECOMMENDED OPERATING CONDITIONS:

	LIN	MITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range (For TA = Full Package Range) Vcc:*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage VIN, VOUT	0	Vcc	V
Operating Temperature TA:			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, tr, tf			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

, '		(CD74F	1C04/	CD54	HC04						Ci	D74H0	CT04/	CD54	нсто	14			
CHARACTERISTIC	l	TEST CONDITIONS		74HC/54HC 74HC 54H TYPES TYPES TYP						TEST		CT/54 TYPES		1	ICT PES	54HCT TYPES		UNITS		
CHARACTERISTIC	V,	I _o	V _{cc}		+25° C		-4 +85		-5 +12		V,	V, V _{cc}		+25° C	;	-40/ +85° C				UNITS
		liiA.	ľ	Min	Тур	Max	Min	Max	Min	Max	ľ	•	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	-	2	-	2	-	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	-	_	0.5	_	0.5	-	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	-	1.35	_	1.35	_	to	-	-	0.8	-	0.8	-	0.8	v
			6	_	_	1.8	-	1.8	_	1.8	}	5.5								
High-Level	V _{IL}		2	1.9	_	-	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	-	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{1H}									
	VıL										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2		V _{IH}									
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage V _{OL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v
CMOS Loads	VIH		6	_	_	0.1	-	0.1	_	0.1	V _{IH}									
	VIL										V _{IL}				İ					
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I,	or		6	-	_	±0.1	-	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										& Gnd								<u> </u>	
Quiescent	V _{cc}										Vcc									
Device	or	0	6	-	-	2	-	20	-	40	or Gnd	5.5	-	-	2	-	20	-	40	μА
Current I _{cc}	Gnd										Gila									
Additional Quiescent Device Current per input pin: 1 unit load Δ lcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	-	490	μА

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
ALL	1.2

^{*}Unit Load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r, t_f = 6 ns)

		Tyl	pical	Units
CHARACTERISTIC		нс	HCT	Units
Propagation Delay, Data Input to Output Y (Fig. 1) (C _L = 15 pF)	t _{PLH} t _{PHL}	6	7	ns
Power Dissipation Capacitance*	C _{PD}	21	24	pF

*CPDI is used to determine the dynamic power consumption, per inverter where:

PD = VCc2f (CPD + CL) where f = input frequency

CL = output load capacitance

Vcc = supply voltage

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_f = 6 \text{ ns}$)

			LIMITS														
		TEST		25	°C		-	40°C t	o +85°	С		55°C to	+125°	С			
CHARACTERISTIC	3	CONDITION	Н	С	н	СТ	74	нс	74F	ICT	54	нс	541	ICT	UNITS		
		v _{cc} v	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.			
Propagation Delay	t _{PLH}	2	_	85	_	_	_	105	_	_	_	130	_				
Input to Output	t _{PHL}	4.5	_	17	_	19	_	21	-	24	_	26		29	ns		
(Fig. 1)		6	_	14		_		18		_	_	22					
Transition Times	t _{TLH}	2	_	75	_	_	-	95	_	_	_	110	_	_			
(Fig. 1)	t _{THL}	4.5	_	15	_	15	-	19	—	19	_	22	-	22	ns		
		6		13				16	_		_	19					
Input Capacitance	Cı		-	10	-	10	_	10	-	.10	-	10	-	10	pF		

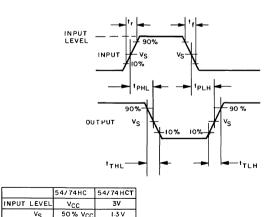
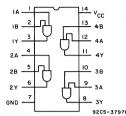


Fig. 1 - Transition times and propagation delay times.

92CS - 36948RI

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

Quad 2-Input AND Gate

Type Features:

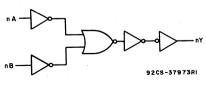
- Buffered inputs
- Typical CD54/74HC08 propagation delay=7 ns @ V_{CC}=5 V, C_L=15 pF, T_A=25° C

The RCA-CD54/74HC08 and CD54/74HCT08 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC08 and CD54HCT08 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC08 and CD74HCT08 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic package (M suffix). Both types are also available in chip form (H suffix).

LOGIC DIAGRAMS

CD54/74HC08



CD54/74HCT08

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation

High Noise Immunity: N_{IL}=30%, N_{IH}=30% of V_{CC} @ V_{CC}=5 V

■ CD54HCT/CD74HCT Types:

4.5 to 5.5 V Operation

Direct LSTTL Input Logic Compatibility

V_{IL}=0.8 V Max., V_{IH}=2 V Min.

CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \, @ \, V_{OL}, \, V_{OH}$

TRUTH TABLE

INP	UTS	OUTPUTS
nA	nB	nY
L	L	L
L	н	L
Н	L	L
н	Н	Н

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V	/)±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Voc + 0.5 V)
DC Vcc OR GROUND CURRENT (Icc):	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (T _{sto})	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

CHARACTERISTIC	LIN	NITS	UNITS	
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A =Full Package-Temperature Range) V _{cc} :*				
CD54/74HC Types	2	6	V	
CD54/74HCT Types	4.5	5.5	\ \ \	
DC Input or Output Voltage V _I , V _O	0	Vcc	V	
Operating Temperature T _A :				
CD74 Types	-40	+85	°c	
CD54 Types	-55	+125		
Input Rise and Fall Times t _r ,t _f				
at 2 V	0	1000		
at 4.5 V	0	500	ns	
at 6 V	0	400		

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD74	HC08.	CD5	HC0	3					С	D74H	CT08	/CD54	4НСТ	08			
CHARACTERISTIC	ſ	TEST CONDITIONS				74HC/54HC TYPES				HC PES	TEST CONDITIONS			CT/54		74HCT TYPES		1	ICT PES	UNITS
	V ₁ I ₀ V mA		V _{cc}		+25°C			-40/ +85° C		5/ 5° C	V,	V _{cc}	V _{cc}		+25° C		0/ 5° C	-55/ +125°C		Julia
				Min	Тур	Max	Min	Max	Min	Max			Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	-	1.5	-		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	_	_	2	_	2	-	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								}
Low-Level			2		_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	-	_	0.8	-	0.8	-	0.8	v
			6		_	1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_		1.9	_	1.9	_	VIL									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	V
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}	İ					Ì			
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48		_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	_	_	0.1		0.1	_	0.1	VIL									
Output Voltage Vol	or	0.02	4.5	_		0.1	_	0.1	_	0.1	or	4.5	-	_	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1		0.1	V _{IH}									
	V _{IL}										V _{IL}	ŀ								
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	_	0.4	v
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									-
Current I _I	or		6	-	-	±0.1	-	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd		<u> </u>	<u> </u>		_					& Gnd							_	_	
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	- 1	-	2	-	20	-	40	· or	5.5	-	-	2	-	20	-	40	μΑ
Current I _{cc}	Gnd					L	L		L	L	& Gnd								<u> </u>	
Additional Quiescent Device Current											V _{cc} -2.1	4.5 to	-	100	360	_	450	_	490	μА
per input pin: 1 unit load Δ l _{cc} *												5.5								

^{*}For dual-supply systems theoretical worst case (V_i = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
All	0.6

^{*}Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu \rm A$ max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

CHARACTERISTIC	SYMBOL	TYP	CAL	UNITS	
CHARACTERISTIC	STMBOL	нс	нст	014113	
Propagation Delay, Data Input to Output Y (Fig. 1) (C _L =15 pF)	t _{PLH} t _{PHL}	7	10	ns	
Power Dissipation Capacitance*	C _{PD}	37	51	pF	

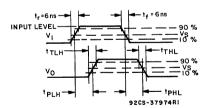
^{*}C_{PD} is used to determine the dynamic power consumption, per gate.

PD=Vcc² fi (C_{PD} + C_L) where f_i=input frequency

C_L=output load capacitance V_{CC}=supply voltage

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_f, t_f = 6 ns)

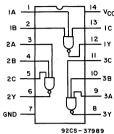
				25	°C		-4	0°C to	o +85°	,C	-55	°C to	+125	°C	
CHARACTERISTIC	SYMBOL	VCC	Н	HC		нст		74HC		74HCT		нс	54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Propagation Delay,	t _{PLH}	2		90		_		115				135		l —	
Input to Output	t _{PHL}	4.5	ľ	18		25		23		31		27		38	ns
(Fig. 1)		6	Ì	25		_		20	ŀ	—		23		_	
Transition Times	t _{TLH}	2		75		_		95		_		110		—	
(Fig. 1)	t _{THL}	4.5		15		15		19		19		22		22	ns
		6	1	13		_		16		_		19		 	
Input		i												_	
Capacitance	Cı		1	10		10		10		10		10		10	pF
		l								1					



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

Fig. 1 - Transition times and propagation delay times.

High-Speed CMOS Logic



Triple 3-Input NAND Gate

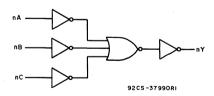
Type Features:

- Buffered inputs
- Typical propagation delay = 8 ns @ $V_{CC} = 5 \text{ V. } C_1 = 15 \text{ pF. } T_A = 25^{\circ} \text{ C}$

FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

The RCA-CD54/74HC10 and CD54/74HCT10 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC10 and CD54HCT10 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC10 and CD74HCT10 are supplied in 14-lead dualin-line plastic packages (E suffix) and in 14-lead dual-inline surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



LOGIC DIAGRAM

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85°C
- Balanced Propagation and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL}=30%, N_{IH}=30% of V_{CC}; @ V_{CC}=5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility VIL=0.8 V Max., VIH=2 V Min. **CMOS Input Compatibility**

 $I_1 \leq 1 \mu A @ V_{OL}, V_{OH}$

TRUTH TABLE

	INPUTS		OUTPUTS
nA	nB	nC	nY
L	L	L	н
L	L	Н	Н
L	Н	L	Н
L	Н	Н	Н
Н	L	L	Н
Н	L	Н	Н
Н	Н	L	Н
Н	Н	Н	L

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} +0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc + 0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT (lcc):	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstq)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C

RECOMMENDED OPERATING CONDITIONS:

CHARACTERISTIC	LIN	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNIIS
Supply-Voltage Range (For T _A =Full Package-Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°c
CD54 Types	-55	+125	
Input Rise and Fall Times t _r ,t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD74	HC10,	CD5	#HC10)					С	D74H	CT10	/CD54	нст	10				
CHARACTERISTIC		TEST CONDITIONS				74HC/54HC TYPES				HC PES	TEST CONDITIONS		ł .	CT/54 FYPE		74HCT TYPES			ICT PES	UNITS	
	V,	I _o	V _{cc}		+25°C			-40/ +85° C		5/ 5°C	V, V	V _{cc}		+25° C		-40/ +85° C		-55/ +125°C		UNITS	
	·	•			Min	Тур	Max	Min	Max	Min	Max		•	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-	_	1.5	-	1.5	_	-	4.5									
Input Voltage V _{IH}			4.5	3.15	_		3.15	_	3.15	_	-	to	2	-	-	2	'	2	_	v	
			6	4.2	_	_	4.2	_	4.2			5.5									
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5									
Input Voltage $V_{\scriptscriptstyle R_L}$			4.5	_	_	1.35	_	1.35	_	1.35	-	to		-	0.8	-	0.8	-	0.8	v	
			6	_	_	1.8	_	1.8	_	1.8		5.5									
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	V _{IL}										
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	v	
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}										
	V _{IL}										VIL										
TTL Loads	or	-4	4.5	3.98		_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v	
·	V _{IH}	-5.2	6	5.48	_		5.34	_	5.2	_	V _{IH}										
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	ViL										
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v	
CMOS Loads	V _{IH}		6	_		0.1	_	0.1	_	0.1	V _{IH}										
	VIL										V _{IL}										
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	_	0.4	٧ ,	
	V _{IH}	5.2	6	_	_	0.26	_	0.33		0.4	V _{IH}				<u> </u>						
Input Leakage	V _{cc}										Any Voltage										
Current I,	or	'	6	-	-	±0.1	–	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ	
	Gnd										& Gnd	_									
Quiescent	V _{cc}										Vcc										
Device	or	0	6	-	-	2	-	20	_	40	or	5.5	-	-	2	-	20	-	40	μΑ	
Current I _{cc}	Gnd			<u> </u>		<u> </u>					Gnd	<u></u>				_					
Additional Quiescent												4.5									
Device Current per input pin: 1 unit load Δ lcc*											V _{cc} -2.1	to 5.5	-	100	360	_	450	-	490	μΑ	

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*					
All	0.6					

^{*}Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu{\rm A}$ max. @ 25°C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t, = 6 ns)

CHARACTERISTIC	SYMBOL	TYP	ICAL	UNITS	
CHARACTERISTIC	STMBOL	HC	нст	UNITS	
Propagation Delay, Data Input to Output Y (Fig. 1) (C _L =15 pF)	t _{РLН} t _{РНL}	8	9	ns	
Power Dissipation Capacitance*	СРО	24	28	pF	

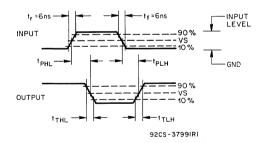
^{*}CPD is used to determine the dynamic power consumption, per gate.

 $PD=V_{CC}^{2}$ fi $(C_{PD}+C_{L})$ where fi=input frequency

C_L=output load capacitance V_{CC}=supply voltage

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_n, t_f = 6 ns)

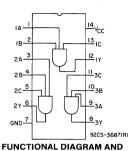
	SYMBOL	vcc	25° C				-40°C to +85°C				-55° C to +125° C				
CHARACTERISTIC			нс		нст		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	tpLH	2		100				125		— "		150		_	
Input to Output	t _{PHL}	4.5		20		24		25		30		30		36	ns
(Fig. 1)		6		17		—		21		_		26		_	
Transition Times (Fig. 1)		2		75		_		95		_		110		_	
	t _{TLH}	4.5	i	15		15		19		19		22		22	ns
	t _{THL}	6		13		—		16				19		_	
Input Capacitance	Cı			10		10		10		10		10		10	pF



	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

Fig. 1 - Transition times and propagation delay times.

High-Speed CMOS Logic



TERMINAL ASSIGNMENT

Triple 3-Input AND Gate

Type Features:

- Buffered inputs
- Typical propagation delay = 8 ns @ V_{CC} = 5 V, C_L = 15 pF,

The RCA-CD54/74HC11 and CD54/74HCT11 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC11 and CD54HCT11 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC11 and CD74HCT11 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-inline surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout [Over Temperature Range]: Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Phillips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL}=30%, N_{IH}=30% of V_{CC} @ V_{CC}=5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL}=0.8 V Max., V_{IH}=2 V Min. CMOS Input Compatibility I₁≤1 µA @ V_{OL}, V_{OH}

nA nB nY

92CS-3697IRI

LOGIC DIAGRAM

TRUTH TABLE

	INPUTS		OUTPUTS
nA	nB	nC	nY
L	L	L	L
L	L	Н	L
L	Н	L	L
L	Н	Н	L
Н	L	L	L
Н	L	Н	L
Н	Н	L	L
Н	Н	Н	Н

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground)0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR V_{I} <-0.5V or V_{i} > V_{ce} +0.5V)
DC OUTPUT CURRENT, I_{OK} (FOR $V_o < -0.5V$ OR $V_o > V_{cc} + 0.5V$)
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR $-0.5V < V_o < V_{cc} + 0.5V$)
DC V _{cc} OR GROUND CURRENT, (I _{cc}): ±50 mA
POWER DISSIPATION PER PACKAGE (PD):
For $T_A = -40$ to $+60$ °C (PACKAGE TYPE E)
For T _A = +60 to+85°C (PACKAGE TYPE E)
For $T_A = -55$ to $+100^{\circ}$ C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For T _A = -40 to +70° C (PACKAGE TYPE M)
For T _A = +70 to +125° C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H55 to +125° C
PACKAGE TYPE E, M40 to +85° C
STORAGE TEMPERATURE (T _{stg})65 to ±150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. $+265^{\circ}$ C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only+300° C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

QUADACTERISTIC	LIN	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _{in} , V _{out}	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		1	CD74HCT11/CD54HCT11																	
CHARACTERISTIC		TEST NDITIONS			IC/54		741 TYI	HC PES		54HC TEST 74HCT/54HCT 74HCT TYPES TYPES TYPES							UNITS			
	۷, ۷	I _o	V _{cc}		+25° C		-40/ +85° C		-55/ +125° C		v,	V _{cc}	+25° C		;	-40/ +85°C		-55/ +125°C		
	•		•	Min	Тур	Max	Min	Max	Min	Max		ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-	_	1.5	<u>-</u> .	1.5	-		4.5					-			
Input Voltage V _™			4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	_	-	2	_	2	_	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_		1.35	_	1.35	-	1.35	-	to	-	-	0.8	-	0.8	-	0.8	v
			6	_	_	1.8	_	1.8		1.8	-	5.5								
High-Level	V_{ν_L}		2	1.9	_	_	1.9	_	1.9	_	V _{IL}				ŀ					
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	V
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V_{IL}			ļ							V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}						ļ			
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage Vo.	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	٧
CMOS Loads	V _{IH}		6	-	_	0.1	_	0.1	_	0.1	V _{IH}		ļ							
	Vil		_	-							V _{IL}									
TTL Loads	or	4	4.5	ļ	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	l v
· · ·	V _{IH}	5.2	6	 -		0.26		0.33	_	0.4	V _{IH}		-				ļ			
Input Leakage	V _{cc}							-	-		Any Voltage									
Current I,	or		6	-	-	±0.1	-	±1	_	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd		-	_				_			& Gnd	<u> </u>		<u> </u>			_	_		
Quiescent	V _{cc}										. V _{cc}									
Device	or	0	6	-	_	2	-	20	-	40	or	5.5	-	-	2	-	20	_	40	μΑ
Current I _{cc}	Gnd	L		<u>L</u>	L				<u> </u>	<u></u>	& Gnd	<u> </u>	-			ļ	ļ			
Additional Quiescent Device Current per input pin: 1 unit load \(\Delta \) lcc*											V _{cc} -2.1	4.5 to 5.5	-	100	360	-	450		490	μА

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
ALL	0.50

^{*}Unit Load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, input t_r , $t_f = 6 \text{ ns}$)

				25	°C		-4	0°C to	o +85°	С	-5				
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	CT	74	нС	74H	ICT	54	нс	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}														
Input to Output		2	-	100		—	_	125	_	_	_	150	_	_	
(Fig. 1)	t _{PHL}	4.5	-	20		28	_	25	—	35	_	30	—	42	ns
		6	l –	17	_	_		21			_	26			
Transition Times	t _{TLH}	2	_	75	_	_	_	95	_	_	_	110	_	_	
(Fig. 1)	t _{THL}	4.5	_	15	-	15	—	19		19	-	22	_	22	ns
		6	-	13				16			_	19	_	_	
										_			_		
Input Capacitance	C,		-	10	—	10	—	10	l —	10	 	10	_	10	рF
							—			-	-	-			

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{ C}$, Input t_r , $t_i = 6 \text{ ns}$)

		Тур	ical	Units
CHARACTERISTIC	SYMBOL	HC	HCT	Units
Propagation Delay, Data Input to Output Y (Fig. 1) (C _L = 15 pF)	t _{PLH} t _{PHL}	8	11	ns
Power Dissipation Capacitance*	C _{PD}	26	28	pF

^{*}CPD is used to determine the dynamic power consumption, per gate.

 $PD = V_{CC}^2 f_i (C_{PD} + C_L)$ where $f_i = input$ frequency

c_L = output load capacitance

V_{cc} = supply voltage

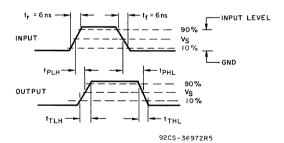
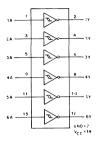


Fig. 1 — Transition times and propagation delay times.

	54/74HC	54/74HCT
INPUT LEVEL	v _{cc}	3V
V _S	50% V _{CC}	1.3V

High-Speed CMOS Logic



Hex Inverting Schmitt Trigger

Type Features:

- Unlimited input rise and fall times
- Exceptionally high noise immunity

FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

The RCA-CD54/74HC14 and CD54/74HCT14 each contain 6 inverting Schmitt Triggers in one package.

The CD54HC14 and CD54HCT14 are supplied in 14-lead ceramic dual-in-line packages (F suffix). The CD74HC14 and CD74HCT14 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both devices are also available in chip form (H suffix).

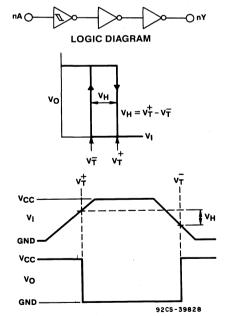


Fig. 1 - Hysteresis definition, characteristic, and test setup.

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity:

N_{IL} = 37%, N_{IH} = 51% of V_{CC}; @ V_{CC} = 5V ■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility $N_{\rm IL}$ = 18%, $N_{\rm IH}$ = 67% of $V_{\rm CC}$ @ $V_{\rm CC}$ = 4.5VCMOS Input Compatibility $I_1 \leq 1 \,\mu A \, @ \, V_{OL}, \, V_{OH}$

TRUTH TABLE

INPUT	OUTPUT
Α	Υ
L	Н
Н	L

H = High Level L = Low Level

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)	±20mA
DC OUTPUT DIODE CURRENT, IOK (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LII	MITS	LIMITO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{CC}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	Unlimited	ns
at 4.5 V	0	Unlimited	ns
at 6 V	0	Unlimited	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			•	CD74H	C14/CD	54HC1	4			CD74HCT14/CD54HCT14								
CHARACTERISTIC	со	TEST CONDITIONS			74HC/54HC TYPES		74HC TYPE		HC PE	TES ⁻ CONDIT		74HCT/ TYF		74HCT TYPE		54HCT TYPE		UNITS
	V _I	I _o mA	V _{cc}	+25	5°C			1	5/ 5°C	V, V	V _{cc}	+25	°C		0/ 5° C		5°C	
	Ť			Min	Max	Min	Max	Min	Max	'	•	Min	Max	Min	Max	Min	Max	
Input Switch			2	0.7	1.5	0.7	1.5	0.7	1.5			_	_	-	_	_	_	
Points V _T +			4.5	1.7	3.15	1.7	3.15	1.7	3.15		4.5	1.2	1.9	1.2	1.9	1.2	1.9	7 v
			6	2.1	4.2	2.1	4.2	2.1	4.2		5.5	1.4	2.1	1.4	2.1	1.4	2.1]
			2	0.3	1	0.3	1	0.3	1			_	_	_	_	_	_	
V _r -			4.5	0.9	2.2	0.9	2.2	0.9	2.2		4.5	0.5	1.2	0.5	1.2	0.5	1.2	v
			6	1.2	3	1.2	3	1.2	3	l ·	5.5	0.6	1.4	0.6	1.4	0.6	1.4]
			2	0.2	1	0.2	1	0.2	1			_	_	_	_		_	
V _H			4.5	0.4	1.4	0.4	1.4	0.4	1.4		4.5	0.4	1.4	0.4	1.4	0.4	1.4	v
			6	0.6	1.6	0.6	1.6	0.6	1.6		5.5	0.4	1.5	0.4	1:5	0.4	1.5	1
High-Level Output	V ₇ -		2	1.9	_	1.9	_	1.9	_	V ₁ -		-	_	_	_	_	_	
Voltage V _{он}	or	-0.02	4.5	4.4	-	4.4	_	4.4	_	or	4.5	4.4	-	4:4	_	4.4	-	v
CMOS Loads	V _T +		6	5.9	_	5.9	_	5.9	_	V _T +			_	_	_	_		
	V ₁ -		_	_	_	_	_	_	_	V _T -		_	_	_	_	_	-	
TTL Loads	or	-4	4.5	3.98	_	3.84	_	3.7		or	4.5	3.98	_	3.84	-	3.7	_	V
	V _T +	-5.2	6	5.48	_	5.34	_	5.2	_	V _T +		_	_	_	-	_	-	
Low-Level Output	V _τ -		2	_	0.1	_	0.1	_	0.1	V _T -		-	_	_	_	_	_	
Voltage V _{OL}	or	0.02	4.5	_	0.1		0.1	_	0.1	or	4.5	-	0.1	_	0.1	_	0.1	V
CMOS Loads	V _T +		6	_	0.1	_	0.1		0.1	V _T +		_		_	_	_		
	V _T -			_	_		_		_	V _T -		-	_	_	_	_	_	
TTL Loads	or	4	4.5	_	0.26	_	0.33	_	0.4	or	4.5	_	0.26		0.33		0.4	v
	V _T +	5.2	6	_	0.26	_	0.33	_	0.4	V _T +			_		_	_	_	
Input Leakage Current I	V _{cc} or Gnd		6	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	±0.1	_	±1	_	±1	μΑ
Quiescent	V _{cc}									V _{cc}								
Device	or	. 0	6	-	2	-	20	-	40	or	5.5		2	-	20	-	40,	μA
Current I _{cc}	Gnd									Gnd								
Additional Quiescent Device Current			•	•	•	•	•			V _{cc} -2.1	4.5 to		/p Max 00 360	-	450	_	490	μΑ
per input pin: 1 unit load Δl_{cc} *											5.5							

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS*
nA	0.6

^{*}Unit load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERISTIC	CL (pF)	TYP HC	ICAL HCT	UNITS
Propagation Delay, A to Y t_{PHL} , t_{PLH}	15	11	16	ns
Power Dissipation Capacitance* C _{PD}		20	20	pF

^{*} C_{PD} is used to determine the dynamic power consumption, per inverter. $P_D = V_{CC}^2 f_1 (C_{PD} + C_L)$ where: $f_1 = \text{input frequency}$ $C_L = \text{output load capacitance}$ $V_{CC} = \text{supply voltage}$

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_t = 6 \text{ ns}$)

				25	°C		-4	l0°C t	o +85°	С	-55° C to +125° C				
CHARACTERISTIC		Vcc	Н	C	Н	СТ	74	нс	74F	ICT	54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	·
Propagation Delay,	t _{PLH}	2		135	_	_	ļ —	170	_		_	205	_	_	
A to Y	t_{PHL}	4.5	_	27	_	38	_	34	 —	48	_	41		57	ns
		6	_	23		_		29		<u> </u>	-	35		<u> </u>	
Output	t _{TLH}	2		75	_	_	_	95	_	_	_	110		_	
Transition Time	t_{THL}	4.5	_	15	l —	15	_	19	_	19	_	22	_	22	ns
		6	_	13	_	_	-	16	-	_	_	19	_	—	
Input	C ₁		_	10	_	10		10		10		10	_	10	pF
Capacitance			1	•			1			1		[]	ĺ	1	

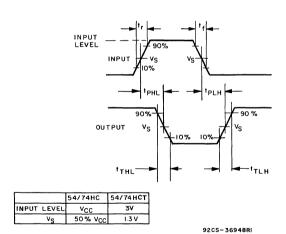
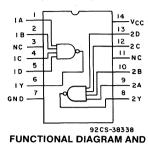


Fig. 2 - Transition times and propagation delay times.

High-Speed CMOS Logic



TERMINAL ASSIGNMENT

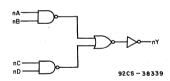
Dual 4-Input NAND Gate

Type Features:

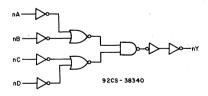
- Buffered inputs (HCT types)
- Typical propogation delay=8 ns @ V_{CC}=5V, C_L=15 pF, T_A=25°C (HC types)

The RCA-CD54/74HC20 and CD54/74HC720 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC20 and CD54HCT20 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC20 and CD74HCT20 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-inline surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



HC LOGIC DIAGRAM (1 GATE)



HCT LOGIC DIAGRAM (1 GATE)

Family Features

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity:

 $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5V$

■ CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL} = 0.8 V max., V_{IH} = 2 V min. CMOS input compatibility I₁ ≤ 1 µA @ V_{OL} V_{OH}

TRUTH TABLE

	INP	JTS	OUTPUTS	
nA	nB	nC	nD	nΥ
L	X	Х	X	Н
Х	L	Х	Х	Н
х	Х	L	X	Н
х	Х	Х	L	Н
Н	Н	Н	Н	L

X = Don't Care

L = Low Voltage Level H = High Voltage Level

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V _{cc}):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{1K} (FOR $V_1 \! < \! -0.5 \ V$ OR $V_1 \! > \! V_{CC} + \! 0.5 \ V)$	± 20 mA
DC OUTPUT CURRENT, I_{OK} (FOR V_{O} $<$ -0.5 V OR V_{O} $>$ V_{CC} +0.5 V)	
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Vo $<$ Voc +0.5 V)	± 25 mA
DC V _{cc} OR GROUND CURRENT (I _{cc})	± 50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For $T_A = -40$ to $+60$ °C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For $T_A = -55$ to $+100$ °C (PACKAGE TYPE F, H)	500 mW
For $T_A = +100$ to $+125$ °C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (T _{stg})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder con	ntacting lead tips only+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN	IITS		
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*				
CD54/74HC Types	2	6	,,	
CD54/74HCT Types	4.5	5.5	V	
DC Input or Output Voltage V _I , V _O	0	V _{cc}	٧.	
Operating Temperature T _A :				
CD74 Types	-40	+85		
CD54 Types	-55	+125	°C	
Input Rise and Fall Times, t _r , t _f				
at 2V	0	1000		
at 4.5 V	0	500	ns	
at 6V	0	400	-	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD74HC20/CD54HC20											CD	74HC	T20/C	D54F	ICT2)		
CHARACTERISTIC		COI	TEST CONDITIONS			74HC/54HC TYPE		i	i i		HC PE			74HCT/54HCT			l .	ICT PE		ICT PE	
CHARACTERIS	TIC	V _i	I _O	V _{cc}		+25°0	:	1	10/ 5°C	-5 +12	5/ 5°C	V _i	Vcc		+25°0	;		10/ 5°C		i5/ !5°C	UNITS
		ľ		ľ	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	V _{IH}			4.5	3.15	_	_	3.15	_	3.15	1		to	2	_	_	2	_	2	_	V
				6	4.2	_	_	4.2	_	4.2	-		5.5								
Low-Level				2	_	_	0.5	-	0.5	_	0.5		4.5								
Input Voltage	VIL			4.5	_	_	1.35		1.35	_	1.35	_	to	_	_	0.8	_	0.8	_	0.8	٧
				6	_	_	1.8		1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VıL									
Output Voltage	Vон	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4		٧
CMOS Loads		Vıн		6	5.9	_	_	5.9	_	5.9	_	VIH									
		VıL										VıL									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	-	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v
		V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	-	V _{IH}									
Low-Level		VIL		2	_	_	0.1	_	0.1	_	0.1	VıL									
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	<u> </u>	0.1		0.1	or	4.5		_	0.1	_	0.1	-	0.1	v
CMOS Loads		V _{IH}		6	_	_	0.1	_	0.1	_	0.1	VIH									
		VIL										VıL									
TTL Loads		or	4	4.5	_		0.26	_	0.33		0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v
		V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage		Vcc										Any Voltage									
Current	, li	or		6	_	_	±0.1	_	±1	-	±1	Between Vcc	5.5	_	_	±0.1	_	±1	_	±1	μΑ
		Gnd					L					& Gnd									
Quiescent		Vcc										Vcc									
Device		or	0	6	_	_	2	_	20	-	40	or	5.5	_	_	2	_	20	-	40	μΑ
Current	Icc	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load \(\Delta \)lcc*		:										Vcc -2.1	4.5 to 5.5		100	360	-	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
All	0.15

^{*}Unit load is $\Delta l_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

QUADA OTERIOTIO	0,410.01	TYP	ICAL	
CHARACTERISTIC	SYMBOL	нс	нст	UNITS
Propagation Delay, Data Input to Output Y (Fig. 1) $(C_L = 15 \text{ pF})$	t _{PLH} t _{PHL}	8	11	ns
Power Dissipation Capacitance*	C _{PD}	26	38	pF

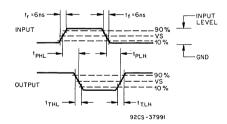
^{*}C_{PD} is used to determine the dynamic power consumption, per gate.

 $PD = V_{CC}^2$ fi $(C_{PD} + C_L)$ where $f_i = input$ frequency

 $C_L = \mbox{output load capacitance.}$ $V_{cc} = \mbox{supply voltage.}$

SWITCHING CHARACTERISTICS (CL = 50 pF, Input t, t = 6 ns)

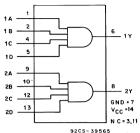
				25	°C		-4	0°C to	+85	°C	-55°C to +125°C				
CHARACTERISTIC	SYMBOL	Vcc	V _{cc} HC		С НС		CT 74		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	100	_	l —	_	125	_	_	_	150	_	_	
Input to Output	t _{PHL}	4.5	<u> </u>	20	_	28	_	25	_	35	_	30	_	42	ns
(Fig. 1)		6		17	_	l —	_	21	_	_	_	26		_	
Transition Times	tTLH	2	_	75	_	—	_	95	_	_	_	110	_	_	
(Fig. 1)	t _{THL}	4.5	-	15	_	15		19	-	19		22		22	ns
	Ì	6	—	13	<u> </u>		_	16	—	l —	 	19	l —	 —	
Input Capacitance	Cı	_	_	10	_	10	_	10	_	10	_	10	_	10	pF



	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _s	50% V _{cc}	1.3V

Fig. 1 — Transition times and propagation delay times.

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

Dual 4-Input AND Gate

Type Features:

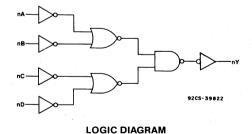
- Buffered inputs
- Typical propagation delay = 9ns @ V_{CC} = 5V, C_L = 15 pF, T_A = 25°C (HC types)

The RCA-CD54/74HC21 and CD54/74HC721 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC21 and CD54HCT21 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC21 and CD74HCT21 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation
 - High Noise Immunity:
 - $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5V$
- CD54HCT/CD74HCT Types:
 - 4.5 to 5.5 V Operation
 - Direct LSTTL Input Logic Compatibility
 - $V_{IL} = 0.8 \ V \ max., \ V_{IH} = 2 \ V \ Min.$
 - CMOS Input Compatibility
 - $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$



TRUTH TABLE

	INP	UTS		OUTPUTS
nA	nB	nC	nD	nΥ
L	Х	Х	X	to L
Х	L	Х	Х	L
Х	Х	L	Х	L
Х	Х	Х	L	L
Н	Н	Н	н	Н

- X = Don't Care
- L = Low Level Voltage
- H = High Level Voltage

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I_o) (FOR -0.5 V $<$ V $_o$ $<$ Vcc + 0.5V)	±25mA
DC Vcc OR GROUND CURRENT (Icc)	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	. Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	. Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tsig)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	LINUTC
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	l ∘c
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _t			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	ì

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD74	HC21/	CD54	1HC21	1	-				С	D74H	CT21/	CD54	нст	21			
CHARACTERISTIC		TEST IDITIONS			IC/54		l	HC PE	54I TY		TEST	ons	ı	74HCT/54HCT TYPES		74F TY	ICT PE	ı	ICT PE	UNITS
CHARACTERISTIC	V,	I _o mA	V _{cc}	-	+25° C	;	-4 +85		-5 +12!		V. V	V _{cc}		+25°C		1	0/ 5° C	-55, +125°		UNITS
		IIIA	"	Min	Тур	Max	Min	Max	Min	Max	V	•	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	-	_	3.15	_	3.15		_	to	2	-	-	2	-	2	-	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	-	_	1.35	_	1.35	_	1.35	-	to	-	_	0.8	-	0.8	-	8.0	v
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	-	4.4	-	4.4	-	V
CMOS Loads	V _{IH}		6	5.9	_	-	5.9	-	5.9		V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	-	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	-	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	-	_	0.1	_	0.1	_	0.1	V _{IH}								!	
	V _{IL}										V _{IL}									
TTL Loads	or	4	4.5	-	_	0.26	-	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6	_	_	0.26	-	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I,	or		6	-		±0.1	-	±1	-	±1	Between	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										V _{cc} & Grid									
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	2	-	20	-	40	or	5.5	-	-	2	-	20	-	40	μΑ
Current I _{cc}	Gnd					<u> </u>					Gnd									
Additional												4.5								
Quiescent Device Current											V _{cc} -2.1	to	_	100	360	-	450	-	490	μΑ
per input pin: 1 unit load Δlcc*												5.5								

^{*}For dual-supply systems theoretical worst case (V_{I} = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS*
ALL	1

^{*}Unit load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

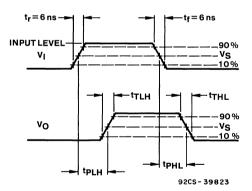
SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERICTIC	CL	TYP	ICAL	UNITS	
CHARACTERISTIC		(pF)	HC	HCT	UNITS
Propagation Delay, Data Input to Output Y (Fig. 1)	t _{PHL} , t _{PLH}	15	9	11	ns
Power Dissipation Capacitance*	C_{PD}	_	36	42	pF

 $^{^*}C_{PD}$ is used to determine the dynamic power consumption, per gate. $P_D = V_{CC}^{-2}f_1 (C_{PD} + C_L)$ where: f_1 = input frequency C_L = output load capacitance V_{CC} = supply voltage

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

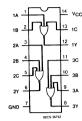
			25	°C		-4	l0° C t	o +85°	С	-5					
CHARACTERISTIC		Vcc	Н	IC	HC		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	—	110	_	_	<u> </u>	140	_	_	_	165	_		
Input to Output	t_{PHL}	4.5		22	_	27	_	28	_	34	_	33	_	41	ns
(Fig. 1)		6	_	19	—	l —	—	24	_	<u> </u>	—	28	_	—	
Transition Times	t _{TLH}	2	_	75	_	_	_	95	_	_	_	110		_	
(Fig. 1)	t_{THL}	4.5	<u> </u>	15	-	15	_	19	_	19	_	22	_	22	ns
		6	_	13	l —	_	_	16	—	<u> </u>	<u> </u>	19	-	_	
Input				10		10		10		10		10		10	~_
Capacitance	C ₁			10		10		10		10	_	10		10	pF



	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 1 — Transition times and propagation delay times.

High-Speed CMOS Logic



Triple 3-Input NOR Gate

Type Features:

- Buffered Inputs
- Typical CD54/74HC27 Propagation Delay = 7ns @ V_{CC} = 5v, C_L= 15pF, T_A = 25° C

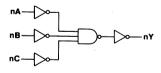
FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

The RCA-CD54/74HC27 and CD54/74HCT27 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The CD54/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC27 and CD54HCT27 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC27 and CD74HCT27 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-inline surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ Vou. VoH



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LOGIC DIAGRAM

L = Low Level

H = High Level

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground)0.5 to + 7 V
DC INPUT DIODE CURRENT, I _{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} +0.5$ V)
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC}$ +0.5V)
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Voc + 0.5V)
DC V _{cc} OR GROUND CURRENT (I _{cc}) ±50mA
POWER DISSIPATION PER PACKAGE (Po):
For T _A = -40 to +60° C (PACKAGE TYPE E)
For T _A = +60 to +85° C (PACKAGE TYPE E)
For T _A = -55 to +100° C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For T _A = -40 to +70° C (PACKAGE TYPE M)
For T _A = +70 to +125° C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H55 to +125° C
PACKAGE TYPE E, M40 to +85° C
STORAGE TEMPERATURE (T _{stg})
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. +265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only+300° C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	ITS	LINUTE
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage V _I , V _O	0	V _{cc}	· V
Operating Temperature T _A :			
CD74 Types	-40	+85	°c
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD74	HC27	/CD5	4HC2	7					С	D74H	CT27	/CD54	нст	27					
CHARACTERISTIC		TEST IDITIONS			HC/54			HC PE	54I TY	HC 'PE	TEST CONDITIO		I	74HCT/54HCT TYPES		1	HCT PE	54I TY	ICT PE			
CHARACTERISTIC	V,	l _o mA	V _{cc}		+25° (;		0/ 5°C		5/ 5°C	V,	V _{cc}		+25°C		+25° C			10/ 5° C	-55/ +125° C		UNITS
	,		•	Min	Тур	Max	Min	Max	Min	Max	'	ľ	Min	Тур	Max	Min	Max	Min	Max			
High-Level			2	1.5	-	_	1.5	-	1.5	-		4.5										
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	_	-	2	-	2	_	v		
			6	4.2	_	-	4.2	_	4.2	_	1	5.5										
Low-Level			2	-	_	0.5	_	0.5	_	0.5		4.5										
Input Voltage V _{IL}			4.5	-	_	1.35	_	1.35	_	1.35	_	to	-	_	0.8	-	0.8	_	0.8	v		
			6	_	_	1.8	-	1.8	_	1.8]	5.5				j)				
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	V _{IL}											
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	-	4.4	-	4.4	_	v		
CMOS Loads	V _{IH}		6	5.9	_	-	5.9	-	5.9	_	V _{IH}	Ì				ĺ						
	VIL										V _{IL}											
TTL Loads	or ,	4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	_	3.7	-	v		
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}											
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	V _{IL}											
Output Voltage V _{OL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V		
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}											
	V _{IL}										V _{IL}											
TTL Loads	or	4	4.5	-	_	0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	–	0.33	-	0.4	V		
	V _{IH}	5.2	6	-	_	0.26	_	0.33	_	0.4	V _{IH}].						
Input Leakage	V _{cc}										Any Voltage											
Current I	or		6	-	-	±0.1	-	±1	-	±1	Between	5.5	-	-	±0.1	ı.—	±1	- 1	±1	μΑ		
	Gnd										V _{cc} & Gnd											
Quiescent	V _{cc}										Vcc											
Device	or	0	6	-	-	2	-	20	–	40	or	5.5	-	-	2	-	20	-	40	μΑ		
Current I _{cc}	Gnd										Gnd											
Additional												4.5										
Quiescent Device Current per input pin: 1 unit load	·										V _{cc} -2.1	to 5.5	-	100	360	-	450	-	490	μΑ		

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
All	1.5

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERISTIC	CL	SYMBOL	TYP	ICAL	UNITS	
CHARACTERISTIC	(pF)	STWBOL	НС	нст	ONTIS	
Propagation Delay, Data Input to Output Y (Fig. 1)	15	t _{PLH} t _{PHL}	7	9	ns	
Power Dissipation Capacitance*	_	C _{PD}	26	28	pF	

^{*}CPD is used to determine the dynamic power consumption, per gate.

 $PD = V_{CC}^2 f_i (C_{PD} + C_L)$

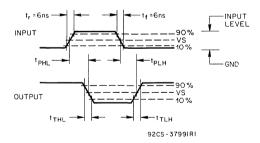
f, = input frequency

C_L = output load capacitance

Vcc = supply voltage

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_f, t_f = 6 ns)

				25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	H	СТ	74	нс	74H	ICT	54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2		95		_		120		—		145		_	
Input to Output	t _{PHL}	4.5		19	İ	23		24		29		29		35	ns
(Fig. 1)		6		16		_		20		_		25		_	
Transition Times	t _{TLH}	2		75		_		95		_		110		_	
(Fig. 1)	t _{THL}	4.5		15		15		19		19		22		22	ns
	1	6		13		-		16		—		19		—	
Input Capacitance	Cı		_	10		10		10		10		10		10	pF



	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, Vs	50% V _{CC}	1.3 V

Fig. 1 - Transition times and propagation delay times.

High-Speed CMOS Logic

Y = ABCDEFGH

8-Input NAND Gate

Type Features:

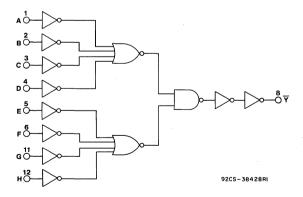
- Buffered inputs and outputs
- Typical propagation delay = 10 ns @ $V_{CC} = 5V$, $C_L = 15 pF$, $T_A = 25^{\circ}C$

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FUNCTIONAL DIAGRAM

The RCA-CD54/74HC30 and CD54/74HCT30 each contain an eight-input NAND gate in one package. They provide the system designer with the direct implementation of the positive logic 8-input NAND function.

The CD54HC/HCT30 are supplied in 14-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT30 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



LOGIC DIAGRAM

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:

2 to 6 V Operation High Noise Immunity:

 $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5 \ V$

■ CD54HCT/CD74HCT Types:

4.5 to 5.5 V Operation

Direct LSTTL Input Logic Compatibility $V_{\text{IL}} = 0.8 \text{ V Max.}, V_{\text{IH}} = 2 \text{ V Min.}$ CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$

	TRUTH TABLE								
		OUTPUT							
A	В	С	D	Е	F	G	Н	Ÿ	
L	Х	Х	Х	Х	Х	Х	Х	Н	
X	L	X	X	Х	X	Х	Х	Н	
X X X X	Х	L	Х	Х	X	Х	X) H	
X	Х	Х	L	X	X	Х	x	Н	
X	X	X	Х	L	Х	Х	X	H	
X	X	Х	Х	Х	L	Х	X	н	
X	Х	X	Х	Х	Х	L	Х	H	
X	X	X	X	X	X	X	L	H	
Н	Н	Н	Н	Н	Н	Н	Н	L	

- H = HIGH voltage level
- L = LOW voltage level
- X = Don't care

MAXIMUM RATINGS, Absolute-Maximum Values:

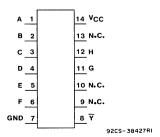
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_{\text{o}} <$ -0.5 V OR $V_{\text{o}} > V_{\text{CC}}$ +0.5V) $\ldots \ldots$	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	
PACKAGE TYPE E. M	
STORAGE TEMPERATURE (T _{stg})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. $$	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	LINITO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	0.0
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	i

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

		(CD74	HC30,	/CD5	4HC3)					c	D74H	CT30	/CD54	нст	30			
CHARACTERISTIC	TEST CONDITIONS			1	74HC/54HC 74HC TYPES TYPE			-	54HC TYPE		TEST CONDITIONS		1			HCT 54HCT			UNITS	
	V, V	I _o	V _{cc}		+25° C	;	l	0/ 5°C		5/ 5°C	V,	V _{cc}		+25° C	;	-40/ +85° C		-55/ +125° C		
	•			Min	Тур	Max	Min	Max	Min	Max	'	ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	_	2	-	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5		ĺ		ĺ				
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	-	to	-	-	0.8	-	0.8	-	0.8	v
			6	_	_	1.8	_	1.8		1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	V _{IL}				Ì			ļ		
Output Voltage V _{он}	or	-0.02	4.5	4.4		_	4.4	_	4.4	_	or	4.5	4.4	_	-	4.4	-	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	VIL										V _{IL}							3.7	_	v
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or 4.5	4.5	3.98	-	-	3.84	-			
	V _{IH}	-5.2	6	5.48		_	5.34	_	5.2	_	V _{IH}									
Low-Level	VIL		2		_	0.1	_	0.1	_	0.1	VıL									
Output Voltage Vo.	or	0.02	4.5	_		0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}		<u> </u>							
	VIL										V _{IL}					İ				
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V.
	V _{iH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage				}					
Current I,	or Gnd		6	-	-	±0.1	-	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-,	±1	μΑ
Quiescent	V _{cc}					_		-	-	-	& Gnd	-		-		-	-	_		
Device	or	0	6	_	_	2	_	20	_	40	V _{cc} or	5.5	_	_	2	_	20	_	40	μΑ
Current I _{cc}	Gnd							-		"	Gnd	5.5			-	ĺ				μ^
Additional			I	L		1	L		I	I		4.5					<u> </u>	-		
Quiescent Device Current per input pin: 1 unit load \Delta Icc*											V _{cc} -2.1	to 5.5	-	100	360	-	450	-	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
All	0.6

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., $360\,\mu A$ max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

CHARACTERISTIC	CL	SYMBOL	TYP	ICAL	UNITS	
CHARACTERISTIC	(pF)	SIMBOL	НС	нст		
Propagation Delay, Data Input to Output \overline{Y} (Fig. 1)	15	t _{PLH} t _{PHL}	10	11	ns	
Power Dissipation Capacitance*	_	C _{PD}	25	26	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per gate.

PD = V_{CC}² f, (C_{PD} + C_L)

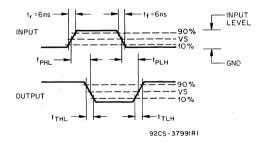
f, = input frequency

C_L = output load capacitance

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (CL = 50 pF, Input t, t = 6 ns)

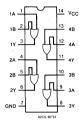
		V _{cc}		25	°C		-4	0°C to	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL		нс		H	СТ	74	нС	74F	ICT	54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.] _
Propagation Delay,	t _{PLH}	2		130		_		165		_		195		_	
Input to Output	t _{PHL}	4.5		26		28		33		35		39		42	ns
(Fig. 1)		6		22		_		28		_		33		_	
Transition Times	t _{TLH}	2		75		T -		95				110		_	
(Fig. 1)	t _{THL}	4.5		15		15		19		19		22		22	ns
		6		13		_		16		_		19		_	
Input Capacitance	Cı		-	10		10		10		10		10		10	pF



	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _s	50% V _{CC}	1.3 V

Fig. 1 - Transition times and propagation delay times.

High-Speed CMOS Logic



Quad 2-Input OR Gate

Type Features:

Typical propagation delay = 7 ns @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C (HC32)

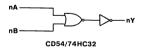
FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

The RCA-CD54/74HC32 and CD54/74HCT32 contain four 2-input OR gates in one package.

The CD54HC/HCT32 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/HCT32 are supplied in 14-lead dual-in-line plastic packages (E sufix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
 Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}



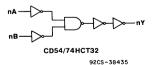


Fig. 1 - Logic diagrams.

TRUTH TABLE

INP	UTS	ОИТРИТ
nA	nB	nY
L	L	L
L	н	н
. н	L	н
Н	н	н

H = HIGH voltage level. L = LOW voltage level.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground)0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} +0.5$ V)
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)
DC DRAIN CURRENT, PER OUTPUT (I $_{o}$) (FOR -0.5 V < V $_{o}$ < V $_{cc}$ + 0.5V)
DC V _{cc} OR GROUND CURRENT (I _{cc})
POWER DISSIPATION PER PACKAGE (Po):
For T_A = -40 to +60° C (PACKAGE TYPE E)
For T _A = +60 to +85° C (PACKAGE TYPE E)
For T _A = -55 to +100°C (PACKAGE TYPE F, H)
For T _A = +100 to +125° C (PACKAGE TYPE F, H)
For T _A = -40 to +70°C (PACKAGE TYPE M)
For T _A = +70 to +125°C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H55 to +125°C
PACKAGE TYPE E. M40 to +85° C
STORAGE TEMPERATURE (T _{stg}) -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. +265° C +265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

0110107510	LIN	IITS	LINUTO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range (For T _A = Full Package Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

				CD	74HC	32/C	D54H	C32					CD	74HC	T32/C	D54F	нстз	2			
CHARACTERISTICS			TEST CONDITIONS			74HC/54HC TYPE		74F TY		54H TYI		TEST	ONS	74HCT/54HCT TYPE			74HCT TYPE		54HCT TYPE		
		V,	Io	V cc	+	25° C	;	-40 +85		-5: +125		V,	V _{cc}	-	-25°C		-4 +85	0/ 5° C	1	5/ 5° C	UNITS
		v	mA	v	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5		_	1.5		1.5	-		4.5								
Input Voltage	VIH	ļ		4.5	3.15	_	_	3.15	_	3.15	-	_	to	2	_	_	2	_	2	_	V
				6	4.2	_	_	4.2	_	4.2	_		5.5					i			
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage	VIL			4.5	_	_	1.35	_	1.35	_	1.35	_	to	_	_	0.8	_	0.8	-	0.8	, V ,
				6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage	Vон	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	٧
CMOS Loads		VIH		6	5.9	_	_	5.9	_	5.9	_	ViH									
		VIL										Vil									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	- -	٧
		ViH	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH	<i>'</i>			ĺ					
Low-Level		VıL		2	_	_	0.1	_	0.1	_	0.1	VıL									
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1		0.1	v v
CMOS Loads		V _{IH}		6	_	_	0.1	_	0.1	_	0.1	ViH	ŀ	,			ļ				
		VIL		<u> </u>								ViL									
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v
		VIH	5.2	6	_	_	0.26	_	0.33	_	0.4	ViH									
Input Leakage Current	l ₁	V _{cc} or Gnd		6	_	_	±0.1	-	±1	-	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	-	±1	_	±1	μΑ
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6	_	_	2		20	_	40	V _{cc} or Gnd	5.5	-	_	2	_	20	_	40	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	Δlcc*											V _{CC} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
All Inputs	1.5

^{*} Unit load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r, t_f = 6 ns)

CHARACTERICTIC		OVIIDOL	TYPICAL		
CHARACTERISTIC	C _L pF	SYMBOL	54/74HC	54/74HCT	UNITS
Propagation Delay	45	t _{PLH}	-		
A, B to Y	15	t _{PHL}	/	9	ns
Power Dissipation Capacitance		C _{PD} *	22	22	pF

^{*} C_{PD} is used to determine the dynamic power consumption, per gate.

 $P_D = f_i V_{CC}^2 (C_{PD} + C_L)$ where:

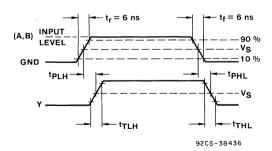
 f_i = input frequency.

C_L = output load capacitance.

V_{cc} = supply voltage.

SWITCHING CHARACTERISTICS (CL = 50 pF, Input t, t, = 6 ns)

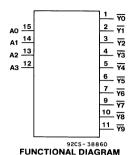
				25°C -40°C to +85°C -							-5	5°C to			
CHARACTERISTIC	SYMBOL	Vcc	нс		нст		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2		90		_		115		_		135		_	
A, B to Y	t _{PHL}	4.5		18		24		23		30		27		36	ns
Figure 2		6		15		_		20		_		23		_	
Transition Times	t _{TLH}	2		75		_		95		_		110		_	
	t _{THL}	4.5		15		15		19		19	ĺ	22		22	ns
Figure 2		6		13		-		16				19			
Input Capacitance	C ₁	_	_	10	-	10	_	10	_	10	_	10	_	10	pF



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, V _s	50% V _{cc}	1.3 V

Fig. 2 - Transition times and propagation delay times.

High-Speed CMOS Logic



BCD to Decimal Decoder (1-of-10)

Type Features:

- Buffered inputs and outputs
- Typical propagation delay = 12 ns @ V_{CC} = 5V, C_L = 15 pF T_A = 25° C (HC42)

The RCA-CD54/74HC42 and CD54/74HCT42 BCD-to-Decimal Decoders utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL decoders with the low power consumption of standard CMOS integrated circuits. These devices have the capability of driving 10 LSTTL loads and are compatible with the standard 54LS /74LS logic family. One of ten outputs (low on select) is selected in accordance with the BCD input. Non-valid BCD inputs result in none of the outputs being selected (all outputs are high).

The CD54HC42 and CD54HCT42 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC42 and CD74HCT42 are supplied in 16-lead dual-in-line plastic packages (E suffix), and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

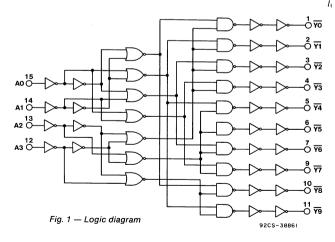
- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:

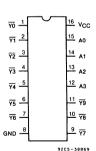
2 to 6 V Operation

High Noise Immunity:

 $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5~V$

■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}





TERMINAL ASSIGNMENT

MAXIMUM RATINGS, Absolute-Maximum Values:

PLY-VOLTAGE, (Vcc):
ges referenced to ground)0.5 to + 7 V
JT DIODE CURRENT, I_{ik} (FOR $V_i < -0.5$ V OR $V_i > V_{cc} + 0.5$ V)
PUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V) ± 20 mA
IN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{CC} + 0.5V)
DR GROUND CURRENT (Icc)
DISSIPATION PER PACKAGE (Po):
= -40 to +60°C (PACKAGE TYPE E)
= +60 to +85°C (PACKAGE TYPE E)
= -55 to +100° C (PACKAGE TYPE F, H)
= +100 to +125°C (PACKAGE TYPE F, H)
= -40 to +70° C (PACKAGE TYPE M)
= +70 to +125°C (PACKAGE TYPE M)
ING-TEMPERATURE RANGE (Ta):
AGE TYPE F, H
AGE TYPE E, M40 to +85° C
GE TEMPERATURE (T _{stg})65 to -150°C
EMPERATURE (DURING SOLDERING):
ance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max
serted into a PC Board (min. thickness 1/16 in., 1.59 mm)
older contacting lead tips only

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage V _I , V _O	0	V _{CC}	V
Operating Temperature T _A :	1		
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

TRUTH TABLE

	inp	uts						Outp	outs				
А3	A2	A1	A0	YO	<u>Y1</u>	<u>¥2</u>	Y3	<u>¥4</u>	Y5	<u>Y6</u>	Y7	<u>Y8</u>	<u>79</u>
L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н
L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н
L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н	Н	Н,
L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	Н
L	Н	L	L	Н	Н	Н	Н	L	Н	Н	Н	Н_	Н
L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н	Н	Η
L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н	Н
L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	Н
Н	L	L	L	Н	Н	Н	Н	Н	Н	Н	Н	L	Н
Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L
Н	L	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Τ
Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
H	Н	L	L	н	Н	Н	Н	Н	Н	Н	Н	Н	Н
Н	Н	L	Н	н	Н	Н	Н	Н	Н	Н	Н	Н	Н
H	Н	Н	L	н	Н	Н	Н	Н	Н	Н	Н	Н	Н
Н	Н	_н	Н	н	Н	Н	Н	Н	Н	Н	Н	Н	Н

L = Low Voltage Level H = High Voltage Level

STATIC ELECTRICAL CHARACTERISTICS

			CD74	HC42	/CD54	HC42	2					С	D74H	CT42	CD54	нст	42			
		TEST IDITIONS		ı	IC/54		741 TYI		54I TYF		TEST		1	CT/54		74F TYI		54H TYI		
CHARACTERISTIC	V, V	I _o	V _{cc}		+25° C	:	-4 +85	0/ 5°C	-5 +12		V, V	V _{cc}		+25° C		-40/ +85°C		-55/ +125° C		UNITS
				Min	Тур	Max	Min	Max	Min	Max			Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}	'		4.5	3.15	_	_	3.15	_	3.15	-	_	to	2	_	-	2	-	2	-	V
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	-	_	0.8	-	0.8	-	0.8	v
			6	-	-	1.8	_	1.8	-	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	1	V _{IL}									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	_	4.4	-	4.4	-	v
CMOS Loads	VIH		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	_	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									ì
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	-	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	-	0.33	-	0.4	v
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage.	V _{cc}										Any									
Current I	or		6	-	_	±0.1	_	±1	-	±1	Voltage Between	5.5	_	-	±0.1	-	±1	_	±1	μΑ
	Gnd										V _{cc} & Gnd									
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	_	_	8	_	80	_	160	or	5.5	-	_	8	_	80	_	160	μΑ
Current Icc	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load		-									V _{cc} -2.1	4.5 to 5.5	-	100	360	_	450	-	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
ALL	1

^{&#}x27;Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu{\rm A}$ max. @ 25° C.

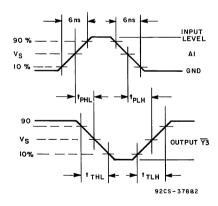
SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$, input t_r , $t_t = 6 \text{ ns}$)

CHARACTERISTIC	CL	SYMBOL	TYP	UNITS				
CHARACTERISTIC	(pF)	STWBOL	54/74HC	54/74HCT				
Any Input to Y	15	t _{PHL} , t _{PLH}	12	14	ns			
Power Dissipation Capacitance*	_	СРД	65	70	pF			

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_l = 6 ns)

		25° C -40° C to +85° C					C	-5							
CHARACTERISTIC SYMB		Vcc	Н	С	H	СТ	74	нС	74F	ICT	54	HC.	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.]
Propagation Delay,	t _{PLH}	2	_	150	_	_	_	190	_	_	_	225	_	_	
Any Input to Y	t _{PHL}	4.5	—	30	l —	35	_	38	_	44	_	45	_	53	ns
		6	—	26	—	_	_	33	<u> </u>	<u> </u>		38	_	-	
Output	t _{THL}	2	T —	75	_	_	_	95	_	_	_	110			
Transition Time	t _{TLH}	4.5	_	15	_	15	—	19	-	19	_	22		22	ns
		6	-	13	_	_	_	16	_		_	19		_	
Input			_	_		_	_	_	_	_	_	T -	_	_	
Capacitance	Cı		_	10	—	10	_	10	_	10	_	10	l —	10	pF
			_	_	l —	_	_	—	_	—	_	_	-	<u> </u>	



	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _S	50% V _{CC}	1.3 V

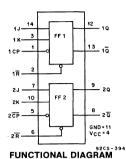
Transition times and propagation delay times.

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where:

f, = input frequency.

C_L = output load capacitance.

Vcc = supply voltage.



Dual J-K Flip-Flop with Reset Negative-Edge Trigger

Type Features:

- Hysteresis on clock inputs for improved noise immunity and increased input Rise and Fall times.
- Asynchronous Reset
- Complementary Outputs
- Buffered Inputs
- Typical $f_{\text{max}} = 60 \text{MHz}$ @ $V_{\text{cc}} = 5 \text{V}$, $C_{\text{L}} = 15 \text{pF}$, $T_{\text{A}} = 25 ^{\circ} \text{C}$

The RCA-CD54/74HC73 and CD54/74HCT73 utilize silicon-gate CMOS technology to achieve operating speeds equivalent to LSTTL parts. They exhibit the low power consumption of standard CMOS integrated circuits, together with the ability to drive 10 LSTTL loads.

These flip-flops have independent J, K, Reset and Clock inputs and Q and \overline{Q} outputs. They change state on the negative-going transition of the clock pulse. Reset is accomplished asynchronously by a low-level input. This device is functionally identical to the HC/HCT 107 but differs in terminal assignment and in some parametric limits.

The 54HCT/74HCT logic family is functionally as well as pin-compatible with the standard 54LS/74LS logic family.

The CD54HC73 and CD54HCT73 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC73 and CD74HCT73 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-inline surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range):
 Standard Outputs 10 LSTTL Loads
 Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 μA @ V_{OL}, V_{OH}

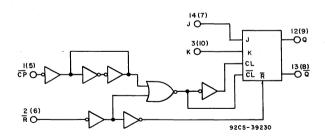


Fig. 1 - Logic diagram.

TRUTH TABLE (EACH FLIP-FLOP)

	INPL	OUT	PUTS		
Ŕ	CP	J	K	Q	Q
L	Х	X	Х	L	Н
Н	$\overline{}$	L	L	No ch	ange
Н	~	Н	L	Н	Ĺ
Н		L	Н	L	Н
Н	\sim	Н	Н	Toggl No ch	е
Н	• н	Х	X	No ch	ange

H = High Level (Steady State)

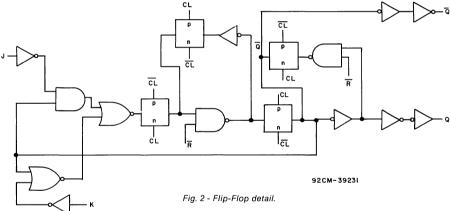
L = Low Level (Steady State)

X = Irrelevant

_ = High-to-Low transition

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR V_i <-0.5 V OR V_i > V_{CC}	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5~V$ or $V_O > 0.5~V$	> V _{cc} +0.5 V)±20mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5V $<$ Vo $<$	$V_{cc} + 0.5 \text{ V}$)
DC Vcc OR GROUND CURRENT (Icc)	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For $T_A = -40$ to $+60$ °C (PACKAGE TYPE E)	500 mW
For $T_A = +60$ to $+85$ °C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For $T_A = -55$ to $+100$ °C (PACKAGE TYPE F, H)	500 mW
For $T_A = +100$ to $+125$ °C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For $T_A = -40$ to $+70$ °C (PACKAGE TYPE M)	400 mW
For $T_A = +70$ to $+125$ °C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 1	0 s max
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 i	mm)
with solder contacting lead tips only	+300°C
CI	N N



RECOMMENDED OPERATING CONDITIONS:
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN		
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :* CD54/74HC Types CD54/74HCT Types	2 4.5	6 5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	٧
Operating Temperature T _A : CD74 Types CD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall Times t _r , t _r † at 2 V at 4.5 V at 6 V	0 0 0	1000 500 400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground. †Applicable for all inputs except clock.

STATIC ELECTRICAL CHARACTERISTICS

CD74HC73, CD54HC73										CD74HCT73, CD54HCT73											
CHARACTERISTIC -			TEST 7					1	74HC 54HC TYPES TYPES			TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS
		V,	lo	Vcc	-	+25°C		-40/ +85°C		-55/ +125°C		V.	Vcc	+25°C			-40/ +85°C		-55/ +125°C		J. J. J. J. J. J. J. J. J. J. J. J. J. J
		V	mA	\	Min	Тур	Max	Min	Max	Min	Max	V	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	V _{IH}			4.5	3.15	_	_	3.15		3.15	_	_	to	2	_	_	2	_	2	-	٧
				6	4.2	_	<u> </u>	4.2		4.2	_		5.5								
Low-Level				2	_	_	0.5		0.5		0.5		4.5								
Input Voltage	VIL			4.5	·	_	1.35	_	1.35		1.35	_	to	_	_	0.8	–	0.8		0.8	V
				6	_	L-	1.8	_	1.8		1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9		1.9	_	VIL						ļ			
Output Voltage	V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-		4.4	-	4.4	_	v
CMOS Loads		V _{IH}		6	5.9		_	5.9	_	5.9	_	V _{IH}									
		VIL										VIL						İ			
TTL Loads		or	-4	4.5	3.98	_	_	3.84	<u> </u>	3.7	_	or	4.5	3.98	-	-	3.84	_	3.7	-	V
		V _{IH}	-5.2	6	5.48			5.34	_	5.2	_ '	Vıн									
Low-Level		VIL		2	_	_	0.1		0.1		0.1	VIL									
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	_	0.1		0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads		V _{IH}		6	_	_	0.1	_	0.1		0.1	V _{IH}									
		VIL										VıL				}					
TTL Loads		or	4	4.5	_	_	0.26	_	0.33		0.4	or	4.5	_	_	0.26	-	0.33	_	0.4	V
		V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _H									
Input Leakage		Vcc										Any Voltage									
Current	l _t	or		6	-	-	±0.1	-	±1	—	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
		Gnd										& Gnd									
Quiescent		Vcc										Vcc									
Device		or	0	6	-	–	4	_	40	_	80	or	5.5	_	-	4	-	40	-	80	μΑ
Current	Icc	Gnd								<u> </u>		Gnd									
Additional Quiescent Device Current per input pin: 1 unit load	Δlcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

 $^{^{\}star}$ For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
All	0.3

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25°C.

SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25°C, Input t_r, t_f=6 ns)

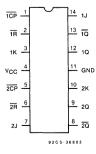
		C∟	TYP	ICAL	1
CHARACTERISTIC	SYMBOL	(pF)	нс	нст	UNITS
Propagation Delay CP to Q	t _{PLH} t _{PHL}	15	13	16	ns
\overrightarrow{CP} to \overline{Q}			13	15	ns
R to Q, Q			12	14	ns
CP Frequency	f _{max}	15	60	60	MHz
Power Dissipation Capacitance*	CPD		28	28	pF

* C_{PD} is used to determine the dynamic power consumption, per flip-flop. $P_D = C_{PD} \ V_{CC}^2$ fi + $\Sigma \ C_L V_{CC}^2$ fo where fi = input frequency, fo = output frequency,

 C_L = output load capacitance, V_{CC} = supply voltage.

PRE-REQUISITE FOR SWITCHING FUNCTION

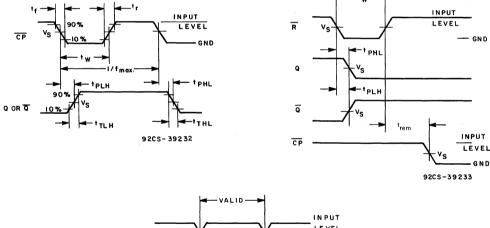
			LIMITS												
		TEST	25°C -40°C to +85°C							-5					
CHARACTERISTIC		CONDITION V _{CC}	Η	С	н	СТ	741	нс	74F	ЮТ	54	нс	54 F	ICT	UNITS
		v	Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	
Pulse Width	tw	2	80	_	_	_	100	_	_	_	120	_	_	_	
CP		4.5	16	_	16	_	20	_	20	—	24		24	_	ns
		6	14				17				20		_		
_		2	80	—	-	—	100	—	—	—	120	-	—	—	
R		4.5	16	-	18	—	20	—	23	_	24	—	27	-	ns
		6	14				17				20				
Set-up Time	tsu	2	80		_	—	100			—	120	l —	_	—	
J, K to CP		4.5	16	_	16	—	20	_	20	_	24	—	24	_	ns
		6	14		-		17	_	_		20				
Hold Time	tн	2	3		_	_	3	—	—	_	3		_	l —	
J, K to CP		4.5	3	—	3		3	—	3	—	3	_	3	_	ns
		6	3	_	_		3		_	_	3	_	_	_	
Removal Time	t _{REM}	2	80		_	l —	100	_		_	120	_	_		
		4.5	16	-	12	_	20	_	15	_	24	_	18	_	ns
		6	14			_	17		_		20	_		_	
CP Frequency	f_{MAX}	2	6	_	_	—	5	_	—		4	_	—	—	
		4.5	30	_	30	—	25		25	—	20	-	20	—	MHz
		6	35	-	_	-	29	-	-	-	23		-	_	

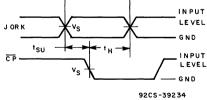


TERMINAL ASSIGNMENT

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_f = 6 \text{ ns}$)

							LIM	ITS						
	TEST		25	°C		-4	0°C to	+85	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	CONDITION	нс		нст		74HC		74HCT		54HC		54HCT		UNITS
	v	Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	2	_	160	_	_	_	200	_	_	_	240	_	_	
t _{PLH} , t _{PHL}	4.5		32	_	38	_	40	—	48		48	—	57	ns
CP to Q	6		28				34		_	<u> </u>	41		_	
	2	—	160	_	l —	_	200	—	—	-	240	-	l —	
CP to Q	4.5	—	32	_	36	_	40	—	45	_	48	—	54	ns
	6		28				34				41			
	2	l —	145	_	_	_	180	_	l —		220	_	_	
R to Q, Q	4.5	—	29	_	34	-	36	—	43		44	—	51	ns
	6		25	_			31				38			
Output Transition	2	_	75	_	_	_	95		_	_	110	_	_	
Time t _{TLH} , t _{THL}	4.5	—	15	—	15	_	19		19		22	—	22	ns.
	6		13				16				19		_	
Input Capacitance C ₁		_	10		10		10	_	10	_	10	_	10	pF

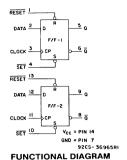




	54/74HC	54/74HCT
Input Level	Vcc	3V
Switching Voltage, Vs	50% V _{cc}	1.3 V

Fig. 3 - Transition times, propagation delay times, and setup and hold times.

High-Speed CMOS Logic



Dual D Flip-Flop with Set and Reset Positive-Edge Trigger

Type Features:

- Hysteresis on clock inputs for improved noise immunity and increased input Rise and Fall times.
- Asynchronous Set and Reset
- Complementary Outputs
- Buffered Inputs
- Typical $f_{\text{max}} = 50 \text{ MHz}$ @ $V_{\text{CC}} = 5V$, $C_{\text{L}} = 15 \text{ pF}$, $T_{\text{A}} = 25^{\circ}C$

The RCA-CD54/74HC74 and CD54/74HC774 utilize silicongate CMOS technology to achieve operating speeds equivalent to LSTTL parts. They exhibit the low power consumption of standard CMOS integrated circuits, together with the ability to drive 10 LSTTL Loads.

This flip-flop has independent DATA, \overline{SET} , \overline{RESET} and CLOCK inputs and Q and \overline{Q} outputs. The logic level present at the data input is transferred to the output during the positive-going 'transition of the clock pulse. \overline{SET} and \overline{RESET} are independent of the clock and are accomplished by a low level at the appropriate input.

The 54HCT/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC74 and CD54HCT74 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC74 and CD74HCT74 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-inline surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

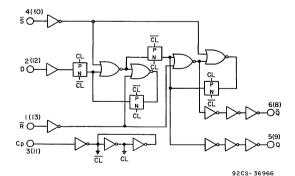


Fig. 1 — Logic Diagram

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads
 Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to + 85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:

2 to 6 V Operation

High Noise Immunity:

 $N_{\rm IL}$ = 30%, $N_{\rm IH}$ = 30% of $V_{\rm CC}$; @ $V_{\rm CC}$ = 5 V

■ CD54HCT/CD74HCT Types:

4.5 to 5.5 V Operation

Direct LSTTL Input Logic Compatibility

 $V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.$

CMOS Input Compatibility

 $I_1 \leq 1 \ \mu A \ @ \ V_{OL} \ V_{OH}$

TRUTH TABLE

	INPL	OUTPUTS				
SET	RESET	СР	D	Q	Q	
L	Н	X	Х	Н	L	
Н	L	X	X	L	Н	
L	L	Χ	X	H*	H*	
Н	Н	~	Н	H	L	
Н	Н		L	L	Н	
Н	Н	L	Χ	Q0	<u> </u>	

H = High Level (Steady State)

L = Low Level (Steady State)

X = Don't Care

NOTES: QO = the level of Q before the indicated input conditions were established.

*This configuration is nonstable, that is, it will not persist when set and reset inputs return to their inactive (high) level.

MAXIMUM RATINGS, Absolute-Maximum Values:

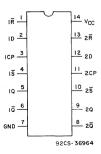
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)	
DC OUTPUT DIODE CURRENT, Iox (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERICTIC	LIM	LIMITO	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	· V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _{in} , V _{out}	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f •			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

[•]Applicable for all inputs except clock.

STATIC ELECTRICAL CHARACTERISTICS

			CD74	HC74/	CD54	HC74						С	D74H	CT74/	CD54	нст	74			
CHARACTERISTIC	i	TEST NDITIONS			IC/54		741 TYI		541 TYF		TEST CONDITIO	ons	74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS
CHAIR CILIIO II C	V,	I _o	V _{cc}	-	+25° C	;	-4 +85	0/ 5°C	-5 +12		V, V _{cc}			+25° C	:	-4 +85	0/ 5° C	-5 +12		Oiti
	•	""	•	Min	Тур	Max	Min	Max	Min	Max	,		Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}		i	4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	-	_	2	-	2	_	V
			6	4.2	_	_	4.2	_	4.2			5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5		_	1.35	-	1.35	_	1.35	-	to	-	-	0.8	-	0.8	-	0.8	٧
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	V _I ,									
Output Voltage V _{UH}	or	-0.02	4.5	4.4		_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}							ļ		
	V _{IL}										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	37		or	4.5	3.98	_	_	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage $V_{O_{k}}$	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	_	0.1	-	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	VIL										Vil									
TTL Loads	or	4	4.5		_	0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	-	0.33	-	0.4	v
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{CC}										Any Voltage									
Current I,	or		6	_	_	±0.1	_	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd						<u></u>				& Gnd							ļ		
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	4	-	40	-	80	or	5.5	-	-	4	-	40	-	80	μΑ
Current I _{cc}	Gnd									<u> </u>	Gnd						<u> </u>	<u> </u>	_	
Additional Quiescent Device Current											V _{cc} -2.1	4.5 to	_	100	360	_	450	_	490	μΑ
per input pin: 1 unit load Δ lcc*												5.5								ĺ

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
D	0.5
R	0.5
CP	0.7
<u>s</u>	0.75

^{*}Unit Load is $\Delta l_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu{\rm A}$ max. @ 25° C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$, input $t_r, t_f = 6 \text{ ns}$)

CHARACTERISTIC	SYMBOL	CL	TYP	UNITS	
CHARACTERISTIC	STMBOL	(pF)	нс	нст	UNITS
Propagation Delay	t _{PLH}				
	tPHL				
CP to Q, Q (Fig. 2)			14	14	
R to Q, Q (Fig. 3)	1	15	17	17	ns
S to Q, Q (Fig. 3)	1		17	17	7
CP Frequency	f _{MAX}	15	50	50	MHz
Power Dissipation Capacitance*	CPD	_	25	30	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per flip-flop.

PD = $C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 f_o)$ where: f_i = input frequency

fo = output frequency

C_L = output load capacitance

V_{cc} = supply voltage

PRE-REQUISITE FOR SWITCHING FUNCTION

								LIM	ITS						
		TEST		25	°C		-4	0°C to	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERI	CHARACTERISTIC CONDITION Vcc (V)		Н	нс		HCT		HC	74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.]
Data to CP	tsu	2	60	_		_	75	_	_	_	90	_	_	_	
Set-up Time		4.5	12	_	12		15	—	15	—	18	_	18	_	
(Fig. 4)		6	10	—	—	_	13		_	_	15	_	—	_	
Hold Time	t _H	2	3	_	_	_	3		_	_	3	_	_	_	1
		4.5	3	_	3	l —	3	—	3	l —	3	-	3	—	
(Fig. 4)		6	3	_	<u> </u>	—	3	_	_		3	_	—	—	
Removal Time	· t _{REM}	2	30	_	—	_	40	_	_	_	45	_	_	_	ns
\overline{R} , \overline{S} to CP		4.5	6	_	6	_	8	—	8	_	9	—	9	_	
(Fig. 3)		6	5	—	_	 	7	_	 	—	8	_	—	_	
Pulse Width	tw	2	80	-	_	_	100	_	_	<u> </u>	120	_	_	_	1
R, S		4.5	16	_	16	_	20	—	20	—	24	_	24	_	
(Figs. 2, 3)		6	14	_	—	_	17		_	_	20	—	 —	_	
Pulse Width	tw	2	80	_	_	_	100	_	_	l –	120	T —	_	_	
CP		4.5	16	—	18	_	20	_	23	—	24	l —	27	_	
(Figs. 2, 3)		6	14	_	 		17	_	—	_	20	_	_		
CP Frequency	f _{MAX}	2	6	_		_	5	_	_		4	_	_	l –	
		4.5	30	-	25	—	25	_	20	_	20		16	_	MHz
		6	35	_	l —	— .	29	l —	_	_	23		l —	_	

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r,t_f = 6 ns)

							LIM	ITS							
CHARACTERISTIC		V		25°C -40°C to +85°C -55°C to +12										°C_	
CHARACTERIS	SIIC	VCC	Н	С	HCT		74HC		74F	ICT	54	нс	54F	ICT	UNITS
		(V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	175	_	_	_	220		_	_	265	_		
CP to Q, Q	t _{PHL}	4.5	-	35	_	35		44	-	44	l —	53	<u> </u>	53	
(Fig. 2)		6	l –	30	_	_		37	_	l —	_	45	_	_	
R, S to Q, Q	t _{PHL}	2	Ι-	200	-	-		250	_	_	_	300	_	-	ns
	t _{PLH}	4.5	_	40	_	40	_	50	l —	50	—	60	_	60	
(Fig. 3)		6	_	34		_	l —	43	_	l —	L	51	l —	-	
Transition Times	tTLH	2	1 =	75	T —	_	_	95	_	_	T —	110	_		
	t _{THL}	4.5	_	15	_	15	_	19	_	19	_	22		22	ļ
(Fig. 5)		6		13	_	_	_	16	—	_	_	19	_		
Input Capacitance	Cı		T_	10		10		10		10		10	_	10	pF

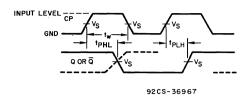


Fig. 2 — Clock pre-requisite and propagation delays.

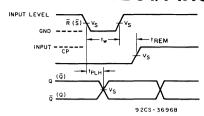


Fig. 3 — Reset or Set pre-requisite and propagation delays

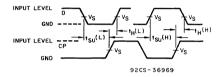


Fig. 4 — Data pre-requisite times.

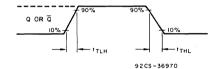
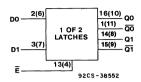


Fig. 5 — Output transition times.

	54/74HC	54/74HCT
INPUT LEVEL	v _{cc}	3V
Vs	50% V _{CC}	1.3V



Dual 2-Bit Bistable Transparent Latch

Type Features:

- True and Complementary Outputs
- Buffered Inputs and Outputs

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC75 and CD54/74HC775 are dual 2-bit bistable transparent latches. Each one of the 2-bit latches is controlled by separate Enable inputs ($\overline{1E}$ and $\overline{2E}$) which are active LOW. When the Enable input is HIGH data enters the latch and appears at the Q output. When the Enable input ($\overline{1E}$ and $\overline{2E}$) is LOW the output is not affected.

The CD54HC/HCT75 are supplied in 16-lead hermetic dualin-line packages (F suffix). The CD74HC/HCT75 are supplied in 16-lead dual-in-line plastic package (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

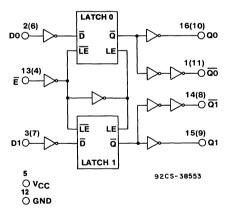


Fig. 1 - Logic Diagram

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCTj: —40 to + 85°C
- Balanced Propagation delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noice Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{cc}; @ V_{cc} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}

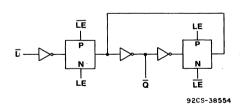


Fig. 2 - Latch Detail

MAXIMUM RATINGS, Absolute-Maximum Values:

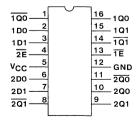
DC SUPPLY-VOLTAGE. (Vcc):
(Voltages referenced to ground) -0.5 to + 7 V
DC INPUT DIODE CURRENT, lik (FOR Vi <-0.5 V OR Vi > Vcc +0.5V)
DC OUTPUT DIODE CURRENT, lok (FOR Vo < -0.5 OR Vo > Vcc +0.5 V)
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Voc +0.5 V)
DC Vcc OR GROUND CURRENT (lcc): ± 50 mA
POWER DISSIPATION PER PACKAGE (P₀):
For T _A = -40 to +60°C (PACKAGE TYPE E)
For T _A = +60 to +85°C (PACKAGE TYPE E)
For T _A = -55 to +100°C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For T _A = -40 to +70° C (PACKAGE TYPE M)
For T _A = +70 to +125° C (PACKAGE TYPE M)
OPERATING -TEMPERATURE RANGE (Ta):
PACKAGE TYPE F, H55 to +125° C
PACKAGE TYPE E, M40 to +85° C
STORAGE TEMPERATURE (Tsig)65 +150° C
LEAD TEMPERATUARE (DURING SOLDERING):
At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s max. +265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only +300° C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LI	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) Vcc:*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	Ì
DC Input or Output Voltage V ₁ V ₀	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	1
CD54 Types	-55	+125	°C
input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

TRUTH TABLE

Inp	uts	Outputs							
D	Ē	Q	Q						
L	Н	L	Н						
Н	Н	Н	L						
X	L	Q0	Q0						

H = High Level

L = Low Level

X = Don't Care

Q0 = The level of Q before the transition of \overline{E} .

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC75/CD54HC75										c	D74F	ICT75	/CD	54HC	T75			
		TEST		74HC/54HC			74	нс	54	нс	TEST		74HCT/54HCT			74F	ЮТ	541	ЮТ	
CHARACTERISTIC	CON	NDITIONS			TYPE	s	TY	PES	ΤY	PES	CONDIT	ONS	1	YPES	3	TYI	PES	TY	PES	UNITS
ONAHAO (EIIIO) IO	V ₁	lo	Vcc		· 25° (9	l	10/ 5°C		55/ 25° C	V ₁	Vcc	+	25° C			10/ 5°C		i5/ !5°C	
	٧	mA	V	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	-	1.5	-		4.5								
Input Voltage ViH			4.5	3.15	_	-	3.15	-	3.15	_		to	2	_	-	2	-	2	-	
			6	4.2	_	_	4.2		4.2	_	-	5.5								v
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								-
Input Voltage VIL			4.5	_	_	1.35	-	1.35	_	1.35		to	-	_	0.8	-	0.8	–	0.8	v
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	-	-	1.9	_	1.9	_	VIL									
Output Voltage Voн	or	-0.02	4.5	4.4	-	-	4.4	_	4.4	-	or	4.5	4.4	-	_	4.4	-	4.4	-	v
CMOS Loads	Vін		6	5.9	_	_	5.9	_	5.9	_	Vıн									
	VIL										VIL									
TTL Loads	or	-4	4.5	3.98	_	_	3.84		3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	\ v
	VIH	-5.2	6	5.48	_	_	5.34	_	5.2	_	Vін									
Low-Level	VIL	<u> </u>	2	-	_	0.1	_	0.1		0.1	VIL								-	
Output Voltage Vol	or	0.02	4.5	_		0.1	_	0.1		0.1	or .	4.5	-	_	0.1	_	0.1	-	0.1	v
CMOS Loads	Vін		6		_	0.1	_	0.1	_	0.1	ViH									
	VIL	<u> </u>									VIL	İ								
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v
	Vıн	5.2	6	<u> </u>	<u> </u>	0.26	_	0.33	_	0.4	ViH		<u> </u>					<u> </u>		
Input Leakage	V cc										Any Voltage									1
Cürrent lı	or		6	-	-	±0.1	-	±1	_	±1	Between Vcc &	5.5	-	-	±0.1	-	±1	-	±1	
	Gnd		<u> </u>								Gnd					<u> </u>	<u> </u>	ļ		Aιι
Quiescent	Vcc										Vcc									
Device	or	0	6	-	-	4	-	40	-	80	or	5.5	-	-	4	-	40	-	80	ДA
Current Icc	Gnd		L	L							Gnd									
Additional quiescent												4.5								
Device Current per input pin:											Vcc-2.1	to	-	100	360	-	450	-	490	ДA
1 unit load ∆lcc*												5.5				<u> </u>				

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
DO, D1	0.8
1E, 2E	1.2

^{*}Unit load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6ns)

CHARACTER	RISTIC	C _L	SYMBOL	TYP	ICAL	UNITS
OHAHAGIEI		(pF)	011111502	HC75	HCT75]
Propagation Delay	D to Q	15	t PLH	9	11	ns
Ì	D to Q	15		10	11	ns
	Enable to Q	15	t _{PHL}	10	11	ns
	Enable to Q	15		11	12	ns
Power Dissipation Cap	ower Dissipation Capacitance*		СРО	46	46	pF

^{*}C_{PD} is used to determine the dynamic power consumption per latch.

 $PD = V_{CC}^2 fi (C_{PD} + C_L)$

fi = Input Frequency

CL = Load Capacitance

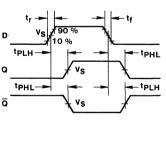
Vcc = Supply Voltage

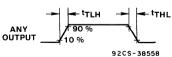
PREREQUISITE FOR SWITCHING FUNCTION

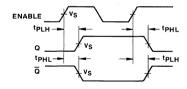
		TEST						LI	MITS							
		CONDITION	ONDITION 25°C					-40°C to + 85°C					-55°C to + 125°C			
		V cc	Н	IC	Н	СТ	74	НС	74H	нст	54	НС	54H	нст		
CHARACTERISTIC		v	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	UNITS	
Pulse Width	tw	2	80		_		100		_		120					
Enable Input		4.5	16		16	ļ	20		20		24		24	ŀ	ns	
		6	14				17		_		20					
Setup Time	tsu	2	60		_		75				90		-			
D to Enable		4.5	12		12		15		15	İ	18		18		ns	
		6	10		_		13		—		15		—			
Hold Time	t _h	2	3		_		3		-		3		_			
Enable to D		4.5	3		3		3		3	1	3		3		ns	
		6	3		—		3		_		3		_			

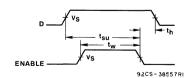
SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_s, t_f = 6 ns)

				25	°C		-4	0°C to	o + 85	°C	-5				
the state of the s			ŀ	łC	н	нст		74HC		нст	54HC		54HCT		
CHARACTERISTIC	SYMBOL	Vcc	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	UNITS
Propagation Delay	t PLH	2	_	110	_	_		140	_	_	_	165	_	_	
Data to Q	t _{PHL}	4.5	—	22	—	28	-	28	_	35	l —	33	_	42	ns
		6	—	19	—	—	_	24	<u> </u>	_	—	28	_	_	
Propagation Delay	t PLH	2		130	_		_	165		_	_	195	_	_	
Data to Q	tehl	4.5	—	26	—	28	—	33	—	35	—	39	_	42	ns
	1	6	—	22	—	—	l —	28	_	—	_	33	_	_	
Propagation Delay	t _{PLH}	2	_	130	_	_	_	165	_		_	195		_	
Enable to Q	t _{PHL}	4.5	l —	26	—	28	—	33	—	35	—	39	_	42	ns
	CFIIC.	6		22	_		—	28	l —	<u> </u>	<u> </u>	33	_	_	
Propagation Delay	t PLH	2	_	130	_	_	_	165	_	_	_	195	_	_	
Enable to Q	t _{PHL}	4.5	-	26	l —	30	—	33	l —	38	l —	39	_	45	ns
<u> </u>		6	l —	22	_	 	_	28	l —	 	_	33			
Output Transition	tтьн	2	_	75	_	_	_	95	_	_	<u> </u>	110		_	
Time	t _{THL}	4.5	—	15	l —	15	_	19	l —	19	_	22		22	ns
		6		13	_		_	16		—	l —	19	_	—	
Input Capacitance	Cı		-	10	-	10	_	10	_	10		10	-	10	pF



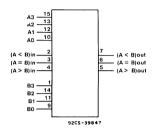






	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _S	50% V _{CC}	1.3 V

High-Speed CMOS Logic



4-Bit Magnitude Comparator

Type Features:

- Buffered inputs and outputs
- Typical propagation delay = 13 ns (Data to Output) @ V_{CC} = 5V, C_L = 15 pF, T_A = 25°C
- Serial or Parallel expansion without external gating.

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC/HCT85 are high-speed magnitude comparators that use silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

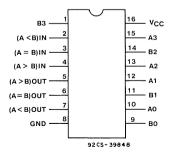
These 4-bit devices compare two binary, BCD, or other monotonic codes and present the three possible magnitude results at the outputs (A > B, A < B, and A = B). The 4-bit input words are weighted (A0 to A3 and B0 to B3), where A3 and B3 are the most significant bits.

The HC/HCT85 are expandable without external gating, in both serial and parallel fashion. The upper part of the truth table indicates operation using a single device or devices in a serially-expanded application. The parallel expansion scheme is described by the last three entries in the truth table. Circuits for serial and parallel comparison of 12 bits are shown in figures 3 and 4, respectively.

The CD54HC/HCT85 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT85 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT/HCU: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I, ≤ 1 µA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

MAXIMUM RATINGS. Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc): (Voltages referenced to ground) -0.5 to +7 V POWER DISSIPATION PER PACKAGE (PD): OPERATING-TEMPERATURE RANGE (TA): PACKAGE TYPE E. M-40 to +85°C STORAGE TEMPERATURE (Tstq).....-65 to +150°C LEAD TEMPERATURE (DURING SOLDERING): At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79$ mm) from case for 10 s max. +265 °C Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)+300°C with solder contacting lead tips only B2 B3 BI BŌ ΑO ĀŌ 40 В1 вз 92CL-39835RI Ā2

Fig. 1 - Logic diagram

TRUTH TABLE

	Compari	ng Inputs		Caso	ading In	puts		Outputs		
A3, B3	A2, B2	A1, B1	A0, B0	A > B	A < B	$\mathbf{A} = \mathbf{B}$	A>B	A < B	$\mathbf{A} = \mathbf{B}$	
A3 > B3	Х	Х	Х	Х	Х	X	Н	L	L	\
A3 < B3	X	Х	X	Х	Х	Х	L	Н	L	l \
A3 = B3	A2 > B2	X	x	Х	Х	Х	н	L	L	1
A3 = B3	A2 < B2	X	x	Х	Х	Х	L	Н	L	<i> </i>
A3 = B3	A2 = B2	A1 > B1	x	Х	Х	Х	н	L	L	single device
A3 = B3	A2 = B2	A1 < B1	x	Х	Х	Х	L.	Н	L	or
A3 = B3	A2 = B2	A1 = B1	A0 > B0	Х	Х	Х	н	L	L	series cascading
A3 = B3	A2 = B2	A1 = B1	A0 < B0	Х	Х	Х	L	Н	L	1 \
A3 = B3	A2 = B2	A1 = B1	A0 = B0	Н	L	L	Н	L	L	
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	Н	L	L	Н	L	1 /
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	Н	L	L	Н	/
A3 = B3	A2 = B2	A1 = B1	A0 = B0	Х	Х	Н	L	L	H	1.)
A3 = B3	A2 = B2	A1 = B1	A0 = B0	н	Н	L	L	L	L	parallel cascading
A3 = B3	A2 = B2	A1 = B1	A0 = B0	L	L	L	н	Н	L	[<i>)</i>

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN	IITS			
CHARACTERISTIC	MIN.	MAX.	UNITS		
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :* CD54/74HC Types CD54/74HCT Types	2 4.5	6 5.5	V		
DC Input or Output Voltage V _I , V _O	0	Vcc	V		
Operating Temperature T₄: CD74 Types CD54 Types	-40 -55	+85 +125	°C		
Input Rise and Fall Times t _r , t _r at 2 V at 4.5 V at 6 V	0 0 0	1000 500 400	ns		

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC85/CD54HC85											CD	74HC	T85/C	D54F	1CT8	5		
CHARACTERISTIC	1	TEST	s	l	74HC/54HC TYPES		ł	74HC TYPES		HC PES	TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		
CHARACTERISTIC	V,	lo 	V _{cc}	_	+25°0	;		10/ 5°C		55/ 15°C	V _i	Vcc	Vcc		+25°C		-40/ +85°C		i5/ !5°C	UNITS
		mA	•	Min	Тур	Max	Min	Max	Min	Max	v ,	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_		1.5	_	1.5	_		4.5								
Input Voltage V _{ін}		:	4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	_	2	_	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	_	_	0.8	_	0.8	_	0.8	v
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage Vон	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
, and the second	VIL										VIL									
TTL Loads	or	-4	4.5	3.98		_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	l _	3.7	_	v
	V _{IH}	-5.2	6	5.48	-	_	5.34	_	5.2	_	ViH	ŀ								
Low-Level	V _{IL}		2	_		0.1	_	0.1	_	0.1	VIL									
Output Voltage Vol.	or	0.02	4.5			0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads	V _{IH}		6	_	-	0.1	_	0.1	_	0.1	ViH									
	VIL										VIL									
TTL Loads	or	4	4.5	_		0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	-	0.33	_	0.4	v
	V _{IH}	5.2	6	_	_	0.26		0.33		0.4	V _{IH}									
Input Leakage Current I	V _{cc} or		6	_	_	±0.1	-	±1	_	±1	Any Voltage Between V _{cc} and	5.5	_	_	±0.1	_	±1	_	±1	μΑ
	Gnd					<u> </u>	<u> </u>	_			Gnd	<u> </u>		<u></u>		_	<u> </u>			
Quiescent Device Current Icc	Vcc										Vcc									
	or	. 0	6	-	-	8	-	80	-	160	or	5.5	-	_	8	-	80	-	160	μΑ
	Gnd			<u> </u>		l	<u> </u>	<u> </u>		<u> </u>	Gnd	ļ	-		<u> </u>		<u> </u>			
Additional Quiescent Device Current per input pin: 1 unit load Δl_{cc}^*											V _{CC} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

 $^{^{\}star}$ For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
A0-A3, B0-B3 and (A=B) in	1.5
(A>B) in, (A <b) in<="" td=""><td>1</td></b)>	1

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 360 μA max. @ 25°C.

SWITCHING CHARACTERISTICS ($V_{\text{CC}} = 5 \text{ V}, \, T_A \, 25^{\circ}\text{C}, \, \text{Input } t_r, \, t_r = 6 \, \text{ns}$)

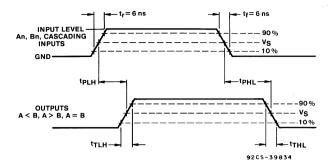
			TYP	ICAL	
CHARACTERISTIC	SYMBOL	C∟ (pF)	54/74HC	54/74HCT	UNITS
Propagation Delay		15			
An, Bn to (A>B)out, (A <b)out< td=""><td></td><td></td><td>16</td><td>15</td><td>ns</td></b)out<>			16	15	ns
An, Bn to (A=B) out	t _{PLH}		14	17	ns
(A>B)in, $(A,in (A=B)in to$	t _{PHL}				
(A>B)out,(A <b)out< td=""><td></td><td></td><td>11</td><td>12</td><td>ns</td></b)out<>			11	12	ns
(A=B) in to (A=B)out			9	13	ns
Power Dissipation Capacitance*	C _{PD}	_	24	26	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

P_D=V_{cc}²fi (C_{PD}+C_L) where: fi=input frequency C_L=output load capacitance V_{cc}=supply voltage

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_f = 6 \text{ ns}$)

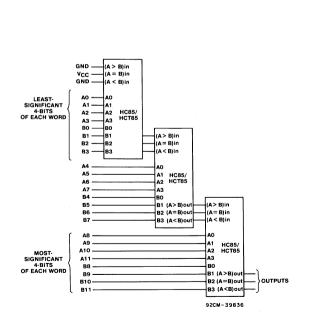
	TEST	LIMITS												
	CONDITION		25	°C		-4	0°C to	+85	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	V _{cc}	Н	С	Н	СТ	74	НС	74F	нст	54	нс	54F	ICT	UNITS
	v	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Propagation Delay tplh	2	_	195	_	_	_	245	_	-	_	295	_	_	
An, Bn to (A>B)out, t _{PHL}	4.5	l —	39	—	37	_	47	—	46	l —	59	_	56	ns
(A <b)out< td=""><td>6</td><td>_</td><td>33</td><td></td><td></td><td></td><td>42</td><td>_</td><td>_</td><td>_</td><td>50</td><td>_</td><td>_</td><td></td></b)out<>	6	_	33				42	_	_	_	50	_	_	
	2	_	175		_	_	240	_	_	_	265	_	<u> </u>	1
An, Bn to	4.5	_	35		40	_	44	_	50	l —	53	_	60	ns
(A=B)out	6	_	30	_	_		37			_	45	_		
(A>B)in, (A <b)in,< td=""><td>2</td><td>_</td><td>140</td><td>_</td><td>_</td><td>_</td><td>175</td><td>_</td><td>_</td><td>_</td><td>210</td><td>_</td><td>_</td><td></td></b)in,<>	2	_	140	_	_	_	175	_	_	_	210	_	_	
(A=B)in to	4.5	_	28		30	_	35	_	38	—	42	—	45	ns
(A>B)out, (A <b)out< td=""><td>6</td><td></td><td>24</td><td>_</td><td></td><td>_</td><td>30</td><td></td><td>_</td><td>_</td><td>36</td><td></td><td></td><td></td></b)out<>	6		24	_		_	30		_	_	36			
	2	_	120	_	_	_	150	_	_	_	180	_	_	
(A=B)in to (A=B)out	4.5		24		31	_	30	—	39	l —	36	_	47	ns
	6	<u> </u>	20			_	26	<u> </u>	<u>L-</u>		31			
Output t _{TLH}	2		75	_			95	_			110	-		l
Transition t _{™L}	4.5	—	15	_	15	_	19	_	19	l —	22	—	22	ns
Time	6	_	13	_	_	_	16				19			_
Input C ₁														
Capacitance		_	10		10		10	_	10	_	10	_	10	pF



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, V _S	50% V _{cc}	1.3 V

Fig. 2 - Transition times, propagation delay times

INPUTS

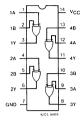


A11 A3 B2 A2 B10 HC/HCT85 A10 В9 A1 B0 Α9 (A=B)out NC B8 A8 (A>B)ou ΑO (A < B)in GND (A= B)in (A> B)in A7 Δ6 A3 B2 АЗ нс/нств5 НС/НСТ85 A2 B1 **A**5 A2 OUTPUTS (A < B)out B4 -(A = B)out (A = B)out A1 (A > B)out вз во (A > B)out Δ3 ΔΩ AO (A < B)in В2 (A = B)in (A > B)in (A = B)in A2 (A > B)in вз АЗ HC/HCT85 RΩ ΑO A2 B1 (A < B)out (A = B)out (A > B)out во GND (A < B)in (A = B)in Vcc GND 92CL-39837

Fig. 3 - Series cascading --- comparing 12-bit words.

Fig. 4 - Parallel cascading --- comparing 12-bit words.

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

Quad 2 - Input EXCLUSIVE - OR Gate

Type Features:

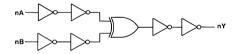
- Four independent EXCLUSIVE OR gates
- Buffered inputs and outputs

Applications:

- Logical comparators
- Parity generators and checkers
- Adders/Subtracters

The RCA CD54/74HC86 and CD54/74HCT86 contain four independent EXCLUSIVE-OR gates in one package. They provide the system designer with a means for implementation of the EXCLUSIVE-OR function.

The CD54HC/HCT86 are supplied in 14-lead cermetic dual-in-line packages (F suffix). The CD74HC/HCT86 are supplied in 14-lead plastic dual-in-line packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



92CS-38429

Fig. 1 - Logic diagram each gate.

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 μA @ V_{OL}, V_{OH}

TRUTH TABLE

INP	UTS	ОИТРИТ
nA	nB	nY
L	L	L
L	Н	н
н	L	н
Н	н	L

H = HIGH voltage level.

L = LOW voltage level.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc): (Voltages referenced to ground)-0.5 to +7 V DC V_{cc} OR GROUND CURRENT (Icc): ± 50 mA POWER DISSIPATION PER PACKAGE (Pn): OPERATING-TEMPERATURE RANGE (TA): PACKAGE TYPE E, M-40 to +85°C STORAGE TEMPERATURE (Tstg).....-65 to +150°C LEAD TEMPERATURE (DURING SOLDERING): At distance $1/16 \pm 1/32$ in, $(1.59 \pm 0.79 \text{ mm})$ from case for 10 s max......+265°C Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN	IITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _i , V _o	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

				CD74	HC86	/CD5	4HC8	6					CD	74HC	T86/0	D54I	нств	6			
CHARACTERIST		1	TEST DITIOI	NS.	l	C/54 TYPE		74F		54H TYI		TEST			74HCT/54HCT TYPE		74H TY		54H TY		UNITS
CHARACTERIST	ics	v,	lo	Vcc	,	25° C	;	-40 +85		-5! +125		Vı	Vcc		·25° C		-4 +85	0/ 5°C		5/ 5° C	UNIIS
		V	mA	v	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5		1.5	_		4.5								
Input Voltage	VIH	1		4.5	3.15	_		3.15		3.15		_	to	2	_	_	2	-	2	_	V
				6	4.2			4.2	_	4.2	_		5.5								
Low-Level				2	_	- 1	0.5		0.5	_	0.5		4.5								
Input Voltage	VIL			4.5	_	_	1.35		1.35	_	1.35		to	_	_	0.8	_	0.8	_	0.8	V
				6	_	_	1.8	_	1.8		1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage	Voh	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads		VIH		6	5.9	_	_	5.9	_	5.9	_	ViH						į			
		VIL										VıL									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	-	v
		VIH	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH									
Low-Level		VIL		2	_	_	0.1	_	0.1	_	0.1	VIL									
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads		V _{IH}	ļ	6	_	_	0.1	_	0.1	_	0.1	ViH				ł	ļ		ļ	ļ	
		VIL										VIL									
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v
		ViH	5.2	6	_		0.26	_	0.33		0.4	V _{IH}									,
Input Leakage Current	l _i	V _{cc} or Gnd		6	_	_	±0.1		±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1	_	±1	μΑ
Quiescent Device																					
Current	Icc	V _{cc} or Gnd	0	6	_	_	2	_	20	_	40	V _{cc} or Gnd	5.5	_	-	2	-	20	-	40	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	ΔΙςς.						<u> </u>	<u> </u>	<u></u>	I	<u> </u>	V _{cc} -2.1	4.5 to 5.5	-	100	360	_	450	-	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
All Inputs	1

^{*} Unit load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ} \text{ C}$, Input $t_{r_i} t_i = 6 \text{ ns}$)

		av	TYPICAL	UNITS	
CHARACTERISTIC	C _L pF	SYMBOL	54/74HC	54/74HCT	UNITS
Propagation Delay, Any Input	15	t _{PLH}	9	13	ns
Power Dissipation Capacitance*	_	СРД	22	27	pF

^{*} CPD is used to determine the dynamic power consumption, per gate.

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where:

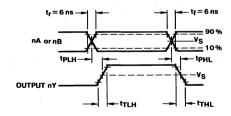
f_i = input frequency.

C_L = output load capacitance.

V_{cc} = supply voltage.

SWITCHING CHARACTERISTICS (C_L = 50 pF, input t_r, t_f = 6 ns)

				25	°C		-4	0°C to	o +85°	,C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	н	C .	н	СТ	74	нс	74F	ICT	54	нс	54F	СТ	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2		120		—		150		-		180		_	
nA, nB to nY	t _{PHL}	4.5	l	24		32		30		40		36		48	ns
		6		20		-		26		_		31		-	
Output Transition	t _{TLH}	2		75		_		95		-		110		-	
Time	t _{THL}	4.5		15		15		19		19		22		22	ns
		6		13		<u> </u>		16				19		—	
Input Capacitance	Ci		_	10	_	10	-	10		10	_	10	_	10	pF

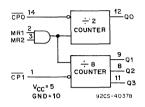


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	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _s	50% V _{cc}	1.3 V

Fig. 2 - Transition times and propagation delay times.

High-Speed CMOS Logic



4-Bit Binary Ripple Counter

Type Features:

- Can be configured to divide by 2, 8, and 16
- Asynchronous Master Reset

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC93 and the CD54/74HCT93 are highspeed silicon-gate CMOS devices and are pin-compatible with low power Schottky TTL (LSTTL). These 4-bit binary ripple counters consist of four master-slave flip-flops internally connected to provide a divide-by-two section and a divide-by-eight section. Each section has a separate clock input (CP0 and CP1) to initiate state changes of the counter on the HIGH-to-LOW clock transition. State changes of the Qn outputs do not occur simultaneously because of internal ripple delays. Therefore, decoded output signals are subject to decoding spikes and should not be used for clocks or strobes.

A gated AND asynchronous master reset (MR1 and MR2) is provided which overrides both clocks and resets (clears) all flip-flops.

Because the output from the divide-by-two section is not internally connected to the succeeding stages, the device may be operated in various counting modes.

In a 4-bit ripple counter the output Q0 must be connected externally to input CP1. The input count pulses are applied to clock input CPO. Simultaneous frequency divisions of 2, 4, 8, and 16 are performed at the Q0, Q1, Q2, and Q3 outputs as shown in the function table. As a 3-bit ripple counter the input count pulses are applied to input CP1.

Simultaneous frequency divisions of 2, 4, and 8 are available at the Q1, Q2, and Q3 outputs. Independent use of the first flip-flop is available if the reset function coincides with the reset of the 3-bit ripple-through counter.

The CD54HC93 and CD54HCT93 are supplied in 14-lead hermetic dual-in-line frit-seal ceramic packages (F suffix). The CD74HC93 and CD74HCT93 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dualin-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

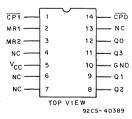
Family Features:

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity:

N_{IL}=30%. N_{IH}=30% of V_{CC}; @ V_{CC}=5 V

■ CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min.

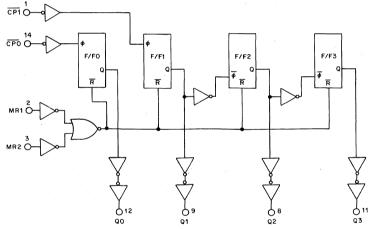
CMOS input compatibility I₁≤1 μA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F,H)	
For T _A = +100 to +125°C (PACKAGE TYPE F,H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	
For $T_A = +70$ to $+125$ °C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F,H	
PACKAGE TYPE E,M	
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C



FUNCTION TABLE (Q0 connected to CP1)

COUNT		OUT	PUTS	
COUNT	Q0	Q1	Q2	Q3
0	L	L	L	L
-1	н :	L ·	L	L
2	L ·	Н	L	L
3	Н	н	L	L
4	L	L	н	L
5	Н	L	н	L
6	L	н	н	L
7	н	н	н	L
8	L	L	L	н
9	Н	L	L	н
10	L	н	L	н
11	H	н	L	н
12	L	L '	н	н
13	H-	L	н	н
14	L	н	н	н
15	н	Н	н	' н

Fig. 1 - HC/HCT93 logic diagram.

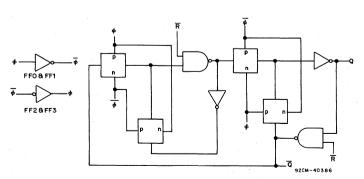


Fig. 2 - Flip-flop (0-3) logic detail.

MODE SELECTION

RESET	INPUTS		OUTPUTS											
MR1	MR2	Q0	Q1	Q2	Q3									
н	н	L	L	L	L									
L	н		CC	unt										
Н	L		cc	unt										
L	L	count												

H = HIGH voltage level

L = LOW voltage level

92CM-40388

STATIC ELECTRICAL CHARACTERISTICS

				CE	74HC	93/C	D54H	C93		-			CD	74HC	T93/C	:D54F	ІСТ9	3			
CHARACTERIS	. 10		TEST	vs	i	IC/54 YPE		74H TYP		54H TYP		TEST CONDITION	NS		CT/54			ICT PES		ICT PES	UNITS
CHAHACTERIS	i iC	V _i	lo	Vcc		+25° C	;	-41 +85		-5: +12!		V,	Vcc		+25° C	;	1	0/ 5° C		5/ 5° C	UNITS
		v	mA	v	Min	Тур	Max	Min	Max	Min	Max	V	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	-	2	-	2	-	V
				6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level				2	_	_	0.5		0.5		0.5		4.5		İ					l	
Input Voltage	VIL			4.5	_	_	1.35		1.35		1.35	_	to	-	_	0.8	_	0.8	-	0.8	V
				6		_	1.8		1.8		1.8		5.5	ļ	ļ		_			<u> </u>	
High-Level		VIL		2	1.9	_	_	1.9	<u> </u>	1.9		VIL							١	1	
Output Voltage	Vон	or	-0.02	4.5	4.4	_	-	4.4	<u> </u>	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	V
CMOS Loads		V _{tH}		6	5.9	_	-	5.9	<u> </u> = -	5.9	_	V _{IH}		-		-		├		├	
TTL Loads		VIL	-4	4.5	3.98	-		3.84		3.7		VIL	4.5	3.98		_	3.84	_	3.7	_	v
TIL Loads		or	<u> </u>	6	_	_	-	5.34	_	5.2		or	4.5	3.98	-	-	3.04	-	3.7	-	· •
Low-Level		VIH	-5.2	2	5.48	=	0.1	5.34	0.1	5.2	0.1	V _{IH}		<u> </u>	-	-	 	-		\vdash	
Output Voltage	Vol	or	0.02	4.5	┢═╌	=	0.1	=	0.1	_	0.1	or	4.5	l_	l _	0.1	_	0.1	_	0.1	v
CMOS Loads	VOL	ViH	0.02	6	=	Ξ-	0.1	_	0.1	-	0.1	ViH	4.5		_	0.1	-	0.1		0	•
Olifoo Loudo		VIL		Ť	-		-		0	-	0.7	VIL	-		<u> </u>		-	 -	_	+	
TTL Loads		or	4	4.5	-	 	0.26	-	0.33	-	0.4	or	4.5	_	-	0.26	l _	0.33	_	0.4	v
		VIH	5.2	6	_	_	0.26	_	0.33	-	0.4	ViH		1				1			
Input Leakage												Any									
Current	h	Vcc	Ì	Ì _					l	1		Voltage			1]	l		١.,	١.
		or		6	-	-	±0.1	-	±1	-	±1	Between	5.5	-	-	±0.1	-	±1	-	±1	μΑ
		Gnd		L				<u></u>		L_		V _{cc} & Gnd	L								
Quiescent		Vcc										V _{cc}									
Device Current	Icc	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
		Gnd	L	<u> </u>					L		l	Gnd			_				<u>_</u>		
Additional													4.5								
Quiescent Device												V _{cc} -2.1	to	_	100	360	_	450	- 1	490	μA
Current per input													5.5								,
pin: 1 unit load	Δlcc*	L							-					1	<u> </u>	L	L	<u> </u>		1	L

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS*
CP0, CP1	0.6
MR1, MR2	0.4

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g. 360 μA max. @ 25° C.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

OUADA OTERICTIO	LIM	ITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage, V _I , V _O	0	V _{cc}	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times, t _r ,t _f :			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input tr,ti=6 ns)

		TYPICAL		
CHARACTERISTIC	C∟ (pF)	НС	HCT	UNITS
Propagation Delay: tplh CP0 to Q0 Output tphL		10	14	
CP1 to Q3	15	21	24	ns
MRn to Qn Output		13	13	
Power Dissipation Capacitance* C _{PD}	_	25	25	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per counter.

 $P_D = C_{PD} V_{CC}^2 fi + \sum C_L V_{CC}^2 f_o$ where $f_i = input$ frequency

fo = output frequency

C_L = output load capacitance

V_{CC} = supply voltage.

PRE-REQUISITE FOR SWITCHING FUNCTION

								LIM	ITS						
		TEST	25° C				-4	0°C to	5 +85°	,C	-5				
CHARACTERISTI	С	CONDITIONS	НС		HCT		74HC		74HCT		541	НС	C 54HCT		UNITS
		V _{cc} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Clock	f _{MAX}	2	6	_	_	_	5	_	_	_	4	_	_	—	
Frequency		4.5	30	-	30	<u> </u>	24	l —	24	l —	20	_	20	-	MHz
		6	35	_	_	—	28	—	—		24	 	—	_	
Clock Pulse Width	tw	2	80	_	_	_	100	_		_	120	_	_	_	
CP0, CP1		4.5	16	-	16	—	20	_	20	_	24	—	24	l —	1
		6	14	l —	l —	_	17	 _			20	_	l —	—	
Reset Pulse Width	tw	2	80	T = _	-	T —	100		_	_	120		—	_	1
		4.5	16	—	16	_	20	_	20	_	24	_	24] —	ns
		6	14	 	-	_	17	-		_	20	_	l —		
Reset Removal Time	t _{REM}	2	50				65		_	_	75	-	_	—	1
		4.5	10	-	10	_	13	_	13	_	15	_	15	_	
		6	9	_	_	l —	11	_	_	_	13	_	<u> </u>		

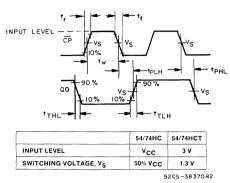


Fig. 3 - Pre-requisite, propagation-delay, and output-transition times.

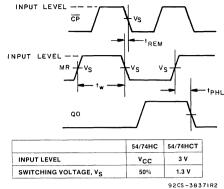
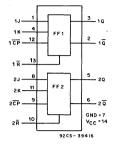


Fig. 4 - Master-Reset pre-requisite and propagation-delay times.

SWITCHING CHARACTERISTICS (C_L=50 pF, Input t_r,t_f=6 ns)

								LIM	ITS						
				25° C -40° C to +85° C									+125	°C	1
CHARACTERIS	STIC	VCC	Н	С	Н	CT	74	НС	74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	<u> </u>	125	_		<u> </u>	155	_	_		190	_	Γ-	
Time:	tpHL	4.5	—	25	—	34	—	31	—	43	_	38	_	51	1
CP0 to Q0		6	—	21	_	-	l —	26	_	—	_	32	_	<u> </u>	
		2		135	_	_	_	170	_	[—	-	205	T —	T-	
CP1 to Q1		4.5	—	27	-	34	l —	34	_	43	-	41	_	51	
		6	_	23	—	 	_	29	_		—	35	—	-	
		2	_	185	Γ-	_	_	230	_	_	T	280	T-	-	
CP1 to Q2		4.5	_	37	-	46	_	46	-	58	l —	56	_	69	
		6		31	l —	_	l —	39		_	_	48	_	_	ns
		2	_	245	_	T	_	305	_	_		370	_	_	1115
CP1 to Q3		4.5	—	49	—	58	l —	61	_	73		74	-	87	l
		6	—	42		_		52	_		_	63	_	l —	
		2	_	155	_		_	195	_		_	235			
MR1, MR2 to Qn		4.5	—	31	—	33	<u> </u>	39	_	41	_	47	—	50	ļ
		6		26		_	_	33	_		_	40	_	_	
Output Transition	t _{THL}	2	_	75	_	_	_	95	_	-	_	110	I —	-	
Time	t _{TLH}	4.5	-	15	—	15	—	19		19	_	22	—	22	
		6	_	13	<u> </u>	_		16			_	19	_		
Input Capacitance	Cı		_	10	_	10	_	10	_	10	-	10	_	10	pF

High-Speed CMOS Logic



Dual J-K Flip-Flop with Reset

Negative-Edge Trigger

Type Features:

- Hysteresis on clock inputs for improved noise immunity and increased input Rise and Fall times.
- Asynchronous Reset
- Complementary Outputs
- Buffered Inputs
- Typical $f_{\text{max}} = 60 \text{ MHz}$ @ $V_{\text{CC}} = 5V$, $C_{\text{L}} = 15 \text{ pF}$, $T_{\text{A}} = 25^{\circ}\text{C}$

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC107 and CD54/74HCT107 utilize silicon-gate CMOS technology to achieve operating speeds equivalent to LSTTL parts. They exhibit the low power consumption of standard CMOS integrated circuits, together with the ability to drive 10 LSTTL loads.

These flip-flops have independent J, K, Reset and Clock inputs and Q and \overline{Q} outputs. They change state on the negative-going transition of the clock pulse. Reset is accomplished asynchronously by a low-level input.

This device is functionally identical to the HC/HCT73 but differs in terminal assignment and in some parametric limits.

The 54HCT/74HCT logic family is functionally as well as pin-compatible with the standard 54LS/74LS logic family.

The CD54HC107 and CD54HCT107 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC107 and CD74HCT107 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

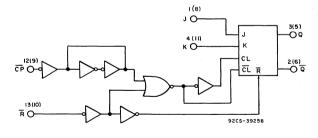


Fig. 1 - Logic diagram.

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:
 2 to 6 V Operation
 High Noise Immunity:
- N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V ■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility

 $V_{\rm IL}$ = 0.8 V Max., $V_{\rm IH}$ = 2 V Min. CMOS Input Compatibility $I_{\rm I} \le 1~\mu A \ @ V_{\rm OL}, V_{\rm OH}$

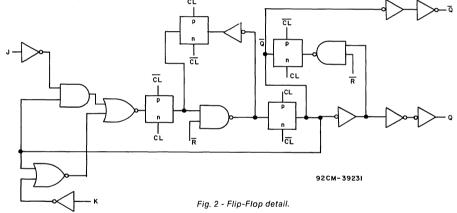
TRUTH TABLE (EACH FLIP-FLOP)

	INPL	OUTPUTS						
R	CP	J	к	Q	ā			
L	X	Х	Х	L	Н			
н	~	L	L	No C	hange			
Н	_	Н	L	н	L			
н	~	L	Н	L	Н			
Н	~	Н	н	Tog	ggle			
Н	н	Х	×	No Change				

H = High Level (Steady State) L = Low Level (Steady State) X = Irrelevant
 = High-to-Low
transition

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{1K} (FOR $V_1 < -0.5$ V OR $V_1 > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT, (I _{CC}):	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For $T_A = -40$ to $+70$ °C (PACKAGE TYPE M)	400 mW
For $T_A = +70$ to $+125$ °C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (T _{stg})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C
CI	^ ^



RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

OLIADA OTERIOTIO	LIMITS						
CHARACTERISTIC	MIN.	MAX.	UNITS				
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} : *							
CD54/74HC Types	2	6	V				
CD54/74HCT Types	4.5	5.5	V				
DC Input or Output Voltage V _I , V _o	0	Vcc	V				
Operating Temperature T _A :							
CD74 Types	-40	+85	°C				
CD54 Types	-55	+125	°C				
Input Rise and Fall Times, t _r , t _f ●							
at 2 V	О	1000	ns				
at 4.5 V	. 0	500	ns				
at 6 V	0	400	ns				

- * Unless otherwise specified, all voltages are referenced to Ground.

 Applicable for all inputs except clock.

STATIC ELECTRICAL CHARACTERISTICS

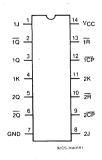
				CD7	4HC1	07, C	D54H	C107					CD7	4HC1	107,	CD54	нст	107			
			TEST DITIO	NS	ı	IC/54 YPE		741 TYF		54H TYF	-	TEST CONDITION		74H0	CT/54			ICT PES		ICT PES	
CHARACTERIS	TIC	V,	lo	V _{cc}		∙25° C	;	-4 +85		-5: +12!		V ₁	Vcc		+25° C	:	l	0/ 5° C	l	5/ 5° C	UNITS
		v	mA	٧	Min	Тур	Max	Min	Max	Min	Max	v	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	-	1.5	_	1.5	_		4.5								
Input Voltage	V_{IH}			4.5	3.15	_	_	3.15		3.15	_	_	to	2		-	2	-	2	-	V
				6	4.2	-	-	4.2		4.2			5.5								٠.
Low-Level		Į		2	_	_	0.5	_	0.5		0.5		4.5	l		ļ					
Input Voltage	VIL			4.5		_	1.35	_	1.35	_	1.35	_	to	-	-	8.0	_	8.0	-	0.8	٧
				6	<u> </u>	_	1.8		1.8	_	1.8		5.5	<u> </u>	L						
High-Level		VIL		2	1.9	_	-	1.9	<u> </u>	1.9		VIL		l	l			Į			
Output Voltage	V_{OH}	or	-0.02	4.5	4.4	<u> </u>	<u> </u>	4.4	<u> </u>	4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	٧
CMOS Loads		VIH		6	5.9	_	_	5.9	<u> - </u>	5.9		V _{IH}		ļ	<u> </u>			ļ		<u> </u>	
		VIL		_			<u> </u>					VIL						l			
TTL Loads		or	-4	4.5	3.98	_	<u> </u>	3.84	<u> _ </u>	3.7		or	4.5	3.98	-	-	3.84	-	3.7	-	٧
		V _{IH}	-5.2	6	5.48		<u> </u>	5.34		5.2		V _{iH}						<u> </u>		<u> </u>	
Low-Level		VIL	l	2	_		0.1	<u> —</u>	0.1		0.1	VIL		İ				ŧ	ļ		
Output Voltage	V_{OL}	or	0.02	4.5		_	0.1	<u> </u>	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	٧
CMOS Loads		V _{IH}		6		ᄂ	0.1	ᆫ	0.1		0.1	V _{IH}		<u> </u>					L	ļ	
		VIL		_				<u> </u>	L			V _{IL}			İ						
TTL Loads		or	4	4.5	_	_	0.26	ᄂ	0.33	<u> </u>	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
		V _{IH}	5.2	6	<u> </u>	_	0.26	<u> </u>	0.33		0.4	VIH		ļ	ļ	<u> </u>		ļ	_	<u> </u>	
Input Leakage		Vcc	1		ļ				ļ			Any									
Current	lı.	or		6	_		±0.1	_	±1	_	±1	Voltage	5.5	_	l —	±0.1	_	±1	_	±1	μΑ
		Gnd										Between					1				Ì
		 		<u> </u>		_	-	├-	-	_	<u> </u>	V _{cc} & Gnd	<u> </u>	┼	<u> </u>		├		 	\vdash	-
Quiescent		Vcc		l _		1	1.					Vcc				4		40		80	١.
Device Current	Icc	or	0	6	-	-	4	-	40	-	80	or	5.5	-	-	"	_	40	-	80	μA
Addisings		Gnd	L	L		L		L	Ļ.,			Gnd		-	-	 	<u> </u>	+	-	 	-
Additional													4.5								
Quiescent Device Current per input												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	A1 *												5.5				1				
pin. i unit.ioad	Δlcc*.	1												<u> </u>			<u></u>			1	L

 $^{^{\}star}$ For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads *
All	0.3

^{*} Unit Load is $\Delta l_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.



TERMINAL ASSIGNMENT

SWITCHING CHARACTERISTICS (Vcc=5 V, T_A=25°C, Input t_r, t_f=6 ns)

		C _∟	TYPI	CAL	
CHARACTERISTIC		(pF)	нс	нст	UNITS
Propagation Delay CP to Q	t _{PLH} t _{PHL}	15	14	18	ns
CP to Q			14	17	ns
\overline{R} to Q, \overline{Q}			13	16	ns
CP Frequency	f _{max}	15	60	56	MHz
Power Dissipation Capacitance*	C _{PD}		31	30	pF

^{*} C_{PD} is used to determine the dynamic power consumption, per flip-flop.

 $P_D = C_{PD} V_{CC}^2 f_i + \sum_i C_L V_{CC}^2 f_o \qquad \text{where } f_i = \text{input frequency, } f_o = \text{output frequency,}$

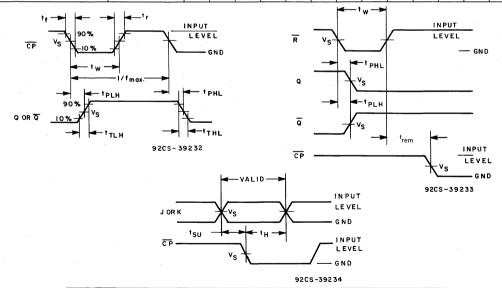
 C_L = output load capacitance, V_{CC} = supply voltage.

PRE-REQUISITE FOR SWITCHING FUNCTION

			LIMITS												
CHARACTERIS	T10	TEST CONDITION		25	°C		-4	0°C to	+85°	С	-5	UNITS			
CHARACTERIS	iic		н	С	н	СТ	741	нс	74F	ICT	54	нс	54F	ICT	UNITS
		V _{cc} V	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Pulse Width	tw	2	80	-	_	_	100	_	_	_	120	_	_	_	
CP		4.5	16	_	18	-	20	—	23	—	24	-	27	-	ns
		6	14				17		_		20		_		
		2 _.	80	_	—	—	100	—	-	-	120	-	—	_	
R		4.5	16	-	24	—	20	-	30	—	24	-	36	-	ns
		6	14	_	_		17	_			20		_	_	
Set-up Time	t_{SU}	2	100	-	—	—	125	-	—	—	150	-	-	-	}
J, K to CP		4.5	20	-	20	—	25	-	25	-	30	-	30	-	ns
		6	17		_		21				26		_		
Hold Time	t _H	2	3	_	_	_	3	-	_	_	3	-	_	-	
J, K to CP		4.5	3	-	5	-	3	—	5	-	3	-	5	—	ns
		6	3	<u> </u>	_	_	3		_		3	_			
Removal Time	t_{rem}	2	60	-	—	-	75	-	—	l —	90	-	_	-	
		4.5	12	—	12	-	15	-	15	—	18	-	18	—	ns
		6	10	_	_		13	_	_	_	15	_		_	
CP Frequency	f_{max}	2	6	-	—	-	5	—	-	—	4	-	—	—	
		4.5	30	-	28	-	25	-	22	-	20	-	19	-	MHz
L		6	35				29		_		23	_			

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

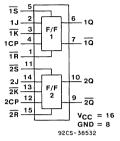
			LIMITS												
01145407751		TEST	25° C					0°C to	o +85°	,C	-55				
CHARACTERIS	STIC		нс		нст		74HC		74HCT		54HC		54НСТ		UNITS
		V _{cc} V	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Propagation	t _{PLH}	2	_	170	_	_	_	215	_	_	-	255	_	_	
Delay	t _{PHL}	4.5	_	34	_	43	_	43	<u> </u>	54	_	51	_	65	ns
CP to Q		6	_	29	_	_	_	37	_	_	_	43		_	
		2		170	l —	_	_	215	_	_	_	255	_	-	
CP to Q		4.5	_	34	 	40	_	43	_	50	_	51	_	60	ns
		6	_	29	_	_	_	37	_	_	_	43		_	
		2	_	155	_	Ī —	l —	195	_	_	_	235	_	_	
R to Q, Q		4.5	_	31	_	38	_	39	-	48	-	47	_	57	ns
		6		26	_	_	<u> </u>	33	_	-	_	40	_	_	
Output	t _{TLH}	2	_	75	_	_	I —	95	_	_	_	110	-	-	
Transition	t _{THL}	4.5	-	15		15	_	19	-	19	_	22	-	22	ns
Time		6	_	13	_	_	_	16	_	_		19		_	
Input Capacitance	Сı		_	10	_	10	_	10	_	10	_	10	_	10	pF



	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _s	50% V _{CC}	1.3 V

Fig. 3 - Transition times, propagation delay times, and setup and hold times.

High-Speed CMOS Logic



Dual J-K Flip-Flop with Set and Reset

Type Features:

- Positive-Edge triggered
- Asynchronous Set and Reset
- 60 MHz Typical Maximum Clock Frequency @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C
- Typical Propagation Delay = 18 ns @ $V_{cc} = 5V$, $C_L = 15pF$, $T_A = 25^{\circ}C$
- Schmitt Trigger Clock Inputs

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC109 and CD54/74HCT109 are dual J-K flip-flops with set and reset. The flip-flop changes state with the positive transition of Clock (1CP and 2CP).

The flip-flop is set and reset by active-low \bar{S} and \bar{R} , respectively. A low on both the set and reset inputs simultaneously will force both Q and \bar{Q} outputs high. However, both set and reset going high simultaneously results in an unpredictable output condition.

The CD54HC109 and CD54HCT109 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC109 and CD74HC1109 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads
- Bus Driver Outputs 15 LSTTL Loads Wide Operating Temperature Range: CD74HC/HCT: —40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noice Immunity: N_{IL} = 30%, N_{IH} = 30% of Vcc @ Vcc = 5 V
- ©CD54HCT/CD74HCT Types:

 4.5 to 5.5 V Operation
 Direct LSTTL Input Logic Compatibility
 V_L = 0.8 V Max., V_{III} = 2 V Min.
 CMOS Input Compatibility
 I_I ≤ 1 uA @ Vo.. VoH

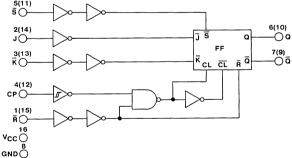
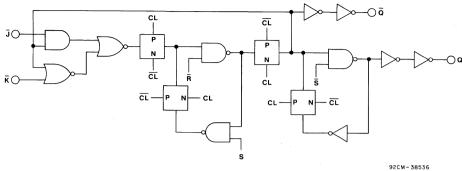


Fig. 1 - Logic diagram

TRUTH TABLE

		Inputs			Outputs
s	Ŕ	СР	J	ĸ	Q Q
L H L H H H H H	ппппппппппппппппппппппппппппппппппппппп	××× 	XXLHLHX	X X L L H H	H L L H H' H' TOGGLE NO CHANGE NO CHANGE

*Unpredictable and unstable condition if both \overline{S} and \overline{R} go high simultaneously.



DETAIL OF FLIP-FLOP

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i \le -0.5 \text{ V OR } V_i \ge V_{CC} +0.5 \text{V}$)	+ 20 mA
DC OUTPUT DIODE CURRENT, lok (FOR $V_0 < -0.5$ OR $V_0 > V_{CC} + 0.5$ V)	+ 20 mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _O < V _{CC} +0.5 V)	+ 25 mA
DC Vcc OR GROUND CURRENT (Icc):	+ 50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	erate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	erate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For $T_A = +70$ to $+125^{\circ}$ C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING -TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H PACKAGE TYPE E, M	55 to +125°C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tsig)	65 +150°C
LEAD TEMPERATUARE (DURING SOLDERING):	
At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC		L	MITS	UNITS
CHARACTERISTIC		MIN.	MAX.	UNITS
Supply-Voltage Range (For TA = Full Package-Tem	perature Range) Vcc:*			
CD54/74HC Types		2	6	V
CD54/74HCT Types		4.5	5.5	
DC Input or Output Voltage V ₁ V ₀		0	Vcc	V
Operating Temperature T _A :				
CD74 Types		-40	+85	
CD54 Types		-55	+125	°C
Input rise and Fall Times tr. tr				
All inputs Except CP	at 2 V	0	1000	
	at 4.5 V	0	500	ns
	at 6 V	0	400	1
Input Rise and Fall Times tr, tf				1
For CP	at 2 V	0	unlimited	มร
	at 4.5 V	0		
	at 6 V	0		1

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

	CD74HC109 / CD54HC109									CD74HCT109 / CD54HCT109									
	TEST		741	HC/54	нс	74	нс	54	нс	TEST 74HCT/54HCT					74HCT		541	ют	
СО	NDITIONS	.	TYPES TYPES TYPE			PES	CONDIT	S TYPES			TYPES		TYPES		UNITS				
1 ' 1 1		1	+ 25		+ 25°C		-40/ + 85°C			νı	Vcc	+ 25° C			-40/ + 85° C		-55/ + 125°C		
\ \ \	mA	"	Min	Тур	Max	Min	Max	Min	Max	ľ	\	Min	Тур	Max	Min	Max	Min	Max	
	ļ - ·	2	1.5	-	-	1.5	_	1.5	_		4.5								
		4.5	3.15	_	-	3.15	_	3.15	_		to	2	_	-	2	_	2	-	v
1		6	4.2	-	-	4.2	-	4.2	_		5.5								
		2	<u> </u>	_	0.5	_	0.5	_	0.5		4.5								
		4.5	_	-	1.35	-	1.35		1.35		to	-	-	0.8	-	0.8	۱ –	0.8	v
		6	_	_	1.8	_	1.8	_	1.8		5.5								
VIL		2	1.9	_	_	1.9	_	1.9	1	VIL									
or	-0.02	4.5	4.4	_	_	4.4	-	4.4	-	or	4.5	4.4	_	-	4.4	_	4.4	_	v
Vін		6	5.9	_	-	5.9	_	5.9	_	ViH									
VIL										VIL									
or	-4	4.5	3.96	_	_	3.84	_	3.7	_	or	4.5	3.98	-	_	3.84	-	3.7	-	v
VIH	-5.2	6	5.48	_		5.34	_	5.2		Vıн									
VIL		2	_	_	0.1	_	0.1	_	0.1	VIL									
or	0.02	4.5	<u> </u>	<u>_</u>	0.1	_	0.1		0.1	or	4.5	-	_	0.1	-	0.1	l –	0.1	v
ViH		6	_	_	0.1	_	0.1		0.1	ViH									
VIL							<u> </u>			VIL					1				
or	4	4.5	<u></u>	_	0.26		0.33	_	0.4	or	4.5	-	_	0.26	-	0.33	_	0.4	v
Vін	5.2	6	_	_	0.26	_	0.33	_	0.4	ViH						L			
Vcc			•							Any Voltage									
or		6	-	—	±0.1	-	<u>±</u> 1	-	±1	Vcc	5.5	-	-	±0.1	_	±1	-	±1	
Gnd				L_		<u> </u>				Gnd									Αu
Vcc										Vcc				1					
or	0	6	_	-	4	-	40	_	80	or	5.5	-	_	4	-	40	-	80	Αц
Gnd										Gnd				L		L		L	
											4.5								
										Vcc-2.1	to	-	100	360	-	450	-	490	Ац
	VIL or VIH VIL or VIH VIL or VH VCC or Gnd VCC	VI IO MA VIL OT -0.02 VIH VIL OT 4 VIH OT 4 VIL OT 4 VIH 5.2 VIL OT 4 VIH 5.2 VCC OT GIND GIND GIND VCC OT 0 GIND GIND	Vi	TEST CONDITIONS	TEST CONDITIONS TYPE VI IO VCC V MIN TYPE 4.5 3.15 — 4.5 3.15 — 6. 4.2 — 4.5 — 4.5 — 6. — 7. — 7. — 7. — 7. — 7. — 7. — 7. — 7	TEST 74HC/54HC TYPES V	TEST CONDITIONS TYPES TY	TEST CONDITIONS TYPES TYPES VI N N N N N N N N N N N N N N N N N N	TEST CONDITIONS TYPES TY	TEST CONDITIONS V	TEST CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS	TEST CONDITIONS TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES CONDITIONS 10	TEST CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES CONDITIONS TYPES	TEST THE TYPES TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES CANDITIONS TYPES CON	TEST CONDITIONS TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES CONDITIONS TYPES TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES	TEST CONDITIONS TYPES TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES CONDITIONS TYPES TOPS	TEST CONDITIONS TYPES TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES T	TEST CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES TYPES CONDITIONS TYPES TYPES TYPES TYPES TYPES TYPES TOPICA 45	TEST CONDITIONS 74HC/54HC TYPES TOPICA TOPICA TYPES TYPES TYPES TYPES TYPES TOPICA TOPICA TYPES TYPES TYPES TYPES TYPES TYPES TOPICA TOPICA TYPES TOPICA TOPICA TYPES TOPICA TYPES TOPICA TYPES TOPICA

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
All	0.3

^{*}Unit Load is Alcc limit specified in Static Characteristics Chart, e.g., 360 µA max. @ 25°C

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA, = 25°C, Input t,t = 6 ns)

			Тур	ical	
CHARACTERISTIC		CL (pF)	54/74HC	54/74HCT	UNITS
Propagation Delay, CP → Q, Q	tрін tpнi	15	14	17	ns
Ī → Q	tегн	15	9	12	ns
Ī→Ā	tрнг	15	13	19	ns
Ā → Q	tрнц	15	15	19	ns
Ā → Q	tегн	15	14	15	ns
CP Frequency	f _{MAX}	15	60	54	MHz
Power Dissipation Capacitance*	C _{PD} *	_	30	33	pF

*CPD is used to determine the dynamic power consumption, per flip-flop.

PD = $C_{PD} V_{CC}^2 fi + \sum V_{CC}^2 C_L$ fo where:

fi = Input Frequency

C_L = Output Load Capacitance

V_{cc} = Supply Voltage fo = Output Frequency

PREREQUISITE FOR SWITCHING FUNCTION

								LIN	AITS						
CHARACTERISTIC		TEST CONDITION		25	°C		-4	10°C t	o +85	°C	-5	5°C to +125°C			UNITS
		Vcc		IC	н	СТ	74	нс	741	нст	54	нс	54H	нст	
		Vec	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Set-up Time	tsu	2	80		l _		100		_		120		_		
J, \overline{K} to CP		4.5	16		18		20		23		24		27	ļ	ns
		6	14		_		1.7		_		20				
Hold Time	th	2	5		-		5		_		5		_		
J, \vec{K} to CP		4.5	5		3		5		3		5		3		ns
		6	5		_		5		_		5		_		
Removal Time	trem	2	80		_		100	i	_		120		_		
$ar{R},ar{S}$ to CP		4.5	16		18		20		23		24		27		ns
		6	14				17		_		20			<u> </u>	
Pulse Width	tw	.2	80		_		100		_		120		_		
CP, R, Š		4.5	16		18		20		23		24		27		ns
		6	14		_		17		_	· .	20				
CP Frequency	fmax	2	6		_		5		_		4		_		
		4.5	30	1	27		25		22		20	Ì	18		MHz
		6	35	1	-		29		_	l	23		_		

SWITCHING CHARACTERISTICS (CL = 50 pF, Input tr, tr = 6 ns)

				25	°C		-4	0°C to	+ 85	°C	-55	5°C to	+ 125	5°C	
CHARACTERISTIC		Vcc	Н	C	Н	CT	74	НС	741	1CT	54	нс	54F	ICT	
CHARACTERISTIC		Vcc	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	UNITS
Propagation Delay,	t _{PHL}	2		175		_		220		_		265		_	
$CP \rightarrow Q, \bar{Q}$	t PHL	4.5	}	35		40	l	44		50		53		60	ns
		6		30		_		37				45		_	
		2		120		_		150		_		180		_	
$\bar{S} \rightarrow Q$	t PLH	4.5		24	ļ	30		30		38		36		45	ns
		6		20				26				31			
		2		155		_		195		_		235		_	
S̄ → Q̄	t PHL	4.5	l	31		45	ļ	39	ļ	56	ļ	47		68	ns
		6		26				33		—		40		_	
		2		185				230		-		280			
$\overline{R} \to Q$	t PHL	4.5		37		45		46		56		56		68	ns
		6		31		_		39				48		<u> </u>	
		2		170		_		215		-		255		-	
$\overline{R} \to \overline{Q}$	t PLH	4.5		34		37		43		46		51		56	ns
		6		29				37		_		43			
Transition	t_{TLH}	2		75	1		İ	95		-	i .	110		-	
Times	t _{THL}	4.5	ł	15		15		19		19		22		22	ns
		6		13			L	16				19			
Input				_		_		-		-		_		_	
Capacitance	С			10	l	10		10		10		10		10	pF
				_		-		_		_		_		<u> </u>	

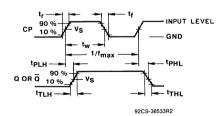


Fig. 2 - Clock to output delays and clock pulse width.

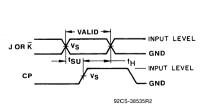


Fig. 4 - Data set-up and hold times.

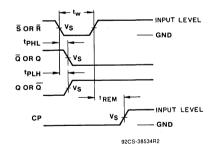
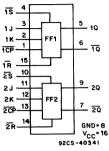


Fig. 3 - Reset or Set prerequisite and propagation delays.

	54/74 HC	54/74 HCT
Input Level	Vcc	3V
Switching Voltage, Vs	50% V cc	1.3V

High-Speed CMOS Logic



Type Features:

Dual J-K Flip-Flop with Set and Reset

Negative-Edge Trigger

- Hysteresis on clock inputs for improved noise immunity and increased input rise and fall times
- Asynchronous set and reset
- Complementary outputs
- Buffered inputs
- Typical $f_{\text{max}} = 60 \text{ MHz}$ @ $V_{\text{CC}} = 5 \text{ V}$, $C_{\text{L}} = 15 \text{ pF}$, $T_{\text{A}} = 25^{\circ} \text{ C}$

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC112 and CD54/74HCT112 utilize silicon-gate CMOS technology to achieve operating speeds equivalent to LSTTL parts. They exhibit the low power consumption of standard CMOS integrated circuits, together with the ability to drive 10 LSTTL loads.

These flip-flops have independent J, K, Set, Reset, and Clock inputs and Q and $\overline{\mathbf{Q}}$ outputs. They change state on the negative-going transition of the clock pulse. Set and Reset are accomplished asynchronously by low-level inputs.

The 54HCT/74HCT logic family is functionally as well as pin-compatible with the standard 54LS/74LS logic family.

The CD54HC112 and CD54HCT112 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC112 and CD74HCT12 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

TRUTH TABLE (EACH FLIP-FLOP)

		OUTPUTS								
s	R	CP	J	К	a	ia				
L	Н	х	Х	Х	н	L				
Н	L	X	х	Х	L	н				
L	L	х	Х	х	н⁺	l L*				
н	Н	\sim	L	L	No CI	nange				
Н	Н	_	Н	L	н	L				
н	Н	~	L	н	L	н				
Н	Н	_	н	н	Toggle					
Н	Н	Н	Х	Х	No Change					

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 μA @ V_{OL}, V_{OH}

H = High steady state.

L = Low steady state.

X = Irrelevant.

= High-to-Low transition.

Output states unpredictable if S and R go High simultaneously after both being low at the same time.

MAXIMUM RATINGS, Absolute-Maximum Values:

GE, (V _{CC}):	DC S
ed to ground)	(V
JRRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} +0.5$ V)	DC I
CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} +0.5$ V)	DC (
Γ , PER OUTPUT (I ₀) (FOR -0.5 V < V ₀ < V _{0c} +0.5 V)	DC I
CURRENT, (lcc):	DC \
N PER PACKAGE (P₀):	POV
C (PACKAGE TYPE E)	Fo
°C (PACKAGE TYPE E)	Fo
)°C (PACKAGE TYPE F, H)500 mW	Fo
25°C (PACKAGE TYPE F, H)	Fo
C (PACKAGE TYPE M)	Fo
5°C (PACKAGE TYPE M)	Fo
RATURE RANGE (T _A):	OPE
H	PΑ
M40 to +85° C	PA
*TURE (T _{stg})65 to +150° C	STO
E (DURING SOLDERING):	
1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	At
PC board (min. thickness 1/16 in., 1.59 mm)	
cting lead tips only+300° C	

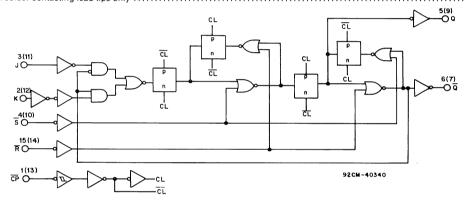


Fig. 1 - Flip-flop logic diagram.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN	птѕ	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	٧
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _f ●			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*} Unless otherwise specified, all voltages are referenced to Ground.

Applicable for all inputs except clock.

STATIC ELECTRICAL CHARACTERISTICS

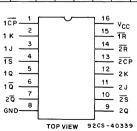
			CD74HC112, CD54HC112									CD74HCT112, CD54HCT112									
0.04.04.0750.071.0			TEST IDITIOI	NS		IC/54 TYPE		741 TY		54I TY		TEST		1	CT/54 TYPE			PE		ICT PE	UNITS
CHARACTERISTICS	•	V _I	lo	Vcc	,	•25° C	;	-4 +85		-5 +12		V,	V _{cc}	+25°C		;	-40 +85°		-55/ +125°		UNITS
		٧	mA	٧	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	ViH			4.5	3.15			3.15	_	3.15	_	_	to	2		_	2	_	2	_	٧
				6	4.2			4.2		4.2			5.5								
Low-Level				2	_	_	0.5	_	0.5		0.5		4.5								
Input Voltage	VıL			4.5	_	_	1.35		1.35	_	1.35	_	to	_	_	0.8	_	0.8	-	0.8	V
				6	_	_	1.8	_	1.8		1.8		5.5								
High-Level		VIL		2	1.9	_	L_	1.9		1.9	_	VIL									
Output Voltage	Vон	or	-0.02	4.5	4.4		_	4.4		4.4		or	4.5	4.4	_	_	4.4	_	4.4	_	V
CMOS Loads		V _{IH}		6	5.9	_	_	5.9	_	5.9	-	V _{IH}									
		٧٦										ViL									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7		or	4.5	3.98	_	_	3.84	_	3.7	_	v
		VIH	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level		VIL		2	_		0.1	_	0.1	_	0.1	ViL									
Output Voltage	VoL	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads		V _{IH}		6	_	_	0.1	_	0.1	_	0.1	ViH		ļ							
		VIL										VIL									
TTL Loads		or	4	4.5	_	_	0.26		0.33	_	0.4	or	4.5	_	_	0.26		0.33	_	0.4	v
		V _{IH}	5.2	6	_	_	0.26		0.33	_	0.4	V _{IH}									
Input Leakage Current	l _t	V _{cc} or Gnd		6		_	±0.1		±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1	_	±1	μΑ
Quiescent Device Current	Icc	Vcc										Vcc									
		or Gnd	0	6	-	_	4	-	40	-	80	or Gnd	5.5	-	_	4	_	40	-	80	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load Δ	vlcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{cc} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
1S, 2S	0.5
1K, 2K	0.6
1R, 2R	0.65
1J, 2J, 1CP, 2CP	1

^{*} Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.



TERMINAL ASSIGNMENT

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r , t_f = 6 ns)

	CHARACTERISTIC						
CHARACTERISTIC	C∟ (pF)	нс	нст	UNITS			
Propagation Delay							
\overline{CP} to Q, \overline{Q}	t _{PLH} , t _{PHL}	15	14	14	ns		
S to Q, Q]	13	13	ns		
\overline{R} to Q, \overline{Q}			15	14	ns		
CP Frequency	f _{max}	15	60	60	MHz		
Power Dissipation Capacitance *	C _{PD}	_	12	20	pF		

^{*} C_{PD} is used to determine the dynamic power consumption, per flip-flop.

 P_{D} = $C_{PD} \; V_{CC}{}^2 f_i + \Sigma \; C_L \; V_{CC}{}^2 f_o$ where: f_i = input frequency

C_L = output load capacitance

fo = output frequency

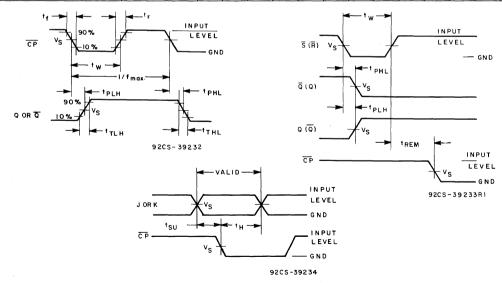
V_{cc} = supply voltage

PRE-REQUISITE FOR SWITCHING FUNCTION

			LIMITS														
	CHARACTERISTIC		TEST 25°C -40°C to +85°C									-55°C to +125°C					
CHARACTERISTIC		CONDITION	Н	С	н	СТ	741	нс	741	ICT	54	нс	54НСТ		UNITS		
		V _{cc} V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.			
Pulse Width	tw	2	80	_	_	_	100	_	_	_	120	-	_	_			
CP		4.5	16		16	—	20	—	20	-	24	_	24	-	ns		
		6	14	_			17	_	_		20		_				
		2	80	-	_	_	100	-	_	-	120	_	_	-			
R, S		4.5	16	-	18	-	20	—	23	—	24		27	-	ns		
		6	14			_	17	_	_	_	20		_	<u>L</u> -			
Set-up Time	tsu	2	80	_	_	_	100	_	-	_	120	_	_	_			
J, K to $\overline{\sf CP}$		4.5	16	-	16	-	20	-	20	-	24	_	24	-	ns		
		6	14	_	<u>L</u>		17			_	20	_	_				
Hold Time	/ t _H	2	0	-	-	-	0	_	-	-	0	_	_	-			
J, K to \overline{CP}		4.5	0	_	3	-	0	-	3	_	0	-	3	-	ns		
		6	0			<u> </u>	0				0	_					
Removal Time	t _{REM}	2	80	-	-	-	100	-	_	-	120	-	-	-			
R to CP		4.5	16	-	20	-	20	-	25	—	24	-	30	-	ns		
S to CP		6	14				17			_	20	_	_				
CP Frequency	f _{max}	2	6	-	-	_	5	_	_	-	4	_	-	-			
		4.5	30	-	30	-	25	-	25	_	20	-	20	-	MHz		
		6	35	_			29		_		23						

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

							LIMITS												
CHARACTERIST	10	TEST CONDITION		25	°C	С		-40°C to +85°C				5°C to	+125	°C	UNITS				
CHARACTERIST			нс		нст		74HC		74HCT		54HC		54HCT		UNITS				
		V _{cc} V	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.					
Propagation	t _{PLH}	2	_	175	_	_	-	220	-	_	-	265	_	_					
Delay	t _{PHL}	4.5	-	35	-	35	-	44	-	44	_	53	—	53	ns				
CP to Q, Q		6	_	30	_	_		37				45	_						
		2	-	155	_	_	_	195	-	_	-	235	-	-					
Ŝ to Q, Q		4.5	-	31	-	32	-	39	-	40	-	47	—	48	ns				
		6	_	26	_	_		33	_	1		40	_						
		2	_	180		_	_	225	_	_	_	270	_	-					
\overline{R} to Q, \overline{Q}		4.5	-	36	-	37	-	45	-	46	-	54	-	56	ns				
		6		31				38	_	<u>L</u>	_	46							
Output Transition	t_{TLH}	2	-	. 75	<u> </u>	-	_	95	-	-	-	110	-	-					
Time	t_{THL}	4.5	-	15	_	15	—	19	_	19	_	22	-	22	ns				
		6	_	13	_			16		_	_	19		_					
Input Capacitance	Cı		_	10	_	10	_	10	_	10	_	10	_	10	pF				



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

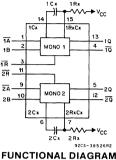
Fig. 2 - Transition times, propagation delay times, and setup and hold times.

File Number 1708

Advance Information/ Preliminary Data

CD54/74HC123, CD54/74HCT123 CD54/74HC423, CD54/74HCT423

High-Speed CMOS Logic



Dual Retriggerable Monostable Multivibrators with Resets

Type Features:

- Overriding RESET Terminates Output Pulse
- Triggering From the Leading or Trailing Edge
- Q and Q Buffered Outputs
- Separate Resets
- Wide Range of Output-Pulse Widths
- Schmitt Trigger on both A and B inputs

The RCA-CD54/74HCT123,423 and CD54/74HCT123,423 are dual monostable multivibrators with resets. They are all retriggerable and differ only in that the 123 types can be triggered by a negative-to-positive reset pulse; whereas the 423 types do not have this feature. An external resistor (R_x) and an external capacitor (Cx) control the timing and the accuracy for the circuit. Adjustment of Rx and Cx provides a wide range of output pulse widths from the Q and Q terminals. Pulse triggering on the A and B inputs occur at a particular voltage level and is not related to the rise and fall times of the trigger pulses.

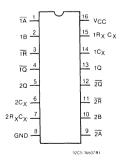
Once triggered, the output pulse width may be extended by retriggering inputs A and B. The output pulse can be terminated by a LOW level on the Reset (R) pin. Trailing-edge triggering (A) and leading-edge triggering (B) inputs are provided for triggering from either edge of the input pulse. If either Mono is not used each input on the unused device (A, B, and R) must be terminated high or low.

The minimum value of external resistance, Rx is typically 500 Ω . The minimum value external capacitance, C_x , is 0 pF. The calculation for the pulse width is $t_w = 0.45 R_x C_x$ at $V_{CC} =$

The CD54HC123,423 and CD54HCT123,423 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC123,423 and CD74HCT123,423 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16lead dual-in-line surface mount plastic packages (M suffix). All types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5$ V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility $V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.$ CMOS Input Compatibility $I_1 \leq 1 \,\mu A \otimes V_{OL}, \, V_{OH}$



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

							D54F					CD74HCT123/CD54HCT123 CD74HCT423/CD54HCT423								l.	
CHARACTERIS	T 10	i	TEST IDITIO	NS		IC/54		74HC 54H TYPES TYPE			TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		}	
CHARACTERIS	iic	V ₁	lo	v cc		+25° C	;	-4 +85	0/ 5° C	-5 +12		V ₁	Vcc		+25° C	;		0/ 5° C	1 -	5/ 5° C	UNITS
		V	mA	v	Min	Тур	Max	Min	Max	Min	Max	٧	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level	· · · · · · · · · · · · · · · · · · ·			2	1.5	-	-	1.5	-	1.5	_		4.5								
Input Voltage	V_{IH}			4.5	3.15	_		3.15	_	3.15	-	_	to	2	_	-	2	_	2	-	V
				6	4.2	_		4.2	_	4.2	_		5.5								
Low-Level				2	- '	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage	VIL			4.5	_	<u> </u>	1.35	_	1.35		1.35	-	to	-	-	8.0	-	0.8	-	0.8	٧
				6	_	_	1.8	_	1.8	_	1.8		5.5						<u> </u>	ļ	
High-Level		VIL		2	1.9	_	_	1.9		1.9	_	VIL							1		
Output Voltage	V_{OH}	or	-0.02	4.5	4.4		_	4.4		4.4	_	or	4.5	4.4	-	- ·	4.4	-	4.4	-	V
CMOS Loads		V _{IH}		6	5.9	_		5.9	<u> </u>	5.9	_	V _{IH}			<u> </u>					<u> </u>	
		VIL			<u> </u>			<u> </u>	L			V _{IL}					l		l .	1	
TTL Loads		or	-4	4.5	3.98	_	<u> </u>	3.84		3.7	<u> </u>	or	4.5	3.98	-	-	3.84	_	3.7	-	V
		V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	.V _{IH}		-				ļ		ļ	
Low-Level		VIL		2	_	_	0.1	_	0.1		0.1	VIL			l		1				
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	느	0.1	-	0.1	or	4.5	-	[-	0.1	_	0.1	-	0.1	V
CMOS Loads		V _{IH} .	<u> </u>	6	<u> </u>	_	0.1	_	0.1	<u> </u>	0.1	V _{IH} .	<u> </u>				ļ	ļ	-		
		VIL		-		-						VIL						ľ			
TTL Loads		or	4	4.5	_	_	0.26	_	0.33		0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	٧
		V _{IH}	5.2	6		_	0.26		0.33		0.4	V _{IH}					<u> </u>	<u> </u>	ļ	├	
Input Leakage		Vcc										Any	İ	1				1	ļ.		
Current	h	or	l	6	-	_	±0.1	_	±1	-	±1	Voltage	5:5	-	-	±0.1	_	±1	-	±1	μΑ
		Gnd			l		l	ļ		}		Between							į	ļ	
Quiescent		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		 		-		-	-			V _{cc} & Gnd		-				<u> </u>	-	_	
Quiescent Device Current		V _{cc}	,	6			8		80		160	V _{cc}	5.5			.8		80	_	160	μA
Device Current	Icc	Gnd	"	٥	_	_	8	_	80	_	160	or Gnd	5.5	-	_	.0	_	80	_	160	μΑ
Additional		Gild	L	L	L	L					L	Gilu		-	_	-	 	-	 	-	
Quiescent Device													4.5			1					
Current per input												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	Δl _{cc} *												5.5				1				

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
All Inputs	0.35

 $^{^{\}star}$ Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu \rm A$ max. @ 25° C.

HC/HCT123 TRUTH TABLE

HC/HCT423 TRUTH TABLE

	INPUTS		OUT	
Ā	В	R	Q	Q
Н	Х	I	L	Н
X	L	н	L	н
L		н	Γ	╻
_	н	н	几	IJ
X	х	L	L	н
L	н		Л	T

	INPUTS		OUTPUTS					
A	В	R	Q	Q				
Н	Х	Н	L	Н				
X	L	н	L	н				
L		Н	J7.	T				
~	н	Н	几	T				
×	Х	L	L	Н				

H = High Level L = Low Level

= Transition from High to Low

X = Irrelevant

= One High Level Pulse ☐ = One Low Level Pulse

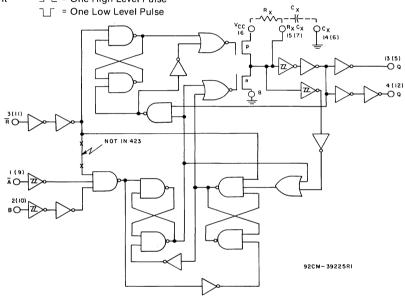


Fig. 1 - Logic diagram for HC/HCT123 and 423.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V_{cc}) : $(Voltages\ referenced\ to\ ground)$. DC INPUT DIODE CURRENT, I_{lsc} (FOR $V_{l} < -0.5\ V$ OR $V_{l} > V_{cc} +0.5\ V)$. DC OUTPUT DIODE CURRENT, I_{lsc} (FOR $V_{o} < -0.5\ V$ OR $V_{o} > V_{cc} +0.5\ V)$. DC DRAIN CURRENT, PER OUTPUT (I_{o}) (FOR $-0.5\ V < V_{o} < V_{cc} +0.5\ V)$. DC Vcc OR GROUND CURRENT, (I_{cc}) : POWER DISSIPATION PER PACKAGE (Po): FOR $T_{a} = -40\ to +60^{\circ}C$ (PACKAGE TYPE E). FOR $T_{a} = -40\ to +85^{\circ}C$ (PACKAGE TYPE F, H). FOR $T_{a} = -55\ to +100^{\circ}C$ (PACKAGE TYPE F, H). FOR $T_{a} = +100\ to +125^{\circ}C$ (PACKAGE TYPE F, H). FOR $T_{a} = +70\ to +125^{\circ}C$ (PACKAGE TYPE M). OPERATING-TEMPERATURE RANGE (T_{a}): PACKAGE TYPE F, H. PACKAGE TYPE F, H. PACKAGE TYPE F, M. STORAGE TEMPERATURE (T_{stg}). LEAD TEMPERATURE (DURING SOLDERING):	#20 mA #20 mA #220 mA #250 mA #250 mA #250 mA #250 mA #250 mA #550 mA #550 mW #550 mW #550 mW #550 mW #550 mW #550 mW #550 mW #550 mW #550 mW #555 to #150° C #550 to #150° C #550 to #150° C
,	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacting lead tips only	

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LII	LIMITS				
CHARACTERISTIC		MIN.	MAX.	UNITS		
Supply-Voltage Range (For T _A = Full Package-Te	emperature Range) V _{cc} :*					
	CD54/74HC Types	2	6	V		
	CD54/74HCT Types	4.5	5.5	V		
DC Input or Output Voltage V _I , V _O		0	V _{cc}	V		
Operating Temperature T _A :	CD74 Types	-40	+85	°C		
	CD54 Types	-55	+125	°C		
Input Rise and Fall Times t _r , t _f on Input R	at 2 V	0	1000	ns		
	at 4.5 V	0	500	ns		
	at 6 V	0	400	ns		
Input Rise and Fall Times t_r,t_f on Input B and \overline{A}	at 2 V	0	Unlimited	ns		
	at 4.5	0	Unlimited	∘ns		
	at 6 V	0	Unlimited	ns		

^{*}Unless otherwise specified, all voltages are referenced to Ground.

PREREQUISITE FOR SWITCHING FUNCTION

CHARACTERISTIC								LIM	IITS						UNITS
		Vcc		25	°C		-4	l0°C to	o +85°	c	-55	°CC t	o +12	5°C	
			н	С	Н	нст		74HC		74HCT		нс	54НСТ		
			Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	
Minimum Input		2	100		_	_	125		_	—	150	_	_	_	
Pulse Width	t_{WL}	4.5	20	-	20	_	25	_	25	-	30	_	30	-	ns
Ā		6	17	_	_	_	21	_	l —	_	26	-	-	_	
В		2	100	_	_	_	125	_	_	-	150	_	-		
	t_{WH}	4.5	20	-	20	_	25	-	25	-	30	-	30	—	ns
		6	17				- 21			-	26				
_		2	100	-	-	-	125	—	-	-	150	-		-	
R	t_{WL}	4.5	20	-	20	_	25	_	25		30	-	30	-	ns
		6	17			_	21				26				
<u>.</u>		2	50	-		—	65	_	-		75	_	-	—	
A & B Hold Time	t _H	4.5	10	-	10	-	13	_	13	_	15	-	15	-	ns
		6	9	_	_		11		_	_	13		<u> </u>	_	
		2	50	-	_	-	65	_	-		75		-	-	
Reset Removal Time	t _{REM}	4.5	10	-	10	_	13	_	13	_	15		15	- '	ns
		6	9				11				13		_		
Retrigger Time #		5	50 Typ.		50	Тур.	63	Гур.	63	Тур.	76	Тур.	76	Тур.	ns
R _x = 10 KΩ	tгт		ļ	71	ļ	71		71		,,,,		71		71.	ļ
Output Pulse		_	1		100		00.7		007		00.0		00.0		
Width Q or Q	tw	5	40	50	40	50	38.7	51.3	38.7	51.3	38.2	51.8	38.2	51.8	us
$R_x = 10 \text{ K}\Omega$, $C_x = 10 \text{ nF}$					l		<u> </u>	<u> </u>	<u> </u>		L	J	<u> </u>		l

[#]Time to trigger depends on the values of R_x and C_x . The output pulse width can only be extended when the time between the active-going edges of the trigger input pulses meet the minimum retrigger time requirement.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25° C, Input t_r , t_f = 6 ns)

0140407700740		TYPICAL	UNITS		
CHARACTERISTIC		C∟ (pF)	54/74HC	54/74HCT	UNITS
Propagation Delay					
Ā, B, R̄ to Q	t _{PLH}	15	25	25	ns
Ā, B, \overline{R} to \overline{Q}	t _{PHL}	15	26	27	ns
Output Pulse Width					
$R_x = 10 \text{ K}\Omega$, $C_x = 10 \text{ nF}$			45	45	μs
Pulse Width Match Between Circuits in the same Package					
$R_x = 10 \text{ K}\Omega$, $C_x = 10 \text{ nF}$			±2	±2	%
Power Dissipation Capacitance *	CPD			_	pF

^{*} CPD is used to determine the dynamic power consumption, per multivibrator.

 $P_D = (C_{PD} + C_x) V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 f_o)$ where:

 f_i = input frequency.

fo = output frequency.

C_L = output load capacitance.

 $C_x = \text{external capacitance}.$

V_{cc} = supply voltage.

assuming $f_i \ll \underline{1}$

tw

SWITCHING CHARACTERISTICS ($C_L = 50$ pF, Input t_r , $t_f = 6$ ns, $R_x = 10$ K Ω , $C_x = 0$)

								LIM	IITS						
CHARACTERISTIC	SYM-			25	°C		-4	0° C to	o +85°	, C	-5	°C	UNITS		
	BOL	V _{cc}	нс		нст		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	
Trigger Propagation	t _{PLH}	2	_	300	_	_	_	375		_	_	450	_	_	
Delay,		4.5	_	60	-	60	—	75	—	75	_	90	_	90	ns
\overline{A} , B, \overline{R} to Q		6	-	51	_	_	-	64	_	—	l –	76	-		
		2	_	320	_	-	_	400	_	-	-	480	_	-	
\overline{A} , B, \overline{R} to \overline{Q}	tpHL	4.5	-	64	_	68	-	80	-	85	_	96	_	102	ns
		6	_	54	_	-		68	_	_		82	_	_	
Reset Propagation	t _{PHL}	2	-	215	-	-	-	270	-	_	-	325	_	_	
Delay,	t _{PLH}	4.5	-	43	-	48	—	54	—	60	-	65	_	72	ns
\overline{R} to Q or \overline{Q}		6	-	37		—	—	46	—	-	-	55	—	_	
Output Transition	tTLH	2	_	75	_		_	95	_	_	_	110	_	_	
Time	t _{THL}	4.5	_	15	_	15	-	19	_	19	-	22	-	22	ns
		6	_	13		_	_	16	_		_	19			
Input Capacitance	Cı		-	10	_	10	_	10	_	10	_	10	_	10	pF

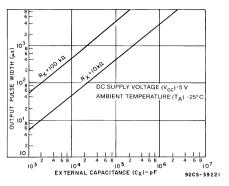


Fig. 3 - Typical output pulse width as a function of C_x for R_x = 10 k Ω and 100 k Ω .

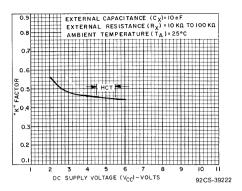


Fig. 4 - Typical "K" Factor as a function of Vcc.

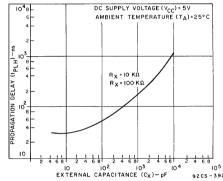
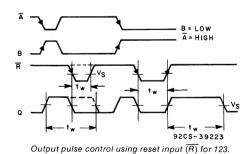
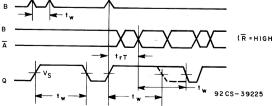


Fig. 5 - Typical propagation delay as a function of External Capacitance (C_x).



Ā B



Output pulse control using retrigger pulse for 123 and 423.

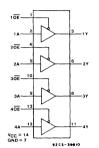
Fig. 2 - Triggering of One Shot by input A or input B for a period tw.

Ā	B = LOW
В	- A = HIGH
₹	-
° vs	-
92CS-39224	

Output pulse control using reset input $\overline{(R)}$ for 423.

	54/74HC	54/74HCT				
Input Level	Vcc	3 V				
Switching Voltage, Vs	50% V _{cc}	1.3 V				

High-Speed CMOS Logic



Quad Buffer; 3-State

Type Features:

- Separate output enable inputs
- 3-state outputs

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC125 and CD54/74HCT125 contain 4 independent 3-state buffers, each having its own output enable input, which when "HIGH" puts the output in the high impedance state.

The CD54HC125 and CD54HCT125 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC125 and CD74HCT125 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-inline surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide Operating Temperature Range: CD74HC/HCT/HCU: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- Alternate Source is Prinips/Signetics
 CD54HC/CD74HC Types:
 2 to 6 V Operation
 High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC},
 @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I, ≤ 1 µA @ V_{OL}, V_{OH}

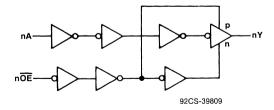


Fig. 1 - Logic diagram.

TRUTH TABLE

Inp	outs	Outputs
nA	nOE	nΥ
Н	L	Н
L	L	L
Χ	Н	Z

H = High Level

L = Low Level

X = Don't Care

Z = High Impedance, OFF State

MAXIMUM RATINGS, Absolute-Maximum Values:

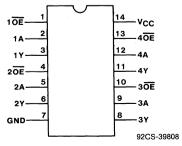
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{1K} (FOR $V_1 < -0.5$ V OR $V_1 > V_{CC} + 0.5$ V)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} $+$ 0.5 V)	±35mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±70mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For $T_A = +60$ to $+85$ °C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For $T_A = -40$ to $+70$ °C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (T _{stg})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIM	ITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :* CD54/74HC Types CD54/74HCT Types	2 4.5	6 5.5	V
DC Input or Output Voltage V _{IN} , V _{OUT}	0	V _{cc}	V
Operating Temperature T _A : CD74 Types CD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall Times t _r , t _f at 2 V at 4.5 V at 6 V	0 0 0	1000 500 400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC125/CD54HC125										CD	74HC	T125	/CD5	4HCT	125		-	
		TEST CONDITIONS				74HC/54HC TYPES		HC PE	541 TY	HC PE	TEST		74HCT/54HCT TYPES			74F TY	ICT PE_	54F TY		
CHARACTERISTIC	V _i	I _o	Vcc	+25°C				-40/ +85°C		5/ 5°C	V,	Vcc		+25°C	;	-40/ +85°C				UNITS
	٧	mA	٧	Min	Тур	Max	Min	Max	Min	Max	1 11	Min	Тур	Max	Min	Max	Min	Max		
High-Level			2	1.5	-		1.5		1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15			3.15	_	3.15	_	-	to	2	_	_	2	_	2	_	٧
			6	4.2	_	_	4.2		4.2	-		5.5								
Low-Level			2		_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5		_	1.35		1.35		1.35	_	to	-	-	0.8	-	0.8	-	0.8	٧ ′
			6		_	1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	-	1.9	_	1.9	_	VIL									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	_	v
CMOS Loads	V _{IH}		6	5.9	_		5.9	_	5.9	_	ViH									
	VIL										VIL									
TTL Loads	or	-6	4.5	3.98	_		3.84	_	3.7	-	or	4.5	3.98	_	-	3.84	-	3.7	-	٧
(Bus Driver)	V _{IH}	-7.8	6	5.48	_		5.34	_	5.2	_	ViH									
Low-Level	VIL	ļ	2	_	_	0.1		0.1	_	0.1	VIL									
Output Voltage Vol	or	0.02	4.5	_		0.1	_	0.1	_	0.1	or	4.5	-	_	0.1	_	0.1	_	0.1	v
CMOS Loads	V _{IH}		6		_	0.1	_	0.1	_	0.1	V _{IH}									
	VIL	ļ 1									ViL									
TTL Loads	or	6	4.5	_		0.26		0.33	_	0.4	or	4.5	_	-	0.26	-	0.33	-	0.4	v
(Bus Driver)	V _{IH}	7.8	6	_	_	0.26		0.33	_	0.4	ViH									
Input Leakage	Vcc										Any Voltage									
Current I _I	or Gnd		6	-	-	±0.1	-	±1	-	±1	Between V _{cc} and Gnd	5.5	-	_	±0.1	-	±1	-	±1	μΑ
Quiescent Device	Vcc										Vcc							_		
Current Icc	or	0	6		_	8	_	80	_	160	or	5.5	_	_	8		80		160	μΑ
	Gnd	Ĭ				ľ				100	Gnd	0.0							"	μ
Additional Quiescent Device Current per Input Pin: 1 Unit Load ΔIcc*											V _{CC} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-State Leakage Current I _{OZ}	V _{IL} or V _{IH}	V _o =V _{cc} or Gnd	6	_	_	±0.5	_	±5	_	±10	V _{IL} or V _{IH}	5.5	_	_	±0.5	_	±5	_	±10	μΑ

 $^{^{\}star}$ For dual-supply systems theoretical worst case (V $_{I}$ = 2.4 V, V $_{CC}$ = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
nA, n OE	1

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 360 μ A max. @ 25°C.

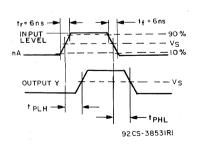
SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input t, t=6 ns)

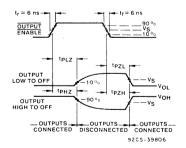
	CL		TYP	ICAL	
CHARACTERISTIC		pF	нс	нст	UNITS
Propagation Delay Time: (Fig. 2) nA to nY	t _{РНL} t _{РLН}	15	8	10	
Output Enabling Time	t _{PZL} , t _{PZH}	15	10	10	ns
Output Disabling Time	t _{PLZ} , t _{PHZ}	15	10	11	
Power Dissipation Capacitance*	C _{PD}	-	29	34	pF

 $^{^*}C_{PD}$ is used to determine the dynamic power consumption, per channel. $P_D = V_{CC}^2$ fi $(C_{PD} + C_L)$ where: fi=input frequency $C_L = 1$ load capacitance $V_{CC} = 1$ voltage

SWITCHING CHARACTERISTICS (C_L=50 pF, Input t_r, t_f=6 ns)

				25°C			-4	0°C to	+85	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	V _{cc}	Н	С	Н	СТ	74	нс	74F	ICT	54	нс	54H	ICT	UNITS
		٧	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	
Propagation Delay	t _{PLH}	2	_	100		_	_	125	_	_	_	150	_	_	
Time nA to nY	t _{PHL}	4.5	_	20		25	_	25	_	31		30	_	38	
(Fig. 2)		6	_	17			-	21	_	_	<u> </u>	26	_	_	
Enable Delay	t _{PZH}	2	_	125	_		_	155	_	_	_	190	_		
Time	t _{PZL}	4.5	<u> </u>	25	_	25	—	31		31	 	38	_	38	
(Fig. 2)		6	_	21		<u> </u>	l	26			_	32			
Disable Delay	t _{PHZ} , t _{PLZ}	2	-	125	_	_	_	155	_	_	_	190	_	_	ns
Time		4.5	_	25	_	28	—·	31	_	35	_	38	-	42	
		6		21	_		_	26			_	32			
Output Transition	t _{TLH}	2	_	60	_	_	-	75	_	_	_	90	_	_	
Time	t _{THL}	4.5	· —	12	_	12	—	15	_	15		18		18	
*		6		10	_	_		13			_	15			
Input Capacitance	Cı	_		10		10		10		10		10	_	10	
3-State Ouput Capacitance	Со		_	20	_	20	_	20	_	20	_	20	_	20	pF





	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 2 — Transition and propagation delay times.

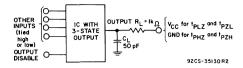
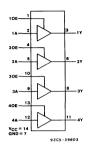


Fig. 3 - Three-state propagation delay test circuit.

High-Speed CMOS Logic



Quad Buffer: 3-State

Type Features:

- Separate output enable inputs
- 3-state outputs

FUNCTIONAL DIAGRAM

The RCA CD54/74HC126 and CD54/74HCT126 contain four independent 3-state buffers, each having its own output enable input, which when "low" puts the output in the high-impedance state.

The CD54HC/HCT126 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/HCT126 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT/HCU: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility $V_{1L} = 0.8 \text{ V Max.}, V_{1H} = 2 \text{ V Min.}$ CMOS Input Compatibility $I_{1} \le 1 \mu A @ V_{OL}, V_{OH}$

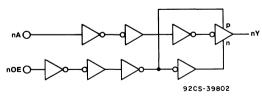


Fig. 1 - Logic Diagram

TRUTH TABLE

Inp	outs	Outputs
nA	nOE	nY
Н	Н	Н
L	H	L
X	L	Z

H = High Level

L = Low Level

X = Don't Care

Z = High Impedance (Off-State)

MAXIMUM RATINGS, Absolute-Maximum Values:

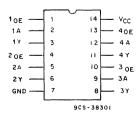
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_I < -0.5$ V OR $V_I > V_{CC} + 0.5$ V)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Vo $<$ Vcc $+$ 0.5 V)	±35mA
DC V _{cc} OR GROUND CURRENT (I _{cc})	±70mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
`STORAGE TEMPERATURE (T _{stg})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIM			
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :* CD54/74HC Types CD54/74HCT Types	2 4.5	6 5.5	V	
DC Input or Output Voltage V _I , V _O	0	V _{cc}	٧	
Operating Temperature T _A : CD74 Types CD54 Types	-40 -55	+85 +125	°C	
Input Rise and Fall Times t, t, at 2 V at 4.5 V at 6 V	0 0 0	1000 500 400	ns	

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC126/CD54HC126										CD	74HC	T126	/CD5	4НСТ	126					
	coi	TEST NDITION	s		IC/54		74I TY		1	HC PE	TEST		74HCT/54HCT TYPES		i			74HCT TYPE		ı	ICT PE	,
CHARACTERISTIC	V ₁	I _o	Vcc	-	+25°C	;	-4 +8		1	55/ 25°C	V ₁	Vcc	_	+25°C			-40/ +85°C				55/ 25°C	UNITS
	V	mA	٧	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max			
High-Level			2	1.5	_	_	1.5		1.5	_		4.5										
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_		to	2	-	_	2	-	2	_	v		
			6	4.2	_	_	4.2	_	4.2	_		5.5										
Low-Level			2			0.5	_	0.5		0.5		4.5										
Input Voltage V _{IL}	1		4.5	_		1.35	_	1.35		1.35	_	to	_	_	0.8	_	0.8	-	0.8	v		
· · · · · · · · · · · · · · · · · · ·			6	_		1.8	<u></u>	1.8		1.8		5.5										
High-Level	VIL		2	1.9			1.9		1.9		VIL											
Output Voltage VoH	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	_	4.4	-	4.4		v		
CMOS Loads	V _{IH}		6	5.9	_	_	5.9		5.9	_	V _{IH}											
	VIL										VIL											
TTL Loads	or	-6	4.5	3.98		_	3.84	_	3.7	_	or	4.5	3.98	-	_	3.84	-	3.7	-	v		
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34		5.2	_	V _{IH}								1			
Low-Level	VIL		2			0.1		0.1	_	0.1	VIL							ĺ				
Output Voltage VoL	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	-	0.1	-	0.1	v		
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}											
	VIL							<u> </u>			VıL											
TTL Loads	or	6	4.5	_		0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v		
(Bus Driver)	V _{IH}	7.8	6			0.26	_	0.33	_	0.4	ViH				L							
Input Leakage	Vcc										Any Voltage											
Current I _I	or		6	_	_	±0.1	_	±1	_	±1	Between Vcc	5.5	-	–	±0.1	_	±1	-	±1	μΑ		
	Gnd										and Gnd											
Quiescent	Vcc										Vcc											
Device	or	0	6	-	_	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ		
Current Icc	Gnd										Gnd											
Additional Quiescent Device Current per input pin: 1 unit load											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ		
3-State Leakage Current loz	V _{IL} or V _{IH}	V₀=Vcc or Gnd	6	_	-	±0.5		±5	_	±10	V _{IL} or V _{IH}	5.5	_	_	±0.5	_	±5	_	±10	μΑ		

 $^{^{\}star}$ For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*						
nA, nOE	1						

^{*}Unit Load is ΔI_{cc} limit specified in Static Characteristics Chart, e.g., 360 μA max. @ 25°C.

SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input tr, tr=6 ns)

	C _L		TYP	ICAL		
CHARACTERISTIC	pF	SYMBOL	нс	нст	UNITS	
Propagation Delay						
Data to Outputs	15	t _{PHL} , t _{PLH}	8	9		
Output Enabling Time	15	t _{PZL} , t _{PZH}	10	10	ns	
Output Disabling Time	15	t _{PLZ} , t _{PHZ}	10	11		
Power Dissipation Capacitance*	_	C _{PD}	30	36	pF	

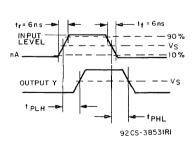
 $^{{}^{\}star}C_{PD}$ is used to determine the dynamic power consumption, per multiplexer.

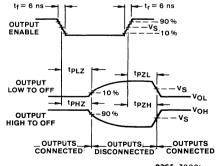
P_D=V_{CC}² fi (C_{PD}+C_L) where: fi=input frequency C_L=load capacitance

C_L=load capacitance V_{cc}=supply voltage

SWITCHING CHARACTERISTICS (CL=50 pF, Input t_r, t_f=6 ns)

				25°C			-4	0°C to	o +85	°C	-5				
CHARACTERISTIC	SYMBOL	ν _{cc}	Н	С	Н	СТ	74	нс	74F	ICT	54	нс	54 F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	100	_	_	_	125	_	_		150	_	_	
Data to Outputs	t _{PHL}	4.5	—	20	_	24	—	25		30	_	30	_	36	
		6	_	17	_	_	-	21			_	36		_	
Enable Delay	t _{PZH}	2	I _	125	_			155	_	_	_	190	_		
Times	t _{PZL}	4.5		25	_	25	—	31	_	31		38	-	38	
		6	_	21	_	<u> </u>		26	_	_	_	32	_		
Disable	t _{PHZ}	2	_	125	_	_	_	155	Ī —	_	_	190	_	_	ns
Delay Times	t _{PLZ}	4.5		25	_	28	_	31		35		38	_	42	}
		6	—	21	_	—	-	26	-	_	-	32	_	<u> </u>	
Output Transition	t _{TLH}	2	_	60	_			75	_	_	_	90	_		
Time	t _{THL}	4.5	-	12		12	-	15	—	15	—	18		18	
		6	—	10	_	_		13	_	_	_	15		_	
Input Capacitance	Cı			10	_	10		10		10	_	10		10	
3-State Output Capacitance	Со	_	-	20		20	_	20	_	20	_	20	_	20	pF





92C\$-3980I

	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, V _S	50% V _{cc}	1.3 V

Fig. 2 — Transition and propagation delay times.

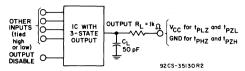
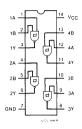


Fig. 3 - Three-state propagation delay test circuit.

High-Speed CMOS Logic



Quad 2-Input NAND Schmitt Trigger

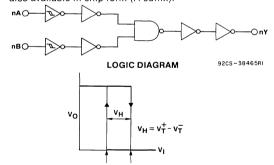
Type Features:

- Unlimited input rise and fall times
- Exceptionally high noise immunity

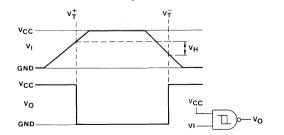
FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

The RCA-CD54/74HC132 and CD54/74HCT132 each contain four 2-input NAND Schmitt Triggers in one package.

The CD54HC132 and CD54HCT132 are supplied in 14-lead ceramic dual-in-line packages (F suffix). The CD74HC132 and CD74HCT132 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both devices are also available in chip form (H suffix).



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Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
 - Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation

High Noise Immunity: $N_{IL} = 37\%$, $N_{IH} = 51\%$ of V_{CC} ; @ $V_{CC} = 5 V$

■ CD54HCT/CD74HCT Types:

4.5 to 5.5 V Operation
Direct LSTTL Input Logic Compatibility $V_{IL} = 0.8 \text{ V Max.}, V_{IH} = 2 \text{ V Min.}$ CMOS Input Compatibility

 $I_{\rm I} \leq 1~\mu A \ @ V_{\rm OL}, V_{\rm OH}$

T	RUTH T	ABLE	
INP	UTS	OUTPUTS	
nA	nB	nY	
L	L	Н	H = High level
L	Н	Н	L = Low level
Н	L	Н	
Н	Н	L	

92CM-38466

Fig. 1 - Hysteresis definition, characteristic, and test setup.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5 \text{ V OR } V_i > V_{CC} + 0.5 \text{ V}$)	+20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_{\text{o}} < -0.5 \text{ V}$ OR $V_{\text{o}} > V_{\text{CC}} + 0.5 \text{V}$)	
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} $+$ 0.5V)	+25mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	
POWER DISSIPATION PER PACKAGE (Pp.):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F. H)	
For $T_A = +100$ to $+125$ °C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	•
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	Unlimited	ns
at 4.5 V	0	Unlimited	ns
at 6 V	0	Unlimited	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			С	D74HC	132/CD	54HC1	32			CD74HCT132/CD54HCT132								
		TEST		74HC	54HC	741	НС	541	нс	TEST	г	74HCT	54HCT	74F	ICT	54H	СТ	1
	со	NDITIO	NS	TY	PE	TY	PE	TY	PE	CONDITI	ONS	TY	PE	TY	PE	TY	PE	
CHARACTERISTIC	٧ı	10	Vcc			-4	0/	-5	5/	V _I	Vcc	.00	۰.	-4	0/	-5	5/	имітѕ
	v	mA	v	+25	٠-٢	+85	s° C	+12	5° C	v	v	+25	·	+85	5°C	+12	5° C	
				Min	Max	Min	Max	Min	Max	1		Min	Max	Min	Max	Min	Max	1
Input Switch			2	0.7	1.5	0.7	1.5	0.7	1.5			-	_	_	_	_	-	
Points V _T ⁺			4.5	1.7	3.15	1.7	3.15	1.7	3.15]	4.5	1.2	1.9	1.2	1.9	1.2	1.9	V
			6	2.1	4.2	2.1	4.2	2.1	4.2		5.5	1.4	2.1	1.4	2.1	. 1.4	2.1]
			2	0.3	1	0.3	1	0.3	1			_	_	_	_	_	_	
v _T -			4.5	0.9	2.2	0.9	2.2	0.9	2.2		4.5	0.5	1.2	0.5	1.2	0.5	1.2	
			6	1.2	3	1.2	3	1.2	3		5.5	0.6	1.4	0.6	1.4	0.6	1.4	
			2	0.2	1	0.2	1	0.2	1]			_			_	_	
V _H			4.5	0.4	1.4	0.4	1.4	0.4	1.4		4.5	0.4	1.4	0.4	1.4	0.4	1.4	V
			6	0.6	1.6	0.6	1.6	0.6	1.6]	5.5	0.4	1.5	0.4	1.5	0.4	1.5	
High-Level Output	VT-		2	1.9		1.9	-	1.9	_	VT-		_	_	_	-	-	-	
Voltage Voн	or	-0.02	4.5	4.4	<u> </u>	4.4	-	4.4	-	or	4.5	4.4	_	4.4	_	4.4	_	V
CMOS Loads	V _T ⁺		6	5.9	-	5.9	-	5.9	-	V _T ⁺		_	_	_	_	_	-	
	٧Ţ			_		_	-	_		V _T -		-	_		_	-	_	
TTL Loads	or	-4	4.5	3.98	_	3.84	_	3.7	_	or	4.5	3.98	_	3.84	_	3.7	_	V
	V _T ⁺	-5.2	6	5.48		5.34		5.2		V _T ⁺			_		_		_	
Low-Level Output	VT-		2	-	0.1	_	0.1	_	0.1	VT-			_		_	-	-	
Voltage V _{OL}	or	0.02	4.5		0.1		0.1	_	0.1	or	4.5	-	0.1		0.1		0.1	٧
CMOS Loads	V _T ⁺		6	-	0.1	-	0.1	_	0.1	V⊤⁺		-	-	-	_	_	-	
	VT ⁻			_	_	_			_	V _T -		_	_	_		_		
TTL Loads	or	4	4.5	_	0.26		0.33	_	0.4	or	4.5	_	0.26	_	0.33	_	0.4	V
	VT ⁺	5.2	6		0.26	_	0.33	-	0.4	V _T ⁺		_		_		_	_	
										Any								
Input Leakage	Vсс									Voltage								
Current I _I	or		6	-	±0.1	-	±1	-	±1	Between	5.5	-	±0.1	_	±1	_	±1	μΑ
	Gnd	1			1		l			V _{CC} and			1					
										Gnd								
Quiescent	v _{CC}									vcc								
Device	or	0	6	_	2	-	20	-	40	or	5.5	_	2	_	20	_	40	μA
Current I _{CC}	Gnd									Gnd			<u>L.</u>					
Additional Quies-												Min Ty	рМах					
cent Device																		
Current per											4.5							
Input Pin:										V _{CC} -2.1	to	<u> </u> - 10	0 360		450	-	490	μA
1 Unit Load ΔICC*											5.5							

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS*
nA, nB	0.6

^{*}Unit load is Δ lcc limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERISTIC		CL	TYP	ICAL	UNITS	
CHARACTERISTIC		(pF)	HC	HCT		
Propagation Delay A, B to Y	t _{PLH} t _{PHL}	15	10	13	ns	
Power Dissipation Capacitance	C _{PD} *	_	30	30	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per gate.

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where:

f_i = input frequency

C_L = output load capacitance

Vcc = supply voltage

SWITCHING CHARACTERISTICS (CL = 50 pF, Input tr,tf = 6 ns)

		TEST		+25	s° C		-4	0°C to	5 +85°	C	-5				
CHARACTERISTIC		CONDITIONS	HC		HCT		74HC		74HCT		54HC		54HCT		UNITS
		VCC (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	125	_		_	156	_	_	_	188		_	
A, B to Y	t_{PHL}	4.5		25	l —	33	_	31	_	41	l —	38		50	ns
		6	 	21	-	—	l —	27	_	-		32	—	l —	
Output	tTLH	2		75	_		_	95			_	110			
Transition Time	t _{THL}	4.5	—	15	—	15	—	19	—	19	—	22	_	22	ns
		6	—	13	-	-	l —	16	_			19		_	
Input Capacitance	Cı	_		10	-	10	_	10	_	10	_	10	_	10	pF

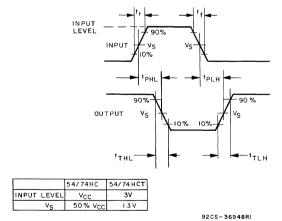
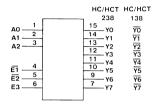


Fig. 2 - Transition times and propagation delay times.

High-Speed CMOS Logic



3-to-8 Line Decoder/Demultiplexer Inverting and Non-Inverting

Type Features:

- Select one of eight data output [active LOW for 138, active HIGH for 238]
- I/O port or memory selector
- 3 Enable Inputs to simplify cascading
- Typical propagation delay of 13ns @ V_{cc} = 5 V, C_L = 15 pF, T_A = +25° C

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC138,238 and CD54/74HCT138,238 are high speed silicon gate CMOS decoders well suited to memory address decoding or data routing applications. Both circuits feature low power consumption usually associated with CMOS circuitry, yet have speeds comparable to low power Schottky TTL logic. Both circuits have 3 binary select inputs (Ao, A1, and A2). If the device is enabled these inputs determine which one of the eight normally high outputs of the HC/HCT138 series will go low or which of the normally low outputs of the HC/HCT238 series will go high.

Two active low and one active high enables $(\overline{E}_1, \overline{E}_2,$ and $E_3)$ are provided to ease the cascading of decoders. The decoder's outputs can drive 10 low power Schottky TTL equivalent loads.

The CD54HC138,238 and CD54HCT138,238 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC138,238 and CD74HCT138,238 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout [Over Temperature Range]: Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT;: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL}=30%, N_{IH}=30% of V_{CC} @ V_{CC}=5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL}=0.8 V Max., V_{IH}=2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{DI}, V_{DI}

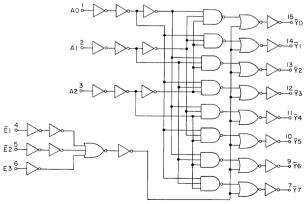


Fig. 1 — Logic Diagram for HC/HCT 138

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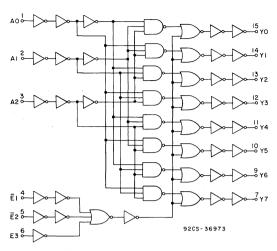


Fig. 2 — Logic Diagram for HC/HCT 238

TRUTH TABLE CD54/74HC138, CD54/74HC138

		INP	UTS						OUTE	LITC			
E	NABL	E	Αſ	DRES	S				0011	015			
E3	E2	E1	A2	A1	A0	YO	<u>¥1</u>	₹ 2	Y 3	¥4	¥5	<u>76</u>	¥7
Х	Х	Н	Х	Х	Χ	Н	Н	Н	Н	Н	Н	Н	Н
L	X	X	X	X	X	н	Н	H,	Н	Н	Н	Н	Н
X	Н	X	X	X	X	н	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н
Н	L	L	L	L	Н	н	L	Н	Н	Н	Н	Н	Н
Н	L	L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н
Н	L	L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	Н
Н	L	L	Н	L.	L	Н	Н	Н	Н	L	Н	Н	Н
Н	L	L	Н	L	Н	н	Н	Н	Н	Н	L	Н	Н
Н	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	Н
Н	L	L	Н	H	Н	Н	Н	. H	Н	Н	Н	Н	L

H = High level, L = low level, X = don't care

TRUTH TABLE CD54/74HC238, CD54/74HCT238

		INP	UTS						OUT	NITO			
E	NABL	E	ΑI	DDRES	SS				OUT	2015			
E3	E2	Ē1	A2	A1	Α0	Y0	Y1	Y2	Y3	Y4	Y5	Y6	Y 7
Х	Χ	Н	Χ	Χ	X	L	L	L	L	L	L	L	L
L	X	X	X	X	X	L	L	L	L	L	L	L	L
X	Н	X	X	X	×	L	L	L	L	L	L	L	L
Н	L	L	L	L	L	н	L	Ļ	L	L	L	L	L
Н	L	L	L	L	Н	L	Н	Ĺ	L	L	L	L	L
Н	L	L	L	Н	L	L	L	H	L	L	L	L	L
Н	L	L	L	Н	Н	L	- L	L	Н	L	L	L	L
Н	L	L	Н	L	L	L	L	L	L	Н	L	L	L
Н	L	L	Н	L	Н	L	L	L	L	L	Н	L	L
Н	L	L	Н	Н	L	L	L	L	L	L	L	Н	L
Н	L	L	Н	Н	Н	L	L	L	L	L	L	Ł	н

H = High level, L = low level, X = don't care

MAXIMUM RATINGS, Absolute-Maximum Values:

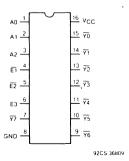
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5 \text{ V OR } V_i > V_{CC} + 0.5 \text{V}$)	±20mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC V _{cc} OR GROUND CURRENT (I _{cc})	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tsig)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIF	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _{in} , V _{out}	.0	Vcc	٧
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT FOR HC/HCT138 FOR HC/HCT238 ALL Y's ARE Y's

STATIC ELECTRICAL CHARACTERISTICS

		CD74	HC13	8/238,	CD5	4HC1	38/23	В			CD74HCT138/238, CD54HCT138/238									
QUADA OTEDIOTIO	ł .	TEST NDITIONS		I	i i			YHC 54HC YPES TYPES			TEST CONDITIONS		74HCT/54HCT TYPES			ICT PES	54HCT TYPES		UNITS	
CHARACTERISTIC	V. V	l _o	V _{cc}		+25°C		-40/ +85° C				V,	V _{cc}		+25° C		-40/ +85° C		-55/ +125°C		UNITS
		mA	"	Min	Тур	Max	Min	Max	Min	Max		ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-	-	1.5	_	1.5	_		4.5								
Input Voltage $V_{\mathbb{H}}$			4.5	3.15	_	_	3.15	-	3.15	_	_	to	2	-	-	2	-	2	-	V
			6	4.2	_	_	4.2	_	4.2			5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	-	to	-	-	0.8	-	0.8	-	0.8	v
			6			1.8	_	1.8	_	1.8		5.5		<u></u>						
High-Level	VIL		2	1.9		_	1.9	_	1.9	_	V _{IL}							1		
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	VIL					L					V _{IL}								l	
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48			5.34	_	5.2	_	V _{IH}									
Low-Level	VIL		2	_	_	0.1		0.1	_	0.1	Vii						1			
Output Voltage Vo.	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	_		0.1	_	0.1	_	0.1	V _{IH}									
	VIL										VIL			ļ						
TTL Loads	or	4	4.5	_		0.26		0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v
	V _{IH}	5.2	6			0.26	_	0.33		0.4	V _{IH}									
Input Leakage	Vcc										Any Voltage							İ		
Current I,	or		6	-	-	±0.1		±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										& Gnd								<u> </u>	
Quiescent	V _{cc}							ŀ			Vcc									
Device	or	0	6	-	-	8	_	80	-	160	or	5.5	-	-	8	-	80	-	160	μA
Current I _{cc}	Gnd		<u> </u>								Gnd								<u> </u>	
Additional Quiescent Device Current per input pin:											V _{cc} -2.1	4.5 to	_	100	360	-	450	_	490	μΑ
1 unit load ∆l _{cc} *											1.	5.5		1			1			

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
A0-A2	1.5
Ē1, Ē2	1.25
E3	1

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, CL = 15 pF, Input t, tr = 6 ns)

			Typical				
CHARACTERISTIC	SYMBOL	нс	нст	Unit			
Propagation Delay, Address to Output Y (C _L =15 pF)	t _{PLH}						
(Fig. 3)	t _{PHL}	13	14	ns			
Power Dissipation Capacitance*	*C _{PD}	67	67	pF			

*C_{PD} is used to determine the dymanic power consumption, per package.

 $PD=V_{CC}^2 f_i (C_{PD} + C_L)$ where $f_i = input$ frequency

c_L output load capacitance

V_{cc} supply voltage

SWITCHING CHARACTERISTICS (CL = 50 pF, Input tr,tf = 6 ns)

		TEST		+25	°C		-4	0°C t	o +85°	,C	-55	5°C to	+125	°C	
CHARACTERISTIC	;	CONDITIONS	НС		Н	нст		74HC		ICT	541	нс	541	ICT	UNITS
		V _{CC} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	150		—	_	190	_	<u> </u>	—	225	- T	-	
Address to Output	t _{PHL}	4.5	_	30	—	35	_	38	—	44	—	45		53	ns
(Fig. 3)		6	_	26		—	_	33	-	_	_	38	 		
Propagation Delay,	t _{PLH}	2	_	150	T —	_	_	190	_	_	_	225	_		
Enable to Output	t _{PHL}	4.5	_	30	_	35	l —	38	—	44	—	45		53	ns
(Fig. 3) HC/HCT138		6	-	26	_	—		33	—	_	-	38	l —	-	
Propagation Delay	t _{PLH}	2	_	175		_	_	220	_	_	-	265	_	_	
Enable to Output	t _{PHL}	4.5	—	35	—	40	—	44	—	50		53	l –	60	ns
(Fig. 4) HC/HCT238		6		30	_	_	_	37	l —	_	—	45	—		
Output	t _{TLH}	2		75	_	_	_	95	_	_		110		_	
Transition Times	t _{THL}	4.5	_	15		15	_	19	—	19	—	22		22	ns
		6	_	13	—	—	_	16		_	—	19	_	_	
Input Capacitance	Сі		_	10		10	_	10	_	10	_	10	_	10	pF

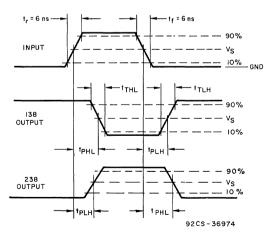


Fig. 3 - Transition times and propagation delay times.

	54/74HC	54/74HCT
INPUT LEVEL	V _{cc}	3V
V _s	50% V _{CC}	1.3V

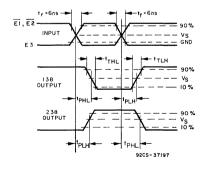
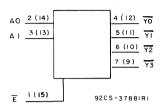


Fig. 4 — Transition times and propagation delay times.

	54/74HC	54/74HCT
INPUT LEVEL	V _{cc}	3V
V _S	50% V _{CC}	1.3V

High-Speed CMOS Logic



Dual 2-to-4 Line Decoder/Demultiplexer

Type Features:

- Multifunction Capability
 Binary to 1-of-4 Decoders or
 1-to-4 Line Demultiplexer
- Active Low Mutually Exclusive Outputs

Applications:

- Memory Decoding
- Data Routing
- Code Conversion

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC139 and CD54/74HCT139 contain two independent binary to one-of-four decoders each with a single active low enable input ($\overline{1E}$, or $\overline{2E}$). Data on the select inputs (1A0 and 1A1 or 2A0 and 2A1) cause one of the four normally high outputs to go low.

If the enable input is high all four outputs remain high. For demultiplexer operation the enable input is the data input. The enable input also functions as a chip select when these devices are cascaded. This device is functionally the same as the CD4556B and is pin compatible with it.

The outputs of these devices can drive 10 low power Schottky TTL equivalent loads. The 54/74HCT logic family is functionally as well as pin equivalent to the 54/74LS logic family.

The CD54HC139 and CD54HCT139 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC139 and CD74HCT139 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

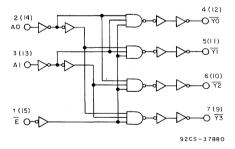


Fig. 1 - Logic diagram for the CD54/74HC/HCT139.

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \;@ V_{OL}, V_{OH}$

TRUTH TABLE

En	Inputs able Sele	ect	Outputs								
E	A1	Α0	<u>73</u>	<u> </u>	<u> </u>	YO					
0	0	0	1	1	1	0					
0	0	1	1	1	0	1					
0	1	0	1	0	1	1					
0	1	1	0	1	1	1					
1	X	×	1	1	1	1					

X = Don't Care

Logic 1 = High Logic 0 = Low

MAXIMUM RATINGS, Absolute-Maximum Values:

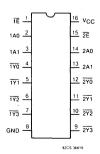
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} +0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I ₀) (FOR -0.5 V < V ₀ < V _{CC} +0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT, (I _{CC}):	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN	IITS	
CHARACTERISTIC	LIMITS MIN. MAX. 2 6 4.5 5.5 0 Vcc -40 +85 -55 +125 0 1000		UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	v
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

·		c	D74H	C139/	CD54	HC13	39					CD	74HC	T139/	CD54	нст	139			UNITS
CHARACTERISTIC		TEST IDITIONS			IC/54		741 TYF		54I TYF		TEST CONDITIO	ons	1	CT/54		74H TYF		54F TYF		
CHARACTERISTIC	۷, ۷	I _o mA	V _{cc}	-	+25° C	;	-4 +85		-5 +12	5/ 5°C	V,	V _{cc}		+25° C	:	1	0/ i° C		5/ 5° C	UNITS
	•			Min	Тур	Max	Min	Max	Min	Max	'	ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	-	2	-	2	_	V
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5		0.5		0.5		4.5								-
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	-	-	0.8	-	0.8	-	0.8	· V
			6	_	_	1.8	_	1.8	_	1.8	<u></u>	5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	_	4.4	-	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	-	V _{IH}									
-	VIL										Vil							-		
TTL Loads	or	-4	4.5	3.98	-	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}						ļ	ļ		
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	VıL									
Output Voltage V _{OL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}	-	_							
	V _{IL}		·								V _{IL}			l						
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6		_	0.26	_	0.33	_	0.4	V _{IH}		ļ			<u></u>		<u> </u>		
Input Leakage	V _{cc}										Any Voltage						ļ			
Current I	or		6	-	-	±0.1	_	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd								<u> </u>		& Gnd		_	<u> </u>	<u></u>	<u> </u>		1		
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μA
Current I _{cc}	Gnd				L						Gnd				<u> </u>	<u> </u>		<u> </u>		
Additional Quiescent Device Current											V _{cc} -2.1	4.5 to	-	100	360	_	450	-	490	μА
per input pin: 1 unit load Δ lcc*												5.5								

^{*}For dual-supply systems theoretical worst case (V_i = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads *
All	0.7

^{*}Unit Load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ} \text{ C}$, Input t_r , $t_f = 6 \text{ ns}$)

CUADACTERISTIC	CL	CVMDOL	Гур	LINUTO	
CHARACTERISTIC	(pF)	SYMBOL	54/74HC	54/74HCT	UNITS
Propagation Delay	15	t _{PHL}	12	14	no
Select to Output	15	t _{PLH}	12	14	ns
Enable to Output	15		11	14	ns
Power Dissipation Capacitance*	_	C _{PD}	55	59	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per decoder/demux.

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

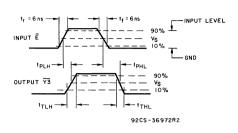
				25	°C		-4	0°C to	o +85°	C	-5	°C			
CHARACTERISTIC	SYMBOL	Vcc	нс		н	нст		74HC		74HCT		нс	54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	145	_	_	_	180	_	_	_	220	_	_	
A0, A1 to Outputs	t _{PHL}	4.5	_	29	-	34	-	36	_	43		44	_	51	ns
		6	_	25				31			<u> </u>	38			
	t _{PLH}	2	_	135	_	_	_	170	_	—	_	205	_	_	
E to Outputs	t _{PHL}	4.5	-	27	-	34	-	34	-	43	_	41	_	51	ns
		6		23				29			_	35			
Output Transition	t _{TLH}	2	-	75	_	_		95	_	_	_	110	_	-	
Time	t _{THL}	4.5	-	15	-	15	-	19	—	19		22	-	22	ns
		6		13	_	_	_	16	_	_	_	19	_	_	
Input Capacitance	Cı		_	10	_	10	_	10	_	10	_	10		10	pF

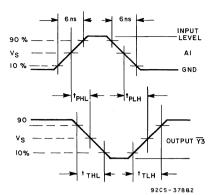
 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where:

f_i = input frequency

 $C_L = output load capacitance.$

 V_{CC} = supply voltage.

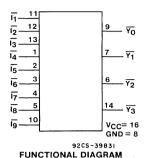




Transition times and propagation delay times.

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V₃	50% V _{cc}	1.3 V

High-Speed CMOS Logic



10-to-4-Line Priority Encoder

Type Features:

- Buffered inputs and outputs
- Typical CD54/74HC147 propagation delay = 13ns @ V_{cc}=5 V, C_L=15 pF, T_A=25°C

The RCA-CD54/74HC147 and CD54/74HCT147 are high-speed silicon-gate CMOS devices and are pin-compatible with low power Schottky TTL (LSTTL).

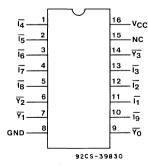
The CD54/74HC147 and CD54/74HCT147 9-input priority encoders accept data from nine active LOW inputs (\overline{I}_1 to \overline{I}_9) and provide binary representation on the four active LOW outputs (\overline{Y}_0 to \overline{Y}_3). A priority is assigned to each input so that when two or more inputs are simultaneously active, the input with the highest priority is represented on the output, with input line \overline{I}_9 having the highest priority.

These devices provide the 10-line to 4-line priority encoding function by use of the implied decimal "zero". The "zero" is encoded when all nine data inputs are HIGH, forcing all four outputs HIGH.

The CD54HC/HCT147 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/HCT147 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT/HCU: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

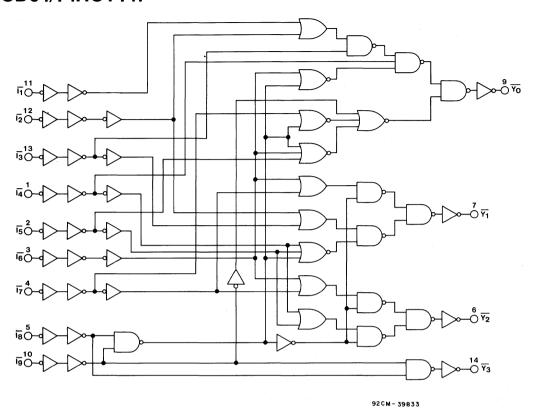


Fig. 1 - Logic Diagram

TRUTH TABLE

				Inputs	3					Out	puts	
T ₁	T₂	T ₃	T_4	T ₅	T ₆	T ₇	T ₈	T ₉	Y ₃	Y ₂	$\overline{\mathbf{Y}}_1$	Y ₀
Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	I
X	Х	Х	X	Х	Х	Х	Х	L	L	Н	Н	L
x	Х	Х	Χ	X	Χ	Х	L	Н	L	Н	Н	н
X	Х	Х	Х	Х	X	L	Н	Н	н	L	L	L
X	Х	Х	Х	X	L	Н	Н	Н	Н	L	L	Н
Х	Х	Х	X	L	. н	Н	Н	Н	Н	L	Н	L
Х	Х	Х	L	Н	Н	Н	Н	Н	H	L	Н	- Н
X	Х	L	Н	Н	Н	Н	Н	Н	Н	Н	L	ᆫ
X	L	Н	Н	Н	Н	Н	Н	Н	Н	H	L	н
L	Н	Н	Н	Н	Н	Н	Н	Н	Н	_ H	Н	L

H = High Logic Level, L = Low Logic Level, X = Irrelevant.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_{i}\!<\!-0.5$ V OR $V_{i}\!>\!V_{CC}+0.5$ V)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_{\text{O}} < -0.5 \text{V}$ OR $V_{\text{O}} > V_{\text{CC}} + 0.5 \text{V})$	±20mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5V $<$ Vo $<$ Vcc $+$ 0.5 V)	$\dots \dots \pm 25$ mA
DC V _{cc} OR GROUND CURRENT (I _{cc})	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For $T_A = +60$ to $+85$ °C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For $T_A = -40$ to $+70$ °C (PACKAGE TYPE M)	400 mW
For $T_A = +70$ to $+125$ °C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (T _{stg})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max \dots	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

_	LIM	ITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :* CD54/74HC Types CD54/74HCT Types	2 4.5	6 5.5	v
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A : CD74 Types CD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall Times t _r , t _f at 2 V at 4.5 V at 6 V	0 0 0	1000 500 400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD	74HC	147/C	D54H	IC147						CD74	нст	147/C	D54F	ICT14	17		
		TEST CONDITIONS						54I TY		TEST CONDITIONS		l	T/54 YPES		74HCT TYPE		54HCT TYPE			
CHARACTERISTIC	V ₁	lo	V _{cc}	-	+25°C		-40/ -55/ +85°C +125°C			٧ _.	V _{cc}	+25°C				10/ 5°C	1 -	5/ 5°C	UNITS	
	\ \ \	mA	*	Min	Тур	Max	Min	Max	Min	Max	\ \ \	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_		3.15		3.15		_	to	2	_	_	2	-	2	-	٧
			6	4.2	_	_	4.2		4.2			5.5								
Low-Level			2	_	_	0.5		0.5		0.5		4.5				ļ				
Input Voltage V _{IL}			4.5		_	1.35	_	1.35	_	1.35	_	to	_	_	0.8	-	0.8	-	0.8	V
			6			1.8		1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage VoH	or	-0.02	4.5	4.4	_	_	4.4	_	4.4		or	4.5	4.4		-	4.4	-	4.4	_	٧
CMOS Loads	V _{IH}		6	5.9	_	_	5.9		5.9		V _{1H}									
	VIL							L			VIL									
TTL Loads	or	-4	4.5	3.98		_	3.84		3.7	_	or	4.5	3.98	_	_	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48		_	5.34	_	5.2	_	ViH									
Low-Level	VIL		2	_	_	0.1	_	0.1		0.1	VIL			ļ						
Output Voltage Vol.	or	0.02	4.5	_		0.1	_	0.1		0.1	or	4.5	-	-	0.1	-	0.1	_	0.1	٧
CMOS Loads	V _{IH}		6	_		0.1	_	0.1		0.1	V _{IH}									
	VIL										VIL									
TTL Loads	or	4	4.5	_		0.26	_	0.33		0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	٧
	V _{IH}	5.2	6		_	0.26	_	0.33		0.4	ViH			ļ						
Input Leakage	Vcc										Any Voltage									
Current I _I	or		6	-	_	±0.1	_	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										and Gnd	_					<u> </u>		<u> </u>	
Quiescent Device Current Icc	Vcc										Vcc									
Current Icc	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
	Gnd										Gnd	<u></u>				<u> </u>	<u> </u>		<u> </u>	
Additional Quiescent Device Current per Input Pin: 1 Unit Load Alcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	-	450	-	490	μΑ

^{*} For dual-supply systems theoretical worst case ($V_1 = 2.4 \text{ V}$, $V_{CC} = 5.5 \text{ V}$) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
$\overline{I}_1, \overline{I}_2, \overline{I}_3, \overline{I}_6, \overline{I}_7$	1.1
$\overline{1}_4, \overline{1}_5, \overline{1}_8, \overline{1}_9$	1.5

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 360 μ A max. @ 25°C.

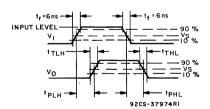
SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input tr, tr=6 ns)

		TYP	ICAL	
CHARACTERISTIC	SYMBOL	нс	нст	UNITS
Propagation Delay, Data Input to Output Y (Fig. 1) $(C_L=15 pF)$	t _{PLH} t _{PHL}	13	14	ns
Power Dissipation Capacitance*	СРД	32	42	pF

 $^{{}^{\}bullet}C_{PD}$ is used to determine the dynamic power consumption, per package. PD= $V_{cc}{}^{2}$ fi ($C_{PD}+C_{L}$) where fi= input frequency C_{L} =output load capacitance V_{cc} =supply voltage

SWITCHING CHARACTERISTICS (CL=50 pF, Input tr, tr=6 ns)

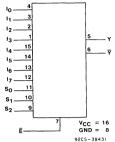
				25	°C		-4	0°C to	+85	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	V _{cc}	Н	С	н	СТ	74	нс	74⊦	ICT	54	нс	54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2		160		_		200		_		240		_	
Input to Output	t _{PHL}	4.5	1	32		35		40		44		48		53	ns
(Fig. 1)		6		27				34		_		41		_	
Transition Times	t _{TLH}	2		75		_		95		_		110		_	
(Fig. 1)	t _{THL}	4.5		15		15		19		19		22		22	ns
		6		13		_		16		_		19		_	
Input															
Capacitance	Cı			10		10		10		10		10		10	рF



	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

Fig. 1 - Transition times and propagation delay times.

High-Speed CMOS Logic



8-Input Multiplexer

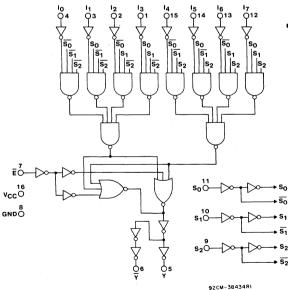
Type Features:

- Complementary data outputs
- Buffered inputs and outputs

FUNCTIONAL DIAGRAM

The RCA CD54/74HC151 and CD54/74HCT151 are single 8-channel digital multiplexers having three binary control inputs, SO, SI and SI and an active low enable (\overline{E}) input. The three binary signals select 1 of 8 channels. Outputs are both inverting $\overline{(Y)}$ and non-inverting $\overline{(Y)}$

The CD54HC/HCT151 devices are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT151 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types:
- 4.5 to 5.5 V Operation
 - Direct LSTTL Input Logic Compatibility
 - $V_{\rm IL} = 0.8 \text{ V Max.}, V_{\rm IH} = 2 \text{ V Min.}$
 - CMOS Input Compatibility
 - $I_1 \leq 1 \,\mu A \oplus V_{OL}, V_{OH}$

FUNCTION TABLE

					INPU	TS						оит	PUTS
Ē	S ₂	S ₁	So	I _o	l ₁	l ₂	l ₃	14	15	I ₆	l ₇	Y	Υ
Н	Х	X	X	Х	Х	Х	Х	Х	Х	Х	X	Н	L
L	L	L	L	L	Χ	Χ	Χ	Χ	Χ	Χ	Χ	Н	L
L	L	L	L	Н	Χ	Х	Χ	Χ	Χ	Χ	Χ	L	н
L	L	L	Н	X	L	Х	Χ	Х	Х	Χ	Х	Н	L
L	L	L	Н	Х	Н	Χ	Χ	Χ	Χ	Х	Х	L	н
l L	L	Н	L	X	Χ	L	Χ	Χ	Χ	Χ	Χ	Н	L
L	L	Н	L	х	Х	Н	Χ	Χ	Χ	Χ	Χ	L	н
L	L	Н	Н	X	Χ	Χ	L	Χ	X	Х	Х	Н	L
L	L	Н	Н	х	Χ	Χ	Н	Χ	Χ	Х	Χ	L	н
L	Н	L	L	X	Х	Χ	Χ	L	Х	Χ	Χ	Н	L
L	Н	L	L	X	Х	X	Χ	Н	Х	X	Х	L	н
L	н	L	Н	X	Х	Х	Χ	Χ	L	Χ	Χ	Н	L
L	Н	L	Н	X	Х	Χ	Χ	Χ	Н	Χ	Χ	L	н
L	н	Н	L	l x	Х	Х	Х	Х	Х	L	X	Н	L
L	Н	Н	L	x	Х	Х	Х	Х	Х	Н	X	L] н]
L	н	Н	Н	x	Х	Х	Х	Х	Х	Χ	L) н	L
L	Н	Н	Н	X	X	X	Х	X	X	X	Н	L	Н

H = HIGH voltage level.

L = LOW voltage level.

X = Don't care.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_{O} < -0.5$ V OR $V_{O} > V_{CC} + 0.5$ V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±25 mA
DC V _{cc} OR GROUND CURRENT (I _{cc}):	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For $T_A = -55$ to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T_A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING)	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

STATIC ELECTRICAL CHARACTERISTICS

				CI	D74H	C151	/CD54	HC1	i1				CD7	4НСТ	151/C	D54F	ICT1	51			
			TEST CONDITIONS			74HC/54HC 74HC TYPE TYPE				54HC TYPE		TEST	74HC	TYPE		74H TY		54HCT TYPE		• • · · · · · · · · · · · · · · · · · ·	
CHARACTERISTIC	S	V ₁	I _o	Vcc	,	+25°C		-40/ +85°C		-5: +12:		V,	V _i V _{cc}		+25°C		-40/ +85° C		-55/ +125° C		UNITS
		v	mA	v	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	-	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15	-	_	3.15		3.15	_	_	to	2	_	_	2	-	2	-	v
				6	4.2	_	_	4.2	_	4.2			5.5								
Low-Level				2		_	0.5	_	0.5	_	0.5		4.5								
Input Voltage	VIL			4.5		-	1.35		1.35	_	1.35		to	-	-	0.8	-	0.8	-	0.8	v
				6	_		1.8	_	1.8		1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VIL		ļ							
Output Voltage	V _{он}	or	-0.02	4.5	4.4			4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	-	4.4	_	V
CMOS Loads		V _{IH}		6	5.9	_		5.9	-	5.9		V _{IH}							,		
		VIL										VIL									
TTL Loads		or	-4	4.5	3.98	_		3.84	1	3.7	_	or	4.5	3.98	-	-	3.84	_	3.7	-	v
		ViH	-5.2	6	5.48	_	_	5.34	ı	5.2	_	V _{IH}									
Low-Level		VIL		2		_	0.1	_	0.1	_	0.1	VIL									
Output Voltage	VoL	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	_	0.1	_	0.1	-	0.1	V
CMOS Loads		V _{IH}		6	_	_	0.1	_	0.1	_	0.1	ViH									
		VıL										VIL									
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	_	0.33	_	0.4	v
		V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	ViH									
Input Leakage Current	lı	V _{cc} or Gnd		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_		±0.1	_	±1	_	±1	μΑ
Quiescent Device												V _{cc}									
Current	lcc 3	V _{cc} or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μΑ
	. 3	Gnd										Gnd									·
Additional						•															
Quiescent Device													4.5								
Current per												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
Input Pin: 1 Unit Load	Δl _{cc} *												5.5			1	1				

^{*}For dual-supply systems theoretical worst case (V_{I} = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
Select	1.5
Data	0.45
Enable	0.3

^{*} Unit load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

0.000.000000000000000000000000000000000	LIM	IITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t, t			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t_{ft} t_f = 6 ns)

			TYPICAL			
CHARACTERISTIC	CHARACTERISTIC C _L SYMBOL pF		54/74HC	54/74HCT	UNITS	
Propagation Delays		t _{PLH}		10		
Any data input to Y	15	t _{PHL}	14	16	ns	
Any data input to Y	15	t _{PLH} /t _{PHL}	15	15	ns	
Any select to Y	15	t _{PLH} /t _{PHL}	15	17	ns	
Any select to Y	15	t _{PLH} /t _{PHL}	17	18	ns	
Enable to Y	15	t _{PLH} /t _{PHL}	11	12	ns	
Enable to Y	15	t _{PLH} /t _{PHL}	12	15	ns	
Power Dissipation Capacitance*	_	C _{PD}	59	58	pF	

^{*} C_{PD} is used to determine the dynamic power dissipation per device:

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where:

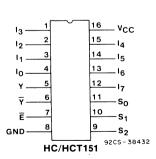
 f_i = input frequency.

C_L = output load capacitance.

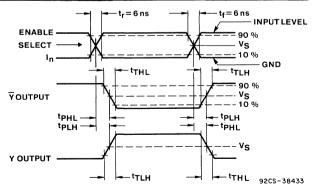
V_{cc} = supply voltage.

SWITCHING CHARACTERISTICS ($C_L = 50$ pF, Input t_r , $t_t = 6$ ns)

				25	°C		-4	0°C to	+85°	,C	-58	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	н	СТ	74	нс	74F	ЮТ	541	нс	54H	ICT	UNITS
			Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Мах.	
Propagation Delay,	t _{PLH}	2		170				215		-		255		 -	
Any Data Input to Y	t _{PHL}	4.5 6		34 29		38		43		48		51 43		57	ns
		2		185		_		230		=		280		-	
Any Data Input to Y	t _{PLH}	4.5		37		36		46		45		56		54	ns
	t _{PHL}	6		31		_		39		_		48		_	
		2		185		-		230		-		280		_	
Any Select to Y	t _{PLH}	4.5		37		41		46		51		56		62	ns
	t _{PHL}	6		31		-		39				48			
		2		205		-		255		-		310		— .	
Any Select to Y	t _{PLH}	4.5		41		43		51		54		62		65	ns
	t _{PHL}	6		35				43		_		53			
		2		140		-		175		-		210		-	
Enable to Y	t _{PLH}	4.5		28		29		35	1	36		42		44	ns
	t _{PHL}	6		24				30		_		36			
·		2		145		_		180		-		220		-	
Enable to Y	t _{PLH}	4.5		29		36		36		45		44		54	ns
	t _{PHL}	6		25				31				38			
Output Transition	t _{TLH}	2		75		-		95		-		110		-	
Time	t _{THL}	4.5		15		15		19		19		22		22	ns
		6		13		_		16		_		19		_	
Input Capacitance	Cı	_	_	10	_	10	_	10	_	10	_	10	_	10	pF



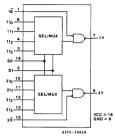
TERMINAL ASSIGNMENT



	CD54/74HC	CD54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, V _s	50% V _{cc}	1.3 V

Fig. 2 - Propagation delays to Y and \overline{Y} outputs.

High-Speed CMOS Logic



Dual 4-Input Multiplexer

Type Features:

- Common select inputs
- Separate enable inputs
- Buffered inputs and outputs

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC153 and CD54/74HCT153 are dual 4-to-1-line selector/multiplexers which select one of four sources for each section by the common select inputs, S0 and S1. When the enable inputs ($1\overline{\text{E}}$, $2\overline{\text{E}}$) are HIGH, the outputs are in the LOW state.

The CD54HC/HCT153 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/HCT153 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT/HCU: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation
 - High Noise Immunity: $N_{\rm IL}$ = 30%, $N_{\rm IH}$ = 30% of $V_{\rm CC}$; @ $V_{\rm CC}$ = 5V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation

 Direct LSTTL Input Logic Compatibility

 V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.

 CMOS Input Compatibility

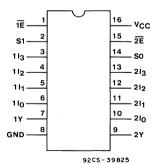
 $I_1 \leq 1 \,\mu A$ @ V_{OL} , V_{OH}

TRUTH TABLE

	ect uts			Enable	Output		
Sı	So	I ₀	l ₁	l ₁ l ₂ l ₃		Ē	Y
Х	Х	Х	X	X	Х	Н	L
L	L	L	Х	X	Х	L	L
L	L	Н	Х	X	X	L	Н
L	Н	Х	L	Х	Х	L	L
L	Н	X	lн	Х	X	L	н
Н	L	Х	Х	L	X	L	L
Н	L	Х	X	Н	X	L	H
Н	Н	X	Х	X	L	L	Ĺ
Н	Н	l v	l v	l x	Н	1 1	н

Select inputs A and B are common to both sections. H = High Level, L = Low Level, X = Don't Care.

LOGIC DIAGRAM



TERMINAL ASSIGNMENT

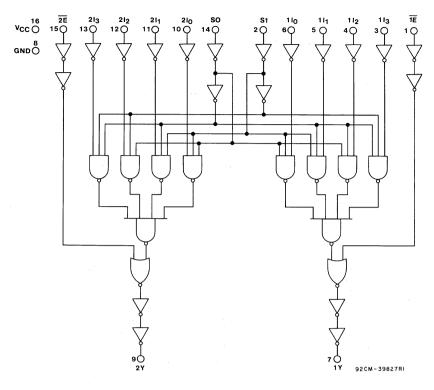


Fig. 1 - Logic diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, I_{iK} (FOR V_i $<$ -0.5 V OR V_i $>$ V_{CC} +0.5V) \hdots	±20mA
DC OUTPUT DIODE CURRENT, l_{OK} (FOR $V_{\text{o}}\!<$ -0.5 V OR $V_{\text{o}}\!>V_{\text{CC}}$ +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC}) ·	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

STATIC ELECTRICAL CHARACTERISTICS

		C	:D74H	C153	CD54	IHC15	53					CE	74HC	T153	CD54	нст	153			
CHARACTERISTIC	CO	TEST CONDITIONS			74HC/54HC 74HC TYPES TYPE			54HC TYPE		TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPE		54HCT TYPE		UNITS	
	V, V	I _o	V _{cc}		+25° C	:	-4 +85	0/ 6° C	-5 +12		V, V	V _{cc}		+25° C	;	-4 +85	0/ 5° C	-5 +12		ONTO
			"	Min	Тур	Max	Min	Max	Min	Max		1 1	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-		1.5	_	1.5	_		4.5								
Input Voltage V ₁			4.5	3.15	_	_	3.15		3.15		-	to	2	-	-	2	_	2		v
			6	4.2	_	_	4.2	_	4.2			5.5								
Low-Level			2	_	_	0.5		0.5		0.5	ļ	4.5								
Input Voltage V _{II}			4.5	_		1.35	_	1.35		1.35	-	to	-		0.8	-	0.8	-	0.8	V
			6	_		1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9		_	1.9	_	1.9		V _{IL}									
Output Voltage Vol	or	-0.02	4.5	4.4	_	_	4.4		4.4	_	or	4.5	4.4	-	-	4.4		4.4	-	V
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}							<u> </u>		
	V _{IL}			-							V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	<u> - </u>	3.84	_	3.7	_	or	4.5	3.98	_	-	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48			5.34		5.2	_	V _{IH}							-	-	
Low-Level	V _{tL}		2	_	_	0.1		0.1	_	0.1	V _{IL}									
Output Voltage Vol	ı	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-		0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	-	_	0.1	_	0.1	_	0.1	V _{IH}	-							_	
	V _{IL}			-							V _{IL}									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33		0.4	or	4.5	-		0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH} Any					-				
Input Leakage	V _{cc}										Voltage									
Current I	or Gnd		6	-	-	±0.1	_	±1	_	±1	Between V _{cc}	5.5	_	_	±0.1	-	±1	-	±1	μΑ
Quiescent	V _{cc}			-				_			& Gnd V _{cc}									
Device	or	0	6	_	_	8	_	80	-	160	or	5.5	_	_	8	_	80	_	160	μΑ
Current I _{cc}											Gnd									,
Additional		.L		Ь	L	I	L			L		4.5								
Quiescent Device Current											V _{cc} -2.1	to	_	100	360	_	450	_	490	μA
per input pin: 1 unit load ΔIcc*												5.5								

^{*}For dual-supply systems theoretical worst case (V, = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
DATA	0.45
ENABLE	0.6
SELECT	1.35

^{*}Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu{\rm A}$ max. @ 25° C.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	ITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

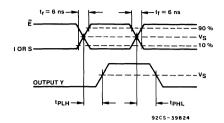
^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (Vcc = 5 V, T_A = 25°C, Input t₆ t_f = 6 ns)

CHARACTERISTIC		CL (=5)		ICAL UES	UNITS
		(pF)	HC	HCT	
Propagation Delay,					
Select to Outputs	t _{PHL} t _{PLH}	15	13	14	
Data to Outputs	t _{PLH}	15	12	9	ns
	t _{PHL}	15	12	14	
Enable to Outputs	t _{PLH} t _{PHL}	15	9	11	
Power Dissipation Capacitance*	C _{PD}	_	45	45	pF

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

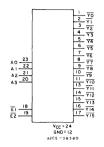
				25	°C		-4	0°C to	o +85°	С	-55° C to +125° C				
CHARACTERISTIC		V _{cc}	HC		нст		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	160	_	_		200	_	—		240	_	-	
S to Y	t _{PHL}	4.5	l –	32	—	34	—	40	_	43	—	48	_	51	ļ
		6	_	27	_	_	_	34	L-		_	41	<u> </u>	_	
I to Y	t _{PLH}	2	_	145	_	_	_	180	_	_	_	220	_	-	
		4.5		29	_	24	_	36	_	30	_	44	_	36	
		6	-	25	_	_	_	31	Í —	—		38		Í —	
l to Y	t _{PHL}	2	_	145	_	_	_	180	_		_	220	_		ns
		4.5	-	29	_	34	_	36	_	43	_	44	_	51	
		6	_	25	_	_	_	31	-	_	—	38	l —	 —]
Ē to Y	t _{PLH}	2		120	_		_	150	_	—	_	180	_	_	
	t_{PHL}	4.5	-	24	_	27	—	30	_	34	-	36	_	41	
		6	-	20	—			26		_	_	31		—	
Output Transition	t _{TLH}	2	—	75	_	_	_	95	_	<u> </u>	_	110	_	_	
Time	t _{THL}	4.5	-	15	<u> </u>	15		19	—	19	<u> </u>	22	—	22	
		6	-	13	—	—	_	16	-	-	—	19	_		
Input	C ₁			10		10		10		10		10		10	pF
Capacitance	— O1			10		10		10		_ '0		10		10	PF



	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 2 - Transition and propagation delay times.

High-Speed CMOS Logic



4-to-16 Line Decoder/Demultiplexer

Type Features:

 Two enable inputs to facilitate demultiplexing and cascading functions Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range:
- CD74HC/HCT: -40 to +85° C Balanced Propagation Delay and Transition Times

FUNCTIONAL DIAGRAM

The RCA CD54/74HC154 and CD54/74HCT154 are 4-to-16 line decoders/demultiplexers with two enable inputs. $\overline{E1}$ and E2. A High on either enable input forces the output into the High state. The demultiplexing function is performed by using the four input lines, A0 to A3, to select the output lines YO to Y15, and using one enable as the data input while holding the other enable low.

The CD54HC154 and CD54HCT154 are supplied in 24-lead dual-in-line frit-seal ceramic packages (F suffix). The CD74HC154 and CD74HCT154 are supplied in 24-lead dual-in-line, narrow-body plastic packages (EN suffix), in 24-lead dual-in-line, wide-body plastic packages (E suffix), and in 24-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Significant Power Reduction Compared to LSTTL Logic ICs

- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ $V_{CC} = 5 V$
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility $V_{\text{IL}} = 0.8 \text{ V Max., } V_{\text{IH}} = 2 \text{ V Min.}$ CMOS Input Compatibility $I_1 \leq 1 \,\mu A \, @ \, V_{OL}, \, V_{OH}$

TRUTH TABLE

	INPUTS												OUT	PUTS							
Ē1	E2	А3	A2	A1	A0	YO	¥1	Y2	Y3	¥4	Y5	Y6	¥7	Y8	Y9	Y10	Y11	Y12	Y13	Y14	Y15
L	L	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
L	L	L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
L	L	L	L	Н	L.	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	н
L	L	L	L	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	н
L	L	L	Н	L	L	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	H.	Н	н
L	L	L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н
L	L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	н
L	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н
L	L	Н	L	L	L	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	Н	Н
L	L	Н	L	L	Н	Н	Н	Н	Η	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	Н	н
L	L	Н	L	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	Н	Н	Н	н
L	L	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	Н	Н	Н
L	L	H	Н	L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	Н	н
L	L	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	Н	Н
L	L	H	Н	Н	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L	H
L	L	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	L
L	Н	X	Χ	Χ	Χ	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Η	Н	Н	н
Н	L	X	Χ	Χ	Х	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	H
Н	Н	X	Х	Х	Х	Н	Н	Н	Н	Н	Н	Н	Н	Н	Н	·H	Н	Н	Н	Н	н

H = High Level, L = Low Level, X = Don't Care.

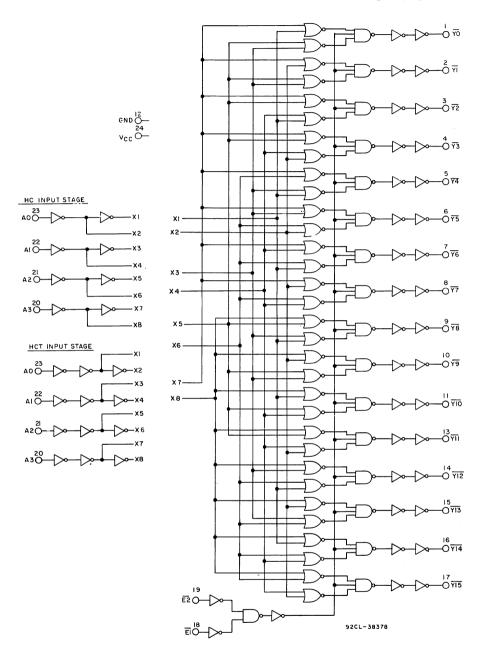


Fig. 1 - Logic diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5 V)	±20 mA
DC OUTPUT DIODE CURRENT, l_{OK} (FOR V_O $<$ -0.5 V OR V_O $>$ V_{CC} +0.5 V) $\ldots \ldots$	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I_0) (FOR -0.5 V $<$ V $_0$ $<$ V $_{cc}$ +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT, PER PIN (Icc):	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (Ta):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING)	
At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79 \text{ mm})$ from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C
With Solder contacting lead tips only	

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIA	MITS		
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*				
CD54/74HC Types	2	6	l v	
CD54/74HCT Types	4.5	5.5	V	
DC Input or Output Voltage V _I , V _O	0	Vcc	V	
Operating Temperature T _A :				
CD74 Types	-40	+85	°C	
CD54 Types	-55	+125	°C	
Input Rise and Fall Times, t _r , t _f				
at 2 V	0	1000	ns	
at 4.5 V	0	500	ns	
at 6 V	0	400	ns	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

				CD	74HC	154/0	D54F	IC154	1				CD7	4НСТ	154/0	D54F	ICT1	54			
CHARACTERISTICS		TEST CONDITIONS						74HC 54HC TYPE TYPE		TEST CONDITIONS			TYPE		741- TY		54H TY	ICT PE	UNITS		
		V,	I _o	Vcc	+25°C		-40/ +85° C		-55/ +125°C		V,	Vcc		•25° C	;	-40/ +85° C				UNITS	
			mA	v	Min	Тур	Max	Min	Max	Min	Max	٧	>	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15	1	_	3.15	-	3.15	1	_	to	2	-	-	2	-	2	-	٧
				6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level				2	_	-	0.5		0.5		0.5		4.5								
Input Voltage	VIL			4.5	_	_	1.35	_	1.35	_	1.35	_	to	_	_	0.8	\ -	0.8	_	0.8	v
				6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9		VIL									
Output Voltage	Vон	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	-	4.4	_	4.4	_	v
CMOS Loads		VIH		6	5.9	_	_	5.9	_	5.9	_	VIH		}							
		VıL										VIL									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v
		ViH	-5.2	6	5.48		_	5.34	_	5.2	_	V _{IH}									
Low-Level		VıL		2	_	_	0.1	_	0.1	_	0.1	VıL									
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	_	0.1		0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads		VIH		6	_	_	0.1	_	0.1	_	0.1	ViH				, i					
		VIL										VIL									
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5		_	0.26	_	0.33	_	0.4	v
		ViH	5.2	6	_	_	0.26	_	0.33	_	0.4	ViH									
Input Leakage Current	lı	V _{cc} or Gnd		6	_	-	±0.1		±1	1	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1	_	±1	μΑ
Quiescent Device												Vcc									
Current	Icc	V _{cc} or Gnd	0	6	_	-	8	-	80	-	160	or Gnd	5.5	-	-	8	_	80	-	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	ΔΙςς.		l				<u> </u>					V _{CC} -2.1	4.5 to 5.5	_	100	360		450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case ($V_1 = 2.4 \text{ V}$, $V_{CC} = 5.5 \text{ V}$) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
A0 — A3	1.4
E1, E2	1.3

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ} \text{ C}$, Input t_r , $t_t = 6 \text{ ns}$)

			TYPICAL			
CHARACTERISTIC	C∟ pF	SYMBOL	54/74HC	54/74HCT	UNITS	
Propagation Delay	45	t _{PHL}	14	14		
Address to Output	15	t _{PLH}	14	14	ns	
E1 to Output	15	t _{PHL}	14	14		
E1 to Output	15	t _{PLH}	14	14	ns	
E2 to Output	15	t _{PHL}	14	14		
Ez to Output	15	t _{PLH}	14	14	ns	
Power Dissipation Capacitance*	_	C _{PD}	88	84	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per device.

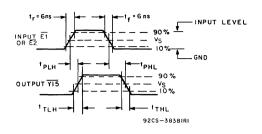
 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where: $f_i = input$ frequency.

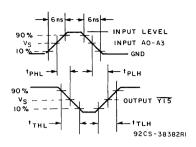
C_L = output load capacitance.

V_{cc} = supply voltage.

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

				25	°C		-4	0°C to	+85°	C	-55°C to +125°C				
CHARACTERISTIC	SYMBOL	Vcc	нс		нст		74HC		74HCT		54HC		54H	нст	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	175	_	_	_	220	_	_	_	265	_	_	
Address to Outputs	t _{PHL}	4.5	-	35	_	35	 —	44	—	44	_	53	 	53	ns
		6	_	30	—		_	37		L		45	_	_	
	t _{PLH}	2	-	175	_	_		220	_	-	-	265	_	_	
E1 to Outputs	t _{PHL}	4.5	—	35	-	34	_	44	_	43	_	53	—	51	ns
		6	-	30	 	_	_	37				45	_	_	
	t _{PLH}	2	I —	175	l –	_	_	220	_	-	_	265	-	-	
E2 to Outputs	t _{PHL}	4.5	-	35	_	34	—	44	_	43	—	53	—	51	ns
		6	_	30	_	_		37		_	_	45	_	_	
Output Transition	t _{TLH}	2	-	75	_	-	-	95	_	-	_	110	_	-	
Time	t _{THL}	4.5	-	15	_	15	-	19	-	19	_	22	—	22	ns
		6		13		_	_	16	_	_		19	_	_	
Input Capacitance	Cı		_	10		10	_	10	_	10	_	10	_	10	pF

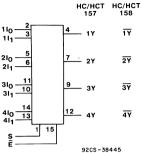




	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, Vs	50% V _{CC}	1.3 V

Fig. 2 - Propagation delay and transition times.

High-Speed CMOS Logic



Quad 2-Input Multiplexers

HC/HCT157 Non-Inverting HC/HCT158 Inverting

Type Features:

- Buffered inputs
- Typical Propagation Delay (In to Output) = 10 ns (HC157) @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C

Family Features:

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC157, 158 and CD54/74HCT157, 158 are quad 2-input multiplexers which select four bits of data from two sources under the control of a common Select input (S). The Enable input (E) is active LOW. When (E) is HIGH, all of the outputs in the 158, the inverting type, (1Y-4Y) are forced HIGH and in the 157, the non-inverting type, all of the outputs (1Y-4Y) are forced LOW, regardless of all other input conditions.

Moving data from two groups of registers to four common output busses is a common use of these devices. The state of the Select input determines the particular register from which the data comes. They can also be used as function generators.

The CD54HC157, 158 and CD54HCT157, 158 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC157, 158 and CD74HCT157, 158 are supplied in 16-lead dual-in-line plastic packages (E suffix). The CD74HC157, 158 and CD74HCT157, 158 are supplied in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

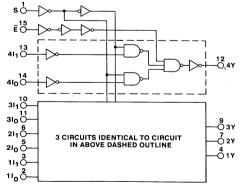


Fig. 1 - Logic Diagram for HC/HCT157.

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 μA @ V_{OL}, V_{OH}

FUNCTION TABLE

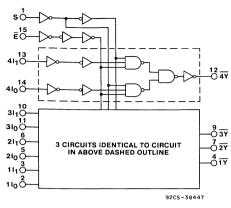
		0-14			Output				
	Enable	Select Input	Da Inp		157	158			
	E	S	Io	11	Y	Y			
	Н	Х	Х	Х	L	Н			
	L	L.	L	X	L	Н			
1	L	L	н	Х	Н	L			
	L	н	Х	L	L	н			
	L	Н	Х	н	н	L			

L = LOW voltage level.

H = HIGH voltage level.

X = Don't care.

92CM-38446



vcc 15 E 14 III 4I0 4 I, HC/HCT158 12 5 4Y * 210 6 11 211 31₀ 10 * 2Y 31₁ 9 37 · GND 92CS-37008

* For HC/HCT157 these outputs are 1Y, 2Y, 3Y, 4Y,

TERMINAL ASSIGNMENT

Fig. 2 - Logic Diagram for HC/HCT158.

MAXIMUM RATINGS; Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I _{IK} (FOR V ₁ < -0.5 V OR V ₁ > V _{CC} +0.5 V)	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I ₀) (FOR -0.5 V < V ₀ < V _{cc} +0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT (I _{CC}):	±50 mA
POWER DISSIPATION PER PACKAGE (Pp.):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

OLIADA OTERIOTIO	LIN			
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*				
CD54/74HC Types	2	6	V	
CD54/74HCT Types	4.5	5.5	V	
DC Input or Output Voltage V _{in} , V _{out}	0	V _{cc}	V	
Operating Temperature T _A :				
CD74 Types	-40	+85	°C	
CD54 Types	-55	+125	°C	
Input Rise and Fall Times, tr, tr				
at 2 V	0	1000	ns	
at 4.5 V	0	500	ns	
at 6 V	0	400	ns	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD	74HC	:157/	158/C	D54H	C157	/158			CE	74HC	T157/	158/C	D54H	ICT15	7/158	3		
			TEST IDITION	15		IC/54 TYPE		74F		54H TY		TEST	ONS		T/54	нст	74H TY		54H TY		UNITS
CHARACTERISTI	cs	V,	Io	Vcc	,	-25° C	:	-4(+85		-5: +125		Vı	Vcc	+25° C			-40/ +85° C		-55/ +125°C		UNITS
		٧	mA	v	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	_	_	2	_	2	_	v
				6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage	VIL			4.5	_		1.35	_	1.35	_	1.35	_	to	_	_	0.8	_	0.8	_	0.8	v
				6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage	Vон	or	-0.02	4.5	4.4	_	_	4.4	_	4.4		or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads		ViH		6	5.9	_	_	5.9	_	5.9	_	ViH									
		VIL										VIL									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	l v
		ViH	-5.2		5.48		_	5.34	_	5.2		ViH									
Low-Level		VIL		2	_	_	0.1		0.1	_	0.1	VıL									
Output Voltage	Vol	or	0.02	4.5	_	_	0.1		0.1		0.1	or	4.5	_		0.1	_	0.1	_	0.1	v
CMOS Loads	. 01	VIH		6	_	_	0.1	_	0.1		0.1	ViH									
		VIL										ViL									
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v
		VIH	5.2	6	_	_	0.26	_	0.33	_	0.4	Visi									
Input Leakage Current	l _i	V _{cc} or Gnd		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1	_	±1	μΑ
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6	_	-	8	_	80	_	160	V _{cc} or Gnd	5.5	_	_	8	_	80	_	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	ΔΙςς.						•					V _{cc} -2.1	4.5 to 5.5	-	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

INPUT LOADING TABLE

INPUT	UNIT L	OADS *				
INPOT	HCT 157	HCT 158				
I (ALL)	0.95	0.4				
Ē	0.6	0.6				
S	3	2.8				

^{*} Unit load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C, Input t, t = 6 ns)

		0.445.01		UNITS			
CHARACTERISTIC	C∟ pF	SYMBOL	HC157	HCT157	HC158	HCT158	UNITS
Data to Output	15	t _{РН} L t _{РLН}	10	12	11	13	ns
Enable to Output	15	t _{РНL} t _{РLН}	11	12	13	15	ns
Select to Output	15	t _{PHL}	12	15	12	14	ns
Power Dissipation Capacitance*		СРД	62	70	35	35	pF

^{*} C_{PD} is used to determine the dynamic power consumption, per multiplexer.

 $P_D = C_{PD} V_{CC}^2 f_i + \sum C_L V_{CC}^2 f_o$ where:

 f_i = input frequency.

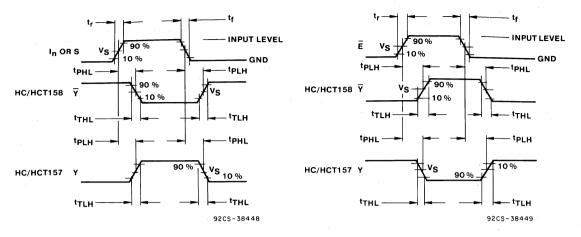
fo = output frequency.

C_L = output load capacitance.

V_{cc} = supply voltage.

SWITCHING CHARACTERISTICS (C) = 50 pF. Input to t = 6 ns)

				25	°C		-4	0°C to	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	V _{cc}	н	С	н	СТ	74	нс	74F	ICT	54	нс	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	-	125	_	-	_	155	_	_	-	190	=		
Data to Output	t _{PHL}	4.5	_	25	-	30	—	31	—	38	-	38	—	45	ns
(Figure 3) HC/HCT157		6	-	21	-	-	\	26	-	-	-	32	l —	-	
Propagation Delay	t _{PLH}	2	_	135		_	_	170	_	-	_	205	_	<u> </u>	
Enable to Output	t _{PHL}	4.5	_	27	_	30	_	34		38	—	41	_	45	ns
(Figure 4) HC/HCT157		6	_	23	_	_	l —	29	_	_	_	35	-	_	
Propagation Delay	t _{PLH}	2	-	145			=	180	_	-	_	220			
Select to Output	t _{PHL}	4.5	_	29	_	37	_	36	_	46	_	44	_	56	ns
(Figure 3) HC/HCT157		6	_	25	-	_	l —	31	_	_	_	38		_	
Propagation Delay	t _{PLH}	2	-	140	_	† -	_	175	_	=	_	210	=	1-	-
Data to Output	t _{PHL}	4.5	_	28	_	32	_	35	_	40	_	42		48	ns
(Figure 3) HC/HCT158		6	_	24		-	 	30	_	_	_	36	_	_	
Propagation Delay	t _{PLH}	2	-	160		_	_	200			-	240	_	-	
Enable to Output	t _{PHL}	4.5	_	32	_	37	_	40	_	46	_	48	_ '	56	ns
(Figure 4) HC/HCT158		6	_	27	_	-	_	34	_	_	_	41	_		1
Propagation Delay	t _{PLH}	2	_	150	_	_	_	190	-	-	_	225	= -		
Select to Output	t _{PHL}	4.5	_	30	_	35	_	38	_	44	_	45	_	53	ns
(Figure 3) HC/HCT158		6	_	26	_	_	_	33	_	_	-	38	_	_	İ
Output Transition	t _{TLH}	2	=	75	_	-	_	95	_	_	_	110		 _	
Time	t _{THL}	4.5	_	15		15	_	19	_	19	_	22	_	22	ns
(Figure 3 or 4)		6		13	_	_	_	16	l –	_	_	19	_	_	
Input Capacitance	Cin		-	10	-	10		10	-	10	<u> </u>	10	 	10	pF



	54/74HC	54/74HCT
Input Level	Vcc	3 V
Vs	50% V _{cc}	1.3 V

Fig. 3 - Inputs or select to output propagation delays and output transition times.

Fig. 4 - Enable to output propagation delays and output transition times.

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High-Speed CMOS Logic

FUNCTIONAL DIAGRAM

PO PI P2 P3 SPE 9 14 5 6 14 00 CP 2 13 Q1 MR 1 12 Q2 PE 7 11 Q3 TE 10 92CS-37958

Presettable Counters

CD54/74HC/HCT160 BCD Decade Counter, Asynchronous Reset CD54/74HC/HCT161 4-Bit Binary Counter, Asynchronous Reset CD54/74HC/HCT162 BCD Decade Counter, Synchronous Reset CD54/74HC/HCT163 4-Bit Binary Counter, Synchronous Reset

Type Features:

- Synchronous Counting and Loading
- Two Count Enable Inputs for n-Bit Cascading
- Asynchronous Reset (CD54/74HC/HCT160, 161)
- Synchronous Reset (CD54/74HC/HCT162, 163)
- Look-Ahead Carry for High-Speed Counting

The RCA-CD54/74HC/HCT160, 161, 162, and 163 devices are presettable synchronous counters that feature lookahead carry logic for use in high-speed counting applications. The CD54/74HC/HCT160 and 161 are asynchronous reset decade and binary counters, respectively; the CD54/74HC/HCT162 and 163 devices are decade and binary counters, respectively and are reset synchronously with the clock. Counting and parallel presetting are both accomplished synchronously with the negative-to-positive transition of the clock.

A low level on the synchronous parallel enable input, SPE, disables the counting operation and allows data at the P0 to P3 inputs to be loaded into the counter (provided that the setup and hold requirements for SPE are met).

All counters are reset with a low level on the Master Reset input, MR. In the CD54/74HC/HCT162 and 163 counters (synchronous reset types), the requirements for setup and hold time with respect to the clock must be met.

Two count enables, PE and TE, in each counter are provided for n-bit cascading. In all counters reset action occurs regardless of the level of the SPE, PE and TE inputs (and the clock input, CP, in the CD54/74HC/HCT160 and 161 types).

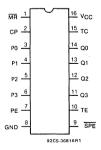
If a decade counter is preset to an illegal state or assumes an illegal state when power is applied, it will return to the normal sequence in one count as shown in state diagram.

The look-ahead carry feature simplifies serial cascading of the counters. Both count enable inputs (PE and TE) must be high to count. The TE input is gated with the Q outputs of all four stages so that at the maximum count the terminal count (TC) output goes high for one clock period. This TC pulse is used to enable the next cascaded stage.

The CD54HC160 through 163 and the CD54HCT160 through 163 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC160 through 163 and the CD74HCT160 through 163 are supplied in 16-lead dual-in-line plastic packages (E suffix), and in 16-lead dual-in-line surface mount plastic packages (M suffix). All types are also supplied in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- Alternate Source is Frimps/Signetics
 CD54HC/CD74HC Types:
 2 to 6 V Operation
 High Noise Immunity: N_{IL} = 30%, N_{IH} = 30%
 of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 μA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

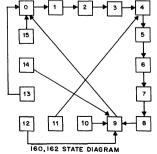
MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc): (Voltages referenced to ground) DC V_{cc} OR GROUND CURRENT. (I_{cc}): ±50 mA POWER DISSIPATION PER PACKAGE (PD): 400 mW For T_A = -40 to +70° C (PACKAGE TYPE M) OPERATING-TEMPERATURE RANGE (Ta): PACKAGE TYPE E, M-40 to +85° C STORAGE TEMPERATURE (Tstq) -65 to +150° C LEAD TEMPERATURE (DURING SOLDERING): Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacting lead tips only 03 QO Q3 Q MP D 03 03 DO Q ΤZ Ŧ3 Tī CP QC നു ആ * CONNECT TO V_{CC} FOR I62 # CONNECT TO GND FOR I60

Fig. 1 - Logic diagram for the CD54/74HC/HCT160 and 162.

92CL-37960RI

9205-4025981



NOTE: ILLEGAL STATES IN BCD COUNTERS CORRECTED IN ONE COUNT.

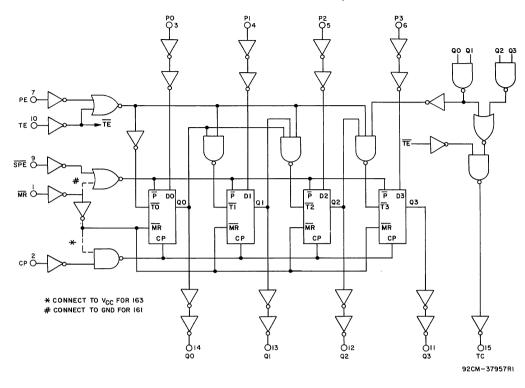


Fig. 2 - Logic diagram for the CD54/74HC/HCT161 and 163.

MODE SELECT - FUNCTION TABLE, 160, 161

ODEDATING MODE			INP	UTS			OUTPUTS			
OPERATING MODE	MR	СР	PE	TE	SPE	Pn	Qn	тс		
Reset (Clear)	L	х	х	×	х	х	L	L		
Daniel Land	н		х	х	ı	ı	L	L		
Parallel Load	н		×	x	1	h	н	(a)		
Count	Н		h	h	h(c)	х	count	(a)		
06-11-11	н	х	l(p)	х	h(c)	х	q _n	(a)		
Inhibit	н	х	x	l(p)	h(c)	×	q _n	L		

MODE SELECT - FUNCTION TABLE, 162, 163

		INPUTS										
OPERATING MODE	MR	СР	PE	TE	SPE	Pn	Q _n	тс				
Reset (Clear)	1		х	×	х	х	L	L				
	h(f)		х	х	1	1	L	L				
Parallel Load	h(f)		×	x	I	h	Н	(d)				
Count	h(f)		. h	h	h(f)	х	count	(d)				
	h(f)	Х	ı(e)	х	h(f)	Х	q _n	(d)				
Inhibit	h(f)	×	×	ı(e)	h(f)	×	q _n	L				

H = HIGH voltage level steady state.

L = LOW voltage level steady state.

h = HIGH voltage level one setup time prior to the LOW-to-HIGH clock transition.

I = LOW voltage level one setup time prior to the LOW-to-HIGH clock transition.

X = Don't care.

q = Lower case letters indicate the state of the referenced output prior to the LOW-to-HIGH clock transition.

= LOW-to-HIGH clock transition.

NOTES

- (a) The TC output is HIGH when TE is HIGH and the counter is at Terminal Count (HHHH for 161 and HLLH for 160).
- (b) The HIGH-to-LOW transition of PE or TE on the 54/74161 and 54/74160 should only occur while CP is HIGH for conventional operation.
- (c) The LOW-to-HIGH transition of SPE on the 54/74161 and 54/74160 should only occur while CP is HIGH for conventional operation.
- (d) The TC output is HIGH when TE is HIGH and the counter is at Terminal Count (HLLH for 162 and HHHH for 163).
- (e) The HIGH-to-LOW transition of PE or TE on the 54/74163 should only occur while CP is HIGH for conventional operation.
- (f) The LOW-to-HIGH transition of SPE or MR on the 54/74163 should only occur while CP is HIGH for conventional operation.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

0	LIN	MITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, tr, tr			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		CD74	HC16	0-163	/CD5	4HC1	60-16	3			CE	74H	CT160)-163/	CD54	нст	160-1	63		
CHARACTERISTIC	1	TEST			IC/54 ERIE:		741 SER		54I SER		TEST			CT/54 ERIE		74H SER		54H SER	- 1	UNITS
CHARACTERISTIC	V _i	lo mA	V _{cc}		25° C	:	-40 +85		-5: +12!		V, V	V _{cc}		+25° C	:	-4 +85	0/ 5° C	-5 +12	5/ 5° C	UNITS
		IIIA	•	Min	Тур	Max	Min	Max	Min	Max		•	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	-		4.5								
Input Voltage V _{IH}			4.5	3.15	_		3.15	_	3.15	_	_	to	2	-	-	2	-	2	-	v
	<u> </u>		6	4.2	_		4.2	_	4.2	_		5.5								
Low-Level			2			0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}		1	4.5	_	_	1.35	_	1.35		1.35	_	to	-	_	0.8	-	0.8	_	0.8	v
			6	_	_	1.8		1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	VIL					İ		İ		
Output Voltage Von	or	-0.02	4.5	4.4		_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	V
CMOS Loads	V _{IH}		6	5.9			5.9	_	5.9	_	ViH									
	VIL										VIL									
TTL Loads	or	-4	4.5	3.98			3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	_	٧
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH		ļ.,							
Low-Level	VIL		2	_	_	0.1	_	0.1		0.1	VIL									
Output Voltage Vol	or	0.02	4.5		_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	–	0.1	V
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	ViH						<u> </u>			
	VIL	L									VIL		ļ		,	i				
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	VIH				<u> </u>		<u> </u>			
Input Leakage	Vcc			ļ							Any Voltage									
Current I	or		6	-	-	±0.1		±1	-	±1	Between V _{cc} and	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										Gnd						<u> </u>			
Quiescent	Vcc										Vcc			İ			ŀ			
Device	or	0	6	-	_	8	-	80	–	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current lcc	Gnd										Gnd									
Quiescent Device Current per input pin: 1 unit load \(\Delta\) Lcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	-	490	μΑ

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input I	Loading Table
Input	Unit Loads *
P0-P3	0.25
PE	0.65
CP	1.05
MR	0.8
SPE	0.5
TE	1.05

*Unit load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERISTIC	CVMDOL	SYMBOL CL TYPICAL					
CHARACTERISTIC	STMBUL	(pF)	54/74HC	54/74HCT	UNITS		
Propagation Delay CP to TC	t _{PHL}	15	15	18	ns		
CP to Qn	t _{PLH}	15	15	16	ns		
TE to TC		15	9	13	ns		
MR to Qn (160, 161)	t _{PHL}	15	18	21	ns		
Power Dissipation Capacitance *	C _{PD}	_	60	63	pF		

CPD is used to determine the dynamic power consumption, per package.

C_L = output load capacitance. V_{CC} = supply voltage.

PREREQUISITE FOR SWITCHING FUNCTION

							LIM	ITS						
CHARACTERISTIC	TEST		25	°C		-4	0°C te	+85°	.c_	-55	5°C to	+125	°C	UNITS
CHARACTERISTIC	CONDITIONS	Н	С	н	CT .	741	нС	74F	ICT	54	нс	54F	ICT	UNITS
	V _{cc} V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	- 44-
	2	6	 	=		5	_	-	_	4	-	=	-	
Max. CP Freq. * f _{MAX}	4.5	30	_	30	l —	24		24	l —	20	_	20	_	MHz
	6	35	-	 —		28		_		24	—	l —	_	·
	2	80	_			100	_	_	_	120		_	_	
CP Width (Low) tw(L)	4.5	16	_	16	_	20	_	20	l —	24	—	24 -	-	ns
	6	14	—	—	—	17	—	_	-	20	—	_	—	
	2	100	T =	_	_	125	_	_	<u> </u>	150	—	_	_	
MR Pulse Width tw	4.5	20	l —	25	—	25	—	31	—	30	 -	38	—	ns
	6	17	_	—	l —	21	—	l —	<u> </u>	26	<u> </u>		L —_	
	2	60	-	T-	_	75	_		_	90	T -	<u> </u>		
Setup Time tsu	4.5	12	l —	10	_	15	l —	13	_	18	—	15	—	ns
Pn to CP	6	10			_	13	l —	l —	l —	15	_	_	-	1
	2	50	T-	1-	T — T	65	_	—	<u> </u>	75	_		_	
Setup Time tsu	4.5	10	l —	13	l —	13	l —	16	_	15	_	20	_	ns
PE or TE to CP	6	9	_	<u> </u>	l —	11	_		—	13	—	—	—	
	2	60	T —	T —	_	75	_	_	_	90	—	—	T =	
Setup Time tsu	4.5	12	l —	12	_	15	l —	15	l —	18	—	18	_	ns
SPE to CP	6	10		-	l —	13	-		l —	15	l —	_	—	
	2	65	—	 	_	80	T —	T=		100	_			
Setup Time tsu	4.5	13	_	13	_	16	l —	16		20	_	20		ns
MR to CP (162, 163)	6	11	_	l —	_	14	l —	—		17] —	—	—	
	2	3	T —	T —	_	3		T -	_	3	_		_	
Hold Time t _H	4.5	3	_	5		3	_	5	—	3	-	5	 —	ns
Pn to CP	6	3	_	_	_	3	_	-	l —	3	-	l —	 -	
	2	0	—	-	T-	0	T —	_	T-	0	T —	T —	T-	
Hold Time t _H	4.5	0	_	3	_	0	-	3	_	0	—	3	_	ns
TE or PE to CP	6	0	-	_	_	0	l -	_	—	0	-	۱ —	-	1
	2	3	-	T -	T -	3	_	_	_	3	_	_	—	
Hold Time 160, t _H	4.5	3	-	3	-	3	—	3	l —	3		3	_	ns
SPE to CP 162	6	3	1 —	l —.	_	3	_	_	-	3	—	l —	-	
	2	0	T	1-	Ι-	0	_	T-	Γ-	0	Τ-	Γ-	-	
161, t _H	4.5	0		3	—	0	_	3	-	0	—	3	-	ns
163	6	0			—	0	-	-	l –	0	—	l –	l —	
	2	75	1-	1-	1-	95	 	_	1 —	110	-	_	Ι-	
Recovery Time tREC	4.5	15	_	15		19	_	19	_	22	_	22	_	ns
MR to CP	6	13	_	l —	1 -	16	_	<u> </u>	_	19		l —	_	

^{*} Applies to non-cascaded operation only. With cascaded counters clock to terminal count propagation delays, count enables (PE or TE)-to-clock set-up times, and count enables (PE or TE)-to-clock hold times determine max. clock frequency. For example with these HC devices:

fmax (CP) = ≈ 21 MHz (min.) 37 + 10 + 0

 $P_D = C_{PD} V_{CC}^2 f_1 + \sum (C_L V_{CC}^2 f_0)$ where: $f_1 = input$ frequency. $f_0 = output$ frequency.

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_f = 6 \text{ ns}$)

					LIMITS											
CHARACTERISTIC		TEST CONDITION	25° C				-40°C to +85°C				-55°C to +125°C				UNITS	
			нс		нст		74HC		74HCT		54HC		54HCT		ONTIS	
		V _{cc} V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Propagation Delay	t _{PLH}	2	—	185	_	_	-	230	-	_	-	280	-			
CP to TC	t _{PHL}	4.5°	_	37	_	42	—	46	_	53	_	56	—	63	ns	
		6	_	31				39	_	l –	_	48	<u> </u>	<u>L</u>		
	t _{PLH}	2	_	185	-	_	_	230	_	_	_	280	_	-		
CP to Qn	tPHL	4.5	_	37	-	39	-	46	—	49	—	56	-	59	ns	
		6	<u></u>	31		_		39		_		48				
	t _{PLH}	2	 	120	-	-	_	150	—	-	-	180	—	-		
TE to TC	t _{PHL}	4.5	—	24	—	32	-	30	-	40	_	36	—	48	ns	
		6		20		_	_	26	_	_	_	31		-		
		2	—	210	_	-	_	265	-	—	_	315	—	-		
MR to Qn,	t _{PHL}	4.5	-	42		50	-	53	—	63	—	63	-	75	ns	
(160, 161)		6	_	36		_		45	_			54				
		2	—	210	-	-	-	265	-	-	-	315	_	-		
MR to TC	t _{PHL}	4.5	_	42	-	50	-	53	-	63	-	63	-	75	ns	
		6	<u> </u>	36	_	<u> </u>	_	45	<u> </u>	-		54		<u> </u>		
		2	—	75	–	-	_	95	-	-	-	110	—	_		
Output Transition	t _{TLH}	4.5	—	15	-	15	-	19	-	19	-	22	-	22	ns	
Time	t _{THL}	6	_	13				16			<u> </u>	19	<u> </u>	<u> </u>		
Input Capacitance	Cin			10	_	10		10		10	_	10		10	pF	

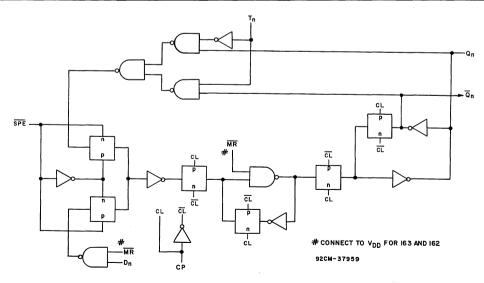
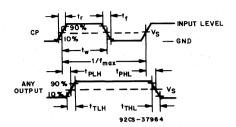
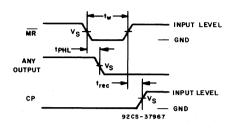
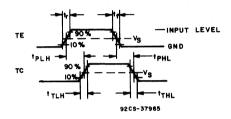


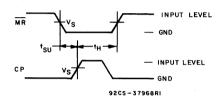
Fig. 3 - Detail of flip-flops for all types.

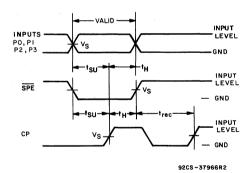
Transition times, propagation delay times, setup, hold, and recovery times.

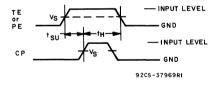










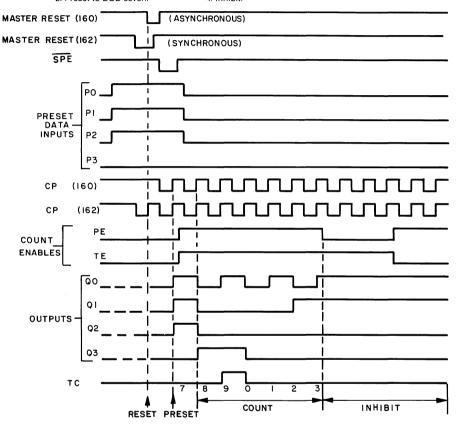


	CD54/74HC	CD54/74HCT
Input Level	Vcc	3 V
V _s	0.5 V _{cc}	1.3 V

Timing diagrams for the CD54/74HC/HCT160 and 162.

Sequence illustrated in waveforms

- Reset outputs to zero.
 Preset to BCD seven.
- 3. Count to eight, nine, zero, one, two, and three.
- 4. Inhibit.

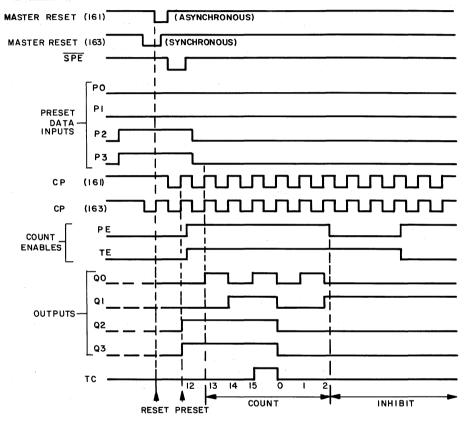


92CM-37963RI

Timing diagrams for the CD54/74HC/HCT161 and 163.

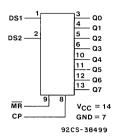
Sequence illustrated in waveforms

- 1. Reset outputs to zero.
- 2. Preset to binary twelve.
- 3. Count to thirteen, fourteen, fifteen, zero, one, and two.
- 4. Inhibit.



92CM-37962

High-Speed CMOS Logic



8-Bit Serial-In/Parallel-Out Shift Register

Type Features:

- Buffered Inputs
- Asynchronous Master Reset
- Typical $f_{MAX} = 60 \text{ MHz}$ @ $V_{CC} = 5V$, $C_L = 15 \text{ pF}$, $T_A = 25^{\circ} C$

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC164 and CD54/74HCT164 are 8-bit serial-in parallel-out shift registers with asynchronous reset. Data is shifted on the positive edge of Clock (CP). A LOW on the Master Reset ($\overline{\text{MR}}$) pin resets the shift register and all outputs go to the LOW state regardless of the input conditions. Two Serial Data inputs (DS1 and DS2) are provided, either one can be used as a Data Enable control.

The RCA CD54/74HC164 are supplied in 14-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT164 are supplied in a 14-lead plastic dual-in-line plastic package (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). The CD54/74HC/HCT164 are also supplied in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity:

 $N_{\rm IL}$ = 30%, $N_{\rm IH}$ =30% of $V_{\rm CC}$; @ $V_{\rm CC}$ =5 V

92CM-3850IR2

■ CD 54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL}=0.8 V Max., V_{IH}=2 V Min. CMOS Input Compatibility

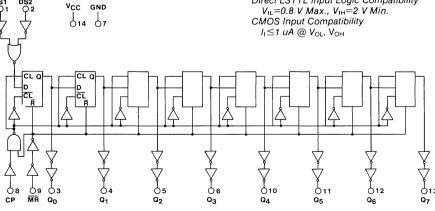


Fig. 1 - Logic diagram for the CD54/74HC164, CD54/74HCT164

MODE SELECT — TRUTH TABLE

Operating		Inp	uts		Outputs						
Mode	MR	CP	DS1	DS2	QO	Q1	_	Q7			
Reset (Clear)	L	X	X	Х	L	L	_	L			
	Н	5	1		L	q _o	_	q ₆			
	H		- 1	h	L	q _o	_	q ₆			
Shift	H		h	1	L	q₀	_	q ₆			
	<u> </u>	<u></u>	h	h	Н	qo	_	q ₆			

FLIP FLOP DETAIL

92CS-38500RI

H=HIGH voltage level.

h=HIGH voltage level one setup time prior to the LOW-to-HIGH clock transition.

L=LOW voltage level.

I=LOW voltage level one setup time prior to the LOW-to-HIGH clock transition.

q=Lower case letters indicate the state of the reference input (or output) one setup time prior to the LOW-to-HIGH-clock transition.

X=Don't care.

_/ =LOW-to-HIGH clock transition.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V _{CC}):
(Voltages referenced to ground)
DC INPUT DIODE CURRENT, $I_{\rm IK}$ (FOR $V_1 < -0.5$ V OR $V_1 > V_{\rm CC} + 0.5$ V)
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_0 <$ -0.5 V OR $V_0 > V_{CC}$ +0.5 V)
DC DRAIN CURRENT, PER OUTPUT (I _O) (FOR -0.5 V $<$ V _O $<$ V _{CC} + 0.5 V)
DC V _{CC} OR GROUND CURRENT (I _{CC})
POWER DISSIPATION PER PACKAGE (PD):
For T _A = -40 to +60°C (PACKAGE TYPE E)
For T _A ++60 to +85°C (PACKAGE TYPE E)
For T _A = -55 to +100°C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For T _A = -40 to +70° C (PACKAGE TYPE M) 400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE E, M40 to +85° C
PACKAGE TYPE F, H55 to +125° C
STORAGE TEMPERATURE (T _{stg})
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s max
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	LINUTO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{CC}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		(CD74H	C164	CD54	HC16	4				CD74HCT164/CD54HCT164									
CHARACTERISTIC	1	TEST		l	1		1	74HC TYPES		HC PES	TEST		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS
	V _i	I _O	V _{CC}		+25°C		-40/ -55/ +85°C +125°C		V 1	v _i v _{cc}		+25°C		-40/ +85° C		-55/ +125° C				
	V	mA	\ \	Min	Тур	Max	Min	Max	Min	Max	v	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5		-	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_		3.15	_	3.15		_	to	2	-	-	2	-	2	-	٧
			6	4.2			4.2		4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	-	to	-	-	0.8	_	0.8	_	0.8	٧
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	V _{IL}		2	1.9	_		1.9	_	1.9		VIL									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	٧
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9		V _{IH}						ļ		<u> </u>	
	VIL										VIL								1	
TTL Loads	or	-4	4.5	3.98		-	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2		V _{IH}		<u> </u>						ļ	
Low-Level	VIL		2	_		0.1	_	0.1	_	0.1	VIL									
Output Voltage V _{OL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	٧
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}		ļ				<u> </u>		ļ	
	VIL										VIL									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}								ļ	
Input Leakage	Vcc										Any Voltage									
Current I ₁	or		6	-	-	±0.1	-	±1	-	±1	between V _{CC} &	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										Gnd					<u> </u>	<u> </u>		ļ	
Quiescent	Vcc										V _{CC}				l					
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{CC}	Gnd							<u> </u>	<u> </u>		Gnd		ļ				<u> </u>		_	
Additional Quiescent Device Current per input pin: 1 unit load											V _{CC} -2.1	4.5 to 5.5	_	100	360	-	450	-	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
Date Shift-In (1,2)	0.3
MR	0.9
Clock	0.7

^{*}Unit Load is $\Delta\,I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25°C, Input t_r, t_r=6 ns)

	HARACTERISTIC		CVMPOL	Тур	LINUTO	
C	MARACIERISTIC	C _L pF	SYMBOL	54/74HC	54/74HCT	UNITS
Maximum Clock Freq	uency	15	f _{MAX}	60	54	MHZ
Propagation Delay:	CP to Qn	15	t _{PLH} , t _{PHL}	14	15	ns
	MR to Qn	15	t _{PHL}	11	16	ns
Power Dissipation Ca	pacitance	_	C _{PD} *	47	49	pF

 $C_{\mbox{\scriptsize PD}}$ is used to determine the dynamic power consumption, per device.

 $P_D = C_{PD} V_{CC^2} f_I + \Sigma (C_L V_{CC^2} f_O)$ where:

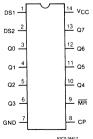
f_I = input frequency.

f_O = output frequency. C_L = output load capacitance.

V_{CC} = supply voltage.

PREREQUISITE FOR SWITCHING FUNCTION

			25°C				-40° C t	o +85°C	:	_					
CHARACTERISTIC	SYMBOL	V _{CC}	н	С	н	СТ	741	нс	74H	СТ	541	нс	C 54F		UNITS
	`		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Clock		2	6	-	_	. —	5	_		_	4	_	_	T -	
Frequency	f _{MAX}	4.5	30	-	27	_	24	-	22	-	20	-	18	-	MHz
		6	35	_		_	28		_	_	24		_		
MR Pulse Width		2	60	_	_	_	75	-	_	_	90		-	-	
	t _W	4.5	12	-	18	-	15	-	23		18	-	27	-	ns
ν.		6	10		_	<u> </u>	13	_	-		15	_		_	
CP Pulse Width		2	80	_	_	_	100	_	_	_	120	_		-	
	t _W	4.5	16	_	18	_	20	_	23	-	24	-	27	-	ns
		6	14	_			17	_			20			_	
Setup Time		2	60	_	-	_	75	-	-	_	90	_	_	_	
	tsu	4.5	12	-	12	_	15	-	15	-	18	-	18	-	ns
		6	10	_		-	13	_		_	15	_			
Hold Time		2	4	_	_	_	4		_	_	4	_		-	
	t⊢	4.5	4	-	4	_	4	_	4	-	4	_	4	-	ns
		6	4	_		_	4	_			4	_		-	
MR to CP		2	80	_	_	_	100	_	_	-	120	-	_	_	
Removal Time	t _{REM}	4.5	16	-	16		20	-	20	-	24	-	24		ns
		6	14	_	_	_	17	_	_	-	20			_	

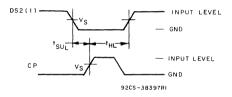


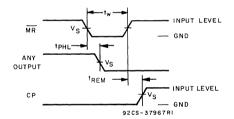
TERMINAL ASSIGNMENT

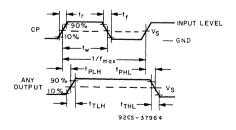
SWITCHING CHARACTERISTICS (C_L=50 pF, Input t_r, t_i= 6 ns)

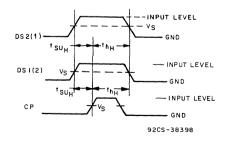
				25	°C			-40° C t	o +85° C						
CHARACTERISTIC	SYMBOL	Vcc	н	нс		нст		74HC		74HCT		нс	54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	170	_	_	_	212	_	_	_	255	T_	_	
CP to Qn	t _{PHL}	4.5	_	34	_	36	_	43	-	45	_	51	-	54	ns
		6	_	29	-	-	-	36	-	-	_	43	-		
MR to Qn		2	_	140	_	_	_	175	_	_	_	210	T-	_	
	l .	4.5	i –	28	-	38	_	35	-	46	-	42	-	57	ns
	t _{PHL}	6	-	24	<u> </u>	L	_	30			_	36			
Output		2		75	_	_	_	95	_	_	_	110	_	-	
Transition Time	t _{TLH}	4.5	_	15	_	15	_	19	_	19	_	22	_	22	ns
	t _{THL}	6	-	13		L – _		16				19	_	-	
Input Capacitance	Cı	_	_	10	_	10	_	10	_	10	-	10	_	10	pF

Transition times, propagation delay times, setup, hold times, and removal times.



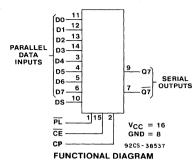






	54/74HC	54/74HCT
INPUT LEVEL	vcc	3 V
SWITCHING VOLTAGE, VS	50% V _{CC}	1.3 V

High-Speed CMOS Logic



8-Bit Parallel-In/ Serial-Out Shift Register

Type Features:

- Buffered Inputs
- Asynchronous Parallel Load
- Complementary Outputs
- Typical $f_{MAX} = 60 \text{ MHz}$ @ $V_{CC} = 5V$, $C_L = 15 \text{ pF}$, $T_A = 25^{\circ} \text{ C}$

The RCA-CD54/74HC165 and CD54/74HCT165 are 8-bit parallel or serial-in shift registers with complementary serial outputs (Q7 and $\overline{Q7}$) available from the last stage. When the parallel load (\overline{PL}) input is LOW, parallel data from the D0 to D7 inputs are loaded into the register asynchronously. When the \overline{PL} is HIGH, data enters the register serially at the DS input and shifts one place to the right (Q0-Q1-Q2, etc.) with each positive-going clock transition. This feature allows parallel-to-serial converter expansion by tying the Q7 output to the DS input of the succeeding device.

For predictable operation the LOW-to-HIGH transition of \overline{CE} should only take place while CP is HIGH. Also, CP and \overline{CE} should be LOW before the LOW-to-HIGH transition of PL to prevent shifting the data when \overline{PL} goes HIGH.

The CD54HC/HCT165 devices are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/HCT165 devices are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

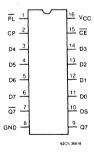
- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity:

 $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5 \ V$

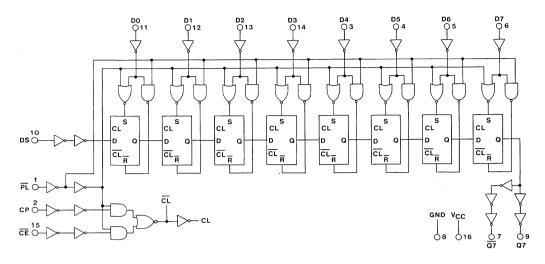
CD54HCT/CD74HCT Types:
 4.5 to 5.5 V Operation
 Direct LSTTL Input Logic Compatibility

 $V_{\rm IL} = 0.8 \text{ V Max.}, V_{\rm IH} = 2 \text{ V Min.}$

CMOS Input Compatibility $I_1 \leq 1 \mu A \otimes V_{OL}$, V_{OH}



TERMINAL ASSIGNMENT



92CM-38538R2

Fig. 1 — Logic diagram for the CD54/74HC165 and CD54/74HCT165.

TRUTH TABLE

Operating			Inpu	ıts	Q _n F	Register	Outputs		
Modes	PL	CE	CP	DS	D0-D7	Q0	Q1-Q6	Q7	Q7
Parallel Load	L	Х	X	Х	L	L	L-L	L	Н
	L	Х	X	Х	Н	Н	H-H	н	L
Serial Shift	Н	L		I	Х	L	q ₀ -q ₅	q_6	$\overline{q_6}$
	Н	L		h	X	Н	q₀-q₅	q_6	$\overline{q_6}$
Hold "Do Nothing"	Н	Н	х	Х	Х	q ₀	q ₁ -q ₆	q ₇	q ₇

- H = HIGH voltage level
- h = HIGH voltage level one setup time prior to the LOWto-HIGH clock transition.
- L = LOW voltage level.
- I = LOW voltage level one setup time prior to the LOWto-HIGH clock transition.
- qn = Lower case letters indicate the state of the referenced output one set-up time prior to the LOW-to-HIGH clock transition.
- X = Don't care.

 √ = LOW-to-HIGH clock transition.

STATIC ELECTRICAL CHARACTERISTICS

		c	D74H	C165	/CD54	4HC16	55					CE	74HC	T165	CD54	нст	165			
CHARACTERISTIC	l	TEST NDITIONS			IC/54		1	HC PE	1	HC PE	TEST CONDITION			CT/54		74F TY	ICT PE	54F TY	ICT PE	UNITS
CHARACTERISTIC	V, V	I _o	V _{cc}		+25° C	;		0/ 5° C	-5 +12		V,	V _{cc}		+25° C	;	-4 +85		-5 +12	5/ 5°C	ONITS
			ľ	Min	Тур	Max	Min	Max	Min	Max	,	•	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15		_	3.15		3.15	_		to	2		_	2	-	2	_	V
	ļ,		6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	<u></u>	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35		to	-	_	0.8	_	0.8	-	0.8	V
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	V _n		2	1.9	_	_	1.9	_	1.9		VIL									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4		or	4.5	4.4	_	-	4.4	-	4.4	-	V
CMOS Loads	V _{IH}		6	5.9	_	-	5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_ '	or	4.5	3.98	-	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2		V _{IH}									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1		0.1	V _{IL}									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6		_	0.1	_	0.1		0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	4	4.5	_	-	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	٧
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
input Leakage	V _{cc}										Any Voltage									
Current I _i	or		6	-	_	±0.1	-	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1		±1	μΑ
	Gnd										& Gnd		<u> </u>							
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-		8	-	80	-	160	or	5.5	-	-	8		80		160	μΑ
Current I _{cc}	Gnd										Gnd						_			
Additional Quiescent Device Current per input pin:											V _{cc} -2.1	4.5 to	_	100	360	_	450		490	μΑ
1 unit load ΔI _{cc} *												5.5								

 $^{^{}ullet}$ For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
DS, D0 to D7	0.35
CP, PL	0.65

^{*}Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	.5 to + 7 V
DC INPUT DIODE CURRENT, I _{IK} (FOR V ₁ < -0.5 V OR V ₁ > V _{CC} +0.5V)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_{o} $<$ -0.5 V OR V_{o} $>$ V_{CC} +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I_o) (FOR -0.5 V $<$ V $_o$ $<$ Vcc + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50mA
POWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	. 500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _a = +100 to +125°C (PACKAGE TYPE F, H)	to 300 mW
For T. = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	to 70 mW
DPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	to +125° C
PACKAGE TYPE E, M40) to +85° C
STORAGE TEMPERATURE (T _{stg})65	to +150° C
EAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ in. (1.59 \pm 0.79 mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

OLIADACTERIOTIO	LIN	IITS	LINUTO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

ALLA PARTICIPATO	CL	SYMBOL	TYP	ICAL	UNITS
CHARACTERISTIC	(pF)	STWBOL	нс	нст	011110
Propagation Delay CP to Q7	15	t _{PHL}	13	17	ns
PL to Q7	15	t _{PLH}	14	17	ns
D7 to Q7	15		12	14	ns
Power Dissipation Capacitance	-	C _{PD}	17	24	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PG} \, V_{CC}^2 \, f_i + \Sigma \, (C_L \, V_{cc}^2 \, f_0)$ where:

f, input frequency

fo output frequency

C_L output load capacitance.

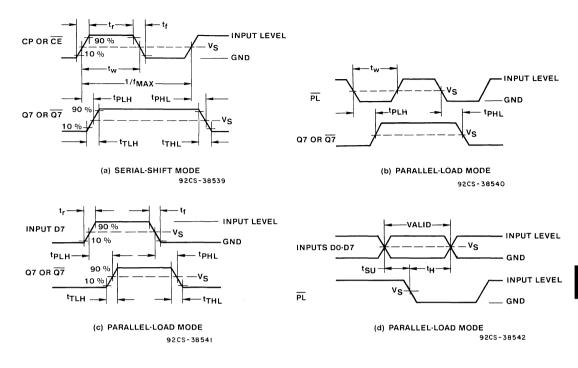
 V_{cc} = supply voltage.

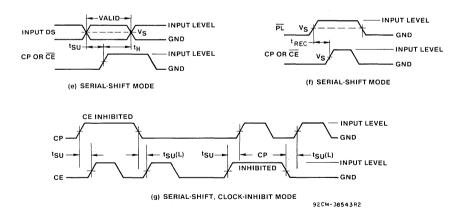
PRE-REQUISITE FOR SWITCHING FUNCTION

					25	°C		-4	0°C te	o +85°	С	-5	5°C to	+125	°C	
CHAF	RACTERISTIC	SYMBOL	Vcc	Н	С	Н	СТ	74	НС	74H	ICT	54	нС	54F	ICT	UNITS
			-	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
CP Pu	ilse Width	t _{wL}	2	80		_	_	100	_	_	_	120	_	-	_	
		twn	4.5	16	_	18		20	-	23	—	24		27	-	ns
			6	14				17		_	_	20	-			
	The state of the s		2	80	_	-	_	100	_	_	_	120	_	_	_	
PL Pu	lse Width	twL	4.5	16	_	20	_	20	_	25	_	24	_	30		ns
			6	14		_		17		_		20			_	
Set-up	Time		2	80	_	_	_	100	_	_	_	120	_			
	DS to CP	t _{su}	4.5	16	_	20		20		25		24		30	l —	ns
		1	6	14	_	_	_	17	-	1 1		20	-			
			2	80	_	_		100	_	_	_	120	-	_	_	
	CE to CP	t _{SU(L)}	4.5	16		- 20	_	20	_	25	—	24		30	_	ns
			6	14	_			17	_ 1	_	_	20				
			2	80	_	_	_	100	_	_	_	120	_		_	
	D0-D7 to PL	t _{su}	4.5	16	l —	20		20	—	25	_	24	-	30	_	ns
			6	14		_	_	17				20		_	_	
Hold 7	Γime		2	35		_	_	45	_		_	55	_	_	_	
	DS to CP	t _H	4.5	7	l —	7	—	9	—	9	-	11	_	11	_	ns
	or CE		6	6	_			8	_	_		9	_		_	
			2	0	_	_	_	0	_	_	_	0	-	_	_	
	CE to CP	tн	4.5	0	l —	0		0	_	0	—	0		0		ns
			6	0	_	_		0	_	_		0				
Recove	ery Time		2	100	-	_	_	125	_	_	—	150		<u> </u>	I —	
	PL to CP	tREC	4.5	20	-	20	—	25		25	—	30	-	30	-	ns
			6	17	<u> </u>			21				26				
Maxim	num Clock		2	6	-	-		5	_	_	-	4	- ¹	_	-	I
Pulse	Frequency	f _{MAX}	4.5	-30	-	27	_	24	_	22	—	20		18	-	MHz
			6	35			<u> </u>	28	<u></u>	_		24	<u> </u>		_	

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,,t=6 ns)

				25	°C		4	0°C to	o +85°	C	-5					
CHAF	RACTERISTIC	SYMBOL	Vcc	Н	C	Н	СТ	74	нс	74F	ICT	54	нС	54F	ICT	UNITS
				Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propag	gation Delay	t _{PLH}	2	_	165	_	_	. —	205	_	-	_	250	_	_	
	CP or CE to	t _{PHL}	4.5	—	33	-	40	—	41	_	50	_	50	l —	60	ns
ļ	Q7 or Q7]	6	_	28	_	_	_	35	_	_	l	43	—	-	
		t _{PLH}	2	_	175	_	_	_	220	_	-	_	265	_		
	PL to Q7 or	t _{PHL}	4.5	_	35		40		44	_	50	_	53	_	60	ns
	Q7		6	<u> </u>	30	_	_	_	37	_	-	_	45	-		
1	D7 to Q7 or	t _{PLH}	2	_	150	_	_	_	190	_	_	_	225	_	I —	
	Q7	t _{PHL}	4.5	_	30	_	35		38	_	44	_	45	_	53	ns
	Q/		6		26	_	_		33	_			38			
		t _{TLH}	2	-	75	_	_	_	95	_		_	110	_	_	
Outpu	t Transition	t _{THL}	4.5	_	15		15	_	19	—	19	_	22	_	22	ns
Time		-	6		13		_	_	16		l —		19	<u> </u>		
				T —	T -	_	_	_	_	-	_		_	-	_	
Input (Capacitance	Cı		-	10	l —	10	_	10	-	10	—	10	—	10	pF
		1		_		—						L –		_	_	

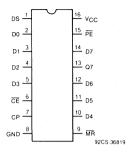




	54/74HC	54/74HCT
Input Level	V _{CC}	. 3V
Switching Voltage, Vs	50% V _{CC}	1.3 V

Fig. 2 — Switching waveforms for the CD54/74HC165 and the CD54/74HCT165

High-Speed CMOS Logic



8-Bit Parallel-In/Serial-Out Shift Register

Type Features:

- Buffered inputs
- Typical $f_{MAX} = 50 \text{ MHz}$ @ $V_{CC} = 5V$, $C_L = 15 \text{ pF}$, $T_A = 25^{\circ} \text{ C}$

TERMINAL ASSIGNMENT

The RCA-CD54/74HC166 and CD54/74HCT166 8-bit shift register is fabricated with silicon gate CMOS technology. It possesses the low power consumption of standard CMOS integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky device.

The CD54/74HCT166 is functionally as well as pin compatible with the standard 54LS/74LS166.

The 166 is an 8-bit shift register that has fully synchronous serial or parallel data entry selected by an active LOW Parallel Enable (\overline{PE}) input. When the \overline{PE} is LOW one setup time before the LOW-to-HIGH clock transition, parallel data is entered into the register. When \overline{PE} is HIGH, data is entered into internal bit position Q0 from Serial Data Input (Ds), and the remaining bits are shifted one place to the right (Q0 \rightarrow Q1 \rightarrow Q2, etc.) with each positive-going clock transition. For expansion of the register in parallel to serial converters, the Q7 output is connected to the DS input of the succeeding stage.

The clock input is a gated OR structure which allows one input to be used as an active LOW Clock Enable (\overline{CE}) input. The pin assignment for the CP and \overline{CE} inputs is arbitrary and can be reversed for layout convenience. The LOW-to-HIGH transition of \overline{CE} input should only take place while the CP is HIGH for predictable operation.

A LOW on the Master Reset $\overline{(MR)}$ input overrides all other inputs and clears the register asynchronously, forcing all bit positions to a LOW state.

The CD54HC166 and CD54HCT166 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC166 and CD74HCT166 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: NIL = 30%, NIH = 30% of Vcc; @ Vcc = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility VIL = 0.8 V Max., VIH = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ VoL, VoH

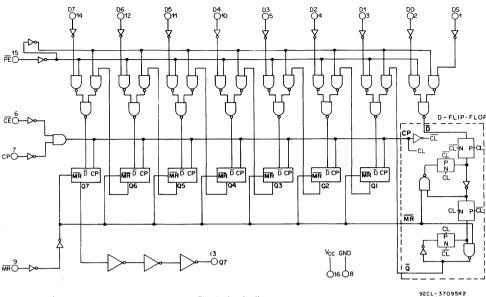


Fig. 1 - Logic diagram.

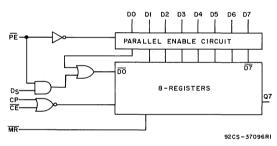


Fig. 2 - Functional diagram.

TRUTH TABLE

		<u> </u>			Parallel	Intern Q Stat	Q States	
Master Reset	Parallel Enable	Clock Enable	Clock	Serial	Do D7	Qo Q) 1	Output Q7
L	х	Х	Х	Х	Х	L	L	L
Н	x	L	L	x	×	Q00	Q10	Q0
Н	L	L	~	x	ah	a	b	h
Н	н	L		н	×	н (Q0n	Q6n
Н	Н	L		L	×	L	Q0n	Q6n
н	x	Н	_~	x	×	Q00	Q10	Q 70

H = high level (steady state).

a . . . h = the level of steady-state input at inputs Do thru D7, respectively.

L = low level (steady state).

Q00, Q10, Q70 = the level of Q0, Q1, or Q7, respectively, before the indicated steady-state input conditions were established.

X = irrelevant (any input, including transitions).

= transition from low to high level.

Qon, Qon = the level of Qo or Q6, respectively, before the most recent transition of the clock.

STATIC ELECTRICAL CHARACTERISTICS

· · · · · · · · · · · · · · · · · · ·		c	D74H	C166	/CD54	HC16	66					CE	74HC	T166	/CD54	нст	166			
CHARACTERISTIC		TEST NDITIONS			IC/54		74HC 54HC TYPES TYPES				TEST CONDITIONS		(CT/54 TYPE:			ICT PES		ICT PES	
CHARACTERISTIC	V,	I _o	V _{cc}		+25°C			-40/ +85° C		5/ 5°C	V,	V _{cc}		+25° C		-40/ +85° C		-55/ +125°C		UNITS
		""	ľ	Min	Тур	Max	Min	Max	Min	Max	•	ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-	_	1.5	_	1.5	_		4.5								
Input Voltage V _m			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	-	-	2	-	2	-	V .
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								-
Input Voltage V_{IL}			4.5	_	_	1.35	-	1.35	-	1.35	_	to	-	-	0.8	_	0.8	_	0.8	V
			6	_		1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	V_{i_k}									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4		V
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{D1}									
	V _{IL}										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_		3.84	_	3.7	_	or	4.5	3.98	-	_	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V,,,									
Low-Level	V _{IL}		2	-	_	0.1	_	0.1	_	0.1	V _{1.}									
Output Voltage Vo.	or	0.02	4.5	_	_	0.1		0.1	-	0.1	or	4.5	-	_	0.1	-	0.1	-	0.1	V
CMOS Loads	VIH		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	VIL										V _{IL}									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6	_	_	0.26	_	0.33	-	0.4	V _{u+}									
Input Leakage	Vcc								1		Any Voltage									
Current I,	or		6		-	±0.1	_	±1	-	±1	Between V _{cc}	5.5	-	_	±0.1	-	±1		±1	μΑ
	Gnd										& Gnd	_								
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	_	-	8	_	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd	_	_	<u> </u>	_					<u> </u>
Additional Quiescent												4.5								
Device Current per input pin:											V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
1 unit load Δ lcc*											L	5.5		1	<u> </u>		<u> </u>	L	<u></u>	

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
DS, D0-D7	0.2
PE	0.35
CP, CE	0.5
MR	0.2
	I .

*Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, I_{IK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)	±20mA
DC OUTPUT DIODE CURRENT, Iox (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50mA
POWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	. Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	. Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN	MITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range (For TA = Full Package Temperature Range) VCC:*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage VIN, VOUT	0	Vcc	V
Operating Temperature TA:			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, tr, tr			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ} \text{ C}$, Input t_r , $t_t = 6 \text{ ns}$)

		C,	Ту	oical	
CHARACTERISTIC	рF	нс	нст	Units	
Clock to O	PLH PHL	15	13	17	ns
Maximum Clock Frequency f	мах	15	50	50	MHz
Power Dissipation Capacitance*	O _{PD}	_	41	٠ 41	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D=C_{PD} \ V_{CC}^2 \ f_i + \Sigma \ (C_L \ V_{CC}^2 \ f_o)$ where: f_i =input frequency

fo=output frequency

C_L=output load capacitance

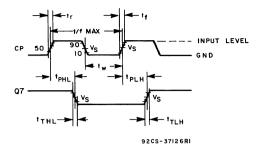
V_{cc}=supply voltage

PRE-REQUISITE FOR SWITCHING FUNCTION

-	-		LIMITS												
CHARACTERIST		TEST	25° C				-4	0°C te	o +85°	,C	-55° C to +125° C				UNITS
CHARACTERIST	10		нс		нст		74HC		74HCT		54HC		54HCT		UNITS
		Vcc V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	
Clock Frequency	fmax	2	6		_	Ì	5		-		4		_		
Fig. 3		4.5	30		25		25		20		20		16		MHz
		6	35		_		29		_		23		_		
MR Pulse Width	tw	2	100		_		125		_		150		_		
Fig. 4		4.5	20		35		25		44		30		53		ns
		6	17		_		21		<u> </u>		26		_		
Clock Pulse Width	tw	2	80		-		100		_		120		_		
Fig. 3		4.5	16		20		20		25		24		30		ns
		6	14		_	ŀ	17				20		_		
Set-up Time	tsu	2	80		_		100		_		120		_		
Data and CE to		4.5	16		16		20		20		24		24		ns
Clock, Fig. 5, 6		6	14		—		17		—		20		-		
Hold Time	t _H	2	1		_		1		_		1		-		
Data to Clock,		4.5	1		0		1		0		1		0		ns
Fig. 5		6	1		—		1		ļ. —	İ	1		—		
Removal Time	tREM	2	0		_		0		_		0		l —		
MR to Clock		4.5	0		0		0		0	1	0		0		ns
Fig. 4		6	0		_		0		—		0		l —		
Set-up Time	tsu	2	145		_		180		_		220				
PE to CP		4.5	29		30		36		38		44		45		ns
Fig. 6		6	25		_		31		l —		38		_		
Hold Time	t _H	2	0		-		0		_		0		_		
PE to CP or CE		4.5	0		0		0		0		0		0		ns
Fig. 6		6	0				0		l –		0		_		

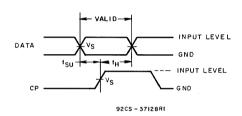
SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_s, t_f = 6 ns)

							LIM	ITS	,						
0114040750107		TEST	25° C				-4	0°C te	+85°	c	-55	UNITS			
CHARACTERISTIC		CONDITION	нс		нст		74HC		74HCT		54HC		54HCT		UNITS
		Vcc V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	tPLH	2		160		_		200		_		240		_	
Clock to Output	tPHL	4.5		32		40		40		50		48		60	ns
Fig. 3		6		27		_		34				41		_	
Output Transition	tTLH	2		75		-		95		_		110		_	
Time	tTHL	4.5		15		15		19		19		22		22	ns
Fig. 3		6		13		_		16				19		_	
Propagation Delay	tPHL	2		160		_		200		_		240		_	
MR to Output		4.5		32		40		40		50		48		60	ns
Fig. 4		6		27				34				41		_	
Input Capacitance	Cı			10		10		10		10		10		10	pF



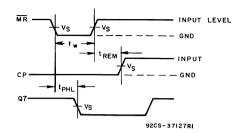
 V_S
 50% V_{CC}
 1.3 V

Fig. 3 - Clock pre-requisite times and propagation and output transition times.



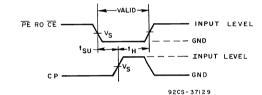
	54/74HC	54/74HCT
INPUT LEVEL	V _{cc}	3.0 V
V _S	50% V _{CC}	1.3 V

Fig. 5 - Data pre-requisite times.



	54/74HC	54/74HCT
INPUT LEVEL	v _{cc}	3.0 V
ν _s	50% V _{CC}	1.3 V

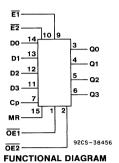
Fig. 4 - Master reset pre-requisite times and propagation delays.



	54/74 HC	54/74 HCT
INPUT LEVEL	V _{cc}	3.0 V
V _S	50% V _{CC}	1.3 V

Fig. 6 - Parallel enable or clock enable pre-requisite times.

High-Speed CMOS Logic



Quad D-Type Flip-Flop, 3-State Positive-Edge Triggered

Type Features:

- 3-state buffered outputs
- gated input and output enables

The RCA CD54/74HC173 and CD54/74HCT173 high speed 3-STATE QUAD D TYPE FLIP-FLOPS are fabricated with silicon gate CMOS technology. They possess the low power consumption of standard CMOS Integrated circuits, and can operate at speeds comparable to the equivalent low power Schottky devices. The buffered outputs can drive 15 LSTTL loads. The large output drive capability and 3-STATE feature make these parts ideally suited for interfacing with bus lines in bus oriented systems.

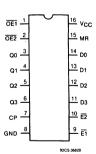
The four D TYPE FLIP-FLOPS operate synchronously from a common clock. The outputs are in the 3-STATE mode when either of the two output disable pins are at the logic "1" level. The input ENABLES allow the flip-flops to remain in their present states without having to disrupt the clock. If either of the 2 input ENABLES are taken to a logic "1" level, the Q outputs are fed back to the inputs, forcing the flip flops to remain in the same state. Reset is enabled by taking the MASTER RESET (MR) input to a logic "1" level. The data outputs change state on the positive going edge of the clock.

The CD54/74HCT173 logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC173 and CD54HCT173 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC173 and D74HCT173 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range):
 Standard Outputs 10 LSTTL Loads
 Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

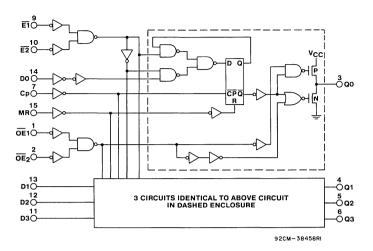
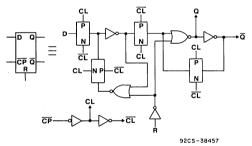


Fig. 1 — Logic diagram for the CD54/74HC/HCT173.



Flip-Flop Detail

TRUTH TABLE

		nputs			
		Data	Enable	Data	Output
MR	СР	E1	E2	D	a
l н	x	x	X	х	1
L	ΙË	x	â	Ιŝ	ا مَ
L	ر ا	H	Х	l x	Qo
L	- <u>-</u> -	X	Н	X	Qo
l L	_~	L	L	L	L
l L		l L	L	l H	Н

When either $\overline{OE1}$ or $\overline{OE2}$ (or both) is (are) high the output is disabled to the high-impedance state, however, sequential operation of the flip-flops is not affected.

H = high level (steady state) X = don't care (any input including transitions)

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_1 < -0.5$ V OR $V_1 > V_{CC} + 0.5$ V)	± 20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_O < -0.5 V OR V_O > V_{CC} +0.5 V)	$\dots \dots \pm 20 \text{ mA}$
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR:-0.5 V < Vo < Vcc +0.5 V)	± 35 mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	± 70 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacti	ng lead tips only+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIMITS MIN. MAX. 2 6 4.5 5.5 0 V _{cc} -40 +85 -55 +125 0 1000 0 500		
CHARACTERISTIC		MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC173/CD54HC173									CD74HCT173/CD54HCT173									
	coi	TEST	s	1	IC/54		I	HC PE	54I TY	HC PE	TEST			CT/54		74H TY	ICT PE	54H TY	ICT PE	
CHARACTERISTIC	V _i	lo	Vcc		+25°0	•	l	10/ 5°C	ı	5/ 5°C	V _i	Vcc		+25°0	•	l	10/ 5°C	-55/ +125°C		UNITS
	v	mA	V	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	-	2	_	2	-	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35		1.35		1.35	_	to	-	_	0.8	-	0.8	_	0.8	v
			6	_	_	1.8	_	1.8		1:8		5.5								
High-Level	VIL		2	1.9	_	<u> </u>	1.9	_	1.9	_	VıL					İ				
Output Voltage Vон	or	-0.02	4.5	4.4	_		4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	_	4.4	-	l v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	VIL										VıL									
TTL Loads	or	-6	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2		Vін									
Low-Level	VIL		2	_	_	0.1		0.1	_	0.1	VıL							İ		
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	_	0.1	-	0.1	v
CMOS Loads	V _{IH}		6		_	0.1	_	0.1	_	0.1	ViH									
	VIL										VıL									
TTL Loads	or	6	4.5			0.26	_	0.33		0.4	or	4.5	_	_	0.26	-	0.33	-	0.4	v
(Bus Driver)	V _{IH}	7.8	6	_	_	0.26	_	0.33	_	0.4	V _{iH}									
Input Leakage	Vcc	l						}			Any Voltage									
Current I ₁	or		6	_	_	±0.1	_	±1	_	±1	Between V _{cc}	5.5	-	_	±0.1	_	±1	–	±1	μΑ
	Gnd										& Gnd	-,_								
Quiescent	Vcc										Vcc									
Device	or	0	6	-	_	8	_	80	-	160	or	5.5	-	-	8	_	80	-	160	μА
Current Icc	Gnd										Gnd			ļ		ļ				
Additional Quiescent Device Current per input pin: 1 unit load											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-State Leakage Current	V _{IL} or V _{IH}	V _o =V _{cc} or Gnd	6	-	-	±0.5	-	±5.0	_	±10	V _{IL} or V _{IH}	5.5	-	-	±0.5	_	±5.0	-	±10	μΑ

^{*}For dual-supply systems theoretical worst case (V_{i} = 2.4 V, V_{cc} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
D0-D3	0.15
<u>E1</u> & <u>E2</u>	0.15
CP	0.25
MR	0.2
OE1 & OE2	0.5

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$, input t_r , $t_t = 6 \text{ ns}$)

CHARACTERISTIC		CL	TYP	TYPICAL			
CHARACTERISTIC		(pF)	нс	нст	UNITS		
Propagation Delay,	t _{PLH}	15	17	10			
Clock to Q	t _{PHL}	15		18	ns		
Propagation Delay,	t _{PLZ}	4.5					
Output Disable and Enable to Q	tenz	15	12	12	ns		
	t _{PZL}	4.5	40				
	t _{PZH}	15	12	14	ns		
Maximum Clock Frequency	f _{max}	-	60	60	MHz		
Power Dissipation Capacitance*	C _{PD}	_	29	34	pF		

 $^{^*}C_{PD}$ is used to determine the dynamic power consumption, per package. $P_D = C_{PD} \; V_{CC^2} \; f_i + \Sigma \; C_L \; V_{CC^2} \; f_o$ where: $f_i =$ input frequency, $f_o =$ output f

PREREQUISITE FOR SWITCHING FUNCTION

								LIM	ITS						
CHARACTERIS	TIC	TEST CONDITION		25	°C		-4	0°C to	+85	°C	-5	UNITS			
OHAHAOTEHIO			н	C	н	СТ	74	нс	74F	ICT	T 54HC		54НСТ		Oitilis
		V _{cc} V	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	
Maximum Clock		2	6		_		5		_		4		_		
Frequency	f _{max}	4.5	30		20		24	1	16		20		13		MHz
Fig. 3		6	35				28				24				
		2	80		_		100		_		120		_		
MR Pulse Width	$t_{\mathbf{w}}$	4.5	16		15		20		19		24		22		ns
Fig. 4		6	14		_		17				20		_		
		2	80.		—		100		· —		120		—		
Clock Pulse Width	ı t _w	4.5	16		25		20		31		24		38		ns
Fig. 3		6	14				17		_		20		_		
Set-up Time		2	60		_		75		_		90		-		
Data to Clock		4.5	12		12		15		15		18		18		ns
Fig. 5	t _{SU}	6	10		_		13		_		15		_		
Set-up Time		2	60		—		75		—		90		_		
E to Clock		4.5	12		18		15		23		18		27		ns
	t _{su}	6	10				13		_		15		_		
Hold Time		2	3		-		3		-		3		-	ł	
Data to Clock		4.5	3		0		3		0		3		0		ns
Fig. 5	t _H	6	3		_		3		_		3				
Hold Time		2	0		-		0		—		0		-	1	
E to Clock		4.5	0		0		0		0	ļ.	0		0		ns
	t _H	6	0			<u> </u>	0		_	ļ	0	<u> </u>	_		
Removal Time		2	60		-		75		-		90		-		
MR to Clock	t _{REM}	4.5	12		12	-	15		15		18	1	18		ns
		6	10		—		13	<u> </u>			15		_		

where: f_i = input frequency, f_o = output frequency, C_L = output load capacitance, V_{CC} = supply voltage.

SWITCHING CHARACTERISTICS (V_L = 50 pF, Input t_r, t_f = 6 ns)

								LIM	ITS						
CHARACTERIST		TEST		25	°C		-4	0°C to	+85	°C	-5	5°C to	+125	s°C	UNITS
CHARACTERIST	IC	CONDITION	н	С	н	СТ	74	нс	74F	нст	54	нс	54H	ЮТ	UNIIS
		V _{cc}	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	
Propagation Delay	t _{PLH}	2	_	200	_	_	_	250	_	_	_	300	_	_	
Clock to Output	t _{PHL}	4.5	—	40	—	43	—	50	—	54	_	60	-	65	ns
Fig. 3		6		34		L-		43	_			51	_		
Propagation Delay		2	—	175	—	-	—	220	_	_	_	265	_	_	
MR to Output	t _{PHL}	4.5		35	—	37	—	44	—	46	_	53	—	56	ns
Fig. 4		· 6		30			_	37	_			45	_		
Propagation Delay,	t_{PLZ}	2	—	150	—	—	—	190	—	_	_	225	—	—	
Output Enable to	Q t _{PHZ}	4.5		30	_	30	—	38	_	38	_	45	_	45	ns
		6	_	26			_	33			_	38	_	_	
	t _{PZL}	2	_	150	—	-	_	190	_	_	_	225	_	-	
	t _{PZH}	4.5	_	30	_	35		38	_	44	_	45	_	53	ns
Fig.6		6	_	26		_		33		<u> </u>	_	38	_	-	
Output Transition	t _{TLH}	2	_	60		_		75	_	_	_	90	_	-	
Time	t _{THL}	4.5	_	12	_	12	_	15	_	15	_	18	_	18	ns
Fig. 3		6	_	10	_	_		13	_	_	_	15	_	_	
Input Capacitance	Сі	_	_	10		10		10		10		10		10	pF
3-State Output Capacitance	Co		_	20	_	20	_	20	_	20	_	20		20	pF

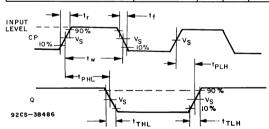


Fig. 3 — Clock to output delays and clock pulse width.

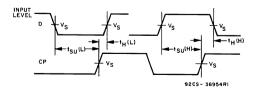


Fig. 5 — Data set-up and hold times.

	CD54/74HC	CD54/74HCT
Input Level	V _{cc}	3 V
Vs	0.5 V _{cc}	1.3 V

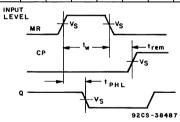


Fig. 4 — Master reset pulse width. Master reset to output delay and master reset to clock recovery time.

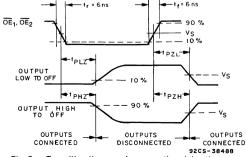
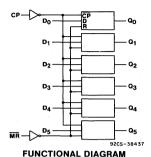


Fig. 6 — Transition times and propagation delay times.

High-Speed CMOS Logic



Hex D-Type Flip-Flop with Reset Positive-Edge Triggered

Type Features:

- Buffered Positive-Edge-Triggered Clock
- Asynchronous Common Reset

The RCA-CD54/74HC174 and CD54/74HC1714 are edge triggered flip-flops which utilize silicon gate CMOS circuitry to implement D-type flip-flops. They possess low power and speeds comparable to low power Schottky TTL circuits. The devices contain 6 master-slave flip-flops with a common clock and common reset. Data on the D input having the specified setup and hold times is transferred to the Q output on the low to high transition of the CLOCK input. The MR input, when low, sets all outputs to a low state.

Each output can drive 10 low power Schottky TTL equivalent loads. The CD54/74HCT174 is functionally as well as pin compatible to the 54LS174/74LS174.

The CD54HC174 and CD54HCT174 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC174 and CD74HCT174 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs — 10 LSTTL Loads Bus Driver Outputs — 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}

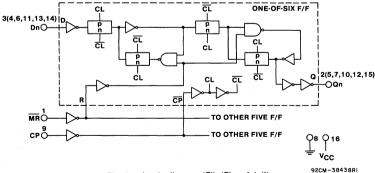


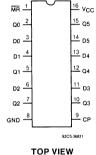
Fig. 1 — Logic diagram (Flip/Flop detail)

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_1 < -0.5$ V OR $V_1 > V_{CC} + 0.5$ V)	$\dots \dots \pm 20 \ mA$
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	$\dots \dots \pm 20 \ mA$
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Vo $<$ Vcc +0.5 V)	aaaaaaaaaaaaaaaaaaaaaaaaaaaaaaaaaaaa
DC V _{cc} OR GROUND CURRENT (I _{cc}):	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (Tstg)	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacting le	

TRUTH TABLE (EACH FLIP-FLOP)

	INPUTS		оитритѕ
RESET (MR)	CLOCK	DATA Dn	Qn
L	х	х	L
н		н	н
н	~	L	L
н	L	х	Qo



MR -1

H = High Level (Steady State)

L = Low Level (Steady State)

X = Irrelevant

✓= Transition from Low to High Level

Qo, = Level Before the Indicated Steady-State Input Conditions were established

TERMINAL ASSIGNMENT

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIMITS					
CHARACTERISTIC	MIN.	MAX.	UNITS			
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{CC} :* CD54/74HC Types CD54/74HCT Types	2 4.5	6 5.5	v			
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V			
Operating Temperature T _A : CD74 Types CD54 Types	-40 -55	+85 +125	°C			
Input Rise and Fall Times, t _r , t _r at 2 V at 4.5 V at 6 V	0 0	1000 500 400	ns			

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

				CD	74HC	174/C	D54H	IC174						CD74	HCT	174/C	D54F	ICT17	4		
			TEST	s		IC/54 TYPE			HC PE	54i TY		TEST		1 7	CT/54 TYPE		74H TY		54H TY	-	
CHARACTERIST	IIC	V 1	lo .	Vcc	-	⊦25°C	;	-4 +85		-5 +12		V 1	V _{cc}	4	+25°C	:		0/ 5°C	-55/ +125°C		UNITS
		V	mA	٧	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15	_	_	3.15		3.15	_	-	to	2	_	-	2	-	2	-	V
				6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level				2	_	_	0.5		0.5	_	0.5		4.5								
Input Voltage	V_{IL}			4.5		_	1.35	-	1.35	_	1.35	_	to	-	_	0.8	_	0.8		0.8	٧
				6	_	_	1.8		1.8	_	1.8		5.5					ļ			
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VIL					ĺ				
Output Voltage	V _{он}	or	-0.02	4.5	4.4			4.4	_	4.4	_	or	4.5	4.4	_	–	4.4	-	4.4	-	V
CMOS Loads		V _{IH}		6	5.9	_	_	5.9		5.9	_	V _{IH}		Ŀ							
		VIL										VıL									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	-	3.84	-	3.7	-	v
		V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}			ļ						
Low-Level		. V _{IL}		2	_	_	0.1	_	0.1	_	0.1	VIL				ł					
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	_	0.1		0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	٧
CMOS Loads		V _{IH}		6	_		0.1	<u>-</u>	0.1	_	0.1	V _{IH}									
		VIL										VıL									
TTL Loads		or	4	4.5	_		0.26	_	0.33		0.4	or	4.5	_	-	0.26	-	0.33	-	0.4	V
		V _{IH}	5.2	6	_		0.26		0.33	_	0.4	V _{IH}					<u> </u>				
Input Leakage Current	l _i	V _{cc} or		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc}	5.5	_	_	±0.1	_	±1		±1	μΑ
		Gnd	Ė									& Gnd					ĺ				
Quiescent		Vcc										Vcc									
Device		or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	-	160	μΑ
Current	Icc	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load 2	71cc .											V _{cc} -2.1	4.5 to 5.5	_	100	360	-	450	-	490	·μA

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
СР	0.80
MR	0.55
D	0.15

^{*}Unit load is Δ I_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

PREREQUISITE FOR SWITCHING FUNCTION

							_	LIM	ITS						
CHARACTERIS	TIC	TEST CONDITION		25	°C		-4	0°C to	+85	°C	-5	5°C to	+125	s°C	UNITS
CHARACTERIS	IIC		н	С	н	СТ	74	нс	74F	ICT	54	нс	54F	ЮТ	UNIIS
		V _{cc} V	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Clock Pulse		2	80	-		_	100	-	_	—	120	–	_	_	
Width	tw	4.5	16	_	20	-	20	-	25	—	24	–	30	-	ns
Fig. 3		6	14				17		_		20	_	_		
Ì		2	80	—	—	—	100	-	—	—	120	—	—	—	
MR Pulse Width	tw	4.5	16	_	25	<u> </u>	20		31	_	24	-	38	_	ns
Fig. 4		6	14	_			17				20				
Setup Time Data		2	60	_	_	—	75	-	_	—	90	-	—	—	
to Clock	t _{su}	4.5	12	_	16	_	15	-	20	_	18	-	24	_	ns
Fig. 5		6	10	_			13				15				
Hold Time Data		2	5	_	—	-	5	-	—	_	5	_	_	—	
to Clock	t_{H}	4.5	5	_	5	—	5	-	5	—	5	-	5	_	ns
Fig. 5		6	5	_		_	5				5	<u> </u>	_		
Removal Time		2	5	_	_	_	5	_	_	_	5	_	-	_	
MR to Clock	t _{rem}	4.5	5	-	12	_	5	-	15	_	5	-	18	-	ns
Fig. 4		6	5		_	_	5				5	<u> </u>		_	
		2	6	_	_		5	_	_	_	4	_	_	_	
Clock Frequency	f_{max}	4.5 6	30 35	_	25 —	 -	24 28	_	20 —	 -	20 24	_	17 —	_	MHz

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t, t_f = 6 ns)

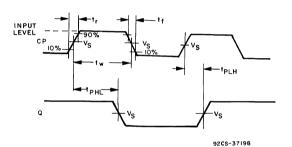
								LIM	IITS							
CHARACTERIC	-10	TEST		25	°C		-4	0°C to	o +85	°C	-5	5°C to	+125	s°C		
CHARACTERIST	IIC	CONDITION	н	С	н	СТ	74	нс	741	СТ	54	нс	541	ICT	UNITS	
		V _{cc} V	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Propagation Delay	t _{PLH}	2	_	165	_	_	_	205	_	_	_	250	_	-		
Clock to Q	t _{PHL}	4.5	—	33	-	40	_	41	-	50		50	—	60	ns	
Fig. 3		6	_	28		_	_	35	_			43		<u> </u>		
Propagation Delay	t _{PLH}	2	_	150		-	-	190	-	-	—	225	_	-		
MR to Q	t _{PHL}	4.5	_	30	_	44	_	38		55	_	45	—	66	ns	
Fig. 4		6	-	26		_	_	33			L —	38				
Output Transition	tTLH	2	_	75	_		_	95	_	-	_	110	_	—		
Time	t _{THL}	4.5	_	15	_	15	_	19	—	19	_	22	_	22	ns	
Fig. 6		6		13				16				19	<u> </u>			
Input Capacitance	Cin		_	10	_	10	_	10	_	10		10	_	10	pF	

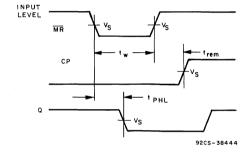
SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t₁ = 6 ns)

		CL	Typica	Typical Values		
CHARACTERISTIC		(pF)	нс	HCT	UNITS	
Propagation Delay —	t _{PLH}	15	13	17	ns	
Clock to Q Fig.3	t _{PHL}	'3	13	''	113	
Propagation Delay —	t _{PLH}	15	12	18	ns	
MR to Q Fig. 4	tehl	15	12	10	115	
Power Dissipation Capacitance*	C _{PD}	_	38	44	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per flip-flop.

 C_L = output load capacitance, V_{CC} = supply voltage





	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Vs	50% V _{CC}	1.3 V

/
V

 V_{cc} 3 V ٧s 50% V_{CC} 1.3 V

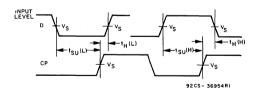
54/74HC

54/74HCT

Fig. 3 — Propagation delay times and clock pulse width.

Fig. 4 — Prerequisite and propagation delay times for master reset.

Input Level



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Vs	50% V _{cc}	1.3 V

Fig. 5 — Pre

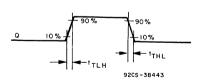
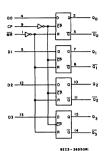


Fig. 6 — Transition times.

 $P_D = C_{PD} \; V_{CC^2} \; f_i + \Sigma \; (C_L \; V_{CC^2} \; f_o) \; \text{where:} \quad f_i = \text{input frequency, } f_o = \text{output frequency,}$

High-Speed CMOS Logic



Quad D Flip-Flop with Reset

Type Features:

- Common Clock and Asynchronous Reset on four D-Type Flip-Flops
- Positive-edge pulse triggering
- Complementary Outputs
- Buffered Inputs
- Typical $f_{MAX} = 50 \text{ MHz}$ @ $V_{CC} = 5 \text{ V}$, $C_L = 15 \text{ pF}$, $T_A = 25^{\circ} \text{ C}$

FUNCTIONAL DIAGRAM

The RCA CD54/74HC175 and the CD54/74HCT175 are high speed Quad D-Type Flip-Flops with individual D-inputs and Q, \overline{Q} complementary outputs. The devices are fabricated using silicon gate CMOS technology. They have the low power consumption advantage of standard CMOS ICs and the ability to drive 10 LSTTL devices.

Information at the D input is transferred to the Q and \overline{Q} outputs on the positive-going edge of the clock pulse. All four Flip-Flops are controlled by a common clock (CP) and a common reset (\overline{MR}) . Resetting is accomplished by a low voltage level independent of the clock. All four Q outputs are reset to a logic 0 and all four \overline{Q} outputs to a logic 1.

The CD54HC175 and CD54HCT175 are supplied in 16-lead dual-in-line ceramic packages (F suffix) and the CD74HC175 and CD74HCT175 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: NIL = 30%, NIH = 30% of VCC; @ VCC = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility VIL = 0.8 V Max., VIH = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ VOL, VOH

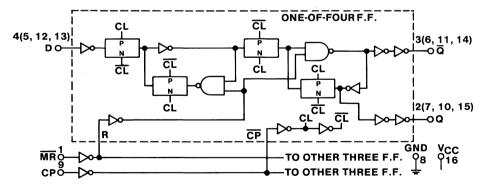


Fig. 1 - Logic block diagram.

92CM-36949R1

MAXIMUM RATINGS, Absolute-Maximum Values:

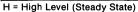
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, I_{IK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)	
DC OUTPUT CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C
RECOMMENDED OPERATING CONDITIONS:	
For maximum reliability, nominal conditions should be selected so that operati	on is always within the following ranges:

<u> </u>	LII	MITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range (For TA = Full Package Temperature Range) Vcc:*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage VIN, VOUT	0	Vcc	V
Operating Temperature TA:			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, tr, tr			
at 2 V	0	1000	ns
at 4.5 V	. 0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

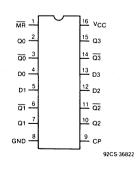
TRUTH TABLE (EACH FLIP-FLOP)

	INPUTS	оиті	PUTS	
RESET (MR)	CLOCK	DATA Dn	Qn	Qn
L	х	х	L	Н
н		н	н	L
н		Ľ	L	н
н	L	х	Qo	Qo



L = Low Level (Steady State)

Input Conditions were Established



TERMINAL ASSIGNMENT

X = Irrelevant

 $[\]mathcal{L}$ = Transition from Low to High Level

Qo, Qo = Levels Before the Indicated Steady-State

STATIC ELECTRICAL CHARACTERISTICS

		c	D74H	C175	/CD54	HC17	'5					CD	74HC	T175	/CD54	HCT.	175			
CHARACTERISTIC	coi		74HC/54HC 74HC TYPES TYPES			54HC TYPES		TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS			
CHARACTERISTIC	V,	I _o mA	V _{cc}	-	+25° C	;	-4 +85		-5 +12		V.	V _{cc}	+25° C		;	-40/ +85° C		-55/ +125° C		UNITS
		mA	*	Min	Тур	Max	Min	Max	Min	Max			Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	-	2	-	2	-	V
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V_{iL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	-	-	0.8	-	0.8	-	0.8	v
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	V _{IL}		2	1.9	_	-	1.9	_	1.9		VIL									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4		4.4	_	or	4.5	4.4	-	-	4.4	_	4.4	_	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		. 2	_	_	0.1	_	0.1	_	0.1	VIL									
Output Voltage V _{OL}	or	0.02	4.5		-	0.1	-	0.1	-	0.1	or	4.5	-	-	0.1	_	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_		0.1	_	0.1	_	0.1	V _{IH}									
	Vil										VIL									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	. v
·	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I _i	or		6	-	-	±0.1	-	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										& Gnd									
Quiescent	V _{cc}										Vcc									
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	–	8	-	80	-	160	μΑ
Current I _{cc}	Gnd				<u> </u>						Gnd									
Additional Quiescent Device Current											V _{cc} -2.1	4.5 to	_	100	360	-	450	_	490	μΑ
per input pin: 1 unit load Δ lcc*												5.5								

 $^{^{\}star}$ For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
MR	1.0
D	0.15
CP	0.6

^{*}Unit Load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

PRE-REQUISITE FOR SWITCHING FUNCTION 54/74HC SERIES AND 54/74HCT SERIES

								LIM	ITS						
		TEST									°C	UNITS			
CHARACTERIS	CHARACTERISTIC		н	ıc	н	ст	741	нс	74H	CT	54	нс	54 F	ICT	UNITS
		Vcc V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Clock Pulse		2	80	-	_	-	100	_	-	_	120	-		-	
Width	tw	4.5	16	-	20	-	20	-	25		24	-	30	_	ns
Fig. 3		6	14	-			17	_		<u> </u>	20		_	<u> </u>	
		2	80	 –	-	_	100	_	_	—	120		_	_	
MR Pulse Width	tw	4.5	16	—	20	—	20	-	25	—	24	-	30	_	ns
Fig. 4		6	14	_	_	<u> </u>	17			_	20	<u> </u>	_	_	
Setup Time Data		2	80	-	_	_	100	-	_	_	120	-	—	-	
to Clock	tsu	4.5	16	-	20	—	20	—	25	—	24	-	30	-	ns
Fig. 5		6	14	-	_		17	_	_		20	_	_		
Hold Time Data		2	5	-	_	—	5		—	-	5	—		—	
to Clock	t _H	4.5	5		5	-	5	—	5	-	5	-	5	-	ns
Fig. 5		6	5	_		_	5			_	5	1-	<u> </u>		
Removal Time		2	5	_			5	_	_	-	5	_		-	
MR to Clock	t _{REM}	4.5	5	-	5	-	5	-	5	—	5	-	5	-	ns
Fig. 4		6	5	-	-	—	5		<u> </u>	_	5	<u> </u>	<u> </u>	1-	
		2	6	_	_		5	_	-	-	4	-	-	-	
Clock Frequency	f _{max}	4.5	30	-	25	_	25	-	20	-	20	-	16	-	MHz
		6	35	_	_	_	29	_	_	_	23	_	_	_	

SWITCHING CHARACTERISTICS (CL = 50 pF, Input t, t= 6 ns)

								LiM	ITS						
CHARACTERIST	10	TEST		25° C				-40° C to +85° C				° C to	+ 125	° C	UNITS
CHARACTERIST	iC .	CONDITION	нс		нст		74HC		74HCT		54HC		54НСТ		UNITS
		V _{cc} V	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	— ·	175	_	-	_	220	_	_	_	265	_	-	
Clock to Q or Q	t _{PHL}	4.5		35	_	33		44	_	41	<u> </u>	53	_	50	ns
Fig. 3		6		30	_		_	37	_	_	_	45	_	—	
Propagation Delay	t _{PLH}	2	-	175	_	_	_	220	_	_	_	265	_	_	
(MR) to Q or Q	tPHL	4.5	—	35	—	40	— ·	44	_	50	—	53	_	60	ns
Fig. 4		6		30	_		_	37	_	_	_	45	-	_	
Output Transition	t _{TLH}	2	-	75	-	_	_	95	_	_	_	110	_	_	
Time	t_{THL}	4.5	-	15		15		19	_	19	_	22		22	ns
Fig. 6		6	_	13	_	—	—	16	_	_	-	19		—	
Input Capacitance	Cı		_	10		10	_	10		10	_	10	_	10	pF

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

		C,	Тур	ical	
CHARACTERISTIC		рĒ	HC	HCT	Units
Propagation Delay-	t _{PLH}	15	14	13	
Clock to Q or Q, Fig. 3	t _{PHL}	15	14	13	ns
Propagation Delay	t _{PHL}	15	14	17	
\overline{MR} to Q or \overline{Q} , Fig. 4	t _{PLH}	15	14	''	ns
Power Dissipation Capacitance*	C _{PD}	_	65	67	pF

^{*}CPD is used to determine the dynamic power consumption, per flip-flop.

PD = $CPDVcc^2f_i + \Sigma CLVcc^2f_o$ where f_i = input frequency, f_o = output frequency,

CL = output load capacitance, VCC = supply voltage

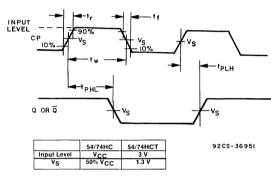


Fig. 3 - Propagation delay times and clock pulse width.

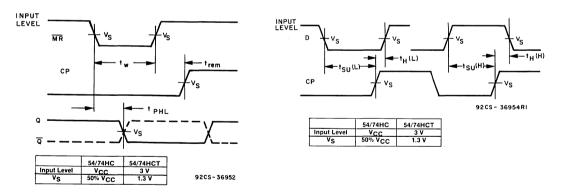


Fig. 4 - Pre-requisite and propagation delay times for master reset.

Fig. 5 - Pre-requisite for clock.

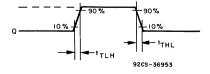
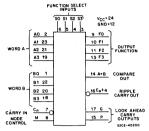


Fig. 6 - Transition times.

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM ACTIVE-HIGH DATA

4-Bit Arithmetic Logic Unit

Type Features:

- Full look-ahead carry for speed operations on long words
- Generates 16 logic functions of two Boolean variables
- Generates 16 arithmetic functions of two 4-bit binary words
- A = B comparator output available (open drain)
- Ripple-carry input and output available
- Available in both narrow- and wide-body plastic packages

The RCA CD54/74HC181 and CD54/74HCT181 are low-power four-bit parallel arithmetic logic units (ALU) capable of providing 16 binary arithmetic operations on two four-bit words and 16 logical functions of two Boolean variables. The mode control input M selects logical (M=High) or arithmetic (M=Low) operation. The four select inputs (S0, S1, S2, and S3) select the desired logical or arithmetic functions, which include AND, OR, NAND, NOR, and exclusive-OR and -NOR in the logic mode, and addition, subtraction, decrement, left-shift and straight transfer in the arithmetic mode, according to the truth table. The HC/HCT181 operation may be interpreted with either active-low or active-high data at the A and B word inputs and the function outputs, by using the appropriate truth table.

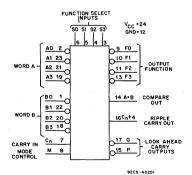
The HC/HCT181 contains logic for full look-ahead carry operation for fast-carry generation using the carry-generate and carry-propagate outputs G and P for the four bits of the HC/HCT181. Use of the HC/HCT182 look-ahead carry generator inconjunction with multiple HC/HCT181s permits high-speed arithmetic operations on long words. A ripplecarry output C_{n+4} is available for use in systems where speed is not of primary importance.

Also included in these devices is a comparator output A = B, which assumes a high level whenever the two four-bit input words A and B are equal and the device is in the subtract mode. A=B is an open-drain output that can be wire-AND connected to give a comparison for more than 4 bits. In addition, relative magnitude information may be derived from the carry-in input C_n and ripple carry-out output C_{n+4} by placing the unit in the subtract mode and externally decoding using the information in the Magnitude Comparison table.

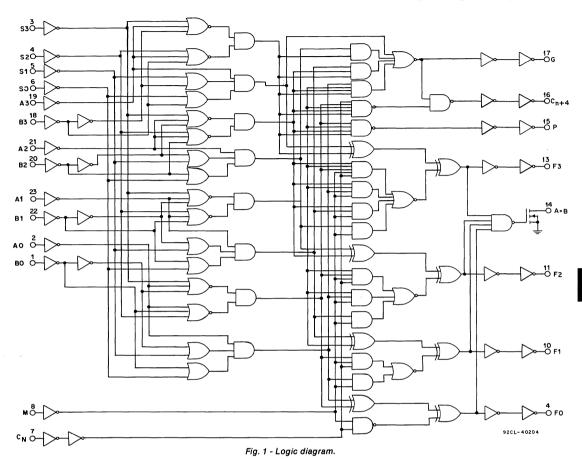
The CD54HC181 and CD54HCT181 are supplied in 24-lead dual-in-line frit-seal ceramic packages (F suffix). The CD74HC181 and CD74HCT181 are supplied in 24-lead dual-in-line, narrow-body plastic packages (EN suffix), in 24-lead dual-in-line, wide-body plastic packages (E suffix), and in 24-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation
 - High noise immunity:
 - N_{IL}=30%, N_{IH}=30% of V_{CC}; @ V_{CC}=5 V
- CD54HCT/CD74HCT types:
 - 4.5 to 5.5 V operation
 - Direct LSTTL input logic compatibility
 - V_{IL}=0.8 V max., V_{IH}=2 V min.
 - CMOS input compatibility
 - $I_{\rm I} \leq 1~\mu A @ V_{\rm OL},~V_{\rm OH}$



FUNCTIONAL DIAGRAM ACTIVE-LOW DATA



FUNCTION TABLES

					Inputs/Outputs Activ	ve High
F	unc	tio	n	Logic	Arithmetic	Function
	Sel	ect		Function	M :	= L
S3	3 S2 S1 S0		SO	M = H	C _n =H (no carry)	C _n =L (with carry)
L	L	L	L	Ā	Α	A plus 1
L	L	L	н	A + B	A + B	(A + B) plus 1
L	L	н	L	ĀB	A + B	(A + B) plus 1
L	L	н	н	Logic 0	minus 1(2's compl.)	Zero
L	н	L	ᅵᅵ	ĀB	A plus AB	A plus AB plus 1
L	н	L	н	B	(A + B) plus AB	(A+B)plusABplus1
L	н	н	ᆫ	А⊕В	A minus B minus 1	A minus B
L	н	н	н	ΑB	AB minus 1	ΑB
Н	L	L	L	Ā + B	A plus AB	A plus AB plus 1
Н	L	L	н	A ⊕ B	A plus B	A plus B plus 1
н	L	н	L	В	(A + B) plus AB	(A+B)plusABplus1
Н	L	н	н	AB	AB minus 1	AB
н	н	L	L	Logic 1	A plus A*	A plus A plus 1
Н	н	L	н	A + B	(A + B) plus A	(A+B) plus A plus 1
Н	Н	н	L	A + B	(A + B) plus A	(A+B) plus A plus 1
н	н	н	н	Α	A minus 1	A

					Inputs/Outputs Acti	ve Low							
F	unc	tio	n	Logic	Arithmetic	Function							
	Sel	ect		Function	M = L								
S 3	S2	S1	S0	M = H	C _n =L (no carry)	C _n =H (with carry)							
L	L	L	L	Ā	A minus 1	Α							
L	L	L	н	ĀB	AB minus 1	AB							
L	L	н	L	Ā + B	AB minus 1	ΑĒ							
L	L	Н	н	Logic 1	minus 1(2's compl.)	Zero							
L	н	L	ᆫ	A + B	A plus (A + B)	A plus (A+B) plus 1							
L	н	L	н	<u> </u>	AB plus (A + B)	ABplus(A+B)plus1							
L	н	н	ᆫ	А⊕В	A minus B minus 1	A minus B							
L	н	н	н	A + B	A + B	(A + B) plus 1							
Н	ᆫ	L	L	ĀB	A plus (A + B)	A plus (A+B) plus 1							
Н	L	L	н	А⊕В	A plus B	A plus B plus 1							
Н	L	Н	L	В	AB plus (A + B)	ABplus(A+B)plus1							
Н	L	н	н	A + B	A + B	(A + B) plus 1							
Н	н	L	L	Logic 0	A plus A*	A plus A plus 1							
Н	н	L	н	ΑB	AB plus A	AB plus A plus 1							
Н	н	н	L	AB	AB plus A	AB plus A plus 1							
Н	Н_	Н	Н	Α	· A	A plus 1							

H = High Level

L = Low Level

^{*} Each bit is shifted to the next more significant position.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc): (Voltages referenced to ground)-0.5 to +7 V DC V_{cc} OR GROUND CURRENT (I_{cc}) ±50 mA POWER DISSIPATION PER PACKAGE (Pn): OPERATING-TEMPERATURE RANGE (TA): PACKAGE TYPE E.M -40 to +85° C STORAGE TEMPERATURE (Tatg)-65 to +150°C LEAD TEMPERATURE (DURING SOLDERING): At distance 1/16 ± 1/32 in. (1.59 ± 0.79 mm) from case for 10 s max. +265°C Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacting lead tips only+300° C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIF	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	\
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°C.
CD54 Types	-55	+125	"
Input Rise and Fall Times, t,t;			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

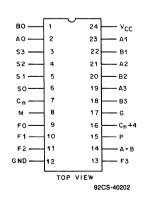
^{*}Unless otherwise specified, all voltages are referenced to Ground.

MAGNITUDE COMPARISON TABLE

A	ctive - H	ligh Data	Active - Low Data					
Input C _n	Output Cn+4	Magnitude	Input Cn	Output C _{n+4}	Magnitude			
1	1	A≤B	0	0	A≤B			
0	1	A < B	1	0	A < B			
1	0	A > B	0	1	A > B			
0	0	A≥B	1	1	A≥B			

1 = High Level

0 = Low Level



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC181/CD54HC181								CD74HCT181/CD54HCT181											
CHARACTERISTIC		TEST CONDITIONS		74HC/54HC TYPE8		74HC TYPES		54HC TYPES		TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES				
		V ₁ I ₀		Vcc	+25°C		-40/ +85°C		-55/ +125°C		V,	Vcc	+25°C		;	-40/ +85° C		-55/ +125°C		UNITS	
		V mA	mA	V	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	-	1.5	_	1.5	_		4.5						<u> </u>		
Input Voltage	VIH			4.5	3.15	_		3.15		3.15	_	_	to	2	l –	-	2	—	2	-	v
				6	4.2	_	_	4.2	ı	4.2	_		5.5	Ĺ	<u> </u>			ļ			
Low-Level				2		<u> </u>	0.5		0.5	_	0.5		4.5								
Input Voltage	VIL			4.5	<u> </u>	_	1.35	_	1.35	_	1.35	_	to	-	-	0.8	-	0.8	-	0.8	٧
				6		<u> </u>	1.8	<u> </u>	1.8	_	1.8		5.5		<u></u>			<u> </u>	_		
High-Level		VIL		2	1.9	_	<u> </u>	1.9	_	1.9	<u> </u>	VIL	İ					ł	1	1	
Output Voltage	V _{OH}	or	-0.02	4.5	4.4	_	_	4.4		4.4	_	or	4.5	4.4	–	-	4.4	-	4.4	-	V
CMOS Loads		ViH		6	5.9	_	_	5.9		5.9		V _{IH}						<u> </u>		L	
		VIL										VIL	·	Į	}	l		1	Į		
TTL Loads		or	-4	4.5	3.98	L		3.84	_	3.7	_	or	4.5	3.98	—	-	3.84	-	3.7	-	٧
		ViH	-5.2	6	5.48	_	<u> </u>	5.34		5.2	_	V _{IH}						Ь		L_	
Low-Level		VIL		2	<u> </u>	_	0.1	<u> </u>	0.1	_	0.1	VIL			ļ			ļ	ļ		
Output Voltage	Vol	or	0.02	4.5	<u> </u>	_	0.1	_	0.1		0.1	or	4.5	-] —	0.1	 	0.1	-	0.1	V
CMOS Loads		V _{IH}		6	<u> </u>	<u> </u>	0.1	_	0.1	_	0.1	V _{IH}		<u> </u>			<u> </u>	L	<u> </u>	<u> </u>	
		VIL				L_	<u> </u>	<u> </u>			_	VIL	ļ	1	ļ		1	[
TTL Loads		or	4	4.5	<u> = </u>	<u> </u> _	0.26		0.33	_	0.4	or	4.5	-		0.26	-	0.33	-	0.4	٧
		V _{IH}	5.2	6		느	0.26	<u> </u>	0.33		0.4	V _{IH}	_	L					_		
Input Leakage		Vcc					[-			Any		(į			
Current	l ₁	or		6	_	_	±0.1	_	±1	_	±1	Voltage	5.5	_	_	±0.1	_	±1	l _	±1	μA
		Gnd		1			[·	į				Between			١.			ŧ		-	
			L		<u> </u>	<u> </u>	_		<u> </u>			V _{cc} & Gnd	L	_			L-	L		<u> </u>	
Quiescent		Vcc										Vcc	l					ļ			
Device Current	lcc	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
		Gnd	L		<u> </u>	L	L	<u> </u>	L		L	Gnd	<u> </u>	<u> </u>		<u> </u>	L.	<u> </u>	<u> </u>	 	
Additional													4.5	ļ	ŀ						
Quiescent Device												V _{cc} -2.1	to	_	100	360	_	450	_	490	μΑ
Current per input													5.5]			,
pin: 1 unit load	Δlcc*												L		<u>L_</u>	<u> </u>	L	L	<u></u>	L	

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*						
S0-S3	1						
All A and B (Data)	0.75						
M, C _n	0.5						

^{*}Unit Load is ΔI_{cc} limit specified in Static Characteristics Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25°C, Input t,t;=6 ns)

011	AD A CTEDIOTIC	0 (=5)	TYPICAL	VALUES	LINUTO	
CHA	ARACTERISTIC	C _L (pF)	НС	нст	UNITS	
	Propagation Delay: tplh, tphl					
	An or Bn to Cn+4	15	19	22		
SUM Mode	A _n or B _n to G	15	18	23		
	A _n or B _n to P	15	14	17		
	A _n or B _n to F _n	15	19	24	1	
	A _n or B _n to C _{n+4}	15	20	23		
	A _n or B _n to G	15	18	23		
DIFFERENCE Mode	A _n or B _n to P	15	14	17	ns	
	A _n or B _n to F _n	15	20	24		
	A_n or B_n to $A = B$	15	21	25		
LOGIC Mode	A _n or B _n to F _n	15	19	23		
SUM and	C _n to C _{n+4}	15	13	18		
DIFFERENCE Mode	C _n to F _n	15	17	20		
Power Dissipation Ca	pacitance* C _{PD}	_	120	140	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 f_i + \Sigma C_L V_{CC}^2 f_o$ where f_i = input frequency

fo = output frequency

C_L = output load capacitance

V_{cc} = supply voltage.

AC Test Setup Reference (Active-Low Data)

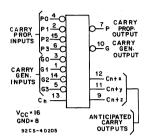
Test Delay Times	AC	Paths	DC Date	DC Data Inputs					
Test Delay Times	Inputs	Outputs	To Gnd	To VCC	Mode*				
SUM _{IN} to SUM _{OUT}	BO	Any F	B1, B2, B3, M, C _n	All Ā's	ADD				
SUM _{IN} to P	ĀŌ	P	A1, A2, A3, M, C _n	All B's	ADD				
SUM _{IN} to G	BÖ	G	All A's, M, C _n	B1, B2, B3	ADD				
SUMIN to Cn+4	BO	Cn+4	All A's, M, C _n	B1, B2, B3	ADD				
C _n to SUM _{OUT}	Cn	Any F	All A's, M	All B's	ADD				
C _n to C _{n+4}	Cn	Cn+4	All Ā's, M	All B's	ADD				
SUM _{IN} to A = B	BO	A = B	All A's, B1, B2, B3, M	Cn	SUBTRACT				
SUM _{IN} to SUM _{OUT} (Logic Mode)	All B's	Any F	All A's, Cn	М	EXCLUSIVE OR				

*ADD Mode: S0, S3 = V_{cc}; S1, S2 = Gnd. SUBTRACT Mode: S0, S3 = Gnd; S1, S2 = V_{cc}.

SWITCHING CHARACTERISTICS (CL = 50 pF, Input t, t, = 6 ns)

		1						LIM	ITS						j
CHADACTEDIC	TIC	V		25	°C		-4	0°C to	o +85°	,C	-5	5°C to	+125	°C]
CHARACTERIS	i i C	VCC	Н	С	Н	CT	741		74H			НС	54H		UNITS
		(V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Propagation Delay,	t _{PLH}	2	_	225	_	_	_	280	<u> </u>	_	_	345	_	_	1
SUM Mode	t _{PHL}	4.5	l —	45	 —	53	—	56	l —	66	_	69	_	80	ì
An or Bn to Cn+4		6		38_		_		48				59			ł
		2	—	210	<u> </u>	<u> </u>	_	265	_	_	_	315	_	_	1
A _n or B _n to G		4.5	_	42	 —	54	—	53	_	53	—	63	—	63	ł
		6		36			<u>L</u>	45		<u>L-</u>	<u>L</u>	54		_	l
		2	<u> </u>	170	_		_	215	_	_	-	255	_	_	
A _n or B _n to P		4.5	l –	34	—	41	—	43	—	51	—	51	—	62	1
		6		29	<u> </u>			37	_			43]
		2	_	230	T —	-	_	290	_	_	 	345	_	_	
A_n or B_n to F_n		4.5	-	46	—	58	_	58	—	58	l —	69	—	69	1
		6		39	<u> </u>	<u> </u>	<u></u>	49	<u> </u>		<u> </u>	59]
Propagation Delay,	tpHL	2		235	—	_	_	285	_	_	_	355	_	_	
DIFFERENCE Mode	t _{PLH}	4.5	-	47	-	55	-	59	l —	69	—	71	_	83	ł
An or Bn to Cn+4		6	-	40	l —	_	_	50	_	_		60	_		
		2	—	215	T —	_	I —	270	—	_	T -	325	_	_]
A _n or B _n to G		4.5	_	43		54		54	l —	54	-	65	l —	65	
		6	_	37		_		46	_	l — .	l	55	_	l —	
		2	_	170	T-	_	_	215	_	_	[—	255	—	_]
A _n or B _n to P		4.5	_	34		40	-	43	—	50	_	51	—	60	ns
		6	_	29	_	_	_	37	_	<u> </u>	_	43	-	_	
		2	T -	235	T -	_	Γ	295	_	Γ-	-	355	-	_]
A_n or B_n to F_n		4.5	_	47	_	57	_	59	l —	71	_	71	_	86	
		6	_	40	l —	<u> </u>	-	50		_	_	60	_	_	
		2	-	245	T —	_	T -	305	_	<u> </u>	T -	370	-	_	
A_n or B_n to $A=B$		4.5	-	49	l —	60	l —	61	_	75	_	74	_	90	
		6	l —	42	_		l —	52		l –	<u> </u>	63	<u> </u>	_	
Propagation Delay,	t _{PHL}	2	T —	230	T	_		290	_	T -	_	345	_	_	
LOGIC Mode	t _{PLH}	4.5	_	46		54	-	58	l —	68	_	69	_	81	
A _n or B _n to F _n		6		39		L		49_	l —_		<u> </u>	59	l –		
Propagation Delay,	t _{PHL}	2	_	165		_	—	205	_		_	250	T —	_	1
SUM & DIFF. Modes	t _{PLH}	4.5	_	33	_	42	—	41	_	53	_	50	l —	63	1
C _n to C _{n+4}		6	_	28		_		35	l —	_	_	43	_	 _	
		2	T —	200	T —	_	T -	250	_	_	T-	300	—	_	1
C _n to F _n		4.5	-	40	-	48		50	l —	56	_	60	—	68	
		6	<u> </u>	34	<u>L</u> _	<u>L</u> _	<u>L</u>	43	_		<u></u>	51	L-		
Output Transition	t _{THL}	2	I -	75		_	T —	95	_	_	_	110	T -	_]
Time	t _{TLH}	4.5	_	15		15	l —	19	_	19	_	22	-	22	
		6	_	13		_	l —	16	l —	<u> </u>	-	19		—	
Input Capacitance	Cı	T	1-	10		10	T -	10	T =	10	_	10		10	pF

High-Speed CMOS Logic



Look-Ahead Carry Generator

Type Features:

- Provides carry look-ahead across a group of four ALUs
- Multi-level look-ahead for high-speed arithmetic operation over long word length

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC182 and CD54/74HC1182 carry lookahead generators are high-speed silicon-gate CMOS devices and are pin compatible with low-power Schottky TTL (LSTTL).

The CD54/74HC/HCT182 accept up to four pairs of active LOW carry propagate $(\overline{P_0}, \overline{P_1}, \overline{P_2}, \overline{P_3})$ and carry generate $(\overline{G_0}, \overline{G_1}, \overline{G_2}, \overline{G_3})$ signals and an active HIGH carry input(C_n). The devices provide anticipated active HIGH carries $(C_{n+x}, C_{n+y}, C_{n+y})$ across four groups of binary adders. The HC/HCT182 also has active LOW carry propagate (\overline{P}) and carry generate (\overline{G}) outputs which may be used for further levels of look ahead.

The logic equations provided at the outputs are:

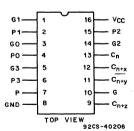
$$\begin{array}{l} C_{n+x} = P_0 C_n \\ C_{n+y} = G_1 + P_1 G_0 + P_1 P_0 C_n \\ \underline{C_{n+y}} = G_2 + P_2 G_1 + P_2 P_1 G_0 + P_2 P_1 P_0 C_n \\ \underline{G} = G_3 + P_3 G_2 + P_3 P_2 G_1 + P_3 P_2 P_1 G_0 \\ \overline{P} = \overline{P_3 P_2 P_1 P_0} \end{array}$$

The CD54/74HC/HCT182 can also be used with binary ALUs in an active LOW or active HIGH input operand mode. The connections to and from the ALU to the carry lookahead generator are identical in both cases.

The CD54HC182 and CD54HCT182 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC182 and CD74HCT182 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High noise immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL input logic compatibility V_{IL} = 0.8 V max., V_{IH} = 2 V Min. CMOS input compatibility I₁ ≤ 1 μA @ V_{OL} V_{OH}



TERMINAL ASSIGNMENT

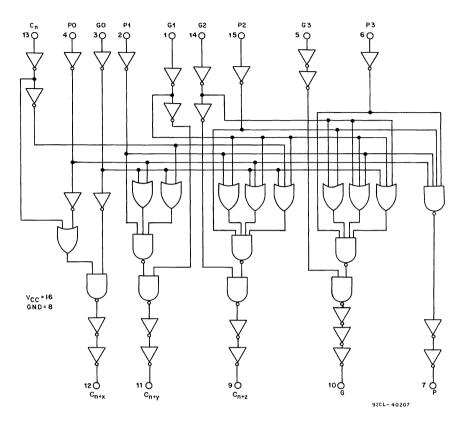


Fig. 1 - Logic diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground)
DC INPUT DIODE CURRENT, $I_{i\kappa}$ (FOR V_i < -0.5 V OR V_i > V_{cc} + 0.5 V)
DC OUTPUT DIODE CURRENT, Ι _{οκ} (FOR V _O < -0.5 V OR V _O > V _{CC} + 0.5 V)
DC DRAIN CURRENT, PER OUTPUT (I ₀) (FOR -0.5 V $<$ V $_{0}$ $<$ V $_{cc}$ + 0.5 V)
DC V _{cc} OR GROUND CURRENT (Icc)
POWER DISSIPATION PER PACKAGE (P₀):
For T _A = -40 to +60°C (PACKAGE TYPE E)
For T _A = +60 to +85°C (PACKAGE TYPE E)
For T _A = -55 to +100° C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For T _A = -40 to +70° C (PACKAGE TYPE M)
For T _A = +70 to +125°C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H55 to +125°C
PACKAGE TYPE E, M
STORAGE TEMPERATURE (Tatg)65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. +265°C +265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIF	AITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _t			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

FUNCTION TABLE

	INPUTS										UTPUT	8	
C _n	Go	Po	G ₁	P ₁	G ₂	P ₂	G₃	P ₃	C _{n+x}	C _{n+y}	C _{n+z}	G	P
X L X H	HLX	H X L	,						L H H				
XXLXXH	хннхгх	XHXXXL	HHHXX	HXXXLL		a.						·	
XXX	H X X	XXX	X H H	X H X	H H H H	H X X			:			1.24	
X X H	X X L X	X X L	X L X	X X L	L X X	X L L					H H H H		
	X X H		XXHH	X H X	XIII	X H X	HHHH	H X X				1111	·
	X X L		X X L X	X X X L	X L X	X X L	X X X	X L L				L L L	
		H X X L		X H X X L		X X H X L		X X H L					H H H L

H = HIGH voltage level

L = LOW voltage level

X = don't care

STATIC ELECTRICAL CHARACTERISTICS

				CD	74HC	182/C	D54H	C182					CD74	нст	182/C	:D54H	ICT1	32			
CHARACTERIS	TIC.		TEST	NS		IC/54 YPE		741 TYF		54I TYF		TEST CONDITION	NS		CT/54			ICT PES	54H TYF		UNITS
CHARACTERIS	iic	V,	l _o	Vcc		•25° C	;	-4 +85		-5 +12	5/ 5°C	V ₁	Vcc		+25° C	;	ı	0/ 5°C	_	5/ 5°C	UNITS
		v	mA	V	Min	Тур	Max	Min	Max	Min	Max	٧	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15	_	-	3.15	_	3.15	-	_	to	2	—	-	2	—	2	-	v
				6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level				2		_	0.5	_	0.5	П	0.5		4.5								
Input Voltage	VIL			4.5	_	-	1.35	_	1.35		1.35	_	to	—	-	0.8	—	8.0	—	0.8	V
				6		_	1.8		1.8	П	1.8		5.5			L					
High-Level		VIL		2	1.9	_		1.9	_	1.9	_	VIL									
Output Voltage	V_{OH}	or	-0.02	4.5	4.4	_		4.4		4.4	_	or	4.5	4.4	-	l —	4.4	-	4.4	-	٧
CMOS Loads		VIH		6	5.9	_	[-	5.9	_	5.9	_	ViH									
		VIL										VIL	l		l	l		1			
TTL Loads		or	-4	4.5	3.98		<u> </u>	3.84	_	3.7		or	4.5	3.98	–	-	3.84	—	3.7	-	V
		V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}						<u> </u>			
Low-Level		VIL		2	<u> </u>	<u>_</u>	0.1	_	0.1	_	0.1	VIL				l		ļ			
Output Voltage	Vol	or	0.02	4.5			0.1		0.1		0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads		VIH		6		_	0.1	_	0.1	_	0.1	V _{IH}						<u></u>			
		V1L		L_	<u> </u>			ļ			L_	VIL					l	ļ	ļ		
TTL Loads		or	4	4.5		<u> </u>	0.26	<u> </u>	0.33	_	0.4	or	4.5	-	-	0.26	_	0.33	[-	0.4	V
		V _{IH}	5.2	6	<u> </u>		0.26	느	0.33	_	0.4	V _{IH}		ļ		ļ			<u> </u>		
Input Leakage		Vcc		1	ļ							Any		ĺ		1			1		
Current	l,	or	ļ	6	_	_	±0.1	_	±1	_	±1	Voltage	5.5	_	l —	±0.1	_	±1	_	±1	μΑ
		Gnd			[-		1	ĺ		Between				1		ļ			
				 	<u> </u>	_	<u> </u>		ļ			Vcc & Gnd				-	_	<u> </u>			
Quiescent		Vcc	_									Vcc		1		١.				100	
Device Current	Icc	or	0	6	_	-	8	-	80	_	160	or	5.5	-	_	8	_	80	_	160	μΑ
Additional		Gnd	L	L	<u> </u>	L	L	L	L	L		Gnd	\vdash	-	-		-		-	-	
Quiescent Device													4.5								
Current per input												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	A 1 *												5.5					1			
pin: 1 unit load	Δlcc*	L											L	L	Щ_	L	L		Ь_	Ь	

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
P ₀ , P ₁ , P ₂ , G ₀ , G ₁	1.5
P ₃ , G ₂ , C _n	1.25
G₃	0.3

Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25°C.

SWITCHING CHARACTERISTICS (V_{CC} = 5·V, T_A = 25°C, Input·t_r, t_f = 6 ns)

			TYPICAL	. VALUES	
CHARACTERISTIC		C _L (pF)	нс	нст	UNITS
Propagation Delay Time:					
P _n to P	t _{РНL} , t _{РLН}	15	9	11	1
C _n to any output	t _{PHL} , t _{PLH}	15	12	17	ns
P _n to any output	t _{PHL} , t _{PLH}	15	12	13	
G _n to any output	t _{PHL} , t _{PLH}	15	11	13	
Power Dissipation Capacitance *	C _{PD}	_	66	72	pF

^{*} C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 f_o)$ where: f_i = input frequency

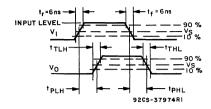
fo = output frequency

C_L = output load capacitance

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (CL = 50 pF, Input t, tf = 6 ns)

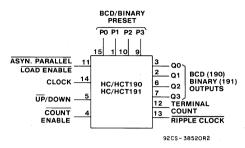
							LIM	IITS						
CHARACTERISTIC	TEST		25	°C		-4	0°C to	o +85°	,C	-55°C to +125°C				UNITS
CHARACTERISTIC	CONDITIONS	н	С	Н	нст		74HC		ICT	54HC		54HCT		UNITS
	V _{cc}	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay, tplh	2	_	120	_	_	_	150	_	_	_	180	_	_	
t _{PHL}	4.5	—	24	-	28	—	30	-	35	—	36	-	42	
P _n to P	6	_	20	_	_	_	26	_			31			
t _{PLH}	2	-	150	_	-	—	190	_	—		225	_	-	
t _{PHL}	4.5	—	30	-	40	—	38	—	50	-	45	-	60	
C _n to any output	6	_	26	_	—	_	33			_	38			
t _{PLH}	2	-	145	-	_	_	180	-	_	<u> </u>	220	_	_	
tphL	4.5	_	29	_	33	_	36	_	41	_	36	_	50	ns
P _n to any output	6	_	25	_	_	_	31		_	_	31	-	-	
t _{PLH}	2	_	135	_	_	_	170	_			205	_	_	
t _{PHL}	4.5	_	27	_	32	l —	34	-	40	_	41	_	48	
G _n to any output	6	_	23	_	l —	_	29	 _	\ _	_	35	_	-	
Transition t _{TLH}	2	—	75	_	T —	_	95	T -	Ī —	_	110		_	
Time t _{THL}	4.5	_	15	_	15	-	19	_	19	_	22	_	22	
	6	_	13	_	_	_	16	_	_	_	19	_	_	
Input C _I		-	10	-	10	_	10	-	10	-	10	_	10	pF



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, V _S	50% V _{cc}	1.3 V

Fig. 2 - Transition times and propagation delay times.

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM

Presettable Synchronous 4-Bit Up/Down Counters

CD54/74HC/HCT190 BCD Decade Counter CD54/74HC/HCT191 Binary Counter

Type Features:

- Synchronous counting and asynchronous loading
- Two outputs for n-bit cascading
- Look-ahead carry for high-speed counting

The RCA-CD54/74HC/HCT190/191 are asynchronously presettable BCD Decade and Binary Up/Down synchronous counters, respectively.

Presetting the counter to the number on preset data inputs (P0-P3) is accomplished by a Low asynchronous parallel load input (PL). Counting occurs when \overline{PL} is high, Count Enable (\overline{CE}) is low, and the Up/Down (\overline{U} /D) input is either low for up-counting or high for down-counting. The counter is incremented or decremented synchronously with the low-to-high transition of the clock.

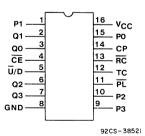
When an overflow or underflow of the counter occurs the Terminal Count output (TC), which is low during counting, goes high and remains high for one clock cycle. This output can be used for look-ahead carry in high-speed cascading (see Fig. 6). The TC output also initiates the Ripple Clock. (\overline{RC}) output which, normally high, goes low and remains low for the low-level portion of the clock pulse. These counters can be cascaded using the Ripple Clock output as shown in Fig. 7.

If a decade counter is preset to an illegal state or assumes an illegal state when power is applied, it will return to the normal sequence in one or two counts as shown in state diagrams.

The CD54HC/HCT190 and the CD54HC/HCT191 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT190 and the CD74HC/HCT191 are supplied in a 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). The CD54/74HC/HCT190 and the CD54/74HC/HCT191 are also supplied in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ V_{OL}, V_{OH}



HC/HCT190, HC/HCT191 TERMINAL ASSIGNMENT

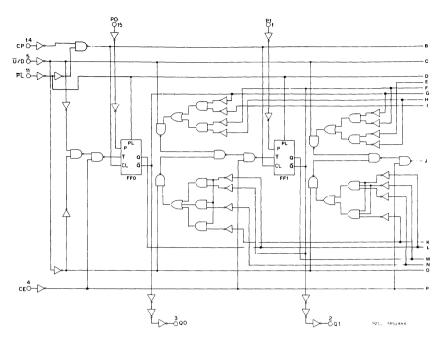


Fig. 1 - Logic diagram for HC/HCT190 (continued on next page).

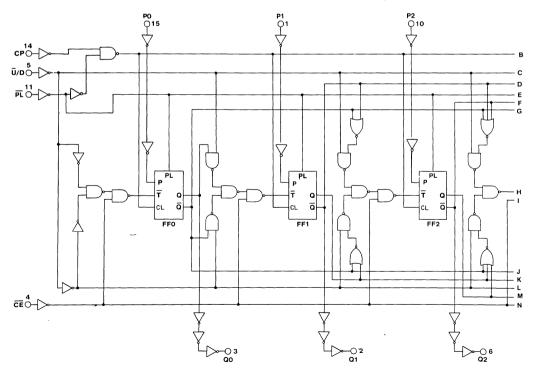


Fig. 2 - Logic diagram for HC/HCT191 (continued on next page).

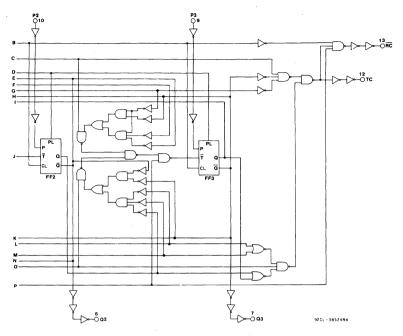


Fig. 1 - Logic diagram for HC/HCT190 (continued from previous page).

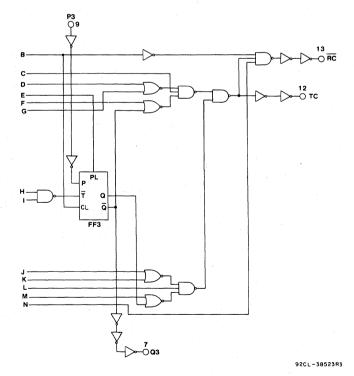


Fig. 2 - Logic diagram for HC/HCT191 (continued from previous page).

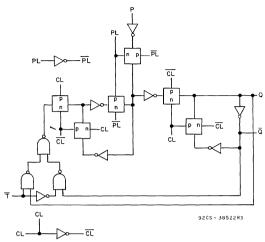


Fig. 3 - Flip-flop cell for HC/HCT190 and HC/HCT191.

TRUTH TABLE

	Inp	uts		Function
PL	CE	Ū/D	CP	1 diletion
Н	L	L		Count Up
Н	L	Н	5	Count Down
L	Х	Х	Х	Asyn. Preset
Н	Н	X	X	No Change

Note:

X = Don't care.

MAXIMUM RATINGS, Absolute-Maximum Values: DC SUPPLY-VOLTAGE. (Voc):

DC SOFFET-VOLTAGE, (VCC).	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} +0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT, (I _{CC})	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	•
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (T _{stg})	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79 \text{ mm})$ from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C
· · · · · · · · · · · · · · · · · · ·	

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERICTIC	LIF	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			ş
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	· ·
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times, t _r ,t _f :			
at 2 V	0	1000	1
at 4.5 V	0	500	ns
at 6 V	0	400	j

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

)		CD74	HCT	190/C	D54H	ICT1	90 91											
			TEST IDITIO	NS		IC/54 TYPE		741 TY		54ł		TEST CONDITIONS		74HCT/54HCT TYPE			74HCT TYPE		54H TY	ICT PE	
CHARACTERIST	ics	V,	I _o	Vcc		25° C	;	-4 +85		-5: +12:		V,	V _{cc}		•25° C	;		0/ 5°C	1 -	5/ 5°C	UNITS
	_	v	mA	v	Min	Тур	Max	Min	Max .	Min	Max	Ň	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_		1.5	_	1.5	_		4.5								
Input Voltage	V_{IH}			4.5	3.15		_	3.15		3.15	_	_	to	2	-	_	2	-	2	-	v
·				6	4.2		_	4.2	_	4.2	_		5.5	<u> </u>				<u> </u>			
Low-Level				2	_	<u> </u>	0.5	_	0.5		0.5		4.5								
Input Voltage	V_{IL}			4.5	_		1.35		1.35		1.35	_	to	-		0.8	-	0.8	_	0.8	V
		ļ		6	_		1.8	_	1.8		1.8		5.5					L.			
High-Level		VIL		2	1.9		_	1.9	_	1.9	_	VIL									
Output Voltage	VoH	or	-0.02	4.5	4.4		<u>_</u>	4.4		4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	V
CMOS Loads		VIH		6	5.9		_	5.9	_	5.9	_	V _{tH}									
		VIL										VIL									
TTL Loads		or	-4	4.5	3.9 8		_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	V
		ViH	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH					l				
Low-Level		VIL		2	_		0.1	_	0.1	_	0.1	VıL									
Output Voltage	VoL	or	0.02	4.5	_		0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads		VIH		6	_		0.1	_	0.1	_	0.1	ViH									
		VIL										VıL									
TTL Loads		or	4	4.5	_		0.26	_	0.33	-	0.4	or	4.5	-	_	0.26	-	0.33	_	0.4	v
		VIH	5.2	6	_	_:	0.26	_	0.33	-	0.4	ViH			ŀ			1			
Input Leakage Current	l _t	V _{cc} or Gnd		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1	_	±1	μΑ
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6	_	_	8	_	80	1	160	V _{cc} or Gnd	5.5	_	_	8	_	80	_	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	Δl _{cc} •											V _{CC} -2.1	4.5 to 5.5	_	100	360		450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
P0-P3	0.4
CP PL	1.5
PL	1.5
Ū/D CE	1.2
CE	1.5

^{*}Unit load is Δ I_{cc} limit specified in Static Characteristics Chart, e.g., 360 μ A max. @ 25° C.

PREREQUISITE FOR SWITCHING FUNCTION

				25	°C		-4	0°C to	o +85°	,C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	н	С	н	СТ	741	нс	74F	ICT	54	нс	54F	ICT.	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Setup Time		2	60	-	_	_	75	_	-	-	90	-	—	-	
Pn to PL		4.5	12	-	12		15	-	15	-	18	-	18	-	
·		6	10	<u> </u>			13	_	_		15	<u> </u>	<u> </u>	<u> </u>	
		2	60	-	-		75	-	-	-	90	-	-	-	
CE to CP	tsu	4.5	12	-	12		15	-	15	-	18	-	18	-	
		6	10				13	_			15		<u></u>	<u></u>	
		2	90	-	-	-	115	-	-	-	135	-	_	_	
U/D to CP		4.5	18	-	18	-	23	-	23	-	27	-	27	-	
		6	15			_	20	_			23				l
Hold Time		2	2	—	-	-	2	-	-	-	2	_	-	-	}
Pn to PL		4.5	2	-	2	-	2	-	- 2	-	2	-	2	-	
		6	2	<u> </u>	<u> </u>		2				2	<u> </u>	<u> </u>	L=_	ns
		2	2	-	-	-	2		-	-	2	—	-	-	113
CE to CP	tн	4.5	2	-	2		2	-	2	-	2	—	2	-	j
		6	2	<u>L-</u> _	L	<u>L-</u>	2	<u> </u>	<u>L-</u>	<u>L</u>	2	<u> </u>	<u> </u>		
		2	0	l —	-	—	0	-	-	-	0	-	-	 -	
U/D to CP		4.5	0	—	0		0	-	0	-	0	_	0	 	1
		6	0		_		0	<u> </u>	<u> </u>	<u> </u>	0				<u> </u>
		2	6	l —	-	-	5	_	_	-	4	-	-	-	l
Maximum Frequency*	f _{MAX}	4.5	30	_	30	_	25	-	25	-	20	-	20	-	MHz
		6	35		L		29		_	_	23				
		2	60		-	-	75	_	_	_	90	-	l –	l –	
Recovery Time	tREC	4.5	12	l —	12	-	15	-	15	-	18	—	18	-	j
		6	10			<u> </u>	13	_		_	15	_	L-]
		2	80	_	-	-	100	_	_	_	120	_	_	_	1
CP Pulse Width	tw	4.5	16	_	16	_	20	_	20	-	24	_	24	-	ns
		6	14			_	17	l –		l –	20	<u> </u>		<u> </u>]
		2	100	-	_	_	125	_	_	_	150	—	_	I]
PL Pulse Width	tw	4.5	20		20	-	25	_	25	-	30	_	30	_	1
		6	17				21			_	26	_			

^{*}Applies to non-cascaded operation only. With cascaded counters clock-to-terminal count propagation delays, count enable (\overline{CE}) -to-clock set-up times, and count enable (\overline{CE}) -to-clock hold times determine max. clock frequency. For example, with these HC devices:

$$f_{\text{max}} \text{ (CP)} = \frac{1}{\text{CP-to-TC prop. delay} + \overline{\text{CE}}\text{-to-CP setup} + \overline{\text{CE}}\text{-to-CP Hold}} = \frac{1}{42 + 12 + 2} \approx 18 \text{ MHz}$$

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

			TYPICAI	L VALUE	s	
CHARACTERISTIC	SYMBOL	F	IC	Н	UNITS	
		190	191	190	191	
Propagation Delay (C _L = 15 pF)						
PL to Qn		16	16	17	17	
Pn to Qn]	14	14	16	16	
CP to Qn]	14	14	14	14	
CP to RC	t _{PLH}	10	10	11	11	ns
CP to TC	t _{PHL}	18	18	18	18]
U/D to RC	7	12	12	12	12]
U/D to TC	7	13	13	16	16]
CE to RC		10	10	11	11	L
Power Dissipation Capacitance	C _{PD} *	59	55	78	68	pF

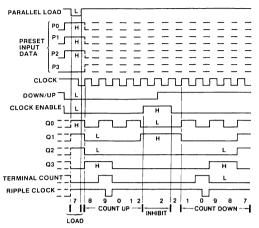
^{*}C_{PD} is used to determine the power consumption, per package.

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

				25	°C		-4	10°C t	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	IC	Н	СТ	74	нс	741	HCT	54	НС	541	НСТ	UNITS
			Min.	Мах.	Min.	Max.	Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Мах.	
Propagation Delay	t _{PLH}	2		195	_	_		245	_	-	_	295	_	-	
PL to Qn	t _{PHL}	4.5	-	39	-	40	_	49	-	50	-	59	-	60	
		6		33			_	42	_			50		_	
	t _{PLH}	2	-	175	_	_	_	220	_	_	-	265	_	-	
Pn to Qn	t _{PHL}	4.5	—	35	_	38	_	44	_	48	-	53	-	57	
		6		30	_	_	_	37	_			45	_	_	
	t _{PLH}	2	—	170	_	_	-	215	_		- 1	255		-	
CP to Qn	t _{PHL}	4.5	_	34	_	35	_	43	_	44	-	51	-	53	
		6		29				37				43			
	t _{PLH}	2	-	125	_	- 1	_	155	_	-	-	190	-	-	
CP to RC	t _{PHL}	4.5	—	25	_	27	-	31	_	34	-	38		41	
		6		21				26		_	_	32			
	t _{PLH}	2		210	_	_	-	265	_	-	-	315	-	-	
CP to TC	t _{PHL}	4.5	_	42	_	42	_	53	_	53	-	63	-	63	ns
		6		36				45	_			54			
	t _{PLH}	2	_	150	_	_	_	190	_	_	_	225	_	_	
U/D to RC	t _{PHL}	4.5	-	30	_	30	_	38		38	-	45	- 1	45	
		6		26		_	_	33			_	38			
	t _{PLH}	2	—	165	_	-	_	205	_	-	_	250	_	-	
U/D to TC	t _{PHL}	4.5	—	33		38	_	41	_	48	_	50	-	57	
		6		28		_		35	_			43			
	t _{PLH}	2	—	125	_	-	_	155	_	_	_	190	_	-	
CE to RC	t _{PHL}	4.5	-	25	_	27	_	31	_	34	_	38	-	41	
		6	<u> </u>	21		_		26	_	_	_	32			
Output Transition	t _{TLH}	2	_	75	_	_	_	95	_	-	_	110	- 1	-]	
Time	t _{THL}	4.5	-	15	_	15	_	19	_	19	_	22	_	22	
Qn, TC, RC		6		13				16	_		_	19			
Input Capacitance	Cı	_	_	10	_	10	_	10	_	10	_	10	_	10	pF

 $PD = C_{PD} \ V_{cc}^2 \ fi + \Sigma \ (C_L \ V_{cc}^2 \ fo) \ where: \ f_i = input \ frequency \quad f_o = output \ frequency \quad C_L = output \ load \ capacitance \quad V_{cc} = supply \ voltage$

TIMING DIAGRAMS



- (1) Load (preset) to BCD seven ı (3) Inhibit
- (2) Count up to eight, nine, zero, one and two ! (4) Count down to one, zero, nine, eight, and seven
- PRESET CLOCK DOWN/UP **ENABLE** Ω2 TERMINAL COUNT П RIPPLE CLOCK 14 15 COUNT UP INHIBIT I LOAD (3) Inhibit
- Sequence:
- (1) Load (preset) to binary thirteen
- (2) Count up to fourteen, fifteen, zero, one, and two

inhibit sequences.

(4) Count down to one, zero, fifteen. fourteen, and thirteen.

Fig. 4 - HC/HCT190 decade counters typical load, count, and inhibit sequences.

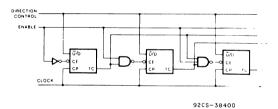


Fig. 6 - Sychronous n-stage counter with parallel gated Terminal Count.

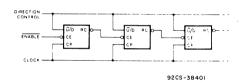
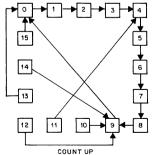
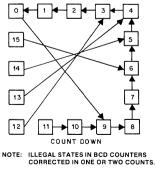


Fig. 5 - HC/HCT191 binary counters typical load, count, and

Fig. 7 - Synchronous n-stage counter using ripple clock.

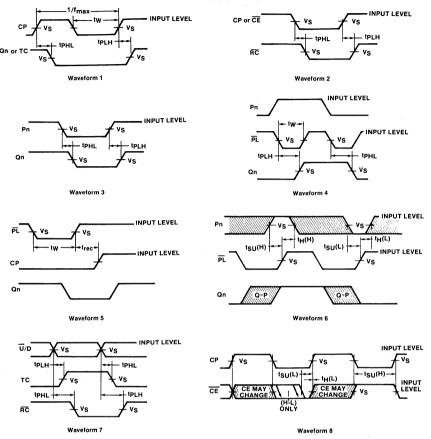


NOTE: ILLEGAL STATES IN BCD COUNTERS CORRECTED IN ONE COUNT.



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Fig. 8 - HC/HCT190 State Diagrams.



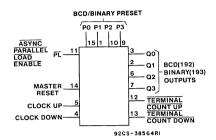
The shaded areas indicate when the input is permitted to change for predictable output performance

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	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, VS	50% VCC	1.3 V

Fig. 9 - Transition, propagation delay, setup and hold, and recovery times.

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM

Presettable Synchronous 4-Bit Up/Down Counters

CD54/74HC/HCT192 BCD Decade Counter, Asynchronous Reset CD54/74HC/HCT193 4-Bit Binary Counter, Asynchronous Reset

Type Features:

- Synchronous counting and asynchronous loading
- Two outputs for n-bit cascading
- Look-ahead carry for high-speed counting

The RCA-CD54/74HC/HCT192/193 are asynchronously presettable BCD Decade and Binary Up/Down synchronous counters, respectively.

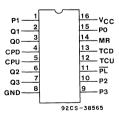
Presetting the counter to the number on preset data inputs (P0-P3) is accomplished by a LOW asynchronous parallel load input (PL). The counter is incremented on the low-tohigh transition of the Clock-Up input (and a high level on the Clock-Down input) and decremented on the low-tohigh transition of the Clock-Down input (and a high level on the Clock-Up input). A high level on the MR input overrides any other input to clear the counter to its zero state. The Terminal Count Up (carry) goes low half a clock period before the zero count is reached and returns to a high level at the zero count. The Terminal Count Down (borrow) in the count down mode likewise goes low half a clock period before the maximum count (9 in the 192 and 15 in the 193) and returns to high at the maximum count. Cascading is effected by connecting the carry and borrow outputs of a less significant counter to the Clock-Up and Clock-Down inputs, respectively, of the next most significant counter.

If a decade counter is preset to an illegal state or assumes an illegal state when power is applied, it will return to the normal sequence in one count as shown in state diagram.

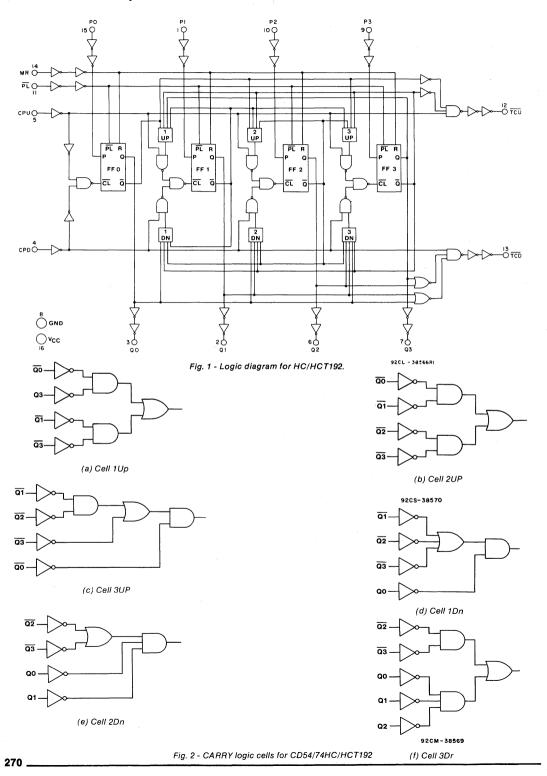
The CD54HC/HCT192 and the CD54HC/HCT193 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT192 and CD74HC/HCT193 are supplied in 16-lead plastic dual-in-line packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). The CD54/74HC/HCT192 and the CD54/74HC/HCT193 are also supplied in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT



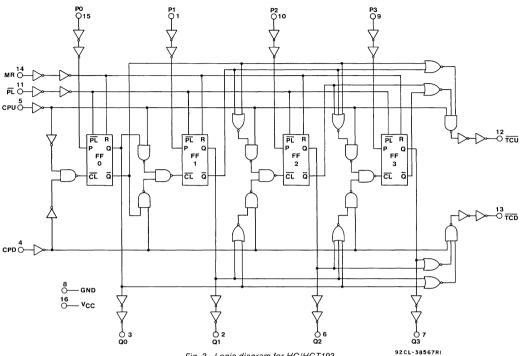


Fig. 3 - Logic diagram for HC/HCT193.

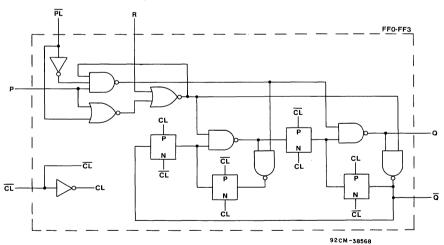


Fig. 4 - Logic diagram of flip-flops for HC/HCT192/193.

TRUTH TABLE

Clock Up	Clock Down	Reset	Parallel Load	Function
\mathcal{I}	Н	L	Н	Count Up
Н	5	L	н	Count Down
Χ	×	Н	x	Reset
Х	X	L	L	Load Preset
	ļ			Inputs

√ = low-to-high transition x = don't care

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT, (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E. M	40 to +85° C
STORAGE TEMPERATURE (Tatg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	MITS	UNITS
CHARACTERISTIC	·MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} .*			
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	'
DC Input or Output Voltage, V _I , V _O	0	V _{cc}	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	·c
CD54 Types	-55	+125	
Input Rise and Fall Times, tr, tr:			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CI	074H	C192/	193C	D54H	C192	/193			CD	74HC1	Г192/1	93/C	D54H	CT19	2/193			
CHARACTERISTI		1	TEST IDITION	15		74HC/54HC TYPE			74HC TYPE		IC PE	TEST CONDITIONS		74HCT/54HCT TYPE			74HCT TYPE		54HCT TYPE		UNITS
CHAHACTERISTI	CS	V,	lo	V _{cc}	+	25°C		-41 +85		-5: +12!		V ₁	V _{cc}	,	∙25° C	;		0/ 5°C	, .	5/ 5° C	UNITS
		٧	mA	٧	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15		_	3.15		3.15	_	_	to	2	_	_	2	-	2	_	v
				6	4.2	_		4.2		4.2	_		5.5	<u> </u>				<u> </u>			
Low-Level				2	_	_	0.5		0.5		0.5		4.5					1			
Input Voltage	VIL		1	4.5		_	1.35	_	1.35	-	1.35	_	to	_	-	0.8	-	0.8	_	0.8	v
				6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	-	V _{IL}									
Output Voltage	Voh	or	-0.02	4.5	4.4	_	_	4.4	<u> </u>	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads		ViH		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
		VIL										VIL									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v
		VIH	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}		j							
Low-Level		VıL		2	_	_	0.1	_	0.1	_	0.1	VIL									
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads		ViH	1	6	_	_	0.1	_	0.1	_	0.1	V _{IH}		ļ						ļ	
		VIL										VıL									
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	Ì_	_	0.26	_	0.33	_	0.4	v
		VIH	5.2	6	_	_	0.26	_	0.33	_	0.4	ViH								1	
Input Leakage Current	lı	V _{cc} or Gnd		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	-	_	±0.1	_	±1	-	±1	μΑ
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6	_	_	8	_	80	_	160	V _{cc} or Gnd	5.5	_	_	8		80	_	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	ΔΙςς.											V _{cc} -2.1	4.5 to 5.5	-	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_{I} = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
P0-P3	0.4
MR	1.45
PL.	0.85
CPU, CPD	1.45

^{*}Unit load is Δ I_{cc} limit specified in Static Characteristics Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25°C, Input t_r,t_r=6 ns)

		TYP	ICAL	
CUADACTERISTIC	SYMBOL	VAL	UES	UNITS
CHARACTERISTIC	STMBOL	HC	нст	UNITS
Propagation Delay (C _L = 15 pF)				
CPU to TCU and CPD to TCD	t _{PLH}	10	11	
CPU; CPD to Qn	t _{PHL}	18	17	ns
PL to Qn		18	21	
MR to Qn	tpHL	17	18	
Power Dissipation Capacitance	C _{PD} *	40	50	pF

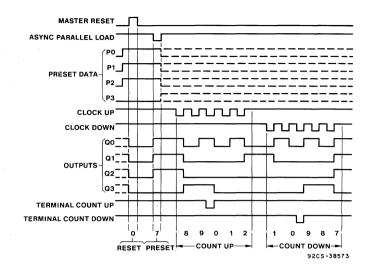
^{*} C_{PD} is used to determine the dynamic power consumption, per package. PD= C_{PD} V_{Cc}^2 fi + Σ (C_L V_{Cc}^2 fo) where: fi=input frequency fi=output frequency C_L =output load capacitance V_{Cc} =supply voltage

Pre-requisite for Switching Function

				25	°C		-4	l0°C te	o +85°	С	-5				
CHARACTERISTIC	SYMBOL	VCC	Н	C	Н	СТ	74	нс	74F	ICT	54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Pulse Width:		2	115	—	_	_	145	_	_	_	175	_	l –	_	
CPU, CPD	t _w	4.5	23		23	_	29	_	29	_	35	l —	35	-	
192		6	20	<u> </u>	_		25	_	_	_	30	_	_	<u> </u>	
CPU, CPD		2	100			_	125			_	150	_	_	_	
		4.5	20	-	23	l —	25	—	29		30	_	35	_	
193		6	17			_	21	_	_	_	26				
		2	80	_	_	_	100	_		_	120	_		-	
PL	tw	4.5	16	—	16	-	20	—	20	_	24	-	24	_	
		6	14			_	17	_	_	_	20	_	_	_	
		2	100		_	_	125	—	-		150		_	—	
MR	$t_{\mathbf{W}}$	4.5	20	_	20	-	25	_	25	—	30		30	—	
		6	17				21				26		_	_	
Setup Time		2	80				100		_	_	120	_	_	_	
Pn to PL	t _{s∪}	4.5	16	_	15	_	20	l —	19	_	24	_	22	—	ns
'		6	14	_	_		17	_	<u> </u>	_	20	_	_		
Hold Time		2	0		-		0	_	-	_	0	—	-	<u> </u>	
Pn to PL	t _H	4.5	0		0	-	0	_	0	_	0		0	—	
		6	0	<u> </u>			0		_	_	0	_			
Hold Time		2	80	-		 	100	_	_	_	120		_	—	
CPD to CPU	t _H	4.5	16	-	16	_	20	—	20	-	24	_	24	_	
or CPU to CPD		6	14		_	_	17				20	_		_	
Recovery Time		2	80	_		-	100	-	—	l —	120	-	_	—	
PL to CPU, CPD	t _{rec}	4.5	16		15		20	_	19	-	24	—	22	<u> </u>	
		6	14	<u> </u>			17				20				
		2	5	<u> </u>	_	—	5	—			5	_		—	
MR to CPU, CPD	t _{rec}	4.5	5	-	5	l —	5	-	5	_	5	-	5	<u> </u>	
		6	5		_	_	5				5				
Maximum Frequency		2	5	<u> </u>		_	4	-	_		3	_	-		
CPU, CPD	f _{MAX}	4.5	22	-	22	_	18		18		15	_	15	_	MHz
192		6	24	<u> </u>	_		21				18				ļ
CPU, CPD		2	5	-	-	-	4	-	-		3	-	-	-	
		4.5	25	-	22	_	20		18	_	17	_	15	_	
193		6	29		_	_	24	_	_	_	20	_	-		

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,t=6 ns)

				25	°C		-4	0°C to	o +85°	,C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	VCC	Н	С	H	CT	74	нс	74H	ICT	54	нс	54 F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	125	_	_	_	155	_	-	_	190	_	_	
CPU to TCU	t _{PHL}	4.5	 -	25	<u> </u>	27	<u> </u>	31	-	34	—	38	—	41	
		6	_	21				26	_			32			
		2	_	125	_	_	_	155	_	_	-	190	_	_	l
CPD to TCD		4.5	_	25	-	27	—	31	-	34	-	38	-	41	l
		6		21	<u> </u>			26		_	_	32			1
		2	_	220	-	—	—	270	—		—	325	—	<u> </u>	
CPU to Qn		4.5	-	43	-	40	-	54	 	50	—	65	—	60	
		6		37				46			_	55		_	
		2	-	220	-	-	-	270	—	_	—	325	-	-	l
CPD to Qn		4.5	—	43	-	40	-	54	—	50	-	65	—	60	
		6	_	37	_	_		46		<u>-</u>		55	_		1
		2	-	220	-	-	-	275	-	-	-	330	-		l
PL to Qn		4.5	-	44	 -	47	—	55	—	59	-	66	—	71	ns
		6	_	37	_		_	47	_	_		56	_	_	
		2	—	200	-	-	-	250	-	-	-	300	-	—	1
MR to Qn		4.5	-	40	-	43	—	50		54	-	60	-	65	
		6		34				43	_		_	51		_	1
Transition Time:	t _{THL}	2	—	75	-	-	—	95	_	-	-	110	—	-	1
Q, TCU, TCD	t _{TLH}	4.5	-	15	-	15	_	19		19	-	22	_	22	
		6		13		_		16		<u> </u>	<u></u>	19		_	
Input Capacitance	Cı		<u> </u>	10		10	<u>L</u>	10	_	10		10		10	pF.



(1) Reset outputs to zero.

(2) Load (preset) to BCD seven.

(3) Count up to eight, nine, terminal count up, zero, one and two.

(4) Count down to one, zero, terminal count down, nine, eight and seven.

(a) HC192 synchronous decade counters. Typical reset, preset and count sequences.



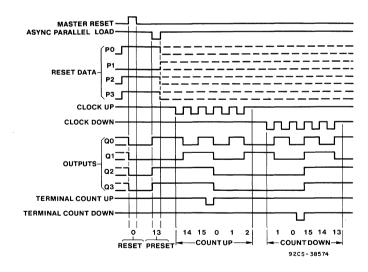
(1) Reset outputs to zero.
(2) Load (preset) to binary thirteen.

(3) Count up to fourteen, fifteen, terminal count up, zero, one and

(4) Count down to one, zero, terminal count down, fifteen, fourteen and thirteen.

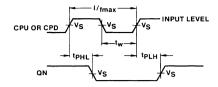
Note 1: Master reset overrides load data and clock inputs

Note 2: When counting up, clock-down input must be high; when counting down, clock-up input must be high.

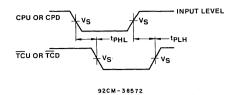


(b) HC193 synchronous binary counters. Typical reset, preset and count sequences.

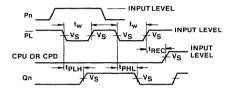
Fig. 6 - Timing diagrams for the CD54/74HC/HCT192(a) and 193(b).



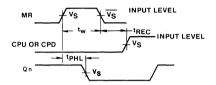
(a) Clock to output delays and clock pulse width.



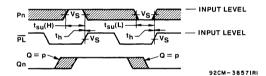
(b) Clock to terminal count delays.



(c) Parallel load pulse width, parallel load to output delays, and parallel load to clock recovery time.



(d) Master reset pulse width, master reset to output delay and master reset to clock recovery time.

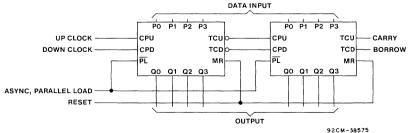


(e) Setup and hold times data to parallel load (PL).

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, VS	50% VCC	1.3 V

Fig. 5 - AC waveforms.

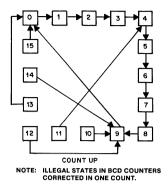
APPLICATION

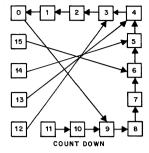


CASCADED UP/DOWN COUNTER WITH PARALLEL LOAD

Technical Data _____

CD54/74HC192, CD54/74HCT192 CD54/74HC193, CD54/74HCT193



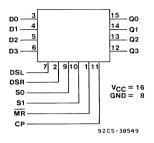


NOTE: ILLEGAL STATES IN BCD COUNTERS CORRECTED IN ONE OR TWO COUNTS.

92CM-40338

Fig. 6 - HC/HCT192 State Diagrams.

High-Speed CMOS Logic



4-Bit Bidirectional Universal Shift Register

Type Features:

- Four Operating Modes: Shift Right, Shift Left, Hold and Reset
- Synchronous parallel or serial operation
- Typical $f_{MAX} = 60 \text{ MHz}$ @ $V_{CC} = 5 \text{ V}$, $C_L = 15 \text{ pF}$, $T_A = 25^{\circ} \text{ C}$
- Asynchronous Master Reset

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC194 and CD54/74HCT194 are 4-bit shift registers with Asynchronous Master Reset (MR). In the parallel mode (S0 and S1 are high), data is loaded into the associated flip-flop and appears at the output after the positive transition of the clock input (CP). During parallel loading serial data flow is inhibited. Shift left and shift right are accomplished synchronously on the positive clock edge with serial data entered at the shift left (DSL) serial input for the shift left mode, and at the shift right (DSR) serial input for the shift left mode. Clearing the register is accomplished by a Low applied to the Master Reset (MR) pin.

The CD54HC/HCT194 devices are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/HCT194 devices are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

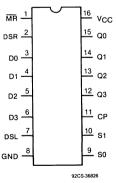
- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
 Significant Power Poduction Compared to LSTIL
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation

High Noise Immunity:

 $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5 \text{ V}$

■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility

 $I_{\rm I} \leq 1~\mu{\rm A}~@~V_{
m OL},~V_{
m OH}$



TERMINAL ASSIGNMENT

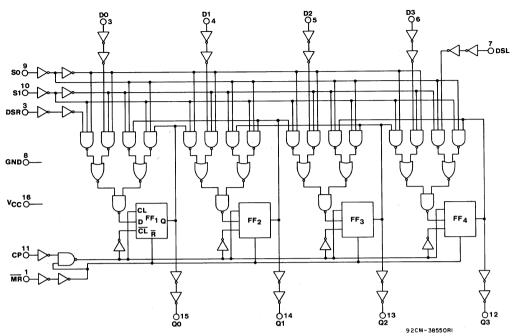


Fig. 1 - Logic diagram for the CD54/74HC194 and CD54/74HCT194.

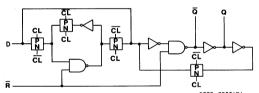


Fig. 2 - Detail of single Flip-Flop for the CD54/74HC194 and CD54/74HCT194.

TRUTH TABLE

Operating				Input	Outputs						
Mode	СР	MR	S ₁	So	DSR	DSL	Dn	Q0	Q1	Q2	Q3
Reset (clear)	Х	L	Х	Х	Х	Х	Х	L	L	L	L
Hold (do nothing)	Х	Н	I(b)	I(b)	Х	Х	Х	q0	q1	q2	q3
Shift Left		Н	h	I(b)	Х	T	Х	q1	q2	q3	L
		н	h	l(b)	x	h	Х	q1	q2	q3	Н
Shift Right	7	Н	l(b)	h	1	Х	Х	L	q0	q1	q2
		Н	l(b)	h	- h	Χ	Х	Н	q0	q1	q2
Parallel Load		Ξ	h	h	Х	Х	dn	d0	d ₁	d ₂	dз

H = HIGH voltage level.

h = HIGH voltage level one setup time prior to the LOW-to-HIGH clock transition.

L = LOW voltage level.

I = LOW voltage level one setup time prior to the LOW-to-HIGH clock transition.

 d_{n} (q_{n}) = Lower case letters indicate the state of the referenced input (or output) one setup time prior to the LOW-to-HIGH clock transition.

X = Don't care.

____ = LOW-to-HIGH clock transition.

NOTE: b. The HIGH-to-LOW transition of the $\rm S_0$, and $\rm S_1$ inputs on the 54/74194 should only take place while CP is HIGH for conventional operation.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, lik (FOR VI < -0.5 V OR VI > Vcc +0.5V)	<u>±</u> 20 mA
DC OUTPUT DIODE CURRENT, lok (FOR Vo < -0.5 OR Vo > Vcc +0.5 V)	<u>±</u> 20 mA
DC DRAIN CURRENT, PER OUTPUT (I ₀) (FOR -0.5 V < V ₀ < V _{0c} +0.5 V)	<u>±</u> 25 mA
DC Vcc OR GROUND CURRENT (Icc):	± 50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	
For T _A = +60 to +85° C (PACKAGE TYPE E)	
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M) Derate Lii	nearly at 6 mW/°C to 70 mW
OPERATING -TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tsig)	65 +150°C
LEAD TEMPERATUARE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LI	MITS	UNITS
	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	
DC Input or Output Voltage V ₁ V ₀	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times to to			
at 2 V	0	1000	1
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

•			С	D74H	C/54I	HC194	•					CD	4HC	T/54H	ICT19	94				
	coi	TEST NDITIONS	3		1C/54			HC PES		HC PES	TEST			CT/54		ŀ	ICT PES		HCT PES	
CHARACTERISTIC	V,	lo	Vcc		+ 25° C			-40/ + 85°C		55/ 25° C	Vı	Vcc	+ 25° C		;	-40/ + 85° C				UNITS
	v	mA	\ \	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	_	1.5	_		4.5								
Input Voltage VIH			4.5	3.15	_	-	3.15	-	3.15	_		to	2	_	_	2	-	2	_	
			6	4.2	_	-	4.2	-	4.2	-	-	5.5								v
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage VIL			4.5	_	_	1.35	-	1.35	_	1.35		to	_	_	0.8	-	0.8	-	0.8	v
			6	_	_	1.8	-	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage Voн	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	-	or	4.5	4.4	–	-	4.4	-	4.4	_	v
CMOS Loads	Vін		6	5.9	_	_	5.9	_	5.9	_	Vін									
	VIL					L					VIL									
TTL Loads	or	-4	4.5	3.98	<u> </u>	_	3.84	<u> </u>	3.7	_	or .	4.5	3.98	-	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	Vін									
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	VIL									
Output Voltage Vol.	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	-	0.1	v
CMOS Loads	Vін		6	_	_	0.1	_	0.1	_	0.1	Vін				ļ.					
	VIL										VIL									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	٧
	ViH	5.2	6	_	-	0.26		0.33	_	0.4	V _{IH}									
Input Leakage	Vcc										Any Voltage	į								
Current li	or		6	–	-	±0.1	_	±1	-	±1	Between Vcc &	5.5	_	_	±0.1	-	±1	_	±1	
	Gnd		<u> </u>								Gnd									Aμ
Quiescent	Vcc		İ								Vcc									
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	_	8	-	80	-	160	Aц
Current Icc	Gnd										Gnd									
Additional quiescent Device Current \(\Delta \cc^* \) per input pin:											Vcc-2.1	4.5 to	_	100	360	_	450	_	490	Aμ
1 unit load												5.5		l		l	l			

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input -	Unit Loads*
СР	0.6
MR	0.55
DSL, DSR, Dn	0.25
Sn	1.10

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, tr = 6 ns)

OHADA OTEDIOTIO		Cr	TYP	UNIT		
CHARACTERISTIC		pF	нс	нст	JAIT	
Propagation Delay,	t _{PLH}	15	14	15	ns	
Clock to Q	tрнц					
Maximum Clock Frequency	fмах	15	60	50	MHz	
Power Dissipation Capacitance*	СРД	_	55	60	pF	

^{*}CPD is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 fi + \Sigma (C_L V_{CC}^2 fo)$ where:

fi = input frequency.

fo = output frequency.

C_L = output load capacitance.

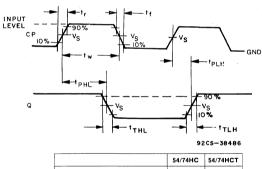
Vcc = supply voltage.

PREREQUISITE FOR SWITCHING FUNCTION

		TEST						LIN	MITS						
		CONDITION		2	5°C		-4	0°C to	+ 85	°C	-5				
CHARACTERISTIC		V cc	ŀ	IC	н	СТ	74	нс	74H	нст	54	нс	541	нст	UNITS
CHARACTERISTIC		V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	UNITS
Max. Clock Frequency	fmax	2	6				5		_		4		_		
Fig. 3		4.5	30	ł	27		24		22		20		18		MHz
		6	35		_	l	28		-		23				
MR Pulse Width	tw	2	80		_		100		_		120		_		
Fig. 4		4.5	16	ļ	18		20		23		24		27	,	ns
		6	14		ļ. —	l	17		_		20		-	}	
Clock Pulse Width	tw	2	80		—		100		_		120		_		
Fig. 3		4.5	16		18		20		23		24		27		ns
		6	14		_	1	17	ĺ		ĺ	20		l —		
Set-up time	t su	2	70		_		90		_		105		_		
Data to Clock		4.5	14		14		18	İ	18		21		21		ns
Fig. 5		6	12		_	ł	15		_		19		l —		
Removal Time	tяєм	2	60		_		75		_		90		<u> </u>		
MR to Clock		4.5	12		14		15		18		18		21		ns
Fig. 4		6	10		_	ŀ	13				15		-		ļ
Set-up Time	tsu	2	80				100		_		120		_		
S1, S0 to Clock		4.5	16		20		20		25		24		30		ns
Fig. 6		6	14		_		17				20		_		
Set-up Time	tsu	2	70		_		90		_		105		_		
DSL, DSR to Clock		4.5	14		14		18		18		21		21]	ns
Fig. 6		6	12		_		15		_		18			İ	
Hold Time	tн	2	0				0				0		_		
S1, S0 to Clock		4.5	0		0		0		0		0		0		ns
Fig. 6		6	0				0				0		_		
Hold Time	tн	2	0				0		_		0		_		
Data to Clock		4.5	0		0		0		0		0		0		ns
Fig. 5		6	0		l —		0		_		0				

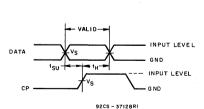
SWITCHING CHARACTERISTICS (CL = 50 pF, Input to tr = 6 ns)

		TEST						LIN	MITS						
		CONDITION		25	°C		-4	0°C to	+ 85	°C	-5	5°C to	+ 12	5°C	
CHARACTERISTIC		Vcc	Н	IC	Н	СТ	74	нс	741	нст	54	НС	54	нст	UNITS
CHARACTERISTIC		V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	UNITS
Propagation Delay	t PLH	2 .		175		_		220				265			
Clock to Output	t _{PHL}	4.5		35		37		44		46		53		56	ns
Fig. 3		6		30		_		37		-		45		- ,	
Output Transition	tтьн	2		75		_		95		_		110		_	
Time	tтнь	4.5		15		15		19		19		22		22	ns
Fig. 3		6		13		_		16				19		_	
Propagation Delay	t PHL	2		140		_		175		_		210		_	
MR to Output		4.5		28		40		35		50		42		60	ns
Fig. 4		6		24				30		_		36		_	
Input Capacitance															
	Cı			10		10		10		10		10		10	pF



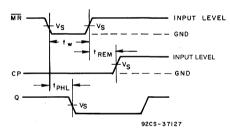
	54/74HC	54/74HC1
INPUT LEVEL	Vcc	3 V
SWITCHING VOLTAGE, VS	50% V _{CC}	1.3 V

Fig. 3 - Clock pre-requisite times and propagation and output transition times.



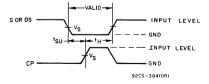
	54/74HC	54/74HCT
INPUT LEVEL	Vcс	3 V
SWITCHING VOLTAGE, VS	50% V _{CC}	1.3 V

Fig. 5 - Data pre-requisite times.



	54/74HC	54/74HCT
INPUT LEVEL	Vcc	3 V
SWITCHING VOLTAGE, VS	50% V _{CC}	1.3 V

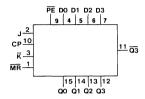
Fig. 4 - Master reset pre-requisite times and propagation delays.



	54/74HC	54/74HCT
INPUT LEVEL	Vcc	3 V
SWITCHING VOLTAGE, VS	50% V _{CC}	1.3 V

Fig. 6 Parallel load or shift-left/shift-right pre-requisite times.

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM

4-Bit Parallel Access Register

Type Features:

- Asynchronous Master Reset
- J, K, (D) inputs to first stage
- Fully synchronous serial or parallel data transfer
- Shift right and parallel load capability
- Complementary output from last stage
- Buffered inputs
- Typical f_{MAX}=50 MHz @ V_{CC}=5 V, C_L=15 pF, T_A=25°C

The functional characteristics of the RCA-CD54/74HC195 and CD54/74HCT195 4-Bit Parallel Access Register are indicated in the Logic Diagram and Function Table. The device is useful in a wide variety of shifting, counting and storage applications. It performs serial, parallel, serial-toparallel, or parallel-to-serial data transfers at very high speeds.

The two modes of operation, shift right (Q0-Q1) and parallel load, are controlled by the state of the Parallel Enable (PE) input. Serial data enters the first flip-flop (Q0) via the J and K inputs when the PE input is high, and is shifted one bit in the direction Q0-Q1-Q2-Q3 following each LOW-to-HIGH clock transition. The J and K inputs provide the flexibility of the JK-type input for special applications and, by tying the two pins together, the simple D-type input for general applications. The device appears as four common-clocked D flip-flops when the PE input is LOW. After the LOW-to-HIGH clock transition, data on the parallel inputs (D0-D3) is transferred to the respective Q0-Q3 outputs. Shift left operation (Q3-Q2) can be achieved by tying the Qn outputs to the Dn-1 inputs and holding the PE input low.

All parallel and serial data transfers are synchronous, occurring after each LOW-to-HIGH clock transition. The HC/HCT195 series utilizes edge-triggering: therefore, there is no restriction on the activity of the J, K, Pn and PE inputs for logic operations, other than the set-up and hold time requirements. A LOW on the asynchronous Master Reset (MR) input sets all Q outputs LOW, independent of any other input condition.

The CD54HC195 and CD54HCT195 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC195 and CD74HCT195 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dualin-line surface mount plastic package (M suffix). Both types are also available in chip form (H suffix).

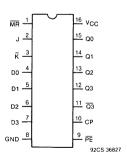
Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:

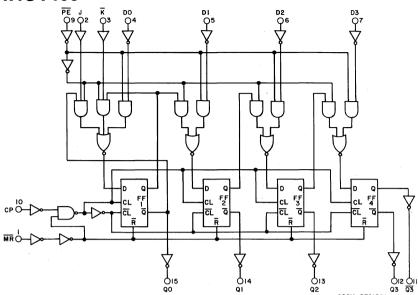
2 to 6 V Operation High Noise Immunity: N_{IL}=30%, N_{IH}=30% of V_{CC} @ $V_{cc}=5 V$

■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility VIL=0.8 V Max., VIH=2 V Min. CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$



TERMINAL ASSIGNMENT



Function Table

Fig. 1 - Logic diagram.

9	2	С	м	-	3	7	0	1	2	R	ł	

				INP	UTS				OI	JTPU	TS	
Operating Modes		MR	CP	PE	J	K	Dn	Q0	Q1	Q2	Q3	Q3
Asynchronous Reset		L	Х	Х	Х	Х	X	L	L	L	L	Н
Shift, Set first stage		Н	_	h	h	h	Х	Н	.qo	q ₁	q ₂	q2
Shift, Reset first stage		Н		h	1	- 1	Х	L	q _o	q ₁	q ₂	q ₂
Shift, Toggle first stage		н		h	h	1	X	go	q _o	q ₁	q ₂	q ₂
Shift, Retain first stage		H		h.	1	h	X	qo	q₀	q ₁	q ₂	q2
Parallel Load		Н		1	Х	X	dn	d₀	d ₁	d₂	d₃	a₃

H=HIGH voltage level.

L=LOW voltage level.

I=LOW voltage level one set-up time prior to the LOW-to-HIGH clock transition.

h=HIGH voltage level one set-up time prior to the LOW-to-HIGH clock transition.

dn (qn)=Lower case letters indicate the state of the referenced input (or output) one set-up time prior to the LOW-to-HIGH clock transition.

J=LOW-to-HIGH clock transition.

MAXIMUM RATINGS, Absolute-Maximum Values:

VOLTAGE. (Vcc):	DC S
oferenced to ground)0.5 to + 7 V	
ODE CURRENT, I_{IK} (FOR $V_1 < -0.5$ V OR $V_1 > V_{CC} +0.5$ V)	
DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)	
JRRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V) $+$ 25mA	
ROUND CURRENT (Icc) ±50mA	
IPATION PER PACKAGE (P _D):	
1 to +60° C (PACKAGE TYPE E)	
D to +85°C (PACKAGE TYPE E)	
to +100°C (PACKAGE TYPE F. H) 500 mW	
00 to +125° C (PACKAGE TYPE F, H)	
0 to +70°C (PACKAGE TYPE M)	

FOR TA - +100 to +125 C (PACKAGE TIPE F, H)	Derate Linearly at 6 mw/ C to 300 mm
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	

OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F. H55 to	+125° C
PACKAGE TYPE E, M	+85° C
STORAGE TEMPERATURE (Tsig) -65 to	+150° C

STORAGE TEMPERATURE (Tstg)		 -65 to +150° C
LEAD TEMPERATURE (DURING	SOLDERING):	

At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	

STATIC ELECTRICAL CHARACTERISTICS

	CD74HC195/CD54HC195										CD74HCT195/CD54HCT195									
CHARACTERISTIC	TEST CONDITIONS			74HC/54HC TYPES			74HC TYPES		54HC TYPES		TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS
CHARACTERISTIC	V, V	I _o mA	V _{cc}	+25° C			-40/ +85° C		-55/ +125° C		V.	V _{cc}	+25°C		;	-4 +85			5/ 5° C	UNITS
				Min	Тур	Max	Min	Max	Min	Max			Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-	-	1.5	_	1.5	-		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	-	-	2	_	2	-	v
			6	4.2	-	_	4.2	_	4.2	_		5.5				ļ				
Low-Level			2	_	_	0.5		0.5		0.5		4.5								
Input Voltage V _{II}			4.5	_	_	1.35	_	1.35	_	1.35] -	to	-	-	0 8	-	0.8	-	0.8	v
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	V _{IL}		2	1.9			1.9		1.9		V _{ii}									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										Vii									
TTL Loads	or	-4	4.5	3.98	_		3.84	_	3.7	-	or	4.5	3.98	-	-	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V,,,									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	V _{II}									
Output Voltage V_{OL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads	VIII		6	_	_	0.1	_	0.1	_	0.1	V,,,									
	V _{IL}										V _{II}									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	Viii	5.2	6	_	_	0.26	_	0.33	_	0.4	V.,,						ļ	ļ	<u> </u>	
Input Leakage	V _{cc}										Any Voltage					{		1		
Current I,	or		6	-	-	±0.1	_	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	± 1	-	±1	μΑ
	Gnd										& Gnd	_	_					<u> </u>	<u> </u>	
Quiescent	Vcc										Vcc									
Device	or	0	6	-	-	8	-	80	_	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd								<u> </u>		Gnd									
Additional Quiescent Device Current per input pin:											V _{cc} 2.1	4.5 to	-	100	360	_	450	-	490	μΑ
1 unit load ΔI_{cc}											1	5.5					ļ			

¹ unit load Δ lcc | For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*						
D0-D3	0.3						
ΡĒ	-0.65						
MR	0.3						
CP	0.3						
J, K	0.3						

*Unit Load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	MITS	шите
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage Vin, Vout	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r ,t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r, t_f = 6 ns)

		C,	Tyl	pical	•• ••
CHARACTERISTIC	SYMBOL	pF	HC	HCT	Units
CP to Qn Propagation Delay	t _{PHL} t _{PLH}	15	14	14	ns
MR to Qn	t _{PHL}	15	13	14	ns
Maximum Clock Frequency	f _{MAX}	15	50	50	MHz
Power Dissipation Capacitance*	C _{PD}		45	50	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per register.

PD = $C_{PD} Vcc^2 fi + \Sigma C_L Vcc^2 fo$ where

fi = input frequency

fo = output frequency

C_L = output load capacitance

Vcc = supply voltage.

Pre-requisite for Switching Function

		·		25	°C		-4	0°C to	+85°	,C	-59	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	CT	741	HC	74H	ICT	54	нС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Clock Frequency	f _{MAX}	2	6	_	_	_	5	_		_	4		_	-	
(Figure 3)		4.5	30	l —	25	—	25	-	20	-	20	 	16	 	ns
		6	35	—		—	29	_	_	—	23	_		_	
MR Pulse Width	tw	2	80	_	_	_	100	_	_	_	120	_	_	_	
(Figure 3)	ļ	4.5	16		20	—	20	_	25	_	24	_	30	—	ns
		6	14	—	—	<u> </u>	17	-		_	20		—	—	
Clock Pulse Width	t _w	2	80	_		_	100		_	_	120	_	_		
(Figure 3)		4.5	16	—	20	—	20		25	—	24	-	30	_	ns
		6	14	—			17	—	_	_	20	—	 –	-	
Set-up Time	t _{su}	2	100	_			125	_	I —	_	150		-	_	
J, K, PE to Clock		4.5	20	l —	20	—	25	_	25	_	30		30		ns
(Figure 5)		6	17	l —			21	_		_	26	_		_	
Hold Time	th	2	3	_	_	_	3	_	—	_	3	_	_	_	
J, K, PE to Clock		4.5	3	l —	3	—	3	_	3	—	3	—	3	—	ns
(Figure 5)		6	3	l —	l —	l —	3	—	l —	—	3	-	_	—	1
Removal Time	t _{REM}	2	80	_	_	_	100	_	_	_	120		_	_	
MR to Clock		4.5	16	—	16	—	20	-	20	—	24	—	24	-	ns
(Figure 3)		6	14	—	—	—	17	—	l —	—	20	—		-	

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,ti=6 ns)

				25	°C		-4	0°C t	o +85°	°C	-5	5°C to	+125	5° C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	H	CT	74	HC	74F	ICT	54	54HC		HCT	UNITS
		1	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.]
Propagation Delay	t _{PLH}	2	-	175	_	_	_	220	_	_		265	_		
CP to Output	t _{PHL}	4.5	_	35	-	35	<u> </u>	44	_	44	—	53	—	53	ns
(Figure 3)		6		30	—	_	—	37	—	_	_	45	 	_	
Propagation Delay	t _{PHL}	2	_	150	_		_	190			—	225	_	-	
MR to Output	t _{PLH}	4.5	_	30	_	35	—	38	_	44	l —	45		53	ns
(Figure 3)		6	_	26	—	—	—	33	—	i —		38	_		
Output Transition	t _{TLH}	2	T —	75	_	_	_	95	_	_	_	110		_	
Time	t _{THL}	4.5	-	15	_	15	_	19	—	19	i —	22	l —	22	ns
		6	—	13		_	<u>-</u>	16	<u> </u>	-	—	19	—	-	
Input Capacitance	Cı		_	10	_	10	_	10	_	10	-	10		10	pF

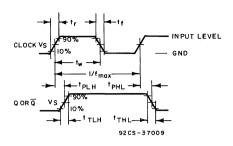


Fig. 3 - Clock pre-requisite and propagation delays and output transition times.

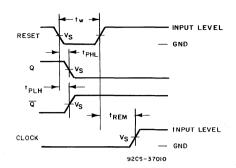


Fig. 4 - Master Reset pre-requisite and propagation delays.

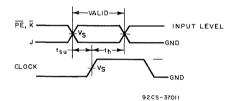


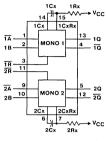
Fig. 5 - J, K or Parallel Enable pre-requisite times.

	HC	HCT
INPUT LEVEL	V _{cc}	3V
V _s	50%	1.3V

File Number 1670

Advance Information/ Preliminary Data

High-Speed CMOS Logic



92CS-38526RI
FUNCTIONAL DIAGRAM

Dual Monostable Multivibrator with Reset

Type Features:

- Overriding RESET Terminates Output Pulse
- Triggering From the Leading or Trailing Edge
- Q and Q Buffered Outputs
- Separate Resets
- Wide Range of Output-Pulse Widths
- Schmitt Trigger on B inputs

The RCA-CD54/74HC221 and CD54/74HCT221 are dual monostable multivibrators with reset. An external resistor (Rx) and an external capacitor (Cx) control the timing and the accuracy for the circuit. Adjustment of Rx and Cx provides a wide range of output pulse widths from the Q and $\overline{\Omega}$ terminals. Pulse triggering on the B input occurs at a particular voltage level and is not related to the rise and fall time of the trigger pulse.

Once triggered, the outputs are independent of further trigger inputs on \overline{A} and B. The output pulse can be terminated by a LOW level on the Reset (\overline{R}) pin. Trailing-edge triggering (\overline{A}) and leading-edge-triggering (B) inputs are provided for triggering from either edge of the input pulse. On power up, the IC is reset. If either Mono is not used each input (on the unused device) must be terminated either high or low.

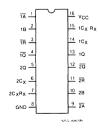
The minimum value of external resistance, R_x , is typically 500Ω . The minimum value of external capacitance, C_x , is 0 pF. The calculation for the pulse width is t_w = 0.7 R_xC_x at V_{CC} = 4.5 V.

The CD54HC/HCT221 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT221 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity:
- N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V ■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.

CMOS Input Compatibility $I_1 \le 1 \mu A @ V_{OL}, V_{OH}$



TERMINAL ASSIGNMENT

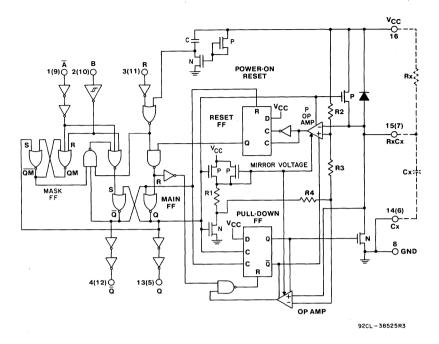


Fig. 1 — Logic diagram

	1	TRUTH TAB	LE	
	INPUTS		OUT	PUTS
A	В	R	Q	Q
Н	Х	Н	L	Н
×	L	н	L	н
L		н	л	T
~_	Н	н	Лī	J.r
X	X	L'	L	Н
L	н		Л*	

H = High Level

= Low Level

= Transition from Low to High = Transition from High to Low = One High Level Pulse

I = One Low Level Pulse

X = Irrelevant

*For this combination the reset input must be low and the following sequence must be used: pin 1 (or 9) must be set high or pin 2 (or 10) set low; then pin 1 (or 9) must be low and pin 2 (or 10) set high. Now the reset input goes from low-to-high and the device will be triggered.

STATIC ELECTRICAL CHARACTERISTICS

		С	D74H	C221/	CD54	HC22	!1					CD	74HC	T221/	CD54	нста	221			
CHARACTERISTIC		TEST IDITIONS		74HC/54HC 74HC 54HC TYPES TYPES				TEST 74HCT/54HCT CONDITIONS TYPES						54H TYI	ICT PES	UNITS				
STATIA OTENIONO	V,	l _o mA	V _{cc}		+25° C	;	-4 +85		-5 +12		V,	V _{cc}		+25° C	;	-4 +85			5/ 5° C	0.1.10
	Ţ	""		Min	Тур	Max	Min	Max	Min	Max			Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5		_	1.5	_	1.5			4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	-	-	2	-	2	-	v
			6	4.2	_	_	4.2		4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35		1.35	_	1.35	-	to	-	-	0.8	_	0.8	-	0.8	V
			6	_	_	1.8		1.8	_	1.8		5.5	ļ							
High-Level	V _{IL}		2	1.9		_	1.9	_	1.9		VIL									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	V
CMOS Loads	V _{IH}		6	5.9	_	_	5.9		5.9		V _{iH}					ļ			-	
	V _{IL}			ļ	<u></u>						V _{IL}	!								
TTL Loads	or	-4	4.5	3.98		_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	\ \
	V _{IH}	-5.2	6	5.48	-	_	5.34	_	5.2	_	V _{iH}		ļ		<u> </u>			ļ	-	
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	_		0.1	_	0.1	_	0.1	V _{IH}	_						-	-	
	V _{IL}		-	-							V _{IL}									
TTL Loads	or	4	4.5	_	_	0.26	-	0.33	_	0.4	or	4.5	_	_	0.26	-	0.33	-	0.4	V
land Land	V _{IH}	5.2	6		_	0.26	_	0.33	_	0.4	V _{IH}				-		-	-	-	
Input Leakage Current I	V _{cc}		6		_	١.,.	_		_		Any Voltage Between	5.5	_	_	±0.1	_	.,	_		
Current I,	or Gnd		°	_	-	±0.1	_	±1	_	±1	V _{cc} & Gnd	5.5		_	±0.1	_	±1	_	±1	μΑ
Quiescent	V _{cc}			_	-					-	V _{cc}		-	-	-	-	-	-		
Device	or	0	6			8		80		160	or	5.5	_	_	8	_	80	_	160	μΑ
Current I _{cc}	Gnd		ľ					55			Gnd	3.3					00			"
Additional	G.13	L	L	L	l	L	L	L	L	L	<u> </u>	4.5						-	ļ	
Quiescent Device Current per input pin: 1 unit load \[\Delta \lambda \lambda \cc^* \]											V _{cc} -2.1	to 5.5	_	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_{I} = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
All Inputs	0.3

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5 \text{ V OR } V_i > V_{CC} + 0.5 \text{V}$)	
DC OUTPUT DIODE CURRENT, Iox (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tstg)	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	٧
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
on Inputs A and R			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns
Input Rise and Fall Times t _r , t _f			
on Input B			
at 2 V	0	Unlimited	ns
at 4.5 V	0	Unlimited	ns
at 6 V	0	Unlimited	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERISTIC		CL	TYP	ICAL	UNITS
CHARACTERISTIC		(pF)	54/74HC	54/74HCT	UNITS
Propagation Delay		-			
\overline{A} , B, \overline{R} to Q	t _{PLH}	15	18	18	ns
\overline{A} , B, \overline{R} to \overline{Q}	t _{PHL}	15	14	14	ns
Power Dissipation Capacitance*	C _{PD}	-	166	166	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per multivibrator.

 $P_D = (C_{PD} + C_x) V_{CC}^2 f_i + \sum (C_L V_{CC}^2 f_o)$ where:

f_i = input frequency. f_o = output frequency.

C_L = output load capacitance.

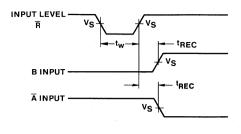
 V_{CC} = supply voltage. assuming $f_i \ll \frac{1}{t_w}$

PREREQUISITE FOR SWITCHING FUNCTION

				25	°C		-4	0°C to	o +85°	С	-5!	5°C to	+125	°C	
CHARACTERISTIC		V _{cc}	Н	С	Н	CT	74	нс	74F	ICT	54	НС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Input Pulse Width		2	70	—	—	—	90	l —	-	—	105	l —	-		
	twL	4.5	14	l —	14		18	_	18	_	21	_	21	l —	ns
Ā		6	12				15		_	_	18		_	_	
		2	70	_	_	_	90	_	_	_	105	_	_	-	
В	twH	4.5	14	-	14	-	18	-	18	-	21	—	21	—	ns
		6	12			_	15				18		_		
ļ		2	70	—	—	—	90	_	—	—	105	—	—	_	
Reset	t_{WL}	4.5	14	—	18	-	18	_	23		21	—	27	—	ns
		6	12				15				18		_		
Recovery Time		2	0	—	_	—	0		-		0	-	—	-	
R to A or B	t _{REC}	4.5	0	—	0	-	0	-	0	-	0	-	0	_	ns
		6	0	_		_	0		_		0				
Output Pulse Width															
QorQ	tw	5	630	770	630	770	602	798	602	798	595	805	595	805	μs
$C_x = 0.1 \mu\text{F R}_x = 10\text{k }\Omega$															
Output Pulse			Тур	oical	Тур	ical									
Width Q or Q	tw	4.5	1.	40	14	40	—	-	-	_	-	_	—	_	ns
C_x = 28 pF, R_x = 2K Ω										ļ		ļ			
$C_x = 1000 \text{ pF}, R_x = 2K \Omega$	tw	4.5	1	.5	1	.5		_		_			_		μs
$C_x = 1000 \text{ pF, } R_x = 10 \text{K } \Omega$	tw	4.5		7		7			_	_	_	_	_		μs

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_r = 6 ns)

				25	°C		-4	0°C to	o +85°	С	-5	°C			
CHARACTERISTIC	SYMBOL	Vcc	Н	С	H	CT	74	нс	74F	ICT	54	нс	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2		210		_	_	265	_	_	_	315	_	_	
Trigger		4.5	l —	42	<u> </u>	42	—	53	_	53	—	63	-	63	ns
\overline{A} , B, \overline{R} to Q		6	l –	36	_	_		45		_	_	54	_		
		2	—	170	_	-	l —	215	-	<u> </u>	_	255	-	_	
Ā, B, R to Q	t _{PHL}	4.5	<u> </u>	34	_	34	<u> </u>	43	—	43	_	51	—	51	ns
		6		29			_	37		_	_	43		_	
Propagation Delay		2	_	160	-	_	—	200	_	_		240		—	
R to Q	t _{PLH}	4.5	-	32	—	38	—	40	_	48	-	48	—	57	ns
		6		27				34			_	41		_	
		2	l –	180	l —	—	_	225		_	-	270	—		
R to Q	t _{PHL}	4.5	_	36	_	37	-	45		46	—	54	_	56	ns
		6	_	31		_		38		_		46		_	
Output		2	-	75	_	—	_	95	l —	—	-	110	_	-	
Transition Time	t _{TLH}	4.5	-	15	-	15	_	19	—	19	—	22	—	22	ns
	t _{THL}	6		13			_	16			_	19			
Input Capacitance	Cin		_	10	l —	10	—	10	—	10	_	10	_	10	рF
Pulse Width match		4.5													
between circuits in		4.5	Тур	ical	Тур	ical									%
the same package		to	±	:2	±	2	_	-	-	-	-	-	_	-	70
$C_x=1000 \text{ pF,R}_x=10 \text{K}\Omega$		5.5						L		<u> </u>	<u> </u>				



92CS-38555

Fig. 2 — Recovery times, \overline{R} to \overline{A} or B.

	54/74HC	54/74HCT
Input Level	VCC	3 V
Switching Voltage, VS	50% VCC	1.3 V

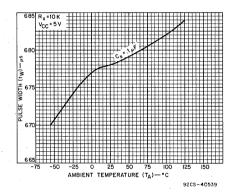


Fig. 4 — HC/HCT221 Output Pulse Width vs. Temperature.

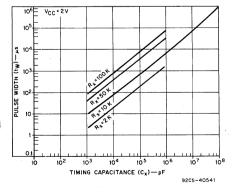


Fig. 6 — HC221 Output Pulse Width vs. Cx.

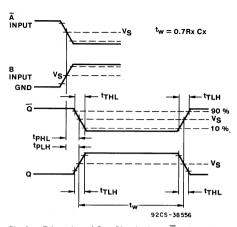


Fig. 3 — Triggering of One Shot by input \overline{A} or input B for a period t_w .

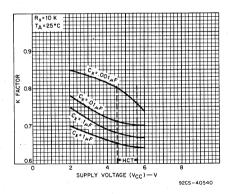


Fig. 5 — HC/HCT221 K Factor vs. Supply Voltage.

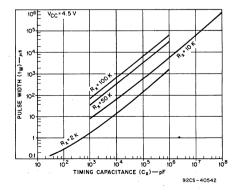


Fig. 7 — HC/HCT221 Output Pulse Width vs. C_x.

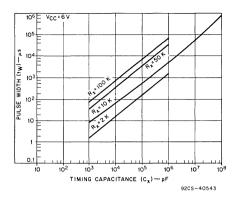
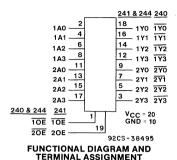


Fig. 8 — HC221 Output Pulse Width vs. C_x.

High-Speed CMOS Logic



Octal Buffer/Line Drivers, 3-State

CD54/74HC/HCT240 Inverting CD54/74HC/HCT241 Non-Inverting CD54/74HC/HCT244 Non-Inverting

Type Features:

- Typical propagation delay = 8 ns
 @ V_{CC}=5 V, C_L=15 pF, T_A=25° C for HC240
- 3-State outputsBuffered inputs
- High-current bus driver outputs

The RCA-CD54/74HC240 and CD54/74HCT240 are inverting 3-state buffers having two active-low output enables. The RCA CD54/74HC/HCT241 and CD54/74HC/HCT244 are non-inverting 3-state buffers that differ only in that the 241 has one active-high and one active-low output enable, and the 244 has two active-low output enables. All three types have identical pinouts.

The CD54HC240/241/244 and CD54HCT240/241/244 are supplied in 20-lead ceramic dual-in-line packages (F suffix). The CD74HC240/241/244 and CD74HCT240/241/244 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). The CD54/74HC/HCT240/241/244 are also supplied in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation

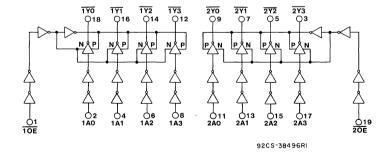
High Noise Immunity:

 $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5$ V

N_{IL}= 30%, N_{IH}=30% of V_{CC}; @ V_{CC}=5 V ■ CD 54HCT/CD74HCT Types: 4.5 to 5.5 V Operation

Direct LSTTL Input Logic Compatibility $V_{\rm IL}$ =0.8 V Mas., $V_{\rm IH}$ =2 V Min. CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \;@ V_{OL}, V_{OH}$



TRUTH TABLE

INP	JTS	ОИТРИТ
10E,20E	A	Y
L	L	Н
L	н	L
Н	Х	Z

(HC/HCT240)

Fig. 1 - CD54/74HC/HCT240 logic diagram.

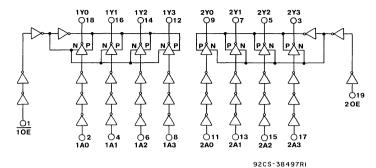


Fig. 2 - CD54/74HC/HCT241 logic diagram.

TRUTH TABLE

INP	UTS	OUTPUT	INP	UTS	OUTPUT
10E	1A	1Y	20E	2A	2Y
L	L	L	L	Х	z
L	н	н	Н	L	L
l н	l x	lzl	н	н	I н

H=HIGH Voltage Level (HCT/HCT241)

L=LOW Voltage Level

X=Immaterial

Z=HIGH Impedance

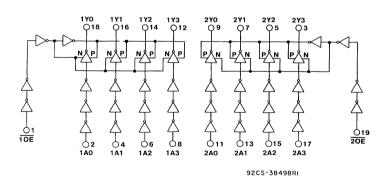


Fig. 3 - CD54/74HC/HCT244 logic diagram.

TRUTH TABLE

INP	JTS	OUTPUT
10E, 20E	Α	Υ
L	L	L
L	Н	Н
Н	x	z

(HC/HCT244)

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc): DC V_{cc} OR GROUND CURRENT, (I_{cc}) ±70 mA POWER DISSIPATION PER PACKAGE (Pn): OPERATING-TEMPERATURE RANGE (TA): PACKAGE TYPE F, H-55 to +125°C PACKAGE TYPE E, M-40 to +85°C STORAGE TEMPERATURE (T_{sta}) .-65 to +150° C LEAD TEMPERATURE (DURING SOLDERING): At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79$ mm) from case for 10 s max. +265°C Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{CC}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	0.0
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC2	40/24	1/244,	CD54	HC24	10/241	/244			CD74	нста	40/24	1/244	CD54	нст	240/2	41/244		
CHARACTERISTIC	co	TEST CONDITIONS		74HC/54HC TYPES		l	HC PES		HC PES	TEST	- 1		CT/54			ICT PES	54F TYI	ICT PES	UNITS	
	V _i	Io	v _{cc}		+25° C	:	-40/ +85° C		-55/ +125°C		V ₁	v _{cc}	+25° C		:	-40/ +85° C		-55/ +125° C		
	V	mA	ď	Min	Тур	Max	Min	Max	Min	Max	V	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage VIH			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	_	2	_	v
			6	4.2	_	_	4.2	_	4.2	-	1	5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage VIL			4.5	_	_	1.35	_	1.35	_	1.35	-	to	_	_	0.8	_	0.8	_	0.8	v
			6	_	_	1.8	_	1.8	_	1.8]	5.5							,	
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads	VIH		6	5.9	_	_	5.9	_	5.9	_	VIH			Ì						
	VIL										V _{IL}									
TTL Loads	or	-6	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	-	3.7	_	v
(Bus Driver)	VIH	-7.8	6	5.48	_	_	5.34	_	5.2	_	VIH									
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	VIL									
Output Voltage V _{OL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	V
CMOS Loads	VIH		6	_	_	0.1	_	0.1	_	0.1	ViH									
	VIL										VIL									
TTL Loads	or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	-	0.4	v
(Bus Driver)	V _{IH}	7.8	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{CC}										Any Voltage									
Current I _I	or		6	_	_	±0.1	-	±1	-	±1	between V _C C	5.5	_	_	±0.1	_	±1	-	±1	μΑ
	Gnd										& Gnd									
Quiescent	Vcc										V _{CC}									
Device	or	0	6	_	_	8	-	80	-	160	or	5.5	_	-	8	_	80	-	160	μΑ
Current I _{CC}	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load											V _{CC} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-state leakage current I _{OZ}	V _{IL} or V _{IH}	V _O =V _{CC} or Gnd	6	_	_	±0.5	_	±5	_	±10	V _{IL} or V _{IH}	5.5	_	_	±0.5	_	±5	_	±10	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Tables

CD54/	74HCT240
Input	Unit Loads*
nA0-A3	1.5
10E	0.7
20E	0.7

CD54/	74HCT241
Input	Unit Loads*
nA0-A3	0.7
10E	0.7
20 <u>E</u>	1.5

CD54/7	74HCT244
Input	Unit Loads*
nA0-A3	0.7
10E	0.7
2OE	0.7

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

SWITCHING CHARACTERISTICS ($V_{\rm CC}$ =5 V, $T_{\rm A}$ =25° C, Input $t_{\rm r}$, $t_{\rm r}$ =6 ns)

CHARACTERISTIC	SYMBOL	C _L 24		10	24	11	24	4	UNITS
		pF	нс	нст	нс	нст	нс	нст	
Propagation Delay Data to Output	t _{PHL} t _{PLH}	15	8	9	9	10	9	10	ns
Output Disable/Enable to Outputs	t _{PZH} , t _{PZL} , t _{PHZ} , t _{PLZ}	15	12	12	12	12	12	12	ns
Power Dissipation Capacitance	C _{PD} *	_	38	40	34	38	46	40	pF

C_{PD} is used to determine the dynamic power consumption per channel.

 $P_D = V_{cc}^2 f_i (C_{PD} + C_L)$

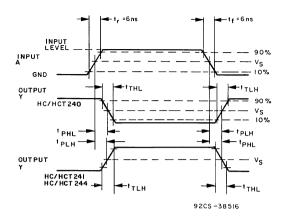
f_i=input frequency.

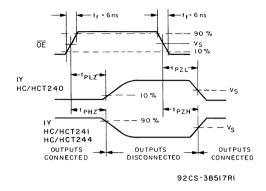
C_L = output load capacitance.

V_{CC} = supply voltage.

SWITCHING CHARACTERISTICS (C_L =50 pF, Input t_r , t_r =6 ns)

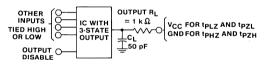
				25	°C			-40° C t	o +85° C	;		-55°C to	+125°(3	
CHARACTERISTIC	SYMBOL	V _{CC}	н	нс		нст		74HC		74HCT		54HC		54HCT	
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	-	100	_	-	_	125	_	_	_	150	_		
Data to Outputs	t _{PHL}	4.5	_	20	_	22	_	25	-	28	—	30	<u> </u>	33	ns
HC/HCT 240		6	_	17	<u></u>		_	21			_	26	_		
Data to Outputs	t _{PLH}	2	_	110		_	_	140	_	-	_	165	_	-	l
HC/HCT241	t _{PHL}	4.5	-	22	-	25	—	28	-	31		33	-	38	ns
		6		19	_			24			_	28			
Data to Outputs	t _{PLH}	2	_	110	-	_		140	_	_	_	165	_	-	
HC/HCT 244	t _{PHL}	4.5	_	22	_	25	_	28		31	_	33		38	ns
		6	-	19	_	l –	-	24	_	_	<u> </u>	28	_	-	
Output	t _{PZH}	2	_	150	_	_	_	190	_	_	_ ·	225	_	-	
Enable and	tpzL	4.5	_	30	_	١ 30	_	38	_	38	-	45		45	ns .
Disable Times	t _{PHZ}	6	_	26		_	_	33		_	-	38	_	_	
	tPLZ														
Output		2	_	60	T_	_		75	_	_	_	90	_	_	
Transition Time	t _{TLH}	4.5	-	12	l _	12	_	15	_	15	_	18	_	18	ns
	t _{THL}	6	_	10	_	_	_	13	_	-	_	15	_	-	
Input															
Capacitance	Cı		_	10	-	10	-	10	_	10	-	10	-	10	pF
3-State															
Output			-	20	_	20	-	20	_	20	_	20	_	20	pF
Capacitance	Со														





	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 2 - Transition times and propagation delay times.

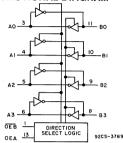


92CS-35I30R2

Fig. 4 - Three-state propagation delay test circuit.

High-Speed CMOS Logic

FUNCTIONAL DIAGRAM



Quad-Bus Transceiver with 3-State Outputs

Type Features:

- Typical propagation delay $(A \rightarrow B)$ of 7 ns @ $V_{CC} = 5 V$ $C_L = 15 pF$, $T_A = 25^{\circ} C$
- 3-state outputs
- Buffered inputs

CD54/74HC242, HCT242

The RCA-CD54/74HC242, 243 and CD54/74HCT242, 243 silicon-gate CMOS 3-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses: They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads.

The CD54/74HC242 and CD54/74HCT242 are inverting buffers; the CD54/74HC243 and CD54/74HCT243 are non-inverting buffers.

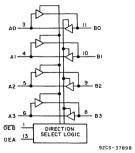
The states of the output enables ($\overline{\text{OEB}}$, OEA) determine both the direction of flow (A to B, B to A), and the 3-state mode.

The CD54HC242, 243 and CD54HCT242, 243 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC242, 243 and CD74HCT242, 243 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}
- @ V_{cc} = 5 V■ CD54HCT/CD74HCT Types:
 - 4.5 to 5.5 V Operation
 - Direct LSTTL Input Logic Compatibility $V_{1C} = 0.8 \text{ V Max.}$, $V_{1H} = 2 \text{ V Min.}$
 - CMOS Input Compatibility
 - CWOS Input Companion
 - $I_1 \leq 1 \mu A @ V_{OL}, V_{OH}$

FUNCTIONAL DIAGRAM



CD54/74HC243, HCT243

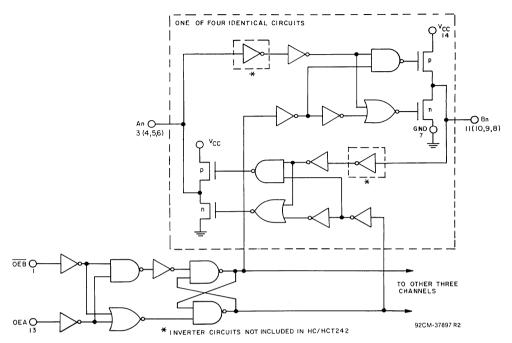


Fig. 1 - Logic diagram for the CD54/74HC/HCT242, 243.

TRUTH TABLE

		нс, нст	242 Series	нс, нст	243 Series			
	TROL	l	PORT	DATA PORT STATUS				
OEB	OEA	A n	Bn	• An	Bn			
Н	н	ठ	ı	0				
L	н	z	z	z	z			
Н	L	z	z	z	z			
L	L	1	 	1	0			

H = High

L = Low

I = Input

O = Output (Same Level as Input)
O = Output (Inversion of Input Level)
Z = High Impedance

To prevent excess currents in the High Z modes all I/O terminals should be terminated with 10 $k\Omega$ to 1 $M\Omega$ resistors.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{ik} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I ₀) (FOR -0.5 V < V ₀ < V _{cc} +0.5 V)	±35 mA
DC Vcc OR GROUND CURRENT, (Icc):	±70 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tato)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN	IITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	\ \ \ \ \
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t, t			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

	CD74HC242/243/CD54HC242/243										CD74HCT242/243/CD54HCT242/243									
	TEST CONDITIONS			1					HC PE	TEST CONDITIONS			CT/54 TYPE			ICT PE	54HCT TYPE		LINITO	
CHARACTERISTIC	V,	I _o	V _{cc}		+25° C	;		0/ 5° C	-5 +12	5/ 5° C	V,	Vcc		+25° C	;	ı	10/ 5° C		5/ 5°C	UNITS
	ď	mA	V	Min	Тур	Max	Min	Max	Min	Max	V	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	<u> </u>	3.15	_	3.15	_	_	to	2	_	-	2	_	2	_	l v
			6	4.2		-	4.2	_	4.2	_	1	5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35] –	to	-	-	0.8	-	8.0	-	0.8	v
			6	_	_	1.8	_	1.8	_	1.8]	5.5								
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	_	4.4	-	4.4	_	v
CMOS Loads	V _{IH}	1	6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										VıL									
TTL Loads	or	-6	4.5	3.98	_	-	3.84	_	3.7	_	or	4.5	3.98	-	_	3.84	-	3.7	-	v
(Bus Driver)	V _{IH}	-7.8	6	5.48	-	_	5.34	-	5.2	_	1 ∨ _{1H}									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage V _{OL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	_	0.1	_	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	_	0.33	_	0.4	v
(Bus Driver)	V _{IH}	7.8	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any									
Current I,	or		6	-	–	±0.1	_	±1	_	±1	Voltage Between	5.5	-	_	±0.1	-	±1	-	±1	μΑ
	Gnd										V _{cc} & Gnd									
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd		L								Gnd									
Additional Quiescent Device Current per input pin: 1 unit load \(\Delta \) lcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	-	490	μΑ
3-State Leakage Current I _{oz}	V _{IL} or V _{IH}	V _o = V _{cc} or Gnd	6	_	_	±0.5	_	±5.0	_	±10	V _{IL} or V _{IH}	5.5	-	_	±0.5	_	±5.0	-	±10	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads *
An, Bn	1.1
OEA, OEB	0.6

^{*}Unit Load is $\Delta l_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu{\rm A}$ max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r, t_f = 6 ns)

01145	CHARACTERISTIC	ayuna.	_					
СНА		CHARACTERISTIC SYMBO		C∟ pF	HC242	HCT242	HC243	HCT243
Propagation Delay		t _{PHL}	15	7	8	7	9	ns
	Data to Output	t _{PLH}	13			,		115
	Enable to High Z	t _{PHZ} , t _{PLZ}	15	12	14	12	14	ns
	Enable from High-Z	t _{PZH} , t _{PZL}	15	12	14	12	14	ns
Power Dissip	ation Capacitance*	CPD	_	85	90	80	91	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per channel.

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where: f_i = input frequency.

C_L = output load capacitance.

V_{cc} = supply voltage.

SWITCHING CHARACTERISTICS (C_L = 50 pF, input t_r , t_f = 6 ns)

				25	°C		-4	0°C to	+85°	С	-55°C to +125°C				
CHARACTERISTIC	SYMBOL	Vcc	н	С	н	ст	741	нс	74H	ICT	54	нс	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	90	_	_	_	115	_	_	-	135	_	_	
Data to Outputs	t _{PHL}	4.5	_	18	_	20	-	23	—	25	_	27	_	30	ns
HC/HCT242		6	_	15	_	_	_	20			-	23			
Propagation Delay	t _{PLH}	2	_	90	_	_	_	115	-	_	_	135	_	_	
Data to Outputs	t _{PHL}	4.5	_	18	—	22	· —	23	—	28	_	27	—	33	ns
for HC/HCT243		6	_	15	_	_		20		_ '	_	23			
Output High-Z:	t _{PZH}	2	_	150	_	_	—	190	_	-	_	225	_	_	
to High Level;	t _{PZL}	4.5	—	30	_	34	—	38	_	43	_	45	_	51	ns
to Low Level		6	_	26	_	_		33			_	38			
Output High Level;	t _{PHZ}	2	_	150	_	_	_	190	_	_	_	225	-	_	
Output Low Level	t _{PLZ}	4.5	-	30	—	35	—	38	_	44	_	45	—	53	ns
to High-Z		6		26			<u> </u>	33			_	38	_	_	
Output Transition	t _{TLH}	2	_	60	_	-	_	75	_	_	_	90	-	-	
Time	t _{THL}	4.5	-	12	_	12	-	15		15	—	18	-	18	ns
		6		10	_		_	13		<u> </u>	_	15		_	
Input Capacitance	Cı		_	10	_	10	_	10		10	_	10	_	10	pF
3-State Output Capacitance	Co		_	20	_	20	_	20	_	20	_	20	-	20	pF

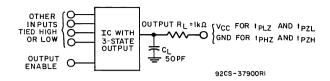
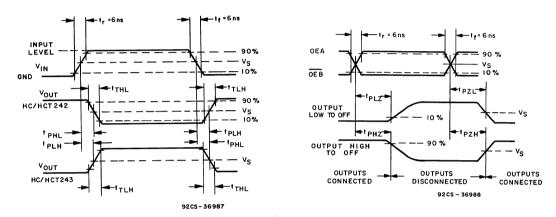


Fig. 2 - Three-state propagation delay test circuit.



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, V _s	50% V _{cc}	1.3 V

Fig. 3 - Transition times and propagation delay times.

NC 2 AO 3 A1 4 A2 5 A3 9 B1 9 B2 8 B3 8 B4 8 B5 8 B3 9 B2 8 B3 8 B4 8 B5 8 B6 8 B7 8 B4 8 B4 8 B4 8 B5 8 B6 8 B7 8 B6 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B7 8 B8 8 B8 8 B8 8 B8 8 B8</t

TERMINAL ASSIGNMENT

ORDERING INFORMATION

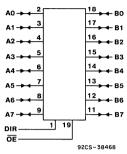
RCA CMOS device packages are identified by letters indicated in the following chart. When ordering a CMOS device, it is important that the appropriate suffix letter be affixed to the type number of the device.

Package	Suffix Letter
Dual-In-Line Plastic	E
Dual-In-Line Frit-Seal Ceramic	F
Dual-In-Line Surface Mount Plastic	M
Chip	Н

The CD54HC/HCT series is supplied in dual-in-line frit-seal ceramic packages (F suffix). The CD74HC/HCT series is supplied in dual-in-line plastic packages (E suffix) and in dual-in-line surface mount plastic packages (M suffix). Both series are supplied in chip form (H suffix).

For example, a CD54HC242 will be identified as the CD54HC242F. The CD74HC242 will be identified as the CD74HC242E.

High-Speed CMOS Logic



Octal-Bus Transceiver, 3-State, Non-Inverting

Type Features:

- Buffered inputs
- 3-State outputs
- Bus line driving capability
- Typical propagation delay (A \leftarrow >B) 9 ns @ V_{CC} = 5V, C_L = 15 pF, T_A = 25° C

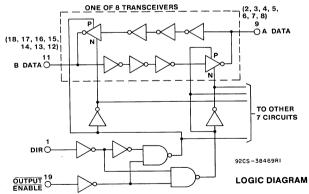
FUNCTIONAL DIAGRAM

The RCA-CD54/74HC245 and CD54/74HCT245 are highspeed octal 3-state bidirectional transceivers intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation while driving large bus capacitances. They provide the low power consumption of standard CMOS circuits with speeds and drive capabilities comparable to that of LSTTL circuits.

The CD54/74HC245 and CD54/74HCT245 allow data transmission from the A bus to the B bus or from the B bus to the A bus. The logic level at the direction input (DIR) determines the direction. The output enable input (\overline{OE}), when high, puts the I/O ports in the high-impedance state.

The HC/HCT245 is similar in operation to the HC/HCT640 and the HC/HCT643.

The CD54HC245 and CD54HCT245 are supplied in 20-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC245 and CD74HCT245 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). Both devices are also available in chip (H suffix) form.



Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:
 - 2 to 6 V Operation
 - High Noise Immunity:
 - $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5 \ V$
- CD54HCT/CD74HCT Types:
 - 4.5 to 5.5 V Operation
 - Direct LSTTL Input Logic Compatibility
 - $V_{\rm IL} = 0.8 \ V \ Max., \ V_{\rm IH} = 2 \ V \ Min.$ CMOS Input Compatibility
 - $I_1 \le 1 \, \mu A \otimes V_{OL}, V_{OH}$

	TRUTH TABLE										
	CON		OPERATION								
ſ	ŌĒ	DIR	OI EIIATION								
Ī	L	L	B DATA TO A BUS								
Ī	L	Н	A DATA TO B BUS								
Ī	Н	Х	ISOLATION								

H = high level, L = low level, X = irrelevant

To prevent excess currents in the High-Z (Isolation) modes all I/O terminals should be terminated with 10K Ω to 1M Ω resistors.

MAXIMUM RATINGS, Absolute-Maximum Values:

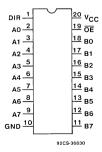
C SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)0.5 to +	- 7 V
C INPUT DIODE CURRENT, I _{IK} (FOR $V_i < -0.5 \text{ V OR } V_i > V_{CC} + 0.5 \text{V}$)	0mA
C OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)	0mA
C DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V)	5mA
C V _{CC} OR GROUND CURRENT (I _{CC})	0mA
OWER DISSIPATION PER PACKAGE (P_D):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	
For T _A = -55 to +100° C (PACKAGE TYPE F, H)) mW
For T _A = +100 to +125° C (PACKAGE TYPE F, H)) mW
For T _A = -40 to +70° C (PACKAGE TYPE M)) mW
For T _A = +70 to +125°C (PACKAGE TYPE M) Derate Linearly at 6 mW/°C to 70	
PERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	25° C
PACKAGE TYPE E, M	85° C
TORAGE TEMPERATURE (T _{stg})65 to +15	50° C
EAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	5° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	00°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	ITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	v
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

		CE	74H	245/	CD54	нст2	45				CD74HC245/CD54HCT245									
CHARACTERISTIC	COI	TEST NDITIONS		1	IC/54		l	HC PE	541 TY	HC PE	TEST			CT/54 TYPE:			ICT PE	54H TY	ICT PE	UNITS
OTATIA OTE III OTI	V,	I _o	V _{cc}		+25° C	;		0/ 6° C		5/ 5°C	V,	V _{cc}	+25°C		;	-40/ +85° C		-55/ +125°C		
				Min	Тур	Max	Min	Max	Min	Max		ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	-	1.5	_	1	4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	_	2	_	l v
		1	6	4.2	_	-	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}		1	4.5	_	_	1.35	_	1.35	_	1.35	-	to	_	_	0.8	_	0.8	_	0.8	v
			6	_	-	1.8	_	1.8	_	1.8	1	5.5							}	1
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	V _{IL}					-				
Output Voltage V _{он}	or	-0.02	4.5	4.4		_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads	VIH	1	6	5.9	-	_	5.9	_	5.9	_	V _{IH}						i			1
	VIL										V _{IL}									
TTL Loads	or	-6	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	V
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2	_	VIH									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	_	0.1		0.1	_	0.1	v
CMOS Loads	V _{IH}	1	6	_	_	0.1	_	0.1	_	0.1	V _{IH}						}			
	VIL										V _{IL}									
TTL Loads	or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	-	0.33	_	0.4	V
(Bus Driver)	V _{IH}	7.8	6	_	_	0.26	_	0.33	_	0.4	V _{IH}		i		i			l		
Input Leakage	V _{cc}										Any									
Current I,	or		6	_	_	±0.1	_	±1	_	±1	Voltage Between	5.5	-	_	±0.1	-	±1	_	±1	μΑ
	Gnd										V _{cc} & Gnd									1
Quiescent	V _{cc}										Vcc									
Device	or	0	6	_	-	8	-	80	_	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load \(\Delta \limit{\log lcc}^* \)											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-State	V _{1L}	V _o = V _{CC}									V _{IL}				_					
Leakage Current	or	or	6	_	_	±0.5	_	±5.0	_	±10	or	5.5	_	_	±0.5	_	±5.0	_	±10	μA
loz	V _{IH}	Gnd									V _{IH}									

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
A _n or B _n	0.4
ŌĒ	1.5
DIR	0.9

^{*}Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, Input t_s, t_t = 6 \text{ ns}$)

CHARACTERISTIC		CL	TYP	ICAL	UNITS
CHARACTERISTIC		(pF)	нс	нст	UNITS
Propagation Delay	t _{PHL}	15	9	10	
Data to Output	t _{PLH}	13	9	10	ns
Enable to High-Z	t _{PHZ} , t _{PLZ}	15	12	12	ns
Enable from High-Z	t _{PZH} , t _{PZL}	15	12	13	ns
Power Dissipation Capacitance*	СРД		53	55	pF

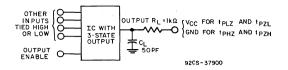
^{*}C_{PD} determines the no-load dynamic power consumption per channel. It is obtained by the following relationship:

SWITCHING CHARACTERISTICS (Input t, t = 6 ns, CL = 50 pF)

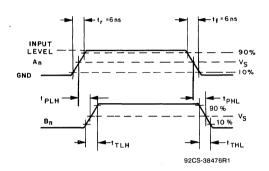
		TEST	LIMITS												
CHARACTERISTIC		CONDITION		25	25°C -40°C to +85°C						-5				
		Vcc	HC		н	нст		74HC		74HCT		54HC		1CT	UNITS
		V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	110		_	_	140	_	_	_	165	_		
Data to Output	t_{PHL}	4.5	_	22	—	26	_	28	_	33	_	33	_	39	ns
		6		19				24	_			28			
Propagation Delay	t _{PLZ}	2	_	150	_	_	_	190	_	—	_	225	_	<u> </u>	
Output Disable		4.5	—	30	_	30	_	38	_	38	_	45	—	45	ns
to Output	t _{PHZ}	- 6	<u> </u>	26		_	_	33	_		_	38			
Propagation Delay	t _{PZL}	2	-	150	—	—	_	190	_	-	_	225	_	—	
Output Enable		4.5		30	_	32	_	38	_	40	_	45	_	48	ns
to Output	t _{PZH}	6		26			_	33	_	—	_	.38	_	-	
Output Transition	t _{TLH}	2	_	60	_	-	_	75		_	_	90	_	_	
Time	t_{THL}	4.5	_	12	—	12	-	15	_	15	l —	18		18	ns
		6		10			_	13				15	_		
Input Capacitance	Cı	_	-	10	-	10	_	10	_	10	_	10	_	10	pF
3-State Output Capacitance	C _o	_	_	20	_	20	_	20	_	20	_	20	_	20	pF

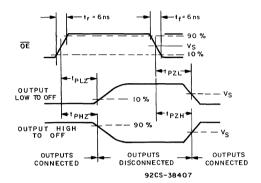
 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where $f_i = input$ frequency,

C_L = output load capacitance, V_{CC} = supply voltage



Three-state propagation delay test circuit.





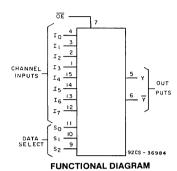
	54/74HC	54/74HCT
Input Level	Vcc	3V
Switching Voltage, V _s	50% V _{CC}	1.3 V

Fig. 1 - Transition times and propagation delay times.

File Number 1489

Advance Information/ Preliminary Data

High-Speed CMOS Logic



8-Input Multiplexer; 3-State

Type Features:

- Selects one of eight binary data inputs
- 3-state output capability
- True and complement outputs
- Typical (data to output) propagation delay of 14 ns @ V_{CC}=5 V. C_L=15 pF, T_A=+25° C

The RCA-CD54/74HC251 and CD54/74HCT251 are 8-channel digital multiplexers with 3-state outputs, fabricated with high-speed silicon-gate CMOS technology. Together with the low power consumption of standard CMOS integrated circuits, they possess the ability to drive 10 LSTTL loads. The 3-state feature makes them ideally suited for interfacing with bus lines in a bus-oriented system.

This multiplexer features both true (Y) and complement $\overline{(Y)}$ outputs as well as an output enable $\overline{(OE)}$ input. The \overline{OE} must be at a low logic level to enable this device. When the \overline{OE} input is high, both outputs are in the high-impedance state. When enabled, address information on the data select inputs determines which data input is routed to the Y and Y outputs. The CD54/74HCT251 logic family is speed, function, and pin-compatible with the standard 54LS/74LS251.

The CD54HC251 and CD54HCT251 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC251 and CD74HCT251 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- Alternate Source is Prinips/Signetics
 CD54HC/CD74HC Types:
 2 to 6 V Operation
 High Noise Immunity:
 N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types:

 4.5 to 5.5 V Operation

 Direct LSTTL Input Logic Compatibility

 V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.

 CMOS Input Compatibility

 I_I ≤ 1 µA @ V_{OL}, V_{OH}

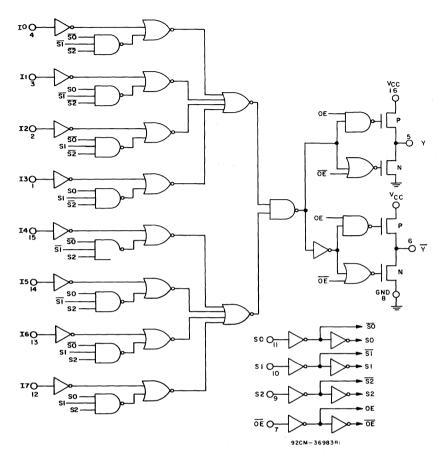


Fig. 3 - Logic diagram for HC/HCT251.

TRUTH TABLE

	ii ii	NPUTS		OUTP	UTS
	SELECT		OUTPUT		$\overline{}$
S2	S1	S0	CONTROL OE		
Х	X	Х	Н	Z	Z
L	L	L	L	10	10
L	L	Н	L	¹ 1	11
L	Н	L	L	12	12
L	Н	Н	L	lβ	lз
Н	L	L	L	14	14
H	L	Н	L	15	15
H	н	L	L	¹ 6	16
∫ н	Н	н	L	17	17

H = high logic level

L = low logic level

X = irrelevant

Z = high impedance (off)

 $I_0, I_1 \dots I_7$ = the level of the respective input

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 \
DC INPUT DIODE CURRENT, I_{IK} (FOR V_i $<$ -0.5 V OR V_i $>$ V_{CC} +0.5V) $\ldots\ldots\ldots$	±20mA
DC OUTPUT CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V)	±25mA
DC Vcc OR GROUND CURRENT (Icc)	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mV
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mV
For T _A = +70 to +125°C (PACKAGE TYPE M)	
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERIOTIC	LIN	LINUTE			
CHARACTERISTIC	MIN.	MAX.	UNITS		
Supply-Voltage Range (For T _A =Full Package Temperature Range)					
V _{cc} :*]				
CD54/74HC Types	2	6	v		
CD54/74HCT Types	4.5	5.5	V		
DC Input or Output Voltage Vin, Vout	0	V _{cc}	V		
Operating Temperature T _A :					
CD74 Types	-40	+85	°C		
CD54 Types	-55	+125	°C		
Input Rise and Fall Times tr, tr					
at 2 V	0	1000	ns		
at 4.5 V	0	500	ns		
at 6 V	0	400	ns		

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		c	:D74H	C251	/CD54	HC2	i1		CD74HCT251/CD54HCT251								251			
		TEST NDITIONS			IC/54		741 TYF			HC PES	TEST CONDITIO		1	CT/54			ICT PES		ICT PES	UNITS
CHARACTERISTIC	V,	l _o	V _{cc}		+25° C	;	-4 +85		-5 +12	5/ 5° C	V ,	V _{cc}	+25° C		;	-40/ +85° C		-5 +12	5/ 5°C	ONITS
	V	mA	\ \	Min	Тур	Max	Min	Max	Min	Max	V	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	-	2	_	v
			6	4.2	_	-	4.2	_	4.2	-		5.5							!	
Low-Level			2	-	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	-	-	1.35	_	1.35	_	1.35	_	to	_	_	0.8	_	0.8	_	0.8	v
			6	-	<u> </u>	1.8	_	1.8	-	1.8	Ì	5.5								
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	-	4.4		4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads	VIH		6	5.9	_	-	5.9	_	5.9	-	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	4 .	4.5	3.98	-	_	3.84	-	3.7	-	or	4.5	3.98	_	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	-	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	-	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage V _{oL}	or	0.02	4.5	-	_	0.1	_	0.1	_	0.1	or	4.5	-	_	0.1	_	0.1	_	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	4	4.5	-	_	0.26	_	0.33	-	0.4	or	4.5	-	-	0.26	-	0.33		0.4	v
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any									
Current I,	or		6	-	_	±0.1	_	±1	_	±1	Voltage Between	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										V _{cc} & Gnd									
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	_	8	-	80	_	160	or	5.5	-	_	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load Δ lcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-State Leakage Current	V _{IL} or V _{IH}	V _o = V _{cc} or Gnd	6	_	_	±0.5	_	±5.0	_	±10	V _{IL} or V _{IH}	5.5	_	_	±0.5	_	±5.0	_	±10	μА

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
S0, S1, S2	0.55
10-17	0.5
ŌĒ	2.65

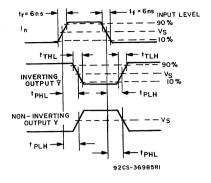
SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r , = t_f = 6 ns)

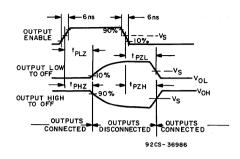
CHARACTERISTIC	SYMBOL	CL	TYP	ICAL	UNITS
CHARACTERISTIC	STNIBOL	(pF)	НС	HCT	UNITS
Propagation Delay	t _{PHL}	15	21	18	ns
Select to Outputs	t _{PLH}	13	21	,,,	113
Data to Outputs		15	12	12	ns
Enable to High-Z and	t _{PLZ} , t _{PHZ}	15	11	12	
Enable from High-Z	t _{PZL} , t _{PZH}	15	''	12	ns
Power Dissipation Capacitance*	C _{PD}	_	60	60	pF

* C_{PD} is used to determine the dynamic power consumption, per package. PD = $V_{Cc}^2 f$, $(C_{PD} + C_L)$ where f_1 = input frequency C_L = output load capacitance V_{CC} = supply voltage

SWITCHING CHARACTERISTICS (C_L = 50 pF, input t_r, = t_f = 6 ns)

			25° C			-4	0°C to	o +85°	С	-5					
CHARACTERISTIC	SYMBOL	Vcc	HC		HCT		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	-	245	_	_	_	305	_	_	_	370	_	-	
Select to Ouputs	t _{PHL}	4.5	-	49	-	42	l —	61	—	53	_	74	_	63	ns
		6	—	42	_	—	<u> </u>	52	_		_	63	_		
Propagation Delay	t _{PLH}	2	_	175	_	_	_	220	_	_	_	265		_	
Data to Outputs	t _{PHL}	4.5	_	35	_	35	_	44	—	44	_	53		53	ns
		6	—	30			-	37	—			45	_	· —	
Propagation Delay		2	T-	140	_	_	_	175		_	_	210			
Enable to High Z &	t _{PLZ} , t _{PHZ}	4.5	l —	28	_	30	_	35	-	38		42		45	ns
Enable From High Z	t _{PZL} , t _{PZH}	6		24		-	l —	30	-	_	_	36	—		
Output Transition	t _{TLH}	2	_	75	_		_	95	_	_	-	110	_	<u> </u>	
Time	t _{THL}	4.5		15	_	15	_	19	—	19		22		22	ns
		6	l —	13	l —	_	_	16	—	_	_	19	_		
Input Capacitance	Cı		_	10		10		10		10		10		10	pF
3-State Output				4.5		1.5		1.5		1.5		4.5		15	_
Capacitance	Co		_	15	_	15		15	_	15	_	15	_	15	pF





	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
V _s	50% V _{cc}	1.3 V

Fig. 1 - Transition times and propagation delay times.

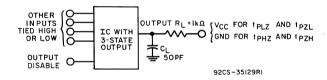
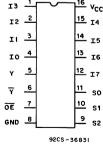
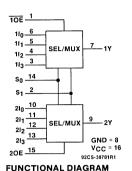


Fig. 2 - Three-state propagation delay test circuit.



High-Speed CMOS Logic



Dual 4-Input Multiplexer

Type Features:

- Common select inputs
- Separate output-enable inputs
- 3-state outputs

The RCA-CD54/74HC253 and CD54/74HCT253 are dual 4-to-1 line selector/multiplexers having 3-state outputs. One of four sources for each section is selected by the common select inputs, S0 and S1. When the output enable ($\overline{10E}$ or $\overline{20E}$) is HIGH, the output is in the high-impedance state.

The CD54HC253 and CD54HCT253 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC253 and CD74HCT253 are in 16-lead dual-in-line plastic packages (E suffix), also in 16-lead dual-in-line surface mount plastic packages (M suffix). These types are also available in chip form (H suffix).

TRUTH TABLE

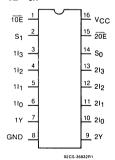
	ect uts		Data I	Inputs	3	Output Enable	Output
S1	S0	I _o	l ₁ l ₂		I ₃	ŌE	Y
X	Х	Х	Х	Х	Х	Н	Z
L	L	L	Χ	Χ	Χ	L	L
L	L	Н	Χ	Χ	Х	L	н
L	Н	Х	L	Χ	Χ	L	L
L	Н	Х	Н	Χ	Χ	L	н
Н	L	X	Χ	L	Χ	L	L
Н	L	х	Χ	Н	Χ	L	н
Н	Н	х	Χ	Χ	L	L	L
ļН	Н	x	Χ	Χ	Н	L	Н

Select inputs S0 and S1 are common to both sections. H = high level, L = low level, X = irrelevant, Z = high impedance (off).

Family Features:

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}=30%, N_{IH}=30% of V_{cc}; @ V_{cc}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility

 $I_1 \leq 1 \ \mu A \ @ \ V_{OL}, \ V_{OH}$



TERMINAL ASSIGNMENT

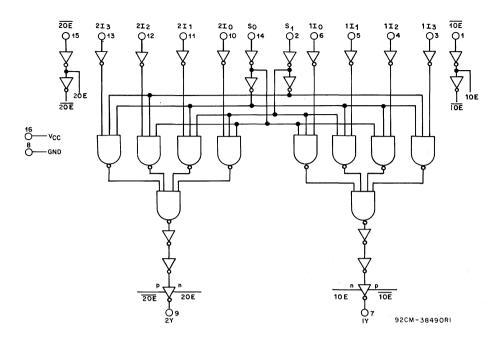


Fig. 1 - Logic diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)	
DC DRAIN CURRENT, PER OUTPUT (I ₀) (FOR -0.5 V < V ₀ < V _{0c} +0.5 V)	±35 mA
DC V _{CC} OR GROUND CURRENT, (I _{CC})	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	. Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	. Derate Linearly at 8 mW/° C to 300 mW
For $T_A = -40$ to $+70^{\circ}$ C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	. Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	•
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (T _{sto})	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79 \text{ mm})$ from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C
with solder soldering road apositiff the transfer of the trans	

STATIC ELECTRICAL CHARACTERISTICS

				CD	74HC	253/0	D54F	1C253	3				CD7	HCT	253/C	D54H	CT25	i3			
014040750074-		i	TEST DITION	74HC/54HC TYPES			74HC TYPE		54HC TYPE		TEST CONDITIONS		74HC	TYPE		74HCT TYPE		54H TY			
CHARACTERISTI	CHARACTERISTIC		Io	Vcc	+25° C			-40/ +85° C		-55/ +125°C		Vı	Vcc	+25° C			-40/ +85°C		-55/ +125° C		UNITS
		٧	mA	٧	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level	V _{IH}			2 4.5	1.5 3.15	=	_	1.5 3.15	_	1.5 3.15	_	_	4.5 to	2	_	_	2	_	2	_	V
				6	4.2		-	4.2	_	4.2	-		5.5				_		_		
Low-Level Input Voltage	VIL			4.5	_	_	1.35	<u> </u>	1.35	<u> </u>	1.35	` _	4.5 to	_	_	0.8	_	0.8	_	0.8	v
				6	_	_	1.8		1.8	_	1.8		5.5								
High-Level Output Voltage	V _{он}	V _{IL}	-0.02	2 4.5	1.9	_	=	1.9	_	1.9 4.4	_	V _{IL}	4.5	4.4	_	_	4.4	-	4.4	_	v
CMOS Loads		V _{IH}		6	5.9		 - -	5.9		5.9	-	V _{IH}		┼							
TTL Loads		V _{IL}	-6	4.5	3.98	_	_	3.84	_	3.7	_	V _{IL} or	4.5	3.98	_	-	3.84	_	3.7	_	V
Bus Driver		V _{IH}	-7.8	6	5.48		_	5.34	_	5.2		V _{IH}		↓		_	-	ļ		_	
Low-Level Output Voltage	Vol	V _{IL}	0.02	2 4.5	<u>-</u>	=	0.1	_	0.1	_	0.1	V _{IL} or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads		VIH		6	_	_	0.1	_	0.1	_	0.1	V _{IH}		ļ	_			-		-	
TTL Loads		V _{IL} or	6	4.5	_	_	0.26	_	0.33	_	0.4	V _{IL}	4.5	-	_	0.26	-	0.33	-	0.4	v
Bus Driver Input Leakage Current	l ₁	V _{IH} V _∞ or Gnd	7.8	6	-	_	±0.1	_	±1	_	±1	V _{IH} Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1		±1	μΑ
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6	_		8	_	80	_	160	V _{cc} or Gnd	5.5	_	_	8	_	80	_	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	Δlcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-State Leakage Current	loz	V _{IL} or V _{IH}	V _o = V _{cc} or Gnd	6	_	_	±0.5	_	±5	_	±10	V _{IL} or V _{IH}	5.5	_	_	±0.5	_	±5	_	±10	μА

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
11 ₀ -11 ₃ , 21 ₀ -21 ₃	0.4
1E ₀ , 2E ₀ , S ₀ , S ₁	1 1

^{*}Unit Load is Δ I $_{CC}$ limit specified in Static Characteristics Chart, e.g., 360 μA max. @ 25° C.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	AITS	LINUTE	
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A =Full Package Temperature Range)				
V _{cc} :*		-		
CD54/74HC Types	2	6	l .,	
CD54/74HCT Types	4.5	5.5	V	
DC Input or Output Voltage, V _I , V _O	0	V _{cc}	V	
Operating Temperature, T _A :				
CD74 Types	-40	+85	°c	
CD54 Types	-55	+125	1	
Input Rise and Fall Times, t _r ,t _f :				
at 2 V	0	1000	1	
at 4.5 V	0	500	ns	
at 6 V	0	400	1	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25°C, Input t_r,t_r=6 ns)

CHARACTERISTIC	C _L	SYMBOL	1	ICAL .UES	UNITS
	pF		HC	НСТ	
Propagation Delay					
Select to Outputs	15	t _{PHL}	14	16	
Data to Outputs		t _{PLH}			ns
Output Enabling Time	15	t _{PZL} , t _{PZH}	9	12	
Output Disabling Time	15	t _{PLZ} , t _{PHZ}	12	12	
Power Dissipation Capacitance*		C _{PD}	46	52	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per multiplexer.

C_L=load capacitance

Vcc=supply voltage

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,t=6 ns)

			T	25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	VCC	Н	C	H	СТ	74	НС	74F	ICT	54HC		54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	175		_		220	_	-	_	265	_	_	
Select to Outputs	t _{PHL}	4.5	-	35	-	40	_	44	-	50	—	53	-	60	
		6	—	30	_	-		37	—	<u> </u>	_	45	_	—	
Propagation Delay	t _{PLH}	2	T —	175	_	_	_	220	_	_	_	265	_		}
Data to Outputs	t _{PHL}	4.5	_	35	_	38	—	44		48		53	l —	57	
		6	_	30	_	-	_	37	_	_	_	45	_	-	
Disable Delay	t _{PHZ}	2		150		_		190	_	_	_	225	_	_	ns
Times	t _{PLZ}	4.5		30	_	30	_	38	_	38	_	45	_	45	
		6	_	26	_		_	33	l —	_	_	38		 -	
Enable Delay	t _{PZH}	2	_	110		_	_	140	_	_	_	165	_	_	1
Times	t _{PZL}	4.5	l —	22	_	30	_	28	_	38	_	33	_	45	ns
		6	_	19	i —	_	l —	24		l —	_	28	l —	—	
Output Transition	t _{TLH}	2	_	60	_	_	_	75	_	_	_	90		_	
Time	t _{THL}	4.5	_	12	_	12	l —	15	_	15		18	_	18	
·		6	_	10		—	-	13		_	_	15	—	-	
Input Capacitance	Cı		_	10	_	10		10	_	10	_	10	_	10	
3-State Output	Co	_	_	20	_	20	_	20		20	<u>-</u>	20	_	20	pF
Capacitance												L			

 $P_D=V_{CC}^2$ fi $(C_{PD}+C_L)$ where: fi=input frequency

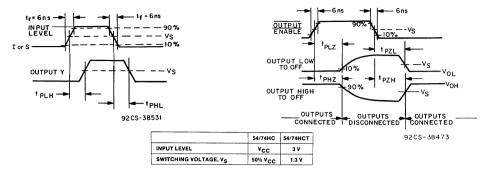


Fig. 2 - Transition and propagation delay times.

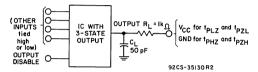
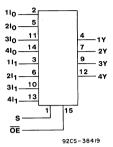


Fig. 3 - Three-state propagation delay test circuit.

High-Speed CMOS Logic



Quad 2-Input Multiplexer with 3-State Non-Inverting Outputs

Type Features:

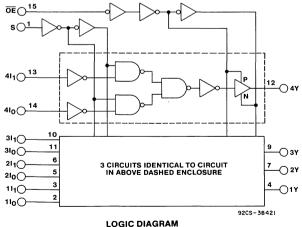
- Buffered Inputs
- Typical Propagation Delay (In to Output) = 12 ns @ V_{CC} = 5v, C_L = 15pF, T_A = 25° C

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC257 and CD54/74HCT257 are quad 2-input multiplexers which select four bits of data from two sources under the control of a common Select input (S). The Output Enable input (OE) is active LOW. When OE is HIGH, all of the outputs (1Y-4Y) are in the high impedance state regardless of all other input conditions.

Moving data from two groups of registers to four common output busses is a common use of the 257. The state of the Select input determines the particular register from which the data comes. It can also be used as a function generator.

The CD54HC257 and CD54HCT257 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC257 and CD74HCT257 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH}= 30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL} V_{OH}

FUNCTION TABLE

Output Enable	nable Input Inputs					
ŌĒ	S	10	11	Y		
Н	х	X	Х	Z		
L	L	L	X	L		
L	L	нх		Н		
L	н	X	L	L		
L	н	X	Н	Н		

H = High level voltage

L = Low level voltage

Z = High impedance (off) state.

X = Don't care

MAXIMUM RATINGS, Absolute-Maximum Values:

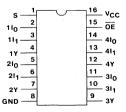
DO CHERLY VOLTAGE (V.).	
DC SUPPLY-VOLTAGE, (Vcc):	054-171
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, $I_{i\kappa}$ (FOR $V_i < -0.5 \text{ V OR } V_i > V_{CC} + 0.5 \text{V}$)	
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5V)	
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	
DC V _{cc} OR GROUND CURRENT (I _{cc})	±70mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	LINUTG	
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*				
CD54/74HC Types	2	6	V	
CD54/74HCT Types	4.5	5.5	\ \ \	
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V	
Operating Temperature T _A :				
CD74 Types	-40	+85	l ∘c	
CD54 Types	-55	+125		
Input Rise and Fall Times t _r , t _f				
at 2 V	0	1000		
at 4.5 V	0	500	ns	
at 6 V	0	400	ł	

^{*}Unless otherwise specified, all voltages are referenced to Ground.



92CS-38420RI

STATIC ELECTRICAL CHARACTERISTICS

		C	D74H	C257	CD54	HC2	57		_			CD	74HC	T257	/CD54	нст	257			
CHARACTERISTIC		TEST NDITIONS			IC/54 ERIE		74 SEF		54I SEF		TEST CONDITIO			CT/54 ERIE		74F SER	ICT	54H SER	ICT	UNITS
on an area of the second	V, V	l _o mA	V _{cc}		+25° C	;		0/ i° C	-5 +12		۷ _.			+25° C	;	-4 +85	0/ 5°C	-5 +12	5/ 5°C	014113
			,	Min	Тур	Max	Min	Max	Min	Max			Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_		1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	. —		3.15	_	3.15	-	-	to	2	-	-	2	-	2	-	v
			6	4.2			4.2		4.2	-		5.5								
Low-Level			2	-	_	0.5	_	0.5		0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35] –	to	-	-	0.8	–	0.8	-	0.8	v
			6	_	_	1.8	-	1.8	_	1.8		5.5			-					
High-Level	V _{IL}		2	1.9	_	-	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	–		4.4	_	4.4	_	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-6	4.5	3.98	_	_	3.84	-	3.7	_	or	4.5	3.98	-	_	3.84	_	3.7	_	. v
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	-	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage V _{OL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-		0.1		0.1	-	0.1	v
CMOS Loads	ViH		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	6	4.5	_		0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	-	0.33		0.4	v
(Bus Driver)	· V _{IH}	7.8	6	_		0.26	-	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any						-			
Current I _i	or		6	-	-	±0.1	_	±1	_	±1	Voltage Between	5.5	-		±0.1	_	±1	-	±1	μΑ
	Gnd										V _{cc} & Gnd									
Quiescent	V _{cc}										Vcc									
Device	or	0	6	_	-	8	-	80	_	160	or	5.5	-	-	8	_	80	_	160	μΑ
Current I _{cc}	Gnd						1				Gnd									
Additional Quiescent Device Current per input pin: 1 unit load \(\Delta \limit{\lambda \lcc^*} \)				-							V _{cc} -2.1	4.5 to 5.5	_	100	360	-	450	_	490	μΑ
3-State	V _{IL}	V _o = V _{CC}									V _{IL}		†		1					
leakage	or	or	6	_	l	±0.5	_	±5	_	±10	or	5.5	_	_	±0.5	_	±5	_	±10	μΑ
current loz	V _{IH}	Gnd		ļ							V _{II}									

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA. **HCT Input Loading Table**

Input	Unit Loads*
Data	0.95
S	3
ŌĒ	0.6

^{*}Unit Load is $\Delta l_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu{\rm A}$ max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

CHARACTERISTIC	CL	SYMBOL	TYP	ICAL	UNITS
CHARACTERISTIC	(pF)	STMBOL	НС	НСТ	ONITS
nl ₀ , nl ₁ , to Y	15	t _{PHL} t _{PLH}	12	13	ns
ŌĒ to Y	15	t _{PZL} t _{PZH} t _{PLZ} t _{PHZ}	12	12.	ns
S to Y	15	t _{PHL} t _{PLH}	14	16	ns
Power Dissipation Capacitance*	_	C _{PD}	45	45	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per multiplexer.

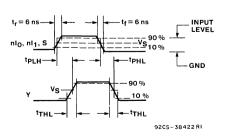
 $PD=V_{CC}^{2}$ fi $(C_{PD}+C_{L})$ where f_i=input frequency

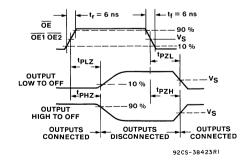
C_L = output load capacitance

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

				25	°C		-4	0°C to	o +85°	C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	C	Н	CT	74	НС	74F	ICT	54	НС	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2		150	_	_	-	190	_	_		225	<u> </u>	l –	
In to Y	t _{PHL}	4.5		30		33	—	_38	—	41	_	45	—	50	ns
(Fig. 2)		6		26	_	_	_	33		_	_	38			
Propagation Delay		2	-	175	—	_	_	220	_	<u> </u>	_	265	_	_	
S to Y	t _{PLH}	4.5	_	35	—	38	_	44	—	48		53	-	57	ns
(Fig. 2)	t _{PHL}	6	-	30	l — .	_	_	37		_	_	45	_	_	
Propagation Delay	t _{PLZ}	2	_	150	_	_		190	_		_	225	_	_	
OE to Y	t _{PZL}	4.5		30	l _	30		38		38	_	45	l	45	ns
(Fig. 3)	t _{PHZ} t _{PZH}	6	-	26	_	_	_	33	_	-	-	38	_	_	
Output Transition		2	<u> </u>	60		_		75			_	90		<u> </u>	
Time	t _{TLH}	4.5	_	12	_	12	_	15	l —	15	_	18	_	18	ns
(Fig. 2)	t _{THL}	6	_	10	-		_	13	_	_	_	15	_	_	
Input	0			10		40		40		40		40		40	
Capacitance	Cı		_	10	_	10	_	10	-	10	-	10	-	10	pF
3-State Output Capacitance	C _o		_	20	_	20	_	20	_	20	_	20	_	20	pF



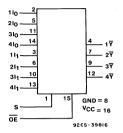


	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _s	50% V _{CC}	1.3 V

Fig. 2 - Inputs or select to output propagation delays and output transition times.

Fig. 3 - Output Enable to output propagation delays.

High-Speed CMOS Logic



Quad 2-Input Multiplexer with 3-State Inverting Outputs

Type Features:

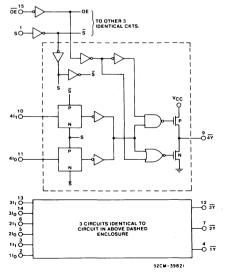
- Buffered inputs
- Typical CD54/74HC258 propagation delay = 7 ns @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC258 and CD54/74HCT258 are quad 2-input multiplexers which select four bits of data from two sources under the control of a common Select input (S). The Output Enable input $(\overline{\text{OE}})$ is active LOW. When $\overline{\text{OE}}$ is HIGH, all of the outputs $(\overline{\text{TY-4Y}})$ are in the high impedance state regardless of all other input conditions.

Moving data from two groups of registers to four common output busses is a common use of the 258. The state of the Select input determines the particular register from which the data comes. It can also be used as a function generator.

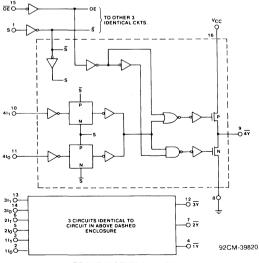
The CD54HC/HCT258 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/HCT258 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



CD54/74HC258 Logic Diagram

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT/HCU: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL} V_{OH}



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground)
DC INPUT DIODE CURRENT, I _{IK} (FOR V ₁ < -0.5 V OR V ₁ > V _{CC} +0.5V)
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5V)
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)
DC V _{CC} OR GROUND CURRENT (I _{CC}) ±70mA
POWER DISSIPATION PER PACKAGE (P₀):
For T _A = -40 to +60° C (PACKAGE TYPE E)
For T _A = +60 to +85°C (PACKAGE TYPE E)
For T _A = -55 to +100°C (PACKAGE TYPE F, H)
For T _A = +100 to +125° C (PACKAGE TYPE F, H)
For T _A = -40 to +70°C (PACKAGE TYPE M)
For T _A = +70 to +125°C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H55 to +125°C
PACKAGE TYPE E, M40 to +85° C
STORAGE TEMPERATURE (T _{stg})65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. +265° C +265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only +300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CUADACTEDICTIC	LIN	IITS	LINUTO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

FUNCTION TABLE

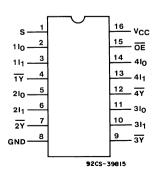
Output Enable	Select Input	l	ata outs	Output
ŌĒ	S	I ₀	11	Ÿ
Н	х	Х	Х	Z
L	L	L	Х	Н
L	L	Н	Х	L
L	н	X.	L	Н
l L	і н	l x	Н	L

H = High level voltage

L = Low level voltage

X = Don't care.

Z = High impedance (off) state



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

		С	D74H	C258/	CD54	HC25	8					CD	74HC	T258/	CD54	нст	258			
CHARACTERISTIC		TEST IDITIONS		ı	IC/54		741 TY		54I TY		TEST CONDITIO		1	T/54 YPES		74H TY		54H TY	- 1	UNITS
CHARACTERISTIC	V, V	I _o	V _{cc}		+25° C	;	-4 +85		-5: +12:		۷. ۷	V _{cc}	+25° C		:	-4 +85		-5 +12!	5/ 5°C	UNITS
	•	IIIA	•	Min	Тур	Max	Min	Max	Min	Max	,	•	Min	Тур	Max	Min	Max	Min	Max	
High-Level	LEMM		2	1.5		_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}		}	4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	_ ;	_	2	-	2	-	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	-	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	-	_	0.8	_	0.8		0.8	v
		ľ	6	_	_	1.8		1.8	_	1.8	l ·	5.5								
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	-	4.4		4.4	_	or '	4.5	4.4	_	_	4.4	Ì —	4.4	_	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9		V _{IH}					ļ				
	V _{IL}										V _{IL}									
TTL Loads	or	-6	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	-	v
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	_	0.1	VIL									
Output Voltage V _{OL}	or	0.02	4.5	-	-	0.1	_	0.1	-	0.1	or	4.5	-		0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	V _{IL}										VIL									
TTL Loads	or	6	4.5	_	-	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
(Bus Driver)	V _{IH}	7.8	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I _I	or		6	-	-	±0.1	-	±1	-	±1	Between	5.5	-	–	±0.1	-	±1	-	±1	μΑ
	Gnd								į		V _{cc} & Grid									
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	_	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load \(\Delta \lambda \lam							•				V _{cc} -2.1	4.5 to 5.5	-	100	360	-	450	_	490	μΑ
3-State	V _{IL}	Vo = Vcc									V _{IL}		†							
leakage	or	or	6	_	_	±0.5	_	±5	_	±10	or	5.5	_	_	±0.5	_	±5	-	±10	μΑ
current I _{oz}	V _{IH}	Gnd									V _{IH}		1							

^{*}For dual-supply systems theoretical worst case (V_i = 2.4 V, V_{cc} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
Data	0.5
s	1.5
ŌĒ	1.5

^{*}Unit Load is Δl_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERISTIC		CL	TYP	ICAL	UNITS
CHARACTERISTIC		(pF)	HC	нст	UNITS
nl₀, nl₁, to ₹	t _{PHL} t _{PLH}	15	7	11	ns
	t _{PZL} t _{PZH}				
ΘE to Y		15	11	11	ns
	t_{PLZ} t_{PHZ}	15	12	12	ns
S to \overline{Y}	t _{PHL} t _{PLH}	15	11	14	ns
Power Dissipation Capacitance*	C_{PD}	_	49	49	pF

^{*} C_{PD} is used to determine the dynamic power consumption, per multiplexer. $P_D = V_{CC}^2$ fi $(C_{PD} + C_L)$ where: fi = input frequency C_L = output load capacitance V_{CC} = supply voltage

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_t = 6 \text{ ns}$)

				25	°C		-4	0°C to	o +85°	С	-5				
CHARACTERISTIC		Vcc	Н	С	Н	СТ	74	нс	74HCT		54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	95	_	_	_	120	_	_	_	145	_	_	
nl_0 , nl_1 , to \overline{Y}	t _{PHL}	4.5	-	19	-	27	_	24	-	34	l —	29		41	ns
(Fig. 2)		6	<u> </u>	15	_	_	_	20			_	25	_	l —	
Propagation Delay		2	-	140	_	_	_	175	_	_	_	210	_	_	
S to \overline{Y}	t _{PLH}	4.5	_	28	<u> </u>	34	_	35	—	43	_	42	_	51	ns
(Fig. 3)	t _{PHL}	6	—	24	_		_	30	—	—	l —	36	_	_	
Propagation Delay		2		140	_	_	_	175	_	_	_	210	_	_	
OE to Y	t_{PZL}	4.5	-	28	_	28	_	35	_	35	_	42	_	42	ns
(Fig. 4)	t _{PZH}	6	_	24	_	_	_	30	l —		l —	36	_	_	
Propagation Delay	t _{PLZ}	2	_	150			_	190	_	_	_	225	_	_	
OE to Y		4.5	_	30	_	30	_	38	_	38	_	45	_	45	ns
(Fig. 4)	t _{PHZ}	6	_	26	_	l —	_	33	_	_	_	38	_	_	
Output Transition	t _{TLH}	2	<u> </u>	60	_		_	75	<u> </u>	Γ-	<u> </u>	90		Γ-	
Time	t _{THL}	4.5	_	12	_	12	_	15	_	15	_	18	_	18	ns
(Fig. 2)		6	_	10	_	_	_	13	-	-	_	15	_	-	
Input				10		10		10		10		10		10	
Capacitance	Cı		-	10	_	10	_	10	_	10	_	10	_	10	pF
3-State Output				00		00		20		00		00		-00	
Capacitance	C ₀			20	_	20	_	20		20		20		20	pF

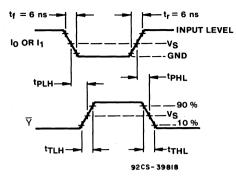


Fig. 2 - Select to output delays.

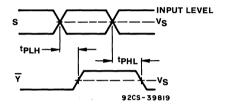


Fig. 3 - Select to output propagation delays.

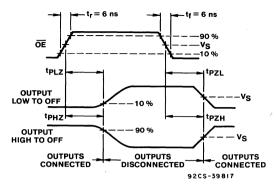
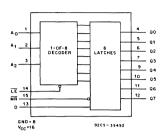


Fig. 4 - Output Enable to output propagation delays.

	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _S	50% V _{CC}	1.3 V

High-Speed CMOS Logic



8-Bit Addressable Latch

Type Features:

- Buffered inputs and outputs
- Four operating modes
- Typical propagation delay of 15 ns @ $V_{CC} = 5 V$, $C_L = 15 pF$, $T_A = +25^{\circ} C$

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC259 and CD54/74HCT259 Addressable Latch features the low-power consumption associated with CMOS circuitry and has speeds comparable to lowpower Schottky.

This latch has three active modes and one reset mode. When both the Latch Enable ($\overline{\text{LE}}$) and Master Reset ($\overline{\text{MR}}$) inputs are low (8-line Demultiplexer mode) the output of the addressed latch follows the Data input and all other outputs are forced low. When both $\overline{\text{MR}}$ and $\overline{\text{LE}}$ are high (Memory Mode), all outputs are isolated from the Data input, i.e., all latches hold the last data presented before the $\overline{\text{LE}}$ transition from low to high. A condition of $\overline{\text{LE}}$ low and $\overline{\text{MR}}$ high (Addressable Latch mode) allows the addressed latch's output to follow the data input; all other latches are unaffected. The Reset mode (all outputs low) results when $\overline{\text{LE}}$ is high and $\overline{\text{MR}}$ is low.

The CD54HC259 and CD54HCT259 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC259 and CD74HCT259 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads
- Bus driver outputs 15 LSTTL loads
 Wide operating temperature range:
 CD74HC/HCT: -40 to +85°C
- Balanced propagation delay and transition times
 Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL} = 30%, N_{IH} = 30% of V_{cc}; @ V_{cc} = 5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL} = 0.8 V max., V_{IH} = 2 V min. CMOS input compatibility I_I≤ 1 μA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{ik} (FOR $V_i < -0.5$ V OR $V_i > V_{cc} + 0.5$ V)	
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For $T_A = -40$ to $+60^{\circ}$ C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	
For $T_A = -40$ to $+70$ °C (PACKAGE TYPE M)	
For $T_A = +70$ to $+125$ °C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	265° C
Unit inserted into a PC board (min. thickness 1/16 in., 1.59 mm) with solder contacting lead	tips only300° C

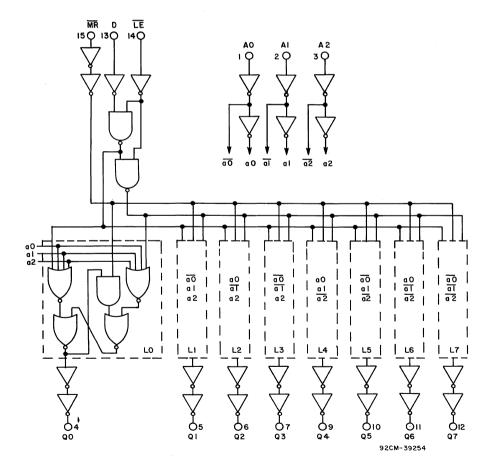


Fig. 1 - Logic diagram.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIM	ITS	LINUTO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply Voltage Range (For T _A = Full Package Temperature Range) V _{CC} : *			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	٧
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _r			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*} Unless otherwise specified, all voltages are referenced to Ground.

TRUTH TABLE

INP	UTS	0.4.1.4	5 1 0#	Function				
MR	LE	Output of Address Latch	Each Other Output	Function				
Н	L	D	Q_{io}	Addressable Latch				
Н	н	Q _{io}	Qio	Memory				
L	L	D	L	8-Line Demultiplexer				
L	Н	L	L	Reset				

H = High level L = Low level

LATCH SELECTION TABLE

Se	elect Inpu	uts	Latch
A 2	A1	Α0	Addressed
L	L	L	0
L	L	Н	1 -
L	Н	L	2
L	Н	Н	3
Н	L	L	4
Н	L	Н	5
Н	Н	L	6
Н	Н	Н	7

D = The level at the data input

 $[\]label{eq:Qio} \textbf{Q}_{io} = \text{The level of } \textbf{Q}_{i} \text{ (i = 0, 1...7, as appropriate) before} \\ \text{the indicated steady-state input conditions were} \\ \text{established.}$

STATIC ELECTRICAL CHARACTERISTICS

				CD7	4HC2	59, C	D54H	C259					CD7	4НСТ	259, (CD541	нст2	59			
CHARACTERISTIC		CON		74HC/54HC TYPES					HC PES	TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS		
		V ₁	lo	Vcc		+25° C	;	-4/ +85		-5 +12		V _I	Vcc		+25° C	;	1	0/ 5° C	-5 +12	5/ 5°C	UNITS
		v	mA	V	Min	Тур	Max	Min	Max	Min	Max	V	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	-		4.5								
Input Voltage	V_{1H}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	-	_	2		2	-	V
				6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level				2	_		0.5	_	0.5	_	0.5		4.5					1			
Input Voltage	V_{IL}		ļ	4.5	_	_	1.35	_	1.35		1.35		to	-	-	0.8	_	0.8		0.8	V
		<u> </u>		6	_	_	1.8	_	1.8	_	1.8		5.5	<u> </u>			ļ			L	
High-Level		VIL	l	2	1.9	_	ᆫ	1.9	_	1.9		VIL				ļ	Į.	l			
Output Voltage	V_{OH}	or	-0.02	4.5	4.4	_	<u> </u>	4.4	_	4.4	<u>L</u>	or	4.5	4.4	-	-	4.4	-	4.4	-	V
CMOS Loads		V _{IH}		6	5.9	_	-	5.9		5.9		V _{IH}		<u> </u>						ļ	
		VIL		L								V _{IL}		i	ļ	1		l			
TTL Loads		or	-4	4.5	3.98	_		3.84	_	3.7		or	4.5	3.98	-	-	3.84	-	3.7	-	V
		V _{IH}	-5.2	6	5.48	_	ļ —	5.34	_	5.2	_	V _{IH}		ļ.,,							
Low-Level		VIL		2		_	0.1	_	0.1	_	0.1	VIL		l		ŀ				l	
Output Voltage	Vol	or	0.02	4.5	<u> </u>	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	_	0.1	-	0.1	٧
CMOS Loads		V _{IH}		6	<u> </u>	_	0.1		0.1	_	0.1	V _{IH}		<u> </u>	<u> </u>	<u> </u>	<u> </u>	ļ		ļ	
		VIL		ļ	<u> </u>		ļ				ļ	VIL		1		l		l			
TTL Loads		or	4	4.5	-	_	0.26	-	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	_	0.4	V
		V _{IH}	5.2	6	-	_	0.26	_	0.33		0.4	V _{IH}	ļ	ļ	ļ	-		ļ	ļ	-	
Input Leakage		Vcc	İ	ļ		ļ						Any							ļ		
Current	h	or		6	_	_	±0.1	_	±1	l –	±1	Voltage	5.5	_	_	±0.1	_	±1	-	±1	μA
*		Gnd		1	İ	1					l	Between			1	1			ļ		
Outros		\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \	<u> </u>	-		-	-	_				V _{cc} & Gnd		-	-	├	+-	-	<u> </u>	-	
Quiescent		Vcc						_			100	Vcc				8	_	80	1	160	μΑ
Device Current	Icc	or Gnd	0	6	-	-	8	_	80	-	160	or Gnd	5.5	-	_	ľ	_	00	_	100	μ^
Additional		Gnd	Ь	L	<u> </u>	L	L	L			L	Gila		 				+	 	 	
Quiescent Device													4.5							1	
Current per input												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	∆l _{cc} *												5.5	1					ĺ		
pin. I unit ioad	TICC													ł	L	Ь	J			1	l

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads *
A0-A2, LE	1.5
D	1.2
MR	0.75

 $^{^{\}star}$ Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 $\mu \rm A$ max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc=5 V, T_A=25°C, Input t_r, t_f=6 ns)

		CL	TYP	ICAL		
CHARACTERISTIC	(pF)	нс	нст	UNITS		
Propagation Delay D to Q	t _{PLH} t _{PHL}	15	15	16	ns	
LE to Q		1	14	16	ns	
A to Q			15	17	ns	
MR to Q		15	13	16	ns	
Power Dissipation Capacitance*	C _{PD}	-	21	22	pF	

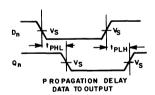
^{*} C_{PD} is used to determine the dynamic power consumption, per package. $P_D = C_{PD}V_{Cc}^2f_i + \Sigma C_LV_{Cc}^2f_o$ where f_i = input frequency, f_o = output frequency, C_L = output load capacitance, V_{CC} = supply voltage.

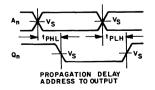
PRE-REQUISITE FOR SWITCHING FUNCTION

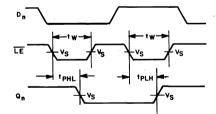
			LIMITS												
		TEST		25°C -40°C to +85°C -55°C to +125°C										°C	UNITS
CHARACTER	ISTIC		н	C	н	СТ	741	нс	74F	ЮТ	54	нс	54H	ICT	UNITS
		V _{cc} V	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	Min	Max	
Pulse Width	twL	2	70	_	_	_	90	_	_	-	105	-	-	_	
LE		4.5	14	-	18	-	18	_	23		21	_	27	_	ns
		6	12				15		_		18	<u> </u>			
		2	70	-	_	-	90	-	—	-	105	-	-	-	
MR	t_{WL}	4.5	14	<u> </u>	18	-	18	-	23	-	21	-	27	—	ns
		6	12			<u> </u>	15	_	_	_	18	_	<u> </u>		
Set-up Time	tsu	2	80	-	-	-	100	-	-	-	120	_	-	_	
D to LE		4.5	16	-	17	-	20	-	21	-	24	-	26	-	ns
		6	14				17				20			_	
		2	80	-	-	-	100	-	—	-	120	-	_	-	
A to LE	tsu	4.5	16	-	17	-	20	-	21	_	24	-	26	-	ns
		6	14				17	_	_		20			_	
Hold Time	tн	2	0	-	—	-	0	-	-	-	0	_	-	-	
D to LE		4.5	0	-	0	_	0	-	0	-	0	-	0	_	ns
		6	0				0	_	_		0	_	_	_	
		2	0	-	-	-	0	_	-	-	0	-	_	-	
A to LE	tн	4.5	0	-	0	-	0	-	0	-	0		0	-	ns
		6	0	_	-	-	0	-	-	_	0		_	-	

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_f = 6 \text{ ns}$)

								LIM	ITS						
		TEST		25	°C		-4	0°C to	+85°	С	-55° C to +125° C				UNITS
CHARACTERIS	STIC	CONDITION	н	С	н	нст		74HC		ICT	54HC		54HCT		UNIIS
		V _{cc}	Min	Max	Min	Мах	Min	Max	Min	Max	Min	Max	Min	Max	
Propagation	t _{PLH}	2	_	185	_	_	_	230	_	_		280	_	_	
Delay	t _{PHL}	4.5	_	37	_	39	—	46	_	49	_	56	_	59	ns
D to Q		6		31		_	_	39		<u> </u>	_	48		_	
		2	<u> </u>	170	_	_	-	215	—	_	_	255	_	_	
LE to Q		4.5	—	34	-	38	—	43	<u> </u>	48	_	51	_	57	ns
		6	_	29		_	_	37			_	43		_	
		2	_	185	_	_	_	230	_	_	_	280	_	_	
A to Q		4.5	_	37	-	41		46	-	51	-	56	—	61	ns
		6	_	31		_	_	39	_		_	48	_	_	
		2	_	155	-	_	_	195	_	-	-	235	_	-	
MR to Q		4.5	_	31	—	39	\	39	l —	49	-	47	-	59	ns
		6		26	_	_	_	33	—	_	-	40	_] —	
Output	t _{TLH}	2	_	75	_	_	_	95	_	_	_	110	-	-	
Transition	t_{THL}	4.5	_	15	_	15	_	19	—	19	-	22	-	22	ns
Time		6	_	13	_		_	16			_	19	_	<u> </u>	
Input	Cı														
Capacitance			_	10	-	10	_	10	_	10	-	10	_	10	pF





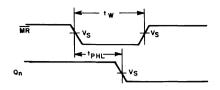


LATCH ENABLE PULSE WIDTH AND LATCH ENABLE TO OUTPUT PROPAGATION DELAY

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _s	50% V _{cc}	1.3 V

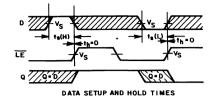
92CM-39256R1

Fig. 2 - AC Waveforms.



MR TO OUTPUT DELAY AND MR PULSE WIDTH

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V₃	50% V _{cc}	1.3 V



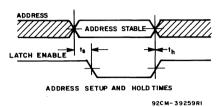
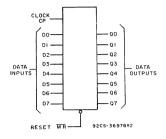


Fig. 3 - AC Waveforms.

High-Speed CMOS Logic



Octal D Flip-Flop with Reset

Type Features:

- Common clock and asynchronous master reset
- Positive-edge triggering
- Buffered inputs
- Typical $f_{\text{max}} = 60 \text{ MHz}$ @ $V_{\text{CC}} = 5 \text{ V}$, $C_{\text{L}} = 15 \text{pF}$, $T_{\text{A}} = 25^{\circ} \text{ C}$

FUNCTIONAL DIAGRAM

The RCA CD54/74HC273 and the CD54/74HCT273 high speed Octal D-Type Flip-Flops with a direct clear input are manufactured with silicon-gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits.

Information at the D input is transferred to the Q outputs on the positive-going edge of the clock pulse. All eight Flip-Flops are controlled by a common clock (CP) and a common reset (\overline{MR}). Resetting is accomplished by a low voltage level independent of the clock. All eight Q outputs are reset to a logic 0.

The CD54HC273 and CD54HCT273 are supplied in 20-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC273 and CD74HCT273 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: $N_{\rm IL}$ = 30%, $N_{\rm IH}$ = 30% of $V_{\rm CC}$ = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ V_{OL} V_{OH}

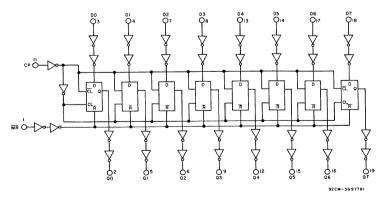


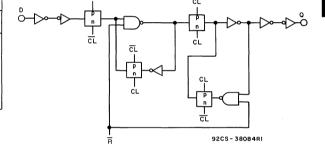
Fig. 1 - Logic diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground)
DC INPUT DIODE CURRENT, I_{IK} (FOR V; $<$ -0.5 V OR V; $>$ Vcc +0.5 V
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o $<$ -0.5 V OR V_o $>$ V_{CC} +0.5 V
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Vo $<$ Vo $<$ +0.5 V)
DC V _{cc} OR GROUND CURRENT, PER PIN (I _{cc}):
POWER DISSIPATION PER PACKAGE (P₀):
For T _A = -40 to +60° C (PACKAGE TYPE E)
For T _A = +60 to +85° C (PACKAGE TYPE E)
For T _A = -55 to +100°C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For T _A = -40 to +70° C (PACKAGE TYPE M)
For T _A = +70 to +125° C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H55 to +125° C
PACKAGE TYPE E, M40 to +85° C
STORAGE TEMPERATURE (Tstq)65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. +265° C +265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only+300°C

TRUTH TABLE (EACH FLIP-FLOP)

	INPUTS							
R <u>ESE</u> T (MR)	CLOCK CP	DATA Dn	Q					
L	х	х	L					
н	~	н	н					
н		L	L					
Н	L	х	Qo					



H = High Level (Steady State)

L = Low Level (Steady State)

X = Irrelevant

 — Transition from Low to High Level

Qo = The Level of Q Before the Indicated Steady-State Input Conditions were Established

Fig. 2 - Flip-Flop detail.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN			
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply Voltage Range (For TA = Full Package Temperature Range) VCC:*				
CD54/74HC Types	2	6	V	
CD54/74HCT Types	4.5	5.5	V	
DC Input or Output Voltage VI, VO	0	Vcc	٧	
Operating Temperature TA:				
CD74 Types	-40	+85	°C	
CD54 Types	-55	+125	°C	
Input Rise and Fall Times, tr, tr				
at 2 V	0	1000	ns	
at 4.5 V	0	500	ns	
at 6 V	0	400	ns	

*Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC273/CD54HC273							CD74HCT273/CD54HCT273													
		TEST CONDITIONS				74HC/54HC 74HC TYPES TYPES				54H TYI		TEST	ons		CT/54		74H TYI	ICT PES	54H TYI	ICT PES	UNITS	
CHARACTERIS	TIC	V, V	lo 	Vcc	,	25° C	;	-4 +85		-5 +12!		V. V	V _{cc}		+25° C			0/ 5°C	-5 +12	5/ 5°C	UNITS	
		٧	mA	٧.	Min	Тур	Max	Min	Max	Min	Max	,	V	Min	Тур	Max	Min	Max	Min	Max		
High-Level				2	1.5		_	1.5	_	1.5	_		4.5									
Input Voltage	ViH			4.5	3.15	_	_	3.15		3.15	_	-	to 5.5	2	-	_	2		2	-	٧	
				6	4.2		_	4.2		4.2	_											
Low-Level				2	_	_	0.5		0.5	_	0.5		4.5									
Input Voltage	VıL			4.5		_	1.35		1.35		1.35	_	to 5.5	-	-	8.0	-	0.8	-	0.8	٧	
				6	_	_	1.8	_	1.8		1.8					ļ						
High-Level		V _{IL}		2	1.9	_	_	1.9	_	1.9	_	VIL		ļ								
Output Voltage	V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	٧	
CMOS Loads		V _{IH}		6	5.9	-	_	5.9	_	5.9		У ^{îн}										
		VIL									_	VIL	l					ł				
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7		or	4.5	3.98	-	'	3.84	-	3.7	-	V	
		V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}		<u> </u>				_				
Low-Level		VIL		2		_	0.1	_	0.1	_	0.1	VIL										
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	٧	
CMOS Loads		V _{IH}		6	_		0.1	_	0.1	<u> </u>	0.1	ViH	ļ	_				1				
		VIL					<u> </u>					VIL										
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	<u> </u>	0.4	or	4.5	_	<u> </u>	0.26	-	0.33	-	0.4	V	
		V _{IH}	5.2	6	<u> </u>	_	0.26		0.33	_	0.4	V _{IH}						<u> </u>	<u> </u>	_		
Input Leakage		Vcc										Any Voltage										
Current	ŀ	or		6	-	-	±0.1	_	±1	_	±1	between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ	
		Gnd			ļ		<u> </u>	ļ				& Gnd	ļ	ļ		ļ		ļ	_	_		
Quiescent		Vcc			-							Vcc										
Device		or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ	
Current	Icc	Gnd										Gnd		1		<u> </u>			<u> </u>	1_		
Additional Quiescent Device Current per input pin: 1 unit load	Δl _{cc} *											V _{cc} -2.1	4.5 to 5.5	-	100	360	-	450	-	490	μΑ	

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS#
MR	1.5
Data	0.4
CP	1.5

^{&#}x27;Unit Load is Δl_{CC} limit specified in Static Characteristics Chart, e.g., 360 μA max. @ 25° C.

MR 1		20 VCC
00 2	- 1	<u>19</u> Q7
D0 3	-	18 D7
D1 4	ļ	17 D6
Q1 5	ļ	16 Q6
Q2 6	- }	15 Q5
D2 ⁷	-	14 D5
D3 8	- 1	13 D4
Q3 9	- 1	12 Q4
CNID 10		11 CP

TERMINAL ASSIGNMENT

PRE-REQUISITE FOR SWITCHING FUNCTION

								LIM	ITS						
OUADA OTEDIST		TEST		25	°C		-4	0°C to	+85°	°C	-55	5°C to	+125	°C	UNITS
CHARACTERIST	ic	CONDITION	н	ıc	н	СТ	74	нс	74H	ICT	541	нс	54H	ICT	UNITS
		V _{CC}	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Clock		2	6		<u> </u>		5		_		4		_		
Frequency	f_{max}	4.5	30		25	ĺ	25		20		20		16		MHz
Fig. 3		6	35	1	_		29		_		23		_		
		2	60		_		75		-		90		-		
MR Pulse Width	$t_{\mathbf{W}}$	4.5	12		12		15		15		18		18		ns
Fig. 4		6	10		_		13		_		15				
		2	80		_		100				120		-		
Clock Pulse Width	tw	4.5	16		20		20		25		24		30		ns
Fig. 3		6	14		_		17		_	}	20		_		
Set-up Time		2	60		_		75		-		70		_		
Data to Clock		4.5	12		12		15		15		18	1	18	1	ns
Fig. 5	tsu	6	10		-		13	İ	_		15		_		
Hold Time		2	3		-		3		-		3		_		
Data to Clock		4.5	3		3		3		3		3		3		ns
Fig. 5	tн	6	3		_		3				3		_		
Removal Time		2	50		-		65				75		-		
MR to Clock	t _{REM}	4.5	10		10		13		13		15		15	-	ns
		6	9		-		11		_		13				

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{ C}$, input t_r , $t_t = 6 \text{ ns}$)

		CL	TYP		
CHARACTERISTIC		pF	HC	нст	UNITS
Propagation Delay, Clock to Q	t _{PLH} t _{PHL}	15	12	12	ns
Maximum Clock Frequency	f _{max}	15	60	50	MHz
Power Dissipation Capacitance*	C _{PD}	_	25	25	pF

* C_{PD} is used to determine the dynamic power consumption, per flip-flop. $P_D = C_{PD}V_{Cc}^2fi + \sum C_LV_{cc}^2fo \quad \text{where fi = input frequency,} \\ C_L = \text{output load capacitance, } V_{Cc} = \text{supply voltage.}$

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_f, t_f = 6 ns)

			LIMITS													
CHARACTERISTIC		TEST		25	°C		-4	0°C t	o +85°	,C	-5	5°C to	+125	°C		
		CONDITION	Н	С	н	СТ	74	нс	74F	ICT	54	нс	54F	ICT	UNITS	
		VCC V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Propagation Delay	t _{PLH}	2		150		_		190		_		225		_		
Clock to Output	t _{PHL}	4.5		30		30		38		38		45		45	ns	
Fig. 3		6.		26		_		30		—	}	38	İ	—		
Propagation Delay		2		150		_		190		_		225		_		
MR to Output	t _{PHL}	4.5		30		32		38		40		45		48	ns	
Fig. 4		6		26		-		33		_		38		—		
Output Transition	t _{TLH}	2		75				95		_		110		_		
Time	t_{THL}	4.5		15		15		19		19	1.	22		22	ns	
Fig. 6		6		13				16				19		_	1	
Input Capacitance	Ci	_		10		10		10		10		10		10	pF	

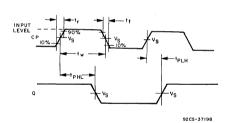


Fig. 3 - Clock to output delays and clock pulse width.

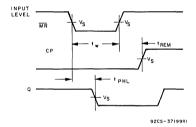


Fig. 4 - Master reset pulse width. Master reset to output delay and master reset to clock recovery time.

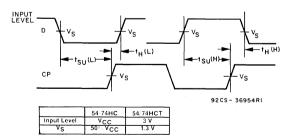


Fig. 5 - Data set-up and hold times.

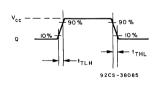
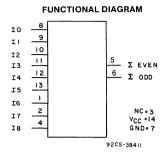


Fig. 6 - Transition times.

High-Speed CMOS Logic



9-Bit Odd/Even Parity Generator/Checker

Type Features:

- Typical propagation delay = 17ns
 Q V_{CC} = 5 V, C_L = 15pF, T_A = 25° C
- Replaces 74LS180 types
- Easily cascadable

Family Features:

 Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads

- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:

2 to 6 V Operation

High Noise Immunity: $N_{IL} = 30\%$, V_{CC} , $N_{IH} = 30\%$ of V_{CC} ; (a) $V_{CC} = 5 \text{ V}$

The RCA-CD54/74HC280 and CD54/74HCT280 are 9-bit odd/even parity, generator checker devices. Both even and odd parity outputs are available for checking or generating parity for words up to nine bits long. Even parity is indicated (ΣE output is high) when an even number of data inputs is high. Odd parity is indicated (ΣO output is high) when an odd number of data inputs is high. Parity checking for words larger than 9 bits can be accomplished by tying the

ΣΕ output to any input of an additional HC/HCT280 parity checker.

The CD54HC280 and CD54HCT280 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC280 and CD74HCT280 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

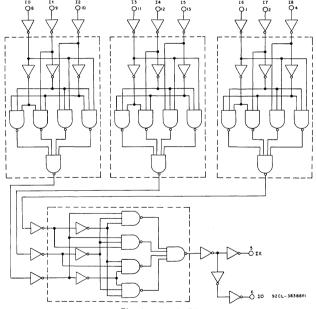


Fig. 1 — Logic Diagram

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, $I_{i\kappa}$ (FOR $V_i < -0.5 \text{ V OR } V_i \geq V_{cc} + 0.5 \text{V}$)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC Vcc OR GROUND CURRENT (Icc)	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	-40 to +85°C
STORAGÉ TEMPERATURE (Tstg)	-65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERIOTIC	LIN	HITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage VIN, VOUT	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°c
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

	CD74HC280/CD54HC280												74HC	T280	CD54	HCT	280			
	l.	TEST IDITIONS		1	IC/54 ERIE		74I SER		54I SEP	HC HES	TEST		í	CT/54 ERIE		1	ICT	54H SEF		
CHARACTERISTIC	V _i	l _o	V _{cc}		+25° C	;	-4 +85	0/ i°C	-	5/ 5°C	V,	V _{cc}		+25° C	;	1	0/ 5° C	ı	5/ 5°C	UNITS
	V	mA	\ \	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-	-	1.5	-	1.5	_		4.5								
Input Voltage V _{in}			4.5	3.15	_	-	3.15	_	3.15	_	_	to	2	<u> </u>	-	2	_	2	-	v
		<u> </u>	6	4.2	_	_	4.2	_	4.2	_		5.5								1
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}		}	4.5	-	_	1.35	-	1.35	_	1.35	_	to	_	-	0.8	-	0.8	_	0.8	v
		1	6	-	_	1.8	_	1.8	-	1.8		5.5								
High-Level	V _{IL}		2	1.9	-	-	1.9	-	1.9	_	V _{IL}									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	-	4.4	-	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	_	V
CMOS Loads	V _{IH}	1	6	5.9	_	_	5.9	-	5.9	-	V _{IH}	Ì		Ì			Ì			· ·
	V _{IL}										VıL									
TTL Loads	or	-4	4.5	3.98	-	_	3.84	_	3.7	-	or	4.5	3.98	_	_	3.84	_	3.7	-	v
	V _n ,	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH							Ì		}
Low-Level	V _{JL}		2	-	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage Vol.	or	0.02	4.5	-	_	0.1	-	0.1	_	0.1	or	4.5	-	-	0.1	_	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	-	_	0.1	_	0.1	-	0.1	V _{IH}									
	VIL										V _{IL}									
TTL Loads	or	4	4.5	-	_	0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	_	0.33	_	0.4	V
•	V _{IH}	5.2	6	-	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	Vac										Any									
Current I	or		6	_	-	±0.1	-	±1	-	±1	Voltage Between	5.5	-	-	±0.1	-	±1	–	±1	μΑ
	Gnd	1						}	ł		V _{cc} & Gnd					1				1
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	8	_	80	-	160	or	5.5	-	_	8	_	80	_	160	μΑ
Current I _{cc}	Gnd										Gnd									
Additional												4.5								
Quiescent Device Current per input pin: 1 unit load											V _{cc} -2.1	to 5.5	-	100	360	-	450	-	490	μΑ

 $^{^{\}circ}$ For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
ALL	, 1

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r,t_f=6 ns)

CHARACTERISTIC	CL	SYMBOL	TYP	CAL	UNITS
CHARACTERISTIC	(pF)	STWIDGE	HC	HCT	011113
Propagation Delay	15	t _{PHL}	17	19	ns
Any Input to ΣO	13	t _{PLH}		13	113
Any Input to ΣΕ	15	t _{PHL}	17	18	ns
Any input to 22		t _{PLH}			
Power Dissipation Capacitance*	-	C _{PD}	58	58	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

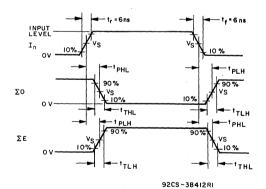
PD = V_{CC}^2 f_i (C_{PD} + C_L) where f_i = input frequency,

C_L = output load capacitance.

V_{cc} = supply voltage

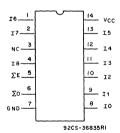
SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r,t_f=6 ns)

				25	°C		-4	0°C to	+85°	,C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	V _{cc}	Н	С	Н	СТ	741	НС	74F	ICT	54	HC	54H	ICT	UNITS
			Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	I -	200	_	_	-	250	_	_	_	300	_	_	
Any Input to ΣO	t _{PHL}	4.5	-	40		45		50	_	56	_	60	_	68	
		6	-	34	_	_	-	43	-	l —	<u> </u>	51			
	t _{PLH}	2	T-	200	-	_	_	250	_	_	_	300	_	_	
Any Input to ΣE	t _{PHL}	4.5	-	40	—	42	_	50	_	53		60	_	63	ns
		6	 –	34		_	_	43	-		_	51	_		
Output Transition	t _{TLH}	2	_	75	_	_	_	95	-	_	-	110	_	-	
Time	t _{THL}	4.5	-	15	_	15	_	19	—	19	_	22	—	22	
		6		13		_		16	_		_	19			
Input Capacitance	Cı		-	10	-	10	_	-10	_	10	_	-10	-	10	pF



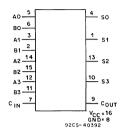
	54/74HC	54/74HC
INPUT LEVEL	Vcс	3 V
SWITCHING VOLTAGE, VS	50% VCC	1.3 V

Fig. 2 — Propagation delay and transition times.



TERMINAL ASSIGNMENT

High-Speed CMOS Logic



4-Bit Binary Full Adder With Fast Carry

Type Features:

- Adds two binary numbers
- Full internal lookahead
- Fast ripple carry for economical expansion.
- Operates with both positive and negative logic

FUNCTIONAL DIAGRAM

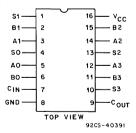
The RCA-CD54/74HC283 and CD54/74HCT283 are binary-full adders that add two 4-bit binary numbers and generate a carry-out bit if the sum exceeds 15.

Because of the symmetry of the add function, this device can be used with either all active-High operands (positivelogic) or with all active-Low operands (negative logic). When using positive logic the carry-in input must be tied low if there is no carry-in.

The CD54HC/HCT283 are supplied in 16-lead hermetic dual-in-line frit seal ceramic packages (F suffix). The CD74HC/HCT283 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 μA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

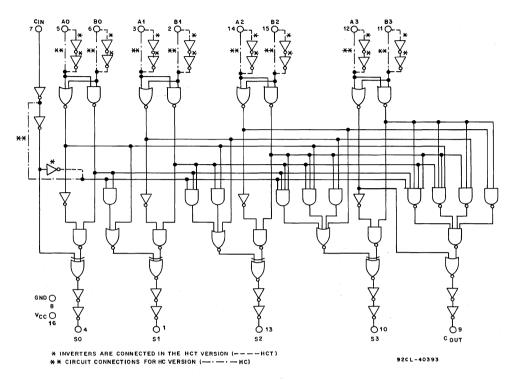


Fig. 1 - Logic diagram for HC/HCT types.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_I < -0.5 \text{ V OR } V_I > V_{CC} + 0.5 \text{ V}$)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT, (I _{CC}):	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (T _{stq})	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit in control into a DO be and (win this language 4/40 in 1,50 mm)	
with solder contacting lead tips only	+300° C

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC283/CD54HC283											CD74	нст	283/C	D54H	ICT2	83			
OUADAGT FRIG	T 10	TEST CONDITIONS				IC/54 YPE:		741 TYF		541 TYF		TEST CONDITION	٧s	74HCT/54HCT TYPES			74HCT TYPES		l	ICT PES	UNITS
CHARACTERIS	iic	V,	lo	Vcc		+25° C	;	-4 +85	0/ 5° C	-5 +12		V _I	Vcc		+25° C	;		10/ 5° C	l	5°C	UNITS
		v	mA	v	Min	Тур	Max	Min	Max	Min	Max	V	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	-		4.5								
Input Voltage	V_{IH}	!		4.5	3.15	_		3.15		3.15	_	_	to	2	-	-	2	-	2	-	V
			ļ	6	4.2	_		4.2	_	4.2	_		5.5								
Low-Level				2	<u> </u>	=	0.5	_	0.5	_	0.5		4.5			ł					
Input Voltage	VIL	1	1	4.5	<u> </u> _		1.35	<u> </u>	1.35	<u> </u>	1.35	-	to	-	-	8.0	-	0.8		0.8	٧
			ļ	6			1.8	<u> _ </u>	1.8		1.8		5.5		ļ	ļ		<u> </u>		ļ	
High-Level		VIL	Ì	2	1.9		<u> </u>	1.9		1.9		VIL			ł	l		1		1	
Output Voltage	VoH	or	-0.02	4.5	4.4		=	4.4:		4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	٧
CMOS Loads		V _{IH}	ļ	6	5.9		-	5.9	=	5.9		V _{IH}			-			├		 	
		VIL	ļ							<u> </u>		VIL				1		1			
TTL Loads		or	-4	4.5	3.98	_	=-	3.84	-	3.7	_	or	4.5	3.98	_	-	3.84	-	3.7	-	V
		V _{IH}	-5.2	6	5.48	=	-	5.34	_	5.2	=	V _{IH}						├			
Low-Level		VIL		2	=		0.1	-	0.1	<u> </u>	0.1	VIL			1						.,
Output Voltage	Vol	or	0.02	4.5 6	-	=	0.1	-	0.1	=	0.1	or	4.5	-	_	0.1	-	0.1	-	0.1	٧
CMOS Loads		VIH		-		=	0.1	-	0.1		0.1	V _{IH}			├			├			
TTL Loads		or	4	4.5	_	_	0.26	-	0.33	-	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v
TTE EUAUS		VIH	5.2	6	_	=	0.26	_	0.33	-	0.4	ViH	4.5	_	_	0.20	-	0.33	_	0.4	ľ
Input Leakage		VIH	3.2	-	┝═┈		0.20	 - -	0.33	 -	0.4	Any					}	 		 	
Current	lı.	Vcc		ĺ	1		1		1		}	Voltage			ł	1		}		1	
	"	or		6	-	-	±0.1	-	±1	-	±1	Between	5.5	-	[—	±0.1	-	±1	-	±1	μΑ
		Gnd	}				1		1	İ		V _{cc} & Gnd								1	
Quiescent		Vcc		<u> </u>			 				<u> </u>	Vcc	_	-	 		_		 		
Device Current	Icc	or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μΑ
		Gnd										Gnd					}	1		1	
Additional										<u> </u>			T								
Quiescent Device												V 0.	4.5	ļ	100	000		450	1	100	
Current per input		1										V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	Δl _{cc} *												5.5			L					

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
Cin	1.5
B1, A1, A0	1
В0	0.4
B3, A3, A2, B2	0.5

^{*} Unit Load is Δl_{cc} limit specified in Static Characteristics Chart, e.g., 360 μA max. @ 25° C.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

011000000000000000000000000000000000000	LIN	LIMITS				
CHARACTERISTIC	MIN.	MAX.	UNITS			
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*						
CD54/74HC Types	2	6	v			
CD54/74HCT Types	4.5	5.5	V			
DC Input or Output Voltage V _I , V _O	0	Vcc	V			
Operating Temperature T _A :						
CD74 Types	-40	+85	°C			
CD54 Types	-55	+125	°c			
Input Rise and Fall Times, t _r , t _f						
at 2 V	0	1000	ns			
at 4.5 V	0	500	ns			
at 6 V	0	400	ns			

^{*} Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

			TYPICAL	VALUES	
CHARACTERISTIC		CL (pF)	нс	нст	UNITS
Propagation Delay,					
C _{IN} to S0	t _{PLH} , t _{PHL}	15	13	13	
Cin to S1	t _{PLH} , t _{PHL}	15	15	18	
C _{IN} to S2	t _{PLH} , t _{PHL}	15	16	19	
Cin to Cout	t _{PLH} , t _{PHL}	15	16	19	ns
Cin to S3	t _{PHL} , t _{PLH}	15	19	22	
A _n , B _n to C _{OUT}	t _{PHL} , t _{PLH}	.15	16	20	
A _n , B _n to S _n	t _{PHL} , t _{PLH}	15	18	21	
Power Dissipation Capacitance *	C _{PD}		70	82	pF

^{*} C_{PD} is used to determine the dynamic power consumption, per package.

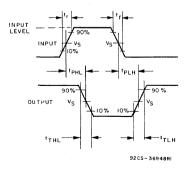
 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where: f_i = input frequency

C_L = output load capacitance

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r , t_t = 6 ns)

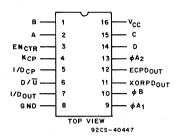
			LIMITS													
		TEST		25	°C		-4	0°C to	o +85°	,C	-5	UNITS				
CHARACTERIST	IC	CONDITION	Н	С	н	ст	741	нс	74F	ICT	54	нс	54F	ICT	UNITS	
		V _{cc} V	Min.	Мах.	Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.		
Propagation	t _{PLH}	2	_	160	_	_	_	200		_	_	240	_	_		
Delay	t _{PHL}	4.5	-	32	-	31	_	40	-	39	_	48	_	47		
C _{IN} to S0		6		27				34			_	41	_			
	t_{PLH}	2	_	180	—	_		225		-		270	-	_		
C _{IN} to S1	t _{PHL}	4.5	-	36		43	-	45	-	54	_	54	—	65		
		6	_	31			_	38	_	_	_	46				
CIN to S2,	t _{PLH}	2		195	-	—	-	245	-		-	295	-			
CIN to COUT	t_{PHL}	4.5	-	39		46	-	49	-	58	-	59	-	69		
		6	<u> </u>	33	_			42				50	<u> </u>			
	t_{PLH}	2		230	-	—	-	290	-	-		345	-	_		
CIN to S3	t_{PHL}	4.5	-	46	_	53	-	58		66	-	69	_	80	ns	
-		6	_	39		_		49		_	_	59	<u> </u>			
	t_{PLH}	2	-	195	_	-	-	245	-	-	-	295	-	-		
A_n , B_n to C_{OUT}	t_{PHL}	4.5	-	39	-	48	-	49	-	60	-	59	-	72		
		6		33				42				50		<u> </u>		
	t_{PLH}	2	-	210	-	-	_	265	-	-	-	315	-	-	}	
A_n , B_n to S_n	t_{PHL}	4.5	-	42	-	49	-	53	-	61	-	63	-	74		
		6	_	36		_		45			_	54		<u> - </u>	,	
Output	t_{TLH}	2	-	75	-	-	-	95	_	-	-	110	-	-		
Transition	t _{THL}	4.5	-	15	-	15	-	19	-	19	-	22	-	22		
Time		6		13	<u> </u>			16			_	19	_	<u> </u>		
Input Capacitance	Cı		-	10	-	10	-	10	_	10	-	10	-	10	pF	



	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 2 - Transition and propagation delay times.

High-Speed CMOS Logic



Digital Phase-Locked-Loop Filter

Type Features:

- Digital design avoids analog compensation errors
- Easily cascadable for higher order loops
- Useful frequency range:
 DC to 55 MHz typical (k-clock)
 DC to 35 MHz typical (I/D-clock)
- Dynamically variable bandwidth
- Very narrow bandwidth attainable
- Power-on reset
- Output capability:

Standard - XORPDout, ECPDout Bus driver - I/Dout

TERMINAL ASSIGNMENT

The RCA-CD54/74HC/HCT297 are high-speed silicon-gate CMOS devices that are pin-compatible with low power Schottky TTL (LSTTL).

These devices are designed to provide a simple, costeffective solution to high-accuracy, digital, phase-lockedloop applications. They contain all the necessary circuits, with the exception of the divide-by-N counter, to build firstorder phase-locked-loops.

Both EXCLUSIVE-OR (XORPD) and edge-controlled phase detectors (ECPD) are provided for maximum flexibility. The input signals for the EXCLUSIVE-OR phase detector must have a 50% duty factor to obtain the maximum lock-range.

Proper partitioning of the loop function, with many of the building blocks external to the package, makes it easy for the designer to incorporate ripple cancellation (see Fig. 2) or to cascade to higher order phase-locked-loops.

The length of the up/down K-counter is digitally programmable according to the K-counter function table. With A, B, C and D all LOW, the K-counter is disabled. With A HIGH and B, C and D LOW, the K-counter is only three stages long, which widens the bandwidth or capture range and shortens the lock time of the loop. When A, B, C and D are all programmed HIGH, the K-counter becomes seventeen stages long, which narrows the bandwidth or capture range and lengths the lock time. Real-time control of loop bandwidth by manipulating the A to D inputs can maximum the overall performance of the digital phase-locked-loop.

The CD54/74HC/HCT297 can perform the classic first-order phase-locked-loop function without using analog components. The accuracy of the digital phase-locked-loop (DPLL) is not affected by VCC and temperature variations but depends solely on accuracies of the K-clock and loop propagation delays.

Family Features:

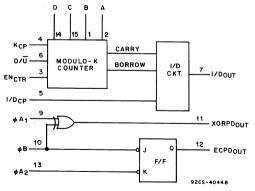
- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation

High Noise Immunity:

NIL = 30%, NIH = 30% of Vcc; @ Vcc = 5 V

■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility

 $I_{\rm I} \leq 1~\mu{\rm A}$ @ $V_{\rm OL},~V_{\rm OH}$



FUNCTIONAL DIAGRAM

The phase detector generates an error signal waveform that, at zero phase error, is a 50% duty factor square wave. At the limits of linear operation, the phase detector output will be either HIGH or LOW all of the time depending on the direction of the phase error $(\phi IN - \phi OUT).$ Within these limits the phase detector output varies linearly with the input phase error according to the gain $K_d,$ which is expressed in terms of phase detector output per cycle or phase error. The phase detector output can be defined to vary between \pm 1 according to the relation:

The output of the phase detector will be $K_d\phi_e$, where the phase error

$$\phi_e = \phi_{IN} - \phi_{OUT}$$

EXCLUSIVE-OR phase detectors (XORPD) and edgecontrolled phase detectors (ECPD) are commonly used digital types. The ECPD is more complex than the XORPD logic function but can be described generally as a circuit that changes states on one of the transitions of its inputs. The gain (K_a) for an XORPD is 4 because its output remains HIGH (XORPD_{OUT} = 1) for a phase error of ¼ cycle.

Similarly, K_d for the ECPD is 2 since its output remains HIGH for a phase error of ½ cycle. The type of phase detector will determine the zero-phase-error point, i.e., the phase separation of the phase detector inputs for a ϕ_e effined to be zero. For the basic DPLL system of Fig. 3, ϕ_e = 0 when the phase detector output is a square wave.

The XORPD inputs are $\frac{1}{2}$ cycle out-of-phase for zero phase error. For the ECPD, $\phi_0 = 0$ when the inputs are $\frac{1}{2}$ cycle out of phase.

K COUNTER FUNCTION TABLE (DIGITAL CONTROL)

D	С	В	Α	MODULO (K)
L	L	L	L	Inhibited
L	L	L	н	2 ³ 2 ⁴
L	L	н	L	24
L	L	Н	Н	2 ⁵
L	Н	L	L	2 ⁶
L	н	L	н	2 ⁷
L	н	н	L	2 ⁸ 2 ⁹
L	Н	Н	н	2 ⁹
Н	L	L	L	2 ¹⁰
Н	L	L	Н	2 ¹¹
Н	L	Н	L.	2 ¹²
Н	L	н	н	2 ¹³
Н	Н	L	L	214
Н	н	L	н	2 ¹⁵
Н	Н	н	, L	2 ¹⁶
Н	н	н	н	2 ¹⁷

The phase detector output controls the up/down input to the K-counter. The counter is clocked by input frequency Mf_c which is a multiple M of the loop center frequency f_c . When the K-counter recycles up, it generates a carry pulse. If the carry and the borrow outputs are conceptually combined into one output that is positive for a carry and negative for a borrow, and if the K-counter is considered as a frequency divider with the ratio Mf_c/K , the output of the K-counter will equal the input frequency multiplied by the division ratio. Thus the output from the K-counter is $(K_d\phi_bMf_c)/K$.

The carry and borrow pulses go to the increment/decrement (I/D) circuit which, in the absence of any carry or borrow pulses has an output that is ½ of the input clock (I/D_{CP}). The input clock is just a multiple, 2N, of the loop center frequency. In response to a carry of borrow pulse, the I/D circuit will either add or delete a pulse at I/D_{Our}. Thus the output of the I/D circuit will be Nf_c + (K_d ϕ_{e} Mf_c)/2K.

The output of the N-counter (or the output of the phase-locked-loop) is thus:

$$f_o = f_c + (K_d \phi_e M f_c)/2KN$$
.

If this result is compared to the equation for a first-order analog phase-locked-loop, the digital equivalent of the gain of the VCO is just Mf_c/2KN or f_c/K for M = 2N.

Thus, the simple first-order phase-locked-loop with an adjustable K-counter is the equivalent of an analog phase-locked-loop with a programmable VCO gain.

The CD54HC297 and CD54HCT297 are supplied in 16-lead hermetic dual-in-line frit-seal ceramic packages (F suffix). The CD74HC297 and CD74HCT297 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

FUNCTION TABLE EXCLUSIVE-OR PHASE DETECTOR

φ A 1	φВ	XORPD OUT
L	L	L
L	H,	н
Н	L	н
н	н	L

FUNCTION TABLE EDGE-CONTROLLED PHASE DETECTOR

φ A ₂	φВ	ECPD OUT
H or L		Н
	H or L	L
HorL		No Change
	HorL	No Change

H = steady-state high level

L = steady-state low level

 \setminus = transition from high to low

= transition from low to high

STATIC ELECTRICAL CHARACTERISTICS

			CI		CD74HCT297/CD54HCT297																
	c	TES ONDIT			74HC/54HC 74HC 54HC TYPES TYPES TYPES		TEST 74HCT/54HCT CONDITIONS TYPES					74H TYF		54H TYF							
CHARACTERISTIC	Vı	lo)	Vcc	,	∙25° C	:		-40/ -55/ +85°C +125°C			V,	Vcc	,	-25°C		-40/ +85° C		-55/ +125°C		UNITS
	٧	m	A	v	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	-	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}				4.5	3.15	_	_	3.15	=	3.15	_	-	to	2	_	_	2	-	2	-	V
				6	4.2	L		4.2		4.2	-		5.5								
Low-Level				2	_	_	0.5	_	0.5		0.5		4.5					l			
Input Voltage V _{IL}				4.5	_	_	1.35	_	1.35	_	1.35	-	to	-	-	0.8	-	0.8		0.8	٧
				6	_	_	1.8	_	1.8	_	1.8		5.5						_		
High-Level	VIL			2	1.9	1.9 — —		1.9		1.9	_	VIL					l	1			
Output Voltage VoH	or	-0.	02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	٧
CMOS Loads	V _{IH}			6	5.9		=	5.9		5.9	_	V _{IH}		L		L		Ь			
TTL Loads	VIL	#	I/D	L			<u> </u>	<u> </u>		<u> </u>		VIL									
Bus Driver and	or	-4	-6	4.5	3.98	=	<u> </u> =	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	V
Standard Output	V _{IH}	-5.2	-7.8	6	5.48	_	느	5.34	_	5.2	_	VIH		<u> </u>	ļ	ļ		<u> </u>		<u> </u>	
Low-Level	VIL	1		2	<u> </u>	_	0.1	_	0.1	_	0.1	VıL									
Output Voltage Vol	or	0.0	02	4.5	_	-	0.1	-	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		,	6.	-	-	0.1	_	0.1	<u> </u>	0.1	V _{IH}	<u> </u>	<u> </u>			<u> </u>		<u> </u>	ـ	
TTL Loads	VIL	#	I/D	<u> </u>	<u> </u>	<u> </u>	<u> </u>	<u> </u>	<u> </u>		<u> </u>	VIL			-					١	
Bus Driver and	or	4	6	4.5	<u> </u>	ᄂ	0.26	<u> </u>	0.33		0.4	or	4.5	-	_	0.26	-	0.33	-	0.4	V
Standard Output	ViH	5.2	7.8	6	_	<u> </u> =	0.26	_	0.33	느	0.4	V _{IH}	<u> </u>	<u> </u>			ļ	ـــ	<u> </u>	<u> </u>	
Input Leakage Current I	V _{cc} or			6	-	_	±0.1	-	±1	_	±1	Any Voltage Between	5.5	_	_	±0.1	-	±1	_	±1	μΑ
	Gnd											V _{cc} & Gnd									
Quiescent	Vcc	 		<u> </u>	-	╁	<u> </u>	-		 	-	Vcc & Gild	-	├		-	-	+-	├	\vdash	
Device Current Icc	or	, ا	1	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μА
Deline Garrent lee	Gnd	`	-	١			١		"			Gnd	5.5	İ		1	l	-	1		<i>[</i>
Additional	2.10	L		L				-			-		\vdash	\vdash	<u> </u>						
Quiescent Device													4.5				1		l		
Current per input	Ì											V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load Δlcc*													5.5						1	1	

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
EN _{CTR} , D/U	0.3
A, B, C, D, K _{CP} , φA ₂	0.6
I/D _{CP} , φA ₁ , φB	1.5

^{*} Unit Load is $\Delta l_{\rm Cc}$ limit specified in Static Characteristics Chart, e.g., 360 μ A max. @ 25° C.

[#] XORPD, ECPD

PRE-REQUISITE FOR SWITCHING FUNCTION

			LIMITS													
CUADACTERISTIC		.,		25	°C			40°C t	o +85°	С	-5	5°C to	+125°	°C	UNITS	
CHARACTERISTIC		V _{cc}	Н	С	н	нст		74HC		74HCT		54HC		54HCT		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Maximum Clock		2	6	-	_	_	5	_	-	-	4	-	_	-		
Frequency	f_{MAX}	4.5	30	-	30	_	24	-	24	-	20	-	20	-	MHz	
K _{CP}		6	35	-	_	} —	28	-	-	-	24	-	_	-		
		2	4	_	_	-	3	-	_	_	2	_	_	_		
1/D _{CP}		4.5	20	. —	20	_	16	-	16	-	13	-	13	-	MHz	
		6	24	_	_	_	19	_	-	-	15	-	_	-		
Clock Pulse Width	t _w	2	80	_		_	100	-	_	_	120	-	-	-		
		4.5	16	_	16	_	20	-	20	_	24	-	24	-	ns	
K _{CP}		6	14		_	_	17	_	_	_	20			_		
		2	125	_	-	i —	155	_	-	-	190	-	_	-		
1/D _{CP}		4.5	25	_	25	-	31	-	31	_	38	-	38	-	ns	
		6	21	_	_		26				32	_	_	_		
Setup Time		2	100	-	-	_	125	_	-	-	150	-	_	_		
D/\overline{U} , EN_{CTR} to K_{CP}	t_{SU}	4.5	20	_	20	–	25	_	25	_	30	_	30	-	ns	
		6	17				21				26	_				
Hold Time		2	0	_	-	_	0	_	_	_	0	-	_	_		
D/U, EN _{CTR} to K _{CP}	t _H	4.5	0	_	0	-	0	_	0	_	0	-	0	-	ns	
		6	0	_	_	-	О	-	–	–	0	–		-		

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r , t_f = 6 ns)

								LIM	ITS						
OLIADA OTERIOTIO				25	°C	°C		40° C t	o +85°	С	-5	5°C to	+125°	,C	UNITS
CHARACTERISTIC		V _{cc}	Н	нс		нст		74HC		74HCT		54HC		54HCT	
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	175	_	_	_	220	_	-	_	265	_	_	
I/D _{CP} to I/D _{OUT}	t _{PHL}	4.5		35	_	35	_	44	_	44	_	53	-	53	
		6	-	30	_	_	_	34	_	_	-	43	-	-	
		2	_	150	_	_	_	190	-	_	_	225			
ϕ A ₁ , ϕ B to XORPD _{OUT}		4.5	_	30	-	30	_	38	-	38	-	45	_	45	
		6		26	_	-		33	-	-	_	38	_	-	
		2	_	200	_	_	_	250	_	_	_	300	_	_	
ϕ B, ϕ A2 to ECPD $_{ ext{OUT}}$		4.5	-	40		40		50	–	50	_	60	_	60	ns
		6	-	34	_	_	_	43	-	-	_	51	-	—	
Output Transition Time		2	_	75	_	_		95		_	_	110	_	_	
XORPD _{OUT}	t _{TLH}	4.5	-	15	_	15		19	_	19	_	22	-	22	
ECPD _{OUT} .	t_{TLH}	6	-	13	_	-	_	16	-	-	—	19	_	-	
		2	_	60	_	_		75	_	_	_	90	_	_	
I/D _{OUT}		4.5	_	12	_	12	_	15	_	15	_	18	_	18	
		6	_	10	_	_		13	_	_	_	15	-	-	
Input Capacitance	Cı		_	10	_	10	_	10	_	10		10	_	10	pF

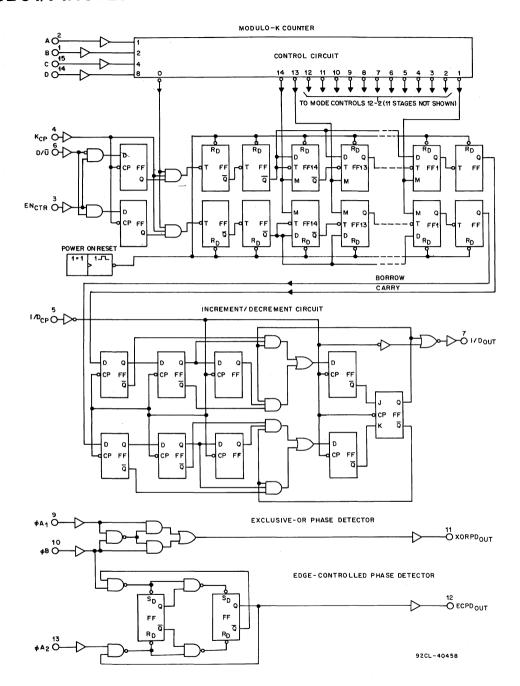


Fig. 1 - Logic diagram.

- 2NfC

CD54/74HC297 CD54/74HCT297

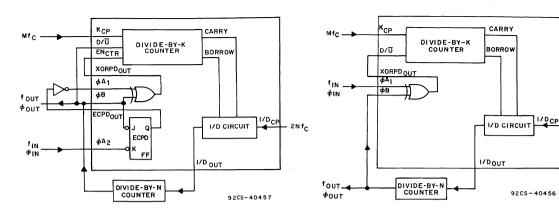


Fig. 2 - DPLL using both phase detectors in a ripple-cancellation scheme.

Fig. 3 - DPLL using EXCLUSIVE-OR phase detection.

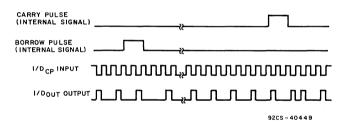


Fig. 4 - Timing diagram: I/Dout in-lock condition.

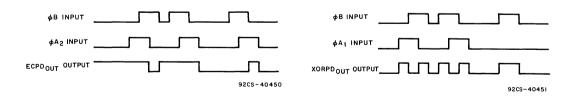


Fig. 5 - Timing diagram: edge-controlled phase comparator waveforms.

Fig. 6 - Timing diagram: EXLUSIVE-OR phase detector waveforms.

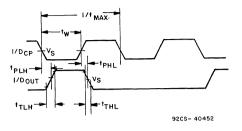


Fig. 7 - Waveforms showing the clock (I/D_{CP}) to output (I/D_{Out}) propagation delays, clock pulse width, output transition times and maximum clock pulse frequency.

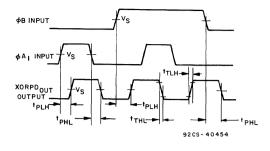
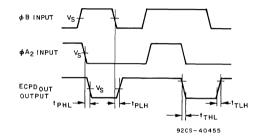


Fig. 8 - Waveforms showing the phase input $(\phi B, \phi A_1)$ to output $(XORPD_{Out})$ propagation delays and output transition times



D/Ū, EN CTR
IN PUT

t_{SU}

K_{CP} INPUT

VS

1/f_{MAX}

92CS-40453

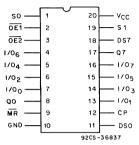
NOTE: THE SHADED AREAS INDICATE WHEN THE INPUT IS PERMITTED TO CHANGE FOR PREDICTABLE OUTPUT PERFORMANCE.

Fig. 9 - Waveforms showing the phase input $(\phi B, \phi A_2)$ to output $(ECPD_{OUT})$ propagation delays and output transition times.

Fig. 10 - Waveforms showing the clock (Kc_P) pulse width and maximum clock pulse frequency, and the input $(D/\overline{U}, EN_{CTB})$ to clock (Kc_P) set-up and hold times.

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _s	50% V _{cc}	1.3 V

High-Speed CMOS Logic



8-Bit Universal Shift Register: 3-State

Type Features:

- Four Operation Modes: Shift Left, Shift Right, Load and Store
- Can be cascaded for N-bit word lengths
- I/O₀-I/O₁ bus drive capability and 3-state for bus oriented applications
- Buffered inputs
- Typical f_{MAX}=50 MHz @ V_{CC}=5 V, C_L=15 pF, T_A=25° C

TERMINAL ASSIGNMENT

The RCA-CD54/74HC299 and CD54/74HCT299 are 8-bit shift/storage registers with 3-state bus interface capability. The register has four synchronous-operating modes controlled by the two select inputs as shown in the mode select (S0, S1) table. The mode select, the serial data (DS0, DS7) and the parallel data (I/O₀-I/O₇) respond only to the low-to-high transition of the clock (CP) pulse. S0, S1 and data inputs must be one set-up time prior to the clock positive transition.

The Master Reset (\overline{MR}) is an asynchronous active low input. When \overline{MR} output is low, the register is cleared regardless of the status of all other inputs. The register can be expanded by cascading same units by tying the serial output (Q0) to the serial data (DS7) input of the preceding register, and tying the serial output (Q7) to the serial data (DS0) input of the following register. Recirculating the (n x 8) bits is accomplished by tying the Q7 of the last stage to the DS0 of the first stage.

The 3-state input/output I(/O) port has three modes of operation:

- Both output enable (OE1 and OE2) inputs are low and S0 or S1 or both are low, the data in the register is presented at the eight outputs.
- When both S0 and S1 are high, I/O terminals are in the high impedance state but being input ports, ready for parallel data to be loaded into eight registers with one clock transition regardless of the status of OE1 and OE2.
- Either one of the two output enable inputs being high will force I/O terminals to be in the off-state. It is noted that each I/O terminal is a 3-state output and an CMOS buffer input.

The CD54HC299 and CD54HCT299 are supplied in 20-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC299 and CD74HCT299 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N₁ = 30% N₂ = 20% of V₂₂ @ V₂₂
- N_{IL}=30%, N_{IH}=30% of V_{CC}; @ V_{CC}=5 V ■ CD54HCT/CD74HCT Types:
 - 4.5 to 5.5 V Operation

 Direct LSTTL Input Logic Compatibility

 V_{IL}=0.8 V Max., V_{IH}=2 V Min.

 CMOS Input Compatibility

 I₁ ≤ 1 μA @ V_{OL}, V_{OH}

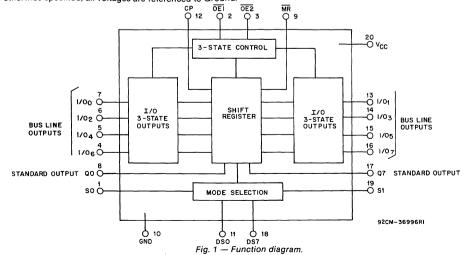
MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V_{cc}):
(Voltages referenced to ground)0.5 to $+$ 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)
DC OUTPUT DIODE CURRENT, l_{OK} (FOR $V_{o} < -0.5$ V OR $V_{o} > V_{CC} + 0.5$ V)
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V)
For Q Outputs
For I/O Outputs
DC V _{CC} OR GROUND CURRENT (I _{CC})
POWER DISSIPATION PER PACKAGE (Pp.):
For T _A = -40 to +60°C (PACKAGE TYPE E)
For T _A = +60 to +85°C (PACKAGE TYPE E)
For T _A = -55 to +100°C (PACKAGE TYPE F, H)
For $T_A = +40$ to $+125$ °C (PACKAGE TYPE F, H)
For T _A = -40 to +70°C (PACKAGE TYPE M)
For T _A = +70 to +125° C (PACKAGE TYPE M) Derate Linearly at 6 mW/° C to 70 mW
OPERATING TEMPERATURE RANGE (TA)
PACKAGE TYPE F, H
PACKAGE TYPE E, M40 to +85° C
STORAGE TEMPERATURE (T _{stg}) -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only +300°C +300°C
RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	LINUTO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage, V _I , V _O	0	V _{cc}	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	3.0
Input Rise and Fall Times, tr, tr:			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

*Unless otherwise specified, all voltages are referenced to Ground.



STATIC ELECTRICAL CHARACTERISTICS

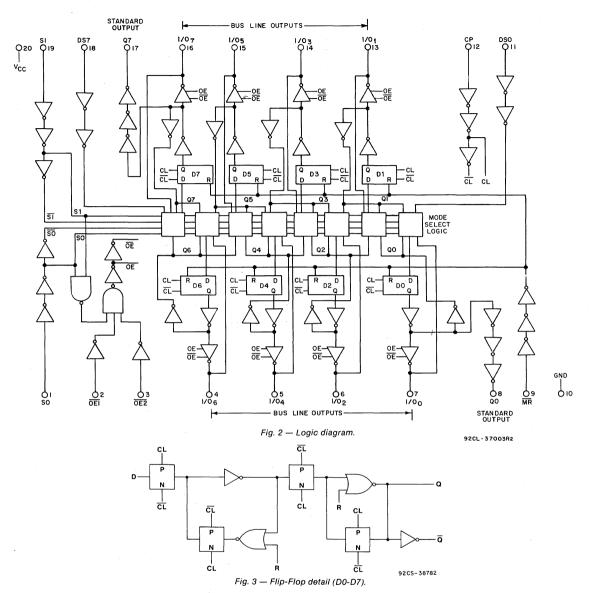
				CD	74HC	299/	CD54	HC29	9				CD74	нст2	99/C[)54H	54HCT299					
QUADA 077710710	c	TES		s	i	IC/54 TYPE		741 TY		54H TYI		TEST	ons	1	T/54		1	YAHCT 54HCT TYPE TYPE			UNITS	
CHARACTERISTIC	V,	lo		Vcc		·25° C	;	-4: +85		-5: +12:		V ₁	V _{cc}	,	25° C		-4 +85					
	V	m A	١.	v	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max		
High-Level				2	1.5	_		1.5	_	1.5	_		4.5									
Input Voltage V _{IH}				4.5	3.15	_	<u> </u>	3.15	_	3.15	1	_	to	2	_	_	2	_	2	_	_	
				6	4.2	_	_	4.2	_	4.2	-		5.5									
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5									
Input Voltage VIL				4.5	_	_	1.35	_	1.35	_	1.35	_	to	_	_	0.8	_	0.8	_	0.8	0.8 V	
		1		6	_	_	1.8	_	1.8	_	1.8		5.5	}								
High-Level	VIL			2	1.9	_	_	1.9	_	1.9	_	VıL										
Output Voltage Von	or	-0.0	2	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	٧	
CMOS Lóads	VIH			6	5.9	_	_	5.9	_	5.9	_	V _{IH}										
TTL Loads	VIL	Qn II	I/On									VıL										
Bus Driver and	or	-4	-6	4.5	3.98	_	_	3.84		3.7		or	4.5	3.98	_	_	3.84	_	3.7	_	٧	
Standard Output	VIH	-5.2	-7.8	6	5.48	_	_	5.34	_	5.2	_	VIH										
Low-Level	VIL			2	_		0.1	_	0.1	_	0.1	VIL									-	
Output Voltage Vol	or	0.0	2	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v	
CMOS Loads	ViH			6	_	_	0.1	_	0.1	_	0.1	ViH							1			
TTL Loads	VIL	Qn II	/On									VIL										
Bus Driver and	or	4	6	4.5	-		0.26		0.33	-	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v	
Standard Output	VIH	-	7.8	6		=	0.26	_	0.33	<u> </u>	0.4	V _{IH}	4.5		_	0.20		0.00		0.4	•	
Input Leakage Current I	V _{cc} or Gnd	0.2	7.0	6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	-	±1	-	±1	μΑ	
Quiescent Device Current I _{cc}	V _{cc} or Gnd	0		6	_	_	8	_	80	_	160	V _{cc} or Gnd	5.5	-	_	8		80	_	160	μΑ	
Additional Quiescent Device Current per Input Pin: 1 Unit Load Δlcc*												V _{CC} -2.1	4.5 to 5.5	_	100	360	 	450	_	490	μΑ	
3-State Leakage Current	V _{IL} or V _{IH}	V _o = V _{cc} or G		6	_	_	±0.5	_	±5	_	±10	V _{IL} or V _{IH}	5.5	-	-	±0.5	-	±5	_	±10	μΑ	

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
S1, MR	0.25
I/O ₀ -I/O ₇	0.25
DS0, DS7	0.25
S0, CP	0.6
OE1, OE2	0.3

^{*}Unit load is Δ l_{cc} limit specified in Static Characteristics Chart, e.g., 360 μ A max. @ 25° C.



MODE SELECT-FUNCTION TABLE

REGISTER OPERATING MODES

FUNCTION			II	NPUT	S			RE	GIST	ER OL	JTPU	TS
FUNCTION	MR	CP	S0	S1	DS0	DS7	I/On	Q0	Q1		Q6	Q7
Reset (Clear)	L	X	X	X	X	X	X	L	L		L	L
Shift Right	H	_	h	I		Х	Х	L	q٥		Q ₅	q ₆
<u>'</u>	Н		h	1	h	Χ_	Х	Н	q _o		q ₅	Q6
Shift Left	Н		1	h	Х	1	Х	q ₁	q2		q ₇	L
	Н		1	h	Х	h	Х	q ₁	q ₂		Q7	Н
Hold (do nothing)	Н				Х	X	X	qo	Q1		Q ₆	q ₇
Parallel Load	Н	_	h	h	X	Х	I	L	L		L	L
	ŀН		h	h	X	Х	h	Н	Н		Н	Н

MODE-SELECT FUNCTION TABLE 3-STATE I/O PORT OPERATING MODE

FUNCTION				INPUT	S	INPUTS/OUTPUTS
FUNCTION	ŌĒ1	OE2	S0	S1	Qn (Register)	1/00 1/07
Read Register	L	L	L	Х	L	L
	L	L	L	X	н	н
	L	L	X	L	L	L
	L	L	x	L	н	Н
Load Register	X	Х	Н	Н	Qn = I/On	I/On = Inputs
Disable I/O	Н	X	Х	Х	×	(Z)
	×	н	X	X	×	(Z)

H = Input voltage high level.

h = Input voltage high one set-up time prior clock transition.

L = Input voltage low level.

I = Input voltge low one set-up time prior clock transition.

X = Voltage level on logic status don't care. Z = Output in high impedance state.

= Low-to-high clock transition.

q_n = Lower case letter indicates the state of the referenced output one set-up time prior clock transition.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERISTIC	SYMBOL	CL	TYPICAL	VALUES	UNITS
CHARACTERISTIC	STWIBOL	(pF)	HC	нст	
Propagation Delay Clock to I/O Outputs (Fig. 4)	t _{PLH}	15	17	19	
Clock Q0 or Q7 (Fig. 4)					ns
MR to Outputs (Fig. 5)	t _{PHL}	15	17	19	
Output Enable and Disable Times (Fig. 6 & 7)	t _{PZL} , t _{PZH} t _{PLZ} , t _{PHZ}	15	10,13,15	10,13,15	
Power Dissipation Capacitance	C _{PD} *	_	150	170	pF

^{*}CPD is used to determine the dynamic power consumption, per register.

PD= $C_{PD} V_{CC}^2 fi + \Sigma (C_L V_{CC}^2 fo)$ where:

f_i=input frequency

C_L=output load capacitance

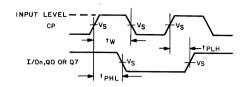
fo=output frequency

V_{cc}=supply voltage Pre-regulate for Switching Function

				25	°C		-4	0°C to	o +85°	Č	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	CT	741	НС	74F	ICT	54	HC	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Maximum Clock		2	6	_	_	_	5	_	_	_	4	_	_	—	
Frequency	fmax	4.5	30	—	25	<u> </u> —	25	—	20	—	20	—	16	—	MHz
		6	35	_	_	_	29	—	_	—	23	—	_	—	
MR Pulse Width	tw	2	50	_	_	_	65	_	_	_	75	_	_	_	
(Fig. 5)		4.5	10	_	15	<u> </u>	13	l —	19	_	15	_	22	—	l
		6	9	_	<u> </u>		11	—	l —	l —	13	—	_	—	
Clock Pulse Width	tw	2	80	_	_	_	100	-	_	—	120	_	_	_	1
(Fig. 4)		4.5	16	_	20	—	20	—	25	-	24		30	—	
		6	14	_	_	—	17	l —	_	l —	20	_	_	—	
Setup Time	tsu	2	100	_	_	_	125	_	_	_	150	_	_		1
DS0, DS7, I/On to Clock		4.5	20	_	20	_	25	—	25	—	30	—	30	—	
(Fig. 8)		6	17	_	_	 	21	l —	—	—	26		l —	-	ns
Hold Time	t _H	2	0		_	_	0	_	_	_	0	_	_	_	1
DS0, DS7, I/On, S0, S1		4.5	0	_	0	 	0	l —	0	—	0	—	0	l —	
to Clock (Fig. 8)	İ	6	0	_	_	_	0	l —		—	0	—	_		
Recovery Time	t _{REC}	2	5	_	_	_	5	_	_	_	5	_	_	T-	
MR to Clock		4.5	5	_	5	l — .	5	_	5	—	5	—	5		
(Fig. 5)		6	5	_	_	<u> </u>	5	—	l —	_	5	—	—	l –	
Setup Time	tsu	2	120	_	_	_	150	_	_	_	180	_	_	Ι –	1
S1, S0 to Clock	1	4.5	24	l —	27	_	30	_	34	—	36	—	41	—	
		6	20	_	_	_	26	l —	_	_	31	_	l —		

SWITCHING CHARACTERISTICS (C_L=50 pF, Input t_r,t_f=6 ns)

				25	°C		-4	IO°C t	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	СТ	74	НС	74H	CT	541	нС	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	200	_			250	_	_	_	300	_	_	
Clock to I/O Output	t _{PHL}	4.5	l —	40	 	45		50	_	56	_	60	-	68	
(Fig. 4)		6		34				43	_			51			
Clock to Q0 and Q7		2	_	200	_	_	_	250	_	_		300		_	
(Fig. 4)		4.5		40	_	45	_	50	_	56	-	60	—	68	
		6		34		_	_	43				51			
Propagation Delay	t _{PHL}	2	_	200	_	_	-	250	_	_	_	300	_	_	
MR to Output		4.5	—	40	—	46	_	50		58	_	60	—	69	
(Fig. 5)		6		34			_	43				51		_	
Output High-Z to	t _{PZH}	2	_	155	_	_	_	195	_	_	_	235	_	_	ns
High Level		4.5	_	31		32		39	_	40	-	47	_	48	
(Fig. 6)		6	_	26	-		_	33		_		40		_	
Output High Level	t _{PHZ}	2	-	185	_	_	_	230	_	_	-	280	_	l —	
to High-Z		4.5	_	37	-	37	<u> </u>	46	l —	46		56	_	56	
(Fig. 6)		6	l —	31	-		_	39				48			
Output Low Level	t _{PLZ}	2	_	155	_	_	_	195	_	_	—	235	—	—	
to High-Z		4.5	1 —	31	—	32	_	39	_	40	i —	47	_	48	
(Fig. 7)		6		26		_		33		_		40			
Output High-Z	tezt	2		130	—	-	—	165	-	<u> </u>	-	195			
to Low Level		4.5	-	26		30	_	33	—	38	-	39	_	45	
(Fig. 7)		6		22				28		_	_	33	<u> </u>		
Output Transition Time	t _{TLH}	2	<u> </u>	75	 	_		95	_		_	110	_	-	
Q0, Q7	t _{THL}	4.5	—	15	 	15		19	_	19	_	22	—	22	
(Fig. 9)		6	_	13		_		16	_		_	19	_		
I/O₀ to I/O ₇		2	—	60	—	_	-	75			-	90		_	
(Fig. 9)		4.5	_	12	_	12		15	_	15	-	18	-	18	
		6		10				13			_	15]
Input Capacitance	Cı	_	_	10		10		10	_	10		10		10	
3-State Output	C _o	—	-	20	-	20	-	20	_	20	-	20	_	20	pF
Capacitance												<u> </u>			



74/54 HC	74/54 HCT
Vcc	3 V
50 % V _{CC}	1.3 V
	Vcc

Fig. 4 — Clock pre-requisite and propagation delays.

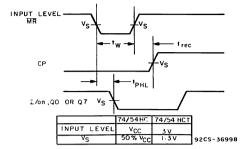
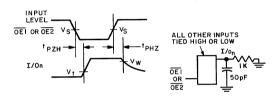
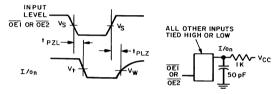


Fig. 5 — Master Reset pre-requisite and propagation delays.



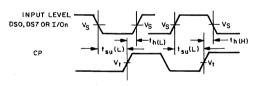
	74/54 HC	74/54 HCT
INPUT LEVEL	v _{cc}	3 V
٧s	50% V _{CC}	1.3 V
٧t	50 % V _{CC}	1.3 V
٧w	90% Vcc	90 % V _{CC}

Fig. 6 — 3-state propagation delays.



	74/54 HC	74 / 54 HCT
INPUT LEVEL	vcc	3 V
٧ _S	50 % V _{CC}	1.3 V
V _f	50 % VCC	1.3V
VW	10% VCC	10% V _{CC}

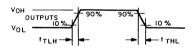
Fig. 7 — 3-state propagation delays.



	74/54 HC	74/54 HCT				
INPUT LEVEL	v _{cc}	3 V				
VS	50 % V _{CC}	1.3 V				
V _t	50 % V _{CC}	1,37				

92CS-3700IRI

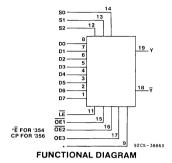
Fig. 8 — Data pre-requisite times.



		74/54 HC	74/54 H CT
INPUT	LEVEL	Vcc	3V
			92 CS - 37002

Fig. 9 — Output transition times.

High-Speed CMOS Logic



8-Input Multiplexer/Register, 3-State

CD54/74HC/HCT354 — Transparent Data & Select Latches CD54/74HC/HCT356 — Edge-Triggered Data Flip-Flops Transparent Select Latches

Type Features:

- Buffered inputs
- 3-State Complementary Outputs
- Bus Line Driving Capability
- Typical propagation delay: V_{CC} = 5V, C_L = 15 pF, T_A = 25° C Data to Output (354) = 18 ns Clock to Output (356) = 22 ns

The RCA-CD54/74HC/HCT354 and CD54/74HC/HCT356 are data selectors/multiplexers that select one of eight sources. In both the HC/HCT354 and HC/HCT356 the data select bits S0, S1, and S2 are stored in transparent latches that are enabled by a low latch enable input, LE.

In the HC/HCT354 the data enable input, \overline{E} , controls transparent latches that pass data to the outputs when \overline{E} is high and latches in new data when \overline{E} is low.

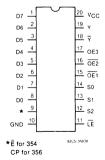
In the HC/HCT356 the data is stored in edge-triggered flip-flops that are triggered by a low-to-high clock transition.

In both types the three-state outputs are controlled by three output-enable inputs $\overline{OE1}$, $\overline{OE2}$, and OE3.

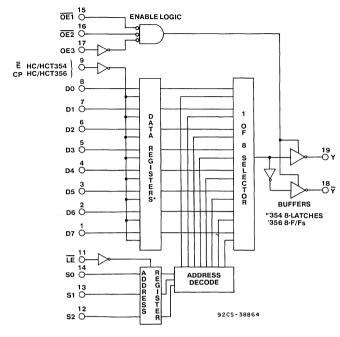
The CD54HC/HCT354/356 are supplied in 20-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT354/356 are supplied in 20-lead plastic dual-in-line plastic packages (E suffix). The CD54/74HC/HCT354/356 are also supplied in chip form (H suffix). The CD74HC/HCT354/356 are also available in plastic surface mounted packages (M suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ Vol. VoH



TERMINAL ASSIGNMENT



Block Diagram

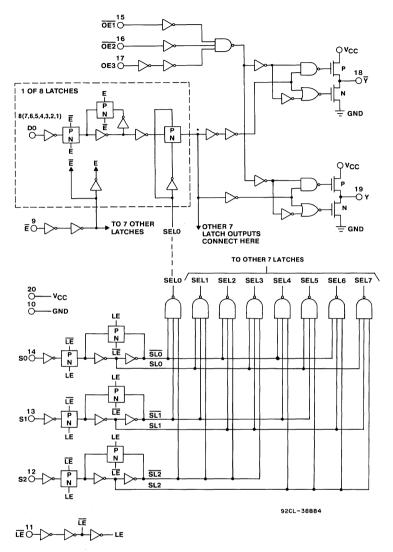
TRUTH TABLE

			Inp	uts					
s	elect	#	Enable Data 'HC354 'HCT354	Clock 'HC356 'HCT356		Outpu		Outp	outs
S2	S1	SO	E	СР	OE1	OE2	OE3	Y	Y
X	Х	X	Х	Х	Н	Х	Х	Z	Z
X	Χ	Χ	X	×	Х	Н	Χ	Z	Z
X	Χ	Χ	X	×	Х	Χ	Ł	Z	Z
L	L	L	L		LLH		Н	D0	D0
L	L	L	Н	HorL	H or L L		Н	DO _n	$D0_n$
L	L	Н	L		_~ L L		Н	D1	D1
L	L	Н	Н	HorL	L	L	Н	$\overline{D1}_n$	D1 _n
L	Н	L	L		L	L	Н	D2	D2
L	Н	L	н	H or L	L	L	Н	D2 _n	$D2_n$
L	Н	Н	L		L	L	Н	D3	D3
L	Н	F3	Н	HorL	L	L	Н	D3 _n	$D3_n$
Н	L	L	L		L	L	Н	D4	D4
H	L	L	Н	HorL	L	L	Н	D4 _n	D4 _n
Н	L	Н	L	_	L	L	Н	D5	D5
Н	L	Н	Н	HorL	. L L H		Н	D5 _n	$D5_n$
H	Н	L	L		L	L	Н	D6	D6
Н	Н	L	Н	HorL	L	L	Н	D6 _n	D6 _n
H	Н	Н	L		L	L	Н	D7	D7
H	Н	Н	Н	HorL	l L	L	Н	D7,	D7.

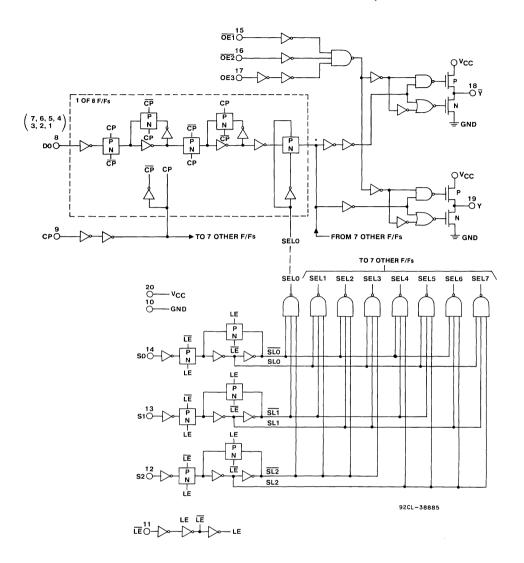
- Notes H = high level (steady state) L = low level (steady state)

- L = low level (steady state)
 X = irrelevant (any input, including transitions)
 Z = high-impedance state (off state)

 = transition from low to high level
 D0 ... D7 = the level of steady-state inputs at inputs D0 through D7,
- $D_0 \dots D_7$ the level of steady-state injures at injuris 20 through D_7 , respectively, at the time of the low-to-high clock transition in the case of HC356 $D0_n \dots D7_n =$ the level of steady state inputs D0 through D7, respectively, before the most recent low-to-high transition of data control
- # This column shows the input address setup with $\overline{\text{LE}}$ low



HC/HCT354 Logic Diagram



HC/HCT356 Logic Diagram

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc)	
(Voltages referenced to ground)	0.5 to +7V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_i < -0.5$ V OR $V_i > 0.5$ V + V_{CC})	±20mA
DC DRAIN CURRENT, PER OUTPUT (I ₀) (FOR -0.5 V $<$ V _o $<$ V _{cc} $+$ 0.5V)	±35mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±70mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	
For T _A = +60 to +85°C (PACKAGE TYPE E)	8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tsig)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range)			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage V _I , V _O	0	V _{CC}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	1
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

	CD74HC354/356/CD54HC354/356											D74H	CT35	4/356	/CD54	нст	354/3	56		
CHARACTERISTIC	TEST CONDITIONS			1	74HC/54HC 74HC TYPE TYPE				HC PE	TEST CONDITIONS		74HCT/54HCT TYPE			74HCT TYPE		54HCT TYPE			
CHARACTERISTIC	V,	l _o	V _{cc}		+25° C	;		0/ 5° C	-5 +12		V,	V _{cc}		+25° C	;	1	i0/ 5°C		5/ 5° C	UNITS
	•	mA	\ \ \	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	_	_	2	_	2	_	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	-	to	_	_	0.8	_	0.8	_	0.8	v
			6	_	_	1.8	-	1.8	_	1.8		5.5								
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	-	or	4.5	4.4	_	_	4.4	_	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-6	4.5	3.98	_	-	3.84	_	3.7	_	or	4.5	3.98	_	-	3.84	-	3.7	-	V
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	-	0.1	V _{IL}									
Output Voltage V _{OL}	or	0.02	4.5	_	_	0.1	_	0.1	-	0.1	or	4.5	-	_	0.1	_	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	-	[-	0.1	_	0.1	-	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v
(Bus Driver)	V _{IH}	7.8	6	_	-	0.26	_	0.33	-	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I ₁	or		6	-	_	±0.1		±1	-	±1	Between	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd										V _{cc} & Gnd									
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	_	-	8	-	80	_	160	or	5.5	-	-	8	_	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd								<u></u>	
Additional Quiescent Device Current per input pin: 1 unit load \(\Delta \) lcc*											V _{cc} -2.1	4.5 to	_	100	360	_	450	-	490	μΑ
3-State Leakage Current I _{oz}	V _{IL} or V _{IH}	V _o = V _{cc} or Gnd	6	_	-	±0.5	_	±5.0	_	±10	V _{IL} or V _{IH}	5.5	-	_	±0.5	-	±5.0	-	±10	μΑ

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{cc} = 5.5 V) specification is 1.8 mA.

HCT354 Input Loading Table

Input	Unit Loads*
D0-D7	0.50
S0, S1, S3	0.70
OE1, OE2	0.80
OE3	0.25
<u>LE</u>	0.25
Ē	0.60

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

HCT356 Input Loading Table

Input	Unit Loads*
D0-D7	0.50
S0, S1, S3	0.70
ŌĒ1, ŌĒ2	0.80
OE3	0.25
Œ	0.25
СР	0.60

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns) — HC/HCT354

CHARACTERISTIC	CL	SYMBOL	TYP	UNITS	
CHARACTERISTIC	(pF)	STWBOL	54/74HC	54/74HCT	ONTIS
Propagation Delay Dn → Y, Ÿ	15	t _{PLH} , t _{PHL}	18	20	ns
Ē → Y, ▼	15	t _{PLH} , t _{PHL}	21	23	ns
Sn→ Y, \overline{Y}	15	t _{PLH} , t _{PHL}	22	25	ns
ĪĒ →Y, Ÿ	15	t _{PLH} , t _{PHL}	24	25	ns
Output Disabling Time	15	t _{PLZ} , t _{PHZ}	13	13, 16	ns
Output Enabling Time	15	t _{PZL} , t _{PZH}	12, 13	14	ns
Power Dissipation Capacitance*	_	C _{PD}	90	92	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per device.

PREREQUISITE FOR SWITCHING FUNCTION -- HC/HCT354

				25	°C		-4	0°C to	o +85°	C	-5	5°C to	+125	°C	1
CHARACTERISTIC	SYMBOL	V_{cc}	Н	С	Н	CT	741	НС	74F	ICT	54	НС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
E pulse width		2	80	_	_		100	_	_	_	120	_	_	_	
	t _{PLH}	4.5	16		16	_	20	—	20	_	24	—	24	_	ns
	t _{PHL}	6	14	_		_	17		 		20		_	_	
LE pulse width		2	80	—	_	_	100	_	_		120	_	_	_	
	t _{PLH}	4.5	16	_	16	_	20	l —	20	_	24	_	24	_	ns
	t _{PHL}	6	14	—	<u> </u>	—	17	-	_	_	20		-	_	
Set Up Times		2	50	_	_		65	l –	_	—	75	_	_	_	
Dn → E	tsu	4.5	10	—	10	l —	13		13	_	15	-	15	 -	ns
		6	9	_	_		11	_	_	<u> </u>	13	<u> </u>		_	
		2	50	_	_	_	65	_	_	-	75	-	_	_	
Sn → LE	tsu	4.5	10	-	10	 	13	<u> </u>	13	_	15	-	15	—	ns
		6	9				11	_			13				
Hold Times		2	45	-	_	_	55	_	-	—	70	-		_	
Dn→Ē	tн	4.5	9	-	9	l —	11	_	11	_	14	l —	14	-	ns
		6	8	<u> </u>		_	9	_	_	—	12			_	
		2	45	_	_	_	55	_	_	_	70		_	_	
Sn → LE	t _H	4.5	9	_	9	-	11	-	11	—	14	—	14		ns
		6	8			<u>l – </u>	9	<u> </u>	<u> </u>		12	<u> </u>		<u> </u>	

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where:

f_i = input frequency,

C_L = output load capacitance.

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_l = 6 ns) — HC/HCT354

				25			-4	0°C t∈	o +85°	С	-5	5°C to	+125	°C		
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	СТ	741	HC	74H	ICT	541	НС	54H	ICT_	UNITS	
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Propagation Delay,	t _{PLH}	2	_	210	_	_	_	265	_	_	_	315	_	_		
Dn → Y, \overline{Y}	t _{PHL}	4.5	-	42		47	_	53	_	59	_	63	_	71	ns	
		6	_	36	_			45	_	_	_	54		_		
		2	_	250	_	_	_	315	_	_	_	375	_	_		
Ē→Y, Ÿ	t _{PLH}	4.5	-	50		54	_	63	—	68	_	75	<u> </u>	81	ns	
	t _{PHL}	6		43				54		_	_	64				
		2	—	260		l —	_	325	-	-	—	390	_	-		
Sn → Y, \overline{Y}	t _{PLH}	4.5		52	l —	59	_	65	-	74	_	78	_	89	ns	
Трн	t _{PHL}	6	<u> </u>	44				55		_		66	_			
		2	_	290	_	-		365	_	_	—	435	-	_		
	t _{PLH}	4.5	_	58	—	63	_	73	-	79	-	87	_	94	ns	
	t _{PHL}	6	—	49			<u> </u>	62		_		74		_		
Output Disabling		2	T-	155	_	_	_	195	-	-	_	235	-	_		
Time		4.5	_	31	—	33	_	39	-	41	-	47	-	50		
OEn to Y, Y	t _{PLZ}	6	-	26		_	_	33		_	_	40		_	ns	
	t _{PHZ}	2	_	155	_	_	_	195	-	_	-	235	-	_	115	
OE3 to Y, \overline{Y}		4.5	_	31	_	39	_	39	_	49	-	47	-	59		
		6	-	26			_	33		_	_	40	_	<u> </u>		
Output Enabling		2	T —	150		_	_	190	_	_	_	225	_	_		
Time	1	4.5	_	30		34	—	38	-	43	_	45		51		
OEn to Y, Y	t _{PZL}	6	_	26	l —	_	 -	33	-	l –	_	38			ns	
	t _{PZH}	2	_	160	_	_	_	200	_	_	_	240	_	_] 115	
OE3 to Y, \overline{Y}	17211	4.5	_	32	_	34	_	40	_	43	_	48	_	51		
		6	-	27		_		34	_		-	41	_	_		
		2	T —	60	_	_	_	75	T -	_	_	90	-	-		
Output	t _{TLH}	4.5	-	12	_	12	 -	15	-	15	_	18	-	18	ns	
Transition Time	t _{THL}	6	l –	10		<u> </u>	<u> </u>	13		_		15				
Input																
Capacitance	Cı		-	10	_	10	-	10	-	10	-	10	-	10	pF	
3-state									†							
Output	Co		-	20	-	20	-	20	-	20	-	20	-	20	pF	
Capacitance																

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r , t_r = 6 ns) — HC/HCT356

CHARACTERISTIC	CL	SYMBOL	TYP	ICAL	UNITS	
CHARACTERISTIC	(pF)	STIVIBUL	54/74HC	54/74HCT	UNITS	
Propagation Delay CP → Y, \overline{Y}	15	t _{PLH} , t _{PHL}	22	22	ns	
Sn→Y, \(\nabla\)	15	t _{PLH} , t _{PHL}	22	25	ns	
ĪĒ → Y, Ÿ	15	t _{PLH} , t _{PHL}	24	25	ns	
Output Disabling Time	15	t _{PLZ} , t _{PHZ}	13	13, 15	ns	
Output Enabling Time	15	t _{PZL} , t _{PZH}	12, 13	14	ns	
Power Dissipation Capacitance*	_	C _{PD}	51	52	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per device.

 $P_D = V_{CC}^2 f_i(C_{PD} + C_L)$ where:

 f_i = input frequency.

C_L = output load capacitance.

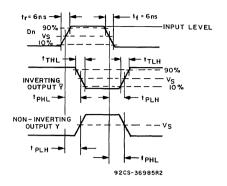
V_{cc} = supply voltage.

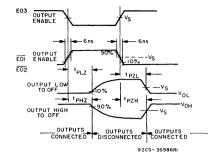
PREREQUISITE FOR SWITCHING FUNCTION — HC/HCT356

				25	°C		-4	0°C te	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	н	СТ	74	нс	74F	ICT	54	нс	54F	I CT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
CP Pulse Width		2	80		_	_	100	_	_		120	_	_	_	
	t _{PLH}	4.5	16	l —	20	l —	20	_	25	_	24	_	30	_	ns
	t _{PHL}	6	14	—	_	_	17	_	_	_	20	l –			
LE Pulse Width		2	80	_		_	100		_		120	_	_	_	
	t _{PLH}	4.5	16		20	_	20		25	_	24	_	30	_	ns
	t _{PHL}	6	14		_	_	17			_	20				
Set Up Times		2	5	_	_	_	5	_		_	5	_		_	
Dn → CP	t _{su}	4.5	5	-	7	_	5	_	9		5		11	—	ns
		6	5	_	_	_	5		_		5		_	_	
		2	5	_	_	_	5		_	_	5	_	_	_	
Sn →LE	t _{su}	4.5	5	_	7		5	_	9	l —	5	—	11		ns
		6	5	_		—	5	_	_	_	5			_	
Hold Times		2	45		_	_	55	_		_	70	_	_	_	
Dn → CP	th	4.5	9		9	—	11	_	11		14	—	14	_	ns
		6	8		_		9	_	_	_	12	_		-	
		2	60	_		_	75	_	-		90	_	_	_	
Sn → LE	t _h	4.5	12	—	12	_	15	—	15	_	18	-	18	_	ns
		6	10		<u> </u>		. 13				15			<u> </u>	

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns) — HC/HCT356

				25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C_	
CHARACTERISTIC	SYMBOL	V _{cc}	Н	IC	Н	СТ	74	нс	74F	ICT	54	нс	54F	1CT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay:		2	_	255	_	_	_	320	_	_	_	385		_	
CP →Y, \overline{Y}	t _{PLH}	4.5	_	51		51		64	_	64	_	77		77	ns
	t _{PHL}	6	-	43	_	_	_	54	_		_	65	_	-	
		2	T -	260	_			325		_	_	390	_	_	
Sn → Y, \overline{Y}	t _{PLH}	4.5		52	_	59	_	65	-	74	_	78	_	89	ns
	t _{PHL}	6	-	44	-		_	55	_	<u> </u>	_	66	-	_	
		2	-	290	_	_	-	365	—	-	_	435	-	_	
ĪĒ →Y, Ÿ	t _{PLH}	4.5	-	58	l —	63	_	73	—	79	—	87	_	94	ns
	t _{PHL}	6	_	49	l —		_	62	_	_	-	74			
Output Disabling			_	155	_	_	_	195	_	-	-	235	_	_	
Time			_	31	—	33	_	39	-	41	_	47	-	50	
OE1, OE2 to Y, Y	t _{PLZ}	2 4.5	-	26	_	l —	—	33	_		_	40			- ns
OE3 to Y, Y	t _{PHZ}	4.5 6		155	I —	—	_	195	-	_	_	235	_		113
		6	-	31	_	37	_	39		46	-	47	-	56	
			-	26	_			33				40			
Output Enabling			Τ-	150	_	_	_	190	_	_	_	225	-	-	
Time			_	30	_	34	_	38	-	43	-	45	-	51	
\overline{OE} 1, \overline{OE} 2 to Y, \overline{Y}	t _{PZL}	2 4.5	_	26	_		_	33				38		_	ns
OE3 to Y, Y	t _{PZH}	4.5		160		_	_	200			_	240	_	-	113
	Ì	٥	_	32	_	34	-	40	-	43	-	48	-	51	
				27	_	<u> </u>	_	34				41	<u></u>		
Output	t _{TLH}	2	T -	60	—	T -	_	75	_	-	-	90	-	-	
Transition Time	tTHL	4.5	-	12	-	12	-	15	-	15	-	18	-	18	ns
	THE	6		10		<u> </u>	_	13	_	<u> </u>	_	15		<u> </u>	
Input Capacitance	C		_	10	_	10	_	10	_	10	_	10	_	10	pF
	-		+	-	1	-	-	+	 	+-	-	+	+	+	 '
3-state Output	Co		-	20	_	20	_	20	_	20	_	20	_	20	pF
Capacitance															





	54/74HC	54/74HCT
Input Level	V _{CC}	3 V
Vs	50% V _{CC}	1.3 V

Fig. 1 — Transition times and propagation delay times.

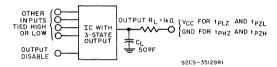
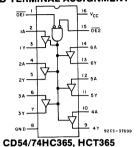


Fig. 2 — Three-state propagation delay test circuit.

High-Speed CMOS Logic

FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT



Hex Buffer/Line Driver, 3-State Non-Inverting and Inverting

Type Features:

- Buffered Inputs
- High Current Bus Driver Outputs
- Typical Propagation Delay t_{PLH}, t_{PHL} = 8 ns @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C

The RCA-CD54/74HC365/366 and CD54/74HCT365/366 silicon gate CMOS 3-STATE buffers are general purpose high speed non-inverting and inverting buffers. They have high drive current outputs which enable high speed operation even when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuitry, yet have speeds comparable to low power Schottky TTL circuits. Both circuits are capable of driving up to 15 low power Schottky inputs.

The CD54/74HC, HCT365 are non-inverting buffers, whereas the CD54/74HC, HCT366 are inverting buffers. These devices have two 3-State control inputs (OE1 and OE2) which are NORed together to control all six gates.

The CD54/74HCT365 and CD54/74HCT366 logic families are speed, function, and pin compatible with the standard 54LS/74LS logic family.

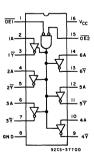
The CD54HC365/366 and CD54HCT365/366 are supplied in 16-lead hermetic dual-in-line packages (F suffix). The CD74HC365/366 and CD74HCT365/366 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30%; @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$

FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT



CD54/74HC366, HCT366

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, lik (FOR Vi < -0.5 V OR Vi > Vcc +0.5 V)	±20 mA
DC OUTPUT CURRENT, lok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < V₀ < Vcc +0.5 V)	±35 mA
DC Vcc OR GROUND CURRENT, PER PIN (Icc):	±70 mA
POWER DISSIPATION PER PACKAGE (PD):	
For TA = -40 to +60°C (PACKAGE TYPE E)	500 mW
For TA = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For TA = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For TA = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

TRUTH TABLES

	Inputs		Outputs
OE ₁	OE ₂	A	Y
L	L	L	L
L	L	Н	н
X	Н	Х	Z
н	×	×	z

CD54/74HC, HCT365

	Inputs		Outputs
OE ₁	OE ₂	A	Y
L	L	L	н
X	H	H X	L Z
Н	×	X	z

CD54/74HC, HCT366



H = HIGH voltage level

Z = High impedance (off) state

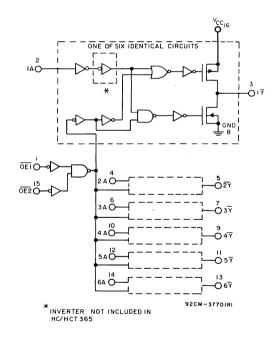


Fig. 1 - Logic diagram for the HC/HCT365 and HC/HCT366. (Outputs for HC/HCT365 are complements of those shown, i.e., 1Y, 2Y etc.)

X = Don't Care

STATIC ELECTRICAL CHARACTERISTICS

		CD74	HC36	5/366	/CD5	4HC3	55/366	6			С	D74H	CT36	5/366	/CD54	нст	365/3	66		
CHARACTERISTIC	1	TEST NDITIONS			IC/54		1	HC PE		HC PE	TEST CONDITION			CT/54 TYPE		1	ICT PE		ICT PE	
CHAHACTERISTIC	V,	I _o	V _{cc}		+25° (;	1	10/ 5°C		5/ 5°C	V,	V _{cc}		+25° C	;		-40/ +85°C		5/ 5°C	UNITS
		mA	•	Min	Тур	Max	Min	Max	Min	Max	ľ	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-	-	1.5	-	1.5	_		4.5								<u> </u>
Input Voltage V _{ін}			4.5	3.15	_	-	3.15	-	3.15	_	l –	to	2	_	_	2	_	2	_	v
			6	4.2	_	_	4.2	_	4.2	-]	5.5								
Low-Level			2	-	_	0.5	-	0.5	-	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	-	1.35	_	1.35	-	to	_	_	0.8	_	0.8	-	0.8	v
			6	_	_	1.8	_	1.8	_	1.8	1	5.5		ì				l		
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	-	4.4	_	4.4	-	or	4.5	4.4	-	_	4.4	_	4.4	_	v
CMOS Loads	V _{IH}		6	5.9	_	-	5.9	_	5.9	-	V _{IH}	}						}		
	V _{IL}										V _{IL}									
TTL Loads	or	-6	4.5	3.98	_	_	3.84	_	3.7	-	or	4.5	3.98	_	_	3.84	-	3.7	_	v
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	-	5.2	_	V _{IM}									
Low-Level	V _{IL}		2	_	_	0.1	_	0.1	-	0.1	V _{IL}									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	-	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads	VIH		6	_	_	0.1	_	0.1	-	0.1	V _{IH}				Ì					
	VIL										V _{IL}									
TTL Loads	or	6	4.5	_		0.26	_	0.33	_	0.4	or	4.5	_	-	0.26	-	0.33	_	0.4	v
(Bus Driver)	V _{IH}	7.8	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any									
Current I,	or		6	_	_	±0.1	_	±1	_	±1	Voltage Between	5.5	_	_	±0.1	-	±1	_	±1	μА
	Gnd										V _{cc} & Gnd			ļ		ļ				
Quiescent	V _{cc}										V _{cc}									
Device	or	О	6	-	_	8	_	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd								1	
Additional Quiescent Device Current per input pin: 1 unit load											V _{cc} -2.1	4.5 to 5.5	-	100	360	_	450	-	490	μΑ
3-State Leakage Current I _{oz}	V _{IL} or V _{IH}	V _o = V _{cc} or Gnd	6	-	_	±0.5	-	±5.0	-	±10	V _{IL} or V _{IH}	5.5	-	-	±0.5	-	±5.0	-	±10	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads *
OE1	0.6
All Others	0.55

^{*}Unit Load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	ITS	LIMITO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	1 1
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (VCC = 5 V, CL = 15 pF, TA = 25°C, Input tr, tr = 6 ns)

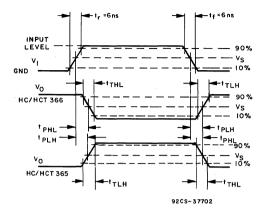
			TYP	ICAL		
CHARACTERISTIC	SYMBOL	3(65	3	66	UNITS
		нс	нст	нс	нст	
Propagation Delay Data to Output	t _{PHL} t _{PLH}	8	9	9	11	ns
Output Enable and Disable to Outputs	tpzH, tpzL, tpHz, tpLz	12	14	12	14	ns
Power Dissipation Capacitance *	C _{PD}	40	42	40	42	pF

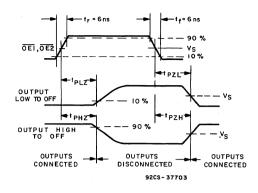
^{*} CPD is used to determine the dynamic power consumption, per buffer.

PD = VCC²fi (CPD + CL) where: fi = input frequency. CL = output load capacitance. VCC = supply voltage.

SWITCHING CHARACTERISTICS (CL = 50 pF, Input tr, tr = 6 ns)

				25	°C		-4	0°C t	o +85°	C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	ıc	Н	СТ	74	нс	74F	ICT	54	нс	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	105	_	_	_	130	_	_	-	160	_	_	
Data to Outputs	t _{PHL}	4.5	-	21	_	25	—	26	-	31	-	32	_	38	ns
HC/HCT365		6	_	18		_	_	22	_		_	27	_	_	
Propagation Delay	t _{PLH}	2	_	110	_	_	_	140	-	_	_	165	_	_	
Data to Outputs	t _{PHL}	4.5	—	22	_	27	_	28	-	34	_	33	_	41	ns
HC/HCT366		6	_	19		_	_	24			_	28			
Propagation Delay	t _{PZH} , t _{PZL} ,	2	_	150	_		_	190		_	_	225	_	-	
Output Enable and	t _{PHZ} , t _{PLZ}	4.5	—	30	_	35	_	38	—	44	_	45	-	53	ns
Disable to Outputs	IPHZ, IPLZ	6	_	26	_	_	_	33		_	_	38		_	
Output Transition	t _{TLH}	2	_	60	_	_	_	75	_	_	_	90	_	_	
Time	t _{THL}	4.5	-	12	_	12	_	15	_	15	-	18	_	18	ns
		6	_	10			_	13			_	15		_	
Input Capacitance	Cı		_	10	_	10	_	10	_	10	_	10		10	pF
3-State Output Capacitance	Co		_	20	_	20	_	20	_	20	_	20		20	pF





	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, Vs	50% VCC	1.3 V

Fig. 2 - Transition times and propagation delay times.

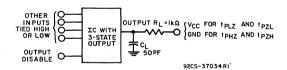


Fig. 3 - Three-stage propagation delay test circuit.

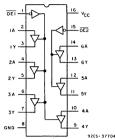
File Number 1538

Advance Information/ Preliminary Data

CD54/74HC367, CD54/74HCT367 CD54/74HC368, CD54/74HCT368

High-Speed CMOS Logic

FUNCTIONAL DIAGRAM



CD54/74HC367, HCT367

Hex Buffer/Line Driver, 3-State

Non-Inverting and Inverting

Type Features:

- Buffered inputs
- High current bus driver outputs
- Two independent 3-state enable controls
- Typical propagation delay t_{PHL} , t_{PLH} = 8 ns @ V_{cc} = 5 V, C_L = 15 pF

The RCA-CD54/74HC367, 368 and CD54/74HCT367, 368 silicon gate CMOS 3-state buffers are general-purpose high-speed non-inverting and inverting buffers. They have high drive current outputs which enable high-speed operation even when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuitry, yet have speeds comparable to low power Schottky TTL circuits. Both circuits are capable of driving up to 15 low power Schottky inputs.

The CD54/74HC, HCT367 are non-inverting buffers, whereas the CD54/74HC, HCT368 are inverting buffers. These devices have two output enables, one enable (OE1) controls 4 gates and the other (OE2) controls the remaining 2 gates.

The CD54/74HCT367 and CD54/74HCT368 logic families are speed, function, and pin compatible with the standard 54LS/74LS logic family.

The CD54HC367 and CD54HCT367 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC367 and CD74HCT367 are in 16-lead dual-in-line plastic packages (E suffix), also in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30%; @ V_{CC} = 5 V
- INIL 30%, Niii 30%; Q Vcc = 5 V

 CD54HCT/CD74HCT Types:

 4.5 to 5.5 V Operation

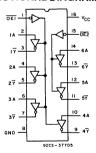
 Direct LSTTL Input Logic Compatibility

 VIL = 0.8 V Max., VIII = 2 V Min.

 CMOS Input Compatibility

 III., III ≤ 1 µA @ VoL, VOH

FUNCTIONAL DIAGRAM



CD54/74HC368, HCT368

MAXIMUM RATINGS, Absolute-Maximum Values:

	DC SUPPLY-VOLTAGE, (V _{cc}):
-0.5 to + 7 V	(Voltages referenced to ground)
±20mA	DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5 \ V$ OR $V_i > V_{CC} + 0.5 V) \ \ldots$
±20mA	DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o <$ -0.5 V OR $V_o > V_{CC}$ +0.5V) .
±35mA	DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Vo $<$ Vcc $+$ 0.5V)
±70mA	DC Vcc OR GROUND CURRENT (Icc)
	POWER DISSIPATION PER PACKAGE (PD):
500 mW	For $T_A = -40$ to $+60^{\circ}$ C (PACKAGE TYPE E)
Derate Linearly at 8 mW/°C to 300 mW	For T _A = +60 to +85° C (PACKAGE TYPE E)
500 mW	For $T_A = -55$ to $+100^{\circ}$ C (PACKAGE TYPE F, H)
Derate Linearly at 8 mW/°C to 300 mW	For T _A = +100 to +125°C (PACKAGE TYPE F. H)
	For T _A = -40 to +70°C (PACKAGE TYPE M)
Derate Linearly at 6 mW/°C to 70 mW	For T _A = +70 to +125° C (PACKAGE TYPE M)
	OPERATING TEMPERATURE RANGE (T _A)
55 to +125° C	PACKAGE TYPE F, H
40 to +85° C	PACKAGE TYPE E, M
-65 to +150° C	STORAGE TEMPERATURE (T _{stq})
	LEAD TEMPERATURE (DURING SOLDERING):
+265° C	At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max
contacting lead tips only+300°C	Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder

TRUTH TABLES

Inp	outs	Outputs
ŌĒ	Α	Y
L	L	Ĺ
L	Н	Н
Н	X	(Z)
	CDE 4/7411	C LICTOCT

CD54/74HC, HCT367

Inp	uts	Outputs	
ŌE	Α	Y	
L	L	Н	
L	н	L	
н	x	(Z)	
	0000000000		

CD54/74HC, HCT368

- L = LOW voltage level.
- H = HIGH voltage level.
- X = Don't care.
- (Z) = High impedance (off) state.

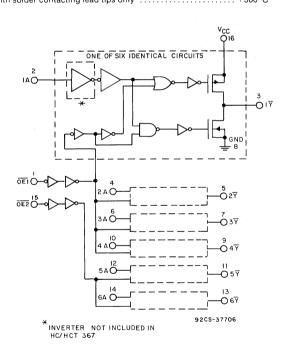


Fig. 1 - Logic diagram for HC/HCT367 and HC/HCT368. (Outputs for HC/HCT367 are complements of those shown, i.e., 1Y, 2Y, etc.).

STATIC ELECTRICAL CHARACTERISTICS

			CD7	4HC3	67/36	8/CD	54HC	367/3	68			CE	74HC	T367/3	168/CI	D54H	CT36	7/368			
		i	TEST CONDITIONS						54H TYI		TEST	ns		TYPE		74H TY		54H TY			
CHARACTERISTIC	cs	V,	Io	Vcc		-25° C	;	-4 +85		-5: +12:		V ₁	V _{cc}		•25° C		-4 +85		-5 +12		UNITS
		v	mA	v	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	ViH			4.5	3.15	_		3.15	_	3.15	_	_	to	2	_	_	2	_	2	-	v
				6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level				2	_	_	0.5		0.5	_	0.5		4.5					l			
Input Voltage	V_{IL}			4.5	<u> </u>	_	1.35	_	1.35	_	1.35	_	to	-	-	0.8	-	8.0	–	8.0	V
				6	_	_	1.8	_	1.8		1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9		1.9	_	VIL				ļ			1		
Output Voltage	V_{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	–	4.4	-	4.4	-	V
CMOS Loads		VIH		6	5.9	_	_	5.9	_	5.9		V _{IH}		ļ			<u> </u>				
		VIL			ļ				<u> </u>	<u> </u>		VIL									
TTL Loads		or	-6	4.5	3.98	_	<u> </u>	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	V
(Bus Driver)		ViH	-7.8	6	5.48			5.34	_	5.2	_	V _{IH}									
Low-Level		VIL		2	_		0.1	_	0.1	<u> </u>	0.1	VIL					Ì				
Output Voltage	V_{OL}	or	0.02	4.5	_		0.1		0.1	_	0.1	or	4.5	-	-	0.1	-	0.1		0.1	V
CMOS Loads		V _{IH}		6		=	0.1	_	0.1		0.1	V _{IH}		_	_		ļ.,	-			
		VIL										VIL									
TTL Loads		or	6	4.5	_		0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	l v
(Bus Driver)		ViH	7.8	6	_	_	0.26	_	0.33	_	0.4	V _{IH}		-			ļ	ļ	<u> </u>		
Input Leakage Current	l _t	V _{cc} or Gnd		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	-	±1	_	±1	μА
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6	_	_	8	_	80	_	160	V _{cc} or Gnd	5.5	_	_	8	_	80	 -	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	ΔΙςς*				•			-				V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μА
3-State Leakage Current	loz	V _{IL} or V _{IH}	V _o = V _{cc} or Gnd	6	_	_	±0.5	_	±5	_	±10	V _{IL} or V _{IH}	5.5	-	_	±0.5	5 —	±5	_	±10	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS*
ŌE1	0.6
ALL OTHERS	0.55

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CUADACTERISTIC	LIN	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	ONITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} .*			
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°c
CD54 Types	-55	+125	"
Input Rise and Fall Times tr, tr			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (Vcc=5 V, CL=15 pF, TA=25°C, Input tr,tr=6 ns)

01101077710710			TYP	TYPICAL					
CHARACTERISTIC	SYMBOL	3	67	3	UNITS				
		нс	нст	нс	нст				
Propagation Delay	t _{PHL}								
Data to Output	tpLH	8	9	9	11	ns			
Output Enable and Disable to Outputs	t _{PZH} , t _{PZL} , t _{PHZ} , t _{PLZ}	12	14	12	14	ns			
Power Dissipation Capacitance *	C _{PD}	40	42	40	42	pF			

^{*}CPD is used to determine the dynamic power consumption, per buffer.

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,,t=6 ns)

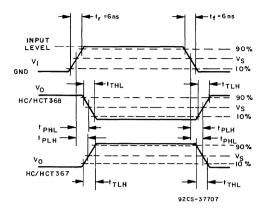
				25	°C		-4	0°C to	o +85°	C	-5				
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	CT	74	НС	74F	ICT	54	нс	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Ī
Propagation Delay	t _{PLH}	2	_	105	_	_	_	130	_	_	_	160	_	_	
Data to Outputs	t _{PHL}	4.5	_	21	—	25	—	26	—	31	—	32	-	38	ns
HC/HCT367		6	_	18	l —	l —	-	24	—		l —	27	l —	—	
Propagation Delay	t _{PLH}	2	_	105	_	_	_	130	_	_	_	160	_	_	
Data to Outputs	t _{PHL}	4.5	_	21	l —	30	l —	26	—	38	·	32	_	45	ns
HC/HCT368	1	6	_	18	_	-	_	24	-	_	—	27	_	_]
Propagation Delay	t _{PZH} , t _{PZL} ,	2	_	150		_	_	190	_	_	_	225			
Output Enable & Disable		4.5	_	30	_	35	<u> </u>	38		44		45	_	53	ns
to Outputs	t _{PHZ} , t _{PLZ}	6	l —	26	_	-	_	33	_	_		38	_	_	
Output Transition	t _{TLH}	2	_	60	_	_	T-	75	_	_	_	90		_	
Time	t _{THL}	4.5	_	12	.—	12		15	l —	15	l —	18	_	18	ns
		6	_	10	_	_	l —	13	_	_	_	15	_	l —	
Input Capacitance	Cı		_	10	_	10	_	10	_	10	_	10	_	10	pF
3-State Output		,		20		100		00		20		20		20	
Capacitance	Co		-	20	-	, 20	_	20	-	20		20	_	20	pF

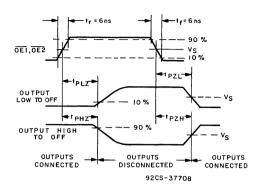
PD = $V_{CC}^2 f_i (C_{PD} + C_L)$ where:

f = input frequency

C_L = output load capacitance

V_{cc} = supply voltage





Input Level	54/74HC	54/74HCT
input Level	VCC	3 V
Switching Voltage, VS	50% VCC	1.3 V

Fig. 2 - Transition times and propagation delay times.

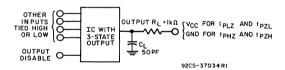
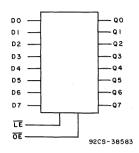


Fig. 3 - Three-state propagation delay test circuit.

High-Speed CMOS Logic



Octal Transparent Latch, 3-State Output

Type Features:

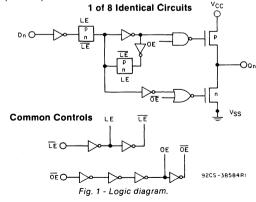
- Common latch enable control
- Common 3-state output enable control
- Buffered inputs
- 3-State outputs
- Bus line driving capacity
- Typical propagation delay = 12 ns @ V_{CC} = 5V, C_L = 15 pF, T_A = 25° C (Data to Output for HC373)

FUNCTIONAL DIAGRAM

The RCA CD54/74HC373/573 and CD54/74HCT373/573 are high speed Octal Transparent Latches manufactured with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LSTTL devices. The CD54/74HCT373/573 are functionally as well as pin compatible with the standard 54/74LS373 and 573.

The outputs are transparent to the inputs when the latch enable (\overline{LE}) is high. When the latch enable (\overline{LE}) goes low the data is latched. The output enable (\overline{OE}) controls the 3-state outputs. When the output enable (\overline{OE}) is high the outputs are in the high impedance state. The latch operation is independent to the state of the output enable. The 373 and 573 are identical in function and differ only in their pinout arrangements.

The CD54HC/HCT373/573 are supplied in 20 lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT373/573 are supplied in a 20-lead plastic dual-in-line plastic package (E suffix) and in 20-lead surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types:
 - 2 to 6 V Operation
 - High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC};
 - @ Vcc = 5 V
- CD54HCT/CD74HCT Types:
 - 4.5 to 5.5 V Operation
 - Direct LSTTL Input Logic Compatibility
 - $V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.$
 - CMOS Input Compatibility
 - $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$

TRUTH TABLE

	Output Enable	Latch Enable	Data	Output
	٦	H	н	н
}	L	н	L	L
	L	L	l '	L
	L	L	h	н
	Н	x	×	z

Note:

- L = Low voltage level
- X = Don't Care
- H = High voltage level
- Z = High Impedance State
- I = Low voltage level one set-up time prior to the high to low latch enable transition
- h = High voltage level one set-up time prior to the high to low latch enable transition

MAXIMUM RATINGS, Absolute-Maximum Values:

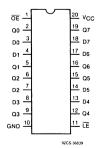
DC SUPPLY-VOLTAGE, (V _{cc}): (Voltages referenced to ground)	-0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_I < -0.5$ V OR $V_I > V_{CC} + 0.5$ V)	
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	
DC DRAIN CURRENT, PER OUTPUT (I ₀) (FOR -0.5 V < V ₀ < V _{cc} +0.5 V)	±35 mA
DC V _{CC} OR GROUND CURRENT, (I _{CC}):	±70 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125° C (PACKAGE TYPE M)	. Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (T _{stg})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

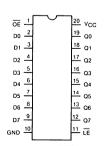
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

011000000000000000000000000000000000000	LIN		
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	v
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _f			
at 2 V	o	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.



CD54/74HC373, CD54/74HCT373 TERMINAL ASSIGNMENT



CD54/74HC573, CD54/74HCT573 TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

					74HC 74HC									774HCT373/CD54HCT373 774HCT573/CD54HCT573							
		ı	TEST DITION	NS	1	IC/54	нс	74H		54H TYI		TEST	ons	74HC	T/54	нст	74H TY		54H TYI	- 1	
CHARACTERISTI	CS	V,	l _o	Vcc	+	-25° C	:	-41 +85		-5: +12:		V,	Vcc	•	25°C		1	0/ 5° C	-5! +12!		UNITS
		٧	mA	v	Min	Тур	Max	Min	Max	Min -	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_		1.5	_	1.5	_		4.5							·	
Input Voltage	V_{IH}		ĺ	4.5	3.15	_	_	3.15	_	3.15	_	-	to	.2	_	_	2	-	2	-	٧
				6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5					İ			
Input Voltage	V_{IL}			4.5		_	1.35	_	1.35		1.35	- 1	to	-	_	0.8	-	0.8	-	0.8	٧
-				6	_	_	1.8	<u></u>	1.8		1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage	V_{OH}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	–	4.4	-	4.4	_	٧
CMOS Loads		ViH		6	5.9		_	5.9	-	5.9		V _{IH}					<u> </u>				
		VIL)	L								VIL									
TTL Loads		or	-6	4.5	3.98	L_	_	3.84		3.7	_	or	4.5	3.98	_	_	3.84	-	3.7	- '	٧
(Bus Driver)		V _{IH}	-7.8	6	5.48			5.34		5.2	_	ViH									
Low-Level		VIL		2	_		0.1		0.1		0.1	VIL						ı			
Output Voltage	V_{OL}	or -	0.02	4.5		_	0.1		0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads		ViH		6		_	0.1		0.1		0.1	V _{IH}									
		VIL										V _{IL}	Ì	1	ł						
TTL Loads		or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v
(Bus Driver)		VIH	7.8	6	_	_	0.26	_	0.33	-	0.4	V _{IH}									
Input Leakage Current	l _i	V _{cc} or Gnd		6	_	_	±0.1	_	±1	-	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	-	±1	_	±1	μΑ
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6	_		8	_	80	_	160	V _{cc} or Gnd	5.5	_	_	8	_	80	_	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	Δlcc*			•	•				•			V _{cc} -2.1	4.5 to 5.5	-	100	360	-	450	_	490	μΑ
3-State Leakage Current		V _{IL} or V _{IH}	V _o =V _{co} or Gnd	6	-	-	±0.5	-	±5	-	±10	V _{IL} or V _{IH}	5.5	-	-	±0.5	5 -	±5	-	±10	μА

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INDUT	UNIT LOADS *					
INPUT	HCT373	HCT573				
ŌĒ	1.5	1.25				
Dn	0.4	0.3				
LE:	0.6	0.65				

^{*} Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input $t_{\rm f}$ $t_{\rm f}$ = 6 ns)

		TYPICAL	UNITS		
CHARACTERISTIC	C∟ (pF)	нс	нст	Julia	
Propagation Delay					
Data to Qn Output (HC/HCT373)	t _{PLH}	15	12	13	ns
(Fig. 3)	t _{PHL}				
Data to Qn Output (HC/HCT573)	t _{PLH}	15	14	17	ns
(Fig. 3)	t _{PHL}	15	14		115
LE to Qn Output	t _{PLH}	15	14	14	ns
(Fig. 4)	t _{PHL}	15	14	14	115
Output Enabling Time	t _{PZL}	15	12	14	ns
(Fig. 6, 7)	t _{PZH}	15	12	14	115
Output Disabling Time	t _{PLZ}	15	12	14	
(Fig. 6, 7)	t _{PHZ}	15	12	14	ns
Power Dissipation Capacitance (HC/HCT573, 373)	C _{PD} *	_	51	53	pF

^{*}CPD determines the no-load dynamic power consumption per latch. It is obtained by the following relationship;

PRE-REQUISITE FOR SWITCHING FUNCTION

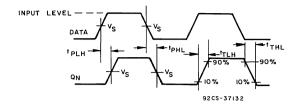
	LIMITS														
CHARACTERIS			25° C					0°C to	+85°	С	-55°C to +125°C				UNITS
CHARACTERIS	TIC	CONDITIONS	Н	C	н	СТ	741	нс	74F	СТ	54	нс	54F	ЮТ	UNITS
		V _{cc} V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
LE Pulse Width	tw	2	80	_	_	_	100	_	_	_	120	_	_	_	
(Fig. 3)		4.5	16	_	16	_	20	_	20	—	24	-	24	—	ns
		6	14	<u> </u>	_	_	17			_	20		<u>L</u>		
Set-up Time	tsu	2	50	-	_	—	65	—		—	75	-	-	_	
Data to LE	573	4.5	10	-	13	_	13	_	16	-	15	_	20	-	ns
(Fig. 4)		6	9	<u> </u>	_		11				13				
Set-up Time	tsu	2	50	-	—	—	65	-	\ —	—	75	<u> </u>	-	-	1
Data to LE	373	4.5	10	_	13	_	13		16	—	15	-	20	-	ns
(Fig. 4)		6	9		_	_	11	<u> </u>		_	13	_			
Hold Time	tн	2	40	_		—	50	-	—	—	60	-	—	—	
Data to LE	573	4.5	8	-	10	—	10	_	13	—	12	-	15	-	ns
(Fig. 4)		6	7			_	9			_	10	<u> </u>			
Hold Time	t _H	2	5	-	-	—	5	-	-	—	5	-	-	-	
Data to LE	373	4.5	5	-	10	-	5	-	13	-	5	—	15	-	ns
(Fig. 4)		6	5	_	l —_	_	5	l –			5		—	_	

 P_D (total power per latch) = $V_{CC}^2 f_i (C_{PD} + C_L)$ where f_i = input frequency,

C_L = output load capacitance, V_{CC} = supply voltage

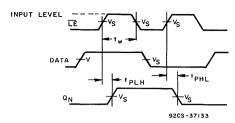
SWITCHING CHARACTERISTICS (Input t, t, = 6 ns, CL = 50 pF)

			LIMITS												
	_	TEST		25	°C		-4	0°C to	+85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC	C	CONDITIONS	Н	С	н	т	741	нс	74 F	ICT	54	нс	54F	ICT	UNITS
-		V _{cc} V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	150	_	_	_	190	_	_	_	225	_	_	
Data to Qn	t _{PHL}	4.5	_	30	—	32	_	38	—	40	_	45	—	48	ns
(Fig. 2) HC/HCT3	73	6		26		_	_	33			_	38			
Data to Qn	t _{PLH}	2		175	-	_	_	220	-	_	_	265	_	-	
(Fig. 2)	t _{PHL}	4.5	_	35	_	40	_	44	_	50	_	53	—	60	ns
HC/HCT573		6		30				37	<u></u>			45			
LE to Qn	t _{PLH}	2	_	175	. —	_	_	220	_	_	_	265	_	-	
	t_{PHL}	4.5	_	35	-	35	_	44	_	44		53	—	53	ns
(Fig. 3)		6		30	_			37				45	<u> </u>		
Output Enabling	t _{PZL}	2	_	150	_	_	_	190	-	_	-	225	-	-	
Time	t _{PZH}	4.5	l —	30	—	35	-	38	—	44	—	45	—	53	ns
(Figs. 5 & 6)		6		26	_	_	_	33	<u> </u>	l <u> </u>		38			
Output Disabling	t _{PLZ}	2	_	150	_	_	_	190	_	_	_	225		_	
Time	t _{PHZ}	4.5	l —	30	-	35	_	38	-	44	—	45	—	53	ns
(Figs. 5 & 6)		6		26				33	_	_		38			
Output Transition	t _{TLH}	2	_	60	_	_	_	75	_	_	_	90	_	-	
Time	t _{THL}	4.5	_	12	-	12	_	15	-	15	-	18	-	18	ns
(Fig. 2)		6	_	10		_		13	_			15	_		
Input Capacitance	Cı	_	_	10		10	_	10		10		10		10	pF
3-State Output Capacitance	Со	_	_	20	_	20		20	_	20	_	20	_	20	pF



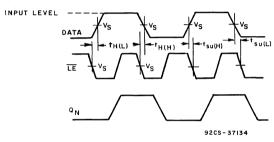
	54/74HC	54/74HCT		
Input Level	Vcc	3 V		
Vs	50% V _{cc}	1.3 V		

Fig. 2 - Data to Q_n output propagation delays and output transition times.



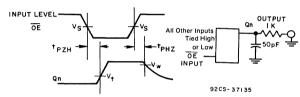
	54/74HC	54/74HCT			
Input Level	Vcc	3 V			
Vs	50% V _{cc}	1.3 V			

Fig. 3 - Latch enable propagation delays.



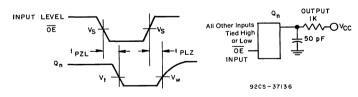
	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Vs	50% V _{cc}	1.3 V

Fig. 4 - Latch enable prerequisite times.



	54/74HC	54/74HCT
Input Level	Vcc	3 V
Vs	50% V _{cc}	1.3 V
Vt	50% V _{cc}	1.3 V
Vw	90% V _{cc}	90% V _{cc}

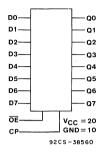
Fig. 5 - Three-state propagation delays.



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Vs	50% V _{cc}	1.3 V
Vt	50% V _{cc}	1.3 V
V _w	10% V _{cc}	10% V _{cc}

Fig. 6 - Three-state propagation delays.

High-Speed CMOS Logic



Octal D-Type Flip-Flop, 3-State Positive-Edge Triggered

Type Features:

- Common 3-State Output Enable Control
- Buffered Inputs
- 3-State Outputs
- Bus Line Driving Capability
- Typical Propagation Delay (Clock to Q) = 15 ns @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C

FUNCTIONAL DIAGRAM

The RCA CD54/74HC374/574 and CD54/74HCT374/574 are Octal D-Type Flip-Flops with 3-State Outputs and the capability to drive 15 LSTTL loads. The eight edge-triggered flip-flops enter data into their registers on the LOW to HIGH transition of clock (CP). The Output Enable (\overline{OE}) controls the 3-state outputs and is independent of the register operation. When Output Enable (\overline{OE}) is HIGH the outputs will be in the high impedance state. The 374 and 574 are identical in function and differ only in their pinout arrangements.

The CD54HC/HCT374/574 are supplied in 20-lead ceramic dual-in-line packages (F suffix). The CD54HC/HCT374/574 are supplied in a 20-lead plastic dual-in-line plastic package (E suffix) and in 20-lead plastic dual-in-line surface mount plastic packages (M suffix). The CD54HC/HCT374/574 are also supplied in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity:

 $N_{\rm IL}$ = 30%, $N_{\rm IH}$ = 30% of $V_{\rm CC}$; @ $V_{\rm CC}$ = 5 V

■ CD54HCT/CD74HCT Types:

4.5 to 5.5 V Operation

Direct LSTTL Input Logic Compatibility

V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.

CMOS Input Compatibility

I_I ≤ 1 µA @ V_{OL}, V_{OH}

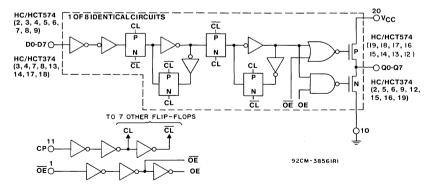


Fig. 1 - Logic diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±35mA
DC V _{CC} OR GROUND CURRENT, PER PIN (I _{CC})	±70mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = ±100 to ±125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	NITS	UNITS	
CHARACTERISTIC	MIN.	MAX.] UNITS	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*				
CD54/74HC Types	2	6	v	
CD54/74HCT Types	4.5	5.5	\ \ \	
DC Input or Output Voltage V _I , V _O	0	V _{cc}	٧	
Operating Temperature T _A :				
CD74 Types	-40	+85		
CD54 Types	-55	+125	°C	
Input Rise and Fall Times t _r , t _f				
at 2 V	0	1000		
at 4.5 V	0	500	ns	
at 6 V	0	400		

^{*}Unless otherwise specified, all voltages are referenced to Ground.

	TRUTH TABLE										
- 11	INPUTS OUTPUTS										
ŌĒ	СР	Dn	Qn								
L	~	Н	Н								
L	~	٦	L								
L	L	Х	Q0								
Н	Х	Х	Z								

HC/HCT374,574

- H = high level (steady state)
- L = low level (steady state)
- X = don't care

 = transition from low to high level

 Q0 = the level of Q before the
- indicated steady-state input conditions were established.
- Z = high impedance

STATIC ELECTRICAL CHARACTERISTICS

						HC37							74HC							
·		TEST NDITIONS	_	l	IC/54 SERIE		74I SEF		54I SER		TEST	ONS	1	T/54 ERIES		74F SEF		54H SEF		
CHARACTERISTIC	V,	l _o	V _{cc}		+25° C	;	-4 +85	0/ 5°C	-5 +12!		V,	V _{cc}	4	•25° C	:	-4 +85		l	5/ 5° C	UNITS
	, V	mA	ď	Min	Тур	Max	Min	Max	Min	Max	V	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	-	3.15	-	3.15	-	-	to	2	_	-	2	-	2	_	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	_	-	0.8	-	8.0	-	0.8	v
			6	_	_	1.8	-	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4		4.4	_	or	4.5	4.4	_	-	4.4	-	4.4	-	v
CMOS Loads	V_{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	VIL										V _{IL}									
TTL Loads	or	-6	4.5	3.98	_	-	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	-	3.7	-	v
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2	_	V _{IH}			}	ļ	}				
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	6	4.5	_	_	0.26	-	0.33	_	0.4	or	4.5	-	-	0.26	_	0.33	-	0.4	v
(Bus Driver)	V _{IH}	7.8	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I,	or		6	-	-	±0.1	-	±1	-	±1	Between	5.5	-	–	±0.1	-	±1	-	±1	μΑ
	Gnd										V _{cc} & Gnd									
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load											V _{cc} -2.1	4.5 to 5.5	-	100	360	-	450	-	490	μΑ
3-State	V _{IL}	V _o = V _{CC}	Γ	Γ	Γ	T-	F	T	Ī		V _{IL}		\vdash			1	1	+		
Leakage Current	or	or	6	_	_	±0.5	_	±5.0	_	±10	or	5.5	_	_	±0.5	_	±5.0	_	<u>±</u> 10	μA
go Guiroin	V.,.	Gnd	-								V _{iH}									
	V .,.	unu		L_		1		L	L		L									

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

1	Unit L	.oads*		
Input	HCT374	HCT574		
D0-D7	0.3	0.4		
CP	0.9	0.75		
ŌĒ	1.3	0.6		

^{*}Unit Load is Δl_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

CHARACTERISTIC	C _L		TYP	ICAL	UNITS
CHARACTERISTIC		(pF)	HC	HCT	UNIIS
Propagation Delay Clock to Q	t _{PLH} t _{PHL}	15	15	15	ns
Propagation Delay Output Disable to Q	t _{PLZ} t _{PHZ}	15	11	11	ns
Propagation Delay Output Enable to Q	t _{PZL} t _{PZH}	15	12	12	ns
Max Clock Frequency	f _{max}	15	60	60	MHz
Power Dissipation Capacitance	C _{PD} *	_	39	47	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 f_i + \Sigma V_{CC}^2 f_o C_L$ where

f_i = input frequency,

fo = output frequency,

C_L = output load capacitance

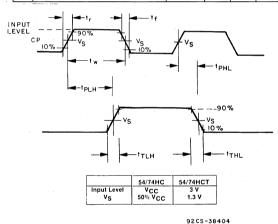
V_{cc} = supply voltage

PREREQUISITE FOR SWITCHING FUNCTION

				25	°C		-4	0°C to	o +85°	,C	-5	5°C to	+125	°C	
CHARACTERISTIC		Vcc	Н	С	Н	CT	74	нс	74F	I CT	54	нс	54F	ICT	UNITS
		V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Clock		2	6	_	_	_	5	_	_	l —	4	_	_	_	
Frequency	f _{MAX}	4.5	30	_	30	—	25	_	25	_	20	-	20	—	MHz
		6	35			_	29	_		_	23	_	_	_	
		2	80	_	_	_	100	_	_	_	120	_	_	_	
Clock Pulse Width	tw	4.5	16	_	16	-	20	l —	20	—	24	_	24	—	ns
Fig. 2		6	14	_			17	_	_	_	20	_	_	_	
Set-up Time		2	60	_	_	-	75	_	_	_	90	_	-	_	
Data to Clock		4.5	12	_	12	_	15	 	15	l —	18	<u> </u>	18	 	ns
Fig. 3	t _{SU}	6	10	_	_	_	13		_	_	15		_		
Hold Time		2	5	_	_	_	5	-	_	-	5	-	_	-	
Data to Clock		4.5	5	—	5	_	5	—	5	-	5	_	5	_	ns
Fig. 3	t _H	6	5		_	_	5	_		_	5	_		—	

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t₅ t_f = 6 ns)

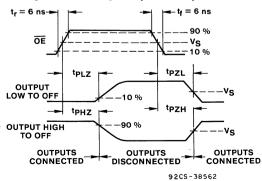
				25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC		Vcc	Н	C	H	СТ	74	нс	74F	ICT	54	нс	54H	ICT	UNITS
		٧.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	165	—	-	_	205	_		<u> </u>	250	—	-	
Clock to Output	t _{PHL}	4.5	-	33	—	33	 -	41	-	41	—	50	l —	50	ns
Fig. 2		6	_	28			_	35	_	_	_	43	_	_]
Propagation Delay	t_{PLZ}	2	_	135	I —		_	170	_	<u> </u>		205	_	_	
Output Disable to Q	t_{PHZ}	4.5	—	27	_	28	-	34	—	35		41	_	42	ns
Fig. 4		6		23	_	_	_	29		_		35	_	_	
Propagation Delay	t _{PZL}	2	_	150	_	_	_	190	_	_	_	225	_	_	
Output Enable to Q	t_{PZH}	4.5	—	30	_	30	_	38	_	38	<u> </u>	45	_	45	ns
Fig. 4		6		26			_	33		_		38	_	_	
Output Transition	t_{TLH}	2	_	60	_	_	_	75	_	_	_	90	_	_	
Time	t _{THL}	4.5	_	12	_	12	-	15	-	15	l —	18	_	18	ns
Fig. 2		6		10	_	_		13	_	_		15	_	_	
Input Capacitance	Cı	_	-	10	_	10	_	10	_	10	-	10	-	10	pF
3-State Output Capacitance	Co	_	_	20	_	20	_	20	-	20	_	20	_	20	. pF

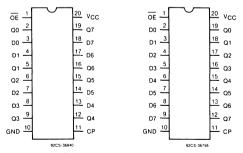


CP V_S V_S 92CS - 36954RI

Fig. 3 — Data set-up and hold times.

Fig. 2 — Clock to output delays and clock pulse width.





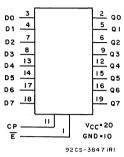
CD54/74HC, HCT374 Types CD54/ TERMINAL ASSIGNMENT TERM

CD54/74HC, HCT574 Types TERMINAL ASSIGNMENT

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 4 — Transition times and propagation delay times.

High-Speed CMOS Logic



Octal D-Type Flip-Flop with Data Enable

Type Features:

- Buffered common clock
- Buffered inputs
- Typical propagation delay = 17ns @ $C_L = 15pF$, $V_{CC} = 5 V$, $T_A = 25^{\circ} C$
- 60 MHz typical maximum clock frequency @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC377 and CD54/74HCT377 are octal D-type flip-flops with a buffered clock (CP) common to all eight flip-flops. All the flip-flops are loaded simultaneously on the positive edge of the clock (CP) when the Data Enable (E) is LOW.

The CD54HC377 and CD54HCT377 are supplied in 20-lead ceramic dual-in-line packages (F suffix). The CD74HC377 and CD74HCT377 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

TRUTH TABLE

OPERATING MODE		OUTPUTS		
OPERATING WIODE	СР	Ē	Dn	Qn
Load "1"		1	h	Н
Load "0"	~	Ī	ı	L
Hold (do nothing)	~	h	Х	no change
Hold (do flottling)	Х	Н	Х	no change

H = HIGH voltage level steady state.

h = HIGH voltage level one setup time prior to the LOWto-HIGH clock transition.

L = LOW voltage level steady state

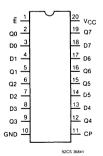
I = LOW voltage level one setup time prior to the LOW-to-HIGH clock transition.

X = Don't care.

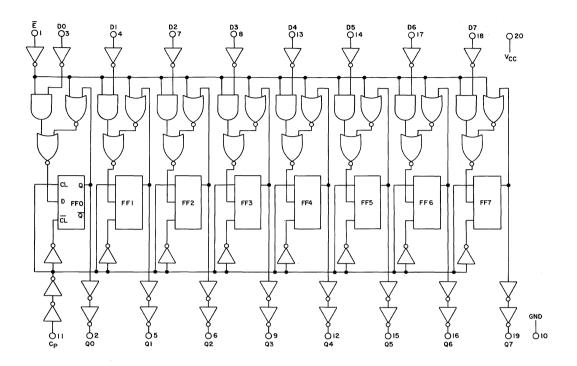
✓= LOW-to-HIGH clock transition.

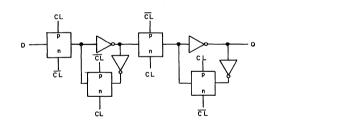
Family Features:

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}= 30%, N_{IH}=30% of V_{CC} @ V_{CC}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility I₁ ≤ 1 µA @ VoL, VoH



TERMINAL ASSIGNMENT





Flip-Flop Detail

Fig. 1 - Logic diagram.

92CL-38576R1

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20mA
DC OUTPUT DIODE CURRENT, IOK (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} $+$ 0.5V)	±25mA
DC V _{cc} OR GROUND CURRENT (I _{cc})	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERICTIC	LIN	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNIIS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

	CD74HC377/CD54HC377											CD	74HC	T377	/CD5	4НСТ	377			
CHARACTERISTIC		TEST NDITIONS		1				HC PE	54I TY	HC PE	TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPE		54HCT TYPE		UNITS
OTAMACTERISTIC	V,	I _o	V _{cc}		+25° (;	1	10/ 5° C	1	5/ 5° C	V,	V _{cc}		+25° C	;	ı	0/ 5°C		5/ 5°C	UNITS
	•	""	ľ	Min	Тур	Max	Min	Max	Min	Max	`	ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	-	1.5	_		4.5								
Input Voltage V _™		:	4.5	3.15		_	3.15	_	3.15	_	_	to	2	_	-	2	-	2	-	v
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4:5	_	_	1.35	_	1.35	_	1.35] -	to	-	-	0.8	-	0.8	-	0.8	v
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	V _{IL}									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_		4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	٧
CMOS Loads	V _{IH}		6	5.9	_		5.9		5.9	_	V _{IH}			<u> </u>						
	VIL										V _{IL}								ľ	
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	VIL		2	_	_	0.1	_	0.1	_	0.1	VıL									
Output Voltage V _{CL}	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}		<u> </u>						<u> </u>	
	VIL			<u> </u>							V _{IL}									,
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}		ļ					<u> </u>		
Input Leakage	V _{cc}										Any Voltage									
Current I,	or		6	-	-	±0.1	-	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd									<u> </u>	& Gnd	L	ļ	<u> </u>	<u> </u>			<u> </u>	<u> </u>	
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd						L			L	Gnd		_	<u> </u>	<u> </u>		<u> </u>	<u> </u>	<u> </u>	
Additional Quiescent												4.5								
Device Current per input pin:											V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
1 unit load ∆lcc*							_					5.5	1	L	1	l			l	

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
Ē	1.5
CP	0.5
All Dn Inputs	0.25

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r, t_f = 6 ns)

CHARACTERISTIC	CL	SYMBOL	TYP	ICAL	UNITS
CHARACTERISTIC	(pF)	STINDOL	HC	нст	ONITS
Maximum Clock Frequency	15	f _{max}	60	50	MHz
Propagation Delay CP——— Q	15	t _{PLH} t _{PHL}	14	16	ns
Power Dissipation Capacitance*	_	C _{PD}	31	35	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per flip flop.

 $P_D = C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{cc}^2 f_0)$ where:

f_i = input frequency

fo = output frequency

C_L = output load capacitance.

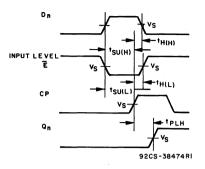
 V_{cc} = supply voltage.

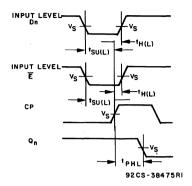
PREREQUISITE FOR SWITCHING FUNCTION

				25	°C		-4	0°C to	o +85°	,C	-5				
CHARACTERISTIC		Vcc	Н	C	H	CT	74	нС	74F	1CT	54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Clock		2	6		_	_	5	_	_	_	4	_	_	_	
Frequency	f_{max}	4.5	30	_	25	_	25	_	20	 	20		16	_	MHz
		6	35	_	_	_	29	_	_	_	23	_		_	
Clock Pulse		2	80	_	_	_	100	_	_	_	120	T	_	-	
width	tw	4.5	16	_	20	—	20		25	_	24	l —	30	_	ns
		6	14			_	17	_		<u> </u>	20	<u> </u>	_	_	
Set-up Time		2	60	—	_	_	75	_	_	_	90	_	_	_	
E, Data to CP	tsu	4.5	12	_	12	—	15	_	15	—	18	—	18	_	ns
		6	10	_	_	-	13	_	_	—	15	—	_	_	
Hold Time,		2	3	T —	_	—	3	_	_	<u> </u>	3	_	_	_	
Data to CP	t _H	4.5	3	_	3	l —	3	_	3	_	3	_	3	_	ns
		6	3			_	3	_		_	3	L-	_	_	
Hold Time		2	5	_	_	_	5	_	_	_	5	_	_	_	
Ē to CP	tн	4.5	5	—	5	<u> </u>	5	—	5	_	5		5	—	ns
		6	5		_	_	5	_		_	5	_			

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t₁, t₁ = 6 ns)

	CHARACTERISTIC			25	°C		-4	0°C to	o +85°	,C	-5				
CHARACTERISTI	C	Vcc	Н	C	Н	СТ	74HC 74		741	74HCT		54HC		ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.]
Propagation Delay,	t _{PLH}	2	—	175	_	_	_	220	_	_	_	265	_	_	
CP to Q	t _{PHL}	4.5	—	35	l —	38	 	44	_	48	_	_53	—	57	ns
		6	—	30	_	_	—	37	—	_	_	45	_	_	
Output		2	T —	75	_	_		95	_	—	_	110	_	_	
Transition Time	t _{TLH}	4.5	_	15	—	15	_	19	_	19	_	22	—	22	ns
	t _{THL}	6	_	13		_		16	<u> </u>	l —	_	19	l —	l —	
Input															
Capacitance	Cı		_	10	_	10		10		10	_	10	_	10	pF

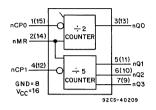




	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, Vs	50% V _{CC}	1.3 V

Fig. 2 - Setup and hold times and propagation delay times.

High-Speed CMOS Logic



Dual Decade Ripple Counter

Type Features:

- Two BCD decade or bi-quinary counters
- One package can be configured to divide-by-2, 4, 5, 10, 20, 25, 50 or 100
- Two master reset inputs to clear each decade counter individually

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC390 and CD54/74HCT390 dual 4-bit decade ripple counters are high-speed silicon-gate CMOS devices and are pin compatible with low-power Schottky TTL (LSTTL). These devices are divided into four separately clocked sections. The counters have two divide-by-2 sections and two divide-by-5 sections. These sections are normally used in a BCD decade or bi-quinary configuration, since they share a common master reset (nMR). If the two master reset inputs (1MR and 2MR) are used to simultaneously clear all 8 bits of the counter, a number of counting configurations are possible within one package. The separate clock inputs (nCPO and nCP1) of each section allow ripple counter or frequency division applications of divide-by-2, 4, 5, 10, 20, 25, 50 or 100. Each section is triggered by the HIGH-to-LOW transition of the input pulses (nCP0 and nCP1).

For BCD decade operation, the nQ0 output is connected to the nCP1 input of the divide-by-5 section. For bi-quinary decade operation, the nQ3 output is connected to the nCP0 input and nQ0 becomes the decade output.

The master reset inputs (1MR and 2MR) are active-HIGH asynchronous inputs to each decade counter which operates on the portion of the counter identified by the "1" and "2" prefixes in the pin configuration. A HIGH level on the nMR input overrides the clock and sets the four outputs LOW.

The CD54HC390 and CD54HCT390 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC390 and CD74HCT390 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
 Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- □ CD54HC/CD74HC Types:
 2 to 6 V Operation
 High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC},
 @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, IIK (FOR VI < -0.5 V OR VI > Vcc + 0.5 V)	±20 mA
DC OUTPUT DIODE CURRENT, lok (FOR Vo < -0.5 V OR Vo > Vcc + 0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = -40 to +70° C (PACKAGE TYPE M) For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79$ mm) from case for 10 s max.	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C

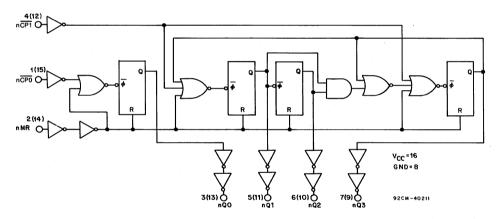


Fig. 1 - Logic diagram, one-half of HC/HCT390.

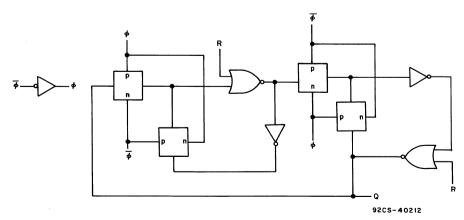


Fig. 2 - Flip-flop logic detail.

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIF	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
Vcc:*	1	}	
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	1
Input Rise and Fall Times, t,tf:			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

TRUTH TABLE

INP	UTS	
СР	MR	ACTION
	L	NO CHANGE
	L	COUNT
×	Н	ALL Qs LOW

H = HIGH voltage level

L = LOW voltage level

X = Don't Care

/ = LOW-to-HIGH ϕ transition

 $= HIGH-to-LOW \phi transition$

BCD COUNT SEQUENCE FOR 1/2 THE "390"

COUNT		OUT	PUTS	
COON	Q0	Q1	Q2	Q3
0	L	L	L	L
1	Н	L	L	L
2	L	Н	L	L
3	Н	Н	L	L
4	L	L	Н	L
5	Н	L	Н	L
6	L	Н	Н	L
7	Н	Н	Н	L
8	L	L	L	Н
9	н	L	L	H

Note:

Output nQ0 connected to nCP1 with counter input on nCP0.

BI-QUINARY COUNT SEQUENCE FOR 1/2 THE "390"

COUNT		OUT	PUTS	
COOM	Q0	Q1	Q2	Q3
0	L	L	L	L
1	L	н	L	L
2	L	L	н	L
3	L	н	н	L
4	L	L	L	Н
5	н	L	L	L
6	Н	н	L	L
7	Н	L	н	L
8	н	Н	н	L
9	Н	L	L	Н

Note:

Output nQ3 connected to nCP0 with counter input on nCP1.

STATIC ELECTRICAL CHARACTERISTICS

	CD74HC390/CD54HC390												CD74	нст	390/C	D54H	ICT3	90			
CHARACTERIS	T 10	l	TEST IDITIOI	NS.		74HC/54HC TYPES					HC PES	TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS
CHARACTERIS	iic	v, 1		Vcc		•25° C	;	-4 +85		-5: +12!		V _i	Vcc		+25° C	:	1	0/ 5°C	_	5/ 5° C	UNITS
		V	mA	V	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_		1.5	_	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15	_		3.15	_	3.15	_	-	to	2	–	<u> </u>	2	-	2	[-	V
				6	4.2	_	<u>L-</u> _	4.2	<u> </u>	4.2			5.5				<u> </u>	L			
Low-Level				2	<u> </u>	<u> </u>	0.5	<u> </u>	0.5	_	0.5		4.5					-		}	
Input Voltage	V_{1L}			4.5	_	_	1.35	_	1.35		1.35	_	to	-	_	0.8	-	0.8	-	0.8	V
				6	_	_	1.8	_	1.8		1.8		5.5	ļ				ļ		<u> </u>	
High-Level		VIL		2	1.9	_	<u> </u>	1.9	_	1.9		VIL									
Output Voltage	V _{он}	or	-0.02	4.5	4.4	_	드	4.4		4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	V
CMOS Loads		V _{IH}		6	5.9	_	느	5.9	<u> </u>	5.9		V _{IH}					_	ļ			
		VIL					<u> </u>					VIL	ļ			}		ļ	}		
TTL Loads		or	-4	 	3.98		 -	3.84	=	3.7	=	or	4.5	3.98	-	-	3.84	-	3.7	-	V
		V _{IH}	-5.2	6	5.48		 	5.34	-	5.2		V _{IH}	_	<u> </u>				├	├	├ ─	
Low-Level		VIL		2	├	_	0.1	Ι=	0.1		0.1	VIL		l	1	١		١	1		
Output Voltage	Vol	or	0.02	4.5	-	_	0.1	_	0.1	<u> </u>	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	٧
CMOS Loads		V _{IH}		6	 - -	=	0.1		0.1	_	0.1	V _{IH}	-	-				├	-		
TTL Loads		VIL	4	4.5	-	-	0.26	_	0.33	 -	0.4	VIL	4.5	_		0.26	_	0.33	_	0.4	v
TTE LOADS		Or VIH	5.2	6	=	=	0.26	=	0.33	=	0.4	or V _{IH}	4.5	-	-	0.26	-	0.33	_	0.4	· •
Input Leakage		VIH	5.2	-	┝═┈	 -	0.20	Η=-	0.33	 -	0.4	Any	 	-		-	-	 	-	╁	
Current	l _i	Vcc			ì		ĺ					Voltage					1	ł	1	1	
Carroni	"	or		6	} —	-	±0.1	-	±1	-	±1	Between	5.5	-	-	±0.1	-	±1	-	±1	μΑ
i		Gnd			l		Ì					Vcc & Gnd					l	ì	}		
Quiescent		Vcc					 					Vcc	_		<u> </u>			<u> </u>	_	 	
Device Current	lcc	or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μA
		Gnd			Ì							Gnd	}							1	
Additional			L		·															1	
Quiescent Device													4.5		100						
Current per input												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	Δlcc*												5.5	1	Ì	l		Ì	1		

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
nCP0	0.45
nCP1, MR	0.6

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_f , t_f = 6 ns)

CHARACTERISTIC	CL	TYP	UNITS		
CHARACTERISTIC	(pF)	HC	нст	UNIIS	
Propagation Delay	t _{PLH}				
	t _{PHL}				
nCP0 to Q0 Output	ľ		14	17	
nCP1 to Q3		15	15	18	ns
MR to Qn Output	tphL		16	18	7
Power Dissipation Capacitance*	C _{PD}	_	28	32	pF

*CPD is used to determine the dynamic power consumption, per counter.

PD = $C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 f_o)$ where: f_i = input frequency

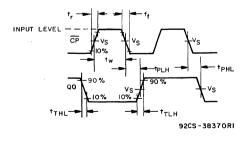
fo = output frequency

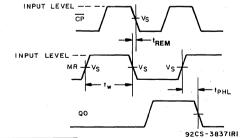
C_L = output load capacitance

Vcc = supply voltage

PRE-REQUISITE FOR SWITCHING FUNCTION

			I	LIMITS											
				25	°C		-4	0°C t	o +85°	°C	-5	5°C to	+125	°C]
CHARACTERISTIC		CONDITIONS	Н	C	HCT		74HC		74HCT		54HC		54HCT		UNITS
		V _{cc} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Clock	f _{MAX}	2	6	—	_	_	5	I -	_	_	4		[—	_	
Frequency		4.5	30	-	27	—	24	l —	22	<u> </u>	20	—	18	i —	
		6	35	_	—	<u> </u>	28	 	—	_	24	l —	_	—	
Clock Pulse Width	tw	2	80	_	_	_	100	_	_	_	120	_		_	
nCP0, nCP1		4.5	16	_	19	l —	20	_	24		24	_	29	—	İ
		6	14	_	_	_	17	l —	l —	_	20	_	_	_	
Reset Removal Time	t _{REM}	2	70	_	_	_	90	_	_	_	105	_	_	_	ns
		4.5	14	 	15	l —	18	_	19	_	21	l —	22	_	l
		6	12	_	<u> </u>	l —	15	 	_		18		<u> </u>	<u> </u>	
Reset Pulse Width	tw	2	50		_		65	_	_		75		_	-	
'		4.5	10	_	13	_	13		16		15		20	-	
		6	9	l —		-	11	-	 —	 —	13	. —	_	—	Ì





	54/74HC	54/74HCT
INPUT LEVEL	Vcс	3 V
SWITCHING VOLTAGE, VS	50% VCC	1.3 V

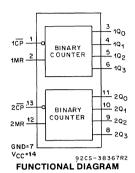
Fig. 3 - Input pulse pre-requisite, propagation-delay, and output-transition times.

Fig. 4 - Master-Reset pre-requisite and propagation-delay times.

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

								LIM	ITS						
CHARACTERIS	TIC	VCC		25	°C		-4	0°C to	o +85°	,C	-5	5°C to	+125	s° C	UNITS
OTATIAOTEMIO	,,,,	(V)	Н	С	HCT		74HC		74HCT		54	НС	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	175		<u> </u>	_	220		-	_	265	_	_	
Time:	t _{PHL}	4.5	-	35		40	_	44		50	_	53	—	60	
nCP0 to nQ0		6	_	30				37				45		_	
		2	_	185	_	—	_	230	_			280	_	_	
nCP1 to nQ1		4.5	[—	37	ĺ —	43	—	46	—	51	—	56	—	65	1
		6		31	_	<u> </u>		39				48		_	
Í		2	- T	245	_	_	_	305	_	<u> </u>		370	-	-	1
nCP1 to nQ2		4.5	_	49	—	55	-	61	—	69	—	74	—	83	
		6		42				52				63	_		
		2	-	180		_		225	_	-	_	270	_	-	
nCP1 to nQ3		4.5		36	—	42	-	45	—	53		54	—	63	ns
		6		31			_	38		L –		46	_	_	
nCP0 to nQ2		2	—	365	_	-	_	455	-	_	_	550	_	I —]
(nQ0 connected to r	nCP1)	4.5	_	73		84	-	91	_	105	_	110		126	
		6	_	62		-		77	l –			94	_	-	
		2	T	190	_	_	_	240	_	—	_	285	_		
MR to Qn		4.5	-	38		42	_	48	—	53	_	57	—	63	
		6	-	32	l —	—	l —_	41	Ĺ —	_	<u> </u>	48	<u> </u>		ĺĺ
Output Transition	t _{THL}	2	T -	75	_	—	_	95	_	_	_	110	_	T -	
Time	t _{TLH}	4.5		15	l —	15	-	19		19		22	—	22	1
		6	_	13	_		_	16	L_		<u></u>	19	L-		
Input Capacitance	Cı			10		10	_	10	_	10		10		10	pF

High-Speed CMOS Logic



Dual 4-Stage Binary Counter

Type Features:

- Fully static operation
- Buffered inputs
- Common reset
- Negative-edge clocking
- Typical $f_{MAX} = 60 \text{ MHz}$ @ $V_{cc} = 5V$, $C_L = 15 \text{ pF}$, $T_A = 25^{\circ} \text{ C}$

The RCA-CD54/74HC393 and CD54/74HCT393 are 4-stage ripple-carry binary counters. All counter stages are master-slave flip-flops. The state of the stage advances one count on the negative transition of each clock pulse; a high voltage level on the MR line resets all counters to their zero state. All inputs and outputs are buffered.

The CD54HC393 and CD54HCT393 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC393 and CD74HCT393 are supplied in 14-lead dual-in-line plastic package (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}=30%, N_{IH}=30% of V_{CC} @ V_{CC}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility

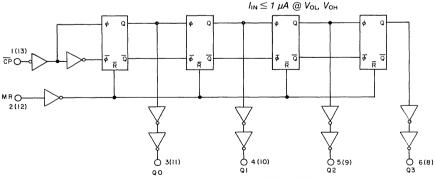


Fig. 1 - Logic diagram, one-half of HC/HCT393.

92CM - 38368R3

MAXIMUM RATINGS, Absolute-Maximum Values:

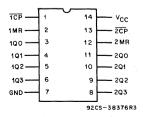
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, $I_{i\kappa}$ (FOR $V_i < -0.5$ V OR $V_i > V_{cc} + 0.5$ V) .	
DC OUTPUT DIODE CURRENT, lok (FOR V_o < -0.5 V OR V_o > V_{cc} +0.5	
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Voc +0.5 V	
DC V _{cc} OR GROUND CURRENT, (I _{cc})	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, HPACKAGE TYPE E, M	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (T _{stg})	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LII	UNITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times, t,,t;			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

				CD	74HC	393/0	D54F	IC393	3				CD	74HC	T393/	CD54	нст	393				
CHARACTERISTI	c		TEST IDITIOI	NS	l	IC/54 TYPE		741 TY		54F TY		TEST CONDITIO	ons	741:0	TYPE		1	ICT PE	54F TY	ICT PE		
CHAIRO ILIIGH	•	V,	lo	Vcc		-25°C	:	-4 +85		-5: +12:		V,	Vcc	,	∙25° C	;		0/ 5°C	-	5/ 5° C	UNITS	
		v	mA	V	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max		
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5									
Input Voltage	V_{IH}		ŀ	4.5	3.15		_	3.15		3.15	_	-	to	2	_	_	2	-	2	-	V	
				6	4.2	_	_	4.2	_	4.2	-		5.5								1	
Low-Level		}	ŀ	2	_	_	0.5	_	0.5	_	0.5		4.5								1	
Input Voltage	V_{IL}			4.5		_	1.35	_	1.35	_	1.35	_	to	_	_	0.8	_	0.8	-	0.8	v	
				6	_	_	1.8	_	1.8	_	1.8		5.5									
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	V _{IL}										
Output Voltage	Voh	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v	
CMOS Loads		ViH		6	5.9	_	_	5.9	_	5.9	-	V _{IH}										
		VIL										VIL										
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v	
		VIH	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH				1						
Low-Level		VIL		2		_	0.1	_	0.1	_	0.1	Vil										
Output Voltage	VoL	or	0.02	4.5		_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	l v	
CMOS Loads		ViH		6	_	_	0.1		0.1	_	0.1	ViH		ļ				ļ		,		
		VIL										VıL										
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v	
		ViH	5.2	6	_		0.26	_	0.33		0.4	ViH		ł								
Input Leakage Current	l ₁	V _{cc} or Gnd		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1	_	±1	μΑ	
Quiescent Device												Vcc										
Current	Icc	V _{cc} or Gnd	0	6	_	_	8	_	80	_	160	or Gnd	5.5	_	_	8	_	80	-	160	μΑ	
Additional Quiescent Device Current per Input Pin: 1 Unit Load	Δlcc*		1									V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ	

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
nCP	0.4
nMR	1

^{*}Unit load is Δ I_{cc} limit specified in Static Characteristics Chart, e.g., 360 μ A max. @ 25° C.

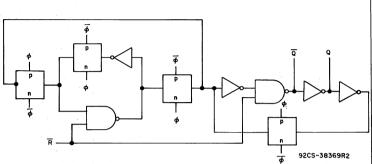


Fig. 2 - Flip-flop logic detail.

TRUTH TABLES

CP		OUTF	PUTS	
COUNT	Q0	Q1	Q2	Q3
0	L	L	Г	L
1 1	Н	L	L	L
2	L	Н	L	L
3	Η	Н	L	L
4	L	L	Н	L
5	Н	L	Н	L
6	L	Н	Н	L
7	Н	Н	Н	L
8	L	L	L	Н
9	Н	L	L	Н
10	L	Н	L	Н
11	н	H.	L	Н
12	L	L	н	H.
13	н	L	Н	н
14	L	Н	Н	н
15	Н	н	Н	Н

СР	MR	OUTPUT
	L	NO CHANGE
	L	COUNT
×	н	LLLL

X = Don't Care

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r , t_t = 6 ns)

		C,	Typical						
CHARACTERISTIC	 SYMBOL	рĒ	HC	HCT	Units				
Propagation Delay nCP to nQ0 Output	t _{PLH} t _{PHL}	15	12	13					
Propagation Delay Qn to Qn + 1	t _{PLH}	15	4	4	ns				
Propagation Delay MR to Qn Output	t _{PHL}	15	11	13					
Power Dissipation Capacitance*	C _{PD}	T - 1	20	21	pF				

 $^{^{\}star}C_{PD}$ is used to determine the power consumption. PD=C_{PD} V_{cc}^2 fi + Σ (C_L V_{cc}² fi/M) where: M=2¹,2²,2³,2⁴

C_L=output load capacitance fi=input frequency

Pre-requisite for Switching Function

			25°C				-4	0°C to	o +85°	C	-5				
CHARACTERISTIC	SYMBOL	VCC	Н	С	Н	CT	741	НС	74H	ICT	54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Maximum Clock		2	6	 -	_	_	5	_	_	_	4	_	_	1-	
Frequency	f _{MAX}	4.5	30	 	27	 	24	_	22	 	20	_	18	-	MHz
		6	35	-	_	l —	28	 	l —	_	24	—	<u> </u>	-]
Clock Pulse Width	tw	2	80	_	_	_	100	_	_		120	_	_	-	
		4.5	16	-	19	_	20	—	24	—	24	_	29	-	
		6	14		-	_	17	_	—	—	20	—		_	
Reset Recovery Time	trec	2	5	-	-	_	5	_	_	_	5	_	_	—	
		4.5	5	 	5	_	5	_	5	<u> </u>	5	—	5	_	ns
		6	5	-		_	5	—	_	l —	5			—	
Reset Pulse Width	tw	2	80	-	1-	-	100	_	_	_	120	_	_	_	
		4.5	16	l —	16	_	20	_	20	_	24	_	24	l —	
		6	14	\ 	_	—	17	-	_	_	20		_	<u> </u>	Ì

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,,t=6 ns)

			25°C			-4	0°C t	o +85°	°C	-5					
CHARACTERISTIC	SYMBOL	Vcc	H	С	Н	CT	74	HC	74F	ICT	54	НС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Propagation Delay	t _{PLH}	2		45	_	T —	_	55	_	_	_	70	_	_	
Time:	t _{PHL}	4.5	l —	9	—	12	l —	11	l —	15	l —	14	—	18	
Qn to Qn+1		6	—	8	l —	_	—	9	_	-	_	12	_	—	
	t _{PLH}	2		150	_	—	_	190	_	-		225		_	Ì
nCP to nQ0	t₽HL	4.5	 	26	—	32	—	38	_	40	—	45	_	48	
		6		26	—	—	—	33	l —	-	-	38	_	—	
	t _{PLH}	2	—	195	_	-	_	245			_	295	_	-	Ì
nCP to nQ1	t _{PHL}	4.5	—	38	-	32	l —	49	—	55	_	59	_	66	
'		6	_	33	—	—	—	42	_	 	_	50	_	—	
	t _{PLH}	2	_	240		_	_	300	_	_	_	360	_	_	1
nCP to nQ2	t₽HL	4.5	—	48	—	50	_	60	_	70	_	72	-	84	ns
		6	—	41	—	-	_	51	_	—	_	61	—	—	
	t _{PLH}	2	_	285	_		_	355	_	_	_	430	-	_	1
nCP to nQ3	t _{PHL}	4.5	—	57	—	62	—	71	—	85	_	86	—	102	ļ
		6	\ —	48	l —	-	—	60	_	-	_	73	—	—	
140.1.0	t _{PLH}	2	_	135	_	_	_	170	_	_	_	205	_	_	1
MR to Qn	t _{PHL}	4.5	_	27	—	32	-	24		40	_	41	_	48	
		6		23	-	-	—	29	_	_	-	35	—	_	
Output Transition	t _{THL}	2	_	75	_	_	_	95	_	_	_	110	_	_	1
Time	t _{TLH}	4.5	—	15		15	—	19	_	19	—	22	—	22	
		6	—	13		-	-	16	-	-		19	-	-	
Input Capacitance	Cı	_	-	10	_	10		10	_	10	_	10	-	10	pF

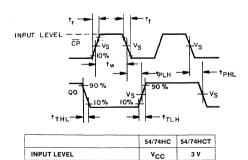


Fig. 3 - Clock pre-requisite, propagation-delay, and
output-transition times

50% VCC

1.3 V

92CS-38370R2

SWITCHING VOLTAGE, VS

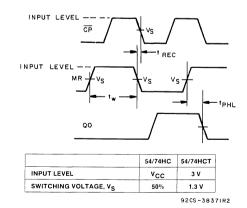
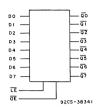


Fig. 4 - Master-Reset pre-requisite and propagation-delay times.

High-Speed CMOS Logic



Octal Inverting Transparent Latch, **3-State Outputs**

Type Features:

- Common latch-enable control
- Common 3-state output-enable control
- Buffered inputs
- 3-State outputs
- Bus line driving capacity
- Typical propagation delay = 13 ns @ $V_{CC} = 5 \text{ V}$, $C_L = 15 \text{ pF}$, $T_A = 25^{\circ} \text{ C}$ (Data to Output)

FUNCTIONAL DIAGRAM

The RCA CD54/74HC/HCT533/563 are high-speed Octal Transparent Latches manufactured with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LSTTL devices.

The outputs are transparent to the inputs when the latch enable $\overline{(LE)}$ is high. When the latch enable $\overline{(LE)}$ goes low the data is latched. The output enable (OE) controls the 3-state outputs. When the output enable (OE) is high the outputs will be in the high impedance state. The latch operation is independent of the state of the output enable.

The CD54/74HC533 and CD54/74HCT533 are identical in function to the CD54/74HC563 and CD54/74HCT563 but have different pinouts. The CD54/74HC533 and CD54/ 74HCT533 are similar to the CD54/74HC373 and CD54/ 74HCT373; the latter are non-inverting types.

The CD54HC/HCT533/563 are supplied in 20-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/ HCT533/563 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features

- Fanout (Over Temperature Range): Standard Outputs — 10 LSTTL Loads Bus Driver Outputs — 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation and Transition Times
- Significant Power Reduction Compared to LŠTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:

2 to 6 V Operation High Noise Immunity:

 $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$:

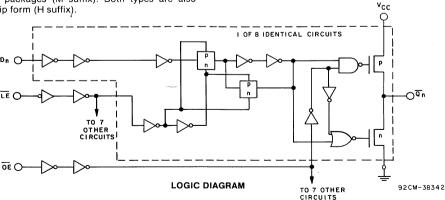
@ $V_{CC} = 5 V$

■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation

Direct LSTTL Input Logic Compatibility $V_{\rm IL}=0.8~V~Max.,~V_{\rm IH}=2~V~Min.$

CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$



MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground)
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{cc} + 0.5$ V)
DC OUTPUT DIODE CURRENT, l_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)
DC DRAIN CURRENT, PER OUTPUT (I _O) (FOR -0.5 V < V ₀ < V _{0c} +0.5 V)
DC V $_{\text{CC}}$ OR GROUND CURRENT (I $_{\text{CC}}$):
POWER DISSIPATION PER PACKAGE (Po):
For $T_A = -40$ to $+60$ °C (PACKAGE TYPE E)
For $T_A = +60$ to $+85$ °C (PACKAGE TYPE E)
For $T_A = -55$ to $+100$ °C (PACKAGE TYPE F, H)
For $T_A = +100$ to $+125$ °C (PACKAGE TYPE F, H)
For T_A = -40 to +70°C (PACKAGE TYPE M)
For T _A = +70 to +125°C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H
PACKAGE TYPE E, M40 to +85°C
STORAGE TEMPERATURE (T _{stg})
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. $+265^{\circ}$ C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) with solder contacting lead tips only +300°C
RECOMMENDED OPERATING CONDITIONS:

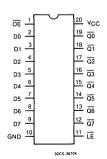
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

QUADACTERISTIC	LIM	IITS		
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*				
CD54/74HC Types	2	6	l v	
CD54/74HCT Types	4.5	5.5	V	
DC Input or Output Voltage V _{IN} , V _{OUT}	0	V _{cc}	V	
Operating Temperature T _A :				
CD74 Types	-40	+85	°C	
CD54 Types	-55	+125	°C	
Input Rise and Fall Times, t _r , t _f				
at 2 V	0	1000	ns	
at 4.5 V	0	500	ns	
at 6 V	0	400	ns	

^{*}Unless otherwise specified, all voltages are referenced to Ground.



CD54/74HC533, CD54/74HCT533 TERMINAL ASSIGNMENT



CD54/74HC563, CD54/74HCT563 TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

					74HC 74HC													HCT5			
,		1	TEST	S	l	IC/54		741 TY	HC PE	54I	HC PE	TEST		l	CT/54 TYPE		1	ICT PE	1	ICT PE	
CHARACTERIS	TIC	V 1	lo	V _{cc}	-	+25°0	;		10/ 5°C	i	5/ 5°C	V _i	Vcc		+25°C	;	1	10/ 5°C		55/ 25°C	UNITS
		V	mA	٧	Min	Тур	Max	Min	Max	Min	Max	ľ	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5		1.5			4.5								
Input Voltage	V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	-	2	_	v
				6	4.2	_	_	4.2	_	4.2	_		5.5					į			
Low-Level				2	_		0.5	_	0.5		0.5		4.5								
Input Voltage	VIL			4.5		_	1.35		1.35		1.35	-	to	-	_	0.8	-	8.0	-	0.8	v
				6		_	1.8		1.8		1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	Vit.									
Output Voltage	Von	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	. or	4.5	4.4	_	-	4.4	_	4.4		٧
CMOS Loads		V _{IH}		6	5.9	_	_	5.9		5.9	_	Vін									
		VIL										Vil							ĺ		
TTL Loads		or	-6	4.5	3.98	_	_	3.84		3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
(Bus Driver)		V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2		V _{IH}						<u> </u>			
Low-Level		VIL		2	<u> </u>	_	0.1		0.1		0.1	Vil			ł			Ì			
Output Voltage	V_{OL}	or	0.02	4.5	_	_	0.1		0.1		0.1	or	4.5	-	-	0.1	_	0.1	-	0.1	v
CMOS Loads		V _{IH}		6	_		0.1		0.1	_	0.1	V _{IH}						<u> </u>			
		VIL										VıL	İ		i		}	ļ			
TTL Loads		or	6	4.5	_	_	0.26	_	0.33		0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v
(Bus Driver)		V _{IH}	7.8	6	_	_	0.26	_	0.33	_	0.4	ViH			<u> </u>	<u></u>	<u> </u>	L		<u> </u>	
Input Leakage		Vcc										Any Voltage					ļ			}	
Current	l _l	or		6	-	-	±0.1	-	±1	-	±1	Between V _{cc} &	5.5	-	-	±0.1	-	±1	_	±1	μΑ
		Gnd							L_			Gnd					ļ	↓_	_	-	
Quiescent		Vcc		}]		Vcc									
Device		or	0	6	-	-	8	-	80	-	160	or Gnd	5.5	-	-	8	-	80	-	160	μΑ
Current	Icc	Gnd		L		<u> </u>		<u> </u>	L							_		<u> </u>	<u> </u>	<u> </u>	
Additional Quiescent Device Current per input pin: 1 unit load Δlcc*	-											V _{CC} -2.1	4.5 to 5.5	-	100	360	_	450	_	490	μΑ
3-State Leakage Current	loz	V _{IL} or V _{IH}	V _o =V _{cc} or Gnd	6	-	_	±0.5	_	±5.0	_	±10	V _{IL} or V _{IH}	5.5	_	_	±0.5	-	±5.0	-	±10	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
DO — D7	0.15
<u>LE</u>	0.30
ŌĒ	0.55

^{*}Unit load is Δl_{cc} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input t,t=6 ns)

			T	TYPICAL VALUES						
CHARACTERISTIC		C _L	Н	C	Н	CT	UNITS			
		(pF)	533	563	533	563	1			
Propagation Delay Data to Qn Output	t _{PLH}	15	13	12	14	12				
Fig. 3	t _{PHL}	15	13	12	14	12				
Propagation Delay LE to Qn Output	t _{PLH}	15	14	13	16	14				
Fig. 4	t _{PHL}	15	14	13	10	'*	ns			
Output High Z to High Level, Fig. 6	t _{PZH}	15	12	12	14	14	7 115			
Output High Z to Low Level, Fig.7	t _{PZL}	15	12	12	14	14				
Output High Level to High Z, Fig. 6	t _{PHZ}	15	12	12	12	14				
Output Low Level to High Z, Fig. 7	t _{PLZ}	15	12	12	12	14				
Power Dissipation Capacitance	C _{PD} *		42	42	42	42	pF			

^{*}CPD determines the no-load dynamic power consumption per latch. It is obtained by the following relationship:

 P_D (total power per latch) = $C_{PD} V_{CC}^2 fi + \Sigma C_L V_{CC}^2 f_o$ where f_i = input frequency

fo = output frequency

C_L = output load capacitance

V_{cc} = supply voltage.

PRE-REQUISITE FOR SWITCHING FUNCTION

								LIM	IITS						
		TEST		25	°C		-4	l0°C to	o +85°	С	-5	55° to	+125°	С	
CHARACTERIS	STIC	CONDITION	Н	С	Н	СТ	74	нс	74F	ICT	54	нс	54F	ICT	UNITS
		V _{cc} V	Min.	Max.	Min.	Мах.	Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Max.	
LE Pulse Width	tw	2	80	_	_	l –	100	_	-	_	120	_	_	-	
(Fig. 4)		4.5	16	_	16	_	20	_	20	—	24		24		ns
		6	14		_	_	17		_	_	20		_		
Set-up Time	tsu	2	50	_	_	_	65	_	_	_	75	_	_	_	
Data to LE		4.5	10	_	10	_	13	_	13	_	15	-	15	-	ns
(Fig. 5)		6	9	_	-	-	11	_		_	13		_		
Hold Time	t _H	2	35	_	_	_	45	_	_	_	55	_	_	_	
Data to LE	533	4.5	7	—	8	_	9	-	10	_	11	-	12	-	ns
(Fig. 5)		6	6	—	—	—	8	-		_	7	-	-	—	
		2	4	_	_	_	4	_	_	_	4	_		_	
	563	4.5	4	-	5	-	4		5	-	4	-	5	-	ns
		6	4	—	-	_	4	-	_	-	4	-	_		

TRUTH TABLE

Output Enable	Latch Enable	Data	Q Output
L	Н	Н	L
L	н	L	Н
L	L	ı	н
L	L	h	L
н	х	x	Z

Note:

L = Low voltage level

H = High voltage level

I = Low voltage level one set-up time prior to the high to low latch enable transition

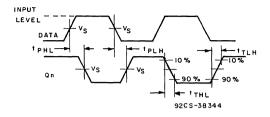
h = High voltage level one set-up time prior to the high to low latch enable transition

X = Don't care

Z = High impedance state

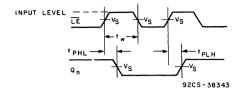
SWITCHING CHARACTERISTICS (CL = 50 pF, input t_r , t_f = 6 ns)

			LIMITS												
		TEST		+25	°C		-4	0°C t	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERIS	STIC	CONDITIONS	нс		HCT		74HC		74HCT		54HC		54HCT		UNITS
		V _{CC} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	/ t _{PLH}	2	_	165	_	_	—	205	_	_	_	250	_	<u> </u>	
Data to Qn	t _{PHL}	4.5	—	33	 -	34	—	41	—	43		50	-	51	ns
	533	6	_	28	_	—	—	35	—	—	—	43	—	-	
	t _{PLH}	2	_	175	_	_	_	220	_	_	_	265	_	Γ-	
LE to Qn	t _{PHL}	4.5	—	35	_	38	-	44	—	48		53	_	57	ns
	533	6		30	_	_	_	37	_			45			
Enable Times	t _{PZH}	2	_	150	_	_	_	190	_	_	_	225	-	_	
	t _{PZL}	4.5	-	30	—	35	—	38	—	44	—	45	_	53	ns
	533	6	_	26		—	l —	33		_		38			
Disable Times	t _{PHZ}	2	_	150	—	_	[—	190	-	_	-	225	-	-	
	t _{PLZ}	4.5	-	30	_	30		38	_	38		45	-	45	ns
,	533	6	·—	26	l —	_	_	33		_	_	38	l –		
Propagation Delay	/ t _{PLH}	2	_	150	_	_		190		_	_	225	-	-	
Data to Qn	t _{PHL}	4.5	l —	30	-	30	l —	38		38	-	45	—	45	ns
	563	6	—	26	—	_	 -	33	l —		_	38		-	
	t _{PLH}	2		165	_	_	_	205	Γ-	_	_	250	I -	-	
LEto Qn	t _{PHL}	4.5	—	33	l —	35	_	41	—	44	_	50	_	53	ns
	563	6	—	28	-	-	—	35	-		_	43	-		
Enable and	t _{PZH} , t _{PZL}	2	_	150	_	_	_	190	—			225		T -	
Disable Times	t _{PHZ} , t _{PLZ}	4.5] —	30	 	35		38	-	44	-	45	—	53	ns
	563	6		26	l —	l —	_	33		—		38	<u> </u>	_	
Input Capacitance	C _I		_	10		10	_	10	_	10	_	10		10	pF
3-State Output Capacitance	Со		_	20	_	20	_	20		20	_	20	-	20	pF



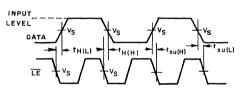
	54/74HC	54/74HCT
Input Level	Vcc	3 V
Vs	50% Vcc	1.3 V

Fig. 3 — Data to Q_n output propagation delays and output transition times.



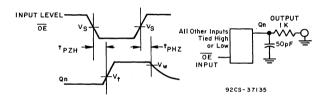
	54/74HC	54/74HCT
Input Level	Vcc	3 V
Vs	50% V _{cc}	1.3 V

Fig. 4 — Latch enable propagation delays.



92CS-38345

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Vs	50% Vcc	1.3 V



	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Vs	50% V _{cc}	1.3 V
Vt	50% V _{CC}	1.3 V
V.,	90% V _{CC}	4.15 V

Fig. 5 — Latch enable pre-requisite times.

Fig. 6 - 3-state propagation delays.

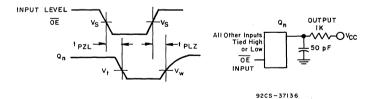
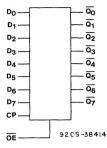


Fig. 7 — 3-state propagation delays.

High-Speed CMOS Logic



Octal D-Type Flip-Flop, 3-State, Inverting Positive-Edge Triggered

Type Features:

- Common 3-state output-enable control
- Buffered inputs
- 3-State outputs
- Bus line driving capability
- Typical propagation delay = 13 ns @ V_{cc} = 5V, C_L = 15 pF, T_A = 25°C (clock to output)

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC534, 564 and CD54/74HCT534, 564 are high speed OCTAL D-TYPE FLIP-FLOPS manufactured with silicon gate CMOS technology. They possess the low power consumption of standard CMOS integrated circuits, as well as the ability to drive 15 LSTTL loads. Due to the large output drive capability and the 3-STATE feature, these devices are ideally suited for interfacing with bus lines in a bus organized system. The two types are functionally identical and differ only in their pinout arrangements.

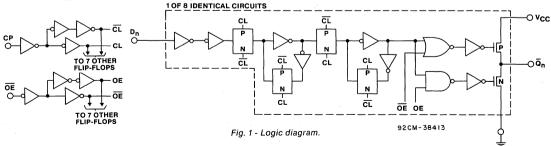
The CD54/74HC534, 564 and CD54/74HCT534, 564 are positive edge triggered flip-flops. Data at the D inputs, meeting the setup and hold time requirements, are inverted and transferred to the Q outputs on the positive going transition of the CLOCK input. When a high logic level is applied to the OUTPUT ENABLE input, all outputs go to a high impedance state, regardless of what signals are present at the other inputs and the state of the storage elements.

The CD54/74HCT logic family is speed, function, and pin compatible with the standard 54LS/74LS logic family.

The CD54HC and CD54HCT devices are supplied in 20-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC and CD74HCT devices are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs — 10 LSTTL Loads Bus Driver Outputs — 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC}=5V ■ CD54HCT/CD74HCT Types:
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL}=0.8 V Max., V_{IH}=2 V Min. CMOS Input Compatibility I_I ≤ 1 μA @ V_{OL}, V_{OH}



MAXIMUM RATINGS, Absolute-Maximum Values:

The same of the sa
DC SUPPLY-VOLTAGE (Vcc):
(Voltages referenced to ground)0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_1 < -0.5$ V OR $V_1 > V_{CC} +0.5$ V)
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} +0.5$ V)
DC DRAIN CURRENT, PER OUTPUT (I _O) (FOR -0.5 V $<$ V _O $<$ V _{CC} +0.5 V)
DC V_{cc} OR GROUND CURRENT (I _{cc}): \pm 70 mA
POWER DISSIPATION PER PACKAGE (P _ν):
For $T_A = -40$ to $+60$ °C (PACKAGE TYPE E)
For $T_A = +60$ to $+85$ °C (PACKAGE TYPE E)
For $T_A = -55$ to $+100$ °C (PACKAGE TYPE F, H)
For $T_A = +100$ to $+125$ °C (PACKAGE TYPE F, H)
For T _A = -40 to +70°C (PACKAGE TYPE M)
For T _A = +70 to +125°C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H55 to +125° C
PACKAGE TYPE E, M40 to +85°C
STORAGE TEMPERATURE (Tstg) -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. $+$ 265 $^{\circ}$ C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIM		
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _t			
at 2V	0	1000	ns
at 4.5 V	0	500	ns
at 6V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

TRUTH TABLE

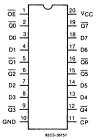
	Inputs							
ŌĒ	СР	Dn	Qn					
L		Н	L					
L		L	Н					
L	L	X	No Change					
Н	· X	X	Z					

Note:

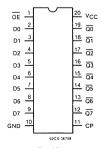
X=Don't care

Z=High impedance state

_/=Low-to-High transition



Top View CD54/74HC, HCT534 Types TERMINAL ASSIGNMENT



Top View CD54/74HC,HCT564 Types TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC534 CD74HC564											CD74HCT534/CD54HCT534 CD74HCT564/CD54HCT564										
			TEST IDITIONS	3	1	IC/54 TYPE		741 TY			HC PE	TEST CONDITIONS		74HCT/54HCT TYPE					74HCT TYPE		54HCT TYPE		UNITS
CHARACTERISTI		V, V	l _o mA	V _{cc}	-	+25°C	;	-4 +85		-5 +12	5/ 5°C	V,	V _{cc}	+	+25°C	;	i .	10/ 5°C	-55/ +125°C				
	ļ	•	ША	•	Min	Тур	Max	Min	Max	Min	Max		ľ	Min	Тур	Max	Min	Max	Min	Max			
High-Level				2	1.5			1.5	_	1.5	_		4.5										
Input Voltage	V _{IH}			4.5	3.15	-	_	3.15	_	3.15	_	_	to	2	_	-	2	-	2	-	v		
				6	4.2		_	4.2	_	4.2	_		5.5										
Low-Level				2	_		0.5	_	0.5	_	0.5		4.5										
Input Voltage	VIL			4.5	_		1.35		1.35	_	1.35	-	to		_	0.8	-	0.8	_	0.8	V,		
				6	_	_	1.8	_	1.8	_	1.8		5.5		-								
High-Level		VIL		2	1.9	_	_	1.9		1.9		VIL				Ì			ŀ				
Output Voltage V	/он	or	-0.02	4.5	4.4	_		4.4	_	4.4	-	or	4.5	4.4	_	_	4.4	_	4.4	_	v		
CMOS Loads		V _{IH}		6	5.9		_	5.9	_	5.9	_	ViH											
		VIL										VIL											
TTL Loads		or	-6	4.5	3.98	_	_	3.84		3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	٧		
(Bus Driver)		V _{IH}	-7.8	6	5.48		_	5.34	_	5.2	_	ViH											
Low-Level		VIL		2	_	_	0.1	_	0.1	_	0.1	VIL											
Output Voltage \	Vol	or	0.02	4.5			0.1	_	0.1	_	0.1	or	4.5	-	_	0.1	-	0.1	-	0.1	v		
CMOS Loads		V _{IH}		6		_	0.1	_	0.1	_	0.1	ViH											
		VIL										VIL	j						j				
TTL Loads	l	or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	-	0.33	-	0.4	v		
(Bus Driver)		ViH	7.8	6	_	_	0.26	_	0.33		0.4	ViH											
Input Leakage		Vcc										Any Voltage											
Current	l,	or		6	-	-	±0.1	-	±1	–	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ		
		Gnd										& Gnd						<u> </u>	<u> </u>				
Quiescent		Vcc										Vcc											
Device		or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	–	160	μА		
Current	Icc	Gnd		<u> </u>		<u> </u>			<u> </u>	<u></u>		Gnd	_					<u> </u>					
Additional Quiescent Device Current per input pin: 1 unit load ΔI	l _{cc} *											V _{cc} -2.1	4.5 to 5.5	_	100	360	-	450	_	490	μΑ		
3-State Leakage Current	loz	V _{IL} or V _{IH}	V₀=Vcc or Gnd	6	-	_	±0.5	-	±5.0	_	±10	V _{IL} or V _{IH}	5.5	_	_	±0.5	_	±5.0	_	±10	μΑ		

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA:

HCT Input Loading Table

Input	Unit Loads*
D ₀ —D ₇	0.15
СР	0.30
ŌĒ	0.55

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, Input t_s, t_t = 6 \text{ ns}$)

		C _L	ТҮР		
CHARACTERISTIC		(pF)	нс	нст	UNITS
Propagation Delay Clock to Q	t _{PLH}	15	13	14	ns
Propagation Delay Output Disable to Q	t _{PLZ} t _{PHZ}	15	12	12	ns
Propagation Delay Output Enable to Q	t _{PZL} t _{PZH}	15	12	14	ns
Maximum Clock Frequency	f _{max}	15	60	50	MHz
Power Dissipation Capacitance*	C _{PD}	_	32	36	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

PREREQUISITE FOR SWITCHING FUNCTION

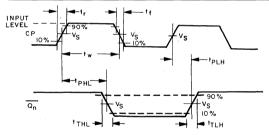
								LIM	ITS						
		TEST		25°	, C		-4	0° C to	o +85°	С	-55	s° C to	+125	° C	
CHARACTERIS	TIC	CONDITION V _{cc}	Н	С	нст		74	74HC		74HCT		нс	54HCT		UNITS
		Vcc	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Мах.	
Maximum Clock		2	6	_	_	_	5	—	_	_	4	_	_	_	
Frequency	f_{max}	4.5	30	_	25	_	25	—	20	_	20	_	16	<u> </u>	MHz
		6	35	_	_	_	29	_	-	_	23		_		
Clock Pulse Width		2	80	_	_	_	100		_	_	120	_	_	_	
	n t _w	4.5	16	_	20		20		25	-	24	-	30	_	ns
Fig. 2		6	14	_	_	_	17	-		_	20	_	_	_	
Set-up Time		2	60	_	_	_	75	_	_	_	90	_		_	
Data to Clock		4.5	12	_	20	_	15	_	25	_	18		30	-	ns
Fig. 3	tsu	6	10	-		_	13	_	-	—	15	_		—	
Hold Time		2	5	_		_	5	_	_	_	5	_	_	_	
Data to Clock	534	4.5	5		5	_	5		5	_	5		5	—	ns
Fig. 3	tн	6	5	_		_	5	_		_	5			—	
		2	5	_		_	5	_	_	_	5	_			
	564	4.5	5	—	3	-	5	-	3		5		3	—	ns
	t _H	6	5		_	-	5	_	_		5	_		_	

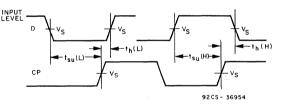
 $P_D = C_{PD} V_{CC}^2 f_i + \Sigma C_L V_{CC}^2 f_o$ where: $F_i = \text{input frequency } f_o = \text{output frequency}$,

 C_L = output load capacitance, V_{CC} = supply voltage.

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_f = 6 \text{ ns}$)

		TEST CONDITION				-4	0°C to	+85	°C	-5					
CHARACTERIST	IC		н	C	Н	СТ	74	нС	74F	ICT	54	нс	54F	ICT	UNITS
		V _{cc} V	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay Clock to Output Fig. 2	t _{PLH} t _{PHL}	2 4.5 6	_ _ _	165 33 28	_ _ _	_ 35 _	111	205 41 35		- 44 -	_ _ _	250 50 43	_ _ _	_ 53 _	ns
Propagation Delay Output Disable to Q Fig. 4 534	t _{PLZ}	2 4.5 6	_ _ _	150 30 26	<u>-</u>	30 —	_	190 38 33	_	38 —	_ _ _	225 45 38	_ _ _	45 —	ns
Propagation Delay Output Disable to Q Fig. 4 564	t _{PLZ}	2 4.5 6	- - -	135 27 23	 - -	_ 30 _	_	170 34 29	_	38 —		205 41 35	_	 45 	ns
Propagation Delay Output Enable to Q Fig. 4	t _{PZL}	2 4.5 6	_	150 30 26	 -	 35 	_	190 38 33	=	44 —	_	225 45 38	_	_ 53 _	ns
Output Transition Time Fig. 2	t _{TLH} t _{THL}	2 4.5 6	<u>-</u>	60 12 10	_ 	_ 12 _		75 15 13		15 —		90 18 15	_ _	_ 18 _	ns
Input Capacitance	Сι	_		10		10	_	10		10	_	10	_	10	pF
3-State Output Capacitance	Со	_	_	20	_	20	_	20	_	20	_	20	_	20	pF





92CS-38442

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Vs	50% Vcc	1.3 V

Fig. 2—Clock to output delays and clock pulse width.

	54/74HC	54/74HCT
Input Level	Vcc	3 V
V _s	50% V _{cc}	1.3 V

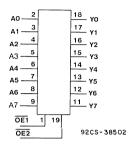
Fig. 3 — Data set-up and hold times.

0E	90 %
OUTPUT LOW TO OFF	— 10 %
OUTPUT HIGH TO OFF	90 %
OUTPUTS CONNECTED	OUTPUTS DISCONNECTED 92CS-38407
	9203-36407

	54/74HĆ	54/74HCT
Input Level	Vcc	3 V
Vs	50% V _{cc}	1.3 V

Fig. 4 — Transition times and propagation delay times.

High-Speed CMOS Logic



Octal Buffer and Line Drivers, 3-State

Type Features:

- 540 Inverting
- 541 Non-Inverting
- Buffered Inputs
- 3-State Outputs
- Bus Line Driving Capability
- Typical Propagation Delay = 9 ns @ V_{CC} = 5 V, C_L = 15pF, T_A = 25° C

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC540 and CD54/74HCT540 are Inverting Octal Buffers and Line Drivers with 3-State Outputs and the capability to drive 15 LSTTL loads. The RCA-CD54/74HC541 and CD54/74HCT541 are Non-Inverting Octal Buffers and Line Drivers with 3-State Outputs that can drive 15 LSTTL loads. The Output Enables $\overline{(OE1)}$ and $\overline{(OE2)}$ control the 3-State Outputs. If either $\overline{OE1}$ or $\overline{OE2}$ is HIGH the outputs will be in the high impedance state. For data output $\overline{OE1}$ and $\overline{OE2}$ both must be LOW.

The CD54HC and CD54HCT devices are supplied in 20-lead ceramic dual-in-line packages (F suffix). The CD74HC and CD74HCT devices are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range):
 Standard Outputs 10 LSTTL Loads
 Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- □ CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}: @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 μA @ V_{OL}, V_{OH}

TRUTH TABLE

i	NPUTS	3	OUTPUTS			
OE1	ŌE2	An	HC/ HCT540	HCT541		
L	L	Н	L	Н		
Н	Х	X	Z	Z		
X	Н	X	Z	Z		
L	L	L	Н	L		

H = HIGH Voltage Level

L = LOW Voltage Level

X = Immaterial

Z = High Impedance

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V _{cc}):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±35mA
DC V _{cc} OR GROUND CURRENT, PER PIN (I _{cc})	±70mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	
For T _A = +60 to +85°C (PACKAGE TYPE E)	. Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	•
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tstg)	65 to · 150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	*
with solder contacting lead tips only	+300°C

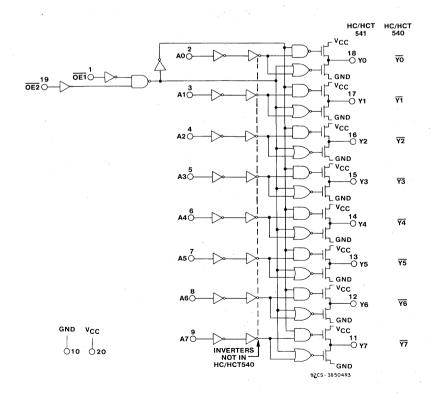


Fig. 1 — Logic diagram for the CD54/74HC/HCT 540 & 541

STATIC ELECTRICAL CHARACTERISTICS

			D74H										74HC							
CHARACTERISTIC	TEST CONDITIONS			1	74HC/54HC TYPES					HC PE	TEST CONDITIONS		74H:CT/54HCT TYPES			74HCT TYPE		54HCT TYPE		UNITS
CHARACTERISTIC			V _{cc}	-	+25° C		-40/ -55/ +85°C +125°C		V _I V _{cc}	+25° C		;	-40/ +85° C		-55/ +125° C					
				Min	Тур	Max	Min	Max	Min	Max			Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_		to	2	_	_	2	_	2	_	v
			6	4.2	_	_	4.2	_	4.2	_		5.5			ļ		1			
Low-Level			2			0.5	-	0.5	_	0.5		4.5								
Input Voltage V _{ii}			4.5	_	_	1.35	_	1.35	_	1.35	-	to	_	_	0.8	_	0.8	_	0.8	v
			6	_	_	1.8	_	1.8	_	1.8	İ	5.5								
High-Level	V _{IL}		2	1.9	_	_	1.9		1.9	_	V _{IL}									
Output Voltage Von	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4		v
CMOS Loads	V		6	5.9	_	_	5.9		5.9	_	V _{D4}									
	V _{IL}										V _{IL}									
TTL Loads	or	-6	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2	_	V _{oe}							i		
Low-Level	V,		2	_	_	0.1	_	0.1	_	0.1	V _i									
Output Voltage Vo.	or	0.02	4.5	_	_	0.1	_	0.1	-	0.1	or	4.5		_	0.1	_	0.1	_	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V						}			
	V,_										V,,									
TTL Loads	or	6	4.5	_		0.26		0.33	_	0.4	or	4.5	_		0.26		0.33	_	0.4	v
(Bus Driver)	V _{isc}	7.8	6	_	_	0.26	-	0.33	_	0.4	ViH						l.			
Input Leakage	Vcc										Any									
Current I,	or		6	_	_	±0.1	_	±1	_	±1	Voltage Between	5.5	_	_	±0.1	_	±1	_	<u>:</u> 1	μА
	Gnd										V∈∈ & Gnd									
Quiescent	Ve										V _{e,r}									
Device	or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	-	80	_	160	μA
Current I _{cc}	Gnd										Gnd						}			
Additional Quiescent Device Current per input pin: 1 unit load Δl_{cc}											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	-	490	μΑ
3-State	V.	V = V _{cc}									V									
Leakage Current	or	or	6	-	-	±0.5	-	±5.0	-	±10	or	5.5	-	_	±0.5	-	±5.0	-	<u>±</u> 10	μΑ
loz	V _{in}	Gnd									V, _H							ĺ		

*For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA. HCT Input Loading Tables

_			_
	CD54/74	HCT 540	
	Input	Unit Loads*	
	A0 — A7	1	
	ŌE2	0.75	
	ŌE1	1.15	

CD54/74 HCT 541							
Input	Unit Loads*						
A0 — A7	0.4						
ŌE2	0.75						
ŌE1	1.15						

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

OLIADA OTERIOTIO	LIN	IITS	LINUTE
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _{IN} , V _{OUT}	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C _
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r , t_f =6 ns)

CHARACTERISTIC		C _L	5	40	5	UNITS		
		(pF)	HC	HCT	HC	HCT		
Propagation Delay		15	9	9	9	11		
Data to Output	t _{PHL} t _{PLH}	13	9	9	9	1 ''	ns	
Output Enable and Disable to Outputs	t _{PZH} , t _{PZL} , t _{PHZ} , t _{PLZ}	15	13	14	14	14	ns	
Power Dissipation Capacitance*	C_{PD}		50	55	48	55	pF	

^{*}C_{PD} is used to determine the dynamic power consumption per channel.

 $PD = V_{CC}^2 f_i (C_{PD} + C_L)$

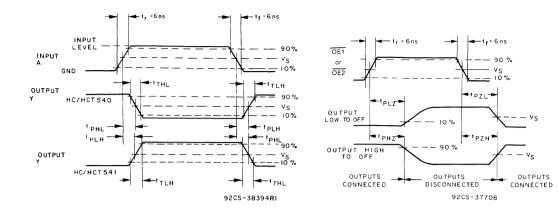
f_i = input frequency,

C_L = output load capacitance

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (C_L=50 pF, Input t_r,t_f=6 ns)

				25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	V_{cc}	Н	С	Н	СТ	741	нс	74F	ICT	54	нС	54H	ICT	UNITS
			Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2		110	_	_	_	140	_	_	-	165	_	_	
Data to Outputs	t _{PHL}	4.5	_	22		24		28	_	30	_	33	_	36	ns
HC/HCT 540		6	_	19	_		_	24		_	_	28			
Propagation Delay	t _{PLH}	2	Τ-	115	_	_		145		_	_	175	_	_	
Data to Outputs	t _{PHL}	4.5	_	23		28	_	29	_	35	_	35		42	ns
HC/HCT541		6	_	20	_	_	_	25	_	-	<u> </u>	30	_	_	
Propagation Delay	t _{PZH} , t _{PZL} ,	2	T —	160	_	_	_	200	_	_	_	240	_	_	
Output Enable and	t _{PHZ} ,	4.5	_	32	_	35	_	40	—	44	_	48	_	53	ns
Disable to Outputs	t _{PLZ}	6	-	27	_	_	_	34		_	_	41			
Output Transition	t _{TLH}	2	T —	60	_	_	-	75	_		_	90	_	_	
Time	t _{THL}	4.5	_	12	_	12	_	15	_	15	_	18	_	18	ns
		6	-	10	_	_	<u> </u>	13	_	_	_	15		—	l
Input Capacitance	Cı		_	10	_	10	_	10	_	10	_	10		10	pF
3-State Output				20		20		20		20		20		20	
Capacitance	Co		-	20	-	20	_	20	_	20	-	20	-	20	pF



	54/74HC	54/74HCT
Input Level	V _{CC}	3V
Switching Voltage, Vs	50% V _{CC}	1.3 V

Fig. 3 — Transition times and propagation delay times.

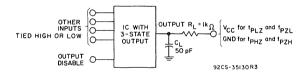


Fig. 4 — Three-state propagation delay test circuit.

OE1 -	0	20	vcc
A0 2		19	OE2
A1 3		18	Y0
A2 4		17	Υī
A3 5		16	<u>72</u>
A4 6		15	<u>73</u>
A5 7		14	<u>74</u>
A6 8		13	¥5
A7 9		12	76
GND 10		11	7 7
		ı	
	9205	3684	5

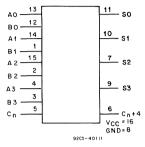
CD54/74HC, HCT540 Types TERMINAL ASSIGNMENT

_	
OE1 -	20 VCC
A0 2	19 OE2
A1 3	18 YO
A2 4	17 Y1
A3 5	16 Y2
A4 6	15 Y3
A5 7	14 Y4
A6 8	13 Y5
A7 9	12 Y6
GND 10	11 Y7
L_	
	92CS-36866

CD54/74HC, HCT541 Types TERMINAL ASSIGNMENT



High-Speed CMOS Logic



4-Bit BCD Full Adder With Fast Carry

Type Features:

- Adds two decimal numbers
- Full internal lookahead
- Fast ripple carry for economical expansion

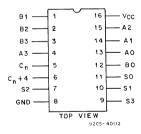
FUNCTIONAL DIAGRAM

The RCA-CD54/74HC583 and CD54/74HC7583 are binary-coded-decimal (BCD) full adders that add two 4-bit BCD numbers and generate a carry-out bit if the sum exceeds 9.

The CD54HC/HCT583 are supplied in 16-lead hermetic dual-in-line frit seal ceramic packages (F suffix). The CD74HC/HCT583 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
 - CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 μA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

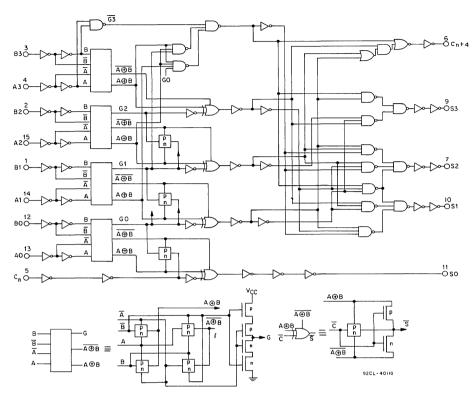


Fig. 1 - Logic diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc + 0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (T _{stg})	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	UNITS		
CHARACTERISTIC	MIN.	MAX.	OMITS	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			<u> </u>	
CD54/74HC Types	2	6	V	
CD54/74HCT Types	4.5	5.5	l v	
DC Input or Output Voltage V _I , V ₀	0	V _{CC}	V	
Operating Temperature T _A :				
CD74 Types	-40	+85	°C	
CD54 Types	-55	+125	°C	
Input Rise and Fall Times, t _r , t _f				
at 2 V	0	1000	ns	
at 4.5 V	0	500	ns	
at 6 V	0	400	ns	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

CD74HC583/CD54HC583												CD74HCT583/CD54HCT583									
		ı	TEST CONDITIONS			74HC/54HC TYPES			74HC 54H TYPES TYP			TEST CONDITION	1 S	74HCT/54HCT TYPES			74HCT TYPES		54H TYF		UNITS
CHARACTERISTIC		V ₁	lo	Vcc	,	•25° C	;	-4 +85		-5: +12!		V ı	Vcc		+25° C		ĺ	0/ 6°C	ſ	5/ 5°C	UNIIS
		v	mA	٧	Min	Тур	Max	Min	Max	Min	Max	V	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	ViH	Ì		4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	-	-	2	–	2		V
		L		6	4.2	_	_	4.2	-	4.2	_		5.5								
Low-Level				2		_	0.5		0.5	<u> </u>	0.5		4.5		Į		l				
Input Voltage	VIL			4.5		느	1.35	5 — 1.35 — 1.35		-	to	-	-	0.8	-	0.8		0.8	V		
		L		6	ᆫ	_	1.8	_	1.8		1.8		5.5	L					L		
High-Level		VIL		2	1.9	_	<u> </u>	1.9	<u> </u>	1.9		VIL		1	}	ł	ł	١.	Į		
Output Voltage	V_{OH}	or	-0.02	4.5	4.4	느		4.4		4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	٧
CMOS Loads		V _{IH}		6	5.9	_		5.9	_	5.9	_	V _{IH}		<u> </u>				L		₩-	<u> </u>
		VIL						L_			VIL		1	[ĺ	1					
TTL Loads		or	-4	4.5	3.98	<u> </u>		3.84	<u> </u>	3.7	-	or	4.5	3.98	-	-	3.84	-	3.7	-	V
		VIH	-5.2	6	5.48	_		5.34	_	5.2	-	V _{IH}	<u> </u>	-	-		-	—	ـ	↓	
Low-Level		VIL	}	2	<u> </u>	_	0.1		0.1	_	0.1	VIL		ļ	ļ	,		ļ			
Output Voltage	V_{OL}	or	0.02	4.5	느	_	0.1	<u> </u>	0.1	=	0.1	or	4.5	-	-	0.1	1 -	0.1	-	0.1	V
CMOS Loads		V _{IH}		6	=	느	0.1	<u> </u>	0.1	-	0.1	V _{IH}	ļ	—	<u> </u>	├—		<u> </u>	<u> </u>	├ ─	
		VIL	<u> </u>	├			_	_	<u> </u>		_	VIL		1 1	l			ł	ł		
TTL Loads		or	4	4.5	├-	-	0.26	_	0.33	-	0.4	or	4.5	-	-	0.26	-	0.33	_	0.4	V
		ViH	5.2	6	_	_	0.26	-	0.33	=	0.4	V _{IH}		-	├		-	├	-	├	
Input Leakage		Vcc		İ		1	ł		1	ļ	\	Any		i	1		1	ł			
Current	h	or		6	-	-	±0.1	_	±1	-	±1	Voltage	5.5	-	۱ —	±0.1	— ·	±1	l –	±1	μΑ
		Gnd		l	1	ĺ	ł		1		l	Between Vcc & Gnd		ł	ł	l	ľ		ł		
Quiescent		Vcc		+-	├		├				├	V _{cc} & Gild	-	┼─	┼	├	╁	├-	├	-	
Device Current	lcc	or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μΑ
257,00 04110111	100	Gnd	١	١			١		"		"	Gnd		1		١		"			
Additional		1		L	—	L	L		Ь	Ь	Ь—		_	1		_	\vdash	\vdash	\vdash	 	
Quiescent Device													4.5	1	1	1			1	1	
Current per input		}										V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	Δlcc*				5.5]]											
436		dual-su	pply sy	stems	theo	retica	wors	st cas	e (Vı :	2.4 \	/, Vcc	= 5.5 V) specif	icatio	n is 1	.8 mA						

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS *
All	1.5

^{*} Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 µA max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

		TYPICAL			
CHARACTERISTIC	C∟ (pF)	нс	нст	UNITS	
Propagation Delay,					
C _n to S _n	t _{PHL} , t _{PLH}	15	24	24	
A _n or B _n to S _n	t _{PHL} , t _{PLH}	15	23	29	ns
C _n to C _n + 4	t _{PHL} , t _{PLH}	15	15	18	
A _n or B _n to C _n + 4	t _{PHL} , t _{PLH}	15	16	22	
Power Dissipation Capacitance *	CPD	_	50	54	pF

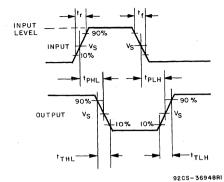
^{*}CPD is used to determine the dynamic power consumption, per package

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$ where: f_i = input frequency C_L = output load capacitance

V_{cc} = supply voltage

SWITCHING CHARACTERISTICS (CL = 50 pF, Input t, t, = 6 ns)

			LIMITS													
CHARACTERISTIC		TEST CONDITIONS	25° C					0°C to	o +85°	,C	-55	5°C to	+125	°C	UNITS	
CHARACTERISTIC			I	С	н	СТ	74	нс	74F	ICT	54	нс	54F	ICT	UNITS	
		V _{cc} V	Min.	Max.	Min.	Max.	Min.	Ma×.	Min.	Max.	Min.	Мах.	Min.	Max.		
Propagation Delay, t _F	н	2	_	290	_	_	_	365	_	_	_	435	_	_		
t _P	4L	4.5	_	58	_	58	_	73	-	73	—	87	_	87		
C _n to S _n		6		49	_			62			_	74				
t _P	.н	2	_	280	-	_	_	350	_	_		420	_	-		
t _P	11.	4.5	_	56	_	68	_	70	-	85		84	-	102		
A _n or B _n to S _n		6	_	48	_	_	-	60	_		_	71	_	_		
t _P	.н	2	_	180	_	_	_	225	_	_	-	270	_	_		
t _P	11.	4.5	_	36	—	42	_	45	_	53	l —	54	—	63	ns	
C _n to C _n + 4		6	_	31	_	_	_	38	_			46	_			
t _P	.н	2	_	195	_	-		245	_	_	_	295	_	_		
t _P	11.	4.5	_	39	_	51		49	_	64	_	59	-	77		
A_n or B_n to $C_n + 4$		6		33	_	_		42			_	50	_			
Transition t _T	.н	2	_	75	_	_	_	95	_	-	_	110	_	_		
Time t _T	_{ال} ا	4.5	_	15	_	15	_	19	_	19	_	22	l —	22		
		6		13	_	_	_	16	-	<u> </u>		19	_	_		
Input Capacitance			_	10	1	10	_	10	_	10	_	10	_	10	pF	



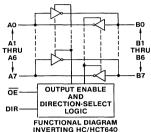
	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, V _s	50% V _{cc}	1.3 V

Fig. 2 - Transition and propagation delay times.

Application

In an application where a binary number whose decimal value is greater than 9 is to be added to a BCD number (0-9), this device can be used to convert the binary number to a BCD number and a carry. The resultant BCD + carry can then be added to the other BCD operand to complete the operation. The conversion from binary to BCD is accomplished by adding the binary number to BCD "0" (binary number on A0-A3 and 0000 on B0-B3).

High-Speed CMOS Logic



92CS-38780

Octal 3-State Bus Transceivers

Inverting (HC/HCT640) True/Inverting (HC/HCT643)

Type Features:

- 3-state outputs
- Buffered inputs
- Applications in multiple-data-bus architecture

The RCA-CD54/74HC640, 643 and CD54/74HCT640, 643 silicon-gate CMOS 3-state bidirectional inverting and non-inverting buffers are intended for two-way asynchronous communication between data buses. They have high drive current outputs which enable high-speed operation when driving large bus capacitances. These circuits possess the low power dissipation of CMOS circuits, and have speeds comparable to low power Schottky TTL circuits. They can drive 15 LSTTL loads.

The CD54/74HC640 and CD54/74HCT640 are inverting buffers; the CD54/74HC643 and CD54/74HCT643 are true/inverting buffers.

The direction of data flow (A to B, B to A) is controlled by the DIR input.

Outputs are enabled by a low on the Output Enable input (OE); a high OE puts these devices in the high impedance mode.

The CD54HC640, 643 and the CD54HCT640, 643 are supplied in 20-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC640, 643 and CD74HCT640, 643 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface mount plastic packages (M suffix). These devices are also supplied in chip form (H suffix).

Family Features:

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}= 30%,N_{IH}=30% of V_{CC} @ V_{CC}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}

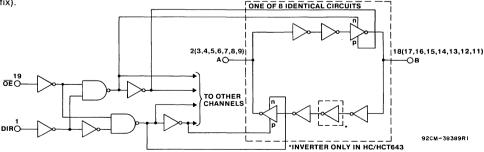
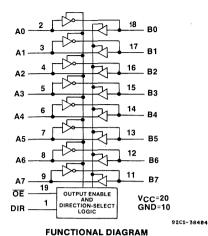


Fig. 1 - Logic diagram.



TRUTH TABLE

CON'	TROL UTS		640 Series PORT TUS	HC, HCTC	PORT
ŌĒ	DIR	A _n	B _n	A _n	B _n
Ĺ	L	ō	ı	0	ı
Н	Н .	Z	Z	Z	Z
Н	Ŀ	Z	Z	Z	Z
L	Н	1	ō	I	ō

To prevent excess currents in the High-Z modes all I/O terminals should be terminated with $10K\Omega$ to $1M\Omega$ resistors.

H = High

O = Output (Same Level as Input)

L = Low

O = Output (Inversion of Input Level)

I = Input

Z = High Impedance

TRUE/INVERTING HC/HCT643

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, IIK (FOR Vi < -0.5 V OR Vi > Vcc +0.5 V) .	±20 mA
DC OUTPUT DIODE CURRENT, l_{OK} (FOR $V_{\text{o}} < -0.5~\text{V}$ OR $V_{\text{o}} > V_{\text{CC}}$ +0.5	V)±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 %	,)±35 mA
DC Vcc OR GROUND CURRENT, (Icc)	±70 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	
For J _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70° C (PACKAGE TYPE M)	
For $T_A = +70$ to $+125^{\circ}$ C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F. H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

OUADA OTEDIOTIO	LIN	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
Vcc:*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage, V ₁ , V ₀	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	1
Input Rise and Fall Times, t _r ,t _f :			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

			CD7	4HC6	40/64	3/CD	54HC	640/6	43			CD	74HCT	640/6	43/CI	054H	CT64	0/643				
		1	TEST		74H	C/54	нс	741	IC.	541	IC	TEST		74HC		нст	74H		54H		1	
CHARACTERISTI	cs	CON	DITIO	NS.	<u> </u>	TYPE		TY	PE	TY	PE	CONDITIO	ONS		TYPE		TY	PE	TY	PE	UNITS	
OHAHAO IZMOTI		V,	lo	Vcc	•	-25° C	:	-4 +85		-5: +12:	- 1	V _i	V _{cc}		25° C		-4 +85	0/ 5°C	-5: +12!		0	
		٧	mA	v	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max		
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5									
Input Voltage	ViH			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	_	2	_	v	
				6	4.2	_		4.2		4.2			5.5									
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5									
Input Voltage	VIL			4.5	_	_	1.35	_	1.35	_	1.35	_	to	-	_	0.8	-	0.8	_	0.8	V	
				6	<u> </u>	<u> </u>	1.8		1.8	_	1.8		5.5									
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VIL										
Output Voltage	VoH	or	-0.0,2	4.5	4.4			4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	v	
CMOS Loads		ViH		6	5.9	_	_	5.9	_	5.9	_	ViH										
		VIL										VIL		ł	}		ł					
TTL Loads		or	-6	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	- 1	٧	
Bus Driver		V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2		ViH										
Low-Level		VIL		2	_	_	0.1		0.1	_	0.1	VIL				ŀ			ļ			
Output Voltage	V_{OL}	or	0.02	4.5	_		0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v	
CMOS Loads		VIH		6	_	_	0.1	_	0.1		0.1	ViH										
		VIL										VIL										
TTL Loads		or	6	4.5	_	_	0.26	_	0.33	<u> </u>	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	٧	
Bus Driver		VIH	7.8	6	<u> </u>	_	0.26	_	0.33	_	0.4	V _{IH}										
Input Leakage Current	l ₁	V _{cc} or Gnd		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1	_	±1	μΑ	
Quiescent Device Current	lcc	V _{cc} or Gnd	0	6	_	_	8	_	80	_	160	V _{cc} or Gnd	5.5	-	_	8	_	80	_	160	μΑ	
Additional Quiescent Device Current per Input Pin: 1 Unit Load	Δl _{cc} *,											V _{cc} -2.1	4.5 to 5.5	_	100	360	-	450	-	490	μF	
3-State Leakage Current	loz	V _{IL} or V _{IH}	Vo= Vcc or Gnd	6	-	-	±0.5	-	±5	-	±10	V _{IL} or V _{IH}	5.5	-	-	±0.5	-	±5	-	±10	μΑ	

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

	UNIT L	OADS *
INPUT	HCT640	HCT643
DIR	0.9	0.9
ŌĒ, A	1.5	1.5
В	1.5	0.4

^{*} Unit load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.



SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ} \text{ C}$, Input t_r , $t_f = 6 \text{ ns}$)

				TYPICAL	VALUES			
CHARACTERIS	TIC CL pF	SYMBOL	HC640	HCT640	HC643	HCT643	UNITS	
Propagation Delay								
$A \rightarrow \overline{B}, B \rightarrow \overline{A}$		t _{PHL} , t _{PLH}	7	9	7	9		
B → A	15			_	9	10	ns	
Enable to High	z	t _{PHZ} , t _{PLZ}	12	12	12	12		
Enable from Hig	gh Z	t _{PZH} , t _{PZL}	12	12	12	13		
Power Dissipation Capacitance	_	C _{PD} *	38	41	45	55	pF	

^{*} C_{PD} is used to determine the dynamic power consumption per channel.

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, input t_r , $t_f = 6 \text{ ns}$)

				25	°C		-4	0°C t	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	н	С	Н	СТ	74	нс	74F	ЮТ	54	нс	54H	НСТ	UNITS
			Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Мах.	
Propagation Delay	t _{PLH}	2	_	90	_	-	_	115		_	_	135	_	-	
$A \rightarrow \overline{B}$ 640/643	t _{PHL}	4.5	-	18	_	22	-	23	-	28	-	27	_	33	ns
$B \rightarrow \overline{A}$		6	_	15	_	-	_	20	_	_	—	23	_	—	
643	t _{PLH}	2	_	110	_	=	-	140	-	-	_	165	_	-	
B → A	t _{PHL}	4.5	—	22	_	26	_	28	—	33	—	33	—	39	ns
		6	_	19	_	-	—	24	—	—	—	28	-	-	
Output High-Z:	t _{PZH}	2	Ι-	150	_	-	T —	190	_	_	_	225	_	-	
To High Level, 640	t _{PZL}	4.5	_	30	_	30	-	38	-	38	—	45	_	45	ns
To Low Level		6	_	26	—	-	-	33	-	—	—	38	_	-	
Output High Level,	t _{PHZ}	2	_	150	_	-	_	190	_	_	_	225	_	_	
Output Low Level	t _{PLZ}	4.5	_	30	_	30	_	38	—	38	-	45	_	45	ns
to High Z		6	—	26	—	-	<u> </u>	33	-	-	—	38	—	_	
Output High Z:	t _{PZH}	2	_	150	_	-	-	190	_	_	_	225	_	-	
To High Level 643	t _{PZL}	4.5	-	30	_	33	-	38	_	41	—	45	—	50	ns
To Low Level		6	-	26	_	—	-	33	—	—	-	38	_	-	
Output High Level, 643	t _{PHZ}	2	-	150	_	_	-	190	_	-	_	225	_	<u> </u>	
Output Low Level 643	t _{PLZ}	4.5	_	30		30	-	38	-	38	-	45		45	ns
to High Z		6	—	26	_	-	—	33	-	_	_	38	-	_	
Output Transition	t _{TLH}	2	_	60	_	_	_	75	-	-	_	90	_	-	
Time	t _{THL}	4.5	_	12	_	12	-	15	-	15	_	18	-	18	ns
		6	-	10		-	-	13	-	-	-	15	-	-	
Input Capacitance	C _{in}		_	10	_	10	_	10		10	-	10	_	10	pF
3-State Output Capacitance	C _o		_	20	_	20	_	20	_	20	_	20	_	20	pF

 $P_D = V_{CC}^2 f_i (C_{PD} + C_L)$, where: f_i = input frequency. C_L = output load capacitance. V_{CC} = supply voltage.

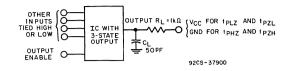


Fig. 2 - Three-state propagation delay test circuit.

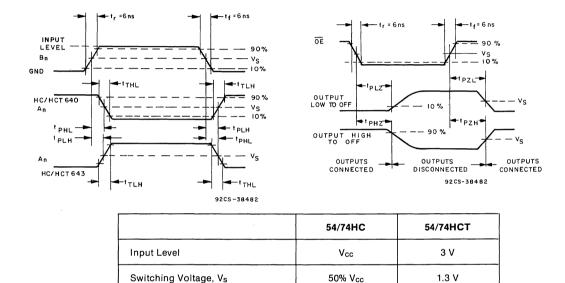
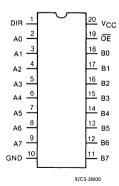


Fig. 3 - Transition times and progagation delay times.

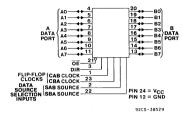


TERMINAL ASSIGNMENT

File Number 1664

Advance Information/ **Preliminary Data**

High-Speed CMOS Logic



Octal Bus Transceiver/Register. 3-State

Type Features:

- Independent Registers for A and B Buses
- CD54/74HC/HCT646 Non-Inverting CD54/74HC/HCT648 Inverting
- 3-State Outputs
- Drives 15LSTTL loads
- Typical Propagation Delay = 12ns (A → B) @ $V_{CC} = 5 \text{ V}, C_L = 15 \text{ pF}, T_A = 25^{\circ} \text{ C}$

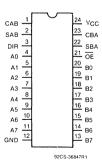
FUNCTIONAL DIAGRAM

The RCA-CD54/74HC646 and CD54/74HCT646 are octal bus transceivers/registers with 3-state non-inverting outputs. The RCA-CD54/74HC648 and CD54/74HCT648 are octal bus transceivers/registers with 3-state inverting outputs. These devices are bus transceivers with D-type flip-flops which act as internal storage registers. Data on the A bus or the B bus can be clocked into the registers on the LOW-to-HIGH transition of either CAB or CBA clock inputs. Output enable (OE) and direction (DIR) inputs control the transceiver functions. Data present at the high impedance output can be stored in either register or both but only one of the two buses can be enabled as outputs at any one time. The select controls (SAB and SBA) can multiplex stored and transparent (real time) data. The direction control determines which data bus will receive data when the output enable (OE) is LOW. In the high impedance mode (output enable HIGH). A data can be stored in one register and B data can be stored in the other register. The clocks are not gated with the direction (DIR) and output enable (OE) terminals; data at the A or B terminals can be clocked into the storage flip-flops at any time

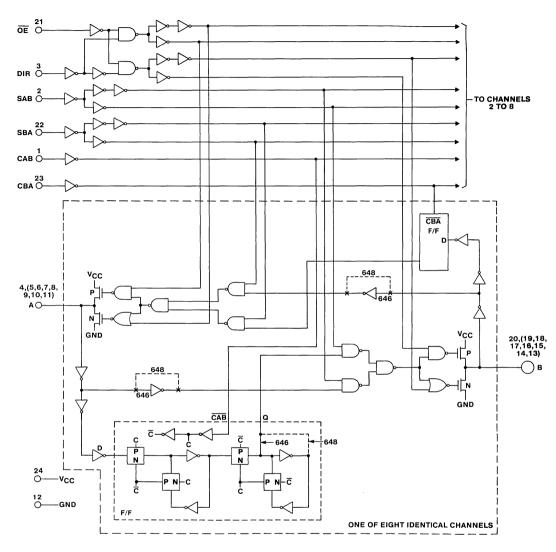
The CD54HC646, 648 and CD54HCT646, 648 are supplied in 24-lead dual-in-line frit-seal ceramic packages (F suffix). The CD74HC646, 648 and CD74HCT646, 648 are supplied in 24-lead dual-in-line, narrow-body plastic packages (EN suffix), in 24-lead dual-in-line, wide-body plastic packages (E suffix), and in 24-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity:
- $\bar{N}_{\rm IL}$ = 30%, $N_{\rm IH}$ = 30% of $V_{\rm CC}$; @ $V_{\rm CC}$ = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility $V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.$ **CMOS Input Compatibility** $I_1 \leq 1 \,\mu A \, @ \, V_{OL}, \, V_{OH}$



TERMINAL ASSIGNMENT



92CL - 3853ORI

Fig. 1 — Logic Diagram.

FUNCTION TABLE

		INP	UTS			DATA	A I/O #	OPERATION (OR FUNCTION
ŌE	DIR	CAB	CBA	SAB	SBA	A0 THRU A7	B0 THRU B7	646	648
X	X	~	Χ	Χ	Х	Input	Not specified	Store A, B unspecified	Store A, B unspecified
X	Χ_	X	~	Х	Х	Not specified	Input	Store B, A unspecified	Store B, A unspecified
Н	X	5	~	X	Х	1	la aut	Store A and B Data	Store A and B Data
Н	Х	H or L	H or L	Х	Х	Input	Input	Isolation, hold storage	Isolation, hold storage
L	L	Х	X	Х	L	0	1	Real-Time B Data to A Bus	Real-Time B Data to A Bus
L	L	Х	H or L	Х	Н	Output	Input	Stored B Data to A Bus	Stored B Data to A Bus
L	Н	Х	Х	L	Χ		0.4-	Real-Time A Data to B Bus	Real-Time A Data to B Bus
L	Н	H or L	X	Н	Х	Input	Output	Stored A Data to B Bus	Stored A Data to B Bus

[#] The data output functions may be enabled or disabled by various signals at the OE and DIR inputs. Data input functions are always enabled, i.e., data at the bus pins will be stored on every low-to-high transition on the clock inputs.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V _{CC}):
(Voltages referenced to ground)
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} -0.5$ V) ± 20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)
DC DRAIN CURRENT, PER OUTPUT (I $_{o}$) (FOR -0.5 V < V $_{o}$ < V $_{cc}$ + 0.5V)
DC V _{cc} OR GROUND CURRENT (I _{cc}) ±70mA
POWER DISSIPATION PER PACKAGE (Pp):
For $T_A = -40$ to $+60$ ° C (PACKAGE TYPE E)
For T _A = +60 to +85°C (PACKAGE TYPE E)
For T _A = -55 to +100°C (PACKAGE TYPE F, H)
For T _A = +100 to +125° C (PACKAGE TYPE F, H)
For T _A = -40 to +70°C (PACKAGE TYPE M)
For T _A = +70 to +125° C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE E, M
PACKAGE TYPE F. H
STORAGE TEMPERATURE (T _{stg})65 to150° C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. -265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERICTIC	LIM	IITS	LINUTC
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	\ \ \
DC Input or Output Voltage V _{IN} , V _{OUT}	0	V _{CC}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	i
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

To prevent excess currents in the High-Z modes all I/O terminals should be terminated with 10KΩ resistors.

STATIC ELECTRICAL CHARACTERISTICS

						1HC64 1HC64							74HC							
CHARACTERISTIC		TEST NDITIONS			IC/54		741 TYI	HC PES	541 TYI		TEST			CT/54 TYPES		74H TYF		54H TYI	ICT PES	UNITS
CHARACTERISTIC	V,	I _o	V _{cc}		+25° C	;		0/ 5° C	-5 +12	5/ 5° C	V, V	V _{cc}		+25° C		-4 +85	0/ 5° C	-55/ +125° C		
		""	ľ	Min	Тур	Max	Min	Max	Min	Max	'	ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	-	1.5	_		4.5								
Input Voltage V _™			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	_	2		v
			6	4.2	_	_	4.2	_	4.2	_	1	5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	_		0.8	_	0.8	- 1	0.8	v
			6		_	1.8	_	1.8	_	1.8	1	5.5								
High-Level	V _{IL}		2	1.9	_	-	1.9	_	1.9	 -	Vil									
Output Voltage V _{CH}	or	-0.02	4.5	4.4	_	_	4.4	-	4.4	-	or	4.5	4.4	_	_	4.4	_	4.4		V
CMOS Loads	V _{in}		6	5.9	_	-	5.9	_	5.9	_	V,,,									
	V _{IL}										Vil									
TTL Loads	or	-6	4.5	3.98	_	_	3.84	_	3.7		or	4.5	3.98	_	_	3.84	_	3.7	_	V
(Bus Driver)	V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2	_	V _n ,									
Low-Level	VıL		2	-	_	0.1	_	0.1	T-	0.1	V _n									
Output Voltage Vo.	. or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads	V _{B4}		6	_	_	0.1	_	0.1	_	0.1	V,,,									
	V _{IL}										VıL									
TTL Loads	or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v
(Bus Driver)	V _{IH}	7.8	6	-	-	0.26	_	0.33	_	0.4	V _n ,	ļ			ĺ					
Input Leakage	V _{cc}										Any									
Current I _I	or		6	_	-	±0.1	_	±1	_	±1	Voltage Between	5.5	_	_	±0.1	_	±1	_	±1	μΑ
	Gnd			İ			ŀ		ļ		V _{cc} & Gnd									
Quiescent	V _{cc}										Voc									
Device	or	0	6	-	_	8	-	80	_	160	or	5.5	_	-	8	_	80	_	160	μΑ
Current I _{cc}	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-State	V _{IL}	V _o = V _{CC}	Ι	Γ	Ī				Γ		V _{IL}		\vdash	_		-				_
Leakage Current	or	or	6	_	_	±0.5	_	±5.0	_	±10	or	5.5	_	_	±0.5	-	±5.0	_	±10	μА
loz	V _{IH}	Gnd									V _{IH}									
	- '''					<u> </u>		<u> </u>		<u> </u>	L	<u></u>			1				1	L

 $^{\circ}$ For dual-supply systems theoretical worst case (V_i = 2.4 V, V_{cc} = 5.5 V) specification is 1.8 mA. HCT Input Loading Table

Input	Unit Loads*
ŌĒ	1.3
DIR	0.75
Clock A→B, B →A	0.6
Select A, Select B	0.45
Inputs A0-A7, B0-B7	0.3

*Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r , t_r = 6 ns)

CHARACTERISTIC		CL	TYP	ICAL	UNITS	
CHARACTERISTIC		(pF)	нс	нст	UNITS	
Propagation Delays Store A Data to B Bus (646)	tрин, t _{РНL}	15	18	18	ns	
Store B Data to A Bus (646)	t _{PLH} , t _{PHL}	15	18	18	ns	
Store A Data to B Bus (648)	t _{PLH} , t _{PHL}	15	20	23	ns	
Store B Data to A Bus (648)	t _{PLH} , t _{PHL}	15	20	23	ns	
A Data to B Bus (646)	t _{PLH} , t _{PHL}	15 ·	12	15	ns	
B Data to A Bus (646)	t _{PLH} , t _{PHL}	15	12	15	ns	
A Data to B Bus (648)	t _{PLH} , t _{PHL}	15	12	15	ns	
B Data to A Bus (648)	t _{PLH} , t _{PHL}	15	12	15	ns	
Select to Data (646)	t _{PLH} , t _{PHL}	15	14	19	ns	
Select to Data (648)	t _{PLH} , t _{PHL}	15	16	19	ns	
3-State Disabling Time	t _{PLZ} , t _{PHZ}	15	14	14	ns	
3-State Enabling Time	t _{PZL} , t _{PZH}	.15	14	19	ns	
Max Frequency	f _{max}	15	60	45	MHz	
Power Dissipation Capacitance*	C _{PD}		52	52	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

PREREQUISITE FOR SWITCHING FUNCTION

				25	°C		-4	0°C to	o +85°	С	-5				
CHARACTERISTIC		V_{cc}	Н	С	Н	СТ	74	НС	74F	ICT	54	НС	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
		2	6			-	5	_	_	_	4	_	_	-	
Maximum Frequency	f _{MAX}	4.5	30	_	25	_	25		20	_	20	_	17	_	MHZ
		6	35	-	_	_	29	_	—	_	23	_	-	-	
0.11.7		2	60	_	_	_	75	_	_	_	90	-	_	_	
Set Up Time	+	4.5	12	_	12	-	15	_	15	_	18	_	18	_	ns
Data to Clock	tsu	6	10	_	—	-	13	_	_	_	15			_	
Hold Time		2	35	_	_	_	45	_	_	T-	55	T —	_	_	
Hold Time		4.5	7		5	-	9	_	5	_	11	_	5	_	ns
Data to Clock t _i	t _H	6	6	_	_	-	8	 -	_	_	9				
		2	80	_	_	T -	100	_	_	_	120	T —	_	_	
Clock Pulse Width	tw	4.5	16	.—	25	_	20	_	31	_	24	l —	38	_	ns
		6	14	-	_	_	17	—	_	_	20	l —	_	<u> </u>	

 $P_D = V_{CC}^2 C_{PD} f_i + \Sigma V_{CC}^2 C_L f_o$ where:

C_L = output load capacitance

V_{cc} = supply voltage

f = input frequency

fo = output frequency

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_f = 6 ns)

				25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC		\mathbf{v}_{cc}	Н	С	Н	СТ	741	нс	74F	ICT	54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,		2	_	220	-		-	275		_		330	_	_	
Store A data to B bus	t _{PLH}	4.5		44	_	44		55		55	—	66	_	66	ns
Store B data to B bus (646)	t _{PHL}	6		37				47	_			5.6	_		
Store A data to B bus	t _{PLH}	2	_	240	_	-	-	300	_	-	_	360	_	–	
Store B data to A Bus	t _{PHL}	4.5	-	48		54	—	60	_	68	_	72	_	81	ns
(648)		6		41		_		51		<u> </u>	_	61			
A data to B bus	t _{PLH}	2	-	135		_	_	170	_	_	_	205	-	-	
B data to A Bus	t _{PHL}	4.5	_	27	-	37	—	34	_	46	_	41	-	56	ns
(646)		6	<u> </u>	23			L — .	29	_		_	35			
Ā data to B bus	t_{PLH}	2		150	—			190	<u> </u>	-		225		—	
B data to A Bus	t_{PHL}	4.5	-	30	—	37	—	38		46	—	45	—	56	ns
(648)		6		26		_		33	_		_	38			
Select to Data		2	-	170	_	-	<u> </u>	215	-	<u> </u>	-	255	-	-	
	t _{PLH}	4.5	-	34	_	46		43	_	58	_	51	_	69	ns
(646)	t _{PHL}	6		29	_	_	_	37	_			43	_	<u></u>	
Select to Data		2	-	190	—	—	-	240	_	-	_	285	_	—	
Colour to Bata	t _{PLH}	4.5	I —	38	-	46	—	48	-	58	-	57	-	69	ns
(648)	t _{PHL}	6		32	ļ —	—	-	39	—	-	<u> </u>	48	_	<u> </u>	,
3-State Disabling Time		2	-	175	_	-	_	220	_	_	_	265	_	_	
Bus to Output or	t _{PLZ}	4.5	-	35	—	35	_	44	-	44	<u> </u>	53	—	53	ns
Register to Output	t _{PHZ}	6	_	30	_	_		37				45	_		
3-State Enabling Time		2	-	175	-		—	220	—	<u> </u>	-	265	—	-	
Bus to Output or	t_{PZL}	4.5	-	35	—	45	-	44	—	56	-	53	·	68	ns
Register to Output	t _{PZH}	6		30				37	_			45	_		
Output Transition Time		2	-	60	-	-		75	—	-	_	90	_	-	
	t _{TLH}	4.5	-	12	_	12	-	15	 -	15	-	18	_	18	ns
	t _{THL}	6	L	10		_		13	_			15			
3-State Output				-		-	-	-	-	—	—	—	-	-	
Capacitance	C。	-	-	20	—	20	—	20	-	20	-	20	-	20	pF
				<u> </u>	<u></u>	<u></u>		<u> </u>							
Input Capacitance	С		_	10	_	10		10	_	10	_	10	_	10	pF

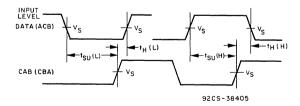
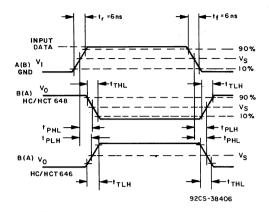
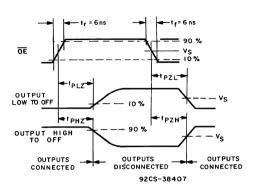


Fig. 2 — Data setup and hold times.

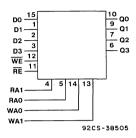




	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 3 — Transition times and propagation delay times.

High-Speed CMOS Logic



4 x 4 Register File

Type Features:

- Simultaneous and Independent Read and Write Operations
- Expandable to 512 Words of n-Bits
- 3-State Outputs
- Organized as 4 Words x 4 Bits Wide
- Typical read time: 16 ns for HC670 at V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C
- Buffered inputs

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC670 and CD54/74HCT670 are 16-bit register files organized as 4 words x 4 bits each. Read and write address and enable inputs allow simultaneous writing into one location while reading another. Four data inputs are provided to store the 4-bit word. The write address inputs (WA0 and WA1) determine the location of the stored word in the register. When write enable (\overline{WE}) is low the word is entered into the address location and it remains transparent to the data. The outputs will reflect the true form of the input data. When (\overline{WE}) is high data and address inputs are inhibited. Data acquisition from the four registers is made possible by the read address inputs (RA1 and RA0). The addressed word appears at the output when the read enable (\overline{RE}) is low. The output is in the high inpedance state when the (\overline{RE}) is high. Outputs can be tied together to increase the word capacity to 512 x 4 bits.

The RCA CD54HC/HCT670 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT670 are supplied in a 16-lead dual-in-line plastic package (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range):
 Standard Outputs 10 LSTTL Loads
 Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation

High Noise Immunity:

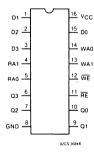
 $N_{\rm IL} = 30\%$, $N_{\rm IH} = 30\%$ of $V_{\rm CC}$; @ $V_{\rm CC} = 5 \ V$

■ CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation

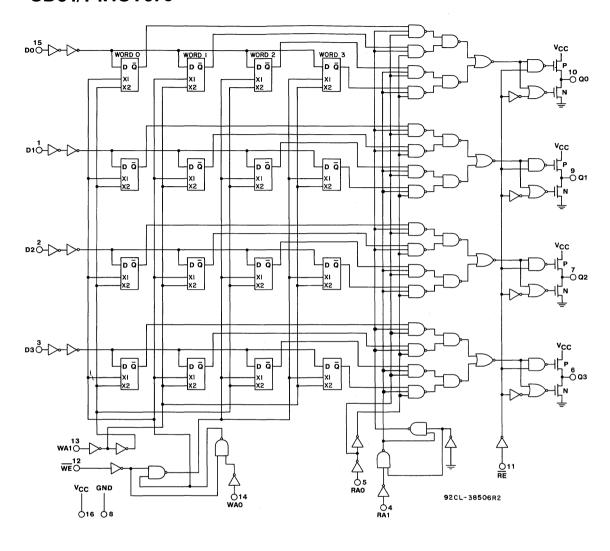
Direct LSTTL Input Logic Compatibility $V_{1L} = 0.8 \text{ V Max.}, V_{1H} = 2 \text{ V Min.}$

CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$



TERMINAL ASSIGNMENT



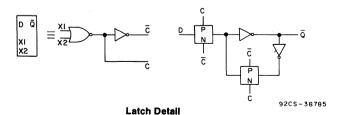


Fig. 1 — Logic Diagram.

WRITE MODE SELECT TABLE

OPERATING	INP	UTS	INTERNAL
MODE	WE	D _N	LATCHES(a)
Maita Data	L	L	L
Write Data	L	н	н
Data		X	no obongo
Latched	Н	_ ^	no change

NOTE:

 a. The Write Address (WA0 and WA1) to the "internal latches" must be stable while WE is LOW for conventional operation.

READ MODE SELECT TABLE

OPERATING		INPUTS	OUTPUT
MODE	RE	INTERNAL LATCHES(b)	Q _N
Read	L	L	L
11000	L	н	Н
Disabled	Н	Х	(Z)

NOTE:

- b. The selection of the "internal latches" by Read Address (RA0 and RA1) are not constrained by WE or RE operation
- H = HIGH voltage level
- L = LOW voltage level
- X = Don't care
- Z = HIGH impedance "off" state.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, $I_{i\kappa}$ (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)	±20mA
DC OUTPUT DIODE CURRENT, IOK (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Vo $<$ Vcc $+$ 0.5V)	±35 mA
DC V _{CC} OR GROUND CURRENT (I _{CC})	±70 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	. Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	., 500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	. Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	IITS	UNITS		
CHARACTERISTIC	MIN.	MAX.	UNITS		
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*					
CD54/74HC Types	2	6	V		
CD54/74HCT Types	4.5	5.5	V		
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V		
Operating Temperature T _A :					
CD74 Types	-40	+85	°C		
CD54 Types	-55	+125			
Input Rise and Fall Times t _r , t _f					
at 2 V	0	1000			
at 4.5 V	0	500	ns		
at 6 V	0	400	}		

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC670/CD54HC670											74HC	T670	/CD54	4HCT	670			
CHARACTERISTIC	COI	TEST NDITIONS			HC/54 SERIE			HC RIES		HC HES	TEST		1	CT/54 ERIE		74HCT SERIES			HCT	
CHARACTERISTIC	V,	I _o	V _{cc}		+25° (;		10/ 5° C		5/ 5°C	V,	V _{cc}		+25° C		1	0/ 5° C	1	5/ 5°C	UNITS
	·			Min	Тур	Max	Min	Max	Min	Max			Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	-	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_] -	to	2	_	-	2	_	2	_	v
			6	4.2	-	_	4.2	-	4.2	_	}	5.5		}				Ì		
Low-Level			2	_	_	0.5	_	0.5	-	0.5		4.5								
Input Voltage V _{IL}		İ	4.5	_	_	1.35	_	1.35	-	1.35	_	to	_	-	0.8	_	0.8	_	0.8	v
			6	_	_	1.8	_	1.8	-	1.8	1	5.5								
High-Level	V _{IL}		2	1.9	_	_	1.9	-	1.9	_	V _{IL}									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-6	4.5	3.98	-	-	3.84	-	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v
Bus Driver	V _{IH}	-7.8	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	_	-	0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage V _{OL}	or	0.02	4.5	_	-	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	l v
CMOS Loads	V _{IH}		6	-	_	0.1	_	0.1	_	0.1	VIH									
	V _{IL}										V _{IL}									
TTL Loads	or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	_	0.33		0.4	v
Bus Driver	V _{IH}	7.8	6	-	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any									
Current I,	or		6	-	–	±0.1	_	±1	-	±1	Voltage Between	5.5	-	_	±0.1	_	±1	_	±1	μΑ
	Gnd										V _{cc} & Gnd									
Quiescent	V _{cc}		ļ								V _{cc}					-				
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	_	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd								L	
Additional Quiescent Device Current per input pin: 1 unit load											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	-	490	μΑ
3-State	V _{IL}	V ₀ = V _{CC}									V _{IL}									
leakage	or	or	6	_	_	±0.5	_	±5	-	±10	or	5.5	_	_	±0.5	-	±5	_	±10	μΑ
current	V _{IH}	Gnd						ļ			V _{1H}									

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
WE	0.3
WAO	0.2
WA1	0.4
RE	1.5
DATA	0.15
RAO	0.4
RA1	0.7

*Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t1 = 6 ns)

CHARACTERISTIC	CL	SYMBOL	TYP	ICAL	UNITS
CHARACTERISTIC	(pF)	STWIDOL	HC	нст	UNITS
Propagation Delay Reading any word	15	t _{PLH} t _{PHL}	16	17	ns
Write Enable to Output	15	t _{PLH} t _{PHL}	21	21	ns
Data to Output	15	t _{PLH} t _{PHL}	21	21	ns
Output Disable Time	15	t _{PLZ} t _{PHZ}	12	14	ns
Output Enable Time	15	t _{PZL} t _{PZH}	12	16	ns
Power Dissipation Capacitance*	_	C _{PD}	59	66	pF



PD = $C_{PD} V_{CC}^2 f_i + \Sigma C_L V_{CC}^2 f_o$ where f_i = input frequency,

fo = output frequency,

 C_L = output load capacitance

V_{cc} = supply voltage

PREREQUISITE FOR SWITCHING FUNCTION

			25° C		-4	0°C t	o +85°	C	-5						
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	СТ	741	НС	74F	ICT	54	НС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Set-up time		2	60	_	_	_	75	_	_	_	90		_	_	
Data to WE	t _{su}	4.5	12	_	14	<u> </u>	15	_	18	<u> </u>	18	—	21	-	ns
		6	10	—	—	_	13	_	— _		15	_	_	_	
Hold time		2	5	_		_	5	_	_	_	5		-	_	,
Data to WE	t _h	4.5	5	_	5	_	5	_	5	_	5	—	5	—	ns
		6	5	_	<u> </u>	_	5			_	5		_	_	l
Set-up time		2	60	_	_	_	75		_	_	90	_	_	_	
Write to WE	t _{su}	4.5	12	_	18	—	15	_	23	_	18	—	27	—	ns
		6	10	_		_	13	_			15	<u> </u>	_		
Hold time		2	5		_	_	5	_	_	_	5	_	_	-	
Write to WE	t _h	4.5	5	_	5	—	5	_	5	_	5	l —	5	—	ns
		6	5	_		_	5	_	_	_	5	_	_		
WE		2	80	_	_	_	100	_	_	_	120	_	-	_	
Pulsewidth	tw	4.5	16	-	20	 	20	l —	25	l —	24	-	30	_	ns
		6	14	-	-	-	17	—	-	-	20	-	-	-	
Latch time		2	100	_	_	_	125	_	_		150	_	_	_	
WE to RA0, RA1	tLATCH	4.5	20	-	25	-	25	-	31	-	30	-	38	-	ns
		6	17	_		_	21	_	_		26	_	_		



SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_l = 6 ns,)

				25	°C		-4	0°C to	ი +85°	С	-5				
CHARACTERISTIC	SYMBOL	Vcc	Н	HC HCT		74	HC	74H	ICT	54	HC	54F	ICT	UNITS	
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	I —	195	_	_	_	245	_	_	_	295	_	_	
Reading any word	t _{PHL}	4.5	-	39	_	40		49	—	50	l —	59	_	60	ns
		6	<u> </u>	33		_	_	42	_		_	50	_	_	
Write Enable	t _{PLH}	2	_	250	_	_	_	315	_	_	_	375	_	_	
to Output	t _{PHL}	4.5	—	50	—	50	_	63	l —	63	 	75		75	ns
	,	6		43		_	_	54				64	_	_	
Data to Output	t _{PLH}	2	T —	256	_	_	_	315	-	_	—	375	_	_	
	t _{PHL}	4.5	-	50	l —	50	_	63	_	63	—	75	_	75	ns
		6	<u> </u>	43			_	54				64	_		
Output Disable Time	t _{PLZ}	2	I -	150	_	-	_	190	—	_	-	225	_	-	
	t _{PHZ}	4.5	l —	30	_	35	<u> </u>	38		44	-	45	-	53	ns
		6	<u> </u>	26			_	33				38	<u> </u>	_	L
Output Enable Time	t _{PZL}	2	-	150	—	—	_	190	—		—	225	l —	_	
	t _{PZH}	4.5		30	_	38	 -	38	_	48	-	45	—	57	ns
		6		26		_		33				38	<u> </u>		
Output Transition	t _{TLH}	2	-	75	l —	—	_	95	_		—	110	_	-	
Time	t _{THL}	4.5	_	15		15	—	19	_	19	-	22	—	22	ns
		6	<u> </u>	13				10			<u></u>	19	<u> </u>	<u> </u>	
3-State Output Capacitance	Co		_	20	_	20	_	20	_	20		20	_	20	pF
Input Capacitance	Cı		-	10	_	10	_	10	_	10	_	10		10	pF

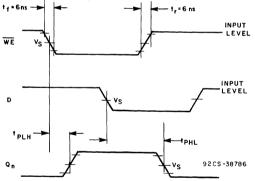


Fig. 2 — Propagation Delay, Write Enable and Data to Output

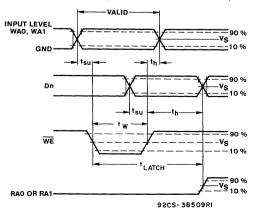


Fig. 4 — Setup and Hold Times, Write Address and Data to Write Enable

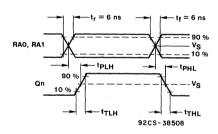


Fig. 3 — Propagation delay, Read Address to Output

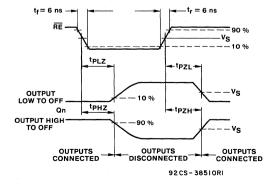


Fig. 5 - 3-State Enable and Disable Times

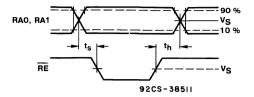
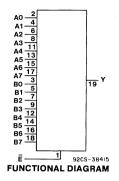


Fig. 6 — Setup and Hold times, Read Address to Read Enable

	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, Vs	50% V _{CC}	1.3 V

High-Speed CMOS Logic



8-Bit Magnitude Comparator

Type Features:

■ Cascadable

The RCA-CD54/74HC688 and CD54/74HCT688 are 8-bit magnitude comparators designed for use in computer and logic applications that require the comparison of two 8-bit binary words. When the compared words are equal the output (Y) is low and can be used as the enabling input for the next device in a cascaded application.

The CD54HC688 and CD54HCT688 are supplied in 20-lead ceramic dual-in-line packages (F suffix). The CD74HC688 and CD74HC7688 are supplied in 20-lead dual-in-line plastic packages (E suffix) and in 20-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

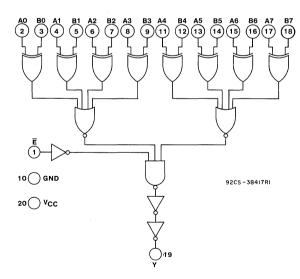


Fig. 1 - Logic diagram.

Family Features:

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}= 30%,N_{IH}=30% of V_{CC}; @ V_{CC}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility I_I≤ 1 µA @ V_{OL}, V_{OH}

TRUTH TABLE

Inpu	ts	Qutputs
A, B	E	Y
A = B	L	L
A≠B	L	Н
x	Н	Н

X = Don't care L = Low level H = High level

MAXIMUM RATINGS, Absolute-Maximum Values:

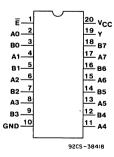
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	
DC DRAIN CURRENT, PER OUTPUT (I₀) (FOR -0.5 V < V₀ < V₀c +0.5 V)	
DC Vcc OR GROUND CURRENT, (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For $T_A = -40$ to $+70^{\circ}$ C (PACKAGE TYPE M)	400 mW
For $T_A = +70$ to $+125^{\circ}$ C (PACKAGE TYPE M)	. Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F. H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIF	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{CC} :*			
CD54/74HC Types	2	6	V .
CD54/74HCT Types	4.5	5.5	v
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°c
CD54 Types	-55	+125	
Input Rise and Fall Times, t _r ,t _f :			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

	-			CD	74HC	688/C	D54F	1C688	3				CD74	нст	388/C	D54H	CT68	88	-		
			TEST IDITIO	NS	ı	IC/54 TYPE		741 TY	HC PE	54I TY		TEST			CT/54		74HCT 54HCT TYPE TYPE				
CHARACTERISTI	CS	V,	l _o	Vcc		•25° C	;	-4 +85		-5 +12		V,	Vcc		+25° C	;	1 '	0/ 5° C		5°C	UNITS
		v	mA	v	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	VIH			4.5	3.15	ı	_	3.15	_	3.15	_	_	to	2	-	-	2	_	2	- !	v
				6	4.2		_	4.2	_	4.2	_		5.5	1						}	
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage	VIL			4.5	_	_	1.35	_	1.35	_	1.35	_	to	_	_	0.8	-	0.8	_	0.8	v
				6	_	_	1.8	_	1.8	_	1.8		5.5	1							
High-Level		VıL		2	1.9	_	_	1.9	_	1.9	_	VıL									
Output Voltage	VoH	or	-0.02	4.5	4.4	_	_	4.4	-	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads		ViH		6	5.9	_	_	5.9	_	5.9	_	ViH	-								
		VIL										VIL									-
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v
		ViH	-5.2	6	5.48	_	_	5.34		5.2		ViH								l	
Low-Level		VIL		2			0.1	_	0.1	_	0.1	VIL									
Output Voltage	Val	or	0.02	4.5		_	0.1	_	0.1	_	0.1	or	4.5	_	<u>ا _</u> '	0.1	_	0.1	_	0.1	v
CMOS Loads	- 02	VIH		6			0.1	_	0.1	_	0.1	ViH									-
		VIL		۰					-		<u> </u>	ViL				<u> </u>			-		
TTL Loads		or	4	4.5		_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v
		VIH	5.2	6			0.26		0.33	_	0.4	ViH	4.0			0.20		0.00			•
Input Leakage Current	lı	V _{cc} or Gnd	0.2	6	_	-	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_		±0.1	_	±1	_	±1	μΑ
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6			8		80	-	160	Vcc or Gnd	5.5	_	_	8	_	80	_	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	Δlcc*				-							V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
Enable	0.7
Data Inputs	0.35

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 360 μA max.@25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25° C, Input tr, tr = 6 ns)

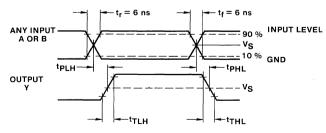
		_	TYPICAL		
CHARACTERISTIC	SYMBOL	C∟ pF	нс	нст	UNITS
Propagation Delay A and B Data to Output	t _{PLH}	15	14	14	
Propagation Delay Enable to Output	t _{PLH}	15	9	9	ns
Power Dissipation Capacitance*	СРД	_	22	22	pF

 $^{^{\}star}C_{PD}$ is used to determine the power consumption, per device. PD= V_{Cc}^2 fi (C_{PD} + C_L) where fi=input frequency C_L =output load capacitance

C_L=output load capacitance V_{cc}=supply voltage

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,t=6 ns)

				25	°C		-4	0°C to	o +85°	C	-5				
CHARACTERISTIC	SYMBOL	VCC	Н	С	H	CT	74	НС	74H	ICT	54	НС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	T -	170	—	_	-	210	T -	-	_	255	_	_	
An to Output	t _{PHL}	4.5	—	34	—	34	_	42	-	42	—	51	_	51	ns
		6	-	29	l —	—		36	—	-	_	43	_	<u> </u>	
	t _{PLH}	2	_	170	_	_	_	210	—	_	_	255	I —	_	
Bn to Output	t _{PHL}	4.5	—	34	—	34	l —	42	—	42	—	51	_	51	ns
		6	—	29	l —	—	-	36	—	—	—	43	_	—	
	t _{PLH}	2	 	120	_	_	_	150	_	_	_	180	_	_	
E to Output	t _{PHL}	4.5	 —	24	_	24	l —	30	—	30	—	36	_	36	ns
		6	j	20	—	— ·		26	—	—	_	30		_	
Output Transition	t _{TLH}	2	_	75	_	_	_	95	_	_	_	110	_	_	
Time	t _{THL}	4.5	_	15	l —	15	-	19	—	19	-	22	_	22	ns
		6	_	13	l —	<u> </u>	_	16	l —	—		19	_	_	
Input Capacitance	Сι		_	10	_	10	_	10	_	10	_	10	_	10	pF

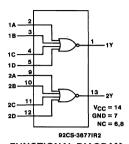


92CS-38416

	54/74HC	54/74HCT
Input Level	VCC	3 V
Switching Voltage, V _S	50% VCC	1.3 V

Fig. 2 - Propagation delay and transition times.

High-Speed CMOS Logic



Dual 4-Input NOR Gate

Type Features:

■ Typical CD54/74HC4002 Propagation Delay = 8ns @ V_{CC} = 5V, C_L = 15pF, T_A = 25° C

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC4002 and CD54/74HCT4002 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The CD54/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC/HCT4002 are supplied in 14-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT4002 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

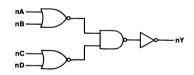


Fig. 1 - LOGIC DIAGRAM (One Gate) for HC4002.

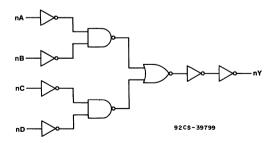


Fig. 2 - LOGIC DIAGRAM for HCT4002.

Family Features:

- Fanout (over temperature range): Standard Outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide Operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High noise immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL input logic compatibility V_{IL} = 0.8 V max., V_{IH} = 2 V Min. CMOS input compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}

TRUTH TABLE

	INPUTS									
nA	пB	nC	nD	nΥ						
L	L	Ĺ	L	Н						
н	x	х	x	L						
X	Н	×	х	L						
X	×	Н	Х	L						
X	×	Х	Н	L						

H = High Level

L = Low Level

X = Don't Care.

MAXIMUM RATINGS, Absolute-Maximum Values:

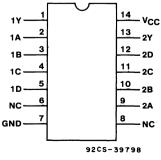
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR V_i < -0.5 V OR V_i > V_{CC} +0.5V)	
DC OUTPUT DIODE CURRENT, I_{OK} (FOR V_o < -0.5 V OR V_o > V_{CC} +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V _o $<$ V _{cc} + 0.5V)	±25mA
DC Vcc OR GROUND CURRENT (Icc)	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	UNITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	}
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.



TERMINAL ASSIGNMENT

STATIC ELECTRICAL CHARACTERISTICS

		CD74HC4002/CD54HC4002									CD74HCT4002/CD54HCT4002									
CHARACTERISTIC	со	TEST CONDITIONS			74HC/54HC 74HC TYPES TYPE		54HC TYPE		TEST CONDITIONS		74HCT/54HCT 74HCT TYPES TYPE					54HCT TYPE				
CHARACTERISTIC	V _i	I _o	V _{cc}		+25° C	;		0/ 5° C	-5 +12	5/ 5°C	V,	V _{cc}		+25° C	;	1	10/ 5° C		5/ 5°C	UNITS
		l IIIA		Min	Тур	Max	Min	Max	Min	Max		•	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	_	-:	2	-	2	-	V
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level			2		_	0.5		0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	L	_	1.35	_	1.35	_	1.35	-	to	-	-	0.8	-	0.8	-	0.8	V
			6	L	_	1.8	_	1.8	_	1.8		5.5								
High-Level	V _{IL}		2	1.9		_	1.9		1.9	_	V _{IL}									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	-	4.4		4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	v
CMOS Loads	V _{IH}	1	6	5.9		_	5.9	_	5.9		V _{IH}							·		
	V _{IL}										ViL									
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	L	_	0.1	_	0.1		0.1	V _{IL}									
Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}		<u> </u>							
	VIL		<u> </u>								V _{IL}									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6	L	_	0.26		0.33	_	0.4	V _{IH}			<u> </u>			<u> </u>			
Input Leakage	· V _{cc}										Any Voltage									
Current I,	or		6	-	-	±0.1	-	±1	-	±1	Between V _{cc}	5.5	-	-	±0.1	-	±1	-	±1	μΑ
	Gnd		<u> </u>	<u> </u>	<u> </u>						& Grid				ļ				_	
Quiescent	V _{cc}										Vcc									
Device	or	0	6	-	-	2	-	20	-	40	or	5.5	-	-	2	-	20	-	40	μA
Current I _{cr.}	Gnd			<u> </u>							Gnd	_				_	<u> </u>			
Additional Quiescent												4.5								
Device Current per input pin:											V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
1 unit load Δl_{cc}^*												5.5								

^{*}For dual-supply systems theoretical worst case (V_i = 2.4 V, $V_{\rm ca}$ = 5.5 V) specification is 1.8 mA.

HCT INPUT LOADING TABLE

INPUT	UNIT LOADS*					
All	0.45					

Unit Load is $\Delta I_{\rm CC}$ limit specified in Static Characteristic Chart, e.g., 360 μ A max. @25° C.

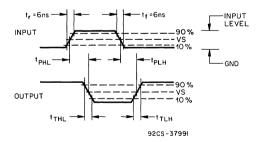
SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

OUADACTERISTIC		CL	TYP	CAL	UNITS	
CHARACTERISTIC		(pF)	HC	HCT	UNITS	
Propagation Delay Time:	t _{PLH}	15	8	9	200	
nA, nB, nC, nD to nY (Fig. 3)	t _{PHL}	15	8	12	ns	
Power Dissipation Capacitance*	C _{PD}	_	22	22	pF	

^{*} C_{PD} is used to determine the dynamic power consumption, per gate. $P_D = V_{CC}^{-2}f_i (C_{PD} + C_L) \text{ where: } f_i = \text{input frequency}$ $C_L = \text{output load capacitance}$ $V_{CC} = \text{supply voltage} .$

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_l = 6 ns)

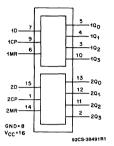
				25	°C		-40° C to +85° C				-55°C to +125°C				
CHARACTERISTIC		Vcc	HC		нст		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	100	_	_		125	_	_	_	150		_	
nA, nB, nC, nD		4.5		20	—	22	_	25	l —	28		30	_	33	!
to nY (Fig. 3)		6		17				21	_	_	L	26	l —	_	ĺ
		2	_	100	_		_	125	_	_	T —	150	_	_]
	t _{PHL}	4.5	-	20	_	29	-	25	—	36	_	30	-	44	ns
		6	_	17	_	l —	-	21	_	l —	l —	26	_	l —	
Transition Time	t _{TLH}	2		75			_	95	_	_	_	110		_	
(Fig. 3)	t_{THL}	4.5	l —	15	—	15	_	19		19	[_	22	_	22	
-		6	—	13	-	l —	_	16	_	l —		19		_	l
Input Capacitance	C ₁		_	10		10	_	10	_	10	_	10	_	10	рF



	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 3 - Transition times and propagation delay times.

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM

Dual 4-Stage Static Shift Register

Type Features:

- Maximum frequency, typically 60 MHz C_L = 15 pF, V_{CC} = 5 V, T_A = 25° C
- Positive-edge clocking
- Overriding reset
- Buffered inputs and outputs

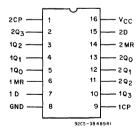
The RCA-CD54/74HC4015 and CD54/74HCT4015 consist of two identical, independent, 4-stage serial-input/paralleloutput registers. Each register has independent CLOCK (CP) and RESET (MR) inputs as well as a single serial DATA input. "Q" outputs are available from each of the four stages on both registers. All register stages are D-type, master-slave flip-flops. The logic level present at the DATA input is transferred into the first register stage and shifted over one stage at each positive-going clock transition. Resetting of all stages is accomplished by a high level on the reset line.

The device can drive up to 10 low power Schottky equivalent loads. The CD54/74HCT4015 is an enhanced version of equivalent CMOS types.

The CD54HC4015 and CD54HCT4015 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4015 and CD74HCT4015 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85°C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}=30%, N_{IH}=30% of V_{cc}; @ V_{cc}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility I₁≤1 µA @ Vo_L, V_{OH}



TERMINAL ASSIGNMENT

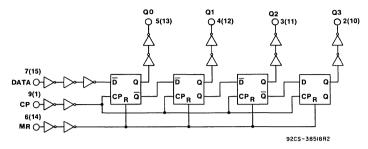


Fig. 1 - Logic diagram for one-half CD54/74HC/HCT4015.

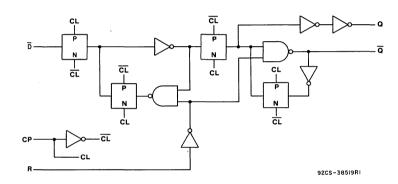


Fig. 2 - Flip-flop detail.

LOGIC TABLE

INPL	ITS		OUTPUTS							
СР	D	R	Qo	Q ₁	Q ₂	Q ₃				
	I	L	L	q′o	q′ı	q′2				
5	h	L	н	q′o	q′ı	q′2				
_	х	L	q′o	q′ı	q′2	q′3				
×	х	н	L	L	L	L				

- H = HIGH voltage level.
- h = HIGH voltage level one setup time prior to the LOWto-HIGH clock transition.
- L = LOW voltage level.
- I = LOW voltage level one setup time prior to the LOW-to-HIGH clock transition.
- q'n= Lower case letters indicate the state of the referenced output one set-up time prior to the LOW-to-HIGH clock transition.
- X = Don't Care.
- = LOW-to-HIGH clock transition.
- = HIGH-to-LOW clock transition.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V _{cc}):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, Iik (FOR Vi < -0.5 V OR Vi > Vcc +0.5 V)	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT, (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	·
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (T _{sto})	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LII	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	v
DC Input or Output Voltage, V _I , V _O	0	V _{cc}	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	⁰ °C
CD54 Types	-55	+125	
Input Rise and Fall Times, t _r ,t _f :			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

STATIC ELECTRICAL CHARACTERISTICS

				CD74	HC40)15/C	D54H	C401	5				CD74	нст4	015/C	D54H	ICT4	015			
CHARACTERISTI			TEST IDITIO	NS	ı	IC/54		741 TY		54i TY		TEST	ons	1	T/54		74H TY	ICT PE		ICT PE	1111170
CHARACTERIST	ics.	V,	lo	V cc		+25° C	;	-4 +85		-5: +12!		V,	Vcc		25°C	;		0/ 5°C		5/ 5°C	UNITS
		٧	mA	٧	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage	VIH		ļ	4.5	3.15	_	_	3.15	-	3.15	-	_	to	2	_	_	2	_	2	_	v
				6	4.2	_	_	4.2	_	4.2	1		5.5								
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage	VIL			4.5	_	_	1.35	-	1.35		1.35	_	to	_	_	0.8	_	0.8	_	0.8	v
				6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	_	-	1.9	_	1.9	_	ViL									
Output Voltage	Vон	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads		ViH		6	5.9	_	_	5.9	_	5.9	_	ViH					l				
		VIL										VIL									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	-	v
		ViH	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH									
Low-Level		VIL		2	_	_	0.1	_	0.1	_	0.1	VIL									
Output Voltage	VoL	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v
CMOS Loads		ViH		6	_	_	0.1	_	0.1		0.1	ViH									
		VIL										VIL									
TTL Loads		or	4	4.5	_	_	0.26		0.33	_	0.4	or	4.5	_	_	0.26	-	0.33	_	0.4	v
		VIH	5.2	6	_	_	0.26	_	0.33	_	0.4	ViH									
Input Leakage Current	l ₁	V _{cc} or Gnd		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1		±1	_	±1	μΑ
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6	-	_	8	-	80	-	160	V _{cc} or Gnd	5.5	_	_	8	_	80	_	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load	Δl _{cc} •											V _{CC} -2.1	4.5 to 5.5	_	100	360		450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
DATA	0.15
CP	0.45
MR	0.15

^{*}Unit load is Δ I_{CC} limit specified in Static Characteristics Chart, e.g., 360 μA max. @ 25° C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

		C,	Ty	pical	11-11-
CHARACTERISTIC	SYMBOL	pF	HC	HCT	Units
Propagation Delay CP to Qn	t _{PHL} t _{PLH}	15	14	14	ns
MR to Qn	t _{PHL}	15	25	25	
Maximum Clock Frequency	f _{MAX}	15	60	60	MHz
Power Dissipation Capacitance*	C _{PD} *	T-1	43	43	pF

 $^{^{\}star}C_{PD}$ is used to determine the dynamic power consumption, per shift register. $P_D=C_{PD}\ V_{Cc}^2$ fi + $\Sigma\ C_L\ V_{Cc}^2$ fo where: fi=input frequency, fo=output frequency C_L =load capacitance

V_{cc}=supply voltage

PREREQUISITE FOR SWITCHING FUNCTION

				25	°C		-4	0°C t	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	СТ	74	НС	74F	ICT	54	нС	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Clock		2	6	_		_	5	-	_	_	4	—	—	_	
Frequency	fmax	4.5	30	l —	30	l —	24	—	24	—	20	_	20	—	MHz
(See Fig. 3)		6	35	_	_	_	28	_	_	_	24	_	l —	—	
Clock Pulse		2	80	_	_	_	100	_	_	_	120	_	_	_	
Width	tw	4.5	16	—	16	_	20	—	20	_	24	_	24	_	
(See Fig. 3)		6	14		—	_	17	_	_	_	20		_	_	}
		2	150	_	_	_	190	_	_	—	225		_	—	Ì
MR Pulse Width	tw	4.5	30	_	30	 	38	—	38	-	45		45		
(See Fig. 4)		6	26	_	_	_	33	—		_	38	 -	_	—	
MR Recovery		2	50	_	_	_	65	_	_	_	75	—	_	_] .
Time	tREC	4.5	10	_	15	_	13	l —	19	—	15	-	22	—	ns
(See Fig. 4)		6	9	—	_	—	11	—	—	—	13	—	_	_	
Setup Time	tsüL	2	60	_	_	_	75	_	_	T	90	_	_	_]
Data-In to CP	tsuн	4.5	12	<u> </u>	16	-	15	_	20	l —	18	_	24	-	
(See Figs. 5 & 6)		6	10	-	 —	_	13	_	—	_	15	_	_	—	
Hold Time:		2	1							Ī					1
Data-In to CP	t _H	4.5	0		0	—	0	_	0	_	0	-	0	—	
(See Figs. 5 & 6)		6		1						İ					

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,,tf=6 ns)

	-			25	°C		-4	0°C to	o +85°	С	-55	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	VCC	Н	С	Н	CT	741	НС	74H	CT	54	НС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Propagation Delay		2	_	175	_	_	_	220	_	_	T	270	_	_	
Clock to Qn		4.5	—	35		35	_	44	_	44	_	54	 	54	
		6	l —	30	\ —	—	l —	37		_	_	46	l —	—	1
	t _{PLH}	2	_	275	_	_	_	345	_	_	_	415	_	_]
MR to Qn	t _{PHL}	4.5	—	55	l —	60	l —	64	_	75	—	83	_	90	
(Clock High)		6	—	47	—	_	_	54	—	 		71	—	—	1
		2	T —	325	_	_	_	400	_	_	_	490	_	_	1
MR to Qn		4.5	l —	65	_	65		81		81		98	l —	98	ns
(Clock Low)	1	6	l —	55	_	l —	_	69		l —	<u> </u>	83		—	
Output Transition	t _{TLH}	2	T —	75	_	T-	_	95	—	_	_	110	_	T —	1
Time	t _{THL}	4.5	_	15	—	15	_	19	l —	19	_	22	_	22	
		6	-	13	—	—	_	16	—	—	—	19	-	-	
Input Capacitance	Cı		T -	10	-	10	_	10	-	10	T-	10	_	10	pF

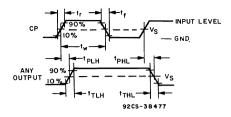


Fig. 3 - Clock-to-output delays and clock pulse width.

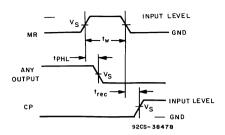


Fig. 4 - Master Reset pulse width. Master Reset to output delay and clock recovery times.

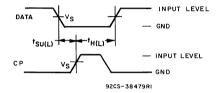


Fig. 5 - Data set-up and hold times.

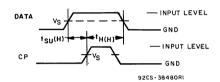
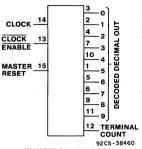


Fig. 6 - Data set-up and hold times.

	54/74HC	54/74HCT
Input Level	VCC	3 V
Switching Voltage, Vs	50% VCC	1.3 V

High-Speed CMOS Logic



Decade Counter/Divider with 10 Decoded Outputs

Type Features:

- Fully static operation
- Buffered inputs
- Common reset
- Positive edge clocking
- Typical $f_{MAX} = 50 \text{ MHz}$ @ $V_{CC} = 5 \text{ V}$, $C_L = 15 \text{ pF}$, $T_A = 25^{\circ} \text{ C}$

FUNCTIONAL DIAGRAM CD54/74HC4017, CD54/74HCT4017

The RCA-CD54/74HC4017 and CD54/74HCT4017 are high speed silicon gate CMOS 5-stage Johnson counters with 10 decoded outputs. Each of the decoded outputs is normally low and sequentially goes high on the low to high transition of the CLOCK (CP) input. Each output-stays high for one clock period of the 10 clock period cycle. The CARRY (TC) output transitions low to high after OUTPUT 10 goes low, and can be used in conjunction with the CLOCK ENABLE (CE) to cascade several stages. The CLOCK ENABLE input disables counting when in the high state. A RESET (MR) input is also provided which when taken high sets all the decoded outputs, except "0", low.

The device can drive up to 10 low power Schottky equivalent loads. The CD54/74HCT4017 is an enhanced version of equivalent CMOS types.

The CD54HC4017 and CD54HCT4017 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4017 and CD74HCT4017 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

TRUTH TABLE

СР	CE	MR	Output State*
L	Х	L	No Change
X	н	L	No Change
X	x	н	"O"=H, "1"-"9"=L
	L	L	Increments Counter
1 ~	x	L	No Change
x	<i>~</i>	L	No Change
н	~	L	Increments Counter

H = High Level

L = Low Level

Tansition = High-to-Low Transition

= Low-to-High Transition

X=Don't Care

*If n<5 TC=H, Otherwise=L

Family Features:

- Fanout (Over Temperature Range):
 Standard Outputs 10 LSTTL Loads
 Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation

High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ V_{CC} = 5V

■ CD54HCT/CD74HCT Types:

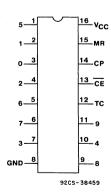
4.5 to 5.5 V Operation

Direct LSTTL Input Logic Compatibility

 $V_{\rm IL} = 0.8 \ V \ Max., \ V_{\rm IH} = 2 \ V \ Min.$

CMOS Input Compatibility

 $I_{\rm I} \leq 1~\mu{\rm A}$ @ $V_{\rm OL},~V_{\rm OH}$



TERMINAL ASSIGNMENT

MAXIMUM RATINGS, Absolute-Maximum Values:

· · · · · · · · · · · · · · · · · · ·	
DC SUPPLY-VOLTAGE (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{IK} (FOR $V_I < -0.5$ V OR $V_I > V_{CC} + 0.5$ V)	± 20 mA
DC OUTPUT DIODE CURRENT, I_{OK} (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V $<$ Vo $<$ Vcc +0.5 V)	± 25 mA
DC V _{CC} OR GROUND CURRENT, (I _{CC})	
POWER DISSIPATION PER PACKAGE (PD):	
For $T_A = -40$ to $+60$ °C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (T _{stq})	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C
· ,	

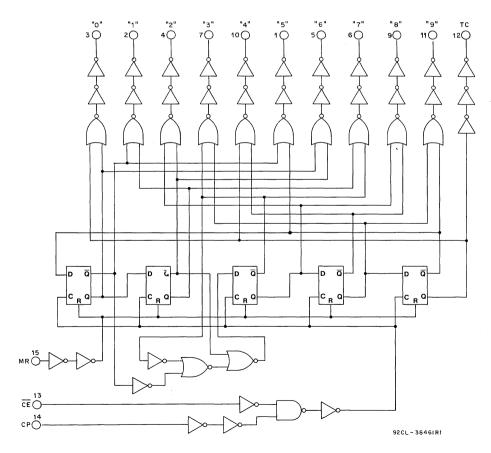


Fig. 1 — Logic diagram for the CD54/74HC/HCT 4017

STATIC ELECTRICAL CHARACTERISTICS

			CD7	4HC4	017/0	D54F	1C40	17 -				(CD741	нст4	017/C	D541	HCT4)17		
01404075010710	coi	TEST NDITION	s	1	IC/54			HC PES	ı	HC PES	TEST CONDITION		ı	CT/54			ICT PES	54F TYI		
CHARACTERISTIC	V,	lo	Vcc		+25°C	3	1	10/ 5°C		55/ 5°C	V 1	V _{cc}	-	+25°C	;	i	10/ 5°C	-5 +12	5/ 5°C	UNITS
	V	mA	٧	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_		1.5	E	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	L_		3.15	_	3.15		-	to.	2	-	_	2	-	2	_	V
			6	4.2	_	_	4.2	<u> </u> _	4.2			5.5								
Low-Level			2	_	_	0.5	_	0.5		0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35		to	-	_	0.8		0.8	-	0.8	٧
			6	_	_	1.8	_	1.8		1.8		5.5								
High-Level	, V _{IL}		2	1.9	_	_	1.9	_	1.9		VIL									
Output Voltage V _{OH}	. or	-0.02	4.5	4.4		_	4.4	_	4.4		or.	4.5	4.4	-	-	4.4	-	4.4		v
CMOS Loads	V _{IH}		6	5.9	_		5.9	_	5.9	_	V _{IH}									
	VIL										VIL					l				
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	-	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48		_	5.34	_	5.2	_	V _{IH}						<u> </u>			
Low-Level	VIL		2	_		0.1	_	0.1		0.1	VIL									!
Output-Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	<u>_</u>	0.1	VIH									
	VIL										VIL			ļ						
TTL Loads	or	4	4.5	_	_	0.26	_	0.33		0.4	or	4.5	-	-	0.26	— <u>.</u>	0.33	_	0.4	· v
	V _{IH}	5.2	6	_		0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage Current	V _{cc}		6	_	_	±0.1	_	±1	_	±1	Any Voltage Between	5.5	_	_	±0.1	_	±1	_	±1	μA
	Gnd										V _{cc} & Gnd						-		-	
Quiescent	Vcc										Vcc		T				T			
Device	or	0	6	_	_	8	_	80	_	160	or	5.5	_		8	_	80	_	160	μΑ
Current Icc	Gnd				l						Gnd				1					
Additional Quiescent Device Current per input pin: 1 unit load					,						V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V_v V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

	
Input	Unit Loads*
СР	0.15
CE	0.25
MR	0.3

^{*}Unit load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25°C.

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIM		
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t, tr			
at 2V	0	1000	ns
at 4.5 V	0	500	ns
at 6V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}$, $T_A = 25^{\circ}\text{C}$, Input t_h $t_f = 6 \text{ ns}$)

		C _L	Typical		
CHARACTERISTIC	SYMBOL	(pF)	нс	нст	UNITS
Propagation Delay CP to Out	t _{PLH}	15	19	19	ns
CP to TC	t _{PLH} t _{PHL}	1 15 1		19	ns
CE to Out	t _{PLH} t _{PHL}	15	21	21	ns
CE to TC	t _{PLH} t _{PHL}	15	21	21	ns
MR to Out	t _{PLH} t _{PHL}	15	19	19	ns
MR to TC	t _{PLH} t _{PHL}	15	19	19	ns
Max. CP Frequency	f _{MAX}	15	60	50	MHz
Power Dissipation Capacitance*	СРД	_	39	39	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package. $P_D = C_{PD} \; V_{CC^2} \; f_i + \Sigma \; C_L \; V_{CC^2} \; f_o \; where \; \; f_i = input \; frequency.$

 $f_o = output frequency.$

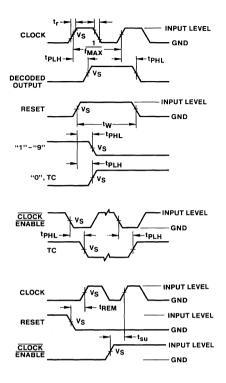
 C_L = output load capacitance. V_{cc} = supply voltage.

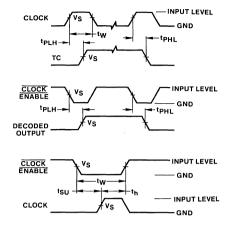
PREREQUISITE FOR SWITCHING FUNCTION

				LIMITS											
CHARACTERISTIC		TEST		25	°C		-4	10°C to	+ 85 °	C	-5]			
OHAHAOTEH	3110	CONDITION	Н	С	Н	СТ	74	НС	74F	ICT	54	HC _	54H	ICT	UNITS
		V _{cc} v	Min.	Мах.	Min.	Мах.	Min.	Мах.	Min.	Мах.	Min.	Мах.	Min.	Max.	
CP Pulse Width	t _w	2 4.5 6	80 16 14	=	_ 16 _	_	100 20 17		_ 20 _		120 24 20		_ 24 _	_	ns
MR Pulse Width	tw	2 4.5 6	80 16 14	=	16 —	_	100 20 17		20 —		120 24 20	_ 	 24 	=	ns
Max. Clock Freq. 1	f _{cL} (max.)	2 4.5 6	6 30 35	=	_ 25 _	=	5 35 49	=	_ 20 _	_	4 20 23	=	17 —	=	MHz
CE to CP Setup Time	tsu	2 4.5 6	75 15 13		15 —	=	95 19 16		19 —	_	110 22 19	=	 22 	=	ns
CE to CP Hold Time	t _H	2 4.5 6	0 0 0	_	_ 0 _		0 0 0	_	_ 0 _	_ 	0 0 0	_	0	_	ns
MR Removal Time	t _{REM}	2 4.5 6	5 5 5		_ 5 _	_	5 5 5	_	_ 5 _		5 5 5	_ 	_ 5 _	=	ns

SWITCHING CHARACTERISTICS ($C_L = 50 \text{ pF}$, Input t_r , $t_f = 6 \text{ ns}$)

				25	°C		-4	10°C to	+85°	Č	-5				
CHARACTERISTIC	SYMBOL	Vcc	Н	C	H	CT	741	НС	74F	ICT	54	НС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Мах.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	230	_	—		290	—	—	_	345	_	_	
CP to any Dec. Out	t _{PHL}	4.5 6	<u>-</u>	46 39	_ _	46 —	_	58 49	-	58 —	_	69 59	-	69 —	ns
CP to TC	t _{PLH} t _{PHL}	2 4.5 6	_	230 46 39	_	 46 	_	290 58 49	_ _ _	_ 58 _	_ 	345 69 59	_	- 69 -	ns
CE to any Dec. Out	t _{PLH} t _{PHL}	2 4.5 6	_	250 50 43	_ _ _	_ 50 _	_	315 63 54	_	- 63 -	_	375 75 64	_	_ 75 _	ns
CE to TC	t _{PLH} t _{PHL}	2 4.5 6	_	250 50 43	_	_ 50 _	_	315 63 54	_	63 —	 - -	375 75 64	_	_ 75 _	ns
MR to any Dec. Out	t _{PLH} t _{PHL}	2 4.5 6		230 46 39	_	 46 	_	290 58 49		 58 	_	345 69 59	_	- 69 -	ns
MR to TC	t _{PLH} t _{PHL}	2 4.5 6		230 46 39	_	- 46 -	_	290 58 49	_	 58 	_	345 69 59	_ 	- 69 -	ns
Transition Time TC, Dec. Out	t _{THL} t _{TLH}	2 4.5 6		75 15 13	_	 15 	_ _ _	95 19 16	_	19 —	_ _ _	110 22 19		_ 22 _	ns
Input Capacitance	C _{IN}		_	10		10	_	10		10	_	10		10	pF

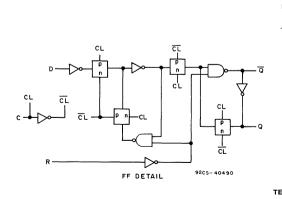


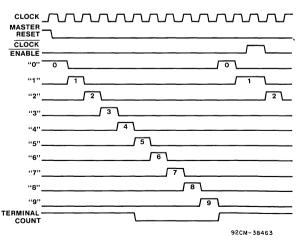


92CL-38462RI

	CD54/74HC	CD54/74HCT
Input Level	Vcc	3 V
Vs	0.5 V _{cc}	1.3 V

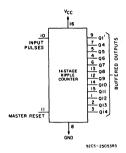
Transition times and propagation delay times.





Timing diagram for the CD54/74HC/HCT4017

High-Speed CMOS Logic



14-Stage Binary Counter

Type Features:

- Fully static operation
- **Buffered** inputs
- Common reset
- Negative edge pulsing
- Typical f_{MAX} = 50 MHz @ V_{CC} = 5 V, C_L = 15, T_A = 25° C

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC4020 and CD54/74HCT4020 are 14stage ripple-carry binary counters. All counter stages are master-slave flip-flops. The state of the stage advances one count on the negative transition of each input pulse; a high voltage level on the MR line resets all counters to their zero state. All inputs and outputs are buffered.

The CD54HC4020 and CD54HCT4020 are supplied in 16lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4020 and CD74HCT4020 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dualin-line surface mount plastic package (M suffix). Both types are also available in chip form (H suffix).

TRUTH TABLE

φ	MR Output State								
1	L	No Change							
~	L	Advance to next state							
х	н	All Outputs are low							

H = high level (steady state)

L = low level (steady state)

X = don't care

Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:

2 to 6 V Operation

High Noise Immunity: N_{IL}=30%, N_{IH}=30% of V_{CC}; @ Vcc=5 V

■ CD54HCT/CD74HCT Types:

4.5 to 5.5 V Operation

Direct LSTTL Input Logic Compatibility VIL=0.8 V Max., VIH=2 V Min.

CMOS Input Compatibility

1, ≤ 1 μA @ VOL, VOH

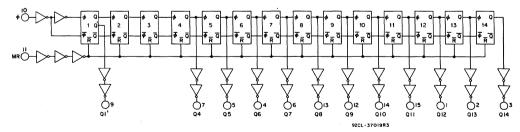


Fig. 1 - Logic block diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground)
DC INPUT DIODE CURRENT, I _{IK} (FOR V, $<$ -0.5 V OR V, $>$ V _{CC} +0.5V)
DC OUTPUT DIODE CURRENT, l_{OK} (FOR $V_o < -0.5$ V OR $V_o > V_{CC}$ +0.5V)
DC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V < V _o < V _{cc} + 0.5V) \dots ±25mA
DC V _{cc} OR GROUND CURRENT (I _{cc})
POWER DISSIPATION PER PACKAGE (PD):
For T _A = -40 to +60°C (PACKAGE TYPE E)
For T _A = +60 to +85° C (PACKAGE TYPE E)
For T _A = -55 to +100°C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For T _A = -40 to +70° C (PACKAGE TYPE M)
For T _A = +70 to 125° C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A):
PACKAGE TYPE F, H55 to +125° C
PACKAGE TYPE E, M40 to +85° C
STORAGE TEMPERATURE (T _{s10})65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. +265° C +265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only +300°C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIF	UNITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
Vcc:*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _{in} , V _{out}	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r ,t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

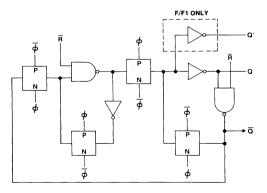


Fig. 2 - Detail for flip-flops 1, 2, 3, 5, 6, 8,10, 11, 13 & 14.

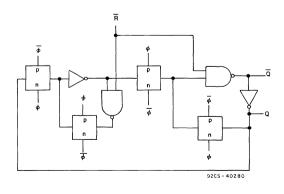


Fig. 3 - Detail for flip-flops 4, 7, 9 & 12.

STATIC ELECTRICAL CHARACTERISTICS

		CE)74H	C4020	CD5	HC40)20					CD7	4HC1	4020	/CD54	нст	4020			
CHARACTERISTIC	ı	TEST NDITIONS			IC/54		741 TYI	HC PES	54I TYF		TEST CONDITION		1	CT/54 TYPES			ICT PES	54H TYI	ICT PES	UNITS
CHARACTERISTIC	V,	I _o	V _{cc}		+25° C	;	-4 +85	0/ 6°C	-5 +12	5/ 5°C	V,	V _{cc}		+25° C	:	1 '	0/ 5°C		5/ 5° C	UNITS
		l ma	*	Min	Тур	Max	Min	Max	Min	Max	' '	٧	Min	Тур	Max	Min	Max	Min ·	Max	÷.
High-Level			2	1.5	_	_	1.5	-	1.5	-		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	l –	to	2	_	_	2	_	2	-	v
			6	4.2	-	_	4.2	_	4.2	_]	5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	-	_	1.35	-	1.35	_	1.35] –	to	_	—	0.8	_	0.8	_	0.8	v
			6	_	_	1.8	-	1.8	-	1.8		5.5.	-							
High-Level	VIL		2	1.9		_	1.9	_	1.9	_	VIL									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	-	_	4.4	_	4.4	_	or	4.5	4.4	–	-	4.4	_	4.4	_	. V
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9		V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-4	4.5	3.98	-	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	-	3.7		v
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	_		0.1	_	0.1	_	0.1	V _{IL}									
Output Voltage V_{OL}	or	0.02	4.5	_	_	0.1	_	0.1		0.1	or	4.5	-	-	0.1	_	0.1	_	0.1	v
CMOS Loads	V _{IH}		6	-	_	0.1	— ,	0.1	_	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	4	4.5			0.26	_	0.33		0.4	or	4.5		–	0.26	-	0.33	-	0.4	v
	V _{IH}	5.2	6	_	_	0.26	_	0.33		0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I,	or		6	_	-	±0.1	_	±1	-	±1	Between V _{cc}	5.5	-	–	±0.1	-	±1		±1	μΑ
	Gnd										& Gnd									
Quiescent	V _{cc}										Vcc									
Device	or	0	6	-	-	8	-	80		160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load Δ lcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

-HCT Input Loading Table

Input	Unit Loads*
MR	0.65
Ø	0.5

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μ A max. @ 25° C.

Q12 1	$\overline{}$	16 VCC
Q13 2		15 Q11
Q14 3		14 Q10
Q6 4		13 Q8
Q5 _5		12 Q9
Q7 <u>6</u>		11 MR
Q4		10 ¢
GND 8		9 Q1'

SWITCHING CHARACTERISTICS ($V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, \text{ Input } t_r, t_i = 6 \text{ ns}$)

CHARACTERISTIC	0,445,01	C,	Туј	oical	l leite
CHARACTERISTIC	SYMBOL	pF	HC	нст	Units
Propagation Delay φ to Q1' Output	t _{PLH} t _{PHL}	15	11	17	ns
Propagation Delay Q _n to Q _n .	t _{PLH} t _{PHL}	15	6	6	ns
Propagation Delay MR to Q _n	t _{PHL}	15	14	17	MHz
Power Dissipation Capacitance*	C _{PD}	-	30	30	pF

*C_{PD} is used to determine the power consumption, per package.

PD = $C_{PD} Vcc^2 fi + \Sigma (C_L Vcc^2 fi/M)$ where: $M = 2^1, 2^4, 2^5 \dots 2^{14}$

C_L = output load capacitance

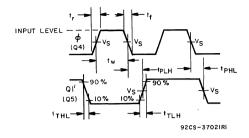
fi = input frequency

Pre-requisite for Switching Function

				25	°C		-4	0°C t	+85°	,C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	HC		HCT		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Input Pulse		2	6	_	_	-	5	—	_	_	4	_	_	_	
Frequency	f _{MAX}	4.5	30	 	25	-	25	—	20	-	20		16	—	MHz
		6	35	-	_	_	29	_	—	—	24	—	l —	—	
Input Pulse Width	tw	2	80	_	_	_	100		_	_	120	_	_		
(Figure 4)		4.5	16		20	_	20	-	25	—	24		30	-	ns
		6	14		 -	 	17	_	—	_	20	-	—	—	
Reset Removal Time	t _{REM}	2	50	_		_	65	_	_	_	75	_	_	-	
(Figure 5)		4.5	10		10	_	13	_	13	—	15	—	15		ns
		6	9		—	_	11	—	_	 	13	_		—	
Reset Pulse Width	tw	2	80	_	_	_	100	_			120	_	_	—	
(Figure 5)		4.5	16	_	20	_	20	-	25		24	—	30	-	ns
		6	14	l —	l –	l –_	17		—	<u> </u>	20	_	_	<u> </u>	

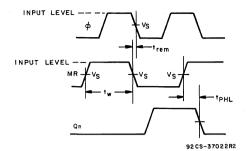
SWITCHING CHARACTERISTICS (CL=50 pF, input t,t;=6 ns)

				25	°C		-4	0°C to	+85°	C	-5				
CHARACTERISTIC	SYMBOL	Vcc	Н	С	HCT		74	нС	74HCT		54HC		54HCT		UNITS
	1		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2		140		_	_	175	_	_	_	210	_	_	
φ to Q1' Output	tpHL	4.5	—	28	l —	40	_	35	 —	50	_	42	—	60	ns
(Figure 4)	Ì	6	-	24		—	_	30		_		36	 —		Ì
Propagation Delay	t _{PLH}	2	_	75	_	_		95	_	_	_	110	_	_	
Q _n to Qn+1	t _{PHL}	4.5	—	15		15	—	19	—	19		22		22	ns
(Figure 4)		6	—	13		_	_	16		 	—	19	-	-	1
Propagation Delay	t _{PHL}	2		170	_	_	_	215	_	_	_	255	_		
MR to Q _n	}	4.5	-	34	—	40	_	43	_	50	-	51	—	60	ns
(Figure 5)	l	6	_	29	_	 	 	37	 	 	_	43	—	—	
Output Transition	tTLH	2	_	75	_	_	_	95	—	_	_	110	_		
Time	t _{THL}	4.5	_	15	 —	15	_	19	l —	19	 	22	-	22	ns
(Figure 4)		6	_	13	—	_	—	16	-	—		19	—	—	
Input Capacitance	Cı		_	10	_	10	_	10	_	10	_	10	_	10	pF



	54/74 HC	54/74 HCT
INPUT LEVEL	V _{cc}	3V
V _S	50%	1.3V

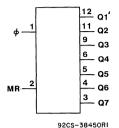
Fig. 4 - Input pulse pre-requisite times, propagation delays and output transition times.



1	54/74 HC	54/74 HCT
INPUT LEVEL	V _{cc}	3V
V _s	50%	1.3V

Fig. 5 - Master Reset pre-requisite and propagation delays.

High-Speed CMOS Logic



7-Stage Binary Ripple Counter

Type Features:

- Fully static operation:
- Buffered inputs:
- Common reset
- Typical f_{MAX} = 50 MHz @ $V_{CC} = 5 V$, $C_L = 15 pF$, $T_A = 25°C$

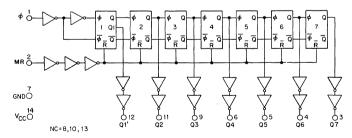
92CS-38450RI CD54/74HC4024, HCT4024 FUNCTIONAL DIAGRAM

The RCA-CD54/74HC4024 and CD54/75HCT4024 are 7-stage ripple-carry binary counters. All counter stages are master-slave flip-flops. The state of the stage advances one count on the negative transition of each input pulse; a high voltage level on the MR line resets all counters to their zero state. All inputs and outputs are buffered.

The CD54HC4024 and CD54HCT4024 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4024 and CD74HCT4024 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Family Features:

- Fanout (over temperature range):
 Standard outputs 10 LSTTL loads
 Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}= 30%, N_{IH}=30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility I_I ≤ 1 µA @Vo_L, Vo_H



92CM-3845IR3

TRUTH TABLE

φ	MR	OUTPUT STATE
	٦	No Change
/	L	Advance to Next State
Χ	Н	All Outputs are Low

H = high level (steady state)

L = low level (steady state)

X = don't care

Fig. 1 - Logic diagram for the CD54/74HC/HCT4024.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, I_{iK} (FOR $V_i < -0.5$ V OR $V_i > V_{cc} + 0.5$ V)	
DC OUTPUT DIODE CURRENT, IOK (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT, (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70° C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	Totale Emounty at 6 mm. 6 to 10 mm.
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	
STORAGE TEMPERATURE (Tatg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIA	MITS	LIMITE
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
Vcc:*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage, V _I , V _O	0	V _{cc}	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r ,t _f :			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

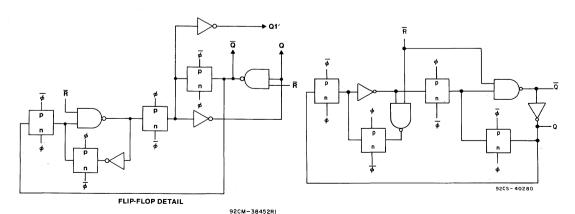


Fig. 2 - Flip-flop No. 1 detail.

Fig. 3 - Detail for flip-flops 2 through 7.

STATIC ELECTRICAL CHARACTERISTICS

				CD74	HC40	024/C	D54H	C402	4				CD74	нст4	024/0	:D54H	ICT4	024				
		l	TEST IDITIOI	NS	l	IC/54 TYPE		741 TY		54H TY		TEST	ons		TYPE			ICT PE		ICT PE	UNITS	
CHARACTERISTI	CS	V,	lo	Vcc	,	+25° C	;	-41 +85		-5: +12!		٧ı	Vcc		+25° C	;		0/ 5°C	_	5/ 5°C	/	
		٧	mA	٧	Min	Тур	Max	Min	Max	Min	Max	٧	V	Min	Тур	Max	Min	Max	Min	Max		
High-Level				2	1.5	_	_	1.5		1.5			4.5									
Input Voltage	VIH			4.5	3.15	_		3.15	1	3.15	_	_	to	2	-	_	2	-	2		v	
				6	4.2	_	<u> </u>	4.2	_	4.2	_		5.5	Ĺ_								
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5									
Input Voltage	VıL			4.5	_	_	1.35	_	1.35	_	1.35	_	to	Í –	_	0.8	_	0.8	-	0.8	v	
				6		_	1.8	_	1.8	_	1.8		5.5	ĺ	ĺ							
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VıL										
Output Voltage	Vон	or	-0.02	4.5	4.4		_	4.4		4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v	
CMOS Loads		ViH		6	5.9	_	_	5.9	_	5.9	_	ViH					ļ					
		VıL										VIL										
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v	
		ViH	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH				ļ						
Low-Level		VIL		2	_	_	0.1	_	0.1	_	0.1	VIL										
Output Voltage	Vol	or	0.02	4.5	_		0.1	_	0.1		0.1	or	4.5	_		0.1	_	0.1	_	0.1	v	
CMOS Loads		VIH		6	_	_	0.1	_	0.1	_	0.1	ViH		ł	1						"	
		VIL			-							VIL		T -								
TTL Loads		or	4	4.5	_	_	0.26	_	0.33		0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v	
		V _{IH}	5.2	6	_		0.26	_	0.33	_	0.4	ViH			ł							
Input Leakage Current	lı	V _{cc} or Gnd		6	-	_	±0.1		±1		±1	Any Voltage Between V _{cc} and Gnd	5.5	_	_	±0.1	_	±1	_	±1	μΑ	
Quiescent Device												.,										
Current	Icc	V _{cc} or	0	6			8		80		160	V _{cc} or	5.5									
		Gnd			_	_	*	_	80	_	160	or Gnd	5.5	-	_	8	_	80	-	160	μΑ	
Additional Quiescent Device Current per Input Pin: 1 Unit Load	ΔΙςς*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ	

^{*}For dual-supply system" theoretical worst case (V_1 = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
ϕ , MR	0.5

*Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 360 μA max.@25° C.

φ <u>1</u>		14 VCC
MR -2		13 NC
Q7 <u>3</u>		12 Q1'
Q6 -4		11 Q2
Q5 — 5		10 NC
Q4 <u>6</u>		9_Q3
GND -7		8_NC
	TOP VIEW	l

TERMINAL ASSIGNMENT

92CS-38453RI

SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25°C, Input t_r,t_f=6 ns)

			TYPICAL	. VALUES		
CHARACTERISTIC	SYMBOL	C∟ (pF)	НС	HCT	UNITS	
Propagation Delay	t _{PHL}	15	11	17		
ϕ to Q1'	t _{PLH}					
	t _{PHL}	15	6	6	ns	
Qn to Qn+1	tplH					
	t _{PHL}	15	14	17		
MR to Q _n	t _{PLH}					
Power Dissipation Capacitance*	CPD	_	30	30	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 fi + \sum (C_L V_{CC}^2 fi/M)$ where:

 $M=2^{1},2^{2},2^{3},2^{4},2^{5},2^{6},2^{7}$

C_L=output load capacitance

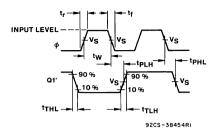
fi=input frequency

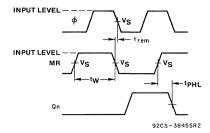
Prerequisite for Switching Function

	SYMBOL			25	°C		-4	0°C to	o +85°	,C	-5				
CHARACTERISTIC		Vcc	C HC		C HC		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Maximum Input		2	6	-	_	_	5	_	_	_	4		i —	<u> </u>	
Pulse Frequency	f _{MAX}	4.5	30	_	25	_	24	—	20	_	20	—	16		MHz
		6	35	_	—		29	_	-	—	24	—	_	_	
Input Pulse Width	tw	2	80	_	_	_	100	—	_	_	120	_	_		
		4.5	16	 	20	_	20	_	25	_	24	—	30	-	
		6	14	_	_	_	17	_	-	_	20	l —	l —	_	
Reset Removal Time	t _{REM}	2	50	_	_	_	65	T ==		_	75	T-	_	_	1
		4.5	10	—	10	_	13	—	13	_	15	_	15	-	ns
		6	9	_	_	_	11	_	_	_	13	_	-	-	
Reset Pulse Width	tw	2	80	_	_	_	100	_	_	_	120		_	_	1
		4.5	16	-	20	—	20	_	25	_	24		30		
		6	14	_	_	_	17	_	_	_	20	_	-	_	

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,t,=6 ns)

				25	°C		-4	0°C t	o +85°	°C	-5				
CHARACTERISTIC	SYMBOL	Vcc	H	С	Н	CT	74	НС	74H	ICT	54	НС	54F	ICT	UNITS
		İ	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Propagation Delay,	t _{PLH}	2	T-	140	_	_	_	175	=	_	_	210	_	_	
ϕ to Q1 $^{\prime}$ Output	t _{PHL}	4.5	_	28	_	40	-	35	_	50	l —	42	_	60	ns
		6	-	24	_	_	_	30	 —	-	—	36	_	_	İ
Propagation Delay	t _{PLH}	2		75	_	_	_	95	_	_	_	110	_	Ι=	
Qn to Qn+1	t _{PHL}	4.5	-	15	_	15	—	19	l —	19	_	22	_	22	ns
		6		13	_	-	—	13	_		_	19	_	-	
Propagation Delay	t _{PHL}	2		170		T —	_	215	_	_	_	255	_	_	
MR to Q _n		4.5	_	34	_	40		43	_	50	_	51	_	60	ns
		6	-	29	_	—	—	27	l —	_	_	43	_	_	
Output Transition	t _{TLH}	2		75	_	_	_	95	_	_	_	110	_	=	
Time	t _{THL}	4.5	_	15	_	15	_	19	_	19	_	22	_	22	ns
		6	_	13	_	_	_	16	<u> </u>] —	_	19	—	_	
Input Capacitance	Cı		_	10	_	10	_	10	<u> </u>	10	_	10		10	pF



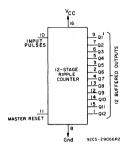


	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 4 - Input Pulse pre-requisite times, propagation delays and output transition times.

Fig. 5 - Master Reset pre-requisite and propagation delays.

High-Speed CMOS Logic



12-Stage Binary Counter

Type Features:

- Fully static operation
- Buffered inputs
- Common reset
- Negative edge pulsing
- Typical f_{MAX} = 50 MHz @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C

FUNCTIONAL DIAGRAM

The RCA-CD54/74HC4040 and CD54/74HCT4040 are 12-stage ripple-carry binary counters. All counter stages are master-slave flip-flops. The state of the stage advances one count on the negative transition of each input pulse; a high voltage level on the MR line resets all stages to their zero state. All inputs and outputs are buffered.

The CD54HC4040 and CD54HCT4040 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4040 and CD74HCT4040 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic package (M suffix). Both types are also available in chip form (H suffix).

TRUTH TABLE

φ	MR	Output State
-	L	No Change
~	L	Advance to next state
Х	н	All Outputs are low

H = high level (steady state)

L = low level (steady state)

X = don't care

Family Features:

- Fanout (Over Temperature Range):
 Standard Outputs 10 LSTTL Loads
 Bus Driver Outputs 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL}= 30%, N_{IH}=30% of V_{CC} @ V_{CC}=5 V
- CD54HCT/CD74HCT Types:

 4.5 to 5.5 V Operation

 Direct LSTTL Input Logic Compatibility

 V_{IL}=0.8 V Max., V_{IH}=2 V Min.

 CMOS Input Compatibility

 I_I ≤ 1 µA @ V_{OL}, V_{OH}

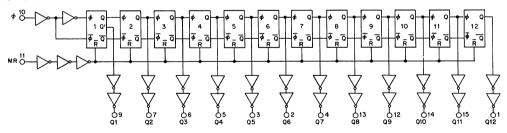


Fig. 1 - Logic block diagram.

92CL-37015R3

MAXIMUM RATINGS, Absolute-Maximum Values:

C SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground) -0.5 to + 7	٧
IC INPUT DIODE CURRENT, I_{IK} (FOR $V_{\text{I}} <$ -0.5 V OR $V_{\text{I}} > V_{\text{CC}}$ +0.5V)	۱A
C OUTPUT DIODE CURRENT, I_{OK} (FOR V_{o} < -0.5 V OR V_{o} > V_{CC} +0.5V)	۱A
IC DRAIN CURRENT, PER OUTPUT (I _o) (FOR -0.5 V $<$ V $_{o}$ $<$ V $_{cc}$ + 0.5V)	
C V _{CC} OR GROUND CURRENT (I _{CC})	۱A
OWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	W
For T _A = +60 to +85°C (PACKAGE TYPE E)	W
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	W
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	W
For T _A = -40 to +70°C (PACKAGE TYPE M)	٦W
For T _A = +70 to +125°C (PACKAGE TYPE M)	٦W
PERATING-TEMPERATURE RANGE (T _A):	
PACKAGE TYPE F, H	,C
PACKAGE TYPE E, M	,C
TORAGE TEMPERATURE (T _{stg})65 to +150°	,C
EAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. +265°	,C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only +300° +300°	,C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	LIMITS					
CHARACTERISTIC	MIN.	MAX.	UNITS				
Supply-Voltage Range (For T _A =Full Package Temperature Range)							
V _{cc} :*							
CD54/74HC Types	2	6	V				
CD54/74HCT Types	4.5	5.5	V				
DC Input or Output Voltage Vin, Vout	0	V _{cc}	V				
Operating Temperature T _A :							
CD74 Types	-40	+85	°C				
CD54 Types	-55	+125	°C				
Input Rise and Fall Times t _r ,t _f							
at 2 V	0	1000	ns				
at 4.5 V	0	500	ns				
at 6 V	0	400	ns				

^{*}Unless otherwise specified, all voltages are referenced to Ground.

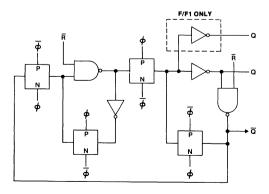


Fig. 2 - Detail for flip-flops 1, 2, 4, 5, 7, 8, 10 & 11.

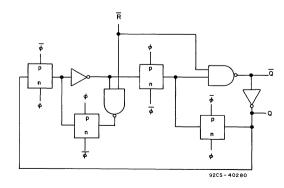


Fig. 3 - Detail for flip-flops 3, 6, 9 & 12.

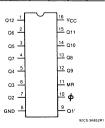
STATIC ELECTRICAL CHARACTERISTICS

		CI	D74H0	C4040	/CD5	4HC40	040					CD	4HC1	4040	/CD54	4НСТ	4040			
CHARACTERISTIC		TEST NDITIONS		ŀ	HC/54		74 TYI	HC PES	541 TYI		TEST		1	CT/54			ICT PES		ICT PES	UNITS
CHARACTERISTIC	V, V	I _o	V _{cc}		+25° C	;		0/ 5° C	-5 +12	5/ 5° C	V,	V _{cc}	+25° C		!5° C		10/ 5°Ç	-55/ +125°C		UNITS
	•	""	ľ	Min	Тур	Max	Min	Max	Min	Max	,	ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	-	2	-	2	-	v
			6	4.2	_	_	4.2		4.2	_		5.5							<u></u>	
Low-Level			2	_	_	0.5		0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	-	to	· —	-	0.8	-	0.8	-	0.8	v
			6	_	_	1.8	_	1.8	_	1.8		5.5								
High-Level	VIL		2	1.9	_	_	1.9	_	1.9		VIL									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4		4.4	_	or	4.5	4.4	-	-	4.4	_	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
	VIL										VIL						-			
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	-	3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}				ļ				ļ	
Low-Level	VIL		2	_	-	0.1	_	0.1	_	0.1	VIL									
Output Voltage Vo.	or	0.02	4.5	_	-	0.1	_	0.1	-	0.1	or	4.5	-		0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	-	_	0.1	_	0.1	_	0.1	V _{IH}				ļ				ļ	
	VIL				ļ						VIL									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	,V
	V _{IH}	5.2	6	_	_	0.26	_	0.33	-	0.4	V _{IH}						ļ		ļ	
Input Leakage	V _{cc}										Any Voltage									
Current I,	or		6	-	_	±0.1	_	±1	_	±1	Between V _{cc}	5.5	_	_	±0.1	_	±1	-	±1	μΑ
	Gnd		_								& Gnd	ļ			ļ		ļ		-	
Quiescent	V _{cc}										V _{CC}									
Device	or	0	6	-	-	8	_	80		160	or Gnd	5.5	-		8	-	80	-	160	μΑ
Current I _{cc}	Gnd					L	l		<u> </u>	L		<u> </u>			-		_		ļ	
Additional Quiescent Device Current per input pin: 1 unit load											V _{GC} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ

^{*}For dual-supply systems theoretical worst case (V_1 = 2.4 V, V_{cc} = 5.5 V) specification is 1.8 mA. HCT Input Loading Table

Input	Unit Loads*
MR	0.65
φ	0.5

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.



SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

	0,410.01	C	Typical						
CHARACTERISTIC	SYMBOL	рF	НС	HCT	Units				
Propagation Delay φ to Q1' Output	t _{PLH} t _{PHL}	15	11	17	ns				
Propagation Delay Q _n to Q _{n,1}	t _{PHL} t _{PHL}	15	4	4	ns				
Propagation Delay to MR to Q _n	t _{PHL}	15	14	17	ns				
Power Dissipation Capacitance*	C _{PD}		40	45	pF				

^{*}C_{PD} is used to determine the power consumption, per package. PD = C_{PD} Vcc² fi + Σ (C_L Vcc² fi/M) where: $M = 2^1, 2^2, 2^3, \dots 2^{12}$ $C_L = \text{output load capacitance}$

fi = input frequency

Pre-requisite for Switching Function

				25	°C		-4	0°C to	o +85°	°C	-55				
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	CT	741	НС	74F	ICT	541	нс	54H	HCT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Maximum Input Pulse		2	6	_	_	_	5	_	_	_	4	T-	_	T -	
Frequency	fmax	4.5	30	l —	25	<u> </u>	25	—	20	-	20	—	16	-	MHz
· ·		6	35	—	—	_	29	—	—	_	24	l —	-	l —	ŀ
Input Pulse Width	tw	2	80	_	_	_	100	_	_	_	120	_		I -	
(Figure 4)	1	4.5	16		20	_	20	l —	25		24	—	30	—	ns
		6	14	-	—	_	17	—	 	_	20	-	-	-	
Reset Removal Time	t _{REM}	2	50	—	I —	—	65	I —	_	_	75	=	_		
(Figure 5)		4.5	10	—	10	—	13	—	13	—	15	—	15	-	ns
	1	6	9	 —		—	11	—		—	13	—] —	—	
Reset Pulse Width	tw	2	80	_	_	_	100	_	-	_	120	_	_	<u> </u>	
(Figure 5)		4.5	16	—	20		20	l —	25		24	—	30	-	ns
		6	14	—	-	—	17		—	_	20	-	—	—	}

SWITCHING CHARACTERISTICS (CL=50 pF, Input t,,t,=6 ns)

				25	°C		-4	0°C to	+85°	C	-5				
CHARACTERISTIC	SYMBOL	Vcc	Н	C	H	CT	74	нс	74H	СТ	54	нс	54H	ICT	UNITS
·]		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	tpLH	2		140		-		175	_	_		210	_	_	
φ to Q1' Output	tpHL	4.5		28	 	40	_	35		50	-	42	_	60	ns.
(Figure 4)		6	—	24	—	—	-	30	-	_	l — _	36	-	-	
Propagation Delay	t _{PLH}	2	_	75	_	_	_	95	I —		_	110	_	_	
Q _n to Qn+1	t _{PHL}	4.5	—	15	—	15	-	19	-	19	—	22	—	22	ns
(Figure 4)		6	l —	13	—	l —	_	16	-	_	-	19	-		}
Propagation Delay	tpHL	2	_	170	-	_	_	215	_	_	-	255		_	
MR to Q _n		4.5	l —	34	—	40	_	43	-	50	—	51	 —	60	ns
(Figure 5)		6	—	29	—	—	-	37		l —		43	-	_	
Output Transition	tTLH	2		75		_	_	95	_	_	_	110	-	_	
Time	t _{THL}	4.5	-	15	—	15	—	19	—	19	-	22	—	22	ns
(Figure 4)	Į.	6		13	-			16	—	l —	<u> </u>	19			
Input Capacitance	Cı		_	10	_	10	_	10	_	10		10	_	10	pF

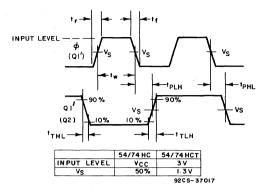


Fig. 4 - Input pulse pre-requisite times, propagation delays and output transition times.

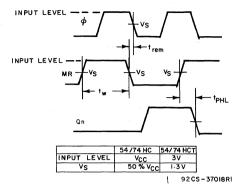


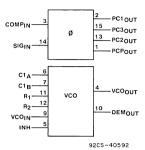
Fig. 5 - Master Reset pre-requisite and propagation delays.

File Number 1854

Advance Information/ Preliminary Data

CD54/74HC 4046A CD54/74HCT 4046A

High-Speed CMOS Logic



FUNCTIONAL DIAGRAM

Phase-Locked-Loop with VCO

Features:

- Operating frequency range of up to 18 MHz (typ.) at V_{CC} = 5 V
- Choice of three phase comparators: EXCLUSIVE-OR: edge-triggered JK flip-flop; edge-triggered RS flip-flop
- Excellent VCO frequency linearity
- VCO-inhibit control for ON/OFF keying and for low standby power consumption
- Minimal frequency drift

 Operating power supply voltage range: VCO section 3 V to 6 V; digital section 2 V to 6 V

Applications:

- FM modulation and demodulation
- Frequency synthesis and multiplication
- Frequency discrimination
- Tone decoding
- Data synchronization and conditioning
- Voltage-to-frequency conversion
- Motor-speed control

The RCA CD54/74 HC/HCT4046A are high-speed Si-gate CMOS devices that are pin compatible with the CD4046B of the "4000B" series. They are specified in compliance with JEDEC standard no. 7

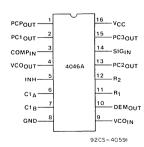
The HC/HCT4046A are phase-locked-loop circuits that contain a linear voltage-controlled oscillator (VCO) and three different phase comparators (PC1, PC2 and PC3). A signal input and a comparator input are common to each comparator.

The signal input can be directly coupled to large voltage signals, or indirectly coupled (with a series capacitor) to small voltage signals. A self-bias input circuit keeps small voltage signals within the linear region of the input amplifiers. With a passive low-pass filter, the 4046A forms a second-order loop PLL. The excellent VCO linearity is achieved by the use of linear op-amp techniques.

The CD54HC4046A and CD54HCT4046A are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC4046A and CD74HCT4046A are supplied in 16-lead plastic dual-in-line packages (E suffix), and in 16-lead surface mount plastic dual-in-line packages (M suffix). The CD54/74HC/HCT4046A are also supplied in chip form (H suffix).

Family Features:

- Fanout (Over Temperature Range); Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT/HCU: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC} @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁≤1 µA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

MAXIMUM RATINGS, Absolute-Maximum Values

DC SUPPLY-VOLTAGE (Vcc):
(Voltages referenced to ground)
DC INPUT DIODE CURRENT, I_{iK} (for $V_i < -0.5 \text{ V}$ or $V_i > V_{CC} + 0.5 \text{ V}$)
DC OUTPUT DIODE CURRENT, I_{OK} (for $V_O < -0.5$ V or $V_O > V_{CC} + 0.5$ V)
DC DRAIN CURRENT, PER OUTPUT (I_0) (for -0.5 V $<$ V $_0$ $<$ V $_{cc}$ + 0.5 V)
DC V _{cc} OR GOUND CURRENT (I _{cc}): ± 50 mA
POWER DISSIPATION PER PACKAGE (P₀):
For $T_A = -40$ to $+60$ °C (PACKAGE TYPE E)
For T _A = +60 to +85°C (PACKAGE TYPE E)
For $T_A = -55$ to $+100$ °C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For $T_A = -40$ to $+70^{\circ}$ C (PACKAGE TYPE M)
For T _A = +70 to +125°C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (Ta):
PACKAGE TYPE F, H55 to +125° C
PACKAGE TYPE E, M
STORAGE TEMPERATURE (T _{stg})65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 \pm 1/32 in. (1.59 \pm 0.79 mm) from case for 10 s max. +265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only+300° C

RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always with the following ranges:

	LIM	ITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (for T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

PIN DESCRIPTION

PIN NO.	SYMBOL	NAME AND FUNCTION
1	PCPout	phase comparator pulse output
2	PC1 _{out}	phase comparator 1 output
3	COMPIN	comparator input
4	VCO _{out}	VCO output
5	INH	inhibit input
6	C1 _A	capacitor C1 connection A
7	C1 _B	capacitor C1 connection B
8	GND	ground (0 V)
9	VCOIN	VCO input
10	DEM _{out}	demodulator output
11	R ₁	resistor R1 connection
12	R₂	resistor R2 connection
13	PC2 _{out}	phase comparator 2 output
14	SIG _{IN}	signal input
15	PC3 _{out}	phase comparator 3 output
16	Vcc	positive supply voltage

GENERAL DESCRIPTION

vco

The VCO requires one external capacitor C1 (between C1_A and C1_B) and one external resistor R1 (between R₁ and GND) or two external resistors R1 and R2 (between R₁ and GND, and R₂ and GND). Resistor R1 and capacitor C1 determine the frequency range of the VCO. Resistor R2 enables the VCO to have a frequency offset if required. See logic diagram, Fig. 1.

The high input impedance of the VCO simplifies the design of low-pass filters by giving the designer a wide choice of resistor/capacitor ranges. In order not to load the low-pass filter, a demodulator output of the VCO input voltage is provided at pin 10 (DEMout). In contrast to conventional techniques where the DEMour voltage is one threshold voltage lower than the VCO input voltage, here the DEMout voltage equals that of the VCO input. If DEMout is used, a load resistor (Rs) should be connected from DEMout to GND; if unused, DEMout should be left open. The VCO output (VCO_{OUT}) can be connected directly to the comparator input (COMPIN), or connected via a frequency-divider. The VCO output signal has a guaranteed duty factor of 50%. A LOW level at the inhibit input (INH) enables the VCO and demodulator, while a HIGH level turns both off to minimize standby power consumption.

Phase Comparators

The signal input (SIG_{IN}) can be directly coupled to the self-biasing amplifier at pin 14, provided that the signal swing is between the standard HC family input logic levels. Capacitive coupling is required for signals with smaller swings.

Phase comparator 1 (PC1)

This is an Exclusive-OR network. The signal and comparator input frequencies (f_i) must have a 50% duty factor to obtain the maximum locking range. The transfer characteristic of PC1, assuming ripple ($f_r = 2f_i$) is suppressed, is:

 $V_{\text{DEMOUT}} = (V_{\text{CC}}/\pi)$ (ϕ_{SIGIN} - ϕ_{COMPIN}) where V_{DEMOUT} is the demodulator output at pin 10; $V_{\text{DEMOUT}} = V_{\text{PC1OUT}}$ (via low-pass filter).

The average output voltage from PC1, fed to the VCO input via the low-pass filter and seen at the demodulator output at pin 10 (V_{DEMOUT}), is the resultant of the phase differences of signals (SIG_{IN}) and the comparator input (COMP_{IN}) as shown in Fig. 2. The average of V_{DEM} is equal to 1/2 V_{cc} when there is no signal or noise at SIG_{IN}, and with this input the VCO oscillates at the center frequency (f_{o}). Typical waveforms for the PC1 loop locked at f_{o} are shown in Fig. 3.

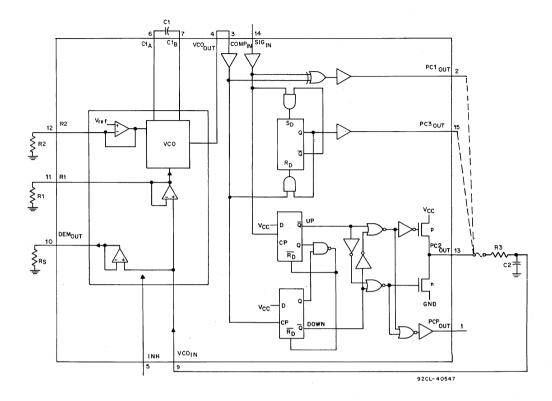


Fig. 1 - Logic diagram.

The frequency capture range ($2f_c$) is defined as the frequency range of input signals on which the PLL will lock if it was initially out-of-lock. The frequency lock range ($2f_L$) is defined as the frequency range of input signals on which the loop will stay locked if it was initially in lock. The capture range is smaller or equal to the lock range.

With PC1, the capture range depends on the low-pass filter characteristics and can be made as large as the lock range. This configuration retains lock behavior even with very noisy input signals. Typical of this type of phase comparator is that it can lock to input frequencies close to the harmonics of the VCO center frequency.

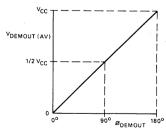


Fig. 2 — Phase comparator 1: average output voltage versus input phase difference:

 $V_{\rm DEMOUT} = V_{\rm PC1OUT} = (V_{\rm CC}/\pi) \, (\phi_{\rm SIGIN} - \phi_{\rm COMPIN}); \ \phi_{\rm DEMOUT} = (\phi_{\rm SIGIN} - \phi_{\rm COMPIN}).$

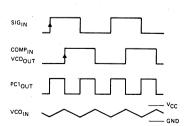


Fig. 3 — Typical waveforms for PLL using phase comparator 1, loop locked at fo.

Phase Comparator 2 (PC2)

This is a positive edge-triggered phase and frequency detector. When the PLL is using this comparator, the loop is controlled by positive signal transitions and the duty factors of SIG_{IN} and COMP_{IN} are not important. PC2 comprises two D-type flip-flops, control-gating and a 3-state output stage. The circuit functions as an up-down counter (Fig. 1) where SIG_{IN} causes an up-count and COMP_{IN} a down-count. The transfer function of PC2, assuming ripple ($f_r = f_i$) is suppressed is:

 $V_{DEMOUNT} = (V_{CC}/4\pi) (\phi_{SIGIN} - \phi_{COMPIN})$ where V_{DEMOUT} is the demodulator output at pin 10: $V_{DEMOUT} = V_{PCZOUT}$ (via low-pass filter).

The average output voltage from PC2, fed to the VCO via the low-pass filter and seen at the demodulator output at pin 10 (V_{DEMOUT}), is the resultant of the phase differences of SIG_{IN} and COMP_{IN} as shown in Fig. 4. Typical waveforms for the PC2 loop locked at f_0 are shown in Fig. 5.

When the frequencies of SIG_{IN} and $COMP_{IN}$ are equal but the phase of SIG_{IN} leads that of $COMP_{IN}$, the p-type output driver at $PC2_{OUT}$ is held "ON" for a time corresponding to the phase difference (ϕ_{DEMOUT}). When the phase of SIG_{IN} lags that of $COMP_{IN}$, the n-type driver is held "ON".

When the frequency of SIG_{IN} is higher than that of COMP_{IN}, the p-type output driver is held "ON" for most of the input signal cycle time, and for the remainder of the cycle both n- and p-type drivers are "OFF" (3-state). If the SIG_{IN} frequency is lower than the COMP_{IN} frequency, then it is the n-type driver that is held "ON" for most of the cycle. Subsequently, the voltage at the capacitor (C2) of the low-pass filter connected to PC2_{OUT} varies until the signal and comparator inputs are equal in both phase and frequency. At this stable point the voltage on C2 remains constant as the PC2 output is in 3-state and the VCO input at pin 9 is a high impedance. Also in this condition, the signal at the phase comparator pulse output (PCP_{OUT}) is a HIGH level and so can be used for indicating a locked condition.

Thus, for PC2, no phase difference exists between SIG_{IN} and COMP_{IN} over the full frequency range of the VCO. Moreover, the power dissipation due to the low-pass filter is reduced because both p- and n-type drivers are "OFF" for most of the signal input cycle. It should be noted that the PLL lock range for this type of phase comparator is equal to the capture range and is independent of the low-pass filter. With no signal present at SIG_{IN}, the VCO adjusts, via PC2, to its lowest frequency.

Phase comparator 3 (PC3)

This is a positive edge-triggered sequential phase detector using an RS-type flip-flop. When the PLL is using this comparator, the loop is controlled by positive signal transitions and the duty factors of SIG_{IN} and COMP_{IN} are not important. The transfer characteristic of PC3, assuming ripple ($f_r = f_i$) is suppressed, is:

 $V_{\text{DEMOUT}} = (V_{\text{CC}}/2\pi) \ (\phi_{\text{SIGIN}} - \phi_{\text{COMPIN}}) \ \text{where} \ V_{\text{DEMOUT}} \ \text{is the} \ \text{demodulator output at pin 10;} \ V_{\text{DEMOUT}} = V_{\text{PC3OUT}} \ (\text{via low-pass filter}).$

The average output from PC3, fed to the VCO via the low-pass filter and seen at the demodulator at pin 10 (V_{DEMOUT}), is the resultant of the phase differences of SIG_{IN} and COMP_{IN} as shown in Fig. 6. Typical waveforms for the PC3 loop locked at f₀ are shown in Fig.7.

The phase-to-output response characteristic of PC3 (Fig. 6) differs from that of PC2 in that the phase angle between SIG_{IN} and COMP_{IN} varies between 0° and 360° and is 180° at

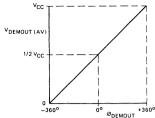


Fig 4 — Phase comparator 2: average output voltage versus input phase difference:

V_{DEMOUT} = V_{PC2OUT} = (V_{CC}/4π) (φ_{SIGIN} - φ_{COMPIN});
φ_{DEMOUT} = (φ_{SIGIN} - φ_{COMPIN}).

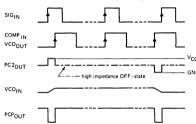


Fig. 5 — Typical waveforms for PLL using phase comparator 2, loop locked at f_o.

the center frequency. Also PC3 gives a greater voltage swing than PC2 for input phase differences but as a consequence the ripple content of the VCO input signal is higher. With no signal present at SIG_{IN}, the VCO adjusts, via PC3, to its highest frequency.

The only difference between the HC and the HCT versions is the input level specification of the INH input. This input disables the VCO section. The comparators' sections are identical, so that there is no difference in the SIG_{IN} (pin 14) or COMP_{IN} (pin 3) inputs between the HC and the HCT versions.

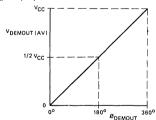


Fig.6 — Phase comparator 3: average output voltage versus input phase difference: $V_{\text{DEMOUT}} = V_{\text{PCSOUT}} = (V_{\text{CC}}/2\pi) \; (\phi_{\text{SIGIN}} - \phi_{\text{COMPIN}});$ $\phi_{\text{DEMOUT}} = (\phi_{\text{SIGIN}} - \phi_{\text{COMPIN}}).$

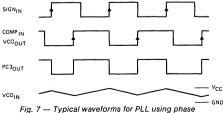


Fig. 7 — Typical waveforms for PLL using phase comparator 3, loop locked at f_o.

STATIC ELECTRICAL CHARACTERISTICS

		CD7	4HC4	046A	CD54	4HC40)46A				CD74HCT4046A/CD54HCT4046A										
		TEST CONDITIONS			IC/54		741 TY	HC PE	541 TY		TEST CONDITION			T/54 YPES		74F TY	ICT PE	54H TY	ICT PE		
VCO SECTION	V _I	I _O	v _{cc}		+25°C		-40/ +85°C		-55/ +125°C		V _I	v _{cc}		-25° C	:	1	-40/ +85° C		5/ 5°C	UNITS	
	٧	mA	v	Min	Тур	Max	Min	Max	Min	Max	v	٧	Min	Тур	Max	Min	Max	Min	Max		
INH			3	2.1	-	_	2.1	-	2.1	_		4.5									
High-Level Input Voltage V _{Iн}		-	4.5	3.15	_	 -	3.15	-	3.15	-	. —	to	2	-	-	2	-	2	-	v	
			6	4.2	_	-	4.2	-	4.2	_		5.5									
INH			3	_	-	0.9	-	0.9	-	0.9		4.5									
Low-Level Input Voltage V _{IL}			4.5	_	_	1.35	_	1.35	_	1.35	_	to	_	_	0.8	_	0.8	_	0.8	v	
			6	_	_	1.8	_	1.8	-	1.8		5.5	ļ			l					
VCO _{OUT}	VIL		3	2.9	_	_	2.9	_	2.9		VIL										
High-Level Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4		-	4.4	-	4.4	-	v	
CMOS Loads	V _{IH}		6	5.9	_	-	5.9	_	5.9	_	VIH										
	VIL										VIL										
TTL Loads	or	-4	4.5	3.98	_	-	3.84	[-	3.7	_	or	4.5	3.98	_	_	3.84	-	3.7	-	· v	
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}										
VCO _{out}	VıL		2	-	_	0.1	-	0.1	_	0.1	VIL										
Low-Level Output Voltage VoL	or	0.02	4.5	-	_	0.1	-	0.1	_	0.1	or	4.5	_	-	0.1	_	0.1	_	0.1	v	
CMOS Loads	ViH		6	-	_	0.1	-	0.1	-	0.1	V _{IH}										
	V _{IL}										VıL										
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_ '	_	0.26	_	0.33	_	0.4	v	
	, V _{IH}	5.2	6	_	-	0.26	-	0.33	-	0.4	Vін		1							ļ	
C1A, C1B	V _{IL}										V _{IL}										
Low Level Output Voltage	or	4	4.5	_	-	0.40	_	0.47	-	0.54	or	4.5	-	-	0.40	-	0.47	_	0.54	v	
(Test purposes Volonly)	V _{IH}	5.2	6	-	_	0.40	_	0.47	_	0.54	V _{IH}	_	-	_	l –	-	-	 –	-		
INH VCO _{IN}	Vcc										Any Voltage										
Input Leakage Current I	or		6	-	-	±0.1	-	±1	-	±1	Between V _{CC}	5.5	-	_	±0.1	_	±1	-	±1	μА	
	Gnd										and Gnd										
			3	-	_	-	-	_	-	-		_	T-	_	_	-	-	-	-		
R1 Range			4.5	3	_	300	-	_	-	_	1	4.5	3	_	300	-	-	-	-	kΩ	
			6	-	_	_	-	-	T-		1	<u> </u>	-	-	_	-	-	-	1-	1	
			3	-	-	Ι-	-	_	<u> </u>	_			_	Γ-	-	-	-	-	1-		
R2 Range		Ì	4.5	3	-	300	-	-	-	-	1		3	_	300	-	-	-	-	kΩ	
		ļ	6	-	-	-	Ι-	T-	Ι-	-	1	ļ	-	-	-	-	-	T-	1-	1	
		~~~	3			No L									No L						
C1 Capacitance			4.5	0		I M		1					0		Į,					pF	
Range			6			1 T									Ŧ		1				
VCOIN	Over th	e range	3	0.9		1.9	T. "	1										Π	1		
Operating Voltage	specifie R1 for I	ed for Linearity	4.5	0.9	1	3.2						4.5	0.9		3.2					v.	
Range	R1 for Linearity See Figs. 8 & 35-38 See Note 2	8 & 35-38				4.6			1		1							1			

NOTES: 1. The value for R1 & R2 in parallel should exeed 2.7 kΩ.
2. The maximum operating voltage can be as high as V_{CC} -0.9 V, however, this may result in an increased offset voltage.

### STATIC ELECTRICAL CHARACTERISTICS

		CD	74HC4	1046A	CD5	HC40	146A				CD74HCT4046A/CD54HCT4046A										
		TEST CONDITIONS			IC/54		74 TY	HC PE	54I TY		TEST CONDITION		1	CT/54		ı	ICT PE	54F TY	ICT PE		
CHARACTERISTIC PHASE	v _i	I _o	v _{cc}		+25° C		-40/ +85° C		-5 +12		V _i	v _{cc}	+25° C		;	1	10/ 5° C		5/ 5° C	UNITS	
COMPARATOR SECTION	V	mA	٧	Min	Тур	Max	Min	Max	Min	Max	٧	V	Min	Тур	Max	Min	Max	Min	Max		
SIG _{IN} , COMP _{IN} DC Coupled			2	1.5	_	_	1.5	_	1.5	_		4.5									
High-Level V _{IH} Input Voltage			4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	-	_	2	-	2	-	V	
			6	4.2	_	_	4.2	_	4.2	_		5.5					ļ				
SIG _{IN} , COMP _{IN} DC Coupled			2	_	_	0.5	_	0.5	_	0.5		4.5									
Low-Level V _{IL} Input Voltage			4.5	_	_	1.35	_	1.35	_	1.35	-	to	-	-	0.8	-	0.8	-	0.8	V	
			6		_	1.8	_	1.8	_	1.8		5.5				ļ					
PCP _{OUT} , PCn OUT High-Level	VIL		2	1.9			1.9	_	1.9	-	Vil					l		l		İ	
Output Voltage Von	or	-0.02	4.5	4.4	_	_	4.4		4.4		or	4.5	4.4	_	-	4.4	-	4.4	-	V	
CMOS Loads	V _{IH}		6	5.9	_	_	5.9		5.9	_	V _{IH}		-				-	_	-		
TTL Loads	V _{IL}	-4	4.5	3.98	_	_	3.84	_	3.7	_	V _{IL} or	4.5	3.98	_		3.84		3.7	_	v	
, TTE LOAGS	ViH	-5.2	6	5.48	_		5.34	-	5.2	_	V _{IH}	4.5	3.50			3.04		3.7	_	•	
PCPout, PCn OUT	Vil	5.2	2	-		0.1	0.04	0.1	-	0.1	VIL				_						
Low-Level Output Voltage Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	V	
CMOS Loads	VIH		6	-		0.1	_	0.1	_	0.1	V _{IH}										
	VIL										VIL										
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v	
	V _{IH}	5.2	6	-	-	0.26	_	0.33	_	0.4	V _{IH}										
SIG _{IN} , COMP _{IN}	Vcc		2	_	_	±3	_	±.4	_	±5	Any										
Input Leakage I	or		3	_	_	±7	_	±9	_	±11	Voltage Between	5.5	_		±30	_	±38	_	±45	μΑ	
Current	Gnd		4.5		_	±18		±23	_	±29	V _{cc} and Gnd	0.5			-50		200			μ	
	G.I.G		6	_	-	±30		±38		±45	Grid										
PC2 OUT 3-State I _{oz}	VIL			1																	
Off-State Current	or V _{iн}		6	-	_	±0.5	-	±5	_	±10		5.5	-	-	±0.5	±5	-	-	±10	μΑ	
SIG _{IN} , COMP _{IN} Input	V _I Self-	Bias	3	_	800	_	_	_	_	_											
Resistance R _i	Oper. Point: ΔV _I = 0.5 V		4.5	-	250	_	_	_	_	-		4.5	-	250	-	-	-	-	_	kΩ	
	See F	ig. 8	6		150		_	_	_	_											

### STATIC ELECTRICAL CHARACTERISTICS

		CD7	4HC4	046A	/CD54	HC40	46A				CD74HCT4046A/CD54HCT4046A									
		TEST CONDITIONS				74HC/54HC TYPES		74HC TYPE		HC PE	TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPE		54HCT TYPE		
CHARACTERISTIC  DEMODULATOR SECTION	V _I	I _O	v _{cc}		+25° C	!5°C		-40/ +85° C		5/ 5° C	V,	v _{cc}	+25° C		;	-40/ +85° C		-55/ +125° C		UNITS
	V	mA	V	Min	Тур	Max	Min	Max	Min	Max	V	V	Min	Тур	Max	Min	Max	Min	Max	
Resistor Range	at R _s > 300 kΩ Leakage		3	50	_	300														1
R _s	Curre	nt can ence	4.5	50	_	300						4.5	5	-	300					kΩ
	V _{DEM} OUT		6	50	_	300														
Offset Voltage	$V_i = V_{VCO\ IN} = \frac{V_{CC}}{2}$		3	-	±30	-										ĺ				
VCO _{IN} , to V _{DEM}	Values	Values taken over Rs range		-	±20	_				İ		4.5	-	±20	-			į		mV
$V_{OFF}$		ig. 15	6	_	±10	_														
Dynamic Output Resistance at DEMout			3	-	25	_														
R _D	V _{DEM} ou	$r = \frac{V_{cc}}{2}$	4.5	-	25	-		}				4.5	-	25	_					Ω
116			6		25	-														
Quiescent Device Current Icc		5 & 14 Vcc									V _{cc}									
Device Guirent 166	Pin 9 a	at Gnd. ns 3 & 14	6	-	-	8	-	80	-	160	or	5.5	-		8	-	80	-	160	μΑ
		xcluded									Gnd				1			ļ		
Additional Quiescent Device					-	;			-		V _{cc} -2.1	4.5								
Current Per Input Pin: 1 unit load $\Delta I_{cc}$											(Excluding Pin 5)	to 5.5	-	100	360	_	450		490	μΑ

^{*}For dual-supply systems theoretical worst case ( $V_1 = 2.4 \text{ V}$ ,  $V_{CC} = 5.5 \text{ V}$ ) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads*
INH	

^{*}Unit Load is  $\Delta l_{\rm CC}$  limit specified in Static Characteristics Chart, e.g., 360  $\mu A$  max. @ 25° C.

### SWITCHING CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r$ , $t_f = 6 \text{ ns}$ )

		TEST CONDIT	TIONS		25	°C			-40°C t	o +85° C	:		-55°C to	+125°	С	
CHARACTERISTIC	С		v	Н	С	н	СТ	74	нс	74F	СТ	54	нс	54F	1CT	UNITS
			V _{CC}	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
PHASE COMPARATOR	SECTIO	ON										1			,	
Propagation Delay,			2	-	200	_	-	-	250	-	-	-	300	-	_	
SIG _{IN} , COMP _{IN}	t _{PLH}	4.		_	40	_	45	-	50	-	56	-	60	-	68	
to PCI _{out}	t _{PHL}		6		34		_		43		_	_	51	_		
SIG _{IN} , COMP _{IN}			2	_	300	-	-	-	375	_	-	-	450	_	-	
to PCP _{out}			4.5	_	60	_	68	-	75	_	85	_	90	_	102	
			6		70				88				109			
SIG _{IN} , COMP _{IN}			2	_	245	_	_	_	305	_	_	-	307	_	-	
to PC3 _{out}			4.5	_	49	-	58	_	61	-	73	_	74		87	
			6		42		<u> </u>		52				63			ns
Output Transition			2	_	75	-	_	-	95	_	_	-	110	_	_	
Time	t _{THL}		4.5	_	15	-	15	_	19	-	19	_	22	-	22	
	ttlH		6		13	<u> </u>			16				19	_	<u> </u>	
Output Enable Time,			2	-	265	_	_	_	330	_	-	-	400	-	_	
SIG _{IN} , COMP _{IN}	t _{PZH}		4.5	_	53	_	60	_	66	_	75	_	80	_	90	
to PC2 _{OUT}	t _{PZL}		6		45				56	_			68		<u> </u>	
Output Disable Time,			2	_	315	_	_	-	395	_	_	-	475	_	_	
SIG _{IN} , COMP _{IN}	t _{PHZ}		4.5	_	63		68	_	79	_	85	_	95	-	102	
to PC2 _{out}	t _{PLZ}		6		74		_	-	93		-		112			
AC Coupled Input				<u> </u>		ICAL										
Sensitivity (p-p)		V ₁ (p-p)	3	11 15		11										S
at SIG _{IN} or			4.5			l .	5						1			mV
COMPIN			6	3	3	3	3	l	L				l			L
VCO SECTION								1		1						
Frequency Stability		R, = 100kΩ	3	_		0.11										
with Temperature	Δf	R ₂ = ∞	4.5	0.	11	0.	11									%/°C
Change	ΔΤ	0 50 5	6			ļ							-		ļ	
Max. Frequency		C ₁ = 50 pF	3	24		24										l
		R ₁ = 3.5kΩ	4.5	2	4	2	:4									MHz
	f _{max}	R ₂ = ∞	6			ļ					<del></del>					
		C ₁ = 0 pF		١.		١,	20		}					ĺ		
		$R_1 = 9.1k\Omega$ $R_2 = \infty$	4.5 6	3	8	38			ļ	İ						MHz
Control Francisco										-	-		<u> </u>			
Center Frequency		C ₁ = 40 pF R ₁ = 3kΩ	3 4.5	1	<b>-</b>	١.	7									MHz
		R ₁ - 3KΩ R ₂ = ∞	4.5 6	'	′	i '	′									IVIHZ
		NCO - V	ь										ļ			
		VCO _{IN} = <u>V_{CC}</u>														
Frequency Linearity,		R ₁ = 100kΩ	3													
Δf _{vco}		R ₂ = ∞	4.5	0.	Л	_	.4									%
VCO		C ₁ = 100 pF	6	0		"	.→								İ	7,0
Offset Frequency		R ₂ = 220kΩ	3			-			-			-	<b>-</b>		<del> </del>	
S. Sect Trequency		C ₁ = 1 nF	4.5		00	A.	00									kHz
		5, 1111	6	"		"			]					]		1112
DEMODULATOR SECT	ION			L				L	Ь	L						
V _{OUT} V _S f _{IN}		R ₁ = 100 kΩ							Ι	Ι	I	T				I
- OUT FORM		R ₂ = ∞								1	1					
		C ₁ = 100 pF	3	-	-	-	-							1		
		R _s = 10 kΩ	4.5	33	30	33	30									mV/kHz
		$R_3 = 100 \text{ k}\Omega$	6	-	-	-	-				1					
		C ₂ = 100 pF														
		C2 - 100 pF		L		L				l	L	L	L		L	L

#### Figure References for DC Characteristics

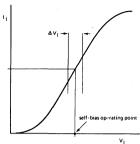


Fig. 8 — Typical input resistance

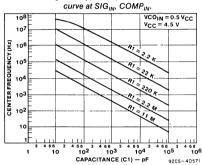


Fig. 10-HCT4046A typical center frequency vs R1, C1 (Vcc=4.5 V).

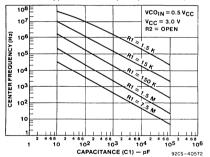


Fig. 12-HC4046A typical center frequency vs R1, C1 (Vcc=3 V, R2=open).

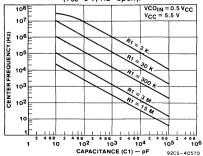


Fig. 14-HCT4046A typical center frequency vs R1, C1 (Vcc=5.5 V).

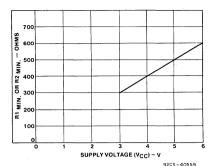


Fig. 9-HC/HCT4046A R1 (min) or R2 (min) vs supply voltage (Vcc).

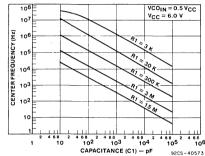


Fig. 11-HC4046A typical center frequency vs R1, C1 (Vcc=6 V).

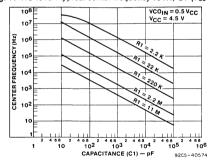


Fig. 13-HCT4046A typical center frequency vs R1, C1 (Vcc=4.5 V).

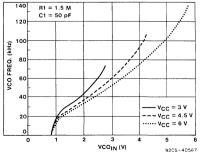


Fig. 15-HC4046A typical VCO frequency vs VCO_{IN} (R1=1.5  $M\Omega$ , C1=50 pF).

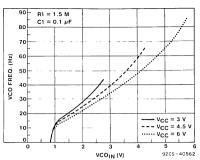


Fig. 16-HC4046A typical VCO frequency vs VCO_{IN} (R1=1.5 M $\Omega$ , C1=0.1  $\mu$ F).

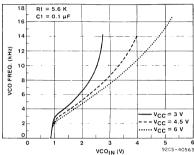


Fig. 18-HC4046A typical VCO frequency vs VCO_{IN} (R1=5.6 k $\Omega$ , C1=0.1  $\mu$ F).

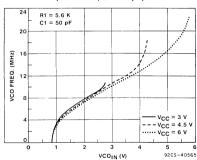


Fig. 20-HC4046A typical VCO frequency vs VCO_{IN} (R1=5.6 k $\Omega$ , C1=50 pF).

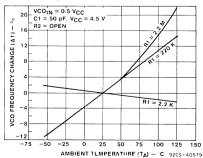


Fig. 22–HC4046A typical change in VCO frequency vs ambient temperature as a function of R1 ( $V_{CC}$ =4.5 V).

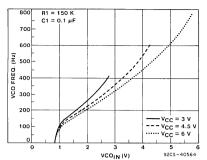


Fig. 17-HC4046A typical VCO frequency vs VCO_{IN}  $(R1=150 \text{ k}\Omega, \text{ C}1=0.1 \text{ }\mu\text{F}).$ 

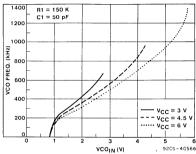


Fig. 19-HC4046A typical VCO frequency vs VCO_{IN} (R1=150 k $\Omega$ , C1=50 pF).

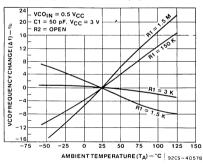


Fig. 21-HC4046A typical change in VCO frequency vs ambient temperature as a function of R1 (Vcc=3 V).

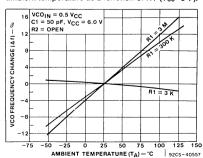


Fig. 23-HC4046A typical change in VCO frequency vs ambient temperature as a function of R1 (Vcc=6 V).

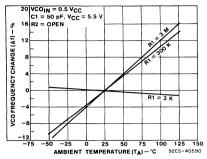


Fig. 24-HCT4046A typical change in VCO frequency vs ambient temperature as a function of R1.

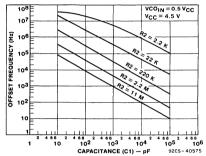


Fig. 26-HC4046A offset frequency vs R2, C1 (Vcc=4.5 V).

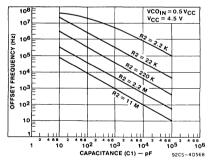


Fig. 28-HCT4046A offset frequency vs R2, C1 (Vcc=4.5 V).

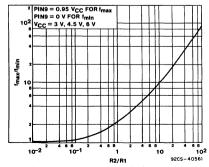


Fig. 30-HC4046A f_{max}/f_{min} vs R2/R1 (V_{CC}=3 V, 4.5 V, 6 V).

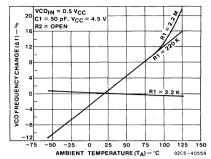


Fig. 25-HC4046A typical change in VCO frequency vs ambient temperature as a function of R1 (Vcc=4.5 V).

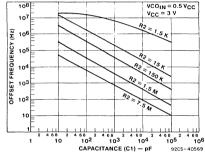


Fig. 27-HC 4046A offset frequency vs R2, C1 (Vcc=3 V).

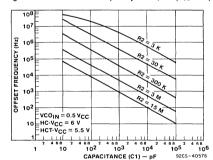


Fig. 29-HC4046A & HCT4046A offset frequency vs R2, C1  $(V_{cc}=6\ V,\ V_{cc}=5.5\ V)$ .

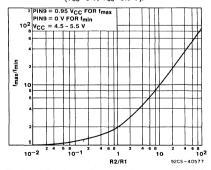


Fig. 31-HCT4046A f_{max}/f_{min} vs R2/R1 (V_{CC}=4.5 V-5.5 V).

### AC WAVEFORMS

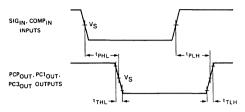


Fig. 32 — Waveforms showing input (SIG_{IN} COMP_{IN}) to output (PCP_{OUT}, PC1_{OUT}, PC3_{OUT}) propagation delays and the output transition times.

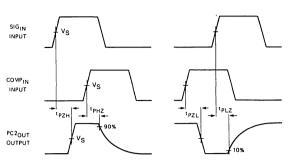
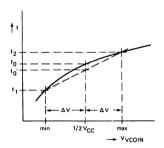


Fig. 33 — Waveforms showing the 3-state enable and disable times for PC2_{OUT}.

	нс	нст
INPUT LEVEL	vcc	3 V
SWITCHING VOLTAGE, VS	50% VCC	1.3 V



 $\Delta V = 0.5 \text{ V}$  over the  $V_{CC}$  range:

for VCO linearity

$$f'_0 = \frac{f_1 + f_2}{2}$$

linearity = 
$$\frac{f'_0 - f_0}{f'_0} \times 100\%$$

Fig. 34 — Definition of VCO frequency linearity.

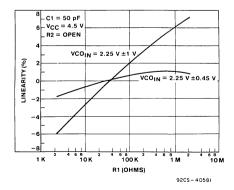


Fig. 35-HC4046A VCO linearity vs R1 (Vcc=4.5 V).

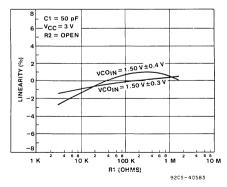


Fig. 36-HC4046A VCO linearity vs R1 (Vcc=3 V).

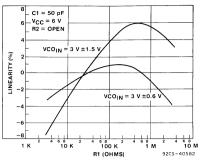


Fig. 37-HC4046A VCO linearity vs R1 (Vcc=6 V).

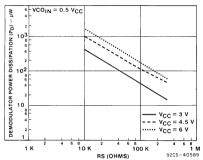


Fig. 39-HC4046A demodulator power dissipation vs RS (typ.)  $(V_{CC}=3\ V;\ 4.5\ V;\ 6\ V)$ .

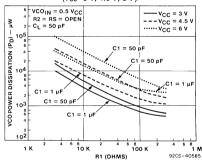


Fig. 41-HC4046A VCO power dissipation vs R1 (C1=50 pF; 1  $\mu$ F).

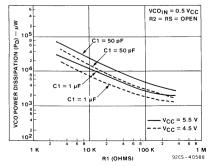


Fig. 43-HCT4046A VCO power dissipation vs R1 (C1=50 pF; 1  $\mu$ F).

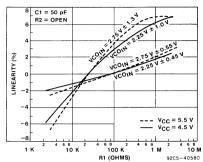


Fig. 38-HCT4046A VCO linearity vs R1 (Vcc=4.5 V, Vcc=5.5 V).

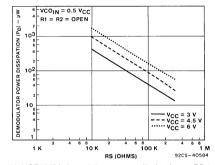


Fig. 40-HCT4046A demodulator power dissipation vs RS (typ.) ( $V_{cc}$ =3 V; 4.5 V; 6 V).

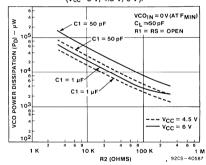


Fig. 42-HCT4046A VCO power dissipation vs R2 (C1=50 pF; 1  $\mu$ F).

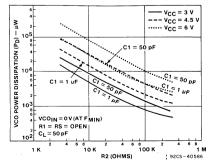


Fig. 44-HC4046A VCO power dissipation vs R2 (C1=50 pF, 1  $\mu$ F).

### HC/HCT 4046A CPD

CHIP SECTION	нс	нст	UNIT
COMPARATOR 1	48	50	
COMPARATORS 2 & 3	39	48	pF
vco	61	53	

#### APPLICATION INFORMATION

This information is a guide for the approximation of values of external components to be used with the 74HC/HCT4046A in a phase-lock-loop system.

References should be made to Figs.10 through 14 as indicated in the table.

Values of the selected components should be within the following ranges.

 $\begin{array}{lll} \text{R1} & \text{between 3 k}\Omega \text{ and 300 k}\Omega; \\ \text{R2} & \text{between 3 k}\Omega \text{ and 300 k}\Omega; \\ \text{R1} + \text{R2} & \text{parallel value} > 2.7 k}\Omega; \\ \text{C1} & \text{greater than 40 pF.} \end{array}$ 

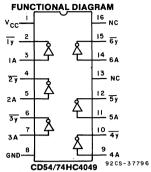
SUBJECT	PHASE COMPARATOR	DESIGN CONSIDERATIONS
		VCO Frequency characteristic
VCO frequency without extra offset	PC1, PC2 or PC3	With R2 = $\infty$ and R1 within the range 3 k $\Omega$ < R1 < 300 k $\Omega$ , the characteristics of the VCO operation will be as shown in Figs. 10-14. (Due to R1, C1 time constant a small offset remains when R2 = $\infty$ .)
		operating without offset: $f_0$ = center frequency: $2f_L$ = frequency lock range.
		Selection of R1 and C1
	PC1	Given f₀, determine the values of R1 and C1 using Figs. 10-14.
	PC2 or PC3	Given $f_{\text{max}}$ and $f_{\text{o}}$ , determine the values of R1 and C1 using Fig. 30. Use Fig. 31 to obtain $2f_{\text{L}}$ and then use this to calculate $f_{\text{min}}$ .
		VCO frequency characteristic
VCO frequency with extra offset	PC1, PC2 or PC3	With R1 and R2 within the ranges $3 \text{ k}\Omega < \text{R1} < 300 \text{ k}\Omega, 3 \text{ k}\Omega, < \text{R2} < 300 \text{ k}\Omega, the characteristics of the VCO operation will be as shown in Figs. 26-29.     $

### **APPLICATION INFORMATION (Cont'd.)**

SUBJECT	PHASE COMPARATOR	DESIGN CONSIDERATIONS
		Selection of R1, R2 and C1
VCO frequency with offset (continued)	PC1, PC2 or PC3	Given $f_o$ and $f_L$ , determine the value of product R1C1 by using Figs.26-29. Calculate $f_{\rm off}$ from equation $f_{\rm off}=f_{\rm CO}=f_L$ . Obtain the values of C1 and R2 by using Figs. 26-29. Calculate the value of R1 from the value of C1 and the product R1C1.
PLL conditions with	PC1	VCO adjusts to $f_o$ with $\phi_{DEMOUT} = 90^{\circ}$ and $V_{VCOIN} = 1/2 V_{CC}$ (see Fig. 2).
no signal at the SIG _{IN} input	PC2	VCO adjusts to $f_o$ with $\phi_{DEMOUT} = -360^{\circ}$ and $V_{VCOIN} = 0$ V (see Fig. 4).
	PC3	VCO adjusts to f _o with $\phi_{\text{DEMOUT}} = +360^{\circ}$ and $V_{\text{VCOIN}} = V_{\text{CC}}$ (see Fig. 6).
PLL Frequency capture range	PC1, PC2 or PC3	Loop filter component selection
		(a) $\tau = R3 \times C2$ (b) amplitude characteristic (c) pole-zero diagram A small capture range (2f _c ) is obtained if $\tau > 2f_c^{\prime} \approx 1/\pi \ (2\pi f_L/\tau_c)^{1/2}$ Fig. 47 — Simple loop filter for PLL without offset.
		INPUT  RA  OUTPUT  M  OUTPUT  M  M  M  M  M  M  M  M  M  M  M  M  M

SUBJECT	PHASE COMPARATOR	DESIGN CONSIDERATIONS
PLL locks on harmonics	PC1 or PC3	yes ·
at center frequency	PC2	no
noise rejection at	PC1	high
signal input	PC2 or PC3	low
	PC1	$f_r=2f_i$ , large ripple content at $\phi_{DEMOUT}=90^\circ$
AC ripple content when PLL is locked	PC2	$f_{r}=f_{i_{1}}$ small ripple content at $\phi_{DEMOUT}=0^{\circ}$
	PC3	$f_r = f_{SIG_{IN}}$ large ripple content at $\phi_{DEMOUT} = 180^\circ$

# **High-Speed CMOS Logic**



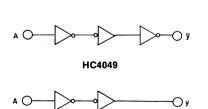
# Hex Buffers, Inverting and Non-Inverting

#### **Type Features**

- Typical propagation delay = 6 ns @ V_{CC} = 5 V, C_L = 15pF, T_A = 25°C
- High-to-low voltage level converter for up to V₁ = 16 V

The RCA-CD54/74HC4049 and CD54/74HC4050 are fabricated with high-speed silicon gate technology. They have a modified input protection structure that enables these parts to be used as logic level translators which will convert highlevel logic to a low-level logic while operating off the low-level logic supply. For example, 0-V to 15-V input logic levels can be down-converted to 0-V to 5-V logic levels. The modified input protection structure protects the input from both positive and negative electrostatic discharge. These parts can also be used as simple buffers or inverters without level translation. The CD54/74HC4049 and CD54/74HC4050 are enhanced versions of equivalent CMOS types.

The CD54HC4049 and CD54/74HC4050 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix) and in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).



LOGIC DIAGRAMS

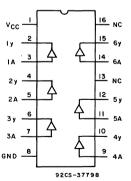
HC4050

92CS-37797

#### **Family Features**

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%,V_{CC}, N_{IH} = 30% V_{CC}; @ V_{CC} = 5 V

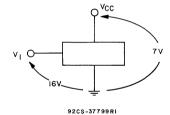
#### **FUNCTIONAL DIAGRAM**



CD54/74HC4050

MAXIMUM RATINGS, Absolute-Maximum Values:	
DC SUPPLY-VOLTAGE, (Vcc)	0.5 to +7 V
DC INPUT VOLTAGE, (V _i )	
(Voltages referenced to ground)	0.5 to +16 V
DC INPUT DIODE CURRENT, $I_{iK}$ (FOR $V_i < -0.5 \text{ V}$ )	20 mA
DC OUTPUT DIODE CURRENT, $I_{OK}$ (FOR $V_o < -0.5$ V OR $V_o > V_{CC} + 0.5$ V)	
DC DRAIN CURRENT, PER OUTPUT (I ₀ ) (FOR -0.5 V $<$ V _o $<$ V _{cc} +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	· · · · · · · · · · · · · · · · · · ·
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tata)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C





### **RECOMMENDED OPERATING CONDITIONS**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERICTIC	LIF	MITS	LINUTC
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
Vcc:*			
CD54/74HC Types	2	6	V
DC Output Voltage, Vo	0	Vcc	V
DC Input Voltage (V _I )	0	15	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t,tf:			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

#### STATIC ELECTRICAL CHARACTERISTICS

			C	D54/74H	IC404	9, CD	54/741	HC40	50			
	•		TEST		741	1C/54	HC	74	НС	541	HC	1
CHARACTERISTIC	ACTERISTIC CONDITIONS SERIES SERIES SERI		RIES	SUNITS								
					Ι.	+25° C		-4	0/	-5	5/	1
		VI	lo	VCC					°C	+12	5°C	
		٧	mA	٧	Min.	Тур.	Max.		Max.		Max.	
				2	1.5	_	_	1.5	_	1.5	_	
High-Level Input Voltage	$V_{IH}$			4.5	3.15	_	<u> </u>	3.15		3.15	_	] v
				6	4.2	_	_	4.2		4.2	_	
	-			2	_	_	0.5	_	0.5	_	0.5	
Low-Level Input Voltage	VIL			4.5		_	1.35	_	1.35		1.35	] V
				6	_	_	1.8	_	1.8	_	1.8	
		VIL		2	1.9	_	_	1.9	_	1.9	_	
High-Level Output Voltage	Voh	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	] V
CMOS Loads		V _{IH}	i	6	5.9	_	_	5.9		5.9	_	
TTL Loads		V _{IL} or	-4	4.5	3.98		<u> </u>	3.84	_	3.7	_	v
(Standard Output)		V _{IH}	-5.2	6	5.48		_	5.34		5.2	_	
		VIL		. 2		_	0.1	_	0.1	_	0.1	
Low-Level Output Voltage	$V_{OL}$	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	] V
CMOS Loads		V _{IH}		6	_	_	0.1	_	0.1	_	0.1	
TTL Loads		V _{IL} or	4	4.5	_		0.26		0.33	_	0.4	v
(Standard Output)		V _{IH}	5.2	6	-	_	0.26	_	0.33	_	0.4	
Input Leakage Current	lı .	V _{cc} or		6		_	±0.1	_	±1	_	±1	μΑ
	"	Gnd										ļ <b>~</b> .
		15		6	_	_	±0.5		±5	_	±5	
Quiescent Device Current	Icc	15 or Gnd	0	6	-	-	2	-	20	-	:40	μΑ

### SWITCHING CHARACTERISTICS (VCC=5 V, TA=25° C, Input $t_{\rm f}$ , $t_{\rm f}$ =6 ns)

CHARACTERISTIC		SYMBOL	54HC AND 74HC			
CHARACTERISTIC	CHARACTERISTIC			UNITS		
Propagation Delay, Data Input to Output	HC4049		6			
(C _L = 15 pF)	HC4050	TPLH, TPHL	0	ns		
Power Dissipation Capacitance*		CPD	35	pF		

* $C_{PD}$  is used to determine the dynamic power consumption, per inverter  $P_D = V_{CC}^2 f_i(C_{PD} + C_L)$  where:  $f_i = \text{input frequency}$   $C_L = \text{output load capacitance}$   $V_{CC} = \text{supply voltage}$ 

### SWITCHING CHARACTERISTICS (CL = 50 pF, Input tr,tf = 6 ns)

			25	25°C -40°C to +85°C-55°C to +125°C				+125° C	;
CHARACTERISTIC	SYMBOL	VCC	Н	IC	74	НС	54	НС	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	]
Propagation Delay	tplH, tpHL	2	_	85	T -	105	_	130	
nA to n  HC4049		4.5		. 17	_	21		26	ns
nA to nY HC4050		6	_	14	_	18	l —	22	
Transition Time	t _{TLH} , t _{THL}	2		75	_	95	_	110	1
		4.5	_	15	<u> </u>	19	_	22	ns
		6	_	13	-	-16	_	19	
Input Capacitance	Cı	_	_	10	_	10	_	10	pF

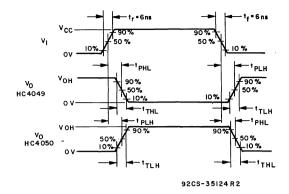
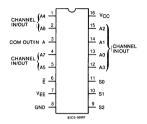


Fig. 1 - Transition times and propagation delay times, combination logic.

# **High-Speed CMOS Logic**



### CD54/74HC/HCT4051 TERMINAL ASSIGNMENT

# Analog Multiplexers/ Demultiplexers

#### Type Features:

- Wide analog input voltage range: ± 5 V max.
- Low "on" resistance: 70  $\Omega$  typ ( $V_{\text{CC}}$ - $V_{\text{EE}}$  = 4.5 V) 40  $\Omega$  typ ( $V_{\text{CC}}$ - $V_{\text{EE}}$  = 9 V)
- Low crosstalk between switches
- Fast switching and propagation speeds
- "Break-before-make" switching

The RCA CD54/74HC/HCT4051, 4052, and 4053 are digitally controlled analog switches which utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

These analog multiplexers/demultiplexers control analog voltages that may vary across the voltage supply range (i.e.  $V_{\text{CC}}$  to  $V_{\text{EE}})$ . They are bidirectional switches thus allowing any analog input to be used as an output and visa-versa. The switches have low "on" resistance and low "off" leakages. In addition, all three devices have an enable control which when, high, disables all switches to their "off" state.

The CD54HC/HCT4051, 4052, and 4053 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC/HCT 4051, 4052, and 4053 are supplied in 16-lead plastic packages (E suffix) and in 16-lead surface mount plastic packages (M suffix). All devices are also available in chip form (H suffix).

#### Family Features:

- Wide Operating Temperature Range: CD74HC/HCT: -40 to ±85° C
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:
  - 2 to 6 V Operation, control; 0 to 10 V, switch High Noise Immunity:
  - $N_{\rm IL} = 30\%$ ,  $N_{\rm IH} = 30\%$  of  $V_{\rm CC}$ ; @  $V_{\rm CC} = 5~V$
- CD54HCT/CD74HCT Types:
  - 4.5 to 5.5 V Operation, control; 0 to 10 V, switch Direct LSTTL Input Logic Compatibility
  - $V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.$
  - CMOS Input Compatibility  $I_1 \leq 1 \, \mu A \otimes V_{OL}, \, V_{OH}$

Vсс ○ 16 TG TG TG TG BINARY TO 1 OF 8 DECODER Осоммон LOGIC LEVEL CONVERSION TG WITH TG TG TG 9205-2008583  $\triangle_7$ 

Fig. 1 - Functional diagram of HC/HCT4051.

# TRUTH TABLE CD54/74HC/HCT4051

INPU	"ON"			
ENABLE	S2	S1	S0	CHANNELS
L	L	L	L	A0
L	L	L	Н	A1
L	L	Н	L	A2
L	∟	Н	H	А3
L	Η	L	L	A4
L	Τ	L	H	A5
L	Н	Н	L	A6
L	Τ	Н	Н	A7
Н	Х	Х	Х	NONE

X = Don't Care

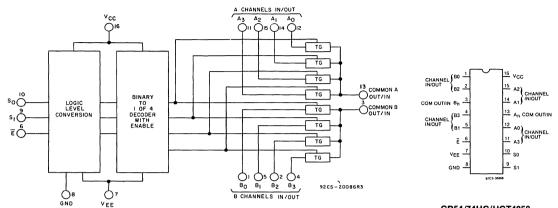


Fig. 2 - Functional diagram of HC/HCT4052.

CD54/74HC/HCT4052 TERMINAL ASSIGNMENT

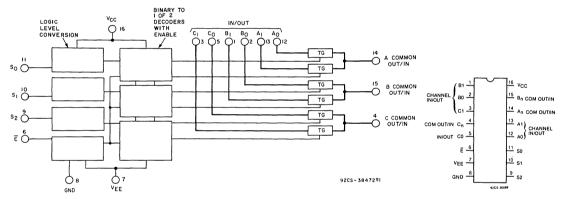


Fig. 3 - Functional diagram of HC/HCT4053.

CD54/74HC/HCT4053 TERMINAL ASSIGNMENT

#### **TRUTH TABLES (Continued)**

#### CD54/74HC/HCT4052

INPL	JT STAT		
ENABLE	S1	S0	"ON" CHANNELS
L	L	L	A0, B0
L	L	Н	A1, B1
L	Н	L	A2, B2
!	Н	Н	A3. B3
Н	Х	Х	NONE

X = Don': Care

### CD54/74HC/HCT4053

INPUT	STAT	ES		
ENABLE	S2	S1	SO	"ON" CHANNELS
L	L	L	L	A0 B0 CO
L	L	L	Н	A0 B0 C1
L	L	Н	L	A0 B1 C0
L	L	Н	Н	A0 B1 C1
L	Н	L		A1 B0 C0
L	Н	L	Н	A1 B0 C1
L	Н	Н	L	A1 B1 C0
L	Н	Н	Н	A1 B1 C1
Н	Х	Х	Х	NONE

X = Don't Care

MAXIMUM RATINGS, Absolute-Maximum Values: (All voltages referenced to Gnd unless otherwise shown)

DC SUPPLY-VOLTAGE (Vcc-Vee)	0.5 to 11 V
DC SUPPLY-VOLTAGE (Vcc-VEE) DC SUPPLY-VOLTAGE (Vcc)	0.5 to +7 V
DC SUPPLY-VOLTAGE (V _{EE} )	+0.5 to -7 V
DC INPUT DIODE CURRENT, $I_{iK}$ (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC SWITCH DIODE CURRENT, IOK (FOR Vi < VEE -0.5 V OR Vi > Vcc + 0.5 V)	±20 mA
• DC SWITCH CURRENT (FOR V _i > V _{EE} -0.5 V OR V _i < V _{CC} + 0.5 V)	+25 mA
DC V _{CC} OR GROUND CURRENT (I _{CC} )	
DC V _{EE} CURRENT (I _{EE} )	20 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125° C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C

• In certain applications, the external load-resistor current may include both V_{cc} and signal-line components. To avoid drawing V_{cc} current when switch current flows into the transmission gate inputs, the voltage drop across the bidirectional switch must not exceed 0.6 volt (calculated from R_{oN} values shown in Electrical Characteristics chart). No V_{cc} current will flow through R_L if the switch current flows into terminal 3 on the HC/HCT4051; terminals 3 and 13 on the HC/HCT4052; terminals 4, 14 and 15 on the HC/HCT4053.

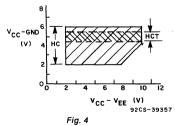
### **RECOMMENDED OPERATING CONDITIONS:**

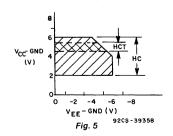
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CULADA OTERNISTIC	LIM	ITS	LINUTC
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
Supply-Voltage Range (For $T_A$ = Full Package-Temperature Range) $V_{CC}$ - $V_{EE}$ CD54/74HC Types CD54/74HCT Types See Fig. 4	2	10	V
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{EE} :*  CD54/74HC Types CD54/74HCT Types See Fig. 5	0	-6	V
DC Input Control Voltage, V ₁	Gnd	V _{cc}	V
Analog Switch I/O Voltage, V _{IS}	VEE	Vcc	V
Operating Temperature T _A : CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t, t at 2 V	0	1000	ns
at 4.5 V	. 0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

### Recommended Operating Area as a Function of Supply Voltages.





### STATIC ELECTRICAL CHARACTERISTICS

		c	D74H	C/CD5	4HC4	051,40	52,405	3						CD7	4HCT/	CD54	HCT40	51,405	2,4053	1			
		EST			l	1C/54I		741		541			TEST			1	CT/54		74H		54H		
CHAR-	CONI	DITIONS	S		ļ	TYPES		+		-	TYPES		CONDITION			TYPES			TYPES		TYPES		UNITS
ACTERISTIC	V _{is}	Vı	VEE	Vcc		+25° C		-40/ -55/ +85°C +125°C			V _{IS}			Vcc	+25°			-4 +85		-5 +12			
	٧	٧	٧	٧	Min	Тур	Max	Min	Max	Min	Max	٧	V	٧	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	_	1.5	_				4.5								
Input				4.5	3.15	_	_	3.15	_	3.15	_		ĺ		to	2	–	–	2	-	2	_	v
Voltage V _{IH}				6	4.2	_	_	4.2	_	4.2	_				5.5		<u></u>						
Low-Level				2	<u> </u>	_	0.5		0.5		0.5				4.5	l	Į.						
Input				4.5	_	_	1.35		1.35		1.35				to	-	-	0.8	-	0.8		0.8	l v
Voltage V _{IL}				6	_	_	1.8	_	1.8	_	1.8				5.5								
"On"	Vcc		0	4.5		70	160	_	200	<u> </u>	240			0	4.5		70	160	_	200	<u> </u>	240	
Resistance	or	VIL	0	6		60	140		175		210				_		_	_	<u> </u>	_	_	_	Ω
lo = 1 mA Ron	VEE	or	-4.5	4.5		40	120	_	150	_	180			-4.5	4.5		40	120		150		180	
l lan	Vcc	ViH	0	4.5	_	90	180		225		270			0	4.5		90	180	_	225	_	270	
(Fig. 15)	to	VIH	0	6		80	160		200	_	240	Same	Same							_			Ω
	VEE		-4.5	4.5		45	130	<u> </u>	162	_	195	as	as	-4.5	4.5	_	45	130	<u> </u>	162		195	
Maximum "On" Resistance			0	4.5		10	_		_	_	_	нс	HC	0	4.5		10		_	_	<u> </u>	_	
between any two channels			0	6	_	8.5		_	_	_	<u> </u>	[					_		_	_	_		Ω
ΔR _{on}			-4.5	4.5		5				_				-4.5	4.5	<u> </u>	5				_		
Switch On/Off Leakage Current I ₁₂	For Switch OFF: When V _{IS} =V _{CC} V _{OS} = V _{EE} ;	V _{IL}																					
1&2 Channels	When V _{IS} =V _{EE} ,		0	6			±0.1	_	±1	_	±1		1	0	6	-	_	±0.1	_	±1		±1	
(4053)	Vos = Vcc For Switch	or	-5	5			±0.1		±1	<u> </u>	±1			-5	5	_	_	±0.1		±1	_	±1	
4 Channels	ON:		0	6	_		±0.1	_	±1		±1		ļ	0	6	_	_	±0.1		±1		±1	μΑ
(4052)	All Applicable Combinations	ViH	-5	5		_	±0.2	_	±2	_	±2			-5	5	_	_	±0.2		±2	_	±2	"
8 Channels	of V _{IS} & V _{OS}		0	6		L-	±0.2		±2		±2			0	6			±0.2		±2	_	±2	
(4051)	Voltage Levels		-5	5			±0.4		±4		±4			-5	5		_	±0.4	_	±4	_	±4	
Control Input Leakage Current IIL	-	V _{cc} or Gnd	0	6	_	_	±0.1	-	±1	_	±1	_			5.5	-	-	±0.1	-	±1	_	±1	μΑ
Quiescent Device Current Icc	When  V _{IS} = V _{EE} ,  V _{DS} = V _{CC} ,	Vcc	0	6	_	-	8	_	80	_	160	Same	Same	0	5.5	_	-	8	-	80	_	160	
I _O = 0	When  V _{IS} = V _{CC} ,  V _{OS} = V _{EE}	or Gnd	-5	5	_	-	16	_	160	_	320	as HC	as HC	-4.5	5.5	-	_	16	-	160	_	320	μΑ
Additional Quiesecent Device Current per input pin: 1 unit load													V _{cc} -2.1		4.5 to 5.5	_	100	360	_	450	_	490	μΑ

 $^{^{\}bullet}$  For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specifications is 1.8 mA.

#### **HCT Input Loading Table**

Туре	Input	Unit Loads*
4051, 4053	All	0.5
4052	All	0.4

^{*}Unit Load is  $\Delta I_{cc}$  limit specified in Static Characteristics Chart, e.g., 360  $\mu$ A max. @ 25° C.

^{**} Any voltage between Vcc & Gnd.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, tr = 6 ns)

CHARACTERICTIC	CVMPOL	CL		LINITO					
CHARACTERISTIC	SYMBOL	рF	4051		40	52	40	53	UNITS
	*		нс	нст	нс	НСТ	нс	HCT	
Propagation Delay							-		
	t _{PHL}	15	4	4	4	4	4	4	ns
Switch IN to OUT	t _{PLH}								
Switch Turn-off (S or E)	t _{PHZ} , t _{PLZ}	15	19	19	21	21	18	18	ns
Switch Turn-on (S or $\overline{\overline{E}}$ )	t _{PZH} , t _{PZL}	15	19	23	27	29	18	20	ns
Power Dissipation Capacitance*	C _{PD}	_	50	52	74	76	38	42	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 fi + \sum (C_L + C_S) V_{CC}^2 fo$ 

fo = output frequency

f_i = input frequency.

C_L= output load capacitance.

C_s = switch capacitance

V_{cc} = supply voltage.

### SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r, t_r = 6 ns)

					<u> </u>	25	°C		-4	0°C to	5 +85°	С	-5	5°C to	+125	°C ·	
CHARACTERIST	пс	SYMBOL	VEE	Vcc	Н	С	Н	CT	74	НС	74H	ICT	54	нс	54H	НСТ	UNITS
					Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Propagation Dela	ıy,		0	2		60		_	_	75	_		_	90	_	_	
Switch In to Out		t _{PLH}	0	4.5	—	12	_	12	_	15	_	15	-	18	_	18	
		t _{PHL}	0	6	—	10		_		13		—	_	15	<b> </b> —	_	
4051, 4052, 40	)53		-4.5	4.5		8		8		10		10	_	12		12	
Maximum			0	2	—	225	l —	—	—	280	_	_	-	340		-	
Switch 4	051		0	4.5	_	45	_	45		56	_	56	_	68	_	68	
Turn "Off"			0	6	—	38			_	48	_	-		57		I -	
Delay from			-4.5	4.5		32		32		40	_	40		48		48	
S or E to		$t_{PHZ}$	0	2		250	_	_		315	_	-	_	375	l —	-	
Switch 4	052	$t_{PLZ}$	0	4.5		50		50		63	· —	63	_	75	—	75	
Output			0	6	_	43	_	—	—	54	_		_	65	—	-	
			-4.5	4.5		38		38		48	_	48		57		57	ns
	1		0	2	-	210	_	-	_	265	_	-		315	_	-	
4	050		0	4.5	-	42	_	44	_	53		55	-	63	<b> </b> -	66	
4	053		0.	6	-	36	_		_	45	-	_	-	54	l —	-	
· · · · · · · · · · · · · · · · · · ·			-4.5	4.5		29		31		36		39		44	_	47	]
Maximum			0	2	_	225	_			280	—	—	-	340	<u> </u>	- 1	
Switch 4	051		0	4.5		45		55	_	56		69	-	68	-	83	1
Turn "On"			0	6	-	38	-	-	_	48		-	_	57		-	
Delay from			-4.5	4.5	_	32		39		40		49		48		59	
S or E to		t _{PZL}	0	2		325	-	-	-	405	—	-	—	490	_	_	
	1052	$t_{PZH}$	0	4.5	_	65	_	70	-	81	<b> </b>	68	-	98	_	105	
Output			0	6	-	55				69	_	_		83	_	-	1
			-4.5	4.5		46		48		58		60		69		72	
			0	2		220	<u> </u>	_	-	275	_	<u> </u>	-	330	-		
4	1053		0	4.5	-	44	_	48	<u> </u>	55	_	60	—	66	_	72	
4	1000		0	6	_	37	-	_	-	47	_	-	-	56	-	-	
			-4.5	4.5		31		34		39		43		47		51	
Input (Control) Capacitance		Cı		_		10	_	10	_	10		10	-	10	_	10	pF

### ANALOG CHANNEL CHARACTERISTICS — TYPICAL VALUES AT TA = 25°C

CHARACTERISTIC	SYMBOL	CONDITIONS	TYPES	VEE (V)	VCC (V)	HC/HCT	UNITS
Switch Input Capacitance	Cı		All			5	
			4051			25	pF
Common Capacitance	Ссом		4052			12	ρi
			4053		ĺ	8	
			4051			145	
Minimum Switch Frequency			4052	-2.25	2.25	165	
Response @ -3 dB	1	See Fig. 6	4053			200	MHz
Figs. 11, 13, 15	f _{MAX}	Notes 1, 2	4051			180	IVITIZ
	1		4052	-4.5	4.5	185	
	ľ		4053			>200	
			4051			N/A	
Crosstalk Between			4052	-2.25	2.25	(TBE)	
Any Two Switches		See Fig. 7	4053	}	}	(TBE)	dB
Note 4		Notes 2, 3	4051			N/A	ub.
	1	140103 2, 0	4052	-4.5	4.5	(TBE)	
			4053	1		(TBE)	
Sine-Wave Distortion		See Fig. 8	All	-2.25	2.25	0.035	%
Sine-wave Distortion		See Fig. 6	All	-4.5	4.5	0.018	70
			4051	1			
E or S to Switch		1	4052	-2.25	2.25	(TBE)	
Feedthrough Noise		See Fig. 9	4053	1			mV
		Notes 2, 3	4051				] ''''
		140103 2, 0	4052	-4.5	4.5	(TBE)	
			4053		1	}	
			4051			-73	
Switch "OFF"		}	4052	-2.25	2.25	-65	
Signal Feedthrough		See Fig. 10	4053	1		-64	dB
Figs. 12, 14, 16		Notes 2, 3	4051			-75	u D
			4052	-4.5	4.5	-67	
		l	4053	1	[	-66	

#### Notes

- 1. Adjust input voltage to obtain OdBm @ Vos for fin = 1 MHz.
- 2. V_{IS} is centered at (V_{CC} V_{EE})/2.
- 3. Adjust input for OdBm.
- 4. Not applicable for HC/HCT4051.

92CS-39354

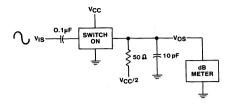


Fig. 6 - Frequency response test circuit.

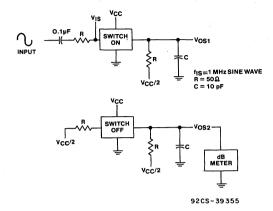


Fig. 7 - Crosstalk between two switches test circuit.

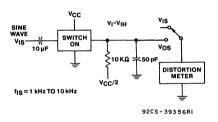


Fig. 8 - Sine wave distortion test circuit.

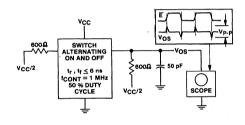


Fig. 9 - Control-to-switch feedthrough noise test circuit.

92CS-39352

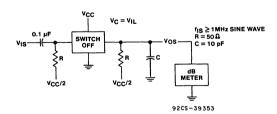
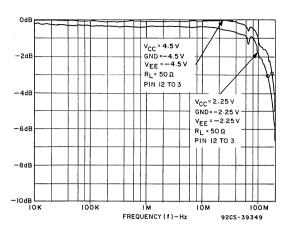


Fig. 10 - Switch off signal feedthrough.



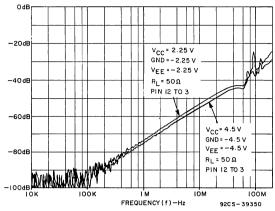


Fig. 11 - Channel on bandwidth (HC/HCT4051).

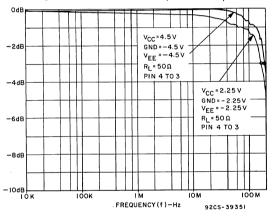


Fig. 12 - Channel off feedthrough (HC/HCT4051).

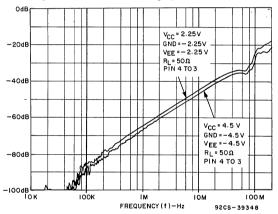


Fig. 13 - Channel on bandwidth (HC/HCT4052).

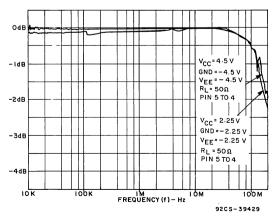


Fig. 14 - Channel off feedthrough (HC/HCT4052).

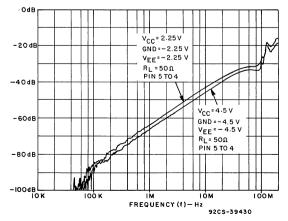


Fig. 15 - Channel on bandwidth (HC/HCT4053).

Fig. 16 - Channel off feedthrough (HC/HCT4053).

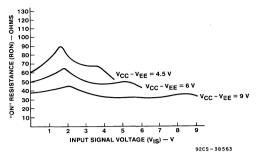
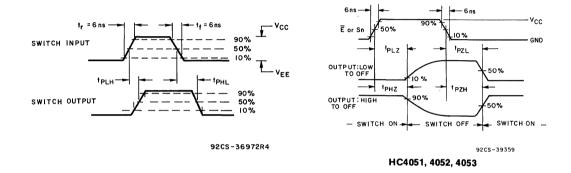
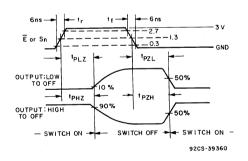


Fig. 17 - Typical ON resistance vs. input signal voltage.





HCT4051, 4052, 4053

Fig. 18 - Switch propagation delay, turn-on, turn-off times.

Fig. 19 - Switch on/off propagation delay test circuit.

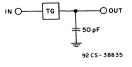
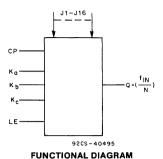


Fig. 20 - Switch In to Switch Out
Propagation delay test circuit.

# **High-Speed CMOS Logic**



# **CMOS Programmable** Divide-by-"N" Counter

#### Type Features:

- Synchronous programmable ÷ N counter: N = 3 to 9999 or 15999
- Presettable down-counter
- Fully static operation
- Mode-select control of initial decade counting function (÷ 10, 8, 5, 4, 2)
- Master preset initialization
- Latchable ÷ N output

The RCA-CD54/74HC4059 and the CD54/74HCT4059 are high-speed silicon-gate devices that are pin-compatible with the CD4059B devices of the CD4000B series. These devices are divide-by-N down-counters that can be programmed to divide an input frequency by any number "N" from 3 to 15,999. The output signal is a pulse one clock cycle wide occurring at a rate equal to the input frequency divided by N. The down-counter is preset by means of 16 jam inputs.

The three Mode-Select Inputs Ka, Kb, and Kc determine the modulus ("divide-by" number) of the first and last counting sections in accordance with the truth table shown in Table I. Every time the first (fastest) counting section goes through one cycle, it reduces by 1 the number that has been preset (jammed) into the three decades of the intermediate counting section and into the last counting section, which consists of flip-flops that are not needed for operating the first counting section. For example, in the ÷ 2 mode, only one flip-flop is needed in the first counting section. Therefore the last counting section has three flip-flops that can be preset to a maximum count of seven with a place value of thousands. If ÷ 10 is desired for the first section, Ka is set "high", Kb "high" and Kc "low". Jam inputs J1, J2, J3, and J4 are used to preset the first counting section and there is no last counting section. The intermediate counting section consists of three cascaded BCD decade (÷ 10) counters presettable by means of Jam Inputs J5 through J16.

The Mode-Select Inputs permit frequency-synthesizer channel separations of 10, 12.5, 20, 25, or 50 parts. These inputs set the maximum value of N at 9999 (when the first counting section divides by 5 or 10) or 15,999 (when the first counting section divides by 8, 4, or 2).

The three decades of the intermediate counter can be preset to a binary 15 instead of a binary 9, while their place values are still 1, 10, and 100, multiplied by the number of the ÷ N mode. For example, in the ÷ 8 mode, the number

#### **Family Features:**

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85°C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types:
  - 2 to 6 V operation High noise immunity:

  - $N_{\rm IL} = 30\%$ ,  $N_{\rm IH} = 30\%$  of  $V_{\rm CC}$ ; @  $V_{\rm CC} = 5~V$
- CD54HCT/CD74HCT types:
  - 4.5 to 5.5 V operation
  - Direct LSTTL input logic compatibility
  - $V_{IL} = 0.8 \ V \ max., \ V_{IH} = 2 \ V \ min.$
  - CMOS input compatibility  $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$

#### Applications:

- Communications digital frequency
- synthesizers: VHF, UHF, FM, AM, etc.
- Fixed or programmable frequency division
- "Time out" timer for consumer-application industrial controls
- Companion Application Note, ICAN-6374, "Application of the CMOS CD4059A Programmable Divide-by-N Counter in FM and Citizens Band Transceiver Digital Tuners"

from which counting down begins can be preset to:

3rd decade:

1500 150

2nd decade: 1st decade:

150

Last counting section 1000

The total of these numbers (2665) times 8 equals 21,320. The first counting section can be preset to 7. Therefore, 21,327 is the maximum possible count in the  $\div$  8 mode.

The highest count of the various modes is shown in the column entitled Extended Counter Range of Table I. Control inputs Kb and Kc can be used to initiate and lock the counter in the "master preset" state. In this condition the flip-flops in the counter are preset in accordance with the jam inputs and the counter remains in that state as long as Kb and Kc both remain low. The counter begins to count down from the preset state when a counting mode other than the master preset mode is selected.

The counter should always be put in the master preset mode before the ÷5 mode is selected. Whenever the master preset mode is used, control signals Kb = "low" and Kc = "low" must be applied for at least 3 full clock pulses.

After the Master Preset Mode inputs have been changed to one of the  $\div$  modes, the next positive-going clock transition changes an internal flip-flop so that the countdown can begin at the second positive-going clock transition. Thus, after an MP (Master Preset) mode, there is always one extra count before the output goes high. Fig. 1 illustrates a total count of 3 ( $\div$  8 mode). If the Master Preset mode is started two clock cycles or less before an output pulse, the output pulse will appear at the time due. If the Master Preset Mode is not used, the counter jumps back to the "Jam" count when the output pulse appears.

A "high" on the Latch Enable input will cause the counter output to remain high once an output pulse occurs, and to remain in the high state until the latch input returns to "low". If the Latch Enable is "low", the output pulse will remain high for only 1 cycle of the clock-input signal.

The CD54HC4059 and CD54HCT4059 are supplied in 24-lead dual-in-line frit-seal ceramic packages (F suffix). The CD74HC4059 and CD74HCT4059 are supplied in 24-lead dual-in-line, narrow-body plastic packages (EN suffix), in 24-lead dual-in-line, wide-body plastic packages (E suffix), and in 24-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

Table I

	Mode elec			First Co Sect	•		Last Cou Secti	•	Counter Range			
!	npu	t		3601	1011			UII	Design	Extended		
			Mode	Can be		Mode	Can be					
			Mode	preset		IVIOGE	preset					
Ka	Kb	Кc	Di-	to a	Jam∙	Di-	to a	Jam●	Max.	Max.		
			vides	max.	inputs	vides	max.	inputs				
Ĺ			by:	of:	used:	by:	of:	used:				
Н	Н	Η	2	1	J1	8	7	J2,J3,J4	15,999	17,331		
L	н	Н	4	3	J1,J2	4	. 3	J3,J4	15,999	18,663		
Н	L	Н	5#	4	J1,J2,J3	2	1	J4	9,999	13,329		
L	L	н	8	7	J1,J2,J3	2	1	J4	15,999	21,327		
Н	Н	L	10	9 J1,J2,J3,J		1	0	_	9,999	16,659		
X	L	L		Master	Preset		Master F	reset				

X = Don't Care

•J1 = Least significant bit.

J4 = Most significant bit.

#Operation in the  $\div$  5 mode (1st counting section) requires going through the Master Preset mode prior to going into the  $\div$  5 mode. At power turn-on, Kc must be "low" for a period of 3 input clock pulses after V_{CC} reaches a minimum of 3 volts.



TERMINAL ASSIGNMENT

#### How to Preset the CD54/74HC/HCT4059 to Desired ÷ N

The value N is determined as follows:

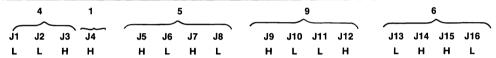
*MODE = First counting section divider (10, 8, 5, 4, or 2)

To calculate preset values for any N count, divide the N count by the Mode. The resultant is the corresponding preset values of the 5th through 2nd decade with the remainder being equal to the 1st decade value.









To verify the results, use Equation 1:

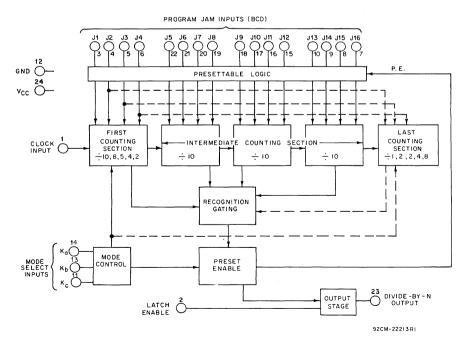


Fig. 1 - Functional block diagram.

MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, $I_{iK}$ (FOR $V_i < -0.5$ V OR $V_i > V_{CC} +0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, IOK (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V	
DC DRAIN CURRENT, PER OUTPUT (I _o ) (FOR -0.5 V $<$ V _o $<$ V _{cc} +0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT (I _{CC} )	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	
For T _A = +60 to +85° C (PACKAGE TYPE E)	
For T _A = -55 to +100°C (PACKAGE TYPE F,H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F,H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F,H	55 to +125°C
PACKAGE TYPE E,M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max.	+265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C

### **RECOMMENDED OPERATING CONDITIONS**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIF	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			ł
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	) v
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r ,t _f :			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

#### STATIC ELECTRICAL CHARACTERISTICS

				CD7	4HC4	059/C	:D54H	IC405	9			CD74HCT4059/CD54HCT4059									
CHARACTERIS		Į.	TEST IDITIO	NS	1	74HC/54HC TYPES					HC PES	TEST CONDITION	NS	74HCT/54HCT TYPES			74HCT TYPES		l	ICT PES	UNITS
		Vı		Vcc		+25° (	;	-4 +85	0/ 5° C	-5 +12		V ₁	Vcc		+25° C	;		0/ 5°C	_	5°C	UNITS
		v	mA	٧	Min	Тур	Max	Min	Max	Min	Max	٧	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	E	1.5	_	1.5	_		4.5								
Input Voltage	$V_{IH}$			4.5	3.15	_	L	3.15	_	3.15	_	-	to	2	-	-	2	–	2	-	V
		ļ		6	4.2	_	<u> </u>	4.2		4.2	_		5.5	<u> </u>							
Low-Level				2		_	0.5		0.5	_	0.5	,	4.5	ľ							
Input Voltage	VIL			4.5	_	_	1.35		1.35		1.35	_	to	-	-	0.8	-	0.8	-	0.8	V
				6	<del> </del> =	=	1.8	_	1.8		1.8		5.5	<u> </u>	<u> </u>				<u> </u>		
High-Level		VIL	l	2	1.9		<u> </u>	1.9	<u> </u>	1.9	<u> </u>	VIL									
Output Voltage	V _{он}	or	-0.02	4.5	4.4	_	<u> </u>	4.4		4.4		or	4.5	4.4	-	_	4.4	-	4.4	-	V
CMOS Loads		V _{IH}		6	5.9	_	<u> </u>	5.9	<u> </u>	5.9		V _{IH}						-		<u> </u>	
		VIL	<u> </u>	-			├—		_		<u> </u>	V _{IL}						l			
TTL Loads		or	-4	4.5	3.98		<u> </u>	3.84		3.7		or	4.5	3.98	-	_	3.84	-	3.7	-	V
<del> </del>		V _{IH}	-5.2	6	5.48	_	ΙΞ.	5.34	_	5.2	_	V _{IH}		├	_		-				
Low-Level		VIL		2		ļ=	0.1	<u> </u>	0.1	_	0.1	V _{IL}		}	1	١		١	ļ		
Output Voltage	Vol	or	0.02	4.5	-	_	0.1	_	0.1		0.1	or	4.5	-	-	0.1	_	0.1	-	0.1	V
CMOS Loads		V _{IH}	<del> </del>	6_	=	-	0.1	_	0.1	-	0.1	ViH		├—		-		-		-	
TTI Lords		VIL	<del></del>	4.5		-	0.00	├	0.00	<del> </del>	-	V _{IL}		ļ		0.00			Į	0.4	v
TTL Loads		or	5.2	4.5	=	=	0.26	=	0.33	=	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	v
Input Leakage		V _{IH}	5.2	6		-	0.26		0.33		0.4	VIH		-			<del>                                     </del>			-	
Input Leakage Current	lı .	Vcc				1						Any Voltage									
Guirent	"	or		6	-	-	±0.1	-	±1	-	±1	Between	5.5	-	-	±0.1	-	±1	-	±1	μΑ
		Gnd										V _{cc} & Gnd		}							
Quiescent		Vcc	<u> </u>	-	-	$\vdash$	$\vdash$	<u> </u>		<del>                                     </del>	-	Vcc & Grid		$\vdash$		<u> </u>	<del>                                     </del>	<u> </u>	<del>                                     </del>		
Device Current	lcc	or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μA
		Gnd	•	-			-					Gnd									-
Additional																					
Quiescent Device													4.5	1							
Current per input												V _{cc} -2.1	to	-	100	360	i –	450	-	490	μA
pin: 1 unit load	Δlcc*												5.5	1							

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads*
All J Inputs	0.5
CP	0.65
LE	1.65
Ka	1
Kb -	1.5
Kc	0.85

^{*}Unit Load is  $\Delta I_{cc}$  limit specified in Static Characteristics Chart, e.g., 360  $\mu A$  max. @ 25° C.

### SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25°C, Input t_r,t_i=6 ns)

			TYPICAL	LVALUES	
CHARACTERISTIC		C _L (pF)	нс	HCT	UNITS
Propagation Delay:	t _{PLH}	15	17	10	
CP to Q	t _{PHL}	15	17	19	
LE to Q		7	14	19	ns ns
CP Frequency	f _{MAX}	15	54	50	MHz
Power Dissipation Capacitance*	C _{PD}		36	36	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 f_i + \sum C_L V_{CC}^2 f_o$  where  $f_i$  = input frequency

fo = output frequency

C_L = output load capacitance

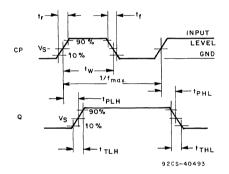
V_{CC} = supply voltage.

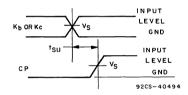
### PRE-REQUISITE FOR SWITCHING FUNCTION

			LIMITS												
		TEST		25	°C		-4	0°C t	o +85°	,C	-5				
CHARACTERIS	STIC	CONDITIONS	нс		HCT		74HC		74HCT		54HC		54HCT		UNITS
		V _{cc} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Pulse Width	tw	2	90	_	_		115	_	_	_	135	_	_	_	
CP		4.5	18	—	20	l —	23	—	25	—	27	_	30	—	
		6	15	_	_	_	20	—	—		23	_	—	<b> </b> —	۱
Setup Time	tsu	2	75	_	_	_	95	_	_	_	110	_	_	_	ns
Kb, Kc to CP		4.5	15	—	15	—	19	_	19	—	22	_	22	_	1
		6	13	—	_	—	16	_	_	—	19	<u> </u>	—	—	
CP Frequency	f _{MAX}	2	5	_	_	_	4	_	_	_	4	_	_	_	
		4.5	27	—	25	—	22	_ ·	20	—	18	—	17	-	MHz
		6	32	—	l —	-	26	—	—	_	21	—	l —	_	l

### SWITCHING CHARACTERISTICS (CL=50 pF, Input tr,tr=6 ns)

				LIMITS											
				25°C -40°C to +85°C -55°C to +125°C								°C			
CHARACTERIS	STIC	Vcc	нс нст			74HC 74HCT				54	HC	54H	ICT	UNITS	
		(V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	I	200		T-	<b>—</b>	250	_	_	_	300	I -	-	
	t _{PHL}	4.5	l —	40	_	46	_	50	—	58	—	60	_	69	
CP to Q		6	—	34	—		—	43	—	] —	_	51	—	-	
		2	_	175	_	_	_	220	_	_	_	265		_	
LE to Q		4.5		35	—	46	_	44	—	58	<u> </u>	53	—	69	ns
		6	-	30	l —	—	l —	37	l —	_	_	45	_	l —	Ì
Output Transition	t _{TLH}	2	_	75		_	_	95	_	_		110	-		1
Time	t _{THL}	4.5	_	15	-	15	_	19	<b> </b>	19	_	22	_	22	1
		6	-	13	—	—	-	16	—	—		19	—	—	
Input Capacitance	Cı		T -	10	T —	10	_	10	_	10	_	10	_	10	pF

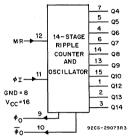




	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage Vs	50% Vcc	1.3 V

Fig. 2 - Transition times, propagation delay times, and setup times.

# **High-Speed CMOS Logic**



# 14-Stage Binary Counter with Oscillator

#### Type Features:

- Onboard oscillator
- Common reset
- Negative edge clocking
- Typical f_{MAX} = 50 MHz @ V_{CC} = 5 V, C_L = 15 pF, T_A = 25° C

#### **FUNCTIONAL DIAGRAM**

The RCA-CD54/74HC4060 and CD54/74HCT4060 each consists of an oscillator section and 14 ripple-carry binary counter stages. The oscillator configuration allows design of either RC or crystal oscillator circuits. A Master Reset input is provided which resets the counter to the all-0's state and disables the oscillator. A high level on the MR line accomplishes the reset function. All counter stages are master-slave flip-flops. The state of the counter is advanced one step in binary order on the negative transition of  $\phi_1$  (and  $\phi_0$ ). All inputs and outputs are buffered. Schmitt trigger action on the input-pulse line permits unlimited rise and fall times.

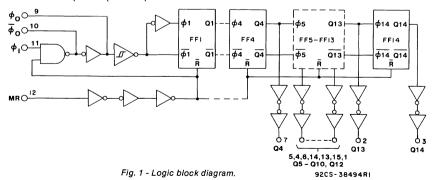
In order to achieve a symmetrical waveform in the oscillator section the HCT4060 input pulse switchpoints are the same as in the HC4060; only the MR input in the HCT4060 has TTL switching levels.

The CD54HC4060 and CD54HCT4060 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4060 and CD74HCT4060 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

#### **Family Features:**

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity:
  - $N_{\rm IL}$  = 30%,  $N_{\rm IH}$  = 30% of  $V_{\rm CC}$ ; @  $V_{\rm CC}$  = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility

 $V_{\rm IL}$  = 0.8 V Max.,  $V_{\rm IH}$  = 2 V Min. CMOS Input Compatibility  $I_{\rm I} \le 1~\mu A~@~V_{\rm OL},~V_{\rm OH}$ 



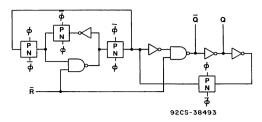


Fig. 2 - Flip-flop detail.

### **TRUTH TABLE**

φ _I	MR	OUTPUT STATE
	L	No Change
~	L	Advance to Next State
Х	Н	All Outputs are Low

H = high level (steady state)

L = low level (steady state)

X = don't care

#### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
DC INPUT DIODE CURRENT, $I_{i\kappa}$ (FOR $V_i < -0.5$ V OR $V_i > V_{cc} +0.5$ V) .	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5	v)±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V	)±25 mA
DC Vcc OR GROUND CURRENT, (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (Pb):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E. M	
STORAGE TEMPERATURE (Tatg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79$ mm) from case for 10 s max.	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

### **RECOMMENDED OPERATING CONDITIONS:**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

OHADAGTEDIGTIG	LIN	AITS	LINUTO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	.,
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{CC}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

### STATIC ELECTRICAL CHARACTERISTICS

		CI	D74H0	<b>24060</b>	CD5	4HC40	060						CD7	4HC	Г4060,	CD5	4НСТ	4060	_	
CHARACTERISTIC	1	TEST			74HC/54HC TYPES			74HC TYPE		HC PE	TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPE		54HCT TYPE		UNITS
	V ₁	Io	<b>v</b> _{cc}		+25° C	;	1 '	10/ 5°C	-5 +12	55/ 5°C	V _I	<b>v</b> _{cc}		+25° C		-40/ +85° C		1		
	\ \	m <b>A</b>	٧	Min	Тур	Max	Min	Max	Min	Max	٧	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5		_	1.5	_	1.5	_		4.5								
Input Voltage VIH			4.5	3.15	_		3.15	_	3.15	_	-	to	2	_	-	2	-	2	-	٧
			6	4.2	_	_	4.2	_	4.2	_		5.5								
Low-Level	1		2		_	0.5	_	0.5	_	0.5		4.5						İ		
Input Voltage VIL			4.5	_	_	1.35	_	1.35	_	1.35	_	to	-	-	0.8	-	0.8	-	0.8	٧
			6	_	_	1.8	_	1.8	_	1.8		5.5						L.		
High-Level	VIL		2	1.9	_		1.9	_	1.9	_	٧,٢ ٠٠									
Output Voltage Q Outputs Vон	or	-0.02	4.5	4.4	_	_	4.4	_	4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	V
CMOS Loads	V _{IH}		6	5.9	_	_	5.9	_	5.9		V _{IH}									
High-Level Output Voltage Vou	VIL										٧,٢ **									
Q Outputs	or	-4	4.5	3.98	_	_	3.84	_	3.7		or	4.5	3.98	_	-	3.84	-	3.7	-	v
TTL Loads	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2		V _{IH}									
Low-Level	VIL		2			0.1	_	0.1		0.1	٧,٢٠٠									
Output Voltage Q Outputs Vol	or	0.02	4.5	_		0.1	_	0.1	_	0.1	or	4.5	-	_	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	=	_	0.1	_	0.1	_	0.1	V _{IH}									
Low-Level	VIL										V _{IL} ···									
Output Voltage Vol. Q Outputs	or	4	4.5	_	_	0.26	_	0.33	-	0.4	or	4.5	-	_	0.26	-	0.33	-	0.4	V
TTL Loads	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	VIH									

^{**}For Pin 11 V_{IH}=3.15 V, V_{IL}=0.9 V.

### STATIC ELECTRICAL CHARACTERISTICS (Cont'd)

		CI	D74HC	4060,	CD54	4HC40	)60						CD7	4HC	T4060,	CD5	4HCT	4060			
CHARACTERISTIC	co	TEST NDITIONS			IC/54		74I TYI	HC PE	54I TYI	HC PE	TEST			74HCT/54HCT TYPES		74F TYI	HCT PE	54ł TY	ICT PE	UNITS	
	V _i	lo	<b>v</b> _{cc}		+25° C	;		ю/ 5° С	-5 +12	5/ 5°C	V _i	<b>v</b> _{cc}	+25° C		;	1	10/ 5°C	l '	55/ 5°C		
	v	mA	\ \	Min	Тур	Max	Min	Max	Min	Max	٧	V	Min	Тур	Max	Min	Max	Min	Max		
High-Level	Vcc		2	1.9	_		1.9	_	1.9		Vcc										
Output Voltage Vон Фо Output (Pin 10)	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	-	4.4	_	4.4	_	v	
CMOS Loads	Gnd		6	5.9	_	-	5.9	-	5.9	_	Gnd										
High-Level	Vcc										Vcc										
ΦO Output (Pin 10)	or	-2.6	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v	
TTL Loads 💠	Gnd	-3.3	6	5.48	_	_	5.34		5.2	_	Gnd										
Low-Level	Vcc		2	-	_	0.1	-	0.1	_	0.1	Vcc										
Output Voltage Vo∟	or	0.02	4.5	-	_	0.1	_	0.1	_	0.1	or	4.5	_	_	0.1	_	0.1	_	0.1	v	
CMOS Loads	Gnd		6	_	_	0.1	_	0.1	_	0.1	Gnd			1							
Low-Level	Vcc										Vcc										
Output Voltage Vo∟	or	2.6	4.5	-	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v	
TTL Loads	Gnd	3.3	6	_	_	0.26	-	0.33	_	0.4	Gnd										
High-Level	V _{IL}										V _{IL} ••										
Output Voltage Vон Ф O Output (Pin 9)	or	-3.2	4.5	3.98	_	_	3.84	-	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v	
TTL Loads	VIH	-4.2	6	5.48	_	_	5.34	_	5.2	_	VIH										
Low-Level	VIL										٧١٢ ٠٠										
Output Voltage Vol.  ## Output (Pin 9)	or	3.2	4.5		_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	-	0.4	v	
TTL Loads	VIH	4.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}										
Input Leakage	V _{CC}										Any Voltage										
Current I	or		6	_	_	±0.1	_	±1	_	±1	between V _C C	5.5	_	_	±0.1	_	±1	_	±1	μΑ	
,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,	Gnd										& Gnd										
Quiescent	V _{CC}										V _{CC}										
Device	or	0	6	_	_	8	_	80	_	160	or	5.5	_		8	_	80	_	160	μΑ	
Current Icc	Gnd										Gnd										
Additional												4.5									
Quiescent											V _{CC} -2.1	to	_	100	360	-	450	-	490	μA	
Device Current		(	l									5.5									
per input pin: 1 unit load Δlcc*														1							
i unit load Alcc	1			1	L	L		L				l			I	1	1	ı			

^{*}For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

### **HCT INPUT LOADING**

INPUT	UNIT LOADS*
MR	0.35

^{*}Unit load is  $\Delta$  I_{CC} limit specified in Static Characteristics Chart, e.g., 360  $\mu$ A max. @ 25° C.



**TERMINAL ASSIGNMENT** 

^{**}Pin II V_{IL} = 0.9V, V_{IH} = 3.15V

[♦]Limits not valid when pin 12 (instead of pin 11) is used as control input.

### SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25°C, Input t, t_f=6 ns)

CHARACTERISTIC			Ту	pical	UNITS
CHARACTERISTIC		C∟ pF	нс	нст	UNITS
Propagation Delay $\phi_1$ to Q4	tpLH tpHL	15	25	25	ns
Propagation Delay Qn to Qn+1	tpLH tpHL	15	6	6	ns
Propagation Delay MR to Qn Output	tpHL	15	14	17	ns
Propagation Dissipation Capacitance*	C _{PD}	_	40	40	pF

 $C_{\mbox{\scriptsize PD}}$  is used to determine the dynamic power consumption, per package.

PD =  $C_{PD} V_{CC}^2 f_1 + \Sigma (C_L V_{CC}^2 f_1/M)$  where:  $M = 2^1, 2^2, 2^3, ... 2^{14}$ 

C_L = output load capacitance

fi = input frequency

#### **Prerequisite for Switching Function**

				25	°C			-40°C t	o +85° C	;		-55° C to	+125°	2	
CHARACTERISTIC	SYMBOL	V _{CC}	н	С	н	ст	741	нс	741	1CT	54	нс	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Maximum Input Pulse		2	6	_	_	_	5	_	-	_	4	_	_	_	
Frequency	t _{MAX}	4.5	30	-	30	_	25	_	25	-	20	-	20	_	MHZ
	1	6	35	_	_	_	29	_	-	_	23	_	_		
Input Pulse Width	t _W	2	80	_	_	_	100	_	_	_	120	_	_	_	
(Figure 4)		4.5	16	-	16	_	20	_	20	_	24	_	24	-	ns
		6	14		_	_	17	_	_		20		_		
Reset Removal Time	t _{REM}	2	100		_	_	125	_	_	_	150	_	_	_	
(Figure 5)		4.5	20	_	26	-	25	_	33	_	30	_	39		ns
		6	17	_	-	-	21		_	_	26	<u> </u>	-	<u> </u>	
Reset Pulse Width	t _W	2	80	_	_	_	100	_	_	_	120	_	_	_	
(Figure 5)		4.5	16	_	25	-	20	-	31	_	24	-	38	_	ns
	1	6	14	_	_	-	17	_	_	_	20	-	_	_	

#### SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_s, t₁ = 6ns)

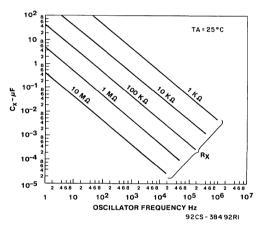
						25°C				-40°C to +85°C				-55°C to +125°C			
CHARACTERISTIC	SYMBOL	<b>v</b> _{cc}	н	С	н	т	741	нс	741	ЮТ	54	нс	54F	СТ	UNITS		
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.			
Propagation Delay	t _{PLH}	2	_	300	_	_	_	375	_	_	_	450	_	_			
φ ₁ to Q ₄	t _{PHL}	4.5	-	60	_	66	_	75	_	83	_	90	-	100	ns		
(Figure 4)	_	6	-	51				64			_	78	_	-			
Propagation Delay	t _{PLH}	2	_	80	_	_	_	100	_	_	_	120	_	_			
Q _n to Q _{n+1}	t _{PHL}	4.5	-	16	-	16	_	20	_	20	_	24	_	24	ns		
(Figure 4)	_	6	-	14	_	_	_	17	l – .			20					
Propagation Delay	t _{PHL}	2	-	175	_	_	_	220	_	_	_	265	_	_			
MR to Q _n	ļ	4.5	_	35	–	44	_	44	_	55	_	53	-	66	ns		
(Figure 5)		6		30				37	_	_		45		_	<u> </u>		
Output Transition	t _{TLH}	2	_	75	_	_	_	95		-	_	110	_	_			
Time	t _{THL}	4.5	-	15		15	_	19	-	19	_	22	_	22	ns		
(Figure 4)		6		13	_			16		_		19	-	_			
Input Capacitance	Ci.																

*TBD

#### TYPICAL LIMIT VALUES FOR Rx AND Cx

CHARACTERISTIC	TEST CONDITIONS	VOLTAGE	TYPICAL MAXIMUM LIMITS
R _x Min.	C _x > 1000 pF	2	
	C _x > 10 pF	4.5	1 ΚΩ
	C _x > 10 pF	6	
R _x Max.	C _x > 10 pF	2	
	C _x > 10 pF	4.5	20 ΜΩ
	$C_x > 10 pF$	6	
C _x Min.	$R_X > 10 \text{ K}\Omega$	2	
	$R_X > 10 \text{ K}\Omega$	4.5	10 pF
	$R_X > 10 \text{ K}\Omega$	6	
	R _x = 1 KΩ	2	1000 pF
	R _x = 1 KΩ	4.5	10 pF
	R _x = 1 KΩ	6	10 pF
Maximum Astable	C _x = 1000 pF, R _x = 1 KΩ	2	0.5 MHz*
Oscillator Frequency	$C_x = 100 \text{ pF}, R_x = 1 \text{ K}\Omega$	4.5	3 MHz*
	$C_x = 100 \text{ pF}, R_x = 1 \text{ K}\Omega$	6	3 MHz*

^{*}At very high frequencies f = 1/2.2 R_xC_x no longer gives an accurate approximation.



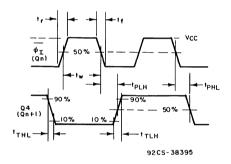


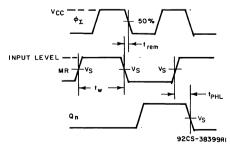
Fig. 4 - Input pulse pre-requisite times, propagation delays and output transition times for both HC and HCT types.

OSC FREQUENCY  $\approx$  1/2.2 R_XC_X

FOR 1 M  $\Omega >$  R  $_{\mbox{\scriptsize X}} >$  1 K  $\Omega_{\mbox{\scriptsize ,}}$ 

 $C_{\chi}$  >10 pF, f < 1 MHZ

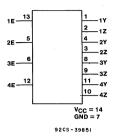
Fig. 3 - Frequency of on-board oscillator as a function of C_X and R_X.



L	54/74HC	54/74HCT
MR Input Level	VCC	3 V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 5 - Master Reset pre-requisite and propagation delays.

# **High-Speed CMOS Logic**



### **Quad Bilateral Switch**

#### **Type Features:**

- Wide analog-input-voltage range: 0-10 V
- Low "ON" resistance: 25 Ω @ V_{CC} = 4.5 V
   15 Ω @ V_{CC} = 9 V
- Fast switching and propagation delay times
- Low "OFF" leakage current

#### **FUNCTIONAL DIAGRAM**

The RCA CD54/74 HC/HCT4066 contains four independent digitally controlled analog switches that use silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

These switches feature the characteristic linear "ON"-resistance of the metal-gate CD4066B. Each switch is turned on by a high-level voltage on its control input.

The CD54HC4066 and CD54HCT4066 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4066 and CD74HCT4066 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

### **Family Features:**

- Alternate Source: Philips/Signetics
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- CD54HC/CD74HC types: 2 V to 10 V operation High noise immunity:
  - N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V & 10 V
- CD54HCT/CD74HCT types: Direct LSTTL input logic compatibility
  - $V_{\rm IL} = 0.8 \text{ V Max.}, V_{\rm IH} = 2 \text{ V Min.}$
  - CMOS input compatiblity  $I_1 \le 1 \mu A \otimes V_{OL}$ ,  $V_{OH}$

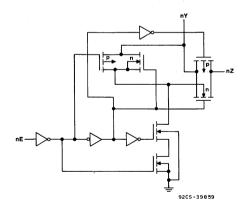


Fig. 1 - Logic diagram (one switch).

#### TRUTH TABLE

INPUT nE	SWITCH
L.	off
Н	on

H = HIGH Level

L = LOW Level

#### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	
HCT Types	0.5 to +7 V
HC Types	0.5 to +10.5 V
DC INPUT DIODE CURRENT, $I_{ik}$ (FOR $V_i < -0.5 \text{ V OR } V_i > V_{cc} + 0.5 \text{ V}$ )	
DC SWITCH DIODE CURRENT, $I_{OK}$ (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	
ullet DC SWITCH CURRENT, Io, (FOR V _I $>$ -0.5 V OR V _I $<$ V _{CC} + 0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT (I _{CC} )	±50 mA
POWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (T _{stg} )	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

• In certain applications, the external load-resistor current may include both V_{CC} and signal-line components. To avoid drawing V_{CC} current when switch current flows into the transmission gate inputs, (terminals 1, 4, 8 and 11) the voltage drop across the bidirectional switch must not exceed 0.6 volt (calculated from R_{on} values shown in the Electrical Characteristics Chart). No V_{CC} current will flow through R_L if the switch current flows into terminals 2, 3, 9 and 10.



**TERMINAL ASSIGNMENT** 

RECOMMENDED OPERATING CONDITIONS: For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

01101000000	LIN		
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*			
CD54/74HC Types	2	10	
CD54/74HCT Types	4.5	5.5	l v
DC Input Voltage, V _c , and Analog Switch Voltage, V _{I/O}	0	Vcc	
Operating Temperature T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f (Control Inputs)		1	-
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 9 V	0	250	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

### STATIC ELECTRICAL CHARACTERISTICS

Characteristic   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Control   Type   Type   Control   Type   Control   Type   Control   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Typ	
From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From   From	UNITS
High-Level Input Voltage ViH — — — — — — — — — — — — — — — — — — —	
Input Voltage   Vih	
Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set   Set	
Low-Level   Input Voltage   Vil.	
Input Voltage   Vil.       4.5       1.35     1.35     1.35     1.35     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7     2.7	V
Input Leakage	'
Input Leakage Current (Any Control)   IIL   Or Gnd   Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or Gnd   Or G	ĺ
Current (Any Control) I _{IL} or Gnd	<u> </u>
Off-Switch   Leakage   Vil.   Or   Gnd   Or   Gnd   Or   Gnd   Or   Gnd   Or   Or   Or   Or   Or   Or   Or   O	μΑ
Leakage Current         V _{IL} or Gnd         V _I or Gnd         10 or Gnd	1
Current         Iz         Gnd         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c         c <th< td=""><td></td></th<>	
"On" Resistance   Vcc   Vcc   Gnd   G   Fig.   Vcc   A.5   C   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.5   B.	l
Resistance lo = 1 mA (Fig. 2)	<del> </del>
September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   September   Sep	1
(Fig. 2) R _{on} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V _{cc} V	1
V _{CC} to Gnd         6         -         24         84         -         105         -         126         V _{CC} to Gnd         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         - </td <td>- </td>	-
Gnd   9   -   16   70   -   88   -   105     Gnd   -   -   -   -   -   -   -   -   -	Ω
"On" Resistance Between Any Two Switches $\Delta R_{on}$	- ''
Between Any Two         Vcc         -         6         -         0.75         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -         -	1
Switches         ΔR _{on} 9         — 0.5         — — — — — — —	1
	1
Quiescent   V _{cc}     6   -   -   2   -   20   -   40   V _{cc}	<del>                                     </del>
Device   Or   -   10   -   16   -   160   -   320   Or   -   5.5   -   -   2   -   20   -   40	1
Current lcc   Gnd	
Additional and and and and and and and and and and	1
Quiescent Device 4.5	μA
Current per 100 360 - 450 - 49	1
Input Pin:	
1 Unit Load $\Delta l_{cc}$	

 $^{^{\}star}$  For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads *
All	1

^{*} Unit load is  $\Delta I_{CC}$  limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

### SWITCHING CHARACTERISTICS (V_{CC} = 5 V, T_A = 25°C, Input t_r, t_f = 6 ns)

CHARACTERISTIC				TYPI	UNITS	
CHARACTERISTIC		C∟ pF	нс	нст	J. Gians	
Propag	Propagation Delay Time:  Switch In to Out  Switch Turn Off		15	4	4	
			15	4	4	
: 			15	12	14	ns ns
	Switch Turn On	t _{PZH} , t _{PZL}	15	8	9	
Power	Power Dissipation Capacitance* C _{PD}		_	25	38	pF

* C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 f_i + \Sigma (C_L + C_S) V_{CC}^2 f_o$  where:  $f_i = input$  frequency

C_L = load capacitance V_{cc} = supply voltage

fo = output frequency

Cs = switch capacitance

### SWITCHING CHAARACTERISTICS (CL = 50 pF, Input tr, tr = 6 ns)

CHARACTERISTIC				25	°C		-4	0°C to	o +85°	,C	-55	5°C to	+125	°C	
		Vcc	н	С	н	СТ	74	нс	74F	ICT	54	нс	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay Time	t _{PLH}	2	_	60	_	_	_	75	_	_	_	90	_	_	
Switch In to Out	t _{PHL}	4.5	-	12	_	12	-	15	_	15	—	18	—	18	
		9		8	_		_	11		<u> </u>	-	13	_	<u> </u>	
Switch Turn On Delay	t _{PZH}	2	_	100	_	-	_	125	_	_	-	150	-	_	
	t _{PZL}	4.5	-	20	—	24	—	25	-	30	—	30		36	ns
		9		12			_	15		_	<u> </u>	18	_	<u> </u>	
Switch Turn Off Delay		2	_	150	_	-	_	190	_	l –	—	225	—	_	
	$t_{\text{PHZ}},t_{\text{PLZ}}$	4.5	—	30	—	35	_	38	-	44	—	45	—	53	ł
		9	L-	24	_			30				36			
Input (Control) Capacitance	Cı	_		10	_	10	_	10	_	10	_	10	_	10	pF

ANALOG CHANNEL CHARACTERISTICS - Typical Values at Tc = 25°C

CHARACTERISTIC	TEST C	CONDITIONS	V _{cc} V	нс	нст	UNITS
Switch Frequency Response Bandwidth	Fig. 3		4.5	200	200	MHz
at -3 dB (Fig. 12)	Notes 1	& 2				
Cross Talk Between Any Two Switches	Fig. 4		4.5	70	70	40
(Fig. 13)	Notes 2	& 3	4.5	-72	-72	dB
Total Harmonic Distortion	1 KHz,	V _{IS} = 4 Vpp	4.5	0.022	0.023	.,
	Fig. 5	V _{IS} = 8 Vpp	9	0.008	N/A	
Control to Switch Feedthrough	Fig. 6		4.5	TBE	TBE	
Noise		_	9	TBE	TBE	mV
Switch "OFF" Signal Feedthrough	Fig. 7		4.5	70	70	45
(Fig. 13)	Notes 2 & 3		4.5	-72	-72	dB
Switch Input Capacitance Cs				5	5	pF

Notes: 1. Adjust input level for 0 dBm at output, f = 1 MHz.

- 2. V_{IS} is centered at V_{CC}/₂.
- 3. Adjust input for 0 dBm at Vis.

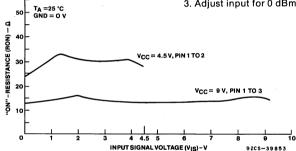


Fig. 2 - Typical "ON" resistance vs. input signal voltage.

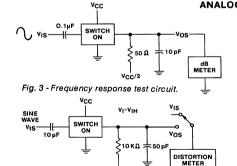


Fig. 5 - Total harmonic distortion test circuit.

fis = 1 kHz TO 10 kHz

Vcc/2

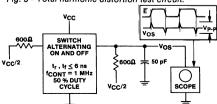


Fig. 6 - Control-to-switch feedthrough noise test circuit.

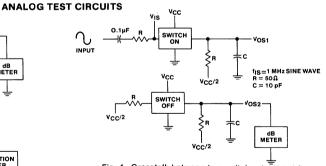


Fig. 4 - Crosstalk between two switches test circuit.

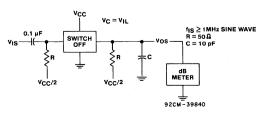
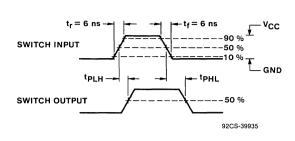


Fig. 7 - Switch off signal feedthrough.

 $t_f = 6 \text{ ns}$ 



INPUT LEVEL = 90 % Vs Е -10 % tPZL t_{PLZ} OUTPUT ---50 % LOW TO OFF tPZH - 90 % OUTPUT ---50 % HIGH TO OFF SWITCH ON ----SWITCH OFF-SWITCH ON 9205-39936

Fig. 8 - Switch propagation - delay times waveforms.

Fig. 9 - Switch turn-on and turn-off propagation delay times waveforms.

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, V _s	50% V _{CC}	1.3 V

 $t_r = 6 \text{ ns}$ 

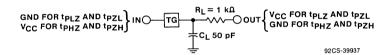


Fig. 10 - Switch on/off propagation delay time test circuit.

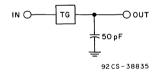


Fig. 11 - Switch-in to switch-out propagation delay time test circuit.

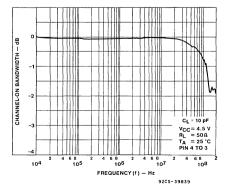


Fig. 12 - Switch frequency response,  $V_{CC}$  = 4.5 V.

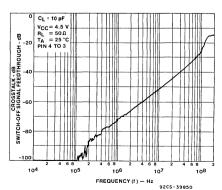
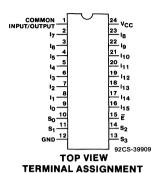


Fig. 13 - Switch-off signal feedthrough and crosstalk vs. frequency,  $V_{\rm CC}$  = 4.5 V.

Advance Information/ Preliminary Data

# **High-Speed CMOS Logic**



# 16-Channel Analog Multiplexer/Demultiplexer

#### Type Features:

- Wide analog input voltage range:
- Low "on" resistance:  $70 \Omega \text{ typ } (V_{CC} = 4.5V)$  $60 \Omega \text{ typ } (V_{CC} = 6V)$
- Fast switching and propagation speeds
- "Break-before-make" switching: (6 ns typ @ 4.5V)
- Available in both narrow and wide-body plastic packages

The RCA-CD54/74HC/HCT4067 are digitally controlled analog switches which utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL with the low power consumption of standard CMOS integrated circuits.

These analog multiplexers/demultiplexers control analog voltages that may vary across the voltage supply range. They are bidirectional switches thus allowing any analog input to be used as an output and visa-versa. The switches have low "on" resistance and low "off" leakages. In addition, these devices have an enable control which when high will disable all switches to their "off" state.

The CD54HC4067 and CD54HCT4067 are supplied in 24-lead dual-in-line frit-seal ceramic packages (F suffix). The CD74HC4067 and CD74HCT4067 are supplied in 24-lead dual-in-line, narrow-body plastic packages (EN suffix), in 24-lead dual-in-line, wide-body plastic packages (E suffix), and in 24-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

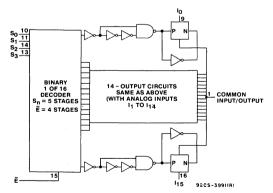


Fig. 1 - Functional diagram.

#### Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54/74HC Types: 2 to 6 V Operation High Noise Immunity:
  - $N_{\rm IL}$  = 30%,  $N_{\rm IH}$  = 30% of  $V_{\rm CC}$ ; @  $V_{\rm CC}$  = 5V
- CD54/74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I₁ ≤ 1 µA @ V_{OL}, V_{OH}

#### TRUTH TABLE

SO	S1	S2	<b>S</b> 3	Ē	Selected Channel
X 0 1 0	X 0 0	X 0 0	X 0 0 0	1 0 0 0	None 0 1 2
1 0 1 0	1 0 0 1	0 1 1	0 0 0 0	0 0 0	3 4 5 6
1 0 1 0	1 0 0 1	1 0 0 0	0 1 1 1	0 0 0 0	7 8 9 10 11
0 1 0 1	0 0 1 1	1 1 1	1 1 1	0000	12 13 14 15

- 1 = High Level
- 0 = Low Level
- X = Don't Care.

#### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, $I_{IK}$ (FOR $V_i$ $<$ -0.5 V OR $V_i$ $>$ $V_{CC}$ +0.5V) $\hdots$	±20mA
DC OUTPUT DIODE CURRENT, $I_{OK}$ (FOR $V_o$ < -0.5 V OR $V_o$ > $V_{CC}$ +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o ) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC Vcc OR GROUND CURRENT (Icc)	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	-40 to +85°C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

#### **RECOMMENDED OPERATING CONDITIONS:**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	UNITS		
CHARACTERISTIC	MIN.	MAX.	UNITS	
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*				
CD54/74HC Types	2	6	V	
CD54/74HCT Types	4.5	5.5	V	
DC Input or Output Voltage V _{IN} , V _{OUT}	0	V _{CC}	٧	
Operating Temperature T _A :				
CD74 Types	-40	+85	°C	
CD54 Types	-55	+125	°C	
Input Rise and Fall Times t _r , t _f (Control Inputs)				
at 2 V	0	1000		
at 4.5 V	0	500	ns	
at 6 V	0	400		

^{*}Unless otherwise specified, all voltages are referenced to Ground.

#### STATIC ELECTRICAL CHARACTERISTICS

		- (	CD74	HC/C	D54H	C4067	,					CE	74HC	T/CE	54HC	CT406	7			
CHARACTERISTIC	TEST CONDITIONS		1	IC/54 TYPES		1	HC PE		HC PE	TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPE		54HCT TYPE		UNITS	
CHARACTERISTIC	LOGIC V _i V	SWITCH V _{IS}	V _{cc}	/ _{cc} +25		+25° C		-40/ +85°C		-55/ +125° C	LOGIC S	SWITCH V _{IS}	+25° C		;	-40/ +85° C		-55/ +125°C		Johns
			ľ	Min	Тур	Max	Min	Max	Min	Max	`	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	-	1.5	-	1.5	-										
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	-	_	2	-	_	2	-	2	-	
			6	4.2	_	_	4.2	_	4.2	_										
Low-Level			2	_		0.5	_	0.5	_	0.5										٧
Input Voltage V _{IL}		1	4.5	_	_	1.35	_	1.35	_	1.35	-	-	-	-	8.0	-	0.8	-	0.8	
			6	_	_	1.8	_	1.8	_	1.8										
Maximum "On"	V _{cc} or	V _{cc}	4.5	_	70	160	-	200	_	240	V _{cc}	V _{cc}	_	70	160	_	200	_	240	
Resistance R _{on}	Gnd	Gnd	6	_	60	140		175	_	210	Gnd	Gnd	_	_	_	_	_	_	_	
I _o = ImA	V _{cc}	V _{cc}	4.5	_	90	180	_	225	_	270	V _{cc} to	V _{cc}		90	180	_	225	_	270	Ω
	Gnd	Gnd	6	_	80	160	_	200	_	240	Gnd	Gnd	_	_	_	_	_	_	_	
Maximum "On" resistance between			4.5	_	10	_	_	_	_				_	10	_	_	_	_	_	
any two switches ΔR _{ON}			6	L	8.5	_	_	_		_			_	_	_	_	_	_	-	
Switch "Off"  Leakage Current I _{1z} 16 Channels	E = V _{cc}	V _{cc} or Gnd	6	_	_	±0.8	_	±8	_	±8	E = V _{cc}	V _{cc} or Gnd	_	_	±0.8	-	±8	_	±8	
Logic	V _{cc}																			
Input Leakage	or	-	6	-	_	±0.1	_	±1	- '	±1	**	-	-	-	±0.1	-	±1	-	±1	
Current I	Gnd	1.									}					-		ŧ		μΑ
Quiescent	V _{cc}										V _{cc}									μΑ
Device Current	or	-	6	-	-	8	-	80	-	160	or	-	-	-	8	-	- 80	-	160	
I _o = OmA I _{cc}	Gnd										Gnd									
Additional Quiescent Device Current per input pin: 1 unit load $\Delta l_{cc}^*$	_	_	_	_	_	_	_		_	_	V _{CC} -2.1	_	_	100	360	-	450	_	490	

^{*}For dual-supply systems theoretical worst case ( $V_1$  = 2.4 V,  $V_{CC}$  = 5.5 V) specification is 1.8 mA.

#### **HCT INPUT LOADING TABLE**

INPUT	UNIT LOADS*
S ₀ - S ₃	0.5
Ē	0.3

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25°C.

^{**}Any Voltage Between Vcc & Gnd.

#### SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input tr, tr = 6 ns)

CHARACTERISTIC		CL (pF)	TYP	ICAL HCT	UNITS
Propagation Delay Time:		15	6	6	
Switch In to Switch Out	$t_{PLH}, t_{PHL}$	15	"	"	
Switch Turn Off					
Ē to Out	$t_{PLZ}, t_{PHZ}$	15	23	23	
Sn to Out	$t_{PLZ}, t_{PHZ}$	15	21	21	ns
Switch Turn On					
Ē to Out	$t_{PZL}$ , $t_{PZH}$	15	23	25	
Sn to Out	t _{PZL} ,t _{PZH}	15	25	25	
Power Dissipation Capacitance*	C _{PD}	_	93	96	pF

 $^{*}C_{PD}$  is used to determine the dynamic power consumption, per package.  $P_{D} = C_{PD} \, V_{CC}^2 \, f_i + \Sigma \, (C_L + C_S) \, V_{CC}^2$  fo where:  $f_i$  = input frequency  $f_C$  = load capacitance C

f_o= output frequency C_s = switch capacitance

V_{cc} = supply voltage

#### SWITCHING CHARACTERISTICS (CL = 50 pF, Input tr, tr = 6 ns)

				25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC		Vcc	Н	С	Н	CT	7.41	НС	74F	ICT	54	нс	54F	ICT	UNITS
		V	Min.	Max.	Min.	Мах.	Min.	Мах.	Min.	Мах.	Min.	Max.	Min.	Max.	
Propagation Delay Time	t _{PLH}	2	_	75	_	_	-	95	_		_	110	_	_	
Switch In to Out	t _{PHL}	4.5	-	15	_	15	—	19	<b>—</b>	19	—	22	—	22	
		6	_	13	_	_	_	16	_	_	-	19	—	_	
Switch Turn-On		2	_	275	_	_	_	345		_	_	415	_	_	
Ē to Out		4.5	_	55	_	60	_	69	_	75		83	—	90	
	$t_{PZL}$	6	—	47	l —		—	59	_	_	<u> </u>	71	—	l —	
	t _{PZH}	2	_	300				375	_	_	_	450		_	
Sn to Out		4.5	_	60	_	60	—	75	_	75	l —	90	l —	90	ns
		6	_	51	_		_	64	_	_	l —	76	_	_	
Switch Turn-Off		2	_	275		_	_	345	_	_		415	_	_	1
E to Out		4.5	_	55	_	55		69	_	69		83	<b> </b>	83	
	$t_{PLZ}$	6	_	47	_	_	_	59	_	_		71	_		
Sn to Out	$t_{\text{PHZ}}$	2	_	290	_	_		365	_	_	_	435	_	_	
		4.5	_	58	_	58	_	73	_	73	_	87	l —	87	
		6		49	<u> </u>	_	_	62		_	_	74	l —	<b> </b>	
Input (Control)				10		10		10		10		10		10	
Capacitance	Cı		_	10		10	_	10	_	10	_	10	_	10	pF

#### ANALOG CHANNEL CHARACTERISTICS — Typical Values at TA = 25°C

CHARACTERISTICS	TEST CONDITION	V _{cc} V	нс/нст	UNITS
Switch Frequency Response at - 3 dB (Fig. 12)	Fig. 3 Notes 1 & 2	4.5	89	MHz
Sine Wave Distortion	Fig. 4	4.5	0.051	%
Feedthrough Noise:  E to Switch S to Switch	Fig. 5 Notes 2 & 3	4.5	TBE TBE	mV
Switch "OFF" Signal Feedthrough (Fig. 13)	Fig. 6	4.5	-75	dB
Switch Input Capacitance	C _S —		5	
Common Capacitance Coc	ом —	_	50	⊢ pF

NOTES: 1. Adjust input level for 0 dBm at output, f = 1 kHz.

- 2.  $V_{\text{IS}}$  is centered at  $V_{\text{cc}}/2$ .
- 3. Adjust input for 0 dBm. at VIS

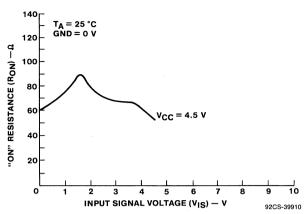


Fig. 2 - Typical "ON" resistance versus input signal voltage.

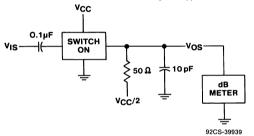


Fig. 3 - Frequency response test circuit.

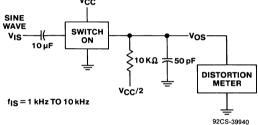


Fig. 4 - Sine wave distortion test circuit.

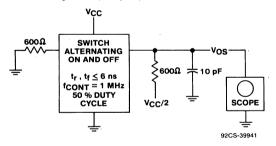


Fig. 5 - Control-to-switch feedthrough noise test circuit.

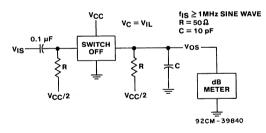


Fig. 6 - Switch off signal feedthrough test circuit.

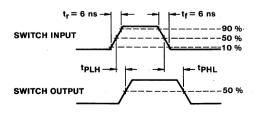


Fig. 7 - Switch propagation-delay times wave forms.

92CS-39914

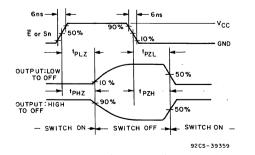


Fig. 8 - Switch turn-on and turn-off propagation delay times wareforms, for HC types.

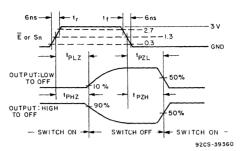
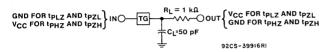


Fig. 9 - Switch turn-on and turn-off propagation delay times waveforms for HCT Types.

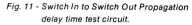


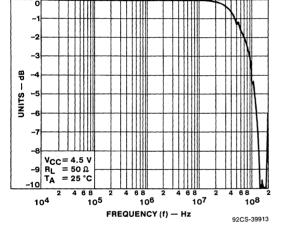
TG OUT

50 pF

92 CS - 38835

Fig. 10 - Switch on/off propagation delay time test circuit.







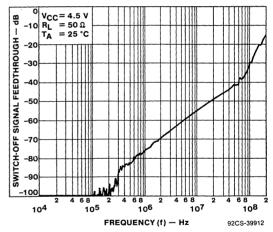
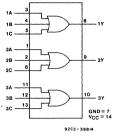


Fig. 13 - Typical switch-off signal feed through vs. frequency.

### **High-Speed CMOS Logic**



# **Triple 3-Input OR Gate**

#### Type Features:

- Buffered inputs
- Typical CD54/74HC4075 Propagation Delay = 8ns @  $V_{CC} = 5V$ ,  $C_L = 15pF$ ,  $T_A = 25^{\circ}C$

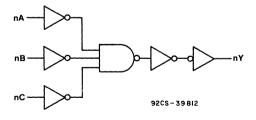
**FUNCTIONAL DIAGRAM** 

The RCA-CD54/74HC4075 and CD54/74HCT4075 logic gates utilize silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. All devices have the ability to drive 10 LSTTL loads. The CD54/74HCT logic family is functionally as well as pin compatible with the standard 54LS/74LS logic family.

The CD54HC4075 and CD54HCT4075 are supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4075 and CD74HCT4075 are supplied in 14-lead dual-in-line plastic packages (E suffix) and in 14-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

#### Family Features:

- Fanout (over temperature range): Standard Outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide Operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High noise immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL input logic compatibility V_{IL} = 0.8 V max., V_{IH} = 2 V Min. CMOS input compatibility I₁ ≤ 1 µA @ V_{OL}, V_{OH}



LOGIC DIAGRAM

#### **TRUTH TABLE**

ı	nΑ	nB	nC	nΥ
	L	L	٦	L
	Н	Х	Х	Η
	Х	Н	Х	Н
	Х	Х	Н	Н

L = Low voltage Level H = High voltage Level X = Don't Care

#### MAXIMUM RATINGS, Absolute-Maximum Values:

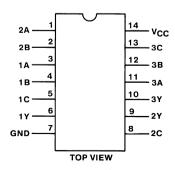
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to $+$ 7 V
DC INPUT DIODE CURRENT, $I_{iK}$ (FOR $V_i$ < -0.5 V OR $V_i$ > $V_{cc}$ +0.5V)	±20mA
DC OUTPUT DIODE CURRENT, $I_{\text{OK}}$ (FOR $V_{\text{o}}\!<$ -0.5 V OR $V_{\text{o}}\!>$ $V_{\text{CC}}$ +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT ( $I_o$ ) (FOR -0.5 V $<$ V $_o$ $<$ V $_{cc}$ + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT (I _{CC} )	±50mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60° C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E) Derate	Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125° C (PACKAGE TYPE F, H) Derate	
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M) Derate	Elinearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (T _{stg} )	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

#### RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	UNITS	
CHARACTERISTIC	MIN.	MAX.	UNIIS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	o °c
CD54 Types	-55	+125	
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	Ì
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.



92CS-39813

**TERMINAL ASSIGNMENT** 

#### STATIC ELECTRICAL CHARACTERISTICS

		CI	74H0	C4075	CD5	4HC40	075				CD74HCT4075/CD54HCT4075									
CHARACTERISTIC	TEST CONDITIONS				74HC/54HC 74HC TYPES TYPE				54I TY		TEST CONDITIONS			CT/54 TYPES			ICT PE		ICT PE	UNITS
onana remone	V _i I _o		V _{cc}		+25° C	•		10/ 5°C	-5 +12	5/ 5°C	V,	V _{cc}		+25° C	;		0/ 5°C	1	5/ 5°C	OMITS
		mA	ľ	Min	Тур	Max	Min	Мах	Min	Max		•	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	_	_	1.5	_	1.5	-		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	-	2	_	٧
			6	4.2	_		4.2	_	4.2	_		5.5								
Low-Level			2		_	0.5	_	0.5	_	0.5		4.5								
Input Voltage V _{IL}			4.5	_		1.35	_	1.35	_	1.35	-	to	-	-	0.8	_	0.8	-	0.8	v
			6	_	_	1.8	_	1.8	_	1.8		5.5		ļ						
High-Level	V _{IL}		2	1.9	_	_	1.9	_	1.9	_	VıL									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4		4.4	_	or	4.5	4.4	—	-	4.4	-	4.4	-	٧
CMOS Loads	V _{IH}		6	5.9		_	5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}				l					
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7		or	4.5	3.98	-	-	3.84	-	3.7	-	٧
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}		2	_	-	0.1	_	0.1		0.1	V _{IL}			İ						
Output Voltage Vol	or	0.02	4.5	_	_	0.1		0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	٧
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	4	4.5	-	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	_	0.33	-	0.4	٧
	V _{IH}	5.2	6	_	_	0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage									
Current I	or		6	_	-	±0.1	_	±1	_	±1	Between V _{cc}	5.5	-	_	±0.1	-	±1	-	±1	μΑ
	Gnd			ļ							& Grid								ļ	
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	_	-	2	-	20	-	40	or	5.5	-	-	2	-	20	_	40	μA
Current I _{cc}	Gnd				L					l	Gnd		<u> </u>	_					ļ	
Additional Quiescent												4.5								
Device Current per input pin:											V _{cc} -2.1	to	_	100	360	-	450	-	490	μΑ
1 unit load △lcc*											l	5.5								

^{*}For dual-supply systems theoretical worst case ( $V_1$  = 2.4 V,  $V_{CC}$  = 5.5 V) specification is 1.8 mA.

#### **HCT INPUT LOADING TABLE**

INPUT	UNIT LOADS*
All	1.6

^{*}Unit Load is  $\Delta I_{CC}$  limit specified in Static Characteristic Chart, e.g., 360  $\mu$ A max. @25° C.

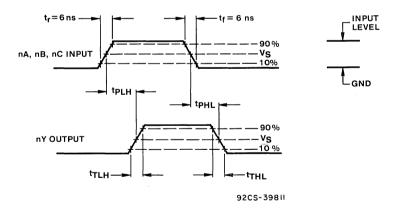
#### SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

0111010710		CL	TYP	CAL	UNITS
CHARACTERISTIC		(pF)	нс	нст	UNITS
Propagation Delay, Data Input to Output Y (Fig. 1)	$t_{PLH}$ , $t_{PHL}$	15	8	9	ns
Power Dissipation Capacitance*	$C_{PD}$	_	26	28	pF

 $^{^{*}}C_{PD}$  is used to determine the dynamic power consumption, per gate.  $P_{D} = V_{CC}^{2}$ fi  $(C_{PD} + C_{L})$  where: fi = input frequency  $C_{L} = load$  capacitance  $V_{CC} = supply$  voltage

#### SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r,t_f = 6 ns)

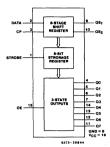
				25	°C		-4	i0° C te	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC		Vcc	Н	С	Н	СТ	74	нс	74F	ICT	54	нс	54F	1CT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	100	_	_	-	125	_	-	_	150	_	-	
Input to Output	$t_{PHL}$	4.5	-	20	_	24		25	—	30	—	30	_	36	ns
(Fig. 1)		6		17	_	l — _	_	21	_			26	_	_	
Transition Times	t _{TLH}	2		75		<u> </u>	_	95	_	_	_	110	_	_	
(Fig. 1)	$t_{THL}$	4.5	_	15	_	15	_	19	i —	19	—	22	—	22	ns
		6		13	_		_	16				19	_		
Input Capacitance	Cı		_	10	_	10	_	10	_	10	-	10	_	10	pF



	54/74HC	54/74HCT
Input Level	V _{CC}	3V
Switching Voltage, V _S	50% V _{CC}	1.3 V

Fig. 1 - Transition times and propagation delay times.

# **High-Speed CMOS Logic**



# 8-Stage Shift-and-Store Bus Register — 3-State

#### Type Features:

- Buffered inputs
- Separate serial outputs synchronous to both positive and negative clock edges for cascading.

**FUNCTIONAL DIAGRAM** 

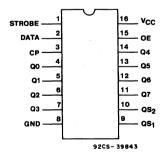
The RCA-CD54/74HC4094 and CD54/74HCT4094 are 8-stage serial shift registers having a storage latch associated with each stage for strobing data from the serial input to parallel buffered 3-state outputs. The parallel outputs may be connected directly to common bus lines. Data is shifted on positive clock transitions. The data in each shift register stage is transferred to the storage register when the Strobe input is high. Data in the storage register appears at the outputs whenever the Output-Enable signal is high.

Two serial outputs are available for cascading a number of these devices. Data is available at the QS1 serial output terminal on positive clock edges to allow for high-speed operation in cascaded systems in which the clock rise time is fast. The same serial information, available at the QS2 terminal on the next negative clock edge, provides a means for cascading these devices when the clock rise time is slow.

The CD54HC4094 and CD54HCT4094 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC4094 and CD74HCT4094 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

#### **Family Features:**

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- I CD54HC/CD74HG Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}



**TERMINAL ASSIGNMENT** 

#### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0,5 to +7 V
DC INPUT DIODE CURRENT, $I_{IK}$ (FOR $V_I$ <-0.5 V OR $V_I$ > $V_{CC}$ + 0.5 V)	±20mA
DC OUTPUT DIODE CURRENT, $l_{OK}$ (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o ) (FOR -0.5 V < V _o < V _{cc} + 0.5 V)	±25mA
DC Vcc OR GROUND CURRENT (Icc)	±50mA
POWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	
For $T_A = +60$ to $+85$ °C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For $T_A = -55$ to $+100$ °C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85°C
STORAGE TEMPERATURE (T _{stg} )	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

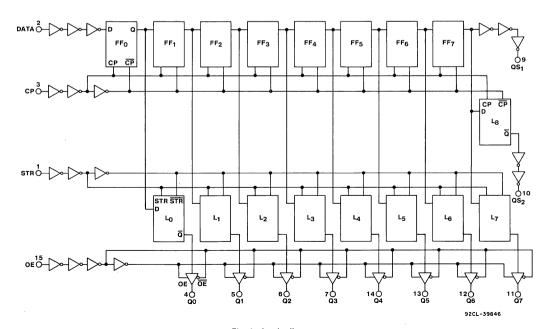


Fig. 1 - Logic diagram.

#### **RECOMMENDED OPERATING CONDITIONS:**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIN	ITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	, 0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

#### **FUNCTION TABLE**

	INP	UTS		PARA OUT		SERIAL OUTPUTS			
СР	OE	STR	D	Q	Qn	QS1*	QS2		
_	L	Х	Х	Z	Z	Q'6	NC		
~	L	Х	Х	Z	Z	NC	Q7		
	Н	L	Х	NC	NC	Q'6	NC		
	Н	Н	L	L	Qn-1	Q'6	NC		
	Н	Н	н	Н	Qn-1	Q′6	NC		
$\sim$	Н	Н	Н	NC	NC	NC	Q7		

H = HIGH voltage level

L = LOW voltage level

X = don't care

X = don to are
NC = No Change
Z = HIGH impedance OFF-state
= LOW-to-HIGH CP transition
= HIGH-to-LOW CP transition

Q'6 = the information in the seventh register stage

^{*}At the positive clock edge the information in the 7th register stage is transferred to the 8th register stage and QS1 output.

#### STATIC ELECTRICAL CHARACTERISTICS

			c	D74H	IC409	4/CD	54HC	4094					CD7	4HC1	4094	CD5	4HCT	4094			
			TEST			74HC/54HC 74HC 54HC TYPES TYPE TYPE					TEST	74HCT/54HCT TYPES			74F TY	ICT PE	54HCT TYPE				
CHARACTERISTIC		V, V	I _O	V _{cc}	-	+25°C	;	-4 +8!		-5 +12		V,	V _{cc}		+25°C	;	-40/ +85°C				UNITS
		<b>V</b>	IIIA	ľ	Min	Тур	Max	Min	Max	Min	Max	·		Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_		1.5		1.5			4.5								
Input Voltage	V _{IH}			4.5	3.15	_		3.15	_	3.15		_	to	2	_	-	2	-	2	-	V
				6	4.2		_	4.2	_	4.2	_		5.5								
Low-Level				2	_		0.5	_	0.5	<u> </u>	0.5		4.5								
Input Voltage	$V_{IL}$			4.5	_		1.35		1.35	_	1.35	_	to	_	_	0.8	_	0.8	_	0.8	٧
				6	-		1.8	_	1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	_		1.9	_	1.9	_	VIL									
Output Voltage	Vон	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	_	_	4.4	_	4.4	_	v
CMOS Loads		V _{IH}		6	5.9	_	_	5.9		5.9	_	ViH									
		VIL										Vil									
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	_	3.84	_	3.7	_	v
		V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	Vы									
Low-Level		VIL		2	_	_	0.1	_	0.1	_	0.1	VIL									
Output Voltage	Vol	or	0.02	4.5	_	_	0.1		0.1	_	0.1	or	4.5	_		0.1	_	0.1	_	0.1	V
CMOS Loads		V _{IH}		6	_	_	0.1		0.1	_	0.1	V _{IH}									
		VIL										VıL									
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	_	0.33	_	0.4	v
		VIH	5.2	6	_		0.26	_	0.33	_	0.4	V _{IH}									
Input Leakage		Vcc										Any Voltage									
Current	lı .	or Gnd		6	-	-	±0.1	_	±1		±1	Between V _{cc} and Gnd	5.5	_	_	±0.1	-	±1	_	±1	μΑ
Quiescent		Vcc										Vcc									
Device		or	0	6		_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μΑ
Current	lcc	Gnd		_			_					Gnd									,
Additional Quiescent Device Current per input pin: 1 unit load Δ	.lcc*											V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-State Leakage Current	loz	V _{IL} or V _{IH}	V₀=Vcc or Gnd	6	-	-	±0.5	_	±5	-	±10	V _{IL} or V _{IH}	5.5	_	_	±0.5	-	±5	_	±10	μΑ

 $^{^{\}star}$  For dual-supply systems theoretical worst case (V  $_{\rm I} = 2.4$  V, V  $_{\rm CC} = 5.5$  V) specification is 1.8 mA.

#### **HCT Input Loading Table**

Input	Unit Loads*
D	0.40
CP, OE	1.50
STR	1.0

^{*}Unit load is  $\Delta I_{\rm CC}$  limit specified in Static Characteristics Chart, e.g., 360  $\mu{\rm A}$  max. @ 25°C.

SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input tr, tr=6 ns)

		CL	TYP	CAL	
CHARACTERISTIC	SYMBOL	(pF)	нс	нст	UNITS
Propagation Delay CP to Qn	t _{PLH}	15	16	18	
CP to QS1			12	16	
CP to QS2			11	15	ns
Output Enabling Time	t _{PZH}		14	14	
Output Disabling Time	t _{PHZ}		10	14	
Max. CP Frequency	f _{MAX}		60	60	MHz
Power Dissipation Capacitance*	C _{PD}	_	90	110	pF

fi=input frequency

fo=output frequency

V_{cc}=supply voltage

#### SWITCHING CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r$ , $t_f = 6 \text{ ns}$ )

			25°C					0°C to	+85	°C	-5				
CHARACTERISTIC		V _{cc}	Н	IC	н	СТ	74	нс	74F	ICT	54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH} t _{PHL}	2 4.5	_	150 30	_	_ 39	_	190 38	  -	— 49	_	225 45	  -	- 59	ns
CP to QS1		6	├─	26	_			33	_			38	_		
CP to QS2		2 4.5 6	—   —   —	135 27 23	_ 	36 —	_ _ _	170 34 29	_ _ _	— 45 —	_ 	205 41 35	_ 	54 —	ns
CP to Qn		2 4.5 6		195 39 33	_ _ _	- 43 -		245 49 42	_ 	 54 	_	295 59 50	_ _ _	 65 	ns
STR to Qn		2 4.5 6	_ _ _	180 36 31		_ 39 _	_	225 45 38		- 49 -	_	270 54 46	_ _ _	_ 59 _	ns
Output Enable to Qn	t _{PZH} t _{PZL}	2 4.5 6	_	175 35 30	_	_ 35 _	_	220 44 37	_	_ 44 _	_	265 53 45	_	_ 53 _	ns
Output Disable to Qn	t _{PHZ}	2 4.5 6	_ _ _	125 25 21		 35 	_ _ _	155 31 26		_ 44 _	_ _ _	190 38 32	_ _ _	 53 	ns
Output Transition Time	t _{THL} t _{TLH}	2 4.5 6	  -  -	75 15 13	_ _ _	 15 	_ _ _	95 19 16		— 19 —	_ _ _	110 22 19	_	_ 22 _	ns
Input Capacitance	Cı		_	10		10	_	10	_	10	_	10	_	10	pF
3-State Output Capacitance	Со		-	15		15		15	_	15	_	15	_	15	pF

#### PRE-REQUISITE FOR SWITCHING FUNCTION

				25	°C		-4	0°C to	+85	°C	-5				
CHARACTERISTIC		Vcc	Н	С	н	СТ	74	нс	74F	ICT	54	нс	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
		2	80	_	_	_	100	_	_	_	120	_	_	_	
CP Pulse Width	tw	4.5	16	_	16	—	20		20		24	—	24		ns
		6	14		_		17		_		20	_			
		2	80	l —	_	_	100	_	_	_	120	<u> </u>	_	_	
STR Pulse Width	twH	4.5	16	-	16	_	20	_	20	—	24	—	24	_	ns
		6	14		_	_	17		_		20	_			
		2	50	_		_	65	_	_	_	75	_	_	—	
Data Setup Time	tsu	4.5	10	<u> </u>	10	<u> </u>	13	-	13	_	15	—	15	—	ns
		6	9				11				13		_	_	
		2	3	_	_	—	3	_		—	3	-	-		
Data Hold Time	$t_{H}$	4.5	3		4	-	3	_	4	-	3		4	—	ns
		6	3		_		3		_	_	3				
		2	100		-	-	125	_	_	-	150	_	-		
STR Setup Time	tsu	4.5	20	_	20	-	25	-	25		30	—	30	-	ns
		6	17	<u> </u>	_	_	21	<u> </u>	_	_	26	<u> </u>		<u> </u>	
		2	0	-	—	—	0	-	—		0	l —	-	-	1
STR Hold Time	t _H	4.5	0	-	0	_	0	-	0	_	0	—	0	-	ns
		6	0			_	0	<u> </u>	_	_	0				
Max. CP		2	6	—	_	-	5	-	—	-	4		-	-	
Frequency	f _{CL(max.)}	4.5	30	—	30	_	24	-	24	-	20	-	20	-	MHz
		6	35				28			<u> </u>	24		-		

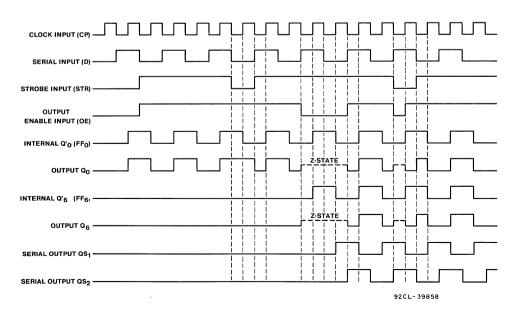


Fig. 2 — Timing Diagram

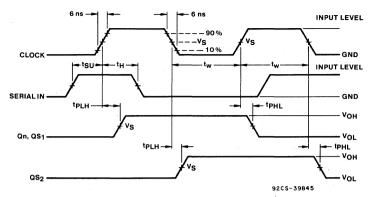
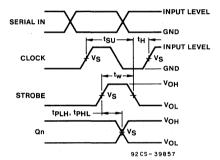


Fig. 3 - Data propagation delays, setup and hold times.



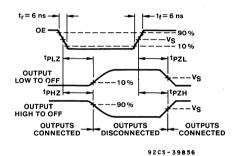
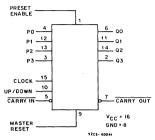


Fig. 4 - Strobe propagation delays, and setup and hold times.

Fig. 5 - Enable and Disable Times.

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

# **High-Speed CMOS Logic**



**FUNCTIONAL DIAGRAM** 

# Presettable Synchronous 4-Bit Up/Down Counters

CD54/74HC/HCT4510 BCD Decade Counter, Asynchronous Reset CD54/74HC/HCT4516 4-Bit Binary Counter, Asynchronous Reset

#### Type Features:

- Synchronous counting and asynchronous loading
- Look-ahead carry for high-speed counting

The RCA CD54/74HC/HCT4510 presettable BCD up/down counter and the CD54/74HC/HCT4516 presettable binary up/down counter consist of four synchronously clocked D-type flip-flops (with a gating structure to provide T-type flip-flop capability) connected as counters. These counters can be cleared by a high level on the Master Reset line, and can be preset to any binary number present on the preset inputs by a high level on the Preset Enable line. The 4510 will count out of non-BCD counter states in a maximum of two clock pulses in the up mode, and a maximum of four clock pulses in the down mode.

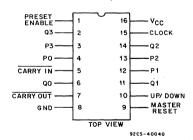
If the Carry-In input is held low, the counter advances up or down on each positive-going clock transition. Synchronous cascading is accomplished by connecting all clock inputs in parallel and connecting the Carry-Out of a less significant stage to the Carry-In of a more significant stage.

The 4510 and 4516 can be cascaded in the ripple mode by connecting the Carry-Out to the clock of the next stage. If the Up/Down input changes during a terminal count, the Carry-Out must be gated with the clock, and the Up/Down input must change while the clock is high. This method provides a clean clock signal to the subsequent counting stage. (See Fig. 5.)

The CD54HC/HCT4510 and the CD54HC/HCT4516 are supplied in 16-lead ceramic dual-in-line frit-seal packages (F suffix). The CD74HC/HCT4510 and the CD74HC/HCT4516 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

#### **Family Features:**

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}=30%, N_{IH}=30% of V_{CC}; @ V_{CC}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility I₁≤1 µA @ VoL, VoH



**TERMINAL ASSIGNMENT** 

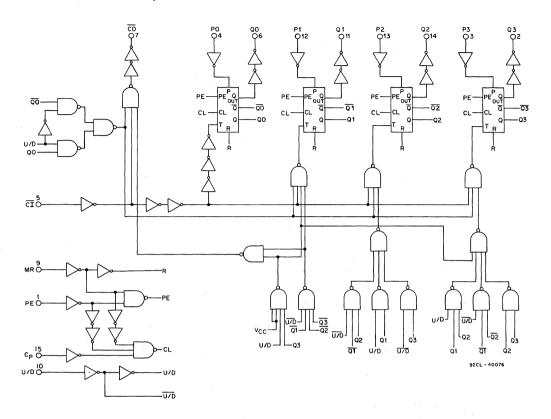


Fig. 1 - Logic diagram for HC/HCT4510.

#### **TRUTH TABLE**

CL	ច	U/D	PE	MR	ACTION
х	Н	х	L	L	NO COUNT
	L	н	L	·L	COUNT UP
	L	L	L	L	COUNT DOWN
x	X	x	н	L	PRESET
х	х	×	x	н	RESET

X = Don't Care H = High Voltage Level L = Low Voltage Level

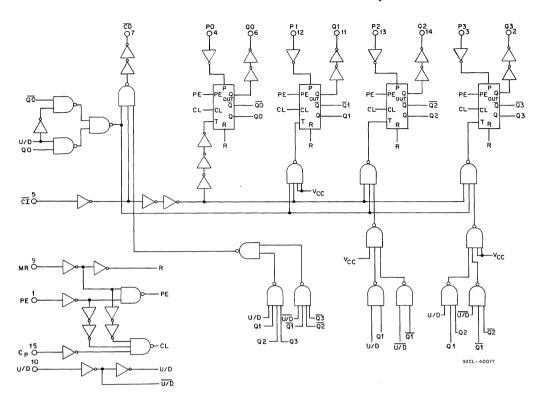


Fig. 2 - Logic diagram for HC/HCT4516.

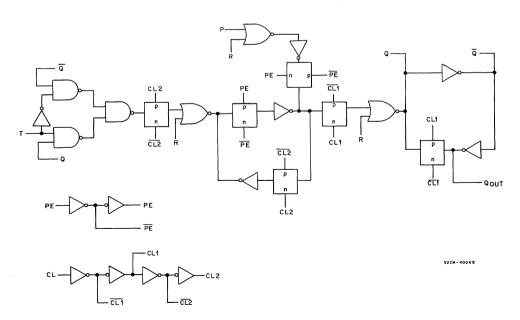


Fig. 3 - Logic diagram of flip-flops for HC/HCT4510/4516.

To	ch	ni	cal	חו	ata	

#### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, $I_{IK}$ (FOR $V_i < -0.5$ V OR $V_i > V_{CC} +0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, $I_{OK}$ (FOR $V_o$ < -0.5 V OR $V_o$ > $V_{CC}$ +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I _o ) (FOR -0.5 V < V _o < V _{cc} +0.5 V)	±25 mA
DC V _{CC} OR GROUND CURRENT (I _{CC} )	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F,H)	
For T _A = +100 to +125°C (PACKAGE TYPE F,H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	
OPERATING-TEMPERATURE RANGE (TA):	•
PACKAGE TYPE F.H	55 to +125° C
PACKAGE TYPE E,M	40 to +85° C
STORAGE TEMPERATURE (T _{stg} )	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79 \text{ mm})$ from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C
<b>5</b>	

#### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERICTIC	LIF	MITS	LINUTC
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range) V _{CC} :*			
CD54/74HC Types	, 2	6	V
CD54/74HCT Types	4.5	5.5	\ <b>v</b>
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :		1	
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	1
Input Rise and Fall Times, tr,tr:			
at 2 V	0	1000	1
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

#### STATIC ELECTRICAL CHARACTERISTICS

CD74HC4510/4516/CD54HC4510/4516												CD74F	ICT4	510/4	516/C	D54H	ICT4	510/4	516		
CHARACTERISTIC		ľ	TEST CONDITIONS			74HC/54HC TYPES		741 TYF		541 TYF		TEST CONDITIO	NS	74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		UNITS
CHAHACTERIS	iic	V,	lo	Vcc		+25°C			-40/ -55/ +85°C +125°			V,	Vcc	+25°C		;	-40/ +85° C		1		UNITS
		v	mA	v	Min	Тур	Max	Min	Max	Min	Max	٧	v	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	-	1.5	-	1.5	_		4.5							<u> </u>	
Input Voltage	VIH			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	—	—	2		2	-	V
				6	4.2			4.2	_	4.2			5.5	L			L	L			
Low-Level			}	2		_	0.5	_	0.5	_	0.5		4.5	l	l			l			
Input Voltage	VIL	İ		4.5			1.35		1.35		1.35	_	to	-	l –	0.8		0.8	-	0.8	٧
				6		_	1.8	_	1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	_	_	1.9		1.9	_	VIL		l	l	ŀ		[		1	
Output Voltage	$V_{OH}$	or	-0.02	4.5	4.4	_		4.4	_	4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	٧
CMOS Loads		V _{IH}		6	5.9	_	<u> </u>	5.9		5.9	_	V _{IH}		l				ļ		<u> </u>	
		VIL				<u> </u>	<u> </u>					VIL		l	ļ			į		İ	
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7		or	4.5	3.98	-	—	3.84	-	3.7	-	٧
		V _{IH}	-5.2	6	5.48	_		5.34	_	5.2	_	V _{IH}		ļ				L			
Low-Level		VIL		2	=	_	0.1	_	0.1		0.1	VIL		Ì	1	1		l	Ì	]	
Output Voltage	Vol	or	0.02	4.5		_	0.1	_	0.1		0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads		V _{IH}		6	_	<u> </u>	0.1	_	0.1		0.1	V _{IH}		<u> </u>				<u> </u>		ļ	
		VIL	ļ		ļ		<u> </u>	<u> </u>		ļ		VIL		ł				ļ			
TTL Loads		or	4	4.5	_		0.26	<u> </u>	0.33		0.4	or	4.5	-	-	0.26	_	0.33	-	0.4	V
		V _{IH}	5.2	6	<u> </u>	_	0.26		0.33	느	0.4	V _{IH}		ļ	<u> </u>		_		-		
Input Leakage		Vcc								}		Any			ł			l			
Current	h	or		6	_	_	±0.1	_	±1	l _	±1	Voltage	5.5	_	_	±0.1	_	±1	_	±1	μΑ
		Gnd								ł		Between		ŀ	1			l			
0.1		<del>  , -</del>									-	V _{cc} & Gnd		-	-			-	-	├	
Quiescent Device Current		Vcc	0	6				_	80		160	Vcc	5.5	_		8		80	_	160	μA
Device Current	Icc	or Gnd	"	0	-	_	8	_	80	_	100	or Gnd	5.5	_	_	ľ	_	80	-	100	μ^
Additional		Gild	L	L	Ц	Щ.	Ц	L	L	L	L	Gilu			-	-			_	$\vdash$	
Quiescent Device													4.5								
Current per input												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	Δlcc*												5.5		1						

^{*}For dual-supply systems theoretical worst case ( $V_1$  = 2.4 V,  $V_{CC}$  = 5.5 V) specification is 1.8 mA.

#### **HCT Input Loading Table**

Input	Unit Loads*
P0-P3	0.75
MR	1.5
U/D, PE, CI	1
CP .	1.25

^{*}Unit Load is  $\Delta I_{CC}$  limit specified in Static Characteristics Chart, e.g., 360  $\mu A$  max. @ 25° C.

#### SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input tr,tr=6 ns)

CHARACTERISTIC		C _⊾ (pF)	45	10	45	16	UNITS
			HC	нст	HC	HCT	
Propagation Delay:							
CP to Qn	t _{PLH} , t _{PHL}	15	18	21	18	21	
CP to CO	t _{PLH} , t _{PHL}	15	22	24	22	24	
PE to Qn	t _{PLH} , t _{PHL}	15	21	22	21	22	20
PE to CO	t _{PLH} , t _{PHL}	15	25	28	25	28	ns
MR to Qn	t _{PHL}	15	18	18	18	18	
MR to CO	t _{PLH}	15	20	20	20	20	
Cl to CO	t _{PLH} , t _{PHL}	15	10	13	10	13	
Power Dissipation Capacitance	C _{PD} *		59	65	68	72	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 f_i + \sum (C_L V_{CC}^2 f_o)$  where  $f_i$  = input frequency

fo = output frequency

C_L = output load capacitance

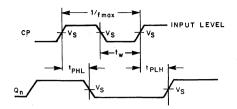
V_{cc} = supply voltage.

#### PRE-REQUISITE FOR SWITCHING FUNCTION

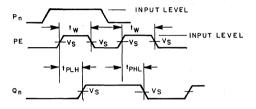
			LIMITS												
		TEST		25	°C		-4	0°C t	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERIST	IC	CONDITIONS	Н	С	Н	)T	741	НС	74H	ICT	54	нС	54H	ICT	UNITS
		V _{cc} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Pulse Width:		2	80		-	_	100		T-	_	120	_	_	-	
СР	tw	4.5	16	_	16	_	20	_	20	_	24	_	24	_	
		6	14	_	_	_	17	l —	_		20	l —		_	
		2	100			_	125	_			150		_	_	
MR	tw	4.5	20	l —	20		25	l —	25	_	30	-	30	_	
		6	17	l —	l —	_	21	_	_	<u> </u>	26	_	_	<u> </u>	
		2	80	_	_	_	100	_	T-	_	120	<del>-</del>	_	_	Ì
PE	tw	4.5	16	l —	16	<b>—</b>	20	_	20	_	24	_	24	_	
		6	14	_	_	_	17	<u> </u>	_	_	20	_	_	_	
Setup Time,	tsu	2	100	_	_	_	125	_	_	_	150	_		_	
Pn to PE,		4.5	20		20	l —	25	_	25	_	30	l —	30		ns
CI to CP		6	17	_	_	_	21	<b> </b>	_	_	26	-	_		
Hold Time,	tн	2	3	_	_	_	3	_	Ι	_	3	<del>-</del>	-		1
Pn to PE		4.5	3	_	3		3	l —	3	_	3	<b> </b> —	3	_	}
		6	3	_	_	_	3		_	_	3	<u> </u>	—	_	
		2	5	_	_	_	5	_		_	5	<u>-</u>	_		Ì
CI to CP	tн	4.5	5		5	_	5	_	5	—	5	-	5	—	ļ
		6	5	_	_	<u> </u>	5	—	ì.—	<b> </b>	5	l —	—	-	Ì
		2	0	_		_	0	_	T —	_	0	T —	_		1
U/D to CP	t _H	4.5	0		0	_	0	_	0	_	0	-	0		ŀ
		6	0	_	—		0	_	—	_	0	—	_	—	
Removal Time:		2	80		_	_	100	_	T —	-	120	_	_	_	
MR to CP	$t_{\text{REM}}$	4.5	16	_	16	—	20	-	20	-	24	—	24	-	
		6	14	l —	l —	l –	17	l —	_	-	20	-	l —	-	1
Maximum Frequency	/	2	6	T —	-	<u> </u>	5		_	_	4	_			
CP	$f_{MAX}$	4.5	30	_	30	—	24	-	24	-	20	—	20	-	MHz
		6	35		l —	_	28	. —	-	—	24	_	<u> </u>	-	}

#### SWITCHING CHARACTERISTICS (CL=50 pF, Input tr,tr=6 ns)

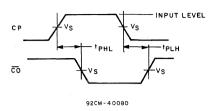
			LIMITS												
				25	°C		-4	0°C t	o +85°	°C	-5	5°C to	+125	°C	
CHARACTERIS	STIC	VCC (V)	Н	C	H	СТ	74	НС	74F	ICT	54	НС	54F	ICT	UNITS
		(۷)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay:	t _{PLH}	2	_	220	_	_	_	275	-	_	-	330	<u> </u>	-	
CP to Qn	t _{PHL}	4.5	-	44	_	50	—	55	—	63	—	66		75	
		6	_	37	_	_		47		_	_	56			
	t _{PLH}	2	-	260		_		325	-	_	_	390	<b>—</b>	_	
CP to CO	t _{PHL}	4.5	-	52	_	58	l —	65	—	73	_	78	<b> </b>	87	
		6		44				55		<u> </u>	_	66			
	t _{PLH}	2	-	250	_	_		315	—			375	-	-	
PE to Qn	t _{PHL}	4.5	-	50	-	53	—	63	—	66	—	75		80	
		6		43			<u> </u>	54		_		64		_	
	t _{PLH}	2	—	300	_		_	375	—	-	—	450	-	_	
PE to CO	t _{PHL}	4.5	-	60	—	68		75	—	85	—	90	—	102	
		6		51				64			_	76	_		ns
		2	—	210	-	—	—	265	—	-	-	315	<b>—</b>	-	'''
MR to Qn	t _{PHL}	4.5	—	42	l —	42	<b>-</b>	53	—	53	—	63	—	63	
		6		36		_	_	45			_	54	_		
		2	—	235	-	-	-	295	—	-	_	355		-	
MR to CO	t _{PLH}	4.5		47	-	47	-	59	—	59	-	71	-	71	1
		6		40		<u> </u>		50	_			60	_	<u> </u>	
	t _{PLH}	2	-	125	-	-	_	155		_	-	190	_	_	
CI to CO	t _{PHL}	4.5	-	25		31		31	_	39	-	38	-	47	
		6		21	_			26	_		<u> </u>	32		_	]
Transition Time:	t _{THL}	2	-	75	—	—	-	95	-	_	-	110	-	-	
Qn, CO	t _{TLH}	4.5	-	15	—	15	-	19	_	19	—	22	-	22	
		6	$\perp =$	13				16		$\perp =$		19		$\perp =$	
Input Capacitance	Cı			10		10	<u> </u>	10	_	10		10		10	pF



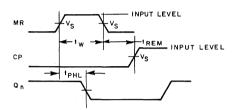
(a) Clock to output delays and clock pulse width.



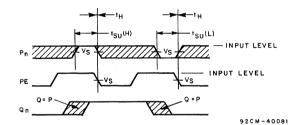
(c) Preset Enable pulse width and Preset Enable to output delays.



(b) Clock to carry out delays.



(d) Master reset pulse width, master reset to output delay and master reset to clock removal time.



(e) Setup and hold times data to Preset Enable (PE).

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

Fig. 4 - AC waveforms.

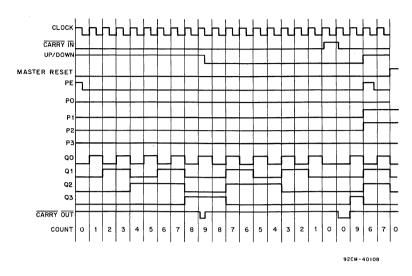


Fig. 5 - Timing diagram for CD54/74HC/HCT4510.

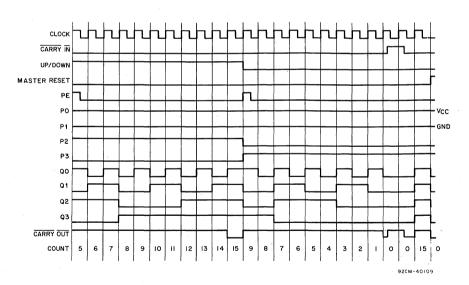
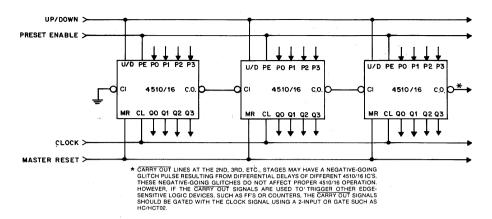
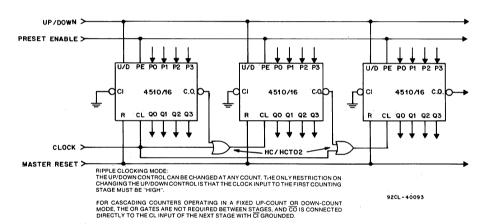


Fig. 6 - Timing diagram for CD54/74HC/HCT4516.



#### (a) Parallel clocking.



#### (b) Ripple clocking.

Fig. 7 - Cascading counter packages.

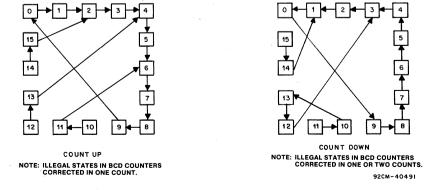
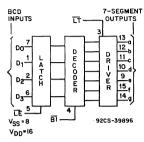


Fig. 8 - HC/HCT4510 State Diagrams.

# **High-Speed CMOS Logic**



#### **FUNCTIONAL DIAGRAM**

# BCD-to-7 Segment Latch/ Decoder/Drivers



#### Type Features:

- High-output sourcing capability-7.5 mA @ 4.5 V, 10 mA @ 6 V (HC4511)
- Input latches for BCD code storage
- Lamp test and blanking capability

The RCA CD54/74HC4511 and CD54/74HCT4511 are BCD-to-7 segment latch/decoder/drivers having four address inputs ( $D_0$ - $D_3$ ), active "Low" blanking and lamp test input, and a latch enable input which, when "High", enables the latches to store the BCD inputs. When Latch Enable is "Low", the latches are disabled, making the outputs transparent to the BCD inputs.

These devices have standard-size output transistors but are capable of sourcing (at standard  $V_{OH}$  levels) up to 7.5 mA at 4.5 V. The HC types can supply up to 10 mA at 6 V.

The CD54HC/HCT4511 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT4511 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

#### **TRUTH TABLE**

							_						_	
LE	ВІ	LT	Dз	D ₂	D ₁	D ₀	а	b	С	d	е	f	g	Display
X	х	L	х	Х	Х	Х	Н	Н	Н	Н	Н	Н	Н	8
X	L	Н	Х	Χ	Χ	Х	L	L	L	L	L	L	L	Blank
L	н	н	L	L	L	L	Н	Н	Н	Н	Н	Н	L	0
L	Н	н	L	L	L	Н	L	Н	Н	L	L	L	L	1
L	н	Н	L	L	Н	L	Н	Н	L	Н	Н	L	н	2
L	н	Н	L	L	Н	Н	Н	Н	Н	Н	L	L	Н	3
L	н	ļ.H	L	Н	L	L	L	Н	Н	L	L	Н	Н	4
L	Η.	Н	L	Н	L	Н	Н	L	Н	Н	L	Н	Н	5
L	Н	н	L	Н	Н	L	L	L	Н	Н	Н	Н	Н	6
L	Н	Н	L	Н	Н	Н	Н	Н	Н	L	L	L	L	7
L	Н	н	Н	L	L	L	Н	Н	Н	Н	Н	Н	Н	8
L	Н	Н	Н	L	L	Н	Н	Н	Н	L	L	Н	Н	9
L	Н	н	Н	L	Н	L	L	L	L	L	Ŀ	L	L	Blank
L	Н	Н	Н	L	Н	Н	L	L	L	L	L	L	L	Blank
L	Н	Н	н	Н	L	L	L	L	L	L	L	L	L	Blank
L	Н	Н	Н	Н	.L	Н	L	L	L	L	L	L	L	Blank
L	Н	н	Н	Н	Н	L	L	L	L	L	L	L	L	Blank
L	Н	Н	Н	Н	Н	Н	L	L	L	L	L	L	L	Blank
lн	lн	۱н	l x⊹	Х	X	X	ı			•				

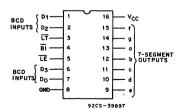
X = Don't Care.

#### Family Features:

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85°C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity:

N_{IL}=30%, N_{IH}=30% of V_{CC}; @ V_{CC}=5 V

■ CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility I_I≤1 µA @ V_{OL}, V_{OH}



**TERMINAL ASSIGNMENT** 

^{*}Depends on BCD code previously appied when  $\overline{LE}$  = L. Note: Display is blank for all illegal input codes (BCD > HLLH).

#### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, $I_{IK}$ (FOR $V_i < -0.5$ V OR $V_i > V_{CC}$ +0.5 V)	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I _o ) (FOR -0.5 V < V _o < V _{cc} +0.5 V).	±25 mÅ
DC Vcc OR GROUND CURRENT (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F,H)	500 mW
For T _A = +100 to +125° C (PACKAGE TYPE F,H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F,H	55 to +125° C
PACKAGE TYPE E,M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150° C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

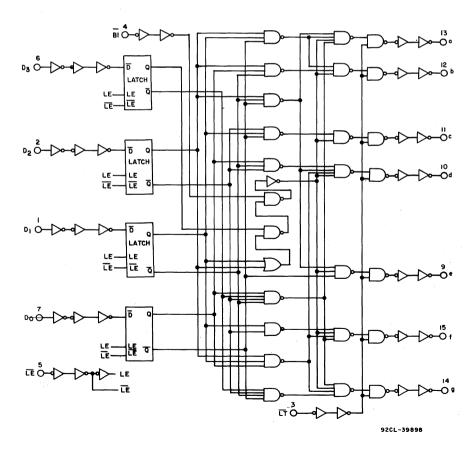


Fig. 1 - Logic diagram.

#### STATIC ELECTRICAL CHARACTERISTICS

	-			CD7	4HC4	511/C	:D54H	IC451	1			C	CD74I	нст4	511/C	D54F	ICT4	511				
CHARACTERIST	ric	1	TEST	NS	1	IC/54		741 TYF	-	541 TYF	HC PES	TEST CONDITION	NS		CT/54		74HCT TYPES		54HCT TYPES		UNITS	
CHARACTERIS		V _i	lo	Vcc		+25° C	:	-4 +85	0/ 6° C	-5 +12	5/ 5° C	V,	Vcc		+25° C		+25° C		-40/ +85° C			-55/ +125°C
		V	mA	V	Min	Тур	Max	Min	Max	Min	Max	V	v	Min	Тур	Max	Min	Max	Min	Max		
High-Level				2	1.5	_	-	1.5	-	1.5	_		4.5									
Input Voltage	$V_{IH}$			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	-	-	2	_	2	-	V	
				6	4.2	_	_	4.2	_	4.2			5.5									
Low-Level				2	_		0.5	_	0.5	_	0.5	•	4.5			ł		ļ	1			
Input Voltage	$V_{IL}$			4.5		<u> </u>	1.35	_	1.35	_	1.35	_	to	-	-	0.8	-	0.8	-	0.8	V	
				6	<u> </u>	_	1.8		1.8	_	1.8		5.5	<u> </u>	ļ			<u> </u>				
High-Level		VIL		2	1.9	_	<u> </u>	1.9		1.9	_	VIL		1	1	ļ		l	ł			
Output Voltage	$V_{OH}$	or	-0.02	4.5	4.4	<u> </u>	<u> </u>	4.4		4.4		or	4.5	4.4	-	-	4.4	-	4.4	-	V	
CMOS Loads		V _{IH}		6	5.9	_	_	5.9		5.9	_	V _{IH}				ļ	L_			ļ		
TTL Loads		VIL						L	L			VIL		ļ		ļ						
Non-Standard		or	-7.5	4.5	3.98	_	_	3.84		3.7		or	4.5	3.98	-	-	3.84	-	3.7	-	V	
Output		V _{IH}	-10	6	5.48	_		5.34		5.2		V _{IH}				ļ ·				<u> </u>		
Low-Level		VIL		2	<u> </u>		0.1	_	0.1	_	0.1	VIL			1				1	ļ		
Output Voltage	Vol	or	0.02	4.5	-	<u> </u>	0.1		0.1	_	0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V	
CMOS Loads		V _{IH}		6	-	_	0.1		0.1		0.1	V _{IH}	ļ	ļ		<u> </u>		ļ				
		VIL							ļ			VIL					İ					
TTL Loads		or	4	4.5	_	-	0.26	_	0.33		0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V	
Standard Output		V _{IH}	5.2	6		_	0.26		0.33	_	0.4	V _{IH}	_					ļ				
Input Leakage		Vcc				1						Any		1		1			1			
Current	h	or	1	6	_	-	±0.1	-	±1	_	±1	Voltage	5.5	-	-	±0.1	_	±1	l —	±1	μΑ	
		Gnd	1					ĺ				Between				1			1			
Quiescent		Vcc					<u> </u>				_	V _{cc} & Gnd	_				-	-	_	<b>-</b>		
Device Current	lcc	or	0	6	_		8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μА	
Device Guirent	ICC	Gnd	"	"	_	-	ľ	-	00	_	160	Gnd	5.5	-	-	"	_	80	_	100	μΑ	
Additional		Gild	<u> </u>		L	L	L	L		L	L	Gilu	-	├	-			<del> </del>	-	<u> </u>		
Quiescent Device													4.5		1	1						
Current per input												Vcc -2.1	to	-	100	360	-	450	-	490	μΑ	
pin: 1 unit load	Δlcc*												5.5									

^{*}For dual-supply systems theoretical worst case ( $V_1$  = 2.4  $V_1$ ,  $V_{CC}$  = 5.5 V) specification is 1.8 mA.

HCT Input Loading Table

Input	Unit Loads*
LT, LE	1.5
Bl, Dn	0.3

^{*}Unit Load is  $\Delta I_{CC}$  limit specified in Static Characteristics Chart, e.g., 360  $\mu A$  max. @ 25° C.

#### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERICTIC	LIN	UNITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	\
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°c
CD54 Types	-55	+125	10
Input Rise and Fall Times, tr.tr:			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

#### SWITCHING CHARACTERISTICS (V_{CC}=5 V, T_A=25° C, Input t_r,t_f=6 ns)

			TYPICAL			
CHARACTERISTIC		C _L (pF)	НС	нст	UNITS	
Propagation Delay:	t _{PLH}	15	25	0.5		
D _n to Output	t _{PHL}	15	25	25		
	t _{PLH}	15	23	23		
LE to Output	tpHL	15	23	23		
	t _{PLH}	15	18	18	ns	
BI to Output	t _{PHL}	15	10	10		
	t _{PLH}	15	13	13		
LT to Output	t _{PHL}	15	13	13		
Power Dissipation Capacitance*	C _{PD}	_	114	110	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 f_i + \sum C_L V_{CC}^2 f_o$  where  $f_i$  = input frequency

fo = output frequency

C_L = output load capacitance

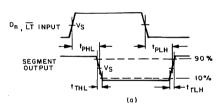
V_{cc} = supply voltage.

#### PRE-REQUISITE FOR SWITCHING FUNCTION

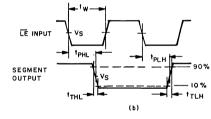
			LIMITS												
TEST				25	°C		-4	0°C to	o +85°	°C	-5	5°C to	+125	°C	1
CHARACTERI	STIC	CONDITIONS	Н	нс		нст		74HC		74HCT		54HC		54HCT	
		V _{cc} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Setup Time,	tsu	2	80	T —	_	_	100	_		T —	120	T -	_	_	
$D_n$ to $\overline{LE}$		4.5	16	-	16	_	20		20	_	24	-	24	—	
		6	14	l -		-	17	_	—	—	20		—	-	
Hold Time,	tн	2	3	_			3	_	_	_	3	I —	_	_	ns
D₁ to LE		4.5	3	-	5	—	3	_	5	-	3		5	_	
		6	3	_	l —	—	3	—	—	_	3	_	_	-	
Latch Enable		2	80	_	_	_	100	_	_	_	120		-	T —	
Pulse Width,	tw	4.5	16		16	—	20	-	20	-	24	—	24	—	MHz
		6	14	_	l —	l –	17	1 —	_		20	_	_	l —	1

#### SWITCHING CHARACTERISTICS (CL=50 pF, Input t,ti=6 ns)

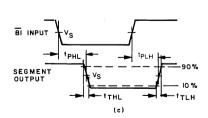
			LIMITS												
				25	°C		-4	0°C to	+85°	,C	-5	5°C to	+125	°C	
CHARACTERIS	STIC	Vcc	Н	НС		нст		74HC		74HCT		НС	54HCT		UNITS
		1	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	l.
Propagation Delay,	tpLH	2	_	300	-	_	I —	375	_	—	I —	450	I —	T-	
D _n to Output	t _{PHL}	4.5	—	60	<u> </u>	60	—	75	—	75		90	l —	90	ns
		6	_	51	—	] —	l —	64	—		l —	77	-	<b> </b>	
	t _{PLH}	2		270	_		_	340	_	_	_	405	_	_	
LE to Output	t _{PHL}	4.5	_	54	_	54	l —	68	_	68	—	81	_	81	ns
		6	_	46	_	_	_	58			_	69	l —	—	}
	t _{PLH}	2	_	220	_	_	_	275		_	_	330	_	T —	
BI to Output	t _{PHL}	4.5	_	44	_	44	<u> </u>	55	—	55	—	66	_	66	ns
		6	1	37	l —	_	l —	47	_	_	-	56	_		
	t _{PLH}	2	T-	160	_	_	_	200	_	_		240	_	T-	
LT to Output	t₽HL	4.5	l —	32	l —	33		40		41	—	48	_	50	ns
		6	<b> </b> —	27	l —	_	_	34	<u> </u>	—	—	41			}
	t _{THL}	2	T —	75		_	_	95	_	_	T-	110	_	T-	
Transition Time	t _{TLH}	4.5	—	15	_	15	l —	19	l —	19	l —	22	l —	22	ns
		6		13	l —	_	l —	16			—	19		—	
Input Capacitance	Cı		<u> </u>	10	_	10	_	10	_	10		10	_	10	pF



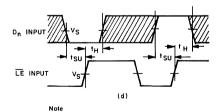
Input (Dn, LT) to output propagation delays and output transition times



Input (LE) to output propagation delays and latch enable pulse width



Input (B1) to output propagation delays.



The shaded areas indicate when the input is permitted to change for predictable output performance.

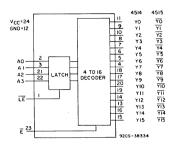
Waveforms showing the data set-up and hold times for Dn input to LE input.

92CM-39899

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

Fig. 2 - AC waveforms.

# **High-Speed CMOS Logic**



# 4-to-16 Line Decoder/Demultiplexer with Input Latches

#### Type Features:

Multifunction capability:
Binary to 1-of-16 decoder
1-to-16 line demultiplexer

#### **FUNCTIONAL DIAGRAM**

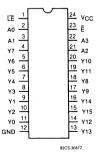
The RCA CD54/74HC4514, 4515 and CD54/74HCT4514, 4515 are high-speed silicon gate devices consisting of a 4-bit strobed latch and a 4-to-16 line decoder. The selected output is enabled by a low on the enable input ( $\overline{E}$ ). A high on  $\overline{E}$  inhibits selection of any output. Demultiplexing is accomplished by using the  $\overline{E}$  input as the data input and the select inputs (A0-A3) as addresses. This  $\overline{E}$  input also serves as a chip select when these devices are cascaded.

When Latch Enable  $\overline{(LE)}$  is high the output follows changes in the inputs (see truth table). When  $\overline{LE}$  is low the output is isolated from changes in the input and remains at the level (high for the 4514, low for the 4515) it had before the latches were enabled. These devices, enhanced versions of the equivalent CMOS types, can drive 10 LSTTL loads.

The CD54HC4514, 4515 and CD54HCT4514, 4515 are supplied in 24-lead dual-in-line frit-seal ceramic packages (F suffix). The CD74HC4514, 4515 and CD74HCT4514, are supplied in 24-lead dual-in-line, narrow-body plastic packages (EN suffix), in 24-lead dual-in-line, wide-body plastic packages (E suffix), and in 24-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

#### Family Features

- Fanout (over temperature range):
   Standard outputs 10 LSTTL loads
   Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL} = 30%, N_{IH} = 30%; @ V_{CC} = 5V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL} = 0.8 V max., V_{IH} = 2 V min. CMOS input compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}



**TERMINAL ASSIGNMENT** 

#### MAXIMUM RATINGS. Absolute-Maximum Values: DC SUPPLY-VOLTAGE (Vcc): (Voltages referenced to ground) -0.5 to +7 V POWER DISSIPATION PER PACKAGE (Pp): OPERATING-TEMPERATURE RANGE (TA): PACKAGE TYPE E. M ......-40 to +85°C STORAGE TEMPERATURE (T_{sto}).....-65 to +150°C LEAD TEMPERATURE (DURING SOLDERING):

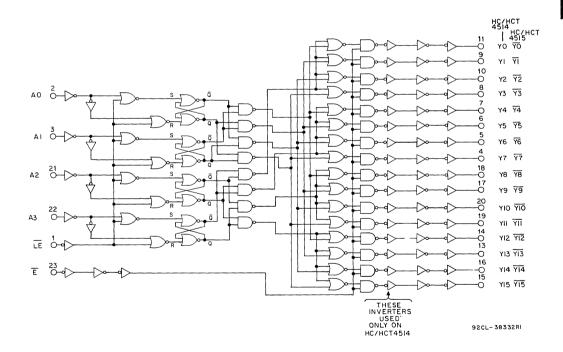


Fig. - Logic diagram for CD54/74HC4514, 4515 and CD54/74HCT4514, 4515.

DECODE TRUTH TABLE ( $\tilde{L}E = 1$ )

	1	DEC(	ODEI UTS	3	ADDRESSED OUTPUT							
ENABLE	А3	A2	A1	A0	4514 = Logic 1 (High) 4515 = Logic 0 (Low)							
0	0	0	0	0	Y0							
0	0	0	0	1	Y1							
0	0	0	1	0	Y2							
0	0	0	1_	1	Y3							
0	0	1	0	0	Y4							
0	0	1	0	1	Y5							
0	0	1	1	0 ,	Y6							
0	0	1	1	1	Y7							
0	1	0	0	0	Y8							
0	1	0	0	1	Y9							
0	1	0	1	0	Y10							
0	1	0	1	1	Y11							
0	1	1	0	0	Y12							
) 0	1	1	0	1	Y13							
0	1	1	1	0	Y14							
0	1	1	1	1	Y15							
1	х	Х	х	Х	All Outputs = 0, 4514 All Outputs = 1, 4515							

X = Don't Care

Logic 1 = High

Logic 0 = Low

### **RECOMMENDED OPERATING CONDITIONS:**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIM	ITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times, t _r , t _f			
at 2V	0	1000	ns
at 4.5 V	0	500	ns
at 6V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

#### STATIC ELECTRICAL CHARACTERISTICS

				CD7	4HC4	514/C	D54F	1C451	15				(	CD74	нст4	514/0	:D54F	ICT4	515			
QUADA OTERIO	-10		TEST	s	ŀ	IC/54			HC PE		HC PE	TEST CONDITION		l	CT/54	нст	1	ICT PE	l	ICT PE		
CHARACTERIST	IIC	1 1 1		V _{cc}			4	-40/ +85°C		5/ 5°C	V,	V _{cc}	+25°C		:	-40/ +85°C		-55/ +125°C		UNITS		
		٧	mA	۷	Min	Тур	Max	Min	Max	Min	Max	V	v	Min	Тур	Max	Min	Max	Min	Max		
High-Level				2	1.5	_	_	1.5	_	1.5	_		4.5									
Input Voltage	V _{IH}			4.5	3.15	_	<u>_</u>	3.15		3.15	_	_	to	2	-	_	2	_	2	-	v	
				6	4.2	_		4.2		4.2	_		5.5									
Low-Level				2			0.5		0.5		0.5		4.5			ĺ			İ			
Input Voltage	VIL			4.5		_	1.35	_	1.35		1.35	_	to	-	-	0.8	_	0.8	_	0.8	v	
				6	_		1.8		1.8	_	1.8		5.5			<u> </u>						
High-Level		VIL		2	1.9	_	_	1.9	_	1.9	_	VıL										
Output Voltage	V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4		or	4.5	4.4	_	-	4.4	-	4.4	-	v	
CMOS Loads		V _{IH}		6	5.9	_		5.9	_	5.9		Vін										
		VIL										VIL										
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	or	4.5	3.98	_	-	3.84	_	3.7	-	٧	
		V _{IH}	-5.2	6	5.48		_	5.34	_	5.2	-	VIH										
Low-Level		VIL		2	_	_	0.1		0.1	_	0.1	VIL										
Output Voltage	VoL	or	0.02	4.5	_	ı	0.1	_	0.1	1	0.1	or	4.5		_	0.1	_	0.1	_	0.1	v	
CMOS Loads		VIH		6	_	_	0.1	_	0.1	-	0.1	ViH										
		VIL										VIL										
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_	_	0.26	-	0.33	_	0.4	v	
		ViH	5.2	6	_	_	0.26	_	0.33		0.4	V _{IH}										
Input Leakage		Vcc										Any Voltage										
Current	l _i	or		6	_	_	±0.1	_	±1	_	±1	Between V _{cc}	5.5	_	_	±0.1	-	±1	-	±1	μΑ	
		Gnd										& Gnd										
Quiescent		Vcc										Vcc										
Device		or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μΑ	
Current	lcc	Gnd										Gnd										
Additional Quiescent Device Current per input pin: 1 unit load Δlcc*												V _{cc} -2.1	4.5 to 5.5	1	100	360	-	450	_	490	μΑ	

^{*}For dual-supply systems theoretical worst case ( $V_1$  = 2.4  $V_1$ ,  $V_{CC}$  = 5.5 V) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads*
A0 — A3	0.15
<u>LE</u>	0.85
Ē	0.3

 $^{^{\}star}$  Unit load is  $\Delta I_{CC}$  limit specified in Static Characteristic Chart, e.g., 360  $\mu A$  max. @ 25°C.

SWITCHING CHARACTERISTICS ( $V_{cc} = 5 \text{ V}, T_A 25^{\circ}\text{C}, Input t_r, t_f = 6 \text{ ns}$ )

		C	Typical		
CHARACTERISTIC	SYMBOL	(pF)	нс нст		UNITS
Propagation Delay Select to Output	t _{PHL}	15	23	25	ns
LE to Output	t _{PHL}	15	19	21	ns
Ē to Output	t _{PHL}	15	14	17	ns
Power Dissipation Capacitance*	СРД		70	75	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

#### PREREQUISITE FOR SWITCHING FUNCTION

		!		25	°C		-4	O°C to	+85	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	H	СТ	74	нс	74F	1CT	54	нс	54H	łCT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
	1	2	75	_	_	_	95	l _	_	_	110		_	I _	,
LE Pulse Width	tw	4.5	15		30	l —	19	-	38	_	22	_	45	_	ns
		6	13	-	_		16		_		19		_		
Select to LE		2	100	_	_	_	125		_	_	150	_	_	_	
Set-up time	t _{su}	4.5	20	_	20	<u> </u>	25	_	25	_	30	_	30	_	ns
		6	17	_	_	—	21	—	_	_	26	-		_	
Select to LE		2	0	_	_	_	0	_	_	_	0	_	_	_	
Hold Time	t _H	4.5	0	-	5	-	0	-	5	—	0	-	5		ns
		6	0	l —	-	_	0	l —	_		0	l —	—	l —	

### SWITCHING CHARACTERISTICS ( $C_L = 50$ pF, Input $t_r$ , $t_f = 6$ ns)

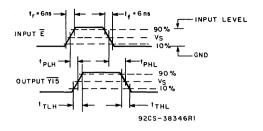
				25	°C		-4	0°C to	+85	°C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	HC		Н	СТ	74HC		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay	t _{PLH}	2	_	275	_	_	_	345	_	_	_	115	_	_	
Select to Outputs	t _{PHL}	4.5	—	55	_	55	_	69	-	69	_	83	_	83	ns
		6	_	47	_	_	_	59		_	_	71	_	_	
	t _{PLH}	2	_	225	_	_	_	280		_	_	340	_	_	
LE to Outputs	t _{PHL}	4.5	_	45	_	50	l —	56	_	63	_	68	_	75	ns
		6	_	38		_	_	48	_	_	_	58	_		
	t _{PLH}	2		175	_		_	220	_	_	_	265	_	_	
E to Outputs	t _{PHL}	4.5	_	35	-	40	l —	44	_	50	—	53	_	60	ns
		6		30	l —	_	<u> </u>	37			_	45	_	_	
Output Transition	t _{TLH}	2	_	75	_	_	_	95	_	<u> </u>	_	110	_	_	
Time	t _{THL}	4.5	<u> </u>	15	_	15	_	19	_	19	_	22	_	22	ns
		6		13	<u> </u>	_		16	_	—	—	19	_	_	
Input Capacitance	Cı			10	_	10		10		10		10		10	pF

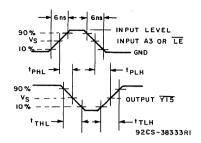
PD = $V_{CC^2} f_i (C_{PD} + C_L)$  where:

f_i = input frequency,

C_L = output load capacitance

V_{cc} = supply voltage

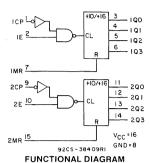




	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

Propagation delay times and transition times for HC/HCT4515.

## **High-Speed CMOS Logic**



### **Dual Synchronous Counters**

CD54/74HC/HCT4518 — BCD CD54/74HC/HCT4520 — Binary

#### Type Features:

- Positive or Negative Edge Triggering
- Synchronous Internal Carry Propagation

The RCA CD54/74HC4518 and CD54/74HCT4518 are dual BCD up-counters. The RCA CD54/74HC4520 and CD54/74HC4520 are dual binary up-counters. Each device consists of two independent internally synchronous 4-stage counters. The counter stages are D-type flip-flops having interchangeable CLOCK and ENABLE lines for incrementing on either the positive-going or the negative-going transition of CLOCK. The counters are cleared by high levels on the MASTER RESET lines. The counter can be cascaded in the ripple mode by connecting Q3 to the ENABLE input of the subsequent counter while the CLOCK input of the latter is held low.

The CD54HC/HCT4518 and CD54HC/HCT4520 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT4518 and CD74HC/HCT4520 are supplied in a 16-lead plastic dual-in-line packages (E suffix), and in 16-lead surface mount plastic dual-in-line packages (M suffix). The CD54/74HC/HCT4518/4520 are also supplied in chip form (H suffix).

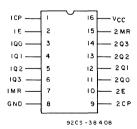
### **Family Features:**

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
  - CD54HC/CD74HC Types: 2 to 6 V Operation

High Noise Immunity:

- $N_{\rm IL} = 30\%$ ,  $N_{\rm IH} = 30\%$  of  $V_{\rm CC}$ ; @  $V_{\rm CC} = 5~V$
- CD54HCT/CD74HCT Types:

  4.5 to 5.5 V Operation
  Direct LSTTL Input Logic Compatibility
  V_{IL} = 0.8 V Max., V_{IH} = 2 V Min.
  CMOS Input Compatibility
  I_I ≤ 1 µA @ V_{OL}, V_{OH}



TERMINAL ASSIGNMENT

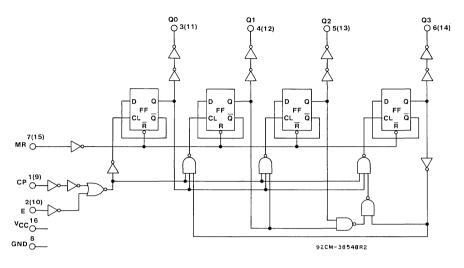


Fig. 1 — CD54/74HC/HCT4518 Logic Diagram

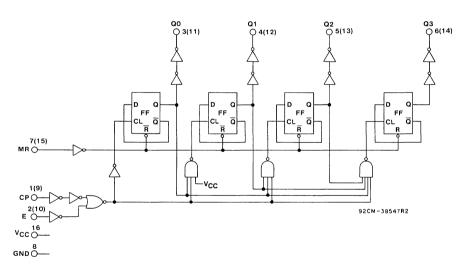


Fig. 2 — CD54/74HC/HCT4520 Logic Diagram

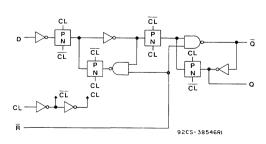


Fig. 3 - Detail of each D Flip-Flop

	T	RUTH TA	ABLE
CP	E	MR	ACTION
	Н	L	Increment Counter
L	$\sim$	L	Increment Counter
~	Х	L	No Change
Х	~	L	No Change
~	L	L	No Change
Н	_	L	No Change
X	X	Н	Q0 thru Q3 = L

X = Don't Care

H = High State

L = Low State

= low-to-high transition

= high-to-low transition

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to + 7 V
DC INPUT DIODE CURRENT, IIK (FOR VI < -0.5 V OR VI > VCC +0.5V)	±20mA
DC OUTPUT DIODE CURRENT, IOK (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)	±20mA
DC DRAIN CURRENT, PER OUTPUT (I _o ) (FOR -0.5 V < V _o < V _{cc} + 0.5V)	±25mA
DC V _{CC} OR GROUND CURRENT, PER PIN (I _{CC} )	±50mA
POWER DISSIPATION PER PACKAGE (Po):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85° C (PACKAGE TYPE E)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F. H)	Derate Linearly at 8 mW/°C to 300 mW
For T _A = -40 to +70° C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125° C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F, H	55 to +125°C
PACKAGE TYPE E, M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	.,65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

### **RECOMMENDED OPERATING CONDITIONS:**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{CC} :*			
CD54/74HC Types	2	6	V
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _{IN} , V _{OUT}	0	V _{cc}	V
Operating Temperature T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
at 2 V	0	1000	ns
at 4.5 V	0	500	ns
at 6 V	0	400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.

### STATIC ELECTRICAL CHARACTERISTICS

		CI	74HC	4518, 4520,	/CD54	HC45	518 520				CD74HCT4518/CD54HCT4518 CD74HCT4520/CD54HCT4520									
CHARACTERISTIC		TEST IDITIONS		ı	IC/54 SERIE:		74I SER	HC	54I SER		TEST		1	CT/54 ERIE		t	ICT IIES		HCT	UNITS
	V,	.   -		+25°C			-40/ +85°C		-55/ +125° C		V,	V _{cc}		+25° C		(	0/ 5° C			UNITS
				Min	Тур	Max	Min	Max	Min	Max		ľ	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	-	-	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	-	_	2	_	2	_	v
			6	4.2	_		4.2		4.2	_		5.5								
Low-Level			2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage $V_{\iota_L}$			4.5	_	_	1.35	_	1.35	_	1.35	_	to	-	-	0.8		0.8		0.8	v
			6	_	_	1.8	_	1.8		1.8		5.5								
High-Level	Vil		2	1.9	_	_	1.9	_	1.9	_	VIL									
Output Voltage V _{он}	or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	_	4.4	-	4.4	-	v
CMOS Loads	V _{IH}		6	5.9	_		5.9	_	5.9	_	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	-4	4.5	3.98	_	_	3.84	_	3.7		or	4.5	3.98	_		3.84	-	3.7	-	V
	V _{IH}	-5.2	6	5.48	_	_	5.34	_	5.2	_	V _{IH}									
Low-Level	V _{IL}	Ì	2	_	_	0.1	_	0.1		0.1	V _{IL}									
Output Voltage V _{ot}	or	0.02	4.5	_	_	0.1	_	0.1		0.1	or	4.5	-	-	0.1	-	0.1	-	0.1	V
CMOS Loads	V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
	V _{IL}										V _{IL}									
TTL Loads	or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
	V _{IH}	5.2	6	_	_	0.26		0.33	_	0.4	V _{IH}									
Input Leakage	V _{cc}										Any Voltage		İ						ļ	1
Current I,	or		6	-	-	±0.1	-	±1	_	±1	Between V _{cc}	5.5	-	-	±0.1		±1	-	±1	μА
	Gnd										& Gnd									
Quiescent	V _{cc}										V _{cc}									
Device	or	0	6	-	-	8	-	80	-	160	or	5.5	-	-	8	-	80	-	160	μΑ
Current I _{cc}	Gnd										Gnd									
Additional Quiescent								-				4.5								
Device Current per input pin: 1 unit load ΔI _{cc} *											V _{cc} -2.1	to -	-	100	360	-	450	-	490	μА

^{*}For dual-supply systems theoretical worst case ( $V_{i}$  = 2.4 V,  $V_{CC}$  = 5.5 V) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads*
MR	1.2
CP	0.25
ENABLE	0.5

^{*}Unit Load is  $\Delta I_{CC}$  limit specified in Static Characteristic Chart, e.g., 360  $\mu$ A max. @ 25°C.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

CHARACTERISTIC	CL	SYMBOL	TYP	ICAL	UNITS
	(pF)	SIMBOL	НС	нст	UNITS
Maximum Clock Frequency	15	f _{MAX}	60	50	MHz
Propagation Delay CP to Qn	15	t _{PLH} t _{PHL}	20	22	ns
Enable to Qn	15	t _{PLH} t _{PHL}	20	23	ns
MR to Qn	15	t _{PLH} t _{PHL}	12	14	ns
Power Dissipation Capacitance*	_	C _{PD}	33	33	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per counter.

fo = output frequency,

C_L = output load capacitance

V_{cc} = supply voltage

### PREREQUISITE FOR SWITCHING FUNCTION

				25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	CT	.74	нС	74F	ICT	54	нС	54F	ICT	UNITS
	]		Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Marrian Clark		2	6	_	_	_	5	_	_	_	4	—	_	_	
Maximum Clock	fmax	4.5	30	_	25	<u> </u>	24	_	20	<u> </u>	20		17	_	MHz
Frequency		6	35		—		28	_	_		24	l —	_	_	
		2	80		_	_	100	_	_	_	120	_		_	
Clock Pulse Width	tw	4.5	16	<u> </u>	20	—	20	_	25	-	24	_	30		ns
		6	14			_	17	_			20		_		
		2	100		-	_	125	_	<b>—</b>	_	150	-	_	_	
MR Pulse Width	tw	4.5	20	—	20	—	25	_	25	—	30	-	30	—	ns
		6	17				21	_			26		_	_	
Setup Time		2	80	_	_	_	100	_	_	_	120	-	_	-	
Enable to CP	t _{su}	4.5	16	_	16	-	20	l —	20	-	24	-	24	<u> </u>	ns
Enable to CP		6	14				17	_	_		20			-	
Removal Time		2	0	_	_	_	0	-		-	0	_	-	-	
MR to CP	t _{REM}	4.5	0		0	-	0	-	0	—	0	_	0	-	ns
WIN to CF		6	0	_	_	<u></u>	0		_	<u> </u>	0				
Setup Time		2	80	_	_	_	100	-	_	-	120	— .	-	—	
	t _{su}	4.5	16	-	16	<u> </u>	20	-	20	—	24	_	24	_	ns
CP to Enable		6	14				17	<u> </u>	_		20	<u> </u>		<u> </u>	İ
Removal Time		2	0	_	_	-	0	_	-	-	0	-		_	
	t _{REM}	4.5	0	-	0	-	0	<u> </u>	0	_	0	_	0	-	ns
MR to Enable		6	0			—	0	-		_	0	l —	_	l —	

SWITCHING CHARACTERISTICS (CL = 50 pF, Input t,t = 6 ns)

	1			25	°C		-4	0°C to	o +85°	С	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	CT	741	НС	74F	ICT	54	НС	54F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	-	240	_	_	_	300	_	_	_	360	_	-	
CP to Qn	t _{PHL}	4.5	—	48	<u> </u>	53	—	60	-	66	_	72	—	80	ns
CP to QII		6	<u> </u>	41	—	<u> </u>		51	_	l –	<u> </u>	61			
		2		240	_	_	_	300	_	_		360	_	-	
Enable to Qn	t _{PLH}	4.5		48	-	55	_	60	-	69	_	72	—	83	ns
		6	_	41	_	_		51	_	_	<u> </u>	61	l —	_	
		2	I —	150	_	I -		190	_	-	_	225	<b>—</b>	ļ. —	
MR to Qn	t _{PHL}	4.5	<u> </u>	30	l —	35	-	38	—	44	-	45	—	53	ns
		6	_	26				33	_	_		38			
Outrut		2	_	75	_	_	_	95	-	_	I -	110	_	-	
Output	t _{THL}	4.5	_	15	_	15	_	19	-	19	—	22	<u> </u>	22	ns
Transition Time t _{TLH}	6		13				16	_	l	_	19	<u> </u>			
Input Capacitance	Cı		_	10	_	10	_	10		10	_	10		10	pF

 $P_D = C_{PD} V_{CC}^2 f_i + \Sigma C_L V_{CC}^2 f_o$  where

f, = input frequency,

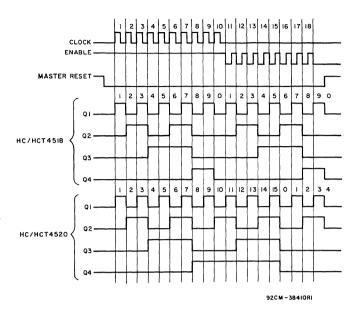
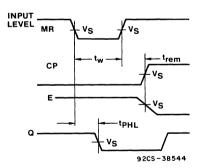
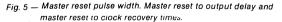


Fig. 4 — Timing Diagrams for CD54/74HC/HCT4518/4520.





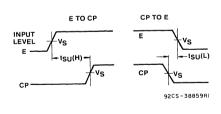
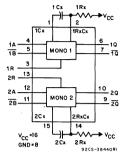


Fig. 6 — Setup Times: E to CP and CP to E.

	54/74HC	54/74HCT
Input Level	V _{cc}	3V
Switching Voltage Vs	50% Vcc	1.3 V

## **High-Speed CMOS Logic**



**FUNCTIONAL DIAGRAM** 

# Dual Retriggerable Precision Monostable Multivibrator

#### Type Features:

- Retriggerable/resettable capability
- Trigger and Reset propagation delays independent of R_x, C_x
- Triggering from the leading or trailing edge
- Q and Q Buffered Outputs available
- Separate Resets
- Wide Range of Output-Pulse Widths
- Schmitt Trigger input on A and B inputs
- Retrigger Time is independent of C_x.

The RCA-CD54/74HC4538 and CD54/74HCT4538 are dual retriggerable/resettable monostable precision multivibrators for fixed voltage timing applications. An external resistor (Rx) and an external capacitor (Cx) control the timing and the accuracy for the circuit. Adjustment of Rx and Cx provides a wide range of output pulse widths from the Q and  $\overline{Q}$  terminals. The propagation delay from trigger input-tooutput transition and the propagation delay from reset input-to-output transition are independent of Rx and Cx.

Leading-edge triggering (A) and trailing edge triggering  $(\overline{B})$  inputs are provided for triggering from either edge of the input pulse. An unused "A" input should be tied to Gnd and an unused  $\overline{B}$  should be tied to V_{cc}. On power up the IC is reset. Unused resets and sections must be terminated. In normal operation the circuit retriggers on the application of each new trigger pulse. To operate in the non-retriggerable mode  $\overline{\Omega}$  is connected to  $\overline{B}$  when leading edge triggering (A) is used or  $\Omega$  is connected to A when trailing edge triggering ( $\overline{B}$ ) is used. The period ( $\tau$ ) can be calculated from  $\tau=(0.7)$  R_x C_x; R_{min} is 5k ohms. C_{min} is 0 pF.

The CD54HC/HCT4538 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT4538 are supplied in 16-lead dual-in-line plastic packages (E suffix), also in 16-lead dual-in-line surface mount plastic packages (M suffix). The CD54/74HC/HCT4538 are also available in chip form (H suffix).

#### Family Features:

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:2 to 6 V Operation

High Noise Immunity:

- $N_{\rm IL} = 30\%$ ,  $N_{\rm IH} = 30\%$  of  $V_{\rm CC}$ ; @  $V_{\rm CC} = 5$  V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility

 $I_1 \leq 1 \,\mu A \otimes V_{OL}, V_{OH}$ 

92CS-38465

**TERMINAL ASSIGNMENT** 

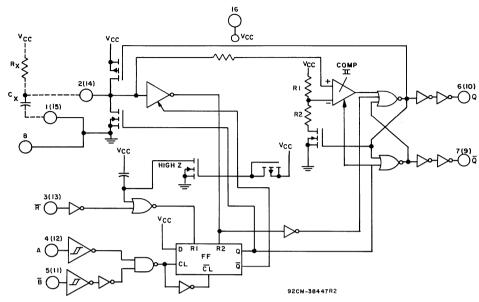
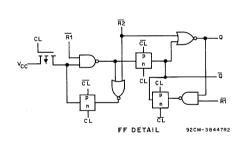


Fig. 1 - Logic diagram (1 mono).

#### **TRUTH TABLE**



	•								
	INPUTS		OUTPUTS						
R	Α	В	a	ā					
L	Х	Х	L	н					
×	Н	X	L	н					
×	X	L	L	н					
н	L		Л	T.					
н		Н	Л	T.					

- H = High Level
- L = Low Level
- T = Low Level
  Transition from Low to High
  Transition from High to Low
  T= One High Level Pulse
  T= One Low Level Pulse
- X = Irrelevant

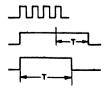
	HC/H	CT4538 FUN	CTIONAL TE	RMINAL CO	NNECTIONS				
FUNCTION	1	V _{cc} TO TERM. NO.		i TO 11. NO.		PULSE RM. NO.	OTHER CONNECTIONS		
	MONO ₁	MONO ₂	MONO ₁	MONO ₂	MONO ₁	MONO ₂	MONO ₁	MONO ₂	
Leading-Edge Trigger/ Retriggerable	3, 5	11, 13			4	12			
Leading-Edge Trigger/ Non-Retriggerable	3	13			4	12	5-7	11-9	
Trailing Edge Trigger/ Retriggerable	3	13	4	12	5	, 11			
Trailing-Edge Trigger/ Non-Retriggerable	3	13			5	11	4-6	12-10	

#### NOTES:

- 1. A RETRIGGERABLE ONE-SHOT MULTIVIBRATOR HAS AN OUTPUT PULSE WIDTH WHICH IS EXTENDED ONE FULL TIME PERIOD (T) AFTER APPLICATION OF THE LAST TRIGGER PULSE.
- 2. A NON-RETRIGGERABLE ONE-SHOT MULTIVIBRATOR HAS A TIME PERIOD (T) REFERENCED FROM THE APPLICATION OF THE FIRST TRIGGER PULSE.

INPUT PULSE TRAIN

RETRIGGERABLE MODE PULSE WIDTH (A MODE) NON-RETRIGGERABLE MODE PULSE WIDTH (A MODE)



#### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc): (Voltages referenced to ground) -0.5 to + 7 V *DC INPUT DIODE CURRENT, I_{IK} (FOR V_i < -0.5 V OR V_i > V_{CC} + 0.5 V) + 20mA DC V_{cc} OR GROUND CURRENT (I_{cc}) ±50mA POWER DISSIPATION PER PACKAGE (PD): For T_A = -55 to +100° C (PACKAGE TYPE F, H) ...... For  $T_A = -40$  to +70°C (PACKAGE TYPE M) 400 mW OPERATING-TEMPERATURE RANGE (Ta): PACKAGE TYPE E. M ......-40 to +85° C STORAGE TEMPERATURE (Tstr) ......-65 to +150°C LEAD TEMPERATURE (DURING SOLDERING): At distance 1/16 + 1/32 in. (1.59 + 0.79 mm) from case for 10 s max. +265°C Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm) *DC INPUT CURRENT FOR Cx Rx PIN = 30 mA

#### RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERICTIC	LIF	MITS	LINUTO
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*			
CD54/74HC Types	2	6	.,
CD54/74HCT Types	4.5	5.5	V
DC Input or Output Voltage V _I , V _O	0	, V _{cc}	٧
Operating Temperature T _A :			
CD74 Types	-40	+85	
CD54 Types	-55	+125	°C
Input Rise and Fall Times t _r , t _f			
Reset Input			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	
Trigger Inputs			
A or $\overline{B}$			
at 2 V	0	Unlimited	
at 4.5 V	0	Unlimited	ns
at 6 V	0	Unlimited	
External Timing Resistor, R _x	5kΩ	#	
External Timing Capacitor, C _x	0	#	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

[#]The maximum allowable values of  $R_x$  and  $C_x$  are a function of leakage of capacitor  $C_x$ , the leakage of the HC4538, and leakage due to board layout and surface resistance. Values of  $R_x$  and  $C_x$  should be chosen so that the maximum current into pin 2 or pin 14 is 30 mÅ. Susceptibility to externally induced noise signals may occur for  $R_x > 1$  M $\Omega$ .

#### STATIC ELECTRICAL CHARACTERISTICS

	CE	74HC	4538	CD54	HC45	38					CD7	4HC1	Γ <b>453</b> 8.	/CD54	нст	4538			
			1	74HC/54HC 74HC TYPE TYPE				TEST CONDITIONS		1			74HCT TYPE		54HCT TYPE		UNITS		
V,	I _o			+25° C	25°C -40/ +85°C		-55/ +125°C		V,	V _{cc}		+25° C		ı		1		UNITS	
·			Min	Тур	Max	Min	Max	Min	Max	,	ľ	Min	Тур	Max	Min	Max	Min	Max	
		2	1.5	_	_	1.5	_	1.5	_		4.5								
		4.5	3.15	_	_	3.15	_	3.15	_	-	to	2	-	-	2	-	2	-	v
	<b> </b>	6	4.2	_	_	4.2		4.2	_		5.5								
	{	2	_	_	0.5	_	0.5	_	0.5		4.5					}		}	
		4.5	_	_	1.35		1.35	_	1.35	-	to	-	-	0.8	-	0.8	-	0.8	٧
		6			1.8		1.8	_	1.8		5.5					ļ			
VIL		2	1.9	_	_	1.9	_	1.9	-	VIL									
or	-0.02	4.5	4.4	_	_	4.4	_	4.4	_	or	4.5	4.4	-	-	4.4	-	4.4	-	v
V _{IH}		6	5.9	_	_	5.9	_	5.9	_	V _{IH}									
$V_{iL}$										VIL									
or	-4	4.5	3.98	_	_	3.84		3.7	_	or	4.5	3.98	-	-	3.84	-	3.7	-	v
ViH	-5.2	6	5.48	_		5.34	_	5.2	_	V _{IH}									
V _{IL}		2	_	_	0.1	_	0.1	_	0.1	$V_{\iota_L}$	}				}				
or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	-	-	-0.1	-	0.1	-	0.1	v
V _{IH}		6	_	_	0.1	_	0.1	_	0.1	V _{IH}									
V _{IL}										VIL									
or	4	4 5	-	_	0.26	-	0.33	-	0.4	or	4.5	-	-	0.26	-	0.33		0.4	v
V _{IH}	5.2	6	_	-	0.26	_	0.33	_	0.4	V _{IH}									
V _{cc}		6	_	_	±0.1	_	±1	_	±1	Any Voltage	5.5	_	_	±0.1		±1	_	±1	μA
or Gnd		6	-	-	±0.05	_	±0.5	-	±0.5	V _{cc}	5.5		-	±0.05	-	±0.5	-	±0.5	μΑ
V _{cc}					-					V _{cc}			l						
or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	_	80	_	160	μΑ
Gnd					-					Gnd									
V _{cc}	0	6	_	_	0.6	_	0.8	_	1	V _{cc} or	5.5	_	_	0.6	_	0.8	_	1	mA
Gnd						{				Gnd				į					
	L	L	L	L		L	L	Ц			4.5			<del>                                     </del>	-	_	-		
										V _{cc} -2.1	to	_	100	360	-	450	-	490	μА
	V _I , V _{IL} or V _{IH} V _{IL} or V _{IH} V _{IL} or V _{IH} V _{IC} or Or Gnd V _{CC} or Gnd V _{CC} or	TEST CONDITIONS  V, Io mA  VIL or -0.02  VIII or -4  VIII or -5.2  VIII or 4  VIII or 4  VIII or 5.2  Viii 5.2  Viii 5.2  Viii 5.2  Viii 7  Gnd Viii 7  Gnd Viii 7  Gnd Viii 7  Viii 7  O 0.02	TEST CONDITIONS  V, Io MA  V 2  4.5  6  V, 2  4.5  6  V, 2  4.5  6  V, 3  Or -0.02  4.5  V, 4.5  6  V, 5  Or -4  4.5  V, 6  V, 6  V, 7  Or -5.2  Or 0.02  4.5  V, 7  Or 4  4.5  V, 7  Or 4  4.5  V, 7  Or 4  4.5  V, 7  Or 4  4.5  V, 7  Or 6  Or 6  V, 8  Or 6  Or 6  Or 6  Gnd  Vcc Or 0 6  Gnd  Vcc Or 0 6  Gnd  Vcc Or 0 6	TEST CONDITIONS  V, Io MA  Vcc Min  2 1.5 4.5 3.15 6 4.2 2 4.5 6  Vii, 2 1.9  or -0.02 4.5 4.4 Vii+ 6 5.9  Vii, 3 -5.2 6 5.48 Vii, 3 -5.2 6 5.48 Vii, 4 4.5  Vii, 5.2 6  Vii, 5.2 6  Vcc or 4 4.5  Gnd  Vcc or 0 6  Gnd  Vcc or 0 6  Gnd  Vcc or 0 6  Gnd  Vcc or 0 6  Gnd  Vcc or 0 6  Gnd  Vcc or 0 6  Gnd  Vcc or 0 6  Gnd  Vcc or 0 6  Gnd	TEST CONDITIONS  V, Io MIN Type  2 1.5 4.5 3.15 6 4.2 4.5 4.5 4.5 7.4 4.5 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.4 4.5 3.98 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 6 5.48 7.5 7.5 6 5.48 7.5 7.5 7.5 7.5 7.5 7.5 7.5 7.5 7.5 7.5	TEST CONDITIONS  V, Io Min Typ Max  2 1.5 0.5 4.5 3.15 0.5 4.5 1.35 6 1.35 6 1.35 7	CONDITIONS         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE         TYPE	TEST CONDITIONS   TAHC/54HC TYPE   T4HC TYPE	TEST CONDITIONS    74HC/54HC TYPE	TEST CONDITIONS  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Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Type   Ty

^{*} For dual-supply systems theoretical worst case (V₁ = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads*
All	0.5

^{*}Unit Load is  $\Delta I_{CC}$  limit specified in Static Characteristic Chart, e.g., 360  $\mu$ A max. @ 25° C.

[•] When testing I_{IL} the Qoutput must be high. If Q is low (device not triggered) the pull-up P device will be ON and the low resistance path from V_{DD} to the test pin will cause a current far exceeding the specification.

SWITCHING CHARACTERISTICS (Vcc = 5 V, TA = 25°C, Input t, t = 6 ns)

CHARAC	CTERISTIC		CL	TYP	ICAL	UNITS
CHARA			(pF)	54/74HC	54/74HCT	Oldino
Propaga	tion Delay					
_	A, B to Q	t _{PLH}	15	21	23	ns
	A, B to Q	t _{PHL}	15	21	23	ns
_	R to Q	t _{PHL}	15	21	17	ns
-	$\overline{R}$ to $\overline{Q}$	t _{PLH}	15	21	21	ns
Power D	issipation Capacitance	C _{PD} *	_	136	134	pF

^{*}CPD is used to determine the dynamic power consumption, per one shot.

assuming  $f_i \ll \frac{1}{\tau}$ 

#### PREREQUISITE FOR SWITCHING FUNCTION

								LIM	ITS						
		ļ		25°	, C		-4	0° C to	+85°	С	-55	° C to	+125	° C	]
CHARACTERISTIC	SYMBOL	V _{cc}	Н	С	Н	СТ	74	НС	74H	ICT	54	нС	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Input Pulse Widths		2	80	_	_	_	100	_	-	_	120	_	_	_	
A, B	twn	4.5	16	-	16		20	_	20	_	24	i —	24		ns
	tw∟	6	14			_	17	_			20	_			
		2	80	_		_	100	_	_	_	120	_	_	_	
R	t _{WL}	4.5	16	_	20	l —	20	-	25	_	24	_	30	l —	ns
	i	6	14	<b> </b>	-	_	17	—	_	-	20	_	_	—	ŀ
Reset Recovery		2	5	<b>—</b>	_	_	5	-	_	T-	5	_	_	_	
Time	t _{REC}	4.5	5	l —	5	_	5	_	5	-	5	l —	5	_	ns
		6	5		_	_	5			<u> </u>	5	_	_		Ì
Retrigger Time			Турі		oical										
(See Fig. 5)	t _{rr}	5		17	75		}								ns

 $P_D = (C_{PD} + C_x) V_{CC}^2 f_i + \sum (C_L V_{CC}^2 f_o)$  where:

f_i = input frequency.

fo = output frequency.

C_L = output load capacitance.

V_{CC} = supply voltage.

### SWITCHING CHARACTERISTICS (CL = 50 pF, Input t, tr = 6 ns)

				25	°C		-4	0°C to	o +85°	C	-5				
CHARACTERISTIC	SYMBOL	Vcc	Н	С	Н	СТ	74	нс	74F	ICT	54	нс	54H	<b>ICT</b>	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PLH}	2	_	250	_	_	_	315	_	_	_	375	_	_	
A, $\overline{B}$ to Q		4.5	-	50	_	55	l —	63	—	69	—	75	_	83	ns
		6		43				54		_	_	64		_	
		2	_	250	_	_	-	315	_	-	_	375	-	_	
A, $\overline{B}$ to $\overline{Q}$	t _{PHL}	4.5	—	50	_	55	—	63	—	69		75	_	83	ns
		6		43	_	_		54	<u> </u>	_	_	64			
		2	_	250	_	_	_	315	_	—	_	375	_	_	
R to Q	t _{PHL}	4.5	—	50	_	40	_	63	_	50	—	75	—	60	ns
		6		43	_	_		54				64		<u> </u>	
		2	_	250	_	_	_	315	_	_	_	375	_	_	
R̄ to Q̄	t _{PLH}	4.5	_	50	_	50	_	63	_	63		75		75	ns
		6		43		_	_	54			_	64		l —	
Output	t _{TLH}	2	_	75	_	_	-	95	_	_	_	110	_		
Transition Time	t _{THL}	4.5	-	15	_	15	_	19	_	19	—	22	—	22	ns
		6	_	13	_	_		16			_	19		<u> </u>	
Output Pulse		3	0.64	0.78		_	0.612	0.812			0 605	0.819	_		
Width	τ	5	0.63	0.77	0.63			1	1					0.805	ms
Rx=10 $\Omega$ , Cx=0.1 $\mu$ F			0.03	0.77	0.00	0.77	0.002	0.730	0.002	0.730	0.555	0.603	0.555	0.003	1115
Output Pulse Width															
Match, Same Pkg.				Тур	± 1%										
Input Capacitance	Ci		_	10		10	_	10	_	10	_	10		10	pF

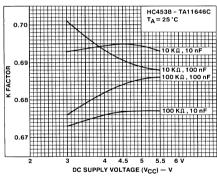


Fig. 2 - K Factor Vs DC Supply Voltage (Vcc)-V.

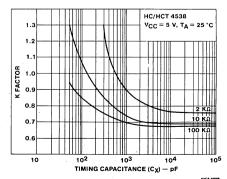


Fig. 4 - K Factor Vs Cx.

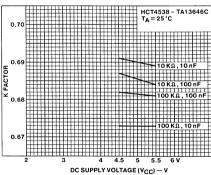


Fig. 3 - K Factor Vs DC Supply Voltage (Vcc)-V.

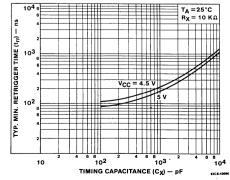
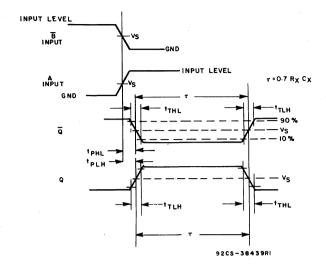
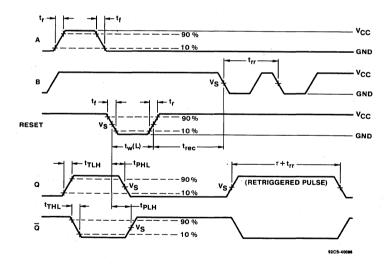


Fig. 5 - Minimum Retrigger Time Vs Timing Capacitance.





	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, VS	50% VCC	1.3 V

Fig. 6 - Switching Waveforms

#### Power-Down Mode

During a rapid power-down condition, as would occur with a power-supply short circuit or with a poorly filtered power supply, the energy stored in  $C_x$  could discharge into Pin 2 or 14. To avoid possible device damage in this mode, when  $C_x$  is  $\geq 0.5$  microfarad, a protection diode with a 1-ampere or higher rating (1N5395 or equivalent) and a separate ground return for  $C_x$  should be provided as shown in Fig. 7.

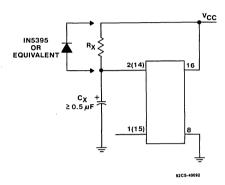


Fig. 7 — Rapid power-down protection circuit.

An alternate protection method is shown in Fig. 8, where a 51-ohm current-limiting resistor is inserted in series with  $C_x$ . Note that a small pulse width decrease will occur however, and  $R_x$  must be appropriately increased to obtain the originally desired pulse width.

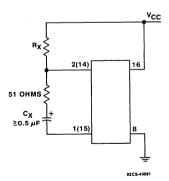
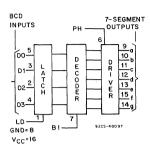


Fig. 8 — Alternate rapid power-down protection circuit.

## **High-Speed CMOS Logic**



**FUNCTIONAL DIAGRAM** 

## BCD-to-7 Segment Latch/ Decoder/Driver for LCDs



#### Type Features:

- Input latches for BCD code storage
- Blanking capability
- Phase input for complementing outputs

The RCA CD54/74HC4543 and CD54/74HCT4543 high-speed silicon-gate devices are BCD-to-7 segment latch/decoder/drivers designed primarily for directly driving liquid-crystal displays. They have an active-high disable input (LD), an active high blanking input (BI) and a phase input (PH) to which a square wave is applied for liquid-crystal applications. This square wave is also applied to the backplane of the liquid-crystal display.

These devices can also be used, in conjunction with current amplifying devices, for driving LEDs, incandescent, fluorescent, and gas-discharge displays. For these applications the phase input provides a means for obtaining active-high or active-low segment outputs. (See Function Table.)

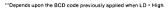
The CD54HC/HCT4543 are supplied in 16-lead ceramic dual-in-line frit-seal packages (F suffix). The CD74HC/HCT-4543 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

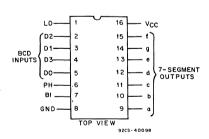
#### **Family Features:**

- Fanout (over temperature range):
   Standard outputs 10 LSTTL loads
   Bus driver outputs 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity:
  - N_{IL}=30%, N_{IH}=30% of V_{CC}; @ V_{CC}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min.
  - CMOS input compatibility I₁≤1 µA @ Vol., Voh

#### **FUNCTION TABLE**

		II	NPUT	S					OI	JTPU	DISPLAY			
LD	BI	PH	D3	D2	D1	D0	a	b	С	d	e	1	g	DISPLAT
Х	Н	L	Х	Χ.	Х	X	L	L	L	L	L	L	L	Blank
Н	L	L	L	L	L	L	н	Н	н	Н	Η.	Н	L	0
н	L	L	L	L	L	н	L	н	н	L	L	L	L	1
н	L	L	L	L	н	L	н	н	L	Н	н	L	Н	2
н	L	L	L	L	н	н	н	н	H	н	L	L	Н	3
н	L	L	L	Н	L	L	L	н	н	L	L	н	н	4
н	L	L	L	н	L	н	н	L	н	н	L	н	н	5
н	L	L	L	н	н	L	н	L	н	н	н	н	Н	6
н	L	L	L	н	н	н	н	н	н	L	L	L	L	7
н	L	L	н	L	L	L	н	н	н	н	н	н	н	8
н	L	L	н	L	L	н	н	н	н	н	L	н	н	9
н	L	L	н	L	н	L	L	L	L	L	L	L	L	Blank
н	L	L	н	L	н	н	L	L	L	L	L	L	L	Blank
н	L	L	н	н	L	L	L	L	L	L	L	L	L	Blank
н	L	L.	н	н	L	н	L	L	L	L	L.	L	L	Blank
н	L	L	н	н	н	L	L	L	L	L	L	L	L	Blank
) н	L	L	lн	н	н	н	L	L	L	L	L	L	L	Blank
L	L	L	x	Х	х	Х	x							
as a	bove	Н	as above					inverse of above					. as above	





TERMINAL ASSIGNMENT

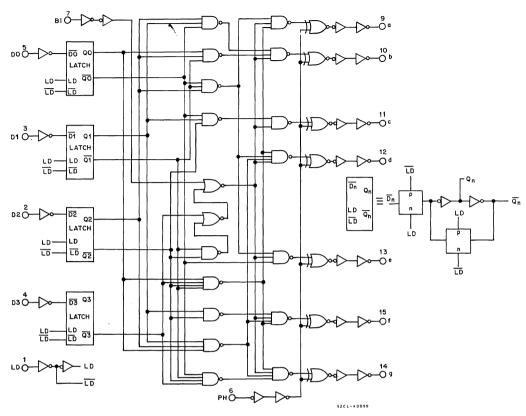


Fig. 1 - Logic diagram.

# **MAXIMUM RATINGS,** Absolute-Maximum Values: DC SUPPLY-VOLTAGE, (V_{CC}):

DO SOFFLI-VOLTAGE, (VCC).	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, IIK (FOR VI < -0.5 V OR VI > VCC +0.5 V)	±20 mA
DC OUTPUT DIODE CURRENT, IOK (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (I _o ) (FOR -0.5 V < V _o < V _{cc} +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT (Icc)	
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	
For T _A = -55 to +100°C (PACKAGE TYPE F,H)	500 mW
For T _A = +100 to +125°C (PACKAGE TYPE F,H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/° C to 70 mW
OPERATING-TEMPERATURE RANGE (TA):	
PACKAGE TYPE F,H	55 to +125° C
PACKAGE TYPE E,M	40 to +85° C
STORAGE TEMPERATURE (Tstg)	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300°C

#### **RECOMMENDED OPERATING CONDITIONS**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

OHADA OTERIOTIO	LIN	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For TA=Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	l v
CD54/74HCT Types	4.5	5.5	\
DC Input or Output Voltage, V _I , V _O	0	Vcc	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°c
CD54 Types	-55	+125	
Input Rise and Fall Times, t _r ,t _f :		T	
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.

#### SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input trt=6 ns)

			TYPICAL			
CHARACTERISTIC		C _L (pF)	HC	HCT	UNITS	
Propagation Delay:	t _{PLH}	45	00	20		
D _n to Output	t _{PHL}	15	28	33		
	t _{PLH}	15	31	32		
LD to Output	t _{PHL}	15	31	32	ns	
	t _{PLH}	15	22	27	_ 115	
BI to Output	t _{PHL}	15	22	21		
	t _{PLH}	15	17	27		
PH to Output	t _{PHL}	15	17	21		
Power Dissipation Capacitance*	C _{PD}	T - 1	52	54	pF	

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

 $P_D = C_{PD} V_{CC}^2 fi + \Sigma C_L V_{CC}^2 f_o$  where  $f_i = input$  frequency

fo = output frequency

C_L = output load capacitance

V_{cc} = supply voltage.

### PRE-REQUISITE FOR SWITCHING FUNCTION

			LIMITS												
		TEST	25°C -40°C to +85°C						-5	]					
CHARACTERISTIC		CONDITIONS	Н	C	НСТ		74HC		74HCT		54HC		54HCT		UNITS
		V _{cc} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Setup Time,	tsu	2	60		_		75			-	90		_	_	
D _n to LD		4.5	12	-	12	_	15	_	15	_	18	_	18	_	
		6	10	-	_	_	13	_		_	15	-	<b> </b> —	-	Ì
Hold Time,	tн	2	30	_	_	T	40	-	_	_	45	_	<u> </u>	T-	
D _n to LD		4.5	6	_	8	_	8	_	10	-	9	<b> </b>	12	—	ns
		6	5	_	_	l —	7	-	—	—	8		_		
Latch Disable		2	50	_	-	Γ-	65	T —	Γ=	_	75	-	_	1-	1
Pulse Width,	tw	4.5	10	-	10	—	13	-	13	<b> </b>	15	l —	15	—	
		6	9	l —	l —	l —	11	_	l —	_	13	l —	-	l –	

#### STATIC ELECTRICAL CHARACTERISTICS

				CD74	HC4	543/C	:D54H	IC454	3			C	D741	HCT4	543/C	:D54H	ICT45	543			
QUADA OTERIO			TEST CONDITIONS			74HC/54HC 74HC TYPES TYPES				54HC TYPES		TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES		LIMITE
CHARACTERISTIC		V _I I _O V _{CC}		+25° C			-40/ +85°C		5/ 5°C	Vı	Vcc		+25°C	;		-40/ +85° C		5/ 5°C	UNITS		
		v	mA	V	Min	Тур	Max	Min	Max	Min	Max	٧	٧	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	-	_	1.5	-	1.5	-		4.5								
Input Voltage	ViH		}	4.5	3.15	_	_	3.15	_	3.15	-	_	to	2	—	-	2	-	2	—	٧
		L		6	4.2			4.2	_	4.2	_		5.5							<u> </u>	
Low-Level				2	_	_	0.5	_	0.5		0.5	• .	4.5	l	1	l				1	
Input Voltage	$V_{1L}$			4.5	_	_	1.35	_	1.35		1.35	_	to	-	—	8.0	-	8.0	-	0.8	V
				6	<u> </u>	<u> </u>	1.8	_	1.8	_	1.8		5.5					L_	_		
High-Level		VIL		2	1.9	_	_	1.9		1.9	_	VIL		ľ	ĺ	ĺ		1		l	
Output Voltage	Voh	or	-0.02	4.5	4.4	_	_	4.4		4.4	_	or	4.5	4.4	—	-	4.4	-	4.4	-	V
CMOS Loads		V _{IH}		6	5.9	_	_	5.9	_	5.9		V _{iH}		_							
		VIL	L		ļ				<u> </u>			VIL			ĺ	İ	ļ	1			
TTL Loads		or	-1	4.5	3.98	_		3.84	_	3.7		or	4.5	3.98	-	<del>-</del> .	3.84	-	3.7	-	V
Non-Standard Ou	tput	VIH	-1.3	6	5.48	_	=	5.34		5.2	느	V _{IH}	_	<u> </u>		ļ		<u> </u>	_	<u> </u>	
Low-Level		VIL		2	느	_	0.1		0.1		0.1	VIL		l	1						
Output Voltage	VoL	or	0.02	4.5	_	_	0.1	_	0.1	<u> </u>	0.1	or	4.5	-	-	0.1	_	0.1	-	0.1	V
CMOS Loads		V _{IH}	-	6	_		0.1	_	0.1	느	0.1	V _{IH}			-	<u> </u>	-		<u> </u>		
TTI 1		VIL	<u> </u>	4.5	<u> </u>	_	0.00		0.00	<u> </u>	-	V _{IL}	4.5	_	_	0.00	_	0.00			v
TTL Loads		or	1.3	4.5 6	-	_	0.26	<u> </u>	0.33	<u>-</u> -	0.4	or	4.5	-		0.26	-	0.33	-	0.4	V
Non-Standard Ou Input Leakage	itput	V _{IH}	1.3	10	-		0.26	_	0.33	<del> -</del>	0.4	V _{IH}		-	-	├—		<del> </del>	<u> </u>	┢	
Current	h	Vcc			1	1						Any Voltage							1		
Current	"	or		6	-	—	±0.1	—	±1	-	±1	Between	5.5	<u> </u> –	l —	±0.1	—	±1	_	±1	μΑ
		Gnd								ł		V _{cc} & Gnd						l		1	
Quiescent		Vcc		<u> </u>	<u> </u>	_	<del> </del>	<del> </del>	H-	-		Vcc		<del>                                     </del>	<del>                                     </del>	-	<del> </del>	-	$\vdash$	$\vdash$	
Device Current	Icc	or	0	6	_	_	8	_	80	_	160	or	5.5	_	_	8	l_	80	_	160	μA
		Gnd		1			-					Gnd			l						<b>,</b>
Additional			L	Ь	Ь		Ь——	—		Ь	_			_	_	_	_	_	_	t	
Quiescent Device													4.5	ĺ			ĺ	ĺ		ĺ	'
Current per input												V _{cc} -2.1	to	_	100	360	-	450	-	490	μΑ
pin: 1 unit load	Δlcc*												5.5							1	

^{*}For dual-supply systems theoretical worst case ( $V_1$  = 2.4 V,  $V_{CC}$  = 5.5 V) specification is 1.8 mA.

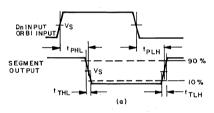
### **HCT Input Loading Table**

Input	Unit Loads*
D0, D1, D2	1
D3, BI	0.5
PH	1.25
LD	1.5

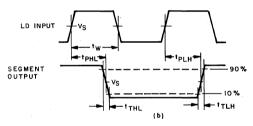
^{*}Unit Load is  $\Delta I_{CC}$  limit specified in Static Characteristics Chart, e.g., 360  $\mu A$  max. @ 25° C.

### SWITCHING CHARACTERISTICS (CL=50 pF, Input t,,t=6 ns)

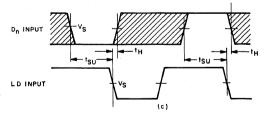
			LIMITS												
				25°C			-4	0°C t	o +85°	°C	-5	1			
CHARACTERIS	CHARACTERISTIC		Н	IC	Н	CT	74	нС	74F	ICT	54	НС	54 F	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Propagation Delay,	t _{PLH}	2	T -	340	_	_	_	425	_	_	_	510	_	_	
D _n to Output	tpHL	4.5	l —	68	_	80	l —	85	_	100	_	102	_	120	ns
		6	] —	58	_		l —	72	_		—	87	_	_	
	t _{PLH}	2		370	_	_	_	465	_	_		555	_	_	
LD to Output	t _{PHL}	4.5	l —	74	_	77		93	l —	96	<u> </u>	111	_	116	ns
		6	l —	63	_		_	79	l —	—	_	94	_	—	
	t _{PLH}	2	<b>—</b>	265				330	_		_	400	_	_	
BI to Output	t _{PHL}	4.5	l —	53	l —	66	<u> </u>	66	l —	83	l —	80	l —	99	ns
		6		45	l —	l —	_	56	l —		—	68		—	
	t _{PLH}	2	_	200		_	_	250	_	_	_	300	_	_	
PH to Output	t _{PHL}	4.5	-	40	l —	66	_	50	_	83	l —	60	—	99	ns
		6	-	34	_		_	43	—	<b> </b> —	—	51	<b> </b>	—	
	t _{TLH}	2	T-	250	_	_	_	315	_		_	375	_	<b>—</b>	
Transition Time	t _{THL}	4.5	_	50	l —	50	_	63	—	63		75	l —	75	ns
		6		43	l —	_	_	54	_	—	—	64	—		
Input Capacitance	Cı		-	10	1-	10		10	<u> </u>	10	T —	10	<b>—</b>	10	pF



(a) WAVEFORMS SHOWING THE ADDRESS AND BLANKING (D_D, BI) TO OUTPUT PROPAGATION DELAYS AND THE OUTPUT TRANSITION TIMES.



(b) WAVEFORMS SHOWING THE LATCH DISABLE INPUT (LD) TO OUTPUT PROPAGATION DELAYS AND THE OUTPUT TRANSITION TIMES.



NOTE: THE SHADED AREAS INDICATE WHEN THE INPUT IS PERMITTED TO CHANGE FOR PREDICTABLE OUTPUT PERFORMANCE.

(c) waveforms showing the address  $(\mathsf{D}_n)$  to latch disable (LD) input set-up and hold times.

92CM-40103

	54/74HC	54/74HCT
Input Level	V _{cc}	3 V
Switching Voltage, Vs	50% V _{CC}	1.3 V

Fig. 2 - AC waveforms.

#### **APPLICATION CIRCUITS**

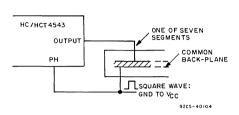


Fig. 3 - Connection to liquid-crystal (LCD) display readout.

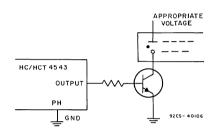


Fig. 5 - Connection to gas-discharge display readout.

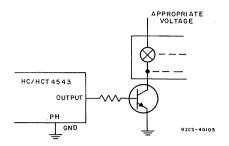


Fig. 4 - Connection to incandescent display readout.

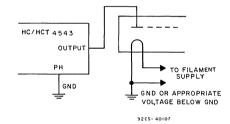
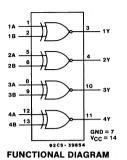


Fig. 6 - Connection to fluorescent display readout.

## **High-Speed CMOS Logic**



### **Quad 2-Input Exclusive-NOR Gate**

#### Type Features:

- Four independent Exclusive-NOR gates
- Buffered inputs and outputs

#### **Applications**

- Logical comparators
- Parity generators and checkers
- Adders/Subtracters

The RCA CD54/74HC7266 contains four independent EX-CLUSIVE-NOR gates in one package. They provide the system designer with a means for implementation of the EXCLUSIVE-NOR function.

This device is functionally the same as the TTL226. They differ in that the HC7266 has active high and low outputs whereas the 226 has open collector outputs.

The CD54HC7266 is supplied in 14-lead ceramic dual-in-line packages (F suffix). The CD74HC7266 is supplied in 14-lead plastic dual-in-line package (E suffix), in a 14-lead dual-in-line surface-mount plastic package (M-suffix), and is also available in chip form (H suffix).

#### **Family Features:**

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}, @ V_{CC} = 5 V
- CMOS Input Compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}

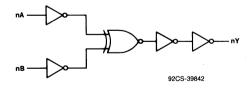


Fig. 1 - Logic diagram each gate.

### **TRUTH TABLE**

INP	INPUTS						
nA	nA nB						
L	L	н					
L	н	L.					
Н	L	L					
Н	Н	Н					

H = HIGH voltage level.

L = LOW voltage level.

### CD54/74HC7266

#### MAXIMUM RATINGS, Absolute-Maximum Values:

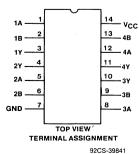
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)0.5 to +7 V	
DC INPUT DIODE CURRENT, $I_{iK}$ (FOR $V_1 < -0.5$ V OR $V_1 > V_{cc} + 0.5$ V)	
DC OUTPUT DIODE CURRENT, $I_{OK}$ (FOR $V_O < -0.5$ V OR $V_O > V_{CC} + 0.5$ V)	
DC DRAIN CURRENT, PER OUTPUT (I _O ) (FOR -0.5 V < V _o < V _{cc} + 0.5 V)±25mA	
DC V _{cc} OR GROUND CURRENT (I _{cc} )	
POWER DISSIPATION PER PACKAGE (Po):	
For $T_A = -40$ to $+60$ °C (PACKAGE TYPE E)	
For T _A = +60 to +85°C (PACKAGE TYPE E)	
For $T_A = -55$ to $+100$ °C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For $T_A = -40$ to $+70$ °C (PACKAGE TYPE M)	
For $T_A = +70$ to $+125$ °C (PACKAGE TYPE M) Derate Linearly at 6 mW/°C to 70 mW	
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M40 to +85°C	
STORAGE TEMPERATURE (Tstg)	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max. $+265^{\circ}\mathrm{C}$	
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only+300°C	

### RECOMMENDED OPERATING CONDITIONS:

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

	LIM	ITS	
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A = Full Package-Temperature Range) V _{cc} :*	2	6	V
DC Input or Output Voltage V _I , V _O	0	Vcc	V
Operating Temperature T _A : CD74 Types CD54 Types	-40 -55	+85 +125	°C
Input Rise and Fall Times t _r , t _f at 2 V at 4.5 V at 6 V	0 0 0	1000 500 400	ns

^{*}Unless otherwise specified, all voltages are referenced to Ground.



# CD54/74HC7266

#### STATIC ELECTRIC CHARACTERISTICS

		CD54/74HC7266												
CHARACTERISTIC	cc	TEST CONDITIONS				HC S		HC PE		HC PE	UNITS			
		V,	I _o	V _{cc}		+25°C			10/ 5°C		55/ 25°C			
		V	mA	V	Min.	Тур.	Max.	Min.	Max.	Min.	Max.			
				2	1.5	_	_	1.5	_	1.5	. —			
High-Level Input Voltage	$V_{IH}$			4.5	3.15	_	_	3.15		3.15	_	V		
				6	4.2	_		4.2		4.2	_			
				2			0.5	_	0.5	_	0.5			
Low-Level Input Voltage	$V_{IL}$			4.5		_	1.35		1.35	_	1.35	V		
				6	_	_	1.8	_	1.8	_	1.8			
		V _{IL}		2	1.9		_	1.9		1.9	_			
High-Level Output Voltage	$V_{OH}$	or	-0.02	4.5	4.4	-		4.4	_	4.4	_	V		
CMOS Loads		V _{IH}		6	5.9	_	_	5.9	_	5.9	_			
TTL Loads		V _{IL} or	-4	4.5	3.98	_		3.84		3.7		V		
		V _{IH}	-5.2	6	5.48		_	5.34		5.2				
		VIL		2	<u> </u>	-	0.1		0.1		0.1			
Low-Level Output Voltage	$V_{OL}$	or	0.02	4.5			0.1	_	0.1	_	0.1	v		
CMOS Loads		V _{IH}		6			0.1		0.1		0.1			
TTL Loads		V _{IL} or	4	4.5	-	_	0.26		0.33	_	0.4	v		
		V _{IH}	5.2	6	-		0.26	_	0.33	_	0.4	]		
Input Leakage Current	l ₁	V _{cc} or Gnd		6			±0.1 —	_	±1 —	_	±1 —	μΑ		
Quiescent Device Current	Icc	V _{cc} or Gnd	0	6		_	2		20		40	μΑ		

### SWITCHING CHARACTERISTICS ( $V_{cc} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, Input t_r, t_f = 6 \text{ ns}$ )

CHARACTERISTIC		C∟ pF	TYPICAL VALUES 54/74HC	UNITS
Propagation Delay, Any Input	t _{PLH} t _{PHL}	15	9	ns
Power Dissipation Capacitance*	СРД	_	33	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per gate.

 $C_{PD}$  is used to determine the dyperior  $C_{PD}$  =  $V_{CC}^2$  fi ( $C_{PD}$ + $C_L$ ) where:  $C_L$  is input frequency.  $C_L$  = output load capacitance.  $C_L$  = supply voltage.

### SWITCHING CHARACTERISTICS ( $C_L = 50 \text{ pF}$ , Input $t_r$ , $t_f = 6 \text{ ns}$ )

			25	°C	-40°C t	o +85°C	-55°C to	+125°C	
CHARACTERISTIC		Vcc	Н	C	74	НС	54	нс	UNITS
			Min.	Max.	Min. Max.		Min.	Max.	1
Propagation Delay	t _{PLH} , t _{PHL}	2	_	115	_	145	_	150	
		4.5		23	-	29	-	35	ns
		6		30	_	25		30	
Output Transition Time	t _{TLH} , t _{THL}	2	_	75	_	95	_	110	
		4.5	_	15	_	19	_	22	ns
		6		13	_	16	-	19	
Input Capacitance	Cı	_	_	10	_	10	_	10	pF

# CD54/74HC7266

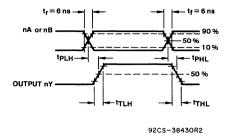
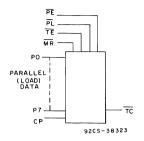


Fig. 2 - Transition times and propagation delay times.

## **High-Speed CMOS Logic**



## 8-Stage Synchronous Down Counters

40102 - 2-Decade BCD Type 40103 - 8-Bit Binary Type

### Type Features:

- Synchronous or asynchronous preset
- Cascadable in synchronous or ripple mode

#### **FUNCTIONAL DIAGRAM**

The RCA-CD54/74HC40102, 40103 and CD54/74HCT40102, 40103 are manufactured with high speed silicon gate technology and consist of an 8-stage synchronous down counter with a single output which is active when the internal count is zero. The 40102 is configured as two cascaded 4-bit BCD counters, and the 40103 contains a single 8-bit binary counter. Each type has control inputs for enabling or disabling the clock, for clearing the counter to its maximum count, and for presetting the counter either synchronously or asynchronously. All control inputs and the TC output are active-low logic.

In normal operation, the counter is decremented by one count on each positive transition of the CLOCK (CP). Counting is inhibited when the TE input is high. The TC output goes low when the count reaches zero if the TE input is low, and remains low for one full clock period.

When the  $\overline{PE}$  input is low, data at the P0-P7 inputs are clocked into the counter on the next positive clock transition regardless of the state of the  $\overline{TE}$  input. When the  $\overline{PL}$  input is low, data at the P0-P7 inputs are asynchronously forced into the counter regardless of the state of the  $\overline{PE}$ ,  $\overline{TE}$ , or CLOCK inputs. Input P0-P7 represent two 4-bit BCD words for the 40102 and a single 8-bit binary word for the 40103. When the MR input is low, the counter is asynchronously cleared to its maximum count (99₁₀ for the 40102 and 225₁₀ for the 40103) regardless of the state of any other input. The precedence relationship between control inputs is indicated in the truth table.

If all control inputs except  $\overline{\mathsf{TE}}$  are high at the time of zero count, the counters will jump to the maximum count, giving a counting sequence of 100 or 256 clock pulses long.

The 40102 and 40103 may be cascaded using the TE input and the TC output, in either a synchronous or ripple mode.

#### **Family Features:**

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85° C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types: 2 to 6 V Operation High Noise Immunity: N_{IL} = 30%, N_{IH} = 30% of V_{CC}; @ V_{CC} = 5 V
- CD54HCT/CD74HCT Types: 4.5 to 5.5 V Operation Direct LSTTL Input Logic Compatibility V_{IL} = 0.8 V Max., V_{IH} = 2 V Min. CMOS Input Compatibility I_I ≤ 1 μA @ V_{OL}, V_{OH}

These circuits possess the low power consumption usually associated with CMOS circuitry, yet have speeds comparable to low power Schottky TTL circuits and can drive up to 10 LSTTL loads.

The CD54HC40102, 40103, and CD54HCT40102, 40103 are supplied in 16-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HC40102, 40103 and CD74HCT40102, 40103 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):
(Voltages referenced to ground) -0.5 to + 7 V
DC INPUT DIODE CURRENT, I _{IK} (FOR V, < -0.5 V OR V, > V _{CC} +0.5V)
DC OUTPUT DIODE CURRENT, lok (FOR Vo < -0.5 V OR Vo > Vcc +0.5V)
DC DRAIN CURRENT, PER OUTPUT (I _o ) (FOR -0.5 V < V _o < V _{cc} + 0.5V)
DC V _{cc} OR GROUND CURRENT (I _{cc} )
POWER DISSIPATION PER PACKAGE (Pp):
For T _A = -40 to +60°C (PACKAGE TYPE E)
For T _A = +60 to +85°C (PACKAGE TYPE E)
For T _A = -55 to +100° C (PACKAGE TYPE F, H)
For T _A = +100 to +125°C (PACKAGE TYPE F, H)
For T _A = -40 to +70°C (PACKAGE TYPE M)
For T _A = +70 to +125°C (PACKAGE TYPE M)
OPERATING-TEMPERATURE RANGE (T _A ):
PACKAGE TYPE F, H
PACKAGE TYPE E, M40 to +85° C
STORAGE TEMPERATURE (T _{sto} ) -65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max. +265° C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)
with solder contacting lead tips only

### **RECOMMENDED OPERATING CONDITIONS:**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

0.000	LIN	LIMITS					
CHARACTERISTIC	MIN.	MAX.	UNITS				
Supply-Voltage Range (For TA = Full Package Temperature Range) VCC:*							
CD54/74HC Types	2	6	V				
CD54/74HCT Types	4.5	5.5	V				
DC Input or Output Voltage VI, Vo	0	Vcc	V				
Operating Temperature TA:							
CD74 Types	-40	+85	°C				
CD54 Types	-55	+125	°C				
Input Rise and Fall Times, tr, tf							
at 2 V	0	1000	ns				
at 4.5 V	0	500	ns				
at 6 V	0	400	ns				

^{*}Unless otherwise specified, all voltages are referenced to Ground.

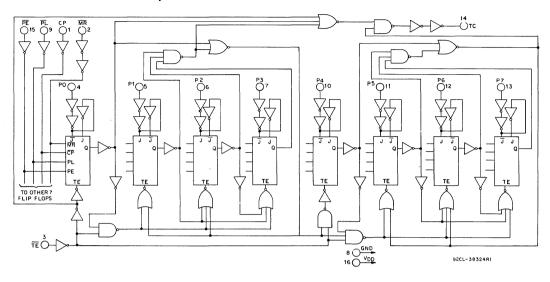


Fig. 1 - Logic diagram for the CD54/74HC/HCT40102.

#### **TRUTH TABLE**

C	ONTRO	L INPUT	s		
MR	PL	PE	TE	PRESET MODE	ACTION
1	1	1	1		Inhibit Counter
1	1 .	1	0		Count Down
1	1	0	х	Synchronous	Preset On Next Positive Clock Transition
1	0	Х	Х		Preset Asynchronously
0	Х	Х	Х	Asynchronously	Clear to Maximum Count

### Notes:

- 1. 0 = Low Level
  - 1 = High Level X = Don't Care
- Clock Connected to Clock Input.
- 3. Synchronous operation: Changes Occur on Negative-to-Positive Clock Transitions.
- 4. Load Inputs: 40102 BCD: MSD = P7, P6, P5, P4 (P7 is MSB) LSD = P3, P2, P1, P0 (P3 is MSB)

40103 Binary: MSB = P7, LSB = P0

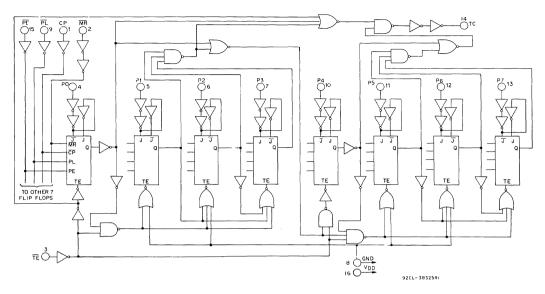
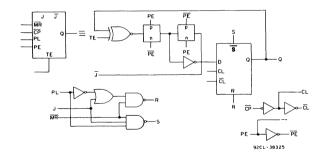


Fig. 2 - Logic diagram for the CD54/74HC/HCT40103.



Flip-Flop detail.

### STATIC ELECTRICAL CHARACTERISTICS

	103/C	D54H	C401	02-40	103		CD74H	CT401	02-40	103/0	D54F	ICT4	0102-	40103								
CHARACTERIST	ice :		TEST IDITIOI	NS		IC/54 TYPE		741 TY		54l TY		TEST			TYPE	нст	l .	ICT PE		ICT PE	UNITS	
CHARACTERIST	ics ·	V ₁ I ₀		Vcc		•25° C	:	-4 +85		-5 +12!		V ₁	Vcc		•25° C	;	1 1	0/ 5°C	i	5/ 5°C	UNITS	
		٧	mA	٧	Min	Тур	Max	Min	Max	Min	Max	V	٧	Min	Тур	Max	Min	Max	Min	Max		
High-Level				2	1.5	_		1.5		1.5	-		4.5									
Input Voltage	VIH	1 .	1	4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	-	-	2		2	_	V	
				6	4.2	_	_	4.2	_	4.2	_		5.5			L						
Low-Level		ĺ		2	_		0.5	_	0.5		0.5		4.5			Ì						
Input Voltage	VIL .	)		4.5	_		1.35		1.35	_	1.35	-	to	-	_	0.8	_	0.8	-	0.8	V	
				6	_	_	1.8	_	1.8	_	1.8		5.5									
High-Level		V _{IL}	ļ	2	1.9		_	1.9		1.9	_	VIL										
Output Voltage	$V_{OH}$	or	-0.02	4.5	4:4	_		4.4	-	4.4	_	or	4.5	4.4	_		4.4	_	4.4	_	v	
CMOS Loads		VIH		6	5.9	_	_	5.9	_	5.9	_	ViH										
1		VIL										VIL										
TTL Loads		or	-4	4.5	3.98	_	_	3.84	_	3.7	_	cr	4.5	3.98	_	_	3.84	_	3.7	_	v	
		VIH	-5.2	6	5.48	_	_	5.34	_	5.2	_	ViH		ı		ļ						
Low-Level		VIL		2	_	_	0.1	_	0.1	_	0.1	VIL										
Output Voltage	Vol	or	0.02	4.5	_	_	0.1	_	0.1	_	0.1	or	4.5	_		0.1	_	0.1	_	0.1	v	
CMOS Loads		V _{IH}		6	_	_	0.1	_	0.1	_	0.1	ViH				ŀ						
		VIL										Vil										
TTL Loads		or	4	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	_		0.26	_	0.33	_	0.4	v	
		VIH	5.2	6	_	_	0.26	_	0.33		0.4	ViH			}		1					
Input Leakage				<u> </u>													-					
Current	l _i	Vcc			ĺ				ł			Any Voltage					1	l		į		
		or		6	-	_	±0.1	-	±1	_	±1	Between	5.5	-	-	±0.1	-	±1	_	±1	μΑ	
1		Gnd		1					ĺ			V _{cc} and Gnd					l					
				-		<u> </u>			<u> </u>			- Gild				<u> </u>			<u> </u>			
Quiescent Device Current	Icc	Vcc							ŀ			Vcc										
	,,,,	or	0	6	_	_	8	_	80	_	160	or	5.5	_	-	8	_	80	_	160	μΑ	
		Gnd				}						Gnd		ļ			ļ					
Additional			L	L	L	L	L	<u> </u>	L		L			-		-		-	-			
Quiescent Device											ĺ		4.5		}		}	1				
Current per												V _{CC} -2.1	to	-	100	360	-	450	-	490	μΑ	
Input Pin:													5.5		}							
1 Unit Load	Δlcc*	1												1		1	}	1	1			

^{*}For dual-supply systems theoretical worst case ( $V_1$  = 2.4 V,  $V_{CC}$  = 5.5 V) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads *
P0 - P7	0.20
TE, MR	0.40
CP	0.60
<u>PE</u>	0.80
PL	1.35

^{*} Unit load is ΔI_{cc} limit specified in Static Characteristic Chart, e.g., 360 μA max. @ 25° C.

### SWITCHING CHARACTERISTICS ( $V_{CC}$ = 5 V, $T_A$ = 25°C, Input $t_r$ , $t_f$ = 6 ns)

OUADACTERISTIC	overnou		TYPICAL	VALUES	LINUTO
CHARACTERISTIC	SYMBOL	C∟ (pF)	нс	нст	UNITS
Propagation Delay	t _{PHL}	45	0.5	05	
CP to TC (Sync. Preset)	t _{PLH}	15	25	25	ns
	t _{PHL}	15	25	26	20
CP to TC (Async. Preset)	t _{PLH}	15	25	26	ns
	t _{PHL}	15	17	21	ns
TE to TC	t _{PLH}	15	17	21	115
	t _{PHL}	15	23	28	ns
PL to TC	t _{PLH}	15	23	20	115
	t _{PHL}	15	23	23	
MR to TC	t _{PLH}	15	23	23	ns
CP Max. Frequency	f _{MAX} .	15	25	25	MHz
Power Dissipation Capacitance*	C _{PD}		25	27	pF

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

V_{cc} = supply voltage.

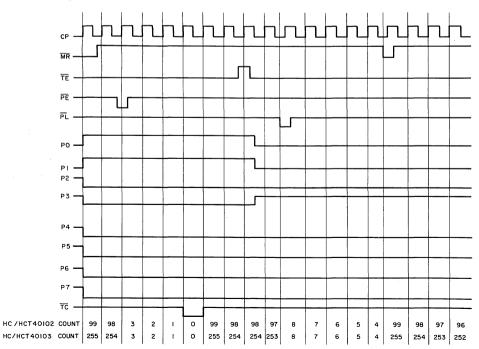


Fig. 3 - Timing diagram for HC/HCT40102 and HC/HCT40103.

 $P_D = C_{PD} V_{CC}^2 f_i + C_L V_{CC}^2 f_o$  where:

 $f_i$  = input frequency.

fo = output frequency.

C_L = output load capacitance.

### PREREQUISITE FOR SWITCHING FUNCTION

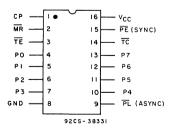
				25	°C		-4	0°C t	o +85°	C	-5	5°C to	+125	°C	
CHARACTERISTIC	SYMBOL	Vcc	Н	C	Н	СТ	74	нС	74F	ICT	54	нС	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
		2	165	_	_	_	205	_	_	_	250	_	_	_	
CP Pulse Width	tw	4.5	33	<u> </u>	35	—	41	—	44	_	50	_	53	l —	ns
		6	28	<b> </b>		—	35	_	_	_	43	_	—	_	
		2	125	-			155	_	_	_	190	_	_	_	
PL Pulse Width	tw	4.5	25	_	43	_	31	l —	54		38	—	65	_	ns
		6	21		_	l —	26	_	_		32	_	_		
		2	125	_		_	135	-	_	_	190	_	_	_	
MR Pulse Width	tw	4.5	25	_	35	-	31	—	44	-	38	-	53	_	ns
		6	21		_		26		l —		32			_	
		2	3	_	_	_	2	_	_	-	2	_	_	_	
CP Max. Frequency*	f _{CP(Max.)}	4.5	15	_	14	—	12		11	-	10	—	9	_	MHz
		6	18				14				12				
		2	100	_	_	_	125	—	l —	_	150	_		-	
P to CP Setup Time	t _{su}	4.5	20	_	24	—	25	—	30	_	30	—	36	_	ns
		6	17	_		<u> </u>	21	<u> </u>		_	26				
		2	75	—	-	—	95	—	l —	_	110	—	_	—	
PE to CP Setup Time	t _{SU}	4.5	15	—	20	—	19		25	_	22	—	30	-	ns
		6	13	_	_		16		_	_	19			_	
		2	150	-	_	-	190	_	-	_	225		_	—	
TE to CP Setup Time	t _{su}	4.5	30	_	40	—	38	_	50	-	45	—	60	-	ns
		6	26	_	_	_	33				38				
		2	5	—	—	-	5		—		5	—	_	_	
P to CP Hold Time	t _H	4.5	5		5	-	5	_	5	-	5	-	5	-	ns
		6	5			_	5	_			5				
		2	0	-	_	—	0			<u> </u>	0	-	-	-	
TE to CP Hold Time	t _H	4.5	0	_	0	—	0		0	-	0		0	—	ns
		6	0				0				0	_		_	
		2	50		_	_	65	_	_	—	75	—	_	-	
MR to CP Removal Time	t _{REM}	4.5	10	_	10	-	13	_	13	_	15	-	15		ns
		6	9	_		<u> </u>	11				13				
		2	2	_	_	-	2	—		-	2	_	_	-	
PE to CP Hold Time	t _H	4.5 6	2 2	_	2	_	2 2	_	2	_	2	_	2	_ _	ns

SWITCHING CHARACTERISTICS ( $C_L$  = 50 pF, input  $t_r$ ,  $t_f$  = 6 ns)

	SYMBOL		25° C				-40°C to +85°C				-55°C to +125°C				
CHARACTERISTIC		Vcc	НС		HCT		74HC		74HCT		54HC		54HCT		UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1
Propagation Delay	t _{PLH}	2	_	300		_	_	375	T —	_	_	450			
CP to TC	t _{PHL}	4.5	l —	60	l —	60	<u> </u>	75	<del> </del>	75	-	90	l —	90	ns
(Async Preset)		6	—	51		—	_	64	<b> </b>	—	-	77	_	_	
		2	_	300		_	_	375	_	_	_	450	_	_	
CP to TC	t _{PLH}	4.5	_	60	—	63	_	75	_	79		90	_	95	ns
(Sync Preset)	t _{PHL}	6	_	51		_	_	64	_			77	_	<u> </u>	
TE to TC		2	I —	200			_	250	_	_		300	_	Γ-	
	t _{PLH}	4.5	l —	40	_	50	_	50	_	63	_	60	_	75	ns
	t _{PHL}	6	_	34		_	_	43	_	_	_	51	_	_	
PL to TC		2	_	275	_	_	_	345	_	_	_	415	_	_	
	t _{PLH}	4.5	_	55		68	_	69	_	85	—	83	_	102	ns
	t _{PHL}	6	_	47	l —	_	_	59	_	_	_	71	-		
MR to TC		2	-	275	_	_	_	345	_	_	_	415	_	_	
	t _{PLH}	4.5	_	55	_	55	<b> </b>	69	_	69	_	83	_	83	ns
	t _{PHL}	6		47		<b> </b> —	_	59	_	l —	_	71	_	l —	
Output Transition Time		2	_	75		_	_	95	_		_	110	_	_	
	t _{TLH}	4.5	<u> </u>	15	_	15	—	19	—	19		22	-	22	ns
	t _{THL}	6	_	13	_			16	_		_	19		_	
Input Capacitance	Cı		_	10		10	_	10		10	_	10		10	pF

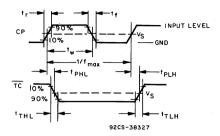
^{*}Noncascaded operation only. With cascaded counters clock-to-terminal count propagation delays, count enables (PE or TE)-to-clock SETUP TIMES, and count enables (PE or TE)-to-clock HOLD TIMES determine max. clock frequency. For example, with these HC devices:

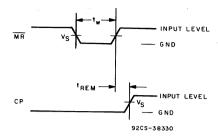
$$C_{P} f_{MAX} = \frac{1}{CP-to-\overline{TC} \text{ prop delay + } \overline{TE}-to-CP \text{ Setup Time + } \overline{TE}-to-CP \text{ Hold Time}} = \frac{1}{60+30+0} \approx 11 \text{ MHz}$$

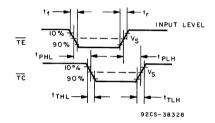


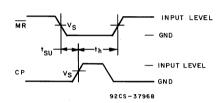
**TERMINAL ASSIGNMENT** 

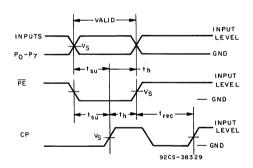
# CD54/74HC40102, CD54/74HCT40102 CD54/74HC40103, CD54/74HCT40103

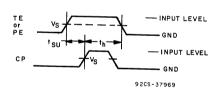








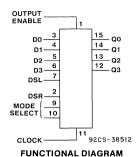




	CD54/74HC	CD54/74HCT
Input Level	Vcc	3 V
Vs	0.5 Vcc	1.3 V

Transition times, propagation delay times, setup and hold times, and removal times.

# **High-Speed CMOS Logic**



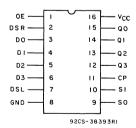
# 4-Bit Universal Bidirectional Shift Register

### Type Features:

- Four operating modes: shift right, shift left, hold and reset
- Three-state outputs
- Synchronous parallel or serial operation
- Typical  $f_{MAX}$ =50 MHz @  $V_{CC}$  = 5 V,  $C_L$  = 15 pF,  $T_A$  = 25° C

The RCA-CD54/74HC40104 and CD54/74HCT40104 are 4-bit shift registers with 3-state bus interface capability. In the parallel mode (S0 and S1 are high), data is loaded into the associated flip-flop and appears at the output after the positive transition of the clock input. During parallel loading serial data flow is inhibited. Shift left and Shift right are accomplished synchronously on the positive clock edge with serial data entered at the SHIFT RIGHT and the SHIFT LEFT serial inputs, respectively. Clearing the register is accomplished by setting both mode controls low and clocking the register. When the output enable input is low, all outputs assume the high impedance state.

The CD54HC/HCT40104 are supplied in 16-lead ceramic dual-in-line packages (F suffix). The CD74HC/HCT40104 are supplied in 16-lead plastic dual-in-line packages (E suffix), also in 16-lead surface mount plastic dual-in-line packages (M suffix). These types are also available in chip form (H suffix).



TERMINAL ASSIGNMENT

### Family Features:

- Fanout (over temperature range): Standard outputs - 10 LSTTL loads Bus driver outputs - 15 LSTTL loads
- Wide operating temperature range: CD74HC/HCT: -40 to +85° C
- Balanced propagation delay and transition times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics
- CD54HC/CD74HC types: 2 to 6 V operation High noise immunity: N_{IL}= 30%, N_{IH}=30% of V_{CC}; @ V_{CC}=5 V
- CD54HCT/CD74HCT types: 4.5 to 5.5 V operation Direct LSTTL input logic compatibility V_{IL}=0.8 V max., V_{IH}=2 V min. CMOS input compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}

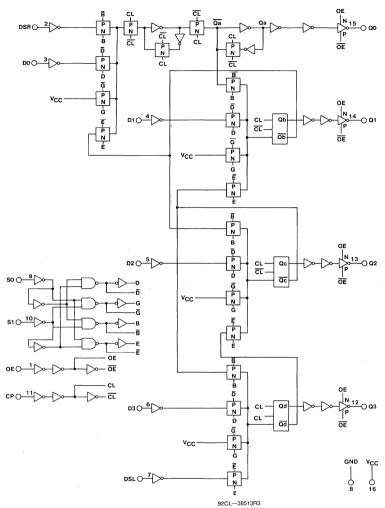


Fig. 1 - Logic diagram.

### TRUTH TABLE

	MODES	SELECT	OUTPUT	
CLOCK	S0	S1	ENABLE OE	ACTION
	L	L	Н	Reset
	н	L	Н	Shift right (Q0 toward Q3)
	L	Н	н	Shift left (Q3 toward Q0)
	н	н	Н	Parallel load
×	х	х	L	Operations occur as shown above, but outputs assume high impedance

L = Low Voltage Level

H = High Voltage Level

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, $I_{IK}$ (FOR $V_I < 0.5 \text{ V OR } V_I > V_{CC} + 0.5 \text{ V})$	±20 mA
DC OUTPUT DIODE CURRENT, $I_{OK}$ (FOR $V_O < -0.5$ V OR $V_O > V_{CC}$ +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±35 mA
DC Vcc OR GROUND CURRENT, (Icc)	±70 mA
POWER DISSIPATION PER PACKAGE (PD):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/° C to 300 mW
For T _A = -40 to +70°C (PACKAGE TYPE M)	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F, H	
PACKAGE TYPE E, M	65 to +150°C
STORAGE TEMPERATURE (T _{stg} )	65 to +150°C
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only	+300° C

### **RECOMMENDED OPERATING CONDITIONS**

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIM	LIMITS				
CHARACTERISTIC	MIN.	MAX.	UNITS			
Supply-Voltage Range (For T _A =Full Package Temperature Range)						
V _{cc} .*						
CD54/74HC Types	2	6	v			
CD54/74HCT Types	4.5	5.5	\			
DC Input or Output Voltage, V _I , V _o	0	V _{cc}	V			
Operating Temperature, T _A :						
CD74 Types	-40	+85	°c			
CD54 Types	-55	+125				
Input Rise and Fall Times, t _r ,t _f :						
at 2 V	0	1000				
at 4.5 V	0	500	ns			
at 6 V	0	400				

^{*}Unless otherwise specified, all voltages are referenced to Ground.

### STATIC ELECTRICAL CHARACTERISTICS

			CD74I	HC40	104/C	D54H	C401	04			CD74HCT40104/CD54HCT40104					104				
CHARACTERISTICS		TEST IDITIO	NS	1	IC/54 TYPE		741 TY		54H TY		TEST		74HC	TYPE		1	ICT PE		ICT PE	
CHARACTERISTICS	V _i	Io	Vcc		+25° C	;	-4 +85		-5: +12!		Vı	Vcc		•25°C	;	1	0/ 5°C	-5 +12	5/ 5°C	UNITS
	. V	mA	٧	Min	Тур	Max-	Min	Max	Min	Max	V	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level			2	1.5	<u> </u>	-	1.5	_	1.5	_		4.5								
Input Voltage V _{IH}			4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	_	2	_	2	_	· v
			6	4.2	_	_	4.2	<b> </b>	4.2	_		5.5				ŀ				
Low-Level			2	_	_	0.5	_	0.5		0.5		4.5								
Input Voltage V _{IL}	1	1	4.5	_		1.35	_	1.35	_	1.35	_	to	-	_	0.8	-	0.8	_	0.8	v
			6		_	1.8	_	1.8	_	1.8		5.5								
High-Level	VIL	١.	2	1.9	_	_	1.9	_	1.9	_	VıL									
Output Voltage V _{OH}	or	-0.02	4.5	4.4	_	_	4.4		4.4	_	or	4.5	4.4	_	_	4.4	-	4.4	-	v
CMOS Loads	V _{IH}		6	5.9			5.9	_	5.9		Vін	<u> </u>								
	VIL										VIL									
TTL Loads	or	-6	4.5	3.98	<u> </u>	_	3.84	_	3.7		or	4.5	3.98	_	_	3.84	-	3.7	_	v
(Bus Driver)	V _{IH}	-7.8	6	5.48		_	5.34	_	5.2	<u> </u>	ViH	<u> </u>	<u> </u>			İ				
Low-Level	VIL		2	_		0.1		0.1	_	0.1	VIL									
Output Voltage Vol	or	0.02	4.5	L-		0.1	_	0.1	_	0.1	or	4.5		_	0.1	-	0.1	-	0.1	v
CMOS Loads	V _{IH}		6	_		0.1	_	0.1	<u>_</u>	0.1	V _{IH}									
	VIL			<u> </u>	<u>L</u>				_		VIL		1							
TTL Loads	or	6	4.5	_	_	0.26	_	0.33	_	0.4	or	4.5	-	_	0.26	-	0.33	-	0.4	.v
(Bus Driver)	VIH	7.8	6	_	_	0.26		0.33	<u></u>	0.4	V _{IH}	<u> </u>								
Input Leakage Current I _I	V _{cc} or Gnd		6	_	-	±0.1	_	±1	_	±1	Any Voltage Between V _{cc} and Gnd	5.5	-	_	±0.1	_	±1	_	±1	μΑ
Quiescent Device Current Icc	V _{cc} or Gnd	0	6	_	_	8	_	80	_	160	V _{cc} or Gnd	5.5	-		8	_	80	_	160	μΑ
Additional Quiescent Device Current per Input Pin: 1 Unit Load			•								V _{cc} -2.1	4.5 to 5.5	_	100	360	_	450	_	490	μΑ
3-State Leakage Current	V _{IL} or V _{IH}	Vo= Vcc or Gnd	6	_	-	±0.5	_	±5	-	±10	V _{IL} or V _{IH}	5.5	-	-	±0.5	-	±5	-	±10	μΑ

^{*}For dual-supply systems theoretical worst case ( $V_i$  = 2.4 V,  $V_{cc}$  = 5.5 V) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads*
OE	1.4
DSR, DSL, D0-D3	0.3
S1, S2	0.7
СР	0.3

^{*}Unit load is  $\Delta$  I_{cc} limit specified in Static Characteristics Chart, e.g., 360  $\mu$ A max. @ 25° C.

### SWITCHING CHARACTERISTICS (Vcc=5 V, TA=25°C, Input tr,tr=6 ns)

		TYP		
CHARACTERISTIC	SYMBOL	VAL HC	HCT	UNITS
Maximum Frequency (C _L = 15 pF)	f _{MAX}	56	50	MHz
Propagation Delay: (C _L = 15 pF) CP to Qn	t _{PLH} t _{PHL}	17	18	
Output Disable Time	t _{PLZ} t _{PHZ}	14	18	ns
Output Enable Time	t _{PZL} t _{PZH}	12	12	
Power Dissipation Capacitance	C _{PD} *	84	85	ρF

 $^{^{\}star}C_{PD}$  is used to determine the dynamic power consumption, per device. PD= $C_{PD}$   $V_{cc}^2$  fi +  $\Sigma$  ( $C_L$   $V_{cc}^2$  fo) where: f,=input frequency f_=output frequency  $C_L$ =output load capacitance

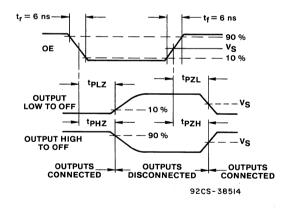
V_{cc}=supply voltage

### Pre-requisite for Switching Function

			25°C			-4	0°C to	o +85°	C	-5							
CHARACTERISTIC	SYMBOL	SYMBOL	SYMBOL	Vcc	Н	С	Н	СТ	74	НС	74H	ICT	54	нС	.541	НСТ	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	1		
Maximum Clock		2	6	-	_	_	5	_			4	_	_	_			
Frequency	f _{MAX}	4.5	28	—	25	—	22	—	20	<b> </b> -	19	—	17	-	MHz		
		6	33	—	—	—	26	—	_	—	22	_	_	-			
Clock Pulse		2	80				100	_	_	_	120	_	_	-			
Width	tw	4.5	16	—	16	_	20	_	20	—	24	_	24	-			
		6	14	l —	—	] —	17	_	_	_	20	_	_	—			
Setup Times Dn,		2	80		_		100		_		120	_	_	_	1		
DSL, DSR, S1,	tsu	4.5	16	-	20	l —	20	_	25	_	24	—	30	-	ns		
and S0 to Clock		6	14	—		-	17	—	_	<b> </b> -	20	<u> </u>	_	—	]		
Hold Times Dn,		2	2	<b>—</b>	T-	_	2		_	_	2	_	_	_	1		
DSO, DSI, S1,	t _H	4.5	2	l —	2	_	2	_	2	-	2	_	2	l —	1		
and S0 to Clock		6	2	_		—	2		_	_	2	_	_	—	]		

### SWITCHING CHARACTERISTICS (CL=50 pF, Input t,,t,=6 ns)

					°C		-4	0°C t	o +85°	C	-5					
CHARACTERISTIC	SYMBOL	SYMBOL	Vcc	Н	C	H	CT	74	нС	74H	ICT	54	нС	54H	ICT	UNITS
			Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.		
Propagation Delay	t _{PLH}	2	_	200	_	T-	_	250	_	_	_	300	_	_		
CP to Qn	t _{PHL}	4.5	l —	40	_	42	_	50	_	53	_	60	_	63		
		6	_	34	<b>—</b>	—	_	43	_	—	_	51	_			
Output Disable	tplz	2		175	_	—	_	219	_	_	_	263	_	_		
Time	t _{PHZ}	4.5	-	35	_	44	_	44	_	55	<u> </u>	53	l —	66		
		6	-	30	_	-	_	37	_	_	—	45	—	l —	ns	
Output Enable	t _{PZL}	2	I -	150		_	_	188	_	_	_	225	_	_	'''	
Time	t _{PZH}	4.5	-	30	_	30		38	_	38	-	45	—	45		
		6	l —	26	_	—	_	32	_	—	—	38	_	l —		
Output Transition	t _{TLH}	2	_	60	_	_	_	75	_	_	_	90	_	_		
Time	t _{THL}	4.5	—	12	_	12	_	15	<u> </u>	15	—	18	_	18		
		6	l —	10	_	—		13	_	—	l —	15	l —	—		
3-State Output Capacitance	Co			20	_	20	_	20		20	-	20	-	20	pF	
Input Capacitance	Cı		1 —	10	_	10	_	10	_	10	_	10	_	10	1	





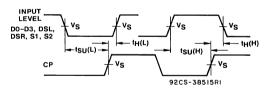
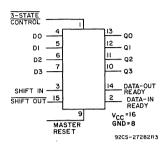


Fig. 3 - Setup and hold times.

	54/74HC	54/74HCT
Input Level	VCC	3 V
Switching Voltage, V _S	50% VCC	1.3 V

# **High-Speed CMOS Logic**



**FUNCTIONAL DIAGRAM** 

# 4-Bit x 16-Word FIFO Register

### Type Features:

- Independent asynchronous inputs and outputs
- Expandable in either direction
- Reset capability
- Status indicators on inputs and outputs
- 3-state outputs
- Shift-out independent of 3-state control

### Applications:

- Bit-rate smoothing
- CPU/terminal buffering
- Data communications
- Peripheral buffering
- Line printer input buffers
- Auto-dialers
- CRT buffer memories
- Radar data acquisition

The RCA-CD54/74HC40105 and CD54/74HCT40105 are high-speed silicon-gate CMOS devices that are compatible, except for "shift-out" circuitry, with the RCA-CD40105B. They are low-power first-in-first-out (FIFO) "elastic" storage registers that can store 16 four-bit words. The 40105 is capable of handling input and output data at different shifting rates. This feature makes it particularly useful as a buffer between asynchronous systems.

Each word position in the register is clocked by a control flip-flop, which stores a marker bit. A "1" signifies that the position's data is filled and a "0" denotes a vacancy in that position. The control flip-flop detects the state of the preceding flip-flop and communicates its own status to the succeeding flip-flop. When a control flip-flop is in the "0" state and sees a "1" in the preceding flip-flop, it generates a clock pulse that transfers data from the preceding four data latches into its own four data latches and resets the preceding flip-flop to "0". The first and last control flip-flops have buffered outputs. Since all empty locations "bubble" automatically to the input end, and all valid data ripple through to the output end, the status of the first control flip-flop (DATA-IN READY) indicates if the FIFO is full, and the status of the last flip-flop (DATA-OUT READY) indicates if the FIFO contains data. As the earliest data are removed from the bottom of the data stack (the output end), all data entered later will automatically propagate (ripple) toward the output.

### **Loading Data**

Data can be entered whenever the DATA-IN READY (DIR) flag is high, by a low to high transition on the SHIFT-IN (SI) input. This input must go low momentarily before the next word is accepted by the FIFO. The DIR flag will go low momentarily, until the data have been transferred to the second location. The flag will remain low when all 16-word locations are filled with valid data, and further pulses on the SI input will be ignored until DIR goes high.

### **Family Features:**

- Fanout (Over Temperature Range): Standard Outputs - 10 LSTTL Loads Bus Driver Outputs - 15 LSTTL Loads
- Wide Operating Temperature Range: CD74HC/HCT: -40 to +85°C
- Balanced Propagation Delay and Transition Times
- Significant Power Reduction Compared to LSTTL Logic ICs
- Alternate Source is Philips/Signetics
- CD54HC/CD74HC Types:
- 2 to 6 V Operation High Noise Immunity:  $N_{IL} = 30\%$ ,  $N_{IH} = 30\%$  of  $V_{CC}$ , @  $V_{CC} = 5$  V
- CD54HCT/CD74HCT Types:
  - 4.5 to 5.5 V Operation
  - Direct LSTTL Input Logic Compatibility  $V_{IL} = 0.8 \text{ V Max.}, V_{IH} = 2 \text{ V Min.}$
  - $V_{IL} = 0.8 \text{ V Max.}, V_{IH} = 2 \text{ V MIN.}$ CMOS Input Compatibility
- $I_1 \leq 1 \,\mu A \oplus V_{OL}, V_{OH}$

### **Unloading Data**

As soon as the first word has rippled to the output, the data-out ready output (DOR) goes HIGH and data of the first word is available on the outputs. Data of other words can be removed by a negative-going transition on the shift-out input (SO). This negative-going transition causes the DOR signal to go LOW while the next word moves to the output. As long as valid data is available in the FIFO, the DOR signal will go high again, signifying that the next word is ready at the output. When the FIFO is empty, DOR will remain LOW, and any further commands will be ignored until a "1" marker ripples down to the last control register and DOR goes HIGH.

If during unloading SI is HIGH, data on the data input of the FIFO is entered in the first location.

### **Master Reset**

A high on the MASTER RESET (MR) sets all the control logic marker bits to "0". DOR goes low and DIR goes high. The contents of the data register are not changed, only declared invalid, and will be superseded when the first word is loaded. Thus, MR does not clear data within the register but only the control logic. If the shift-in flag (SI) is HIGH during the master reset pulse, data present at the input (D0 to D3) are immediately moved into the first location upon completion of the reset process.

### 3-State Outputs

In order to facilitate data busing, 3-state outputs (Q0 to Q3) are provided on the data output lines, while the load condition of the register can be detected by the state of the DOR output. A HIGH on the 3-state control flag (output enable input OE) forces the outputs into the high-impedance OFF-state mode. Note that the shift-out signal, unlike that in

the RCA-CD40105B, is independent of the 3-state output control. In the CD40105B, the 3-state control must not be shifted from High to Low when the shift-out signal is Low (data loss would occur). In the high-speed CMOS version this restriction has been eliminated.

### Cascadina

The 40105 can be cascaded to form longer registers simply by connecting the DIR to SO and DOR to SI. In the cascaded mode, a MASTER RESET pulse must be applied after the supply voltage is turned on. For words wider than four bits, the DIR and the DOR outputs must be gated together with AND gates. Their outputs drive the SI and SO inputs in parallel, if expanding is done in both directions (see Figs. 3 and 4).

The CD54HC40105 and CD54HCT40105 are supplied in 16-lead hermetic dual-in-line frit-seal ceramic packages (F suffix). The CD74HC40105 and CD74HCT40105 are supplied in 16-lead dual-in-line plastic packages (E suffix) and in 16-lead dual-in-line surface-mount plastic packages (M suffix). Both types are also available in chip form (H suffix).

### MAXIMUM RATINGS, Absolute-Maximum Values:

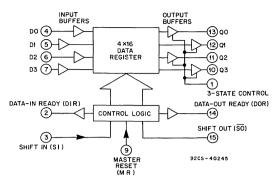
DC SUPPLY-VOLTAGE, (Vcc):	
(Voltages referenced to ground)0.5 to +7 V	/
DC INPUT DIODE CURRENT, $I_{ik}$ (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	
DC OUTPUT DIODE CURRENT, $l_{OK}$ (FOR $V_{o}$ < -0.5 V OR $V_{o}$ > $V_{CC}$ +0.5 V)	
DC DRAIN CURRENT, PER OUTPUT (I₀) (FOR -0.5 V < V₀ < V₀c +0.5 V)	l.
DC V _{cc} OR GROUND CURRENT (I _{cc} )	١.
POWER DISSIPATION PER PACKAGE (P₀):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	/
For T _A = +60 to +85°C (PACKAGE TYPE E)	1
For T _A = -55 to +100° C (PACKAGE TYPE F, H)	/
For T _A = +100 to +125°C (PACKAGE TYPE F, H)	
For T _A = -40 to +70°C (PACKAGE TYPE M)	/
For T _A = +70 to +125° C (PACKAGE TYPE M)	/
OPERATING-TEMPERATURE RANGE (T _A ):	
PACKAGE TYPE F, H	;
PACKAGE TYPE E, M40 to +85° C	)
STORAGE TEMPERATURE (Tatg)65 to +150° C	)
LEAD TEMPERATURE (DURING SOLDERING):	
At distance 1/16 $\pm$ 1/32 in. (1.59 $\pm$ 0.79 mm) from case for 10 s max. +265° C + +265° C	;
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	
with solder contacting lead tips only+300° C	)

### **RECOMMENDED OPERATING CONDITIONS**

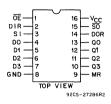
For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	MITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*			
CD54/74HC Types	2	6	v
CD54/74HCT Types	4.5	5.5	<b>V</b>
DC Input or Output Voltage, V _I , V _O	0	Vcc	٧
Operating Temperature, T _A :			
CD74 Types	-40	+85	°c
CD54 Types	-55	+125	- 0
Input Rise and Fall Times, t,tf:			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	

^{*}Unless otherwise specified, all voltages are referenced to Ground.







**TERMINAL ASSIGNMENT** 

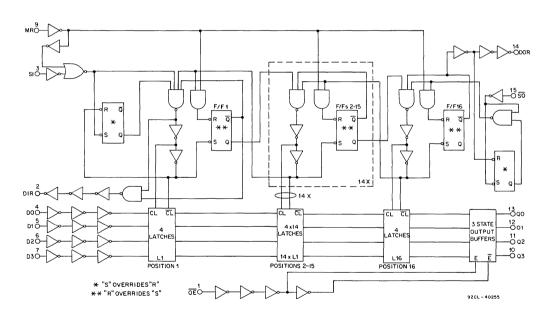


Fig. 2 - Logic diagram.

### STATIC ELECTRICAL CHARACTERISTICS

				CD741	HC40	105/C	D54H	IC401	05			CI	074H	CT40	105/C	:D54H	ICT40	)105			
		TEST CONDITIONS		1	4HC/54HC 74HC TYPES TYPES			54HC TYPES		TEST CONDITIONS		74HCT/54HCT TYPES			74HCT TYPES		54HCT TYPES				
CHARACTERIS	RISTIC		lo	Vcc	-	25° C	;	-4 +85		-5 +12		<b>V</b> ı	<b>V</b> cc		+25°C		ı	0/ 5°.C	-5 +12	5/ 5°C	UNITS
		v	mA	v	Min	Тур	Max	Min	Max	Min	Max	٧	V	Min	Тур	Max	Min	Max	Min	Max	
High-Level				2	1.5	_	_	1.5	=	1.5			4.5								
Input Voltage	ViH	ŀ	·	4.5	3.15	_	_	3.15	_	3.15	_	_	to	2	_	l –	2	l –	2	_	V
		ľ		6	4.2	_	_	4.2	-	4.2	_		5.5					}			
Low-Level				2	_	_	0.5	_	0.5	_	0.5		4.5								
Input Voltage	$V_{tL}$	1	1	4.5		_	1.35		1.35		1.35	_	to	-	—	0.8	—	0.8	—	0.8	V
				6		-	1.8	_	1.8	_	1.8		5.5								
High-Level		VIL		2	1.9	-		1.9		1.9	<u> </u>	V _{IL}						1			
Output Voltage	$V_{OH}$	or	-0.02	4.5	4.4	_		4.4	_	4.4	_	or	4.5	4.4	—	<b> </b> –	4.4	-	4.4	-	V
CMOS Loads		V _{IH}		6	5.9		_	5.9	_	5.9	_	V _{IH}									
		VIL.							L			VIL			ĺ	l	1	Ì			
TTL Loads		or	-4	4.5	3.98		_	3.84	<u> </u>	3.7	_	or	4.5	3.98	—		3.84	-	3.7	-	V
		VIH	-5.2	6	5.48	_	<u> </u>	5.34	_	5.2	_	V _{IH}									
Low-Level		VIL		2	_	<u>_</u>	0.1	<u> </u>	0.1		0.1	VIL		l			ļ	İ			
Output Voltage	Vol	or	0.02	4.5	<u> </u>		0.1		0.1	_	0.1	or	4.5	-		0.1	-	0.1	-	0.1	V
CMOS Loads		V _{IH}		6	_	_	0.1	=	0.1	<u> </u>	0.1	V _{IH}		L				<u> </u>	L		
		VIL										VIL						İ			
TTL Loads		or	4_	4.5			0.26	_	0.33		0.4	or	4.5	-	-	0.26	-	0.33	-	0.4	V
		V _{IH}	5.2	6	_	<u> </u>	0.26	<u> </u>	0.33	-	0.4	V _{IH}		Ь							
Input Leakage		Vcc		ļ								Any		1		į		1			
Current	lı	or		6	l _	_	±0.1	_	±1	l _	±1	Voltage	5.5	_	_	±0.1	_	±1	_	±1	μΑ
		Gnd			ł			l				Between							İ		
<del></del>		<del></del>			-	-	<b>├</b> ─				<u> </u>	V _{cc} & Gnd	<u> </u>	├	-	├	-	├	-		
Quiescent		Vcc	_	١.								Vcc									
Device Current	lcc	or Gnd	0	6	_	_	8	_	80	_	160	or Gnd	5.5	_	_	8	_	80	_	160	μΑ
Additional		T -												Г			$\vdash$			$\vdash$	
Quiescent Device													4.5					456		400	
Current per input												V _{cc} -2.1	to	-	100	360	-	450	-	490	μΑ
pin: 1 unit load	Δlcc*												5.5	1	1					1	
3-State Leakage		VıL	Vo=Vcc				T					VIL									
Current	loz	or:	or	6	_	_	±0.5	_	±5	_	±10	or	5.5	-	l –	±0.5	-	±5	-	±10	μΑ
		. V _{IH}	Gnd	1	l	1	]	l	1			ViH			ŀ				1	1	,

^{*}For dual-supply systems theoretical worst case (V_I = 2.4 V, V_{CC} = 5.5 V) specification is 1.8 mA.

### **HCT Input Loading Table**

Input	Unit Loads*
ŌĒ	0.75
sı, <del>so</del>	0.4
Dn	0.3
MR	1.5

^{*}Unit Load is  $\Delta I_{CC}$  limit specified in Static Characteristics Chart, e.g., 360  $\mu A$  max. @ 25° C.

### SWITCHING CHARACTERISTICS ( $V_{CC} = 5 \text{ V}, T_A = 25^{\circ}\text{C}, \text{ Input } t_r, t_f = 6 \text{ ns}$ )

CHARACTERISTIC	SYMBOL	CL	TYP	TYPICAL			
CHARACTERISTIC	STMBOL	(pF)	HC	нст	UNITS		
Propagation Delay	t _{PLH}						
	t _{PHL}						
MR to DIR, DOR	1		15	15			
SO to Qn		15	35	35	ns		
SI to DIR	t _{PHL}		18	18	7		
SO to DOR			18	18			
Maximum SI, SO Frequency	f _{max} .	15	32	32	MHz		
Power Dissipation Capacitance*	СРД	_	83	83	pF		

^{*}C_{PD} is used to determine the dynamic power consumption, per package.

PD =  $C_{PD} V_{CC}^2 f_i + \Sigma (C_L V_{CC}^2 f_o)$  where:  $f_i$  = input frequency

fo = output frequency

C_L = output load capacitance

V_{cc} = supply voltage

### PRE-REQUISITE FOR SWITCHING FUNCTION

			LIMITS												
		TEST		25	°C		-4	0°C t	o +85°	°C	-5	5°C to	+125	°C	
CHARACTER	ISTIC	CONDITIONS	Н	С	Н	CT	74HC		74HCT		54HC		54HCT		UNITS
		V _{cc} (V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
SI Pulse Width:	tw	2	80	_		_	100	_	_	_	120	_		_	
HIGH or LOW	Fig. 6	4.5	16	<b>—</b>	16	—	20	_	20	—	24	_	24	-	
		6	14			_	17			_	20		_		
SO Pulse Width	tw	2	120	_	_	_	150	_	_		180	T-	_	_	
HIGH or LOW	Fig. 7	4.5	24	l —	16	-	30	—	20		36	—	24	-	
		6	20	L		_	26				31	—	_	_	
DIR Pulse Width	tw	2	200	-	_	_	250	_	_	_	300	Γ-	_	Γ-	
HIGH or LOW	Fig. 6	4.5	40	—	40	<b> </b>	50	-	50	—	60	-	60	-	
		6	34			_	43	_	_	_	51	_	_	-	
DOR Pulse Width	t _w	2	200	_	_	_	250	_	_	_	300	Γ-		_	
HIGH or LOW	Fig. 7	4.5	40		40	—	50		50		60	_	60	-	ns
		6	34	—	<b> </b> —	—	43	—	—	l —	51	—	_	—	l i
MR Pulse Width	tw	2	120	_	_	_	150	_	_	_	180	_	_	-	
HIGH	Fig. 5	4.5	24	<b>-</b>	24	—	30	l —	30	—	36	—	36	_	
		6	20	<b> </b>		—	26	—	—	—	31	l –	_	_	
Removal Time	t _{REM}	2	50	_	_	_	65	-	_	_	75	_	_		
MR to SI	Fig. 12	4.5	10	—	15	l —	13	l —	19	—	15	<u> </u>	22		!
		6	9	_		_	11	_	_	_	13	l —		_	
Setup Time	tsu	2	5	_	_	_	5	_	_	—	5	<u> </u>	_	_	
Dn to SI	Fig. 13	4.5	5	—	0	—	5	—	0	l —	5	<b> </b> -	0	_	
		6	5				5		-	_	5				
Hold Time	t _H	2	125		_	_	155		_	_	190			_	
Dn to SI	Fig. 13	4.5	25	—	25	<b>—</b>	31	l —	31	l —	38	_	38	_	
		6	21	_			26	<u> </u>	_	_	32			—	
Maximum Pulse	f _{MAX}	2	3	_	_		2	_	_	_	2		_	_	
Frequency	Figs. 6, 7	4.5	15		15	-	12	—	12	-	10	—	10	—	MHz
SI, <del>SO</del>		6	18				14			_	12	<u>L</u>			

SWITCHING CHARACTERISTICS (C_L = 50 pF, Input t_r,t_f = 6 ns)

		LIMITS													
CHARACTERIS	TIC	Vcc		25	°C		-4	0°C to	o +85°	Č	-5	5°C to	+125	°C	
CHARACTERIS	, i i c		Н	С		CT	74	нС	74H	ICT	54	НС	54F	ICT	UNITS
		(V)	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	Min.	Max.	
Propagation Delay,	t _{PHL}	2	_	175	_	_	_	220	_	_	_	265	-	_	
	t _{PLH}	4.5		35	—	36	_	44	—	45	—	53	-	54	
MR to DIR, DOR	Fig. 5	6	_	30	<u> </u>			37	L_			45			
Propagation Delay,	t _{PHL}	2	l —	210	—		_	265	-	—	_	315		-	
		4.5	—	42	—	42	_	53	—	53	—	63		63	
SI to DIR	Fig. 6	6		36				45				54			
Propagation Delay,	t _{PHL}	2	_	210	—	—	_	265	_	—	—	315	_	—	İ
<u> </u>		4.5	—	42	—	42	_	53	—	53		63	—	63	
SO to DOR	Fig. 7	6		36			_	45				54			
Propagation Delay,	t _{PHL}	2	_	400	_		-	500	_	-	—	600	—	-	
	t _{PLH}	4.5	-	80	-	80	—	100	-	100	—	120	—	120	
SO to Qn	Fig. 8	6		68	_	<u> </u>		85				102	_		
Propagation Delay/	t _{PLH}	2	_	2000	_	-	-	2500	-	-	—	3000	_	_	
Ripple thru Delay		4.5	<b>—</b>	400	_	400	-	500	_	500	—	600	- <b>-</b>	600	
SI to DOR	Fig. 9	6		340		<u> </u>		425				510			ns
Propagation Delay/	t _{PLH}	2	-	2500	_	—	-	3125	-	_	_	3750	<b>—</b>	_	'''
Ripple thru Delay		4.5	-	500	<b>—</b>	500	-	625	-	625	-	750	-	750	
SO to DIR	Fig. 10	6		425		<u> </u>		532				638			
Propagation Delay/	t _{PHL}	2	-	1500	_	_	-	1900	-	_	_	2250	_	_	ļ
Ripple thru Delay	t _{PLH}	4.5	-	300	-	300	_	380	-	380	-	450	-	450	
SI to Qn		6	<u> </u>	260	<u> </u>	<u> </u>		330		<u> </u>		380		<u> </u>	1
3-State Output	t _{PZH}	2		150	-	-	-	190	-	-	-	225	-	-	l
Enable	t _{PZL}	4.5	-	30		35	-	38	-	44		45		53	
OE to Qn	Fig. 11	6	<b>↓</b> =_	26	<u> </u>	<u> </u>	<del>-</del> -	33	<u> </u>	<u> </u>		38	-	<b>↓</b> = .	
3-State Output	t _{PHZ}	2	_	140	_	-	_	175	—	-	1 —	210	_	_	
Disable	t _{PLZ}	4.5	-	28	-	30		35	_	38	-	42	_	45	
OE to Qn	Fig. 11	6		24	$\vdash =$	<del>  -</del>	<u> </u>	30	<u> </u>	<u> </u>	<u> </u>	36	_		
Output Transition	t _{THL}	2	-	75	-	-	-	95	-	-	-	110	-		
Time	t _{TLH}	4.5	-	15	-	15	-	19	-	19	-	22	-	22	
	Fig. 8	6		13	<b>└</b> =		$\vdash$	16	<b>↓</b>		$\vdash =$	19	<u> </u>	-	
	nput Capacitance Cı			10	<u> </u>	10	<u> </u>	10	<u> </u>	10	<del>  -</del>	10	<u> </u>	10	pF
3-State Output Capacit	tance Co	L	<u> </u>	15	<u> </u>	15		15_	<u> </u>	15		15	<u> </u>	15	

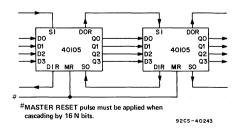


Fig. 3 - Expansion, 4-bits wide by 16 N-bits long.

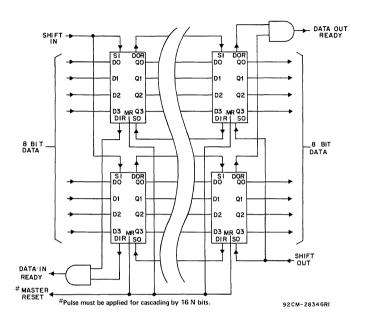


Fig. 4 - Expansion, 8-bits wide by 16 N-bits long using HC/HCT40105.

### **AC WAVEFORMS**

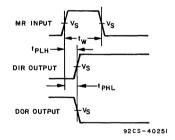


Fig. 5 - Waveforms showing the MR input to DIR, DOR output propagation delays and the MR pulse width.

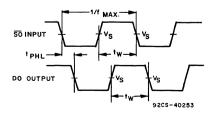


Fig. 7 - Waveforms showing the SO input to DOR output propagation delay. The SO, DOR pulse widths and SO maximum pulse frequency.

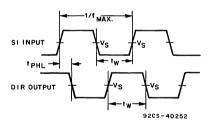


Fig. 6 - Waveforms showing the SI input to DIR output propagation delay. The SI, DIR pulse widths and SI maximum pulse frequency.

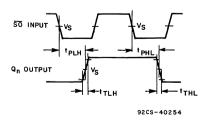


Fig. 8 - Waveforms showing SO input to Q_n output propagation delays and output transition time.

### AC WAVEFORMS (Cont'd)

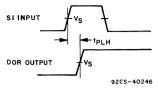


Fig. 9 - Waveforms showing the SI input to DOR output propagation/ripple-through delay.

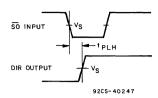


Fig. 10 - Waveforms showing the SO input to DIR output propagation/ripple-through delay.

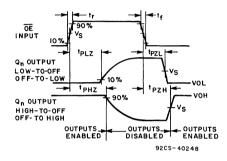


Fig. 11 - Waveforms showing the 3-state enable and disable times for input  $\overline{OE}$ .

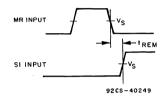
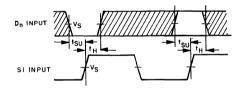


Fig. 12 - Waveforms showing the MR input to SI input removal time.



NOTE
THE SHADED AREAS INDICATE WHEN THE INPUT
IS PERMITTED TO CHANGE FOR PREDICTABLE
OUTPUT PERFORMANCE. 92CS-40250

Fig. 13 - Waveforms showing hold and set-up times for D_n input to SI input.

	54/74HC	54/74HCT
Input Level	Vcc	3 V
Switching Voltage, Vs	50% V _{cc}	1.3 V

• DATA VALID GOES TO HIGH LEVEL IN ADVANCE OF THE DATA OUT BY A MAXIMUM OF 38 ns AT VCC = 4.5 V, FOR CL = 50 pF AND TA = 25° C

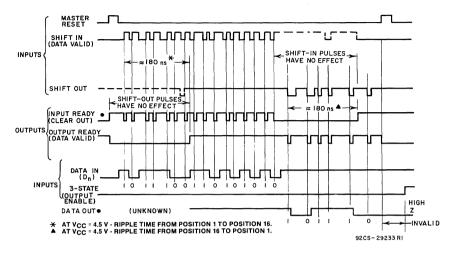
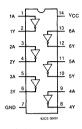


Fig. 14 - Timing diagram for the CD54/74HC/HCT40105.

# **High-Speed CMOS Logic**



# FUNCTIONAL DIAGRAM AND TERMINAL ASSIGNMENT

## **Hex Inverter**

### Type Features:

- Typical propagation delay=6 ns @ V_{CC}=5 V C_L=15 pF, T_A=25° C, fastest part in QMOS line
- Wide operating temperature range: CD74HCU04: -40°C to +85°C
- Balanced Propagation Delay and Transition Times
- Significant power reduction compared to LSTTL logic ICs
- Alternate source is Philips/Signetics

The RCA-CD54/74HCU04 unbuffered hex inverter utilizes silicon-gate CMOS technology to achieve operating speeds similar to LSTTL gates with the low power consumption of standard CMOS integrated circuits. These devices are especially useful in crystal oscillator and analog applications. Figs. 4 and 5 are supplied as design information for the above applications.

The CD54HCU04 is supplied in 14-lead hermetic dual-in-line ceramic packages (F suffix). The CD74HCU04 is supplied in 14-lead dual-in-line plastic packages (E suffix). The CD74HCU04 is supplied in 14-lead dual-in-line surface mount plastic packages (M suffix). These types are also available in chip form (H suffix).

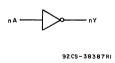


Fig. 1 - Logic diagram.

- CD54HCU04/CD74HCU04 types: 2 to 6 V operation High noise immunity: N_{IL}=20%, N_{IH}=30% of V_{CC}: @ V_{CC}=5 V
- CMOS input compatibility I_I ≤ 1 µA @ V_{OL}, V_{OH}

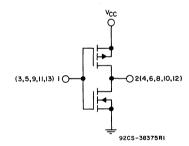


Fig. 2 - Inverter schematic.

# CD54/74HCU04

### MAXIMUM RATINGS, Absolute-Maximum Values:

DC SUPPLY-VOLTAGE, (V _{cc} ):	
(Voltages referenced to ground)	0.5 to +7 V
DC INPUT DIODE CURRENT, $I_{iK}$ (FOR $V_i < -0.5$ V OR $V_i > V_{CC} + 0.5$ V)	±20 mA
DC OUTPUT DIODE CURRENT, Iok (FOR Vo < -0.5 V OR Vo > Vcc +0.5 V)	±20 mA
DC DRAIN CURRENT, PER OUTPUT (Io) (FOR -0.5 V < Vo < Vcc +0.5 V)	±25 mA
DC Vcc OR GROUND CURRENT, (Icc)	±50 mA
POWER DISSIPATION PER PACKAGE (Pp):	
For T _A = -40 to +60°C (PACKAGE TYPE E)	500 mW
For T _A = +60 to +85°C (PACKAGE TYPE E)	
For T _A = -55 to +100°C (PACKAGE TYPE F, H)	500 mW
For T _A = +100 to +125° C (PACKAGE TYPE F, H)	Derate Linearly at 8 mW/°C to 300 mW
	400 mW
For T _A = +70 to +125°C (PACKAGE TYPE M)	Derate Linearly at 6 mW/°C to 70 mW
OPERATING-TEMPERATURE RANGE (T _A ):	Derate Linearly at 6 mw/ C to 70 mw
PACKAGE TYPE F, H	-55 to +125°C
PACKAGE TYPE E, M	-40 to +85° C
STORAGE TEMPERATURE (T _{sto} )	
LEAD TEMPERATURE (DURING SOLDERING):	
At distance $1/16 \pm 1/32$ in. $(1.59 \pm 0.79 \text{ mm})$ from case for 10 s max	+265°C
Unit inserted into a PC Board (min. thickness 1/16 in., 1.59 mm)	200 0
with solder contacting lead tips only	+300°C
,,,,,,,,,,,,,,	

### RECOMMENDED OPERATING CONDITIONS

For maximum reliability, nominal operating conditions should be selected so that operation is always within the following ranges:

CHARACTERISTIC	LIN	IITS	UNITS
CHARACTERISTIC	MIN.	MAX.	UNITS
Supply-Voltage Range (For T _A =Full Package Temperature Range)			
V _{cc} :*	2	6	V
DC Input or Output Voltage, V _I , V _O	0	V _{cc}	V
Operating Temperature, T _A :			
CD74 Types	-40	+85	°C
CD54 Types	-55	+125	1
Input Rise and Fall Times, t _r ,t _f :			
at 2 V	0	1000	
at 4.5 V	0	500	ns
at 6 V	0	400	j

^{*}Unless otherwise specified, all voltages are referenced to Ground.

# CD54/74HCU04

### STATIC ELECTRICAL CHARACTERISTICS

					CD54l	ICU04					
		TEST C	CONDITI	ONS	CD74	HCU04	CD74H	HCU04	CD54	HCU04	
CHARACTER	ISTIC	VI	I _O	VCC	+25	s° C	-40°C to	o +85° C	-55° C to	+125° C	UNITS
		V	mA	٧	Min.	Max.	Min.	Max.	Min.	Max.	
High-Level		T -	_	2	1.7	_	1.7		1.7		
Input Voltage	V _{IH}	-	-	4.5	3.6		3.6	_	3.6		
		_	_	6	4.8		4.8		4.8		
Low-Level		T -	T	2	_	0.3		0.3	_	0.3	
Input Voltage	VIL	-	-	4.5	_	0.8	_	0.8		0.8	
				6	_	1.1		1.1		1.1	
High-Level		VIL		2	1.8	_	1.8	_	1.8	_	,
Output Voltage	Vон	or	-0.02	4.5	4	_	4	_	4	_	V
		ViH	l	6	5.5	_	5.5	_	5.5	_	
		V _{cc} or	-4	4.5	3.98		3.84		3.7		
		Gnd	-5.2	6	5.48	_	5.34	_	5.2	_	
Low-Level		VIL		2	_	0.2	_	0.2	_	0.2	
Output Voltage	Vol	or	0.02	4.5	_	0.5		0.5	_	0.5	
		V _{IH}		6		0.5		0.5	_	0.5	
		V _{cc} or	4	4.5	_	0.26	l –	0.33	I -	0.4	
· ·		Gnd	5.2	6	_	0.26	_	0.33	_	0.4	
Input Leakage		Vcc									
Current	l ₁	or	-	6	_	±0.1	-	±1	<u> </u>	±1	
		Gnd	1			}	ł	ì	l	1	
Quiescent		Vcc									μΑ
Device		or	0	6		2	-	20	-	40	
Current	Icc	Gnd						!	1		

### SWITCHING CHARACTERISTICS (V_{CC} = 5 V, $T_A$ = 25°C, input $t_r$ , $t_t$ = 6 ns)

CHARACTERISTIC	SYMBOL	TYPICAL VALUES CD54/74U04	UNITS
Propagation Delay, Data Input to Output Y (Fig. 3) (C _L =15 pF)	t _{PLH}	5	ns
Power Dissipation Capacitance*	СРД	14	pF

 $^{^{\}bullet}C_{PD}$  is used to determine the dynamic power consumption, per inverter when:  $P_D = V_{CC}^2$  fi  $(C_{PD} + C_L)$  where fi=input frequency

C_L=output load capacitance V_{CC}=supply voltage

### SWITCHING CHARACTERISTICS (CL=50 pF, Input t, t=6 ns)

			25	°C	-40°C t	to +85°C -55°C to +125°C		+125°C		
CHARACTERISTIC	SYMBOL	VCC	CD54/7	4HCU04	CD74	HCU04	CD54I	HCU04	UNITS	
			Min.	Max.	Min.	Max.	Min.	Max.	7	
Propagation Delay	t _{PLH}	2	-	70	_	90	T -	105		
Input to Output	t _{PHL}	4.5	_	14	_	18	-	21	1	
(See Fig. 3)		6	_	12	_	15	_	18	ns	
Transition Times	t _{TLH}	2		75	_	95	_	110	7	
(Fig. 3)	t _{THL}	4.5	_	15	l —	19	-	22	1	
		6	_	13	-	16	-	19	1	
Input Capacitance	Cı	_	See Fig. 5							

# CD54/74HCU04

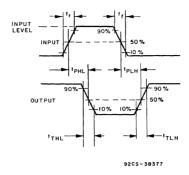


Fig. 3 - Propagation delay and transition times.

# DESIGN INFORMATION FOR CRYSTAL OSCILLATOR AND ANALOG APPLICATIONS

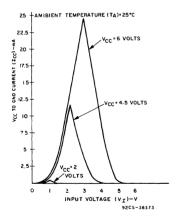


Fig. 4 - Typical inverter supply current as a function of input voltage.

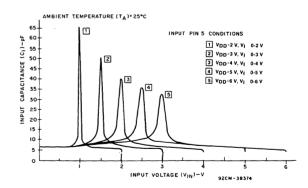


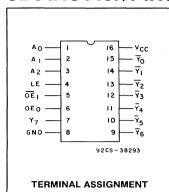
Fig. 5 - Input capacitance as a function of input voltage.

# **Preview Data**

The types shown in the Preview Data section contain information on a product under development. RCA reserves the right to change or discontinue this product without notice.

# CD54HC137/74HC137 CD54HCT137/74HCT137

# 3 to 8 Decoder/Demultiplexer, with Address Latch



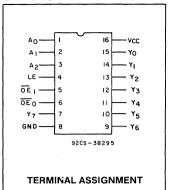
					TF	RUTH	TAB	LE						
		INP	UTS			OUTPUTS								
LE	OE ₀	ŌĒ₁	A ₂	A ₁	$A_0$	$\overline{Y}_0$	$\overline{\mathbf{Y}}_1$	$\overline{\mathbf{Y}_2}$	$\overline{\mathbf{Y}_3}$	<b>Y</b> ₄	$\overline{\mathbf{Y}}_{5}$	$\overline{\mathbf{Y}}_{6}$	$\overline{\mathbf{Y}}_{7}$	
X	Х	Н	Χ	X	Χ	Н	Н	Н	Н	Н	Н	Н	Н	
X	L	Χ	Х	X	Χ	Н	Н	H	Н	Н	Н	Н	H	
L	Н	L	L	L	L	L	Н	Н	Н	Н	Н	Н	Н	
L	Н	L	L	L	Н	Н	L	Н	Н	Н	Н	Н	H	
L	H	L	L	Н	L	Н	Н	L	Н	Н	Н	Н	Н	
L	H	L	L	Н	Н	Н	Н	H	L	H	Н	Н	<u>H</u>	
L	Н	П	Н	L	L	Ι	Н	Н	Н	L	Н	Н	Н	
L	H	L	Н	L	Н	Н	Н	Н	Н	Н	L	Н	н	
L	H	L	H	Н	L	Н	Н	Н	Н	Н	Н	L	Н	
L	Н	L	Н	Н	Н	Τ	_ H	<u>H</u>	Н	_H_	Н	Н	L	
Н	Н	L	Χ	Χ	Χ				*					
* = [	* = Depends upon the address previously applied while LE was at a logic low.													

Typical Switching Characteristics ( $V_{CC} = 5V$ , GND = 0V,  $t_r = t_f = 6ns$ )

OLIADACTERISTICS		15pF	50pF	LINUTO
CHARACTERISTICS		54/74HC/HCT	54/74HC/HCT	UNITS
Propagation Delay Time A to Y	tPHL tPLH	20 14	23 16	
ŌE₁ to Ÿ	tPHL tPLH	15 11	18 12	ns
$OE_0$ to $\overline{Y}$	tPHL tPLH	16 12	18 14	
LE to $\overline{Y}$	tPHL tPLH	21 14	24 17	

# CD54/74HC237 CD54/74HCT237

# 3-to-8 Line Decoder/Demultiplexer with Address-Latches



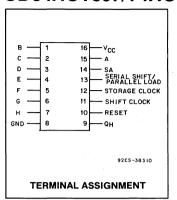
					TI	RUTH	TAB	LE					
	INPUTS							OUTPUTS					
LE	OE₀	ŌĒ₁	A ₂	A ₁	$A_0$	Y ₀	<b>Y</b> ₁	Y ₂	<b>Y</b> 3	<b>Y</b> ₄	<b>Y</b> ₅	<b>Y</b> 6	<b>Y</b> ₇
X	X L	H X	X	X	X X	L	L L	L L	L L	L L	L L	L L	L L
L L	TTTT		L L L	L H L	L H L	HLLL	L H L L	L H L	L L H	L L L		L L L	LLL
L L	TITI	L	Н Н Н	L H H	HTH	L L L	L L L	L L L	L L L	H L L	L H L L	L H L	L L H
Н	Η	L	Х	Χ	Χ				*				
* = [	Depen	ds up	on the	addre	ess pr	evious	ly.						

^{* =} Depends upon the address previously applied while LE was at a logic low.

Typical Switching Characteristics (V_{CC} = 5V, GND = 0V, t_r = t_f = 6ns)

OUADA OTEDIOTIOS		15pF	50pF	
CHARACTERISTICS		54/74HC/HCT	54/74HC/HCT	UNITS
Propagation Delay Time A to Y	tPHL tPLH	15 20	18 22	
ŌĒ₁ to Y	tPHL tPLH	12 17	14 19	ns
OE ₀ to Y	tPHL tPLH	16 17	18 19	
LE to Y	tPHL tPLH	16 21	18 24	

# CD54HC597/74HC597 CD54HCT597/74HCT597



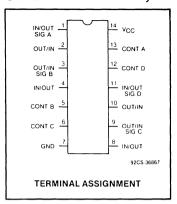
# 8-Bit Serial- or Parallel Input/Serial-Output Shift Register with Input Storage

Typical Switching Characteristics ( $V_{CC} = 5V$ , GND = 0V,  $t_r = t_f = 6ns$ )

CHARACTERISTICS		15pF	50pF	LINUTO
CHARACTERISTICS		54/74HC/HCT	54/74HC/HCT	UNITS
Propagation Delay Time Shift Clock to QH	tpHL, tpLH	14	17	
Storage Clock to QH	tPHL, tPLH	21	24	ns
Parallel Load to QH	tPHL, tPLH	14	17	

# CD54/74HC4016, CD54/74HCT4016

# **Quad Bilateral Switch**



Dynamic Electrical Characteristics @  $T_A = 25$  °C,  $V_{CC} = 5$  V,  $t_r$ ,  $t_f = 6$  ns

Symbol	Parameter	Test Conditions	Typical	Units
tPHL/tPLH	Propagation Delay:	C _L = 15 pF	3	ns
	Sw. Input to Output	C _L = 50 pF	5	ns
	Turn-On Delay	CL = 15 pF	6	ns
	and Turn-Off Delay*	CL = 50 pF	8	ns
RON	On-State Resistance	R _L = 1 KΩ C _L = 50 pF	200	Ω

^{*}Turn-On measured 50% to 50%. Turn-Off measured 50% to 10%.

B ON/OFF CONTROL

C ON/OFF

ENABLE GND

# CD54HC4316/74HC4316

ΥD

92CS-38311

10

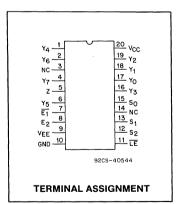
**TERMINAL ASSIGNMENT** 

# **Demultiplexer with Separate** CD54HCT4316/74HCT4316 **Analog and Digital Power Supplies** vcc 14 ΧD

Typical Switching Characteristics (VCC = 5V, GND = 0, tr = tf = 6ns)

CHARACTERISTICS	15pF 54/74HC/HCT	50pF 54/74HC/HCT	UNITS
Propagation Delay Time tpzL, tpzH Switch "Turn-ON"	12	14	ns
Switch "Turn-OFF" tpHz, tpLz	12	14	1

# CD54HC4351/74HC4351 CD54HCT4351/74HCT4351



# 8-Channel Analog Multiplexer/ **Demultiplexer with Address Latch**

Quad Analog Switch/Multiplexer/

**FUNCTION TABLE** 

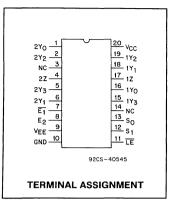
Co	ontrol Inpu				
		S	ele	ct	ON Switches
Enable 1	Enable 2	С	В	Α	(LE = H)*
L	Н	L	L	L	YO
L	Н	L	L	Н	Y1
L	Н	L	Н	L	Y2
L	Н	L	Н	н	Y3
L	Н	Н	L	L	Y4
L	Н	Н	L	Н	Y5
L	н	Н	Н	L	Y6
L	Н	н	Н	Н	Y7
Н	L	X	Х	Х	None

X = Don't Care

^{*}When Latch Enable is low, the Channel-Select data is latched, and the switches do not change state.

# CD54HC4352/74HC4352

# **Dual 4-Channel Analog Multiplexer/** CD54HCT4352/74HCT4352 Demultiplexer with Address Latch



### **FUNCTION TABLE**

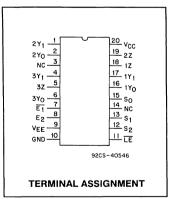
C	ontrol Inpu					
		Se	lect	ONS	vitches	
Enable 1	Enable 2	В	Α	(LE=H)*		
L	Н	L	L	1Y0	2Y0	
L	н	L	н	1Y1	2Y1	
L	н	н	lι	1Y2	2Y2	
L	Н	н	н	1Y3	2Y3	
Н	L	Х	Х	None		

X = Don't Care

*When Latch Enable is low, the Channel-Select data is latched, and the switches do not change state.

# CD54HC4353/74HC4353 CD54HCT4353/74HCT4353

# **Triple 2-Channel Analog** Multiplexer/Demultiplexer with I atch



	TRUTH TABLE												
	INPUTS						CHANN	IELS					
Ē1	E2	LE	S2	S1	SO	NONE							
H X	X	X	X	X	X	NONE							
L	Н	Н	L	L	L	1Y ₀	2Yo	3Yo					
L	Н	Н	L	L	Н	1Yo	2Yo	3Y ₁					
L	Н	Н	L	Н	L	1Y₀	2Y1	3Yo					
L	Н	H	L	Н	Н	1Y ₀	2Y ₁	3Y ₁					
L	Н	H	Н	L	L	1Y ₁	2Yo	3Yo					
L	Н	H	Н	L	Н	1Y ₁	2Yo	3Y ₁					
L	Н	Н	Н	Н	L	1Y ₁	2Y ₁	3Yo					
L	Н	Н	Н	<u>H</u>	Н	1Y ₁	2Y ₁	3Y₁					
L	Н	L	Х	Х	Х	Last	Channels	"On"					
Χ	X	į.	X X X Selected Channels Latched										

Typical Switching Characteristics (V_{CC} = 5V, GND = 0V, t_r = t_f = 6ns)

		CONDITIONS	15pF	50pF	
CHARACTERISTICS		V _{EE}	54/74HC/HCT	54/74HC/HCT	UNITS
Propagation Delay Time	tPHL, tPLH	GND	3	5	
Switch Input to Output		-5	2	4	
Switch Turn "ON"	tPHL, tPLH	GND	14	17	ns
(RL = 1k )		-5	14	17	""
Switch Turn "OFF"	toru toru	GND	17	19	
Switch runi OFF	tPHL, tPLH	-5	14	17	

# 9-Bit x 64-Word FIFO Register; 3-State

# CD54/74HC7030 CD54/74HCT7030

GND 1 GNO 2 GNO 3 DIR 3 SI 4 FOO 5 DO 6 D1 7 D2 8 D3 9 D4 9 D5 10 D6 112 D7 13 D8 13 GND 14		28 VCC 27 MR 26 SO 25 DOR 24 QO 23 Q1 22 Q2 21 Q3 20 Q4 19 Q5 18 Q6 17 Q7 16 Q8 15 OE
	92	CS-40537

TERMINAL ASSIGNMENT

# g Dynamic Electrical Characteristics @ $T_A$ = 25° C, $V_{CC}$ = 5 V, $t_r$ , $t_f$ = 6 ns

Symbol	Parameter	Test Conditions	Typical		Units
		нс	нст		
t _{PHL} /t _{PLH}	Propagation Delay:	C _L = 15 pF	14	16	ns
	SI, SO to DIR, DOR	C _L = 50 pF	17	19	ns
f _{max}	Maximum Clock Frequency	C _L = 15 pF	40	40	MHz

# CD54/74HC7038 CD54/74HCT7038

### 24 VCC 23 OE (B+A) LE _2 22 BO AO 3 21 B1 A1 4 20 B2 5 A2-6 ΑЗ 17 B5 Α5 16 B6 9 Α6 15 B7 A7 10 14 B8 11 A8-GND 12 13 POLARITY 92CS-40538

**TERMINAL ASSIGNMENT** 

# 9-Bit Bus Transceiver with Latch

### Features:

- 48 mA Sink Current
- Inverting and Non-Inverting Data Paths

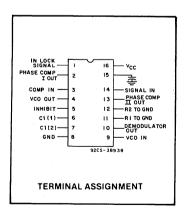
### **TRUTH TABLE**

cc	NTROL INPU	OPERATION			
ŌE(A→B)	ŌE(B→A)	POLARITY	OPERATION		
L	Н	Н	D _n to Q _n		
L	н	L	$\overline{D_{n}}$ to $\overline{Q_{n}}$		
н	L	Н	B data to A		
н	L	L	B data to A		
Н	н	X	Isolation		

Dynamic Electrical Characteristics @  $T_A = 25^{\circ}$  C,  $V_{CC} = 4.5$  V,  $t_r$ ,  $t_f = 6$  ns

Symbol	Parameter	Test Conditions	Typical		Units
!			нс	нст	
t _{PZL} /t _{PLZ}	A or A → B	C _L = 15 pF	23	23	ns
		C _L = 50 pF	26	26	ns
t _{PHL} /t _{PLH}	Bor B → A	C _L = 15 pF	10	10	ns
		C _L = 50 pF	13	13	ns ,

# CD54/74HC7046 CD54/74HCT7046

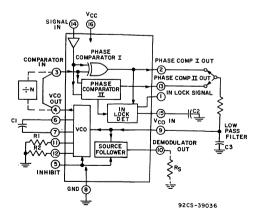


# Phase-Locked Loop with VCO and In-Lock Detector

(Voltage Controlled Oscillator)

### Feature:

■ 11 MHz typ. @ V_{cc}=5 V (output signal)



Phase-locked loop with in-lock detector block diagram.

# **Advanced CMOS Logic**

Advanced CMOS Logic, ACL, is the next step forward in the evolution of CMOS logic. It matches bipolar FAST* in speed, performance and logic type output drive, but at CMOS power levels.

Just as HC/HCT high-speed CMOS logic became an industry standard competing with LSTTL, ACL is expected to become an industry standard offered by a number of the leading CMOS logic suppliers. A JEDEC committee is currently working on specifications for a standardization of 54/74 AC/ACT devices.

Featuring < 3-ns gate propagation delays, ACL is the fastest CMOS logic yet available. (By contrast, the standard propa-

gation delay for CMOS logic is 95 ns, and for high-speed CMOS logic, 9 ns.) ACL can operate at more than 150 MHz. Output drive capability is 24 mA, compared with 6 mA for HC/HCT. This capability enables ACL to drive transmission lines, yet still generate the voltages necessary to operate the receiving logic devices safely.

Because of its low power consumption, ACL is potentially more reliable than bipolar logic. This quality should make ACL the technology of choice in a number of applications, including computers, peripherals, and telecommunications, and in portable and military equipment.

*FAST is a trademark of Fairchild Semiconductor Corp.

ACL .	TYPES •				
PLASTIC * CERDIP *		DESCRIPTION			
CD74AC/ACT00E,M	CD54AC/ACT00F	Quad 2-Input NAND Gate	14		
CD74AC/ACT02E,M	CD54AC/ACT02F	Quad 2-Input NOR Gate	14		
CD74AC/ACT04E,M	CD54AC/ACT04F	Hex Inverter/Buffer	14		
CD74AC/ACT05E,M	CD54AC/ACT05F	Hex Inverter/Buffer with Open-Drain Outputs	14		
CD74AC/ACT08E,M	CD54AC/ACT08F	Quad 2-Input AND Gate	14		
CD74AC/ACT10E,M	CD54AC/ACT10F	Triple 3-Input NAND Gate	14		
CD74AC/ACT20E,M	CD54AC/ACT20F	Dual 4-Input NAND Gate	14		
CD74AC/ACT32E,M	CD54AC/ACT32F	Quad 2-Input OR Gate	14		
CD74AC/ACT74E,M	CD54AC/ACT74F	Dual D-Type Flip-Flop w/SET and RESET	14		
CD74AC/ACT86E,M	CD54AC/ACT86F	Quad 2-Input EXCLUSIVE-OR Gate	14		
CD74AC/ACT109E,M	CD54AC/ACT109F	Dual J-K Flip-Flop w/SET and RESET	16		
CD74AC/ACT112E,M	CD54AC/ACT112F	Dual J-K Flip-Flop w/SET and RESET	16		
CD74AC/ACT138E,M	CD54AC/ACT138F	3-to-8 Line Decoder/Demultiplexer, Inverting	16		
CD74AC/ACT139E,M	CD54AC/ACT139F	Dual 2-of-4 Line Decoder/Demultiplexer	16		
CD74AC/ACT151E,M	CD54AC/ACT151F	8-Input Multiplexer	16		
CD74AC/ACT153E,M	CD54AC/ACT153F	Dual 4-Input Multiplexer	16		
CD74AC/ACT157E.M	CD54AC/ACT157F	Quad 2-Input Multiplexer	16		
CD74AC/ACT158E.M	CD54AC/ACT158F	Quad 2-Input Multiplexer, Inverting	16		
CD74AC/ACT161E,M	CD54AC/ACT161F	Synchronous 4-Bit Binary Counter, Asynchronous Reset	16		
CD74AC/ACT163E,M	CD54AC/ACT163F	Synchronous 4-Bit Binary Counter, Synchronous Reset	16		
CD74AC/ACT164E,M	CD54AC/ACT164F	8-Bit Serial-In Parallel-Out Shift Register	14		
CD74AC/ACT174E,M	CD54AC/ACT174F	Hex D-Type Flip-Flop w/RESET	16		
CD74AC/ACT175E,M	CD54AC/ACT175F	Quad D-Type Flip-Flop w/RESET	16		
CD74AC/ACT191E,M	CD54AC/ACT191F	Synchronous 4-Bit Binary Up/Down Counter	16		
CD74AC/ACT193E,M	CD54AC/ACT193F	Synchronous 4-Bit Binary Up/Down Counter	16		
CD74AC/ACT238E.M	CD54AC/ACT238F	3-to-8 Line Decoder/Demultiplexer	16		
CD74AC/ACT240E,M	CD54AC/ACT240F	Octal Buffer Line Driver, 3-State, Inverting	20		
CD74AC/ACT241E.M	CD54AC/ACT241F	Octal Buffer Line Driver, 3-State	20		
CD74AC/ACT244E.M	CD54AC/ACT244F	Octal Buffer Line Driver, 3-State	20		
CD74AC/ACT245E,M	CD54AC/ACT245F	Octal Bus Transceiver, 3-State	20		
CD74AC/ACT251E.M	CD54AC/ACT251F	8-Input Multiplexer, 3-State	16		
CD74AC/ACT253E,M	CD54AC/ACT253F	Dual 4-Input Multiplexer, 3-State	16		
CD74AC/ACT257E,M	CD54AC/ACT257F	Quad 2-Input Multiplexer, 3-State	16		
CD74AC/ACT258E,M	CD54AC/ACT258F	Quad 2-Line to 4-Line Data Selector	16		
CD74AC/ACT273E,M	CD54AC/ACT273F	Octal D-Type Flip-Flop w/RESET	20		
CD74AC/ACT280E,M	CD54AC/ACT280F	8-Bit Odd/Even Parity Generator/Checker	14		
CD74AC/ACT283E,M	CD54AC/ACT283F	4-Bit Full Adder w/Fast Carry	16		
CD74AC/ACT299E,M	CD54AC/ACT299F	8-Bit Universal Shift Register, 3-State	20		
CD74AC/ACT323E.M	CD54AC/ACT323F	8-Bit Universal Shift Register, 3-State (with Synchronous Reset)	20		
CD74AC/ACT373E.M	CD54AC/ACT373F	Octal Transparent Latch, 3-State	20		
CD74AC/ACT374E,M	CD54AC/ACT374F	Octal D-Type Flip-Flop, 3-State	20		
CD74AC/ACT533E,M	CD54AC/ACT533F	Octal Transparent Latch, 3-State, Inverting	20		
CD74AC/ACT534E,M	CD54AC/ACT534F	Octal D-Type Flip-Flop, 3-State, Inverting	20		
CD74AC/ACT540E.M	CD54AC/ACT540F	Octal Buffer Line Driver, 3-State, Inverting	20		
CD74AC/ACT541E.M	CD54AC/ACT541F	Octal Buffer Line Driver, 3-State	20		
CD74AC/ACT573E,M	CD54AC/ACT573F	Octal Transparent Latch, 3-State	20		
CD74AC/ACT574E,M	CD54AC/ACT574F	Octal D-Type Flip-Flop, 3-State	20		
CD74AC/ACT646E,M	CD54AC/ACT646F	Octal Bus Transceiver/Register, 3-State	24		
CD74AC/ACT648E,M	CD54AC/ACT648F	Octal Bus Transceiver/Register, 3-State, Inverting	24		
CD74AC/ACT7060E.M	CD54AC/ACT7060F	14-Stage Counter with Oscillator	20		
CD74AC/ACT7000E,M	CD54AC/ACT7202F	1024 x 9-Bit Parallel In-Out FIFO	28		
CD74AC/ACT7402E,M	CD54AC/ACT7402F	65 x 5-Bit FIFO	18		

Consult your local Sales Office for availability time frame and other details.

*Package Suffix: E - Dual-In-Line Plastic

F - Dual-In-Line Frit-Seal Ceramic

M - Surface Mount

# **Application Notes**

# Power Consumption in QMOS Logic Circuits

by R. Funk and B. Heinze

QMOS, RCA's high-speed CMOS-logic technology, offers users the best features of both CMOS and TTL technologies: the low-power consumption of CMOS and the fast speeds associated with LSTTL. This Application Note focuses on the primary QMOS feature, low power consumption. The causes of quiescent and dynamic power dissipation in HC and HCT QMOS devices are discussed. The formulas needed to compute the power dissipation in QMOS devices are presented along with sample calculations. A comparison is made of QMOS, LS, and ALS logic types relative to power dissipation.

The significant reduction in power consumption provided by a QMOS logic system compared with the equivalent LSTTL or ALSTTL counterpart design is the primary reason that QMOS is destined to be chosen for new designs and to replace LSTTL or ALSTTL parts in many existing designs. The replacement of LSTTL devices with HCT QMOS types¹ achieves power savings in existing designs where decreased power consumption and dissipation are a distinct advantage. In new designs, only QMOS logic lends itself to batteryoperated portable equipment, such as portable (lap-held) personal computers, and the switch to QMOS is the major trend in PCs using all-CMOS RAMs, ROMs, and peripherals. All-QMOS designs can be powered down to 2-volts standby, increasing battery life. In nonportable designs, QMOS and CMOS LSI logic are also preferred to significantly reduce, in order of priority, cost, size, and weight. Cost reduction is the result of savings in the cost of supply regulators, the elimination of cooling fans and heat sinks, etc.

An equally powerful motivating force behind the use of logic components that dissipate lower power, such as QMOS, is the proven component and equipment reliability enhancement. The junction temperature of the ICs, as well

as the temperature of other equipment components (resistors and capacitors), is much reduced, thereby lengthening life. QMOS failure rates are currently measured at .0015%/1000 hours at 60% UCL for operation at +55° C.

Power consumption in a logic IC must be considered in both of the IC's operating modes, i.e., under static and dynamic conditions. QMOS devices consume only minute amounts of power under static (quiescent) conditions, making power consumed in the dynamic state the major contributor to total power consumption. TTL devices, on the other hand, consume significant amounts of power in the quiescent state, so much in fact, that power consumption in the dynamic state can be masked at frequencies as high as 20 MHz, depending on device complexity. At higher frequencies, the power consumed by TTL devices increases proportionately. Since integrated circuits typically spend a significant percentage of their time either in the quiescent state or operating at average frequencies below 2 MHz. QMOS devices can provide significant and often dramatic power savings.

### QUIESCENT POWER CONSUMPTION

The quiescent power consumption of a logic IC is measured when the system input voltage,  $V_{\text{IN}}$ , equals the device supply voltage,  $V_{\text{CC}}$ , or is at ground potential. Fig. 1(a) is used to illustrate this discussion. In the quiescent state, either the PMOS or NMOS transistor is fully off, and ideally no direct MOS transistor-channel path exists between  $V_{\text{CC}}$  and ground. In reality, however, thermally generated minority-charge carriers present in all reverse-biased diode junctions, Fig. 1(b), allow a very small power-supply leakage current to flow between  $V_{\text{CC}}$  and ground. In QMOS data sheets, this quiescent leakage current is specified as  $I_{\text{CC}}$ .

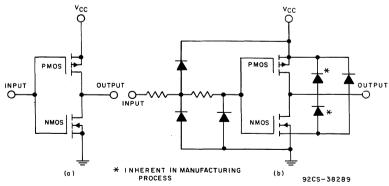


Fig. 1 - (a) Simple QMOS inverter circuit, (b) simple QMOS inverter circuit with input and output ESD protective diodes.

Three factors affect the value of lcc and, therefore, the power dissipation of a device:

Temperature:-Increasing temperature causes an increase in l_c because the minority charge carriers in the reverse-biased diode junctions of QMOS devices are thermally generated.

Device Complexity:-MSI devices will consume more power than SSI devices because there exists a proportionally greater reverse-biased diode-junction area.

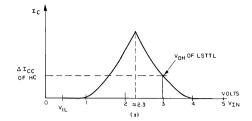
 $V_{CC}$ :-The minority-charge carriers are linearly related to reverse junction voltage.

Table I shows the JEDEC industry standards for 54/74 HC/HCT high-speed CMOS devices, and illustrates the effect of temperature and device complexity on  $I_{\rm CC}$  at the maximum recommended HC operating voltage,  $V_{\rm CC}$  = 6 V. At  $V_{\rm CC}$  = 2 V,  $I_{\rm CC}$  is approximately 1/3 the value shown at  $V_{\rm CC}$  = 6 V. Typical  $I_{\rm CC}$  values are well under the maximum specified values.

Another factor that may add to quiescent, or dc, power consumption is the through current caused by both the PMOS and NMOS transistors of the input stage, Fig. 1(a), being on, at least to some degree, at the same time. For HC devices, where the switching transition occurs at a nominal V_{cc}/2 (see Fig. 2(a)), there is no through current and, hence, no added do power consumption. That is, with V_{II} and V_{IH} voltage levels (low-level and high-level input voltages, respectively) at the inputs, either the PMOS or the NMOS transistor of the HC input stage is completely off. However, for HCT devices, where the switching transition occurs at a nominal 1.3 volts, Fig. 2(b), there is a through-current component when an input high-voltage level of under 4 volts is applied to an input. With this amount of voltage applied, the NMOS transistor is fully on and the PMOS transistor not fully off. This is the situation in an HCT device when, in a QMOS/TTL interface, the input voltage of the QMOS device is the VoH (high-level output voltage) of a TTL family device. The 3.5-volt typical VoH output voltage will fully turn-on the QMOS input NMOS transistor (Fig. 1) but not fully turn-off the PMOS transistor. The current flow that results is specified as  $\Delta I_{cc}$  in QMOS HCT data sheets.

### Computing HC Quiescent-Power Consumption

Quiescent power consumption in an HC device is extremely low, typically under 10 microwatts. The  $\Delta l_{CC}$  plays no part because HC I/O levels are completely compatible:  $V_{OL}$  and  $V_{OH}$  worst-case specifications are 0.1 and  $V_{CC}$ –0.1 volt, very close to ground and  $V_{CC}$ , respectively. Fig. 2(a) illustrates that no  $l_{CC}$  will flow with these  $V_{OL}$  and  $V_{OH}$  voltage levels imposed. However, if inputs are driven beyond  $V_{IL}$  and  $V_{IH}$  toward the switching voltage (centered typically at 2.3 volts), appreciable  $l_{CC}$  will flow. Such a high-current situation exists when an attempt is made to drive an HC input with a



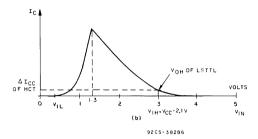


Fig. 2 - (a) HC input, CMOS interface, (b) HCT input, TTL interface.

TTL output. For example, with a TTL  $V_{OH}$  level of 3 volts driving an HC input, not only would a logic error exist, but several milliamperes of  $I_{CC}$  would flow. To overcome this problem, an external pull-up resistor could be used, as shown in Fig. 3, but the resistor would cause significant additional system power consumption because it would have to be kept small in value in order to keep system speed high. RCA HCT QMOS devices are the preferred solution when interfacing CMOS with TTL logic.

In power-critical applications, such as portable batteryoperated equipment or equipment operating in a batterypowered stand-by mode, HC quiescent power consumption may be a significant component of battery drain. The following formula is used to compute HC quiescent power consumption:

$$P_{dc} = V_{CC}I_{CC}$$
 (1

where  $V_{CC}$  is dependent upon the particular application, and  $I_{CC}$  is obtained from the data sheet of the particular device for a  $V_{CC}$  of 6 volts (HC types). The data sheet value given is also valid within the nominal 5 V  $\pm$  10% supply-voltage range of HCT types. The value of  $I_{CC}$  at  $V_{CC}$  = 6 V can be linearly reduced for any desired  $V_{CC}$  voltage; e.g., at  $V_{CC}$  = 2 V, use 1/3 of the limits shown in Table I.

Table I - 54/74HC Family Characteristics

			Temperature (°C)							
Symbol	Parameter		54HC	74HC	74HC		54HC		Units	Test Conditions
	ļ.	V _{cc}	25		-40 to 85		-55 to 125			
		(V)	Min.	Max.	Min.	Max.	Min.	Max.		
Icc	Quiescent									
	Supply Current	1								
	SSI	6	-	2	_	20		40	μΑ	$V_1 = V_{CC}$ or GND
	FF	6	_	4	_	40	—	80	μΑ	I ₀ = 0
	MSI	6	_	8		80	_	160	μΑ	

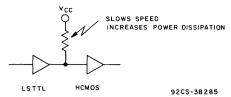


Fig. 3 - Use of pull-up resistor in LSTTL/HC interface.

#### **Computing HCT Quiescent Power Consumption**

Because HCT devices can be substituted for LSTTL devices and/or mixed with LS, ALS, AS, or FAST-TTL-family ICs in a system, their consumption of larger amounts of dc power than HC types is not significant. TTL worst-case output voltages are:  $V_{\text{OL}}=0.4\ V(\text{max})$  and  $V_{\text{OH}}=V_{\text{CC}}-2.1\ V(\text{min})$ . The  $V_{\text{OH}}$  (or logic 1) voltages result in the  $\Delta\text{I}_{\text{CC}}$  current flow illustrated in Fig. 2(b) and already described above. Note that only a logic-1 input causes appreciable quiescent leakage-current flow; a logic-0 input (0.4 V(max)) is close enough to ground to turn the NMOS transistor fully off. The total HCT-device quiescent power consumption is a function of the number of logic-1 inputs applied at the  $V_{\text{IH}}$  voltage level.

QMOS HCT data sheets specify  $\Delta I_{CC}$  at the worst-case input voltage of  $V_{CC}$  – 2.1 V for  $V_{CC}$  ranging from 4.5 volts to 5.5 volts, with normalized limits as shown in Table II.  $\Delta I_{CC}$  is further specified on a per-input-pin basis. This method of specification allows more accurate calculations if all the functions within a device are not being used or are being used at different input levels. For example, assume that two gates of an HCT10, a triple 3-input NAND Gate, are being driven by a TTL device with a 50% duty cycle. Given the information in Table II, quiescent power dissipation is calculated as follows:

$$P_{dc} = V_{cc}I_{cc} + V_{cc}\Delta I_{cc}$$
 (percent duty cycle high) (2) where  $\Delta I_{cc}$  is calculated on a unit-load basis as follows:

$$I_{CC}$$
 = (360  $\mu$ A/unit load) x (0.6 unit loads/input pin) x (6 input pins) (3) = 1.3 mA

#### Therefore:

$$P_{dc} = (5 \text{ V})(2 \mu\text{A}) + (1.3 \text{ mA}) \approx 6.5 \text{ mW}$$

Note that if all of the inputs of an HCT.device are driven by HC or equivalent CMOS output levels, only equation (1) need be used to calculate its static power dissipation. Note also that if a 50% duty cycle is assumed for input signals, the average dc power is 3.25 milliwatts for the HCT type. This figure compares with 35 milliwatts for a 74LS10 IC, and shows that the HCT device still provides a big savings in power, even in the worst-case application.

#### **DYNAMIC POWER CONSUMPTION**

Three factors affect QMOS dynamic power consumption:

- Load capacitance dissipation of output state, Fig. 4. Internal circuit capacitance
- Switching transition currents (when complementary transistors used in switching are both momentarily on)

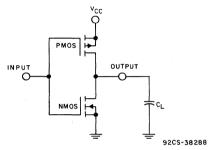


Fig. 4 - Simple QMOS inverter circuit driving a capacitive load.

For power calculation purposes, the load caused by internal device capacitance and switching transition currents is represented in one effective capacitance defined and specified as the  $C_{\rm pd}$ , power dissipation capacitance, the effective internal device capacitance used for operating-

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				CD74	HC10	/CD54	HC10	)					CD74	нст1	0/CD5	4HC	T10			
!		Test		741	HC/54	нс	74	HC	54	нс	Tes	t	74H	CT/54	нст	74F	HCT	541	НСТ	
Charac-	Cc	nditio	ns		Series	3	Se	ries	Se	ries	Condit	ions		Series	:	Se	ries	Se	ries	Units
teristic	Vı	lo	Vcc		+25° C	;	-40/4	-85° C	-5	55/	V _i	Vcc		+25° C	;	-40/+	-85° C	-5	55/	
									+12	5°C								+12	5° C	
	(V)	(mA)	(V)	Min.	Тур.	Max.	Min.	Max.	Min.	Max.			Min.	Тур.	Max.	Min.	Max.	Min.	Max.	
Qui-	Vcc										Vcc									
escent	or	0	6	_	-	2	_	20	_	40	or	5.5	_	_	2	- 1	20	_	40	μΑ
Device	Gnd							}	l		Gnd									
Current							l		1	1										
lcc									1	İ										
Quiescer	nt Dev	ice										4.5								
Device C	urren	t									V _{cc} -2.1	to	_	100	360	_	450	l —	490	μΑ
per input	t pin:											5.5	i			ļ		ł	ļ	'
1 unit loa	ad	$\Delta I_{CC}$										l				1				

^{*}For dual-supply systems theoretical worst case ( $V_1$  = 2.4 V,  $V_{CC}$  = 5.5 V) specification is 1.4 mA.

#### **HCT Input Loading Table**

Input	Unit Loads*
All	0.6

^{*}Unit Load is ΔI_{CC} limit specified in Static Characteristics Chart, e.g., 360 μA max. at 25° C.

power calculations. Each of the above power-consuming factors, along with  $C_{pd}$ , are explained in further detail below.

Unlike quiescent power consumption, dynamic, or operating-power, consumption is computed in the same way for both HC and HCT devices. Therefore, throughout this section, all equations presented are applicable to both HC and HCT devices.

#### Internal Capacitance

Inherent in any active semiconductor is internal parasitic capacitance, i.e., capacitance present in diode junctions, MOS transistor structures, and metal and polysilicon interconnections. This internal capacitance produces the same effect on internal active circuits as external capacitive loads, and varies from one device to another depending on the complexity of the device.

QMOS devices are fabricated by means of a self-aligned polysilicon gate process (3-micron gate length) to reduce this internal capacitance. This process minimizes gate-to-source and gate-to-drain capacitances. Junction capacitances, which are proportional to the junction area, are also reduced because shallower diffusions are utilized.

Fig. 5 illustrates the device parasitic capacitance present in a CMOS inverter.

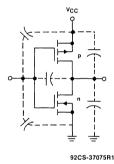


Fig. 5 - Parasitic capacitances in a CMOS inverter.

#### **Switching Transients**

When the basic QMOS inverter circuit, Fig. 6(a), is switching states, either from a logic 1 to a logic 0 or vice-versa, both transistors will be on for a short period of time. This

condition creates a momentary low-resistance path between  $V_{cc}$  and ground, Fig. 6(b). In this transient state, a momentary dc supply current flows and power is consumed. This low-resistance path is obviously a function of the number of transitions the device makes as well as the input-signal rise and fall time. In other words, power loss resulting from internal device switching is proportional to the input frequency (as is power loss due to internal capacitance).

#### Power-Dissipation Capacitance

Since power losses resulting from both net internal device capacitance and switching transient currents are frequency dependent, one term representing both factors is used for practical power-consumption calculations. This term is specified as  $C_{pd}$ , the no-load power dissipation capacitance.  2   $C_{pd}$  is defined for each QMOS device in each data sheet. Further, it is specified per logic function, that is, for each gate or flip-flop within a device. This method allows for more accurate power consumption calculations when logic functions are operating at different frequencies.

Since  $C_{pd}$  encompasses both internal capacitance and switching loads, the internal device operating power per logic function is:

$$P_{pd} = C_{pd} V_{cc}^2 f \tag{4}$$

where f is the operating frequency of the function.

#### COMPUTING HC AND HCT TOTAL POWER DISSIPATION

The formulas for total QMOS power dissipation are a combination of both static and dynamic power-consuming states. For HC devices:

$$P_{\text{total}} = V_{\text{CC}}I_{\text{CC}} + C_{\text{pd}}V_{\text{CC}}^2 f_{\text{in}} + C_{\text{L}}V_{\text{CC}}^2 f_{\text{out}}$$
 (5)

Total HCT power dissipation, when driven by TTL logic, is computed as follows:

$$\begin{aligned} P_{total} &= V_{cc}I_{cc} + \Delta I_{cc}V_{cc}D + C_{pd}V_{cc}^2f_{in} + C_LV_{cc}^2f_{out} & (6) \\ Where & D = Percent duty cycle High \end{aligned}$$

For HCT devices driven by HC devices, or at equivalent I/O voltage levels, equation (5) is used because the input voltage is essentially at  $V_{\text{CC}}$ , not at  $V_{\text{CC}}$  - 2.1 V.

#### QMOS VERSUS LS AND ALS POWER CONSUMPTION

In any integrated circuit, there exists a balance between speed and power consumption. LSTTL logic is relatively fast, but the bipolar circuitry used consumes considerable amounts of dc power. ALSTTL improves upon LSTTL by utilizing advanced finer-line geometry designs and ap-

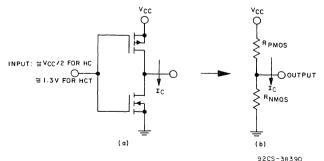


Fig. 6 - (a) Simple QMOS inverter circuit, (b) equivalent schematic of a QMOS inverter whose transistors represent a low resistance path between V_{cc} and ground.

propriately finer fabrication techniques. These improvements both increase speed and decrease dc power consumption by about 50% total for both factors.

CMOS devices consume minute amounts of quiescent power compared to any given TTL bipolar-logic-family device. However, until the development of the QMOS line of logic devices, CMOS devices were relatively slow. Now, QMOS types, by utilizing finer-line design and fabrication techniques, not only consume the minute amounts of dc and operating power of a CMOS device (depending on operating frequency, as previously defined in equations (5) and (6)), but are fast, as described below.

A popular way to illustrate the differences between IC logic families and their technologies is shown in Fig. 7. In the

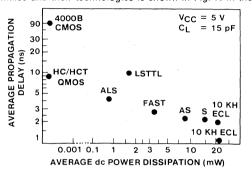


Fig. 7 - Speed/power spectrum for the popular logic technologies.

figure, a 2-input NAND gate is used to illustrate the dc power consumption versus the typical propagation delay for a number of technologies.

Table III is a compilation of speed/power products, in picojoules, for two CMOS-logic families and four TTL bipolar-logic families. In the table, SSI and MSI-complexity devices and those with complex flip-flop arrangements are used to illustrate speed/power differences. The major advantages of the new high-speed QMOS (HC/HCT) logic families are apparent:

- CMOS logic families have a 10³ speed/power advantage over TTL logic families.
- Maximum dc power savings using CMOS are far greater for the more complex MSI logic functions. As shown, a TTLAS160 device consumes 5 x 10³ times more dc power than an HC160.
- QMOS (HC) logic is approximately 10 times faster than equivalent CMOS devices; but retains the ultra-low dc power consumption of CMOS.

Fig. 8 illustrates the operating power consumption for SSI through MSI, QMOS, and LS devices. Note from the figures that CMOS devices realize their true power savings, from dc to several MHz, depending on device type and complexity. QMOS devices consume significant power only when switching, not when idling. TTL's continuous power consumption is the result of the many active bipolar transistors that must be continuously biased.

Fig. 8 also shows that as device complexity increases, the frequency at which CMOS and TTL devices consume the same amount of power increases, as would be expected.

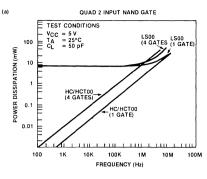
Table III - Speed Power	· Comparison ·	- Major TTL and	CMOS Logic Families
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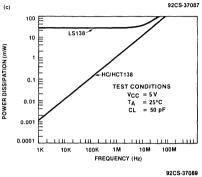
Generic Type	Logic Family	Max. Prop. Delay ¹ (ns)	Max. Power Dissipation ² (mW)	Speed/Power Product ³ (pj)
Gate	CMOS HC00	18	.01	.18
	CD4011	250	.001	.25
	TTL ALS00	13	16.5	215
	LS00	15 (15 pF)	24	363
	AS00	4	95.7	283
	FAST00	5	51	255
FF	CMOS HC74	32	.022	.70
	CD4013	300	.006	1.8
	TTL ALS74	17	22	374
	LS74	40 (15 pF)	44	1760
	AS74	8.5	88	748
	FAST74	8	88	704
MSI	CMOS HC160	35	.044	1.5
Counters	CD40160	400	.028	11.2
	<b>TTL</b> ASL160	17	116	1964
	LS160	27 (15 pF)	176	4752
ł	AS160	6	220	1320
	FAST160	10	275	2750

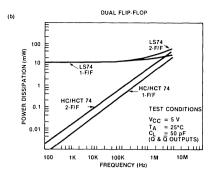
^{1.}  $V_{CC}$  = 5 V,  $C_L$  = 50 pF (15 pF for LS),  $T_A$  = 25° C, max. high or low state.

^{2.} Vcc = 5.5 V - max. dc high or low output conditions.

^{3.} Product of max. prop. delay and max. power dissipation.







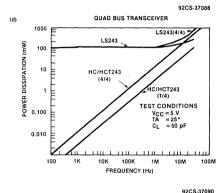


Fig. 8 - Power versus supply graphs for the (a) LS/HC00, (b) LS/HC74, (c) LS/HC7138, and (d) LS/HC243.

QMOS devices also consume more quiescent power as device complexity increases, but the leakage currents that cause the power consumption are of such small magnitude that they can (in most cases) be ignored (see Table I).

The subject figures also illustrate the operating power differences for one function or n functions in an IC package operating at the frequencies shown.

The power-consumption characteristics of these different logic families are easily translated into total system power. Fig. 9 illustrates the power consumed by the different logic families in a small logic system (one gate and two flipflops). The figure shows that QMOS substantially outperforms TTL in power consumption at both the device and the system level.

#### REFERENCES

- The QMOS family consists mainly of two series, the HC, which features CMOS input-voltage-level compatibility, and the HCT, which features LSTTL input-voltage-level compatibility. For a review of these series, see QMOS High-Speed CMOS Logic ICs, RCA Solid State DATABOOK SSD-290.
- 2. See ref. 1 under "Description of QMOS Product Line" for discussion of  $\mathbf{C}_{pd}$ .

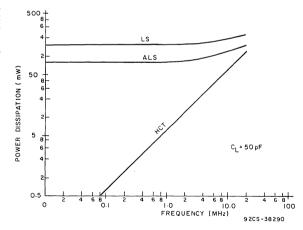


Fig. 9 - Power consumed by different logic families in a small logic system.

# Modification of LSTTL Test Programs to Test HCT High-Speed-CMOS Logic ICs

by R. Funk

The QMOS HCT family of high-speed logic ICs is designed and specified not only to replace LSTTL devices having the same type numbers, but to interface with all TTL, CD4000B CMOS, and QMOS HC logic families. As such, it is indeed one of the more, and perhaps the most, interface-flexible logic family. In existing and new-equipment designs where LSTTL devices are, or could be, used, these devices are easily replaced by RCA's HCT logic family because of the several advantages its QMOS technology has over LSTTL:

- Much lower dc and operating-power requirements
- Improved dc noise margin
- Better balance in output current drive and switching speed
- Much lower input current and three-state output leakage current in high-impedance state
- Improved reliability because of lower junction temperature
- Wider 74-family operating temperature (-40°C to +85°C, not LSTTL's 0°C to 70°C)

But the switch from LSTTL to QMOS has made it necessary for test personnel to switch from the testing of LSTTL functions to the testing of the identical HCT functions; this Note has been written to make that switch as easy as possible. The widely used Teradyne J283 test system is used as a basic frame of reference in this Note; however, the test information given is applicable to most other test equipment and bench-test situations.

A few tests (depending on device tested) in the LSTTL test programs designed to test dc and function on the J283 system are invalid for use with HCT devices, and will consistently produce erroneous results. These tests are easily modified and made valid for QMOS general-logic types. A few additional tests require modification if bus drivers and transceivers are to be tested.

### LSTTL TESTS REQUIRED TO BE MODIFIED FOR QMOS Input Current at $V_1 = 7 \text{ V (Appendix I)}$

Unlike the LSTTL circuit shown in Fig. 1(a), HCT circuits incorporate an input protection network, as shown in Fig. 1(b). Because of this network, input current will flow if the input voltage exceeds  $V_{\rm CC}$ . Therefore, when testing HCT types, change the input voltage from 7 volts to  $V_{\rm CC}$ . To test for the exact HCT low-level input leakage current, modify the input-voltage setting according to the dc characteristics for 54/74HCT circuits given in Appendix II of this Note.

#### Input Clamp Voltage

The HCT input-protection network incorporates a series resistor that will cause the input clamp voltage (with an input current of -18 milliamperes) to be much lower than the -1.5 volts specified for LSTTL. Since the input clamp voltage is not specified for HC circuits, this test could be omitted, or changed to have a conservative limit of -5 volts. This limit assumes a 200-ohm poly-resistor at the input plus -1.5 volts of diode-to-ground potential.

#### **Output Short-Circuit Current**

As shown in Appendix I, an LS02 has an  $I_{OS}$  (short-circuit output current) of -20 to -100 milliamperes. Test one output at a time and do not exceed a one-second test-time duration. For QMOS, make the following current-limit changes:

Standard Logic Types: -20 mA to -70 mA Bus Driver Types: -40 mA to -90 mA

Note that the  $l_{OS}$  test is nonstandard for QMOS HC or HCT types. The standard specified  $t_{TLH}$  and  $t_{THL}$  (transition times, low-to-high and high-to-low) values in QMOS specifications are a preferred method of directly measuring output speed. The  $l_{OS}$  limits are considered to be an indirect (and inaccurate) method of measuring the output sink and source speed characteristics for a given value of load capacitance.

#### Hysteresis (Bus Driver Types)

Many LSTTL bus-driver types undergo a  $\Delta V_T$  test using a 0.2-volt-minimum hysteresis limit. For QMOS HC and HCT, change this minimum to zero volts or bypass this test.

#### Output-Voltage-Low Test Current (Bus-Driver Types)

LSTTL bus drivers have two specifications for  $V_{\text{OL}}$  (low-level output voltage) test current which must be modified as shown below for QMOS types:

		loL
V _{OL} Maximum	LSTTL	HC/HCT Modification
0.4 V	12 mA	6 mA*
0.5 V	24 mA	8 mA

*Specified on QMOS data sheets

It appears from the table above that QMOS low-level output current is inferior to that of LS, i.e., 24 milliamperes versus only 8 milliamperes. However, the  $l_{os}$  current and output  $t_{THL}$  of QMOS are similar to those of LS. The real significance of the 24 milliamperes is the ability of an LSTTL bus driver to directly drive a dc termination, as shown in Fig. 2(a). But

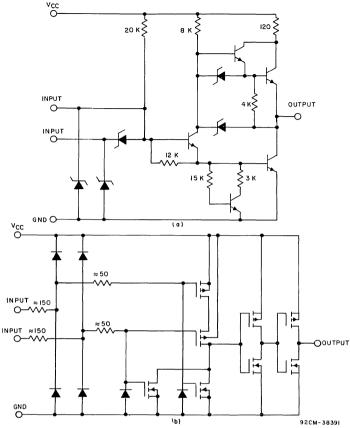


Fig. 1 - Comparison of LSTTL and HCT QMOS circuit structures: (a) two-input LSTTL NAND gate (1/4 54/74LS00), (b) two-input HCT QMOS NOR gate (1/4 CD54/74HCT02).

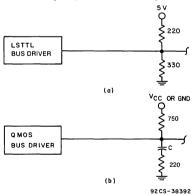


Fig. 2 - 100-ohm-line output termination: (a) LSTTL, 0.25 watt per output, (b) QMOS low-power alternative.

this ability represents a power dissipation of 0.25 watts per output section, and 2 watts per octal. For much lower power dissipation, use a QMOS type and a capacitively coupled 220-ohm resistor as shown in Fig. 2(b). The value of C in the figure depends on data rate.

#### **Continuity Tests**

Keep in mind that the QMOS input structure, Fig. 1(b), has a 150-ohm resistor in series with clamp diodes. Therefore, it is important to keep input current to  $\pm 20$  milliamperes maximum during continuity testing. With this amount of current, the test voltage is  $\pm 5.5$  volts maximum.

#### MORE COMPLETE TESTING OF HC OR HCT QMOS

To test HC or HCT QMOS ICs for low-power QMOS datasheet specifications, several tests other than those listed above may be modified. These modifications to existing LSTTL test limits or conditions are described below.

#### Quiescent Supply Current (Appendix II)

Setting supply current, I_{CC}, for the output-low condition test for HC circuits is no problem, but setting it for the output-high condition is more complicated. If the Teradyne J283 hardware has not been modified to handle CMOS, a comparator should be connected to each of the outputs of the HC circuit when it is placed under test. These comparators cause an extra load current of about 7 microamperes per output; the precise amount of current depends on the specific piece of test equipment. The extra load currents imposed are negligible compared with the I_{CC} of LSTTL circuits, and can be ignored when testing them.

However, these currents can be very significant compared with the total  $I_{\rm CC}$  of an HC type, and must be taken into account when testing HC QMOS types. A solution to this problem is to connect the high outputs of the HC type to  $V_{\rm CC}$  so that they are excluded from the  $I_{\rm CC}$  measuring path. This connection can be made with the Teradyne J283 MTEST VCC1 A B C D, where A, B, C, and D are the outputs in the high state.

### High-Impedance (Off-State) Current For Types Having Three-State Outputs

The high-impedance (off-state) LSTTL tests can be run for QMOS types, but only with much tighter limits, as shown below:

	LSTTL	QMOS
loz	20 <i>μ</i> Α	5 <i>μ</i> Α

where loz is three-state output off-state current.

#### Input Leakage Current (All QMOS Types)

Input-leakage-current LSTTL tests can also be run for QMOS devices but, again, with much tighter limits imposed, as shown below:

	LSTTL	QMOS
I _{IL}	-400 or -800 μA	-1 μA
I _{IH}	+20 μA or +40 μA	+1 μA

where  $I_{\rm IL}$  is low-level input current and  $I_{\rm IH}$  is high-level input current.

#### **FUNCTION TESTING**

QMOS and LSTTL types with the same type numbers have identical truth tables. High level ( $V_{OH}$ ), low level ( $V_{OL}$ ), and three-state ( $\approx$  1.5 volts using LS load circuit) conditions are met when HCT devices are used in place of LS. If ac parameters are measured as part of function testing, LS speed limits are almost always met or improved upon.

Test personnel should be aware that actual ac specifications for HC and HCT QMOS logic ICs are much more realistic than for LS, as shown in the ac test-specification comparison in Table I. Therefore, anyone wishing to test ac parameters should use the specifications and waveform definitions found in the prime source of QMOS information, the QMOS DATABOOK.¹

Table I - AC Test-Specification Comparison

Parameter	LSTTL	HCT QMOS
C∟	15/45 pF	50 pF
Vcc	5 V	4.5 V
Temperature	25° C	25° C,
·		74 (-40 to +85°C)
		54 (-55 to +125°C)

#### REFERENCE

 QMOS High-Speed CMOS Logic ICs, RCA Solid State DATABOOK SSD-290.

#### Appendix I - DC Characteristics for LSTTL Circuits

These figures are for positive-logic NAND gates and inverters with totem-pole outputs. For the characteristics of other types, refer to published data for LSTTL circuits.

Voltages are referenced to GND (ground = 0 V).

				54LS			74LS			
Parameter	Vcc	Symbol	Min.	Тур.	Max.	Min.	Тур.	Max.	Units	Conditions
Operating temperature	*	Tamb	-55		125	0	_	70	°C	
High-level input voltage	*	VIH	2	_	_	2	_	_	٧.	
Low-level input voltage	*	VIL		_	8.0	_	_	8.0	٧	
Input clamp voltage	min.	Vik		_	-1.5	_	_	-1.5	٧	l₁ = −18 mA
High-level output voltage	min.	Voн	2.5	3.4	_	2.7	3.4	_	V	$V_{1L} = max., I_{OH} = -400 \mu A$
Low-level output voltage	min.	Vol	_	0.25	0.4	_	_	0.4	٧	$V_{IH} = 2 V, I_{OL} = 4 mA$
Low-level output voltage	min.	$V_{OL}$		_	_		0.25	0.5	٧	$V_{IH} = 2 V, I_{OL} = 8 mA$
Input current at $V_1 = 7 \text{ V}$	max.	l ₁	_	_	0.1		_	0.1	mΑ	
High-level input current	max.	Iн	_		20		_	20	$\mu$ A	$V_{IH} = 2.7 V$
Low-level input current	max.	l _{1L}	_		-0.4	_	_	-0.4	mΑ	$V_{1L} = 0.4 V$
Short-circuit output current	max.	los	-20		-100	-20	_	-100	mΑ	4

^{*}Over Vcc range.

#### Notes:

For 54LS, Vcc = 4.5 V to 5.5 V; for 74LS, Vcc = 4.75 V to 5.25 V.

All typical values are at V_{CC} = 5 V, T_{amb} = 25° C.

For short-circuit output current, only one output must be shorted, and for not more than one second

### Appendix II - DC Characteristics for the CD54/74HCT Family of Circuits Voltages are referenced to GND (ground = 0 V)

T_{amb} (°C) CD54HCT/74HCT CD74HCT CD54HCT +25 -40 to +85 -55 to +125 Conditions Vcc Other Parameter (V) Symbol Min. Typ. Max. Min. Max. Min. Max. Units V High-level input voltage 4.5-5.5  $V_{\text{IH}}$ 2 2 2 V Low-level input voltage 4.5-5.5 0.8 0.8 0.8 ٧  $V_{IL}$ ٧  $V_{IH}$  or  $V_{IL}$   $-I_0 = 20 \mu A$ 4.5 4.4 4.4 High-level output voltage 4.5 Voн 4.4 all outputs ٧ High-level output voltage 4.5 3.98 3.84 3.7 VIH Or VIL -Io = 4 mA Voн standard outputs 3.98 VIH or VII -lo = 6 mA 3.84 3.7 High-level output voltage 4.5 Voн bus-driver outputs Low-level output voltage 4.5  $V_{OL}$ 0 0.1 0.1 0.1 ٧  $V_{IH}$  or  $V_{IL}$   $I_0 = 20 \mu A$ all outputs Low-level output voltage 0.26 0.33 0.4 VIH Or VIL Io = 4 mA 4.5  $V_{OL}$ standard outputs 4.5 0.26 0.33 0.4 ٧ VIH Or VIL Io = 6 mA Low-level output voltage VoL bus-driver outputs μΑ 5.5 VIH or VIL Input leakage current  $\pm h$ 0.1 1 1 1 μΑ VIH or VIL  $V_s = V_{cc}$ Analog switch off-state 5.5 ±Ιs 0.1 current per channel 3-state output off-state 5.5 ±loz 0.5 5 10 μA VIH OF VIL Vo* current Quiescent supply current 2 20 40 μΑ V_{cc} or  $I_0 = 0$ SSI 5.5 Icc  $I_0 = 0$ 40 80 GND Flip-flops 5.5 Icc 4 μΑ  $I_0 = 0$ 8 80 160 μA 5.5 MSI Icc

 $^{^*}V_0 = V_{CC}$  or GND per input pin; other inputs at  $V_{CC}$  or GND;  $I_0 = 0$ .

## Interfacing HC/HCT QMOS Logic with Other Families and Various Types of Loads

by R. Funk

The demand for smaller, lighter, electronic equipment that consumes little power is constant. And today's logic designers want these qualities matched by digital logic with high operating speeds. However, speed and power, while perhaps paramount in the initial choice of a logic family, are not the only basis for decision. Another very important factor is interface flexibility: the inherent capacity of a family to interface with other logic families and to drive various loads.

This Application Note describes the interface capability of the new high-speed CMOS CD54/74 HC/HCT logic families, probably the most interface-capable families yet devised. Fig. 1 illustrates the low dc power consumption and high speed of the HC/HCT families, both prime qualities for interfacing flexibility. Table I lists other important qualities. All of these characteristics, along with HC/HCT-family static and dynamic noise immunity, are discussed in this Note. The Note describes in detail HC/HCT interfaces with LSTTL, CMOS CD4000B-series, NMOS, and ECL devices, and interfaces with terminated buses, displays, and relay or stepping-motor coils, including interfaces with nonstandard output levels.

#### INTERFACE CONSIDERATIONS

Fig. 1 shows that the speeds of the HC, HCT, and LSTTL logic families are equivalent. In fact, the HCT family is a low-power replacement for the LSTTL family, and is interface compatible with all TTL families. The HC family is a low-power, high-noise-immunity alternative to the LSTTL family, and like the HCT family, will drive all TTL and CMOS families directly at various fanouts, depending on family.

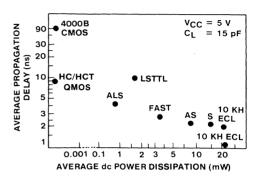


Fig. 1 - Logic-family speed-power chart.

Table II is a tabulation of interface techniques used between various popular logic families; the superiority of the HCT over the TTL family is evident. For example, the table shows there are 4.0f6 possible direct interfaces from HCT and only 2 of 6 for TTL.

#### **CMOS and TTL Output Configurations**

The typical output structure of an HC/HCT CMOS IC is shown in Fig. 2(a). When the output is high or low ( $V_{OL}$ ), its level is very close to  $V_{CC}$  or ground, respectively. In contrast, the high-level output voltage for the standard TTL

Table I - HC/HCT Family Characteristics

Characteristic	нс	нст
Supply Voltage	2 V to 6 V	4.5 V to 5.5 V rated 2 V to 6 V capability
Temperature (74 family) Input Switching Voltage	-40° C to +85° C	-40°C to +85°C
For V _{cc} =5 V: Typical	2.5 V	1.4 V
Worst Case	1 V to 3.5 V	0.8 V to 2 V (same as TTL families)
Output Voltage:		
Driving other CMOS Logic	GND to Vcc	GND to Vcc
Driving TTL (Vol)	0.4 V (10-15 LSTTL loads)	0.4 V (10-15 LSTTL loads)
(V _{он} )	3.7 V	3.7 V
Typ. Output Transition for C _L = 50 pF	7 ns (balanced)	7 ns (balanced)
= '	7 IIS (Dalanced)	
Input Current (typ.)	10 pA	10 pA

	Table II - Inter	facing HC/HC	T QMOS to Other	Logic Familie	<b>es</b>	
TO:	HC 5 V Supply	HCT 5 V Supply	CD5000B 5 V Supply	CD4000B 6-15 V Supply	TTL* 5 V Supply	ECL 10K
FROM:						
HC-5 V supply	direct	direct	direct	CD4504**	direct	10124
HCT-5 V supply	direct	direct	direct	CD4504**	direct	10124
CD4000B—5 V supply	direct	direct	direct	CD4504**	direct	10124
CD4000B 6-15 V supply	4049 or 4050	4049 or 4050	4049 or 4050	direct	4049 or 4050	transistor
TTL*-5 V supply	pull-up resistor	direct	pull-up resistor	CD4504**	direct	10124
ECL-10K/KH	10125	10125	10125	transistor	10124	direct

^{*}Includes LS, S, STD, FAST, ALS, and AS.

^{**}An alternative is a pull-up resistor and the CD40109 type.

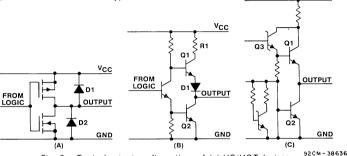


Fig. 2 - Typical output configurations of: (a) HC/HCT devices
- D1 and D2 are the inherent diodes of the p-drain and
the n-drain, respectively, (b) standard TTL, and (c)
low-power Schottky TTL (LSTTL).

circuit shown in Fig. 2(b) is limited by the  $V_{BE}$  of Q1 plus the voltage drop across D1, resulting in a maximum  $V_{OH}$  of 3.5 volts at a  $V_{CC}$  of 5 volts. Further, if a collector current is flowing, R1 will cause an additional voltage drop, and the worst-case  $V_{OH}$  minimum specified for TTL, 2.4 volts (at  $I_{OH}$  maximum) over the full temperature and power supply range, may be realized. The low-level output voltage for TTL is the collector/emitter saturation voltage of Q2, and  $V_{OL}$  will range from 0.2 volt to 0.5 volt maximum depending on the fanout and, hence, total sink current.

In the output structure for the LSTTL device of Fig. 2(c),  $V_{OH}$  is limited by the  $V_{BE}$  of both Q1 and Q3 (the diode is not considered a part of the LSTTL output structure) and is typically 3.4 volts. LSTTL specifications quote  $V_{OH}(min)$  as 2.7 volts over the full temperature range with a  $V_{CC}(min)$  of 4.75 volts. The maximum value of  $V_{OL}$  for LSTTL can, again, range from 0.2 to 0.5 volt depending on application and temperature conditions.

#### CMOS Input Structures

The input structure for HC/HCT devices is shown in Fig. 3(a). Under normal operating conditions, the input voltage should swing within the supply voltage limits of  $V_{\rm CC}$  and ground, since exceeding these limits can cause a current to flow through the input protection diodes, D1 and D2. The maximum transient current permitted through these diodes is 20 milliamperes; if this limit is exceeded, the functionality of the circuit could be impaired. As the MOS transistors Q1 and Q2 are electrically identical, the typical input switching voltage of the HC device is  $V_{\rm CC}/2$ .

۷сс

The input configuration for HCT devices is similar to that for HC circuits, but with the addition of a level-shifting diode, D3, between PMOS transistor Q1 and V_{CC}. This configuration is shown in Fig. 3(b). The effect of D3, combined with the large NMOS transistor Q2, which has a higher gain than PMOS transistor Q1, is to reduce the input switching level to, typically, 1.4 volts.

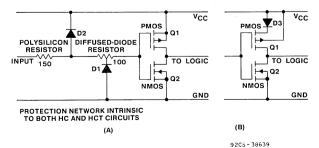


Fig. 3 - Typical input structures of: (a) HC devices, and (b) HCT devices.

The advantage of diode D3 is that it reduces power dissipation when a high input from a TTL output is applied. This high level can be as low as 2.4 volts, and although it will be recognized as a logic 1, the PMOS transistor Q1 will not be fully cut off, allowing a flowthrough current between  $V_{\rm CC}$  and ground. However, D3, and the influence of the backgate (substrate) connection of Q1 to  $V_{\rm CC}$ , dramatically reduces the flowthrough current and, therefore, reduces the power dissipation in the input stage while maintaining device input switching levels compatible with LSTTL.

#### **HC/HCT INTERFACES**

When HCT and LSTTL devices operate from the same supply, the quiescent flowthrough current,  $I_c$ , at  $V_{IH}$  = 2.4 V and  $V_{CC}$  = 4.5 V is typically only 100 microamperes. This means that the HCT input structure provides low CMOStype power dissipation, even when driven from TTL. If  $V_{CC}$  is increased to 5.5 volts, the minimum high-level output voltage also rises 1 volt to 3.4 volts.

When interfacing LSTTL with HC/HCT devices in a dualsupply-voltage system, the following worst-case conditions apply:

V_{OH}(min) for TTL = 2.4 V V_{OH}(min) for LSTTL = 2.7 V and

 $V_{IH}(min)$  for HC devices = 3.85 V (70% of  $V_{CC}$ )

V_{IH}(min) for HCT devices = 2 V

where  $V_{CC} = 4.75$  V for TTL and 5.5 V for HC devices over the full operating temperature range.

It is clear from the above figures that the worst-case TTL high-level output voltage is less than the minimum high-level input voltage for HC devices, and that some special interface technique is required. A solution is provided in the circuit in Fig. 4(a), where pull-up resistor R1 pulls the output

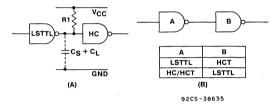


Fig. 4 - Techniques for interfacing: (a) LSTTL with HC devices, and (b) LSTTL with HCT devices, and HC/HCT with LSTTL devices.

voltage of the LSTTL against  $V_{\rm CC}$ . However, this technique is not recommended because the time-constant formed by the pull-up resistor and the stray capacitance ( $C_{\rm S}$ ), plus the load capacitance ( $C_{\rm L}$ ), will increase the propagation delay. Furthermore, with this set-up, the propagation time is less predictable because it relies on both active and passive RC time-constants.

Although a low value for R1 will reduce the propagation delay, it will lead to extra power consumption and reduce the noise-margin-low (discussed further below under Noise Immunity) due to the active load. Both of these unwanted occurrences conflict with the purpose of using HC family devices. In addition, the pull-up resistor requires board space and insertion time, thus increasing production costs. Therefore, the pull-up resistor interface should be used only if unavoidable. The practical solution is to use HCT devices (all types in the CD54/74 family are available in both HC and HCT versions), which interface directly with LSTTL, as shown in Fig. 4(b).

#### **Driving LSTTL**

Since the output of HC devices swings between  $V_{\text{CC}}$  and ground, they are TTL-input compatible, and the interface is a direct connection, Fig. 4(b).

When an HCT device is the driving source for an LSTTL device, the speed can be accurately predicted because the LSTTL logic-switching threshold of 1.3 volts is the same as that for HCT ICs. For HC driving sources, the speed difference introduced by the HC logic switching threshold of, typically, V_{CC}/2 can be calculated from the specified output transition times (obtained from the appropriate Data Sheets).

Table III gives the driving capability (fanout) of HC/HCT devices for the various TTL families.

Table III - Maximum Fanout for HC/HCT Driving TTL

Receiving Input	Standard Output	Bus-Driver Output
TTL	2	3
LSTTL	10	15
STTL	2	3
FAST	6	10

#### CD4000 B-Series CMOS

HC/HCT devices can be coupled directly to standard CD4000B-series CMOS ICs if they operate from the same supply voltage. However, if the circuits have different supply voltages, level shifting is necessary. The configuration shown in Fig. 5(a) illustrates the circuit for HC/HCT to CD4000B interfaces using the CD4504 low-to-high level shifter. Note that this IC is capable of interfacing either TTL output logic levels or CMOS logic levels to a higher output-voltage level. The reader is reminded that the CD4000B CMOS logic family may be operated up to 18 volts; the HC/HCT family operates at up to a 6-volt supply-voltage level, but also down as low as 2 volts.

Fig. 5(b) shows how to interface the CD4000B series with HC/HCT ICs using the CD4049/4050B or HC4049/4050 buffer ICs. These buffers do not have an input clamping diode to  $V_{\rm CC}$ , so that the maximum input level is 15 volts. The logic-level switching threshold remains referenced to  $V_{\rm CC}$ ; therefore, the noise-margin-low will be the same as for the 5-volt specification.

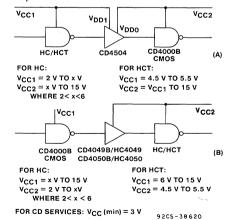


Fig. 5 - Techniques for interfacing: (a) HC/HCT devices with CD4000B series CMOS, and (b) CD4000B series CMOS with HC/HCT devices.

#### **NMOS**

The rules for interfacing TTL apply when interfacing HC/HCT devices with NMOS devices (microprocessors, memories, etc.) since NMOS ICs generally have TTL-compatible inputs and outputs. Exceptions are NMOS ICs with open-drain outputs, where a pull-up resistor must be used to load the output. The HCT device inputs directly accept active NMOS output-voltage levels.

#### ECL 10K

To interface HC/HCT ICs with ECL 10K-series logic, the 10124 TTL-to-ECL and the 10125 ECL-to-TTL translator ICs (for HC/HCT-to-ECL and ECL-to-HC/HCT interfaces, respectively) are used. Note that these devices operate at TTL levels. When employing the 10125 for interfacing HC circuits, the pull-up resistor, R1, must be used in accordance with the instructions for driving HC devices from TTL. The circuit configurations are shown in Figs. 6(a) and 6(b). Note that if an HCT device is used in the ECL interface (the definite preference) the pull-up resistor of Fig. 6(a) is eliminated.

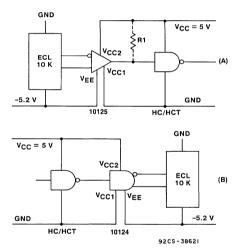


Fig. 6 - Techniques for interfacing: (a) ECL 10K logic with HC/HCT circuits - R1 is only required when driving HC types, and (b) HC/HCT devices with ECL 10K logic.

#### **Terminated Buses**

Buses are used chiefly in industrial applications. The harsh environments found in these applications impose several requirements on microprocessor-based systems; electrical-noise immunity and the need for battery back-up are two examples. The CMOS technology provides the ideal solution to these requirements. The HC CMOS devices offer superior noise immunity, similar operating speed, and lower power dissipation over a wider temperature and supply-voltage range in comparison with LSTTL ICs. The noise immunity in the low logic state is the same for HCT devices as for LSTTL.

The development of a new bus standard for CMOS systems should be based on the performance of the devices available with bus-driver outputs, for example, the CD54/74HC245 transceiver. Figs. 7(a) and 7(b) show examples of conventional TTL and HC/HCT bus terminations, respectively.

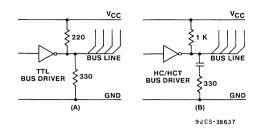


Fig. 7 - Examples of bus terminations used in: (a)conventional bipolar (TTL) technologies and (b) HC/HCT systems.

The particular disadvantage to the theveninized 120-ohm termination of Fig. 7(a), the conventional TTL bus termination, is the 0.25 watt dissipated continuously by the combination of the output driver and the 120-ohm load. This dissipation represents 2 watts for an octal buffer.

The HC/HCT-family bus drivers have a 6-milliampere sink current, not the 12 milliamperes of LSTTL, and are not designed to directly drive the 120-ohm load of Fig. 7(a) for two reasons: first, 2 watts dissipation does not represent a low-power solution, and second, HC/HCT outputs could be designed to match the very high 2-watt-dissipation application of Fig. 7(a), but would also generate much higher switching-current transients, which would push up EMI to inappropriately high levels. Therefore, the interface of Fig. 7(b) is preferred for its much lower power consumption and lower EMI. The value of C in Fig. 7(b) is carefully selected for the range of frequencies (data rates) on the bus.

HC/HCT devices do not generally have input hysteresis, so that Schmitt-trigger circuits should be used if slow, noisy bus rise and fall voltages call for hysteresis in the receiver. The CD54/74HC/HCT14 and 132 are two ICs that can be used for noise-tolerant systems. Five devices in the flip-flop series (CD54/74HC/HCT73, 74, 107, 109, and 112) also have Schmitt triggers in the clock input. Note that HC devices are preferred over HCT devices as bus receivers because of their high low-level-input noise margin (typically 2 volts).

#### Nonstandard Levels

In many applications, CD54/74 high-speed CMOS ICs will have to interface with nonstandard input and output levels, for example, with industrial or automotive systems operating from a 12 to 24-volt supply. The circuits in Figs. 8(a) and 8(b) show the basic design rules for these interfaces. Fig. 8(c) illustrates an example of a user-edge input circuit for interfacing with input levels greater than  $V_{\rm CC}$ . The configuration for HC/HCT devices driving loads from an external power supply is given in Fig. 9(a). Figs. 9(b) and 9(c) show HC/HCT devices driving loads (for example, a relay) on the same supply voltage.

Fig. 10(a) is an interesting low-cost but also lower-speed high-to-low interface: 12 to 5-volt logic levels using only 100-kilohm resistors in series with each input. Fig. 10(b) shows why this interface is reliable with good noise margins; RCA HC/HCT designs guarantee that forced input current into  $V_{\rm CC}$  will result in less than 0.05 of this current flowing into ground. In Fig. 10(b),  $V_{\rm IL}$  at B is less than 0.34 volt, well under the specified  $V_{\rm IL}$  of 1-volt maximum. Other high-to-low voltage-interface combinations with different resistor values may be determined with knowledge of the 0.05 value of current gain ( $\alpha$ ) between adjacent inputs.

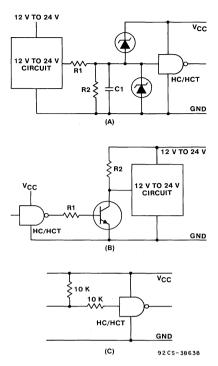


Fig. 8 - Technique for interfacing: (a) nonstandard logic levels with HC/HCT circuits - values of R1 and R2 depend on the output voltage of the driving circuit and C1 depends on the noise and speed, (b) HC/HCT devices with nonstandard logic levels - values of R1 and R2 depend on supply voltage and transistor type, and (c) a useredge input circuit configuration for interfacing with input voltages greater than Vcc.

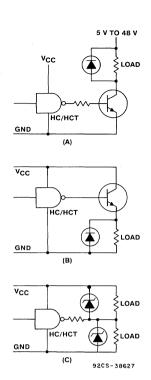


Fig. 9 - Interfacing loaded HC/HCT devices: (a) an external power supply via a transistor, (b) the same power supply via a transistor, (c) the interfacing of HC/HCT directly with loads on the same power supply.

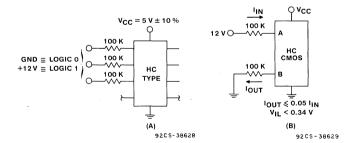


Fig. 10 - Low-cost, low-speed 12-volt-logic to 5-volt-logic interfaces.

The typical value of alpha  $(\alpha)$  for the bipolar parasitic input transistor is 0.001. The low value of alpha is an important feature of the RCA HC/HCT family because it eliminates transient logic errors in the presence of transient voltages exceeding  $V_{CC}$  at any input.

#### Displays

The CMOS technology, with its rail-to-rail output switching,

is just as ideal for HC/HCT family devices driving LCD displays as it has been for CD4000B-series devices. Fig. 11(a) illustrates the basic BCD-to-7-segment LCD interface (HC/HCT4543) plus the single-segment LCD interface using the HC/HCT 86 type. The popular 4511 type is carried into the HC/HCT family for the basic LED BCD-to-7-segment interface, as illustrated in Fig. 11(b).

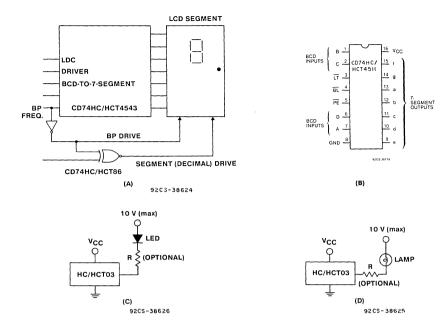


Fig. 11 - Display interfacing: (a) LCD, (b) and (c) LED, (d) lamp.

For single-segment LED interface, the open drain 74HC/HCT03 type is ideal, Fig. 11(c). Since the 03 type does not have an output-to- $V_{\rm CC}$  forward diode in its output circuit, the LED may be supplied by up to 10 volts. R may be useful in limiting current and reducing power. This same 03 type can also be used for driving an indicator lamp, as shown in Fig. 11(d).

#### **Relay or Stepping Motor Coils**

Another application of the open drain HC/HCT03 type is the relay or stepping motor interface shown in Fig. 12. The external diode across the coil absorbs the back emf of the coil.

#### L² MOSFET Power Transistor

RCA logic level ( $L^2$ ) MOS power transistors, Fig. 13, are ideally driven by any HC/HCT output. Higher switching speeds, 200 nanoseconds, are achieved using the bus-drive output types. HC/HCT outputs will reliably switch these new  $L^2$  MOS power devices using only a 5-volt supply for  $V_{\rm CC}$ ; this is truly a breakthrough in power-transistor-interface applications cost.

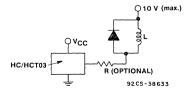


Fig. 12 - Coil driver.

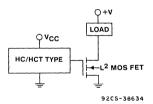


Fig. 13 - L² MOSFET power-transistor drive.

#### NOISE IMMUNITY IN THE HC/HCT FAMILY

#### General

The noise-immunity characteristics of logic devices can be divided into two categories, static and dynamic. Static noise immunity can be divided further into static noise-immunity-low, the difference between the  $V_{\rm IL}({\rm max})$  of the receiving circuit and the  $V_{\rm OL}({\rm max})$  from the driving current, and static noise-immunity-high, the difference between the  $V_{\rm OH}({\rm min})$  from the driving circuit and the  $V_{\rm IH}({\rm min})$  of the receiving circuit.

The guaranteed static noise-immunity characteristics for LSTTL and HC/HCT devices are shown in Table IV. If the static noise margins for LSTTL are assumed to be unity, (for both the high and low states), a direct comparison of LSTTL and HC/HCT static noise margins can be made by taking the ratio shown in Table V. These results are particularly impressive when the extended ambient temperature range and the lower supply voltage of the HC/HCT family is considered.

Table IV - Static Noise Margins for LSTTL at  $V_{\rm CC}$ =4.75 V and HC/HCT Systems at  $V_{\rm CC}$ =4.5 V

	LSTTL	нс	HCT
V _{OH} (min)	2.7 V	4.4 V	4.4
V _{IH} (min)	2 V	3.15 V	2
Noise-Margin-High	0.7 V	1.25 V	2.4 V
V _{IL} (max)	0.8 V	0.9 V	0.8 V
V _{OL} (max)	0.4 V	0.1 V	0.1 V
Noise-Margin-Low	0.4 V	0.8 V	0.7 V

Table V - Ratio of Static Noise Margins, LSTTL to HC/HCT

	LSTTL	нс	нст
Noise-Margin-High	1	1.75	3.4
Noise-Margin-Low	1	2	1.75
Ambient Temperatur	re		
Range (Tamb)	0 to +70°C	-40 to +85° C	-40 to +85°C
Supply Voltage (Vcc)	4.75 V	4.5 V	4.5 V

The graph in Fig. 14(a) compares the static noise margins for HC devices with those for LSTTL. The graph illustrates that while HC circuits can drive LSTTL (as  $V_{OH}(min)$ ) for an HC device is greater than  $V_{IH}(min)$  for an LSTTL device), the

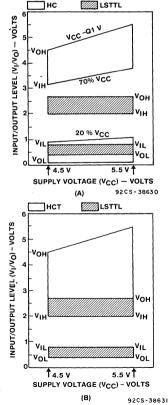


Fig. 14 - Static noise margins for: (a) HC devices compared with LSTTL, and (b) HCT devices compared with LSTTL in a mixed technology system.

converse is not true (since  $V_{OH}(min)$  for LSTTL is less than  $V_{OH}(min)$  for HC; there is no overlap in the noise-margin-high regions). Therefore, the noise-margin-high for LSTTL driving HC devices is said to be negative, which explains the reason for the problematical external pull-up resistor interface described in Fig. 4(a).

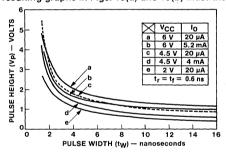
In a mixed-technology system with fully loaded HCT outputs driving LSTTL inputs, the static noise-margin-low is equal for both families, and the HCT devices exhibit an excellent static noise-margin-high that encompasses that displayed by LSTTL. This situation is illustrated by the graph in Fig. 14(b), which shows that HCT and LSTTL devices are fully interchangeable in a mixed-technology system.

#### **Dynamic noise immunity**

Dynamic noise immunity for HC/HCT circuits also falls into two categories, high and low. The dynamic noise-margin-low is, again, the smaller of the two, and is, therefore, the parameter considered here.

To plot the dynamic noise-margin-low for HC/HCT devices, a pulse of known magnitude,  $V_P$ , is applied to the input of a device; its width,  $t_W$ , is then increased until the device just begins to switch. The input level on which  $V_P$  is based is equal to the switching voltage minus the worst-case static noise-margin-low. Pulse width,  $t_W$ , is measured at half pulse height,  $V_P/2$ , and the rise and fall times,  $t_r$  and  $t_r$ , are 0.6 nanosecond.  $V_P$  is reduced in increments and the  $t_W$  for each new value ascertained. The test is repeated over a series of varying supply voltages ( $V_{CC}$  between 2 and 6 volts for HC and at 5 volts for HCT) and output currents,  $I_P$ .

The resulting graphs in Figs. 15(a) and 15(b) illustrate the



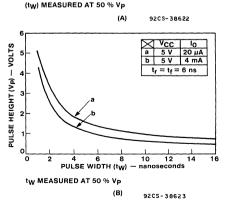


Fig. 15 - Dynamic noise immunity characteristics (worst-case, fully loaded driver) for: (a) HC devices and (b) HCT devices.

dynamic noise immunity characteristics of HC and HCT circuits, respectively. Note that an increase in Io lowers the curve and reduces the dynamic noise immunity. As these curves illustrate for the worst-case conditions with fully loaded HC/HCT devices, a system using only HC or HCT circuits will demonstrate an increase in dynamic noise

immunity, shifting the curves up 0.3 volt.

Derived from the typical input switching threshold levels of 1.3 and 2.5 volts for HC and HCT, respectively, the noise immunity characteristics will show a typical improvement of 0.8 volt in HCT systems and 1.2 volts in HC systems.

## Power-Supply Distribution and Decoupling For QMOS High-Speed-Logic ICs

by R. Funk

The HC and HCT high-speed QMOS IC logic families available from RCA offer the user many advantages over TTL logic families. These advantages include much lower power consumption, better noise margin (mainly in the HC devices), wider operating-voltage range, wider operating-temperature range, lower input current, lower three-state current, superior high-to-low and low-to-high output transition time and propagation delay balance, and better reliability. However, HC/HCT CMOS does share one common liability with LSTTL: switching transients generated on the ground and supply rails can dangerously reduce logic noise margin if not compensated.

Higher speeds, faster edges, and higher output-drive currents cause higher-frequency current transients to be imposed on ground and  $V_{\rm CC}$  rails of an IC. The familiar L di/dt voltage transient is developed, its value depending on the inductance in the ground or  $V_{\rm CC}$  connection from chip to IC lead. For octal bus-driver types, one volt of L di/dt is possible depending on inductance, device decoupling, and power-supply decoupling. This Note focuses on power-supply distribution and decoupling to reduce switching noise. One source of this noise, an important system factor relative to IC switching, is rf radiated noise, noise that can interfere with communications in the local area. Some general ways to reduce L di/dt rf noise, i.e., voltage generation on ground and supply lines, are described below.

#### **POWER DISTRIBUTION**

Before decoupling can provide any noise reduction, there must first be a good power-distribution network. A good ground connection is vital, and so a good connection pattern is required.

The commonly accepted ground pattern shown in Fig. 1

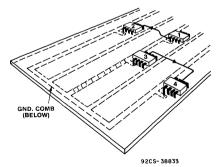


Fig. 1 - Common ground path on two-sided board.

can cause problems. In the figure, an output from device 1 drives an input to device 2, and an output from device 3 drives an input to device 4. Since the signal path 1 to 2 and 3 to 4 are not coupled, there should be no crosstalk. However, devices 1 and 3 share the crosshatched part of the ground line, as shown, and switching of the output of device 1 could produce a spike on the ground of device 3, causing the input to device 4 to switch. It is, therefore, advisable to reduce the single ground path on a double-sided board by using links, as shown in Fig. 2. This advice is especially true for boards

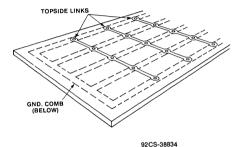


Fig. 2 - Reducing ground paths on two-sided board.

where high currents are switched. Avoid using jumpers like the one shown in Fig. 3 for ground and power line (V_{CC}) connections. Jumpers are unlikely to be used in production printed-circuit boards, but they should also be avoided on prototype and single boards because the inductance they introduce into the lines permits coupling between outputs. Printed-circuit boards equipped with premanufactured ground connections or copper strips to connect the pins to around should be used.

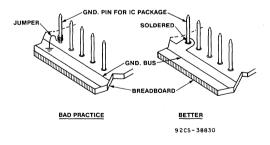


Fig. 3 - Ground connection on a logic board.

An even better solution is to use multilayer printed-circuit boards, where different layers can be used for the supply rails and the copper interconnections. The capacitive coupling between ground and  $V_{\rm CC}$  is essential for high-frequency noise-pulse reduction. The capacitive coupling has the distinct advantage of being free from the inductive effects of the interconnections and, therefore, acts like a discrete decoupling capacitor.

Even with double-sided boards, it is advisable to have the  $V_{\text{CC}}$  and ground lines on opposite sides of the board wherever possible. A less expensive alternative to multilayer boards is the multiwire board, which offers the same high-frequency noise characteristics.

No matter what type of board is used, it is recommended that it have at least five ground pins per connector to assure ground-current distribution. The precautions taken with ground lines also apply to the  $V_{\rm CC}$  line. Power-line stability is a must, a difference of only 0.5 V between  $V_{\rm CC}$  lines can produce unwanted effects. It is advisable to provide separate power stabilization for each board to isolate noise sources and to eliminate large stabilizer circuits with their heavy-gauge (low-impedance) wiring to each board. However, care must be taken in designing power stabilization because a fault on a board's stabilizer circuit may be transmitted via the HC/HCT input structure to other boards, possibly causing damage.

#### DECOUPLING

No matter how good the  $V_{\text{CC}}$  and ground connections, all line-inductance effects cannot be avoided. This is where decoupling plays its part. Ceramic capacitors are the nearest approximation to ideal decoupling capacitors since they have almost no series inductance. But the advantage of using inductance-free capacitors is lost if long connections to the capacitor are used. These over-long connections can result in a tuned LC-circuit with a very high Q factor. The oscillations produced would have a worse effect on the circuit than if there were no decoupling at all. If it is not possible to make the decoupling connections shorter than 20 mm, place tracks in parallel, with a separation of at least one track width, as shown in Fig. 4. Making the connections thicker will have almost no effect.

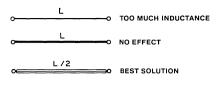


Fig. 4 - Comparison of decoupling tracks.

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The capacitors to be used should be carefully selected. Many capacitors are produced with leads bent, as shown in Fig. 5(a); these may introduce unwanted inductance. The best capacitors are those with leads shaped as in Fig. 5(b).

In tests, good decoupling was obtained by using a minimum of:

- one 47 μF bulk capacitor per standard IC card
- one 1  $\mu$ F tantalum capacitor per 10 packages of SSI logic
- one 22 nF ceramic capacitor for each octal bus-driver circuit and for each counter/shift register (MSI logic)
- one 22 nF ceramic capacitor per four packages of SSI logic

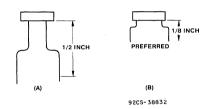


Fig. 5 - Optimum capacitor lead shape.

### Replacing LSTTL with QMOS High-Speed Logic ICs

by J. Nadolski

Until the development of RCA HC and HCT high-speed-CMOS logic ICs, high-speed logic devices were available only in the high-power-consuming bipolar technology. The HC/HCT QMOS family features LSTTL speed along with many performance features superior to LSTTL. HCT CMOS ICs have TTL-compatible input-voltage levels and are intended to be CMOS substitutes for bipolar LSTTL logic ICs of the same type. HC CMOS ICs have CMOS voltage-level input compatibility and feature high noise immunity in all-CMOS system designs.

Replacement of an LSTTL IC with an HCT IC provides the identical logic function, same pin out, same speed, and same general-purpose logic fanout of 10 LSTTL loads, but with much less power dissipation. LSTTL bus-driver types can drive 100-ohm transmission-line terminations, but at a huge sacrifice in system power consumption. Techniques that can be used to terminate 100-ohm lines, and other types of low-power terminations involving LSTTL and QMOS ICs, are presented in this Note.

#### PERFORMANCE COMPARISON

Of paramount importance in the comparison of LSTTL and QMOS (HCT) performance are the identical input-voltage specifications of the two technologies:

V_{IL}(max) = 0.8 V V_{IH}(min) = 2 V

Table I is a comparison of all applications-related parameters. It is evident from this table that not only does HCT QMOS substitute easily for LSTTL, but system performance is enhanced through such characteristics as better signal transition time and propagation delay balance, better noise margin, and lower supply and signal-line currents. The comparisons below follow the organization of Table I.

Power Consumption-(dc)—HCT power consumption is essentially zero in comparison to LSTTL. ac (operating)—HCT power is frequency dependent and comparable to LSTTL at continuously high operating frequencies. Generally, HCT power is much lower because average logic data rates are under 1 MHz.¹

Voltage—HC/HCT CMOS requires much less voltage regulation than LSTTL. HCT devices can actually operate at 2 to 6 volts, although they are specified for 4.5 to 5.5 volts.

**Temperature**—Commercial-grade HC/HCT CMOS is more realistically rated than LSTTL, -40° C to +85° C, not the very limiting 0 to +70° C of most LSTTL 74 families.

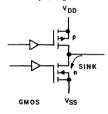
Noise Margin—HCT interfacing with HCT or with LSTTL provides improved noise margin, particularly at the high end of the operating range where outputs swing to 5 volts.

Stability—The CMOS input PMOS/NMOS pair has less switching-voltage shift with temperature variation than

LSTTL, an inherent circuit advantage compared to the LSTTL diode input design with its temperature sensitivity. This HCT advantage provides better noise margin over the device operating-temperature range and better stability of RC astable multivibrators with temperature variation when these circuits employ HCT ICs.

Output Drive Current—HC/HCT CMOS has better source current than LSTTL and sufficient sink current for LSTTL interfacing requirements. Sink current is lower than in LSTTL; this characteristic minimizes current spiking and EMI generation in RCA QMOS devices. This Note will delve into line terminations relative to sink current, the one area where differences in equipment design may exist depending on the high-speed logic family used.

Timing—The HC/HCT output-stage PMOS/NMOS transistors are designed for balance at saturation in order to provide balanced output transistion times. All logic stages employ PMOS/NMOS transistor sizing, Fig. 1, to balance propagation delays, Fig. 2.



SINK AND SOURCE = 4 mA (STANDARD) IOLSTTL LOADS CURRENT = 6 mA (BUS) 15 LSTTL LOADS

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Fig. 1 - Logic stage PMOS and NMOS transistor sizing to balance propagation delays.

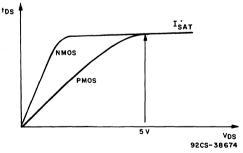


Fig. 2 - Balanced output transition time and propagation delay.

Table I - Comparison of Characteristics of HCT and LSTTL Circuits

Characteristic	QMOS CD74HCTXXXX	74LSTTLXXXX
Quiescent Power Per Gate Per Flip-Flop 4-Stage Counter Per Transceiver/Buffer	0.025 mW 0.05 mW 0.4 mW 0.1 mW	5.5 mW 10 mW 95 mW 60 mW
Operating Power  Per Gate Per Flip-Flop 4-Stage Counter Per Transceiver/Buffer	Frequency In  0.1 MHz 1 MHz 10 MHz  0.2 mW 2 mW 20 mW  0.15 mW 1.5 mW 15 mW  0.24 mW 2.4 mW 24 mW  0.25 mW 2.5 mW 25 mW	Frequency In 0.1-1 MHz 10 MHz 5.5 mW ≅20 mW 10 mW ≅15 mW 95 mW ≅120 mW 60 mW ≅90 mW
Operating Supply Voltage	(HCT) 4.5 V to 5.5 V (HC) 2 V to 6 V	4.75 V to 5.25 V
Operating Temperature Range	-40°C to +85°C	0°C to +70°C
Noise Margin LS to LS HC to HC HCT to HCT (High/Low)	1.4 V/0.9 V 2.9 V/0.47 V	0.7 V/0.4 V — —
Input Switching Voltage Stability over Temp.	$V_{S}\pm 60\;mV$	$V_{\text{S}} \pm 200 \; \text{mV}$
Output Drive Current Source Current at V _{OH} =2.4 V Sink Current Std. Logic V _{OL} =0.4 V Bus Logic V _{OL} =0.5 V	-8 mA 4 mA 6 mA 12 mA	-400 μA 4 mA 12 mA 24 mA
Output Transition Time*  TTLH TTHL  Typical Gate Propagation Delay:*  tpht/tplH Vcc=5 V, CL=15 pF	6 ns 6 ns 8 ns/8 ns	15 ns 6 ns 8 ns/11 ns
Typical Flip-Flop Propagation Delay: V _{CC} =5 V, C _L =15 pF t _{PLH} t _{PHL}	14 ns 14 ns	15 ns 22 ns
Typical Clock Rate of a Flip-Flop	50 MHz	33 MHz
Input Current I _{IL} I _{IH}	-1 μA 1 μA	-0.4 to -0.8 mA 40 μA
3-State Output Leakage Current	±5 <i>μ</i> Α	±20 μA
Reliability %/1000 Hours at 60% Confidence	0.0019 (RCA Report)	0.008 (RADC Report)

^{*}Temperature Coefficient = 0.04 ns/pF for both QMOS and LSTTL.

Frequency—QMOS clock rates are often higher than LSTTL clock rates.

Irrput Current—A big difference between the two technologies is the relatively large continuous dc current that flows in LSTTL interconnect wiring. Essentially no dc input current flows in HC/HCT CMOS. Typically, a few picoamperes of input back-diode current flows. This HCT advantage means better buffering and a wider frequency range in RC oscillators.

Leakage Current—Bus designs are enhanced by a four-times-lower high-Z output leakage current in HC/HCT CMOS as compared to LSTTL. For low-power designs, larger values of terminating resistors can be used.

Reliability—Reliability at 85°C junction temperature is four times improved with HC/HCT CMOS ICs. In fact, since the higher internal IC dissipation of LSTTL raises junction temperature an average of 10°C per IC, reliability improvement is even greater than the four-times improvement indicated.

#### INPUT/BUS/TRANSMISSION-LINE TERMINATION

Termination at inputs and outputs may be different for HCT and LSTTL devices. It is good design practice to properly terminate all unused LSTTL inputs. HCT devices can then be substituted directly, provided the unused input is returned to V_{CC}, ground or through a 1.2 kilohm or higher pull-up resistor. Output terminations are handled differently.

A discussion of termination follows. It is primarily in I/O terminations that differences in circuit design could exist and, hence, require design changes when HCT is substituted for LSTTL.

#### INPUT TERMINATION

The termination of unused inputs in LSTTL is not absolutely necessary because of the internal pull-up of 1.2 kilohms: however, it is good design practice to terminate all unused inputs to prevent linear operation of input circuitry. Such operation causes the circuitry to draw more power than it would under normal operation. The typical resistor values used for pull-up in termination of LSTTL are between 220 ohms and 1.2 kilohms; typical pull-down values are between 680 ohms and 1 kilohm. Unlike the case with LSTTL devices, unused HCT inputs must be terminated since the input is a very high impedance and, if left open, could cause the input circuitry to float into a linear mode of operation. thus drawing excessive current or causing oscillation. HCT devices must be terminated to V_{cc} or ground or with a pull-up or pull-down resistor with a value of 1 kilohm to 1 megohm, as shown in Fig. 3. The large-value resistors reduce the power dissipation of the driving devices.

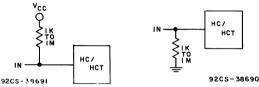


Fig. 3 - Methods of terminating HC I devices: (a) pull-up, (b) pull-down.

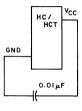
If an HCT cavice is to be used in a plug-in card system, all of the inputs from the card to the system **must** be terminated with pull-up resistance of a minimum value of 10 kilohms. In equipment designs using HC or HCT CMOS devices, where the inputs may be terminated to  $V_{\text{CC}}$ , there is an inherent current when  $V_{\text{CC}}$  is momentarily at ground.

One of the major uses of LSTTL is in computer and microprocessor-based systems. Parts such as bus drivers, transceivers, octal latches, and line drivers are widely used. All of these parts have three-state outputs. Three-state outputs allow a large number of circuits to connect to the same data bus by creating an open circuit on the device's output when it is not being accessed or utilized. The buses are usually terminated by a pull-up or a pull-down resistor. This resistance is necessary to prevent noise from being picked up on the bus. For LSTTL, the value of the pull-up resistor ranges from 330 ohms to a maximum of 100 kilohms. The choice of a pull-up or pull-down resistor will depend on whether a high or low state is required on the bus during the high-impedance state.

Termination resistors are usually placed at the most distant point from the bus-driving device. Multiple termination can be used, but these terminations must be individually high enough in resistance value so that the parallel resistive load on the bus driver is not too low; this load should be approximately 100 ohms minimum theveninized R for LSTTL bus drivers.

The typical values of pull-up for HCT bus drivers range from a minimum of 750 ohms to a maximum of 1 megohm. The choice of the resistor value involves a tradeoff between power and bus speed. A larger value of resistance will save power but will slow down the bus; a smaller value of resistance will speed up the bus, but will waste power. Typical values of pull-down resistance range from 680 ohms to 1 kilohm. A bus termination is a must for HC/HCT devices if the bus is to be in the high-impedance state for more than 100 microseconds. However, it is usually a good idea to terminate the three-state bus in case the system stops momentarily in the high-Z state or there is noise due to crosstalk in the system.

In any bus-driving configuration, all ICs must be by-passed with ceramic by-pass capacitors of at least 0.01 microfarad, as shown in Fig. 4. The capacitor is placed as close as



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Fig. 4 - IC by-passing arrangement in a bus-driving configuration

possible to the ground pin to minimize inductance and, hence, ringing in the ground of the IC. Where HC/HCT is driving a terminated line and some slight ringing into ground exists, and this ringing or noise is above or near the input switching voltage of 1.3 volts, the receiving IC should be an HC CMOS type, which has an input switching point of approximately 2.3 volts (1 volt more than LSTTL or HCT).

In some critical applications where almost no noise can be tolerated, the board or card can be bypassed with a 10-ohm or lower value resistor of the proper power rating in series with the supply line, and a 33 microfarad or larger capacitor across the supply, as shown in Fig. 5. This RC combination is placed at the point where the power supply comes into the board or card.

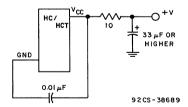


Fig. 5 - By-passing the board or card in a critical operation where almost no noise can be tolerated.

#### **DRIVING TRANSMISSION LINES**

Another type of termination required is that for transmission lines. This type of termination is used where data must travel over long distances in a system, in a large backplane, over coaxial cable, or in twisted-pair lines. This termination creates a low impedance that prevents noise and crosstalk from generating false data. Typical LSTTL systems use

nominal 100-ohm twisted-pair, strip-line, or coaxial transmission-line impedances. This low impedance is necessary to the transmission of signals at high speeds without data degradation due to line capacitance or inductance. Fig. 6 shows a common LSTTL type of transmission-line termination. In order to drive this 120-ohm load, the LSTTL output sink current is required to be at least 24 milliamperes at a  $V_{0L}$  of 0.5 volt.

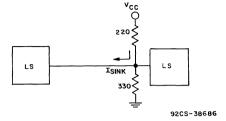


Fig. 6 - Common LSTTL transmission-line termination.

There are two powerful arguments for not duplicating this same 24 mA/0.5 V output specification in a well-designed HC or HCT bus-driver output stage:

- 0.25 watt per output, 2 watts per octal driver, is highpower design, not moderate or low-power equipment design.
- 2. A CMOS output sink current of 24 milliamperes at 0.5 volt will give rise to an objectionably high transient current when switching, and will produce EMI which is objectionably large, much larger than the LSTTL output with the same current/voltage level. Fig. 7 shows the much higher lant in an NMOS output sink transistor versus an n-p-n output sink transistor. last is twice as large, as are dv/dt and EMI, in CMOS as in LSTTL devices.

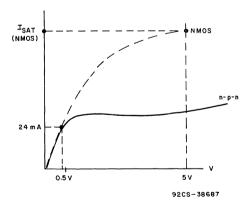


Fig. 7 - Comparison of I_{sat} in an n-p-n transistor and an NMOS transistor.

The RCA QMOS-device output stage is designed to provide typically more than 12 milliamperes at 0.5 volt. The QMOS  $l_{\text{sat}}$  is, then, similar to the LSTTL  $l_{\text{sat}}$ . The all-important noise-generation factor (EMI) is also similar at this current/voltage level.

The lowest impedance that an HCT/HC device can drive in the ac/dc termination described above is approximately 700 ohms, as shown in Fig. 8. This impedance is created with a

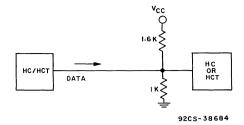


Fig. 8 - Lowest-impedance arrangement in transmission-line termination.

1.6 kilohm pull-up and 1 kilohm pull-down resistor, a combination that retains the 1/3 pull-down to 2/3 pull-up terminating-resistance design criteria. The terminators should be placed as close as possible to the receiving circuit. Higher values of transmission-line impedance can be used to save power, but the advisability of this choice will be determined by the speed of the data on the transmission line and the distance the data must travel.

More than one termination of the type described can be used on the same line if required because of long line length or a very noisy environment; but the designer must remember that the worst-case sinking limit is still 12 milliamperes at 0.5 volt, and should treat these terminating impedances as being in parallel and limited to 700 ohms, as shown in Fig. 9.

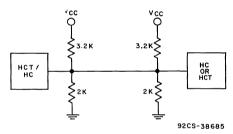


Fig. 9 - Multiple terminations on the same transmission line.

The above termination is useful for both dc and ac transmission-line terminations. With HC/HCT devices, a dc termination is not necessary, but an ac termination is a must. If the designer must have a transmission-line termination in an HC/HCT system, or must intermix families, then a variation on the voltage-divider termination can be used, as shown in Fig. 10.

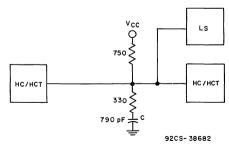


Fig. 10 - Transmission-line termination in HCT system or when families are intermixed.

Capacitor C is used to create a low impedance during switching. HC/HCT outputs can deliver up to 70 milliamperes during switching on bus types and up to 50 milliamperes on standard types. The value of C depends on the maximum frequency, f, of the bus. This value can be determined by the formula:

$$C = \frac{1}{2\pi f X_C} \tag{1}$$

where Xc is approximately 50 ohms.

A typical value for C when  $f_{max}$  is 4 MHz or greater is 790 picofarads. When there is no switching, the only dc current present comes from the pull-up resistor. This configuration not only saves power but allows HC/HCT to drive a modified low-impedance transmission line. The configuration in Fig. 11 pulls the bus into the high state when it is in the high-impedance mode. If a low state is required on the

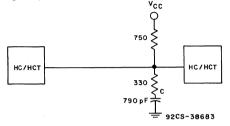


Fig. 11 - Configuration used to pull the bus into the high state when it is in the high-impedance mode.

bus, the configuration in Fig. 12 can be used. If more than one of these terminations are required on the same line, the designer must treat the terminations as being in parallel, and should adjust the values of R and C to comply with the maximum dc sink current of 12 milliamperes at 0.5 volt, as shown in Fig. 13.

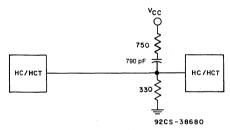


Fig. 12 - Configuration used to pull the bus into the low state when it is in the high-impedance mode.

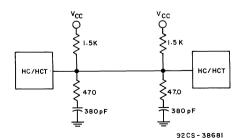


Fig. 13 - When more than one of the terminations of Figs. 11 and 12 are needed, the terminations are adjusted and treated as if they are in parallel.

#### **DRIVING COAXIAL CABLE**

LSTTL ICs can drive transmission lines using coaxial cable. Various types of coaxial and triaxial cable are available, but the most commonly used is the 75-ohm RG-59/59U, which has an impedance of 75 ohms at its nominal operating frequency. LSTTL bus drivers can directly drive almost all of the popular terminations used with coaxial-cable drive. One of the most commonly used is shown in Fig. 14. An

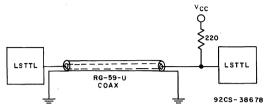


Fig. 14 - A commonly used LSTTL coaxial-cable termination.

HC/HCT device cannot drive any of these terminations without exceeding its maximum sink current. However, HC/HCT devices can drive coaxial cable by using the modified transmission-line termination shown in Fig. 15 or a modified resistor terminator, as shown in Fig. 16. The coaxial cable should be terminated at both ends in cable runs over 50 feet, again keeping in mind the maximum limits of HC/HCT sink current. Equation 1 can be used, with the addition of the figure for the capacitance of the coaxial cable, per foot, to calculate the correct value of capacitance C in Fig. 17.

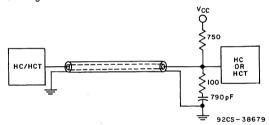


Fig. 15 - Modified transmission-line termination used with HCT devices driving coaxial lines.

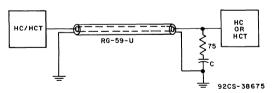


Fig. 16 - Modified resistor termination used with HCT devices to drive coaxial lines.

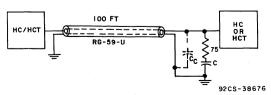


Fig. 17 - Effect of cable capacitance on termination.

By using a modified transmission-line termination for HC/HCT devices, and depending on the maximum frequency to be driven, coaxial cables of various lengths can be CMOS driven. A typical example is shown in Fig. 18, where an HC/HCT device drives more than 50 feet of RG-59U coaxial cable with a modified termination of 75 ohms. A series capacitor in the resistor leg that goes to +Vcc is placed at the receiver end of the cable to eliminate degradation which could cause false data to be received.

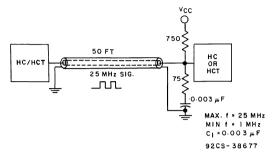


Fig. 18 - Termination configuration used to eliminate possibility of false data at receiver.

#### **DRIVING RIBBON CABLE**

When using HC/HCT ICs to drive signals over ribbon cable, there are length limitations resulting from the high impedance of the CMOS input. The drive limit is two feet maximum at normal data rates when driving without any termination and without the use of an alternate ground scheme (alternating signal carrying and grounded wires, as shown in Fig. 19) in the ribbon cable. Beyond two feet, crosstalk between signal lines can cause errors in data. If the receiving IC is an HC type, the maximum drive lengths can double.

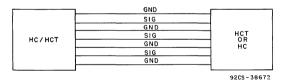


Fig. 19 - Alternate ground arrangement of ribbon cable.

When driving with no termination but with the alternate ground method, the maximum drive length before crosstalk between signal lines can cause errors in data is six feet at normal data rates.

HC/HCT devices can drive longer ribbon cable by using various terminations: pull-up, pull-down, or one of the modified transmission-line terminations. When using a 1-kilohm pull-up resistor per wire as a termination, the maximum length without alternate ground before crosstalk can become a problem is four feet at normal data rates. When using the same setup with an alternate ground scheme, as shown in Fig. 20, the maximum length of drive is

seven feet at normal data rates. The maximum drive limit is six feet, as shown in Fig. 21, when a modified transmission-line termination with an impedance of approximately 100 ohms and no alternate ground scheme is used at normal data rates. More than 15 feet can be driven at a data rate of 10 MHz when the alternate ground scheme is employed along with the termination of Fig. 21. The length can be extended by using any of the above terminations at both the receiving and transmitting ends of the cable.

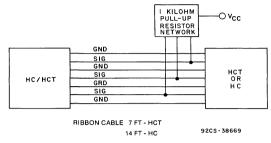


Fig. 20 - Ribbon-cable termination using 1-kilohm pull-up resistor and alternate ground arrangement.

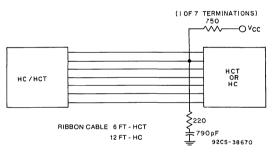


Fig. 21 - HCT ribbon-cable termination for normal data rates using impedance of approximately 100 ohms and no alternate ground system.

There are many other types of transmission-line terminations, but those shown above are the most commonly used with HCT/HC devices. When contemplating terminations of any sort, the designer must remember that HCT/HC devices have a current-sinking limit at 0.4 volt of 6 milliamperes, and at 0.5 volt of 12 milliamperes. These limits **must** be observed. By following the termination criteria described above, system power consumption is reduced, reliability is greatly improved, and system cost is decreased.

#### REFERENCES

 For a full discussion of HC/HCT power consumption and how to calculate it, see RCA Solid State Publication ICAN-7315, "Power Consumption in QMOS Logic Circuits," by R. Funk.

## Astable Multivibrator Design Using High-Speed QMOS ICs

by L. Marechal

This Note describes the design of astable multivibrators using RCA high-speed-CMOS (QMOS) integrated circuits (CD54/74 HC, HCU, HCT04 and 132), and multivibrator performance at frequencies up to 10 MHz.¹ Algebraic equations permit the values of R and C for a given oscillator frequency to be quickly determined. The effect of supply voltage and temperature variation on multivibrator performance is discussed along with the inherently low power consumption of QMOS relative to LSTTL. In addition to much lower power dissipation than other technologies, a distinct advantage of QMOS RC multivibrator design is the choice of a very wide range of  $R_{\rm x}C_{\rm x}$ , which leads to an exceptional frequency range.

#### **OPERATING FREQUENCY**

Fig. 1(a) shows the basic multivibrator circuit configuration. Resistor R and capacitor C fix the operating frequency.  $R_s$  assures that frequency will be independent of minor supply-voltage variations, and reduces the time-period variations to less than 5% with variations in transfer voltage. Fig. 1(b) shows the operating waveforms of the circuit.

Equation (1) determines the time-period T:

$$T = -RC \ln \frac{V_{TR} (V_{CC} - V_{TR})}{(V_{CC} + V_D)^2} - \frac{K}{K+1} RC \ln \frac{K(V_{CC} + V_D)}{K(V_{CC} + V_{TR}) + V_{TR} - V_D}$$
$$- \frac{K}{K+1} RC \ln \frac{K(V_{CC} / V_D)}{K(2V_{CC} - V_{TR}) - V_{TR} - V_D}$$
(1)

where  $V_{CC}$  is the supply voltage,  $V_{TR}$  is the transfer voltage,  $V_D$  is the diode forward voltage drop, and K is  $R_S/R$ .

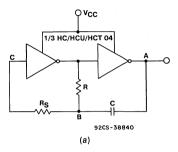
High-speed CMOS devices have a built-in 100 to 150-ohm input resistor which has little influence on speed because C charges and discharges through R and the IC output.

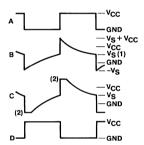
As K approaches infinity, the variation in time period as a function of  $V_{\rm CC}$  approaches zero. Variation in period with transfer voltage is reduced by 10% for K=0 and by 5% for large values of K.

Figs. 2(a) and 2(b) are plots of the theoretical time periods, as calculated from equation (1), for HC and HCT devices, respectively. In all calculations  $V_D$  = 0.6 V. Equation (1) can be simplified for large values of K to the form shown in equation (2):

T = -RC In 
$$\left(\frac{V_{TR}}{V_{CC}+V_{TR}} + In \frac{V_{CC}-V_{TR}}{2V_{CC}-V_{TR}}\right)$$
 (2)

where  $K \ge 10$ .







2. SMALL CLAMPING ACTION OF INPUT DIODES: NEGLIGIBLE FOR LARGE RS; SIGNIFICANT FOR SMALL RS 92CS-38839

(b)

Fig. 1 - (a) Astable multivibrator using the CD54/74 HC/HCU/ HCT04, (b) waveforms for the circuit of (a).

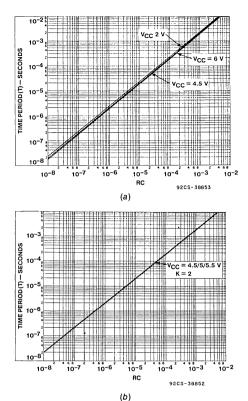


Fig. 2 - Time period (T) as a function of RC using equation (1) for (a) HC04 type and (b) HCT04 type.

Using the HC04 type, equation (2) can be simplified if the valid assumption that  $V_{TR}$  = 0.5  $V_{CC}$  is made. Then:

$$T = 2.2 RC \tag{3}$$

Fig. 3 illustrates how little the choice of either equation (1) or (3) affects results in a practical case.

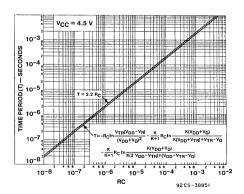
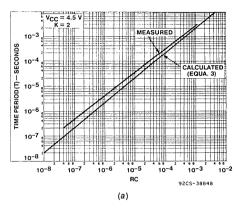
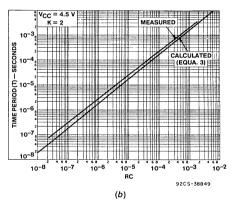


Fig. 3 - Time period as a function of RC using theoretical approach of equation (1) versus equation (3) for type HC04.

Figs. 4(a) through 4(c) show plots of measurements and calculated values of the time-period as a function of the time constant, RC, for the three series HC, HCU, and HCT, respectively. The simplified equation, (3), was used in each case. Note that the plot for the HCT04 (Fig. 4(c)) shows good tracking of calculated values (using equation (3)) with measured values, even though  $V_{\text{TR}}{=}0.31\,V_{\text{CC}}$  instead of 0.5  $V_{\text{CC}}$ .





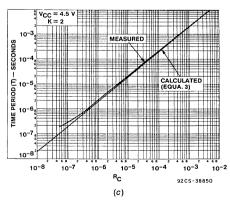


Fig. 4 - Measured versus calculated T as a function of RC for (a) HC04 type, (b) HCU04 type, and (c) HCT04 type.

Fig. 5 identifies the area of validity of R and C for equations (1) and (3). Measurements were made with the time constant as a parameter. The points on the chart are ratios of measured to calculated time period. The design guidelines used to keep the ratio of measured T to calculated T close to one, as shown in Fig. 5, follow.

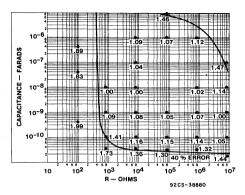


Fig. 5 - Area of theoretical equation validity. Points are ratios of measured to calculated T.

 $R_{\rm S}$  in Fig. 1 must not be made too large, as the multivibrator time constant and phase shift is influenced by this resistance (as well as by stray wiring and breadboard capacitance). A large value of  $R_{\rm S}$  will change the time period and cause spurious oscillations and glitches.

In the oscillator circuit, C should be greater than or equal to 100 pF to eliminate probe and stray capacitance interference. R should be greater than or equal to 100 ohms to support the function of R_s. However, to avoid parasitic oscillation, R must not be made too large. Appropriate values of R and C depend upon circuit design and layout.

Equation (3) is valid for R  $\geq$  50 kilohms and C  $\geq$  1000 pF; use equation (1) for R < 50 kilohms, and C < 1000 pF. However, note that, as implied above, if C is less than 1000 pF, stray capacitance will affect the entire system.

CMOS multivibrator designs have long been known to be temperature insensitive. The variation of the input switching voltage (Vs) with temperature in a QMOS device is only  $\pm 60$  mV over a range of  $-55^{\circ}$ C to  $+125^{\circ}$ C; in contrast, the LSTTL Vs varies  $\pm 200$  mV over the same temperature range. Figs. 6(a) and 6(b) reflect the minor change in period T, less than 3% for HC and 10% for HCU devices over a 150°C temperature range, resulting from the small variation in QMOS Vs.

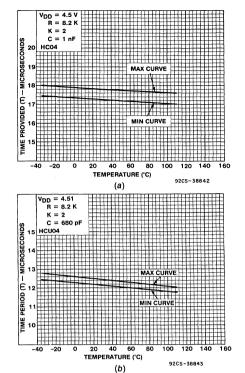


Fig. 6 - Time period as a function of temperature for (a) HC04 type and (b) HCU04 type.

#### **POWER CONSUMPTION**

One of the major advantages of the CMOS technology and, hence, QMOS ICs, is the low power dissipation. The power consumed by the RC oscillator of Fig. 7, using the HCT04 is:

$$P_D = P_A + P_B \tag{4}$$

where

$$P_A \text{ and } P_B = (C_{PD} + C/2)V^2f$$
 (5)

 $C_{PD}$  is a capacitive value used to represent internal inverter power consumption.  $C_{PD}$  is rated at 36 pF on the HC/HCT04 Data Sheet. The C in equation (5) is the RC oscillator capacitance seen as a load that is shared by inverters A and B of Fig. 7.

Table I contains parameters, data, and calculations for five operating frequencies. Fig. 8 shows plots of the measured

Table I - Measured VS Calculated RC-Oscillator Power Dissipation (V_{CC}=5.5 V)

RC	R	C	т	T/C	f	l meas'rd	V _I P meas'rd	(72 pF + C)V ² 2.2 RC P calculated	2.2 RC T	2.2 R T/C
	(ohms)	(F)		(s/F)		(mA)	(mW)	(mW)	(ms)	(s/F)
4.7 10 ⁻⁸	470	10 ⁻¹⁰	166 ns	1.66 10 ³	6.024 MHz	11.066	60.863	50.32	0.1034 <i>μ</i> s	1.034 10 ³
4.7 10 ⁻⁷	4700	10 ⁻¹⁰	1.4 μs	1.40 10 ⁴	714 kHz	2.998	16.489	5.032	1.034 <i>μ</i> s	1.034 10⁴
4.7 10 ⁻⁵	47,000	10 ⁻⁹	116 μs	1.16 10 ⁵	8.62 kHz	0.9082	4.995	0.2946	0.1034	1.034 10 ⁵
4.7 10 ⁻³	47,000	10 ⁻⁷	12.6 ms	1.26 10 ⁵	79.36 Hz	0.644	3.542	0.2926	10.34	1.034 10 ⁵
4.7 10 ⁻²	22,100	$2.2 \ 10^{-6}$	12.4 ms	1.24 10⁴	80.64 Hz	0.707	3.888	0.622	106.964	4.362 10⁴

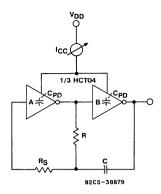


Fig. 7 - RC oscillator circuit.

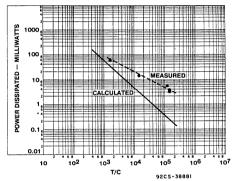


Fig. 8 - Power dissipation in oscillator (using an HCT04) as a function of T/C ratio ( $V_{CC} = 5.5 V$ ).

versus calculated power. Table I and Fig. 8 illustrate two key points concerning RC oscillator power:

- 1. Power is heavily dependent on the value of C.
- Calculations are valid only at higher frequencies, generally above 1 MHz.

Because of the dependence of power on both the frequency and value of C, power is plotted (Fig. 8) as a function of the T/C ratio. Fig. 9 illustrates a common method of reducing QMOS RC-oscillator power consumption. In the circuit, small-valued, current-limiting resistors, R, are placed in series with the circuit dc supply voltage, V_{CC}, and with the ground terminals. This arrangement reduces the CMOS flowthrough current during slow switching transitions, when both the PMOS and NMOS transistors conduct transient current from V_{CC} to ground.

In addition to reducing power consumption, resistor R, also decreases the RC operating frequency. The power reduction is more pronounced with HCU devices, for which the spiking-current component is larger. In these devices, the switch from the low level to the high level and vice versa begins at an input-switching voltage lower in the groundto-Vcc range than in other QMOS types. HC devices do not see a significant reduction in power unless the operating frequency is very high. There is a 20% power reduction at 6 MHz with a 50-ohm Rr, while there is no improvement at all at 10 kHz with the same resistance. In the case of HCU devices, the power benefit from the introduction of the 50-ohm R_r is 60% at 5 MHz, but only 20% at 10 kHz for a V_{cc} of 4.5 V. At low frequency in any QMOS device, the spiking current losses become negligible compared to the power dissipated in the external components.

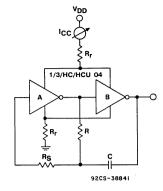
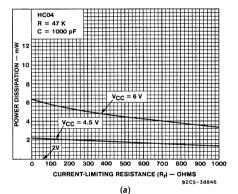


Fig. 9 - Common method of reducing QMOS RC-oscillator power consumption.

The effect of resistor R, in Fig. 9 is to decrease the output charging current of CMOS inverter (B) into capacitor C, hence the increased charging time of C. The impact of R, on frequency when large values of resistor R are used is minimal; there is a 2% frequency decrease for HC and a 2.5% decrease for HCU when R is 47 kilohms, C is 1000 pF, and R, is 1 kilohm. Figs. 10(a) and 10(b) plot power consumption against the value of R, for the HC04 and HCU04 types, respectively.



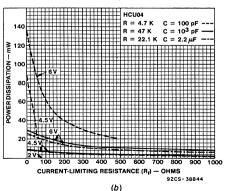


Fig. 10 - Power dissipation in an oscillator as a function of R. In (a) the oscillator employs an HC04, in (b) an HCU04.

#### RC OSCILLATOR USING THE HC/HCT132 SCHMITT TRIGGER

The RCA HC/HCT132 can be used in an astable multivibrator, as shown in Fig. 11. The equation used to calculate the period T is:

$$T = RC \ln \frac{V_{CC} - V_N}{V_{CC} - V_P} + RC \ln \frac{V_P}{V_N}$$
 (7)

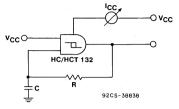


Fig. 11 - The HC/HCT132 in an astable multivibrator circuit.

Fig. 12 plots measured T versus RC for the HC132. Also plotted in Fig. 12 are calculated values of T versus RC using equation (7). Fig. 13 is a plot of measured T versus RC for the HCT132. Figs. 14(a) and 14(b) show measured power dissipation as a function of time-constant RC in oscillators employing the HC132 and HCT132, respectively.

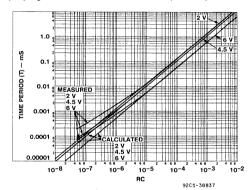


Fig. 12 - Measured and calculated time period of oscillating HC132 as a function of time constant RC.

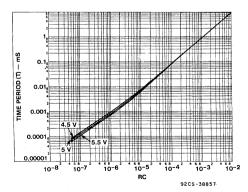
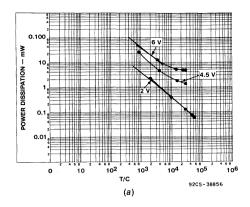


Fig. 13 - Measured time period of oscillating HCT132 as a function of time constant RC.



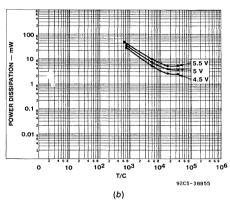


Fig. 14 - Measured power dissipated as a function of T/C, (a) in an oscillating HC132 and (b) in an HCT132.

#### REFERENCES

 For more information on CMOS circuits in oscillators and other timing applications, see:

"Astable and Monostable Oscillators Using RCA CMOS Digital Integrated Circuits," RCA Solid State Application Note ICAN-6466.

"Using the CD4047A in CMOS Timing Applications," RCA Solid State Application Note ICAN-6230.

"Simplified Design of Astable RC Oscillators Using the CD4060B or Two CMOS Inverters," RCA Solid State Application Note ICAN-6883.

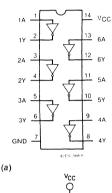
 For a discussion of C_{PD}, see QMOS High-Speed CMOS Logic ICs, RCA Solid State DATABOOK SSD-290, under "Description of QMOS product Line."

## Linear Application of the CD54/74HCU04 QMOS Hex Inverter

by W. Austin

Because the CD54/74HCU04, Unbuffered Hex Inverter, is a QMOS device based on a 3-micron process, it is an excellent high-speed digital switch. Its linear characteristics feature low capacitance and high current drive. A high transconductance associated with the high current drive is contributed by pairs of complementary NMOS and PMOS transistors, which form relatively simple inverting amplifiers. There are six of these transistor-pair amplifiers in the HCU04; each has a common Vcc and ground. A variety of application circuits are included in this Note to illustrate the many uses of the HCU04 amplifier.

The equivalent circuits shown and the characteristics be described in this Note will help the user to apply the HCU04 in linear applications (a knowledge of linear-feedback circuit theory is assumed). Fig. 1 shows the internal functional diagram and the circuit schematic of each inverter.



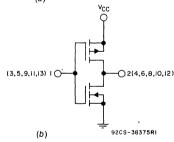


Fig. 1 - The HCU04 Hex Inverter: (a) functional diagram, (b) internal schematic.

#### PMOS AND NMOS DEVICE CHARACTERISTICS

As mentioned above, each pair of PMOS and NMOS devices in the HCU04 make a relatively simple inverting amplifier; one feedback resistor provides static bias. The amplifier transfer characteristic of each unbuffered inverter has a dynamic range of up to three volts, peak-to-peak, with good linearity in the center one volt, peak-to-peak, region. The transfer characteristic of the HCU04 is shown in Fig. 2.

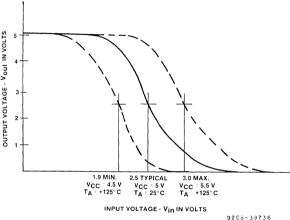


Fig. 2 - Min./max. and typical switching transfer characteristics of the HUC04 Unbuffer Hex Inverter.

The characteristics desired in any high-quality amplifier are high gain, good linearity, and wide bandwidth. The wide bandwidth of the HCU04 is inherent in the QMOS process, but its gain and linearity are a function of the transfer parameters.

The slope of the transfer curve is determined by the transition of the PMOS and NMOS devices; this slope can be evaluated with a sweep at the gate input. On a positive, increasing voltage, the p channel is pinched off near the positive V_{CC} level. The n-channel drain current is enhanced as the voltage increases from ground toward the V_{CC} level. In reverse, the p-channel current is increased with negativegoing input voltage, while the n-channel current is decreased.

Families of curves showing typical drain characteristics for both the PMOS and NMOS devices are shown in Fig. 3. The characteristics are standard for n and p enhancement-type devices. The drain currents in the p and n devices are balanced by device design: the typical n-channel width is 800 microns; the typical p-channel width is 1800 microns. This dimension compensates for the lower PMOS-channel hole mobility.

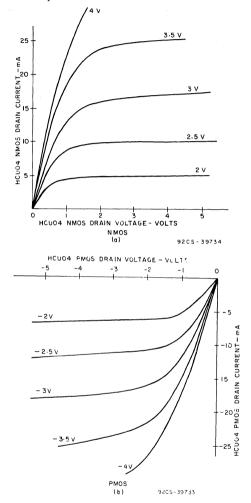


Fig. 3 - Typical drain family characteritics of the HCU04: (a) NMOS and, (b) PMOS sections.

When the inverting amplifier is in an unloaded condition, each PMOS or NMOS device is both a driver and load over some portion of the transfer curve. Since the equity of current in each device must be maintained, and since each device must act as a current sink or source, the amplifier output voltage is determined by the balance of current sink and current source bias conditions. The drain current,  $I_{\rm d}$ , in each amplifier peaks, typically, when both channels are balanced at  $V_{\rm in} = V_{\rm out} = V_{\rm Cc}/2$ . Any imbalance of drain

characteristics may cause a deviation in peak drain current, and produce a crossover offset in the transfer characteristic. Typically, the offset is less than  $\pm 5\%$  of the  $V_{CC}$  range. This figure represents what is called the "offset tolerance."

#### LOADLINE CHARACTERISTICS

To better show how the HCU04 functions in its linear transitions of the input-voltage range, the PMOS and NMOS drain loadlines have been plotted, as the gate voltage,  $V_{\text{in}}$ , is stepped, at incremental points of operation; Fig. 4. The figure includes a 75-ohm loadline at  $V_{\text{cc}}/2$  = 2.5 V as a point of reference.

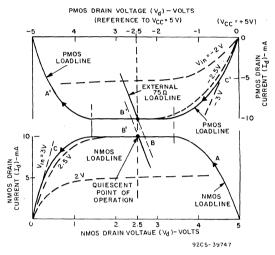


Fig. 4 - Loadline plots on the NMOS and PMOS drain-family characterstics as V_{in} is varied from zero volts to V_{in} = V_{CC} = +5 V in the HCU04.

The loadline curves defined in Fig. 4 by path ABC for the NMOS device and A'B'C' for the PMOS device are the respective loci as Vin varies from ground to Vcc = +5 V for the unloaded HCU04. An optimum external-resistance loadline of the NMOS device is normally a straight line extending with a negative slope from gate cutoff to the quiescent operating point and through to the saturated knee of the family of drain curves. A similar positive slope loadline applies to the PMOS device. Since an MOS transistor is not a linear load element, the extremes of the loadline exhibit the nonlinearity shown in Fig. 4. And because each saturated PMOS or NMOS device is a load in parallel with any external load, nonlinearity may occur at the extremes of drainvoltage swing. An output voltage range of 1.5 to 3.5 volts will provide a linear high-impedance source resistance in parallel with the external 75-ohm load.

In the NMOS loadline area, A, the loadline rises sharply from coordinates  $V_d$  = +5 V and  $I_d$  = 0 mA with a slope equal to the saturated channel resistance of the PMOS device. The +5 V and 0 mA point corresponds to the NMOS channel cutoff. Progressing on the loadline locus: as  $V_{in}$  increases, the curve rounds from A to B, where the PMOS device changes from a saturated device to an active load. As the slope of the curve flattens, a balance of maximum source and sink current is reached. The transition across the flat portion of the loadline curve will occur with a few millivolts of delta change of  $V_{in}$ , and peak  $I_{CC}$  current should occur when  $V_{in} = V_{CC}/2$ .

In the C area of the curve, the PMOS device is a high-impedance active current sink controlling the NMOS drain current, which is decreasing in value as the PMOS channel is being pinched off. A similar description of the PMOS loadline applies to the A'B'C'-curve loadline locus. The combined action of the PMOS and NMOS devices, as V_{in} varies from zero to V_{CC}, produces an active transfer curve.

Balanced PMOS and NMOS characteristics will produce a transition at B and B', where  $V_{in} = 2.5 \text{ V}$  when  $V_{cc} = 5 \text{ V}$ . Any variation in this balance will produce a crossover offset in the transfer characteristic, as described above.

The transition of the loadline characteristic for  $0 < V_{in} < V_{CC}$  produces the transfer characteristic of Fig. 5. At either end of the loadline, the effective amplifier source impedance,  $R_d$ , is low because the internal load consists of the saturated drain of the p or n device. In the center of the range, both the PMOS and NMOS devices are linear, with high effective  $R_d$ . If the  $V_{in}$  signal swings beyond the knee (or corners) of the transfer characteristic, compression of the output signal will result. Fig. 5 shows an example of a linear sinewave input and output signal.

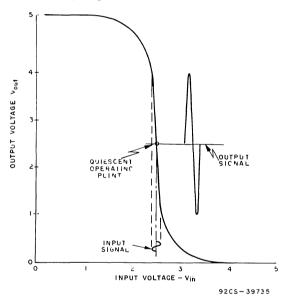


Fig. 5 - Amplifier transfer characteristics of the HCU04 amplifiers.

#### LINEAR-AMPLIFIER MODEL

A linear-amplifier model of the HCU04 includes the inverting amplifier and its associated input, output, and feedback capacitance, as shown in Fig. 6. An external feedback resistor, R₁, provides bias stability.

If the input coupling capacitor,  $C_c$ , is sufficiently large, the op-amp closed-loop gain is given by:

$$A_{fb} = \frac{A_{ol}}{1 + (1/B)(1 - A_{ol})}$$

where  $A_{\text{ol}}$  is the open-loop gain, and B =  $R_{\text{f}}/R_{\text{s}},$  the feedback resistor ratio.

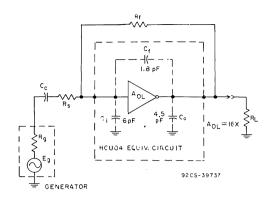


Fig. 6 - Linear model of each of the six amplifiers of the HCU04.

The normal op-amp gain equations usually assume  $A_{oi}$  to be very large, and the output impedance very small. For the circuit of Fig. 6, the gain becomes  $-(R_1/R_s)$ . This approximation will contain some error when applied to the HCU04 because the open-loop gain is typically 16, not a very small number in comparison to the open-loop gain of most op amps.

The feedback-resistor bias will stabilize amplifier operation near the center of the transfer curve; some offset is present, as noted above. The offset will reduce the dynamic range of output, but requires no correction unless dc coupling is used. The expected offset is typically less than  $\pm\,0.25$  volts.

#### **EQUIVALENT CIRCUIT**

Calculations based on an equivalent linear model may be used to predict various biasing results. A two-generator linear-circuit model is shown in Fig. 7.

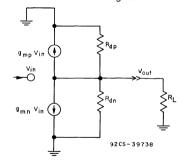


Fig. 7 - Circuit equivalent of the HCU04 with two source generators and no feedback.

Since the  $V_{out}$  node equation for the two generator equivalent circuit is:

$$-g_{mp}(V_{in})-g_{mn}(V_{in})=V_{out}(1/R_{dn}+1/R_{dp}+1/R_{L})$$
 and

$$A_{ol} = V_{out}/V_{in} = \frac{-(g_{mp} + g_{mn})}{(1/R_{dn} + 1/R_{dp} + 1/R_{L})}$$

The source-generator and parallel conductances of the NMOS and PMOS equivalent models may be simply added into one equivalent.

A single-generator model has no restrictions, provided the equivalent circuit is a reasonable linear approximation. A simplified model of the circuit of Fig. 6, with associated capacitance and biasing, is shown in Fig. 8. The single-model equivalent-current generator and effective source impedance may be determined from the separate device models, and is equal to:

$$g_{m} = g_{mp} + g_{mn}$$

$$R_{d} = R_{dp} R_{dn} / (R_{dp} + R_{dn})$$

$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

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$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

$$V_{in} R_{s}$$

Fig. 8 - Simplified HCU04 circuit model with associated capacitance and biasing.

All further references to  $g_m$  and  $R_d$  imply a single-generator model. It should be noted, however, that use of the two-generator equivalent model does have practical merit in the analysis of abnormal input-signal conditions or when considering the effects of  $V_{CC}$  and ground-terminal impedance.

Determination of the  $g_m$  and  $R_d$  parameters is based on either direct evaluation from the drain family characteristics of Fig. 3 or measured data. From the curves of Fig. 3,  $g_m$  is  $\Delta I_{d'} \Delta V_{in}$ , and  $R_d$  is the tangential  $\Delta V_d / \Delta I_d$  slope on the  $V_{in}$  bias line at the point of operation. The simplest way to determine  $g_m$  is to measure  $A \sim A_{oi}$  when  $R_r$  is very large and  $R_s$  is small, e.g., 100 kilohm and 50 ohms, respectively.

When RL is much less than Rd:

$$A \sim -g_m R_L$$
, and  $g_m \sim A/R_L$ 

The gain is then measured under the same conditions with  $R_{\text{L}}$  removed (open) and  $R_{\text{d}}$  as the effective load. For this condition,

, 
$$A \sim -g_m R_d$$
, and  $R_d \sim A/g_m$ 

A variety of amplifier gain conditions have been measured for the circuit of Fig. 9 and, in some cases, calculations have been made for  $g_m$  and  $R_d$ . A tabulation of the results is shown in Table I.

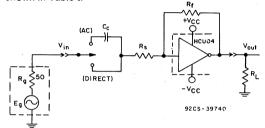


Fig. 9 - Simplified amplifier circuit configuration used to measure gain and equivalent model characteristics. Table 1 shows coults

Table I - Measured Amplifier-Gain Conditions for the Circuit of Fig. 9.

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A. Conditions:  $V_{cc} = \pm 2.5 \text{ V}$ ,  $I_{cc} \sim 6 \text{ mA}$ 

#### Measurement

Measurement No.	AC/Direct (input)	R _s (kΩ)		R _f (kΩ)	R∟ (ohms)	V _{out} /V _{in} (gain)
1 .	Direct	1		3	1000	2
2	Direct	1		3	none	2.4
3	Direct	1		3	75	0.75
4	Direct	0.5	. 4	3	75	1.0
5 ¹	AC	0.05		100	75	1.4
6 ²	AC	0.05		100	none	25

Calculated: 1.  $g_m \sim A/R_L \sim (1.4/75) = 0.0187$  mhos 2.  $R_d \sim A/g_m \sim (25/0.0187) = 1340$  ohms

.

Conditions:  $V_{cc} = \pm 3 \text{ V}$ ,  $I_{cc} \sim 10 \text{ mA}$ 

### Measurement

Measurement No.	AC/Direct (input)	$\mathbf{R_s}$ (k $\Omega$ )	R _f (kΩ)	R _L (ohms)	V _{out} /V _{in} (gain)
11	AC	1 -	100	none	16
2 ²	Direct	0.5	100	75	1.5
3	Direct	1	100	75	1.45
4	AC	3	3	none	0.86

Calculated: 1.  $R_d \sim A/g_m \sim$  (16/0.02) = 800 ohms

2.  $g_m \sim A/R_L \sim (1.5/75) = 0.02$  mhos

Operation of the HCU04 in a multiple output configuration is practical. A circuit using all six amplifiers in parallel is shown in Fig. 10. The table of gain results for a variety of conditions is shown in Table II.

#### **OPEN-LOOP GAIN**

Unlike op-amp gain, HCU04 amplifier gain is not sufficiently high or the output impedance low enough to allow simple

general approximations. However, a simplified method of determining HCU04 amplifier performance in an open-loop condition is possible, and useful, in many applications. A basic open-loop equivalent-circuit model of the HCU04 is shown in Fig. 11. This circuit is based on the equivalent-current-generator model of Fig. 8 with  $R_{\rm S}=0$ . A large value is used for the static bias resistor,  $R_{\rm f}$ , a value much larger than the input source resistance.

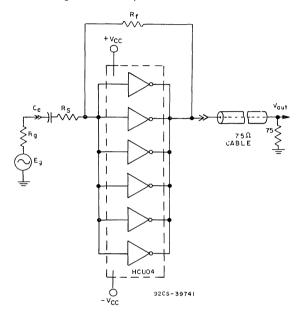


Fig. 10 - Six amplifiers of HCU04 in parallel line driver. Table II shows results.

#### Table II - Measured Results for Multiple Parallel Amplifier of Fig. 10

Conditions:  $V_{cc}$  =  $\pm 2.5$  V,  $I_{cc} \sim 32$  mA

#### Measurement

Measurement No.	R _s (kΩ)	R₁ (kΩ)	R∟ (ohms)	V _{out} /V _{in} (gain)
1	1	1	none	0.9
2 ¹	1	100	none	18
3 ²	0.05	100	75	6.0

Calculated: 1. 
$$R_d \sim (A/g_m) \sim (18/0.08)$$
 = 225 ohms   
2.  $g_m \sim A/R_L \sim (6/75)$  = 0.08 mhos

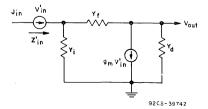


Fig. 11 - Basic equivalent circuit model for simplified gain, Z_{in} and Z_{out} calculations.

Using voltage-node equations with an assumed current drive input,  $J_{\text{in}}$ , the matrix determinant for the circuit of Fig. 11 is:

$$\Delta = \begin{vmatrix} (Y_i + Y_f) & (-Y_f) \\ (g_m - Y_f) & (Y_d + Y_f) \end{vmatrix}$$

The open-loop gain equation is:

$$A = \frac{V_{out}}{Vin'} = \frac{Y_f - g_m}{Y_d + Y_f} \sim \frac{-g_m}{Y_d + Y_f}$$

The admittance terms include frequency, f, where  $\omega$  =  $2\pi f$ . The complex terms are:

$$Y_f = (1/R_f) + j\omega C_f$$

$$Y_i = j\omega C_i$$

$$Y_d = (1/R_d) + j\omega C_o$$

For the low-frequency case, the gain is approximately:

$$A = -g_m R_d || R_f$$

where  $R_d \| R_t$  is  $R_d$  in parallel with  $R_t.$  The  $R_d$  term may be modified to include  $R_d$  in parallel with external load  $R_L.$ 

In the case where there is no external  $R_L$  and  $R_d << R_f$ , the gain solution simplifies to:

$$A \sim -g_m \, R_d$$

In the case where  $R_L << R_d$ , the gain solution simplifies to:

$$A \sim -g_m R_L$$

Both of these simplified expressions provide reasonably accurate values of  $g_m$  and  $R_d$ , and were used to obtain the values in Table I. As the table shows, when the gain (A) was measured as 16 times for the  $\pm$  3-volt  $V_{\rm CC}$  condition with no load, and 1.5 times with a 75-ohm load, the solutions were readily determined to be  $g_m$  = 0.02 mhos and  $R_d$  = 800 ohms. Lower signal levels and smaller values of  $R_L$  will contribute to better accuracy.

When the admittance term  $(Y_d + Y_f)$  of the gain equation is expanded, there is an output rolloff corner frequency,  $f_{\text{out}}$ , of:

$$f_{out} = \frac{1}{2\pi (C_f + C_{out}) |R_d| |R_f|}$$

where, again, Rd | Rt is Rd in parallel in Rt.

It is important to note that the significance of this rolloff corner will depend on the degree of feedback used and the magnitude of  $R_{\text{g}}$  or  $R_{\text{s}}$ . In the true open-loop condition, where  $R_{\text{s}}$  = 0 ohms,  $R_{\text{f}}$  is large, and  $R_{\text{g}}$  is a line or generator source of 50 or 75 ohms, the  $f_{\text{out}}$  corner frequency is the primary bandwidth-limiting factor. Where capacitance  $C_{\text{out}}$  is equal to  $(C_{\text{i}}+C_{\text{o}}),$  as in the case of cascaded HCU04 stages:

$$C_f + C_{out} = C_f + C_i + C_o = (1.8 + 6.0 + 4.5) pF = 12.3 pF$$

$$R_d \parallel R_f \sim R_d \sim 800 \text{ ohms}$$

and

#### INPUT IMPEDANCE:

The input impedance of the HCU04 may be determined by using an input driving point solution with a J_{in} current generator at the input node. The input impedance is:

$$Z_{in}' = \frac{V_{in}'}{I}$$

where:

$$V_{in'} = \frac{\begin{vmatrix} J_{in} & (Y_t) \\ 0 & (Y_d + Y_t) \end{vmatrix}}{\Delta} = \frac{J_{in} (Y_d + Y_t)}{\Delta}$$

Therefore:

$$Z_{in'}$$
  $(Y_d + Y_f)$ 

Expanding the determinant and reordering the above equation yields:

$$Z_{in}' = \frac{1}{Y_i + Y_f(1-A)} = \frac{1}{Y_{in}'}$$

The  $Z_{in}'$  equation is a statement of all input impedances in parallel at the input. It is important to note that the  $Y_f(1-A)$  is the classic Miller-effect feedback factor. Since  $Y_f(1-A)$  can be expanded to  $[(1-A)/R_f] + j\omega C_f(1-A)$ , the effective  $R_{in}$  becomes:

$$R_{in} = (1-A)/R_{f}$$

and the effective Cin becomes:

$$C_{in} = [(1-A)C_{f} + C_{i}]$$

When the signal-source input has a high impedance ( $R_0$  or  $R_9$ ), the input network configuration is equivalent to that shown in Fig. 12. The  $R_L$  network has an input corner-rolloff frequency response,  $f_{in}$ , of:

$$f_{in} = \frac{1}{2\pi(R_{in}||R_s)C_{in}}$$

where Rin | Rs is Rin in parallel with Rs.

The complete input-impedance equation for the network of Fig. 12 is:

$$Z_{in} = R_s + Z_{in}'$$

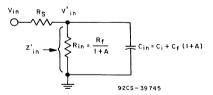


Fig. 12 - Miller-feedback equivalent input circuit of the HCU04.

#### OUTPUT IMPEDANCE

The output-impedance of the HCU04 may be calculated by using a current generator to drive the output terminal. The resulting calculation should include the correct input network termination.

In the open-loop condition, when  $R_s$  or  $R_g$  is much less than  $R_t$ , the output impedance is simply  $R_d$  in parallel with  $R_t$ . However, with  $R_s$  terminated through  $R_g$  at the input, the output impedance may be calculated for the general

feedback condition. The second-order determinant was used for the input-impedance calculation and simply adding  $R_{\text{a}}$  at the input after finding  $Z_{\text{in}}$ . The output impedance can be calculated similarly, using the second order determinant, by including the  $Y_{\text{a}}$  admittance term (or  $Y_{\text{a}}+Y_{\text{g}}$ ) in the y11 term of the matrix determinant; i.e.:

$$\Delta = \begin{vmatrix} (Y_s + Y_i + Y_t) & (-Y_t) \\ (g_m - Y_t) & (Y_t + Y_d) \end{vmatrix}$$

When the output node is driven by a current (Jo):

$$V_{out} = J_o(y11/\Delta)$$

and

$$Z_{out} = \frac{Y_s + Y_i + Y_f}{(Y_d + Y_f)[Y_s + Y_i + Y_f(1 - A)]}$$

This equation may be reduced to a simple form for low frequencies:

$$Z_{out} = \frac{R_d || R_f}{1 - A(R_s/(R_s + R_f))}$$

where Rd || Rf is Rd in parallel with Rf.

#### FEEDBACK EQUATIONS AND GAIN-BANDWIDTH-CIRCUIT MEASUREMENTS

The preceding equations will be very useful in applying the HCU04, particularly in low-frequency applications. However, it is important that the user does not over-simplify solutions and drop terms before evaluating their significance. The general purpose of this Note is to provide fully useful equations and to impress on the user that the standard op-amp equations, for the most part, do not apply well to the HCU04 amplifier.

Because some degree of feedback is desired for good linearity, the need to consider performance with feedback is necessary. An essential consideration is the wideband amplifier performance. The gain-bandwidth response and phase considerations are important, and are treated, with examples, in the following section.

The use of the equations developed above and the gain-bandwidth (GBW) capability of the HCU04 are demonstrated with the aid of Fig. 13. Shown is a single amplifier of the HCU04 in which bypassed 75-ohm resistors are used as protection from power-supply over-voltage. The small-signal equivalent circuit is similar in characteristics to the last example in Table I, except for the power-supply resistors. The  $g_{\rm m}$  and  $R_{\rm d}$  values for that example were determined to be 0.02 mhos and 800 ohms, respectively, and are the values used in the following evaluation.

As noted above, the low-frequency gain may be approximated from the op-amp feedback equation:

$$A_{fb} = \frac{A_{ol}}{1 + (R_s/R_f) (1 - A_{ol})}$$

where:

$$A_{ol} \sim -g_m R_d = -16$$

And for  $R_s = R_f = 3000$  ohms,  $A_{fb} = -0.88 = -1.11$  dB

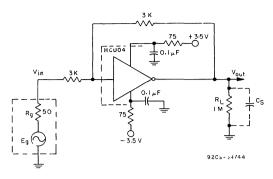


Fig. 13 - Amplifier circuit for gain-bandwidth measurements.

This value is in good agreement with the measured gainbandwidth (GBW) response curve shown in Fig. 14. In addition, as noted above, the high-frequency GBW response includes the input corner-rolloff frequency resulting from the Miller-effect RC input network of Fig. 12.

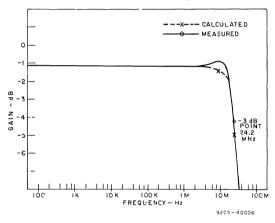


Fig. 14 - Gain-bandwidth measurement showing frequency rolloff response for the circuit of Fig. 13.

The full, high-frequency-gain equation, derived from the third-order determinant, will include both the input and output corner-rolloff frequencies. The matrix determinant is:

$$\Delta = \begin{vmatrix} (Y_a) & (-Y_s) & (0) \\ (-Y_s) & (Y_s + Y_t + Y_t) & (-Y_t) \\ (0) & (-y_t + g_m) & (Y_t + Y_d) \end{vmatrix}$$

and the gain equation is:

$$A_{tb} = \frac{-Y_{s} (g_{m} - Y_{t})}{(Y_{t} + Y_{d}) (Y_{s} + Y_{i} + Y_{t}(g_{m} + Y_{d})}$$

While this equation may be awkward to use, all of its terms are needed to evaluate stray capacity  $(C_s)$  and other loading effects in the application. Normally,  $g_m$  is much greater than  $Y_t$ , so that  $g_m$  -  $Y_t \sim g_m$ .

The gain equation then reduces to the form:

$$A_{fb} = \frac{A_x}{1 + i\omega B_x - \omega^2 C_x}$$
 (1)

Where  $A_x$  is the low-frequency gain, and the complex demoninator is the complete factor for gain and phase response versus frequency. The  $A_x$ ,  $B_x$  and  $C_x$  terms are defined as follows:

$$A_x = \frac{-g_m H_d}{(1 + R_d/R_f) + (R_s/R_f) (1 + g_m R_d)}$$

$$\begin{split} B_x &= -(A_x/g_m R_d)[(C_o + C_f) R_d + [(C_i + C_o) R_s R_d / R_f] + (C_i + C_f) R_s + \\ & g_m C_f R_s R_d] \end{split}$$

$$C_x = -(A_x/g_mR_d)[R_sR_d(C_fC_i + C_oC_i + C_oC_f)]$$

Using parameter values already defined from the circuits of Figs 6 and 13:

$$A_x = \frac{-0.02 \times 800}{(1 + 800/3000) + (3000/3000) (1 + 0.02 \times 800)} = -0.876$$

Before calculating the frequency dependent  $B_x$  and  $C_x$  terms, it is important to note the special conditions for phase shift. Equating the real term of the denominator of equation 1 to zero yields:

$$\omega^2 C_x = 1$$

The gain equation under this special condition is:

$$A_{t}b = \frac{A_{x}}{i\omega B_{x}}$$

The fact that there is only an imaginary (complex) term in the denominator is a statement of 90° phase lag, which is a defined measurement point on the phase curve of Fig. 15.

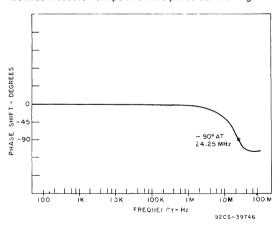


Fig. 15 - Phase measurement showing phase shift for the circuit of Fig. 13.

The capacitance output term for the 90° phase shift is:

$$C_o = \frac{-(g_m/\omega^2 A_x R_s) - C_f C_i}{(C_f + C_i)}$$

Substituting values for the 24.2 MHz point noted on Fig. 15, a phase shift of 90° yields:

$$C_0 = 40.5 pF$$

The capacitance output term C_o includes all stray capacitance plus the HCU04 equivalent output capacitance of 4.5 pF. The stray and fixturing capacitance, C_s, is:

$$C_s = (40.5 - 4.5) = 36 pF$$

To evaluate  $A_{tb}$  for this condition, the  $B_x$  and  $C_x$  values are calculated as follows (using  $g_mR_d=(0.02)(800)=16$ , and noting that C in pF times R in kilohms carriers a 10-9 multipler):

$$\begin{split} B_x &= -(A_x/g_m R_d) \; [(C_o + C_f) R_d + (C_i + C_o) (R_s/R_f) R_d + (C_i + C_f) R_s + g_m R_d C_f R_s] \end{split}$$

$$= 9.9 \times 10^{-9}$$

$$C_x = -(A_x/g_mR_d)[(R_sR_d)][(C_fC_i + C_oC_i + C_oC_f)]$$

= - 
$$(-0.876/16[(3)(0.8)][(1.8)(6.0)+(40.5)(6.0)+(40.5)(6.0)$$
  
 $(1.8)]10^{-18}$ 

$$= 42.93 \times 10^{-18}$$

Verifying that  $\omega^2 C_x = 1$ :

$$\omega^2 C_x = (2\pi f)^2 C_x = (2\pi)^2 (24.2 \times 10^6)^2 (42.93 \times 10^{-18}) \sim 1$$

Then A_{fb} at 90° is:

$$A_{fb} = A_x/j\omega B_x = (-0.876)/j(2\pi)(24.2 \times 10^6)(9.9 \times 10^{-9})$$
  
=  $(-0.876/j1.5) = -0.584 \angle -90^\circ$ 

The magnitude of the gain in dB at 90° phase lag is:

$$A_{fb} = 20 \log |0.584| = -4.67 dB$$

The actual measured results from the curve of Fig. 14 shows -4.3dB, which verifies, with practical agreement, the actual and calculated results. Using the complex  $A_{1b}$  equation to verify the gain at 10 MHz, the results of the gain calculation are -1.47 dB at -40.17° of phase lag.

The slight peaking noted at 10 MHz is not unusual in wideband circuits with feedback. In the range of 10 MHz and beyond, peaking or ripple effects are commonly present in the GBW response because of lead inductance and stray capacitance both in the signal links and in the filtering components. Care must be exercised in circuit layout and in component specification, as an excess of peaking will cause undesired overshoots and ringing on pulse edges.

Additional gain-bandwidth curves are shown in Fig. 16. Note that the high frequency rolloff is a function of load and feedback, but is typically 6-dB per octave. The bandwidth can be extended at a sacrifice of gain. Bandwidth extending may be done with loading or peaking. Both RC and RLC can be used to peak the input signal.

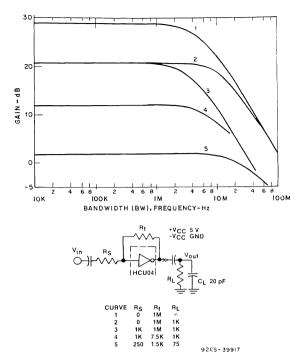


Fig. 16 - Linear-amplifier gain/bandwidth curves.

# **GENERAL APPLICATIONS OF THE 74HCU04**

The low output impedance and video-bandwidth capability of the HCU04 suggest a wide variety of applications in linear signal amplifiers. Line-driver capability may be achieved by paralleling output amplifiers and applying feedback to assure low output impedance. The HCU04 may be used for both linear and digital data transfer. Real-time feedback conditions may be modified by using transmission-gate switching with such devices as the QMOS CD74HC4016 or CD74HC4052.

#### Video Switch

An example of a video-switching video-amplifier is shown in Fig. 17. The CD74HC4052 is a QMOS dual 4-input analog multiplex switch that is used to direct one of four inputs to the HCU04 video amplifier. An LED indicator shows which channel has been selected. One amplifier of the HCU04 is used as a buffer amplifier that drives four other amplifiers in parallel. These four amplifiers, in turn, drive a 75-ohm cable and load.

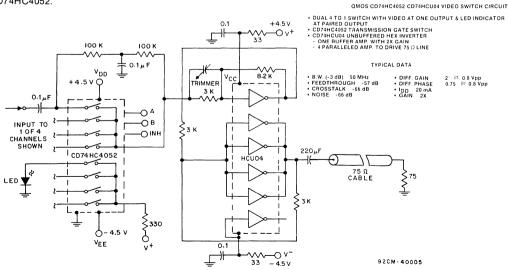


Fig. 17 - Video-switch circuit employing QMOS CD74HC4052 and HCU04.

Bandwidth peaking is accomplished in the first video amplifier by the trimmer capacitor. One amplifier remains open for use as a parallel-signal amplifier, e.g., for audio signals. However, any unused amplifier should have the input returned to  $V^+$  ( $V_{CC}$ ) or  $V^-$  (GND) to eliminate current drain. The peaking circuits provide for an exceptional 50-MHz gain-bandwidth capability at 2X gain. Other typical data is shown in the table accompanying the figure.

#### Audio/Tone Amplifier

The circuit of Fig. 18 is an audio or tone driver for highefficiency, 32-ohm speakers or a headset. Although the power output is limited by the 5-volt supply, the use of the HCU04 as a tone amplifier or beeper is practical with this type of circuit.

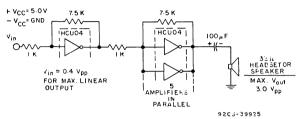


Fig. 18 - Audio/tone amplifier.

# **Other Linear Applications**

The circuits of Fig. 19(a) through 19(h) are general applications of the HCU04 in both the linear and switching modes. With 25 mA of drive capability, the HCU04 amplifier can directly drive LED indicators or provide high-current base drive for a transistor lamp, solenoid, or relay driver, as shown in Figs. 19a and 19b.

Fig. 19(c) shows a possible use of the HCU04 with photocells or thermistors in a sensor amplifier application for light or heat control.

The circuit of Fig. 19(d) shows an HCU04 driving a TTL 2-input NAND gate. This circuit is employed where a TTL interface is needed.

Fig. 19(e), the simplest form of a low-pass filter, shows a capacitor-feedback arrangement in use with the HCU04 amplifier. Additional poles may be added with additional filter stages. In the example shown, the gain is unity and the 3-dB rolloff frequency is 5 kHz.

An emitter-follower may be coupled to the output and included in the feedback loop of the HCU04 amplifier, as shown in Fig. 19(f). The use of positive and negative power-supply voltages is optional. As another option, the output may be changed to a complementary-symmetry drive. With the emitter follower shown, the base-emitter offset of 0.7 volts reduces the linear dynamic range of the output drive signal.

The circuit of Fig. 19(g) is an adjustable current sink in which the current, I_c, in the output transistor, is approximately equal to 2.5/R. Fig. 19(h) shows a more general circuit for adjusting both voltage and current.

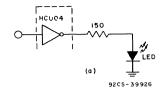


Fig. 19 - (a) LED driver.

Note: For circuits (a) through (e),  $+V_{CC} = 5 \text{ V}$ ,  $-V_{CC} = ground$ .

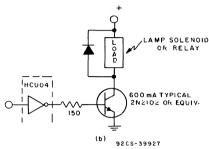


Fig. 19 - (b) Lamp, solenoid, or relay driver.

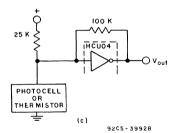


Fig. 19 - (c) Photocell or thermistor driver.

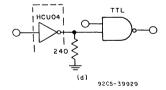


Fig. 19 - (d) TTL driver.

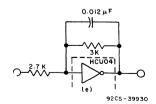


Fig. 19 - (e) Unity gain low-pass filter: 3-dB rolloff  $\sim$  5 kHz.

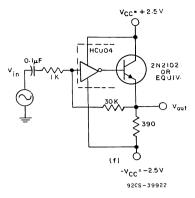


Fig. 19 - (f) Low Zout amplifier.

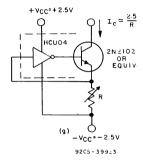


Fig. 19 - (g) Fixed-current-source driver.

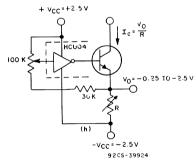


Fig. 19 - (h) Adjustable low-Z_{OUT} dc source or adjustable current sink.

# **Oscillator Applications**

The circuit of Fig. 20(a) is a 3.58 MHz clock generator that may be VCO controlled by replacing the 10 pF capacitor with a varactor.

Uniformity of balance in the HCU04 leads to better frequency-range control in applications where the frequency is crossover dependent. The circuit of Fig. 20(b) can be changed in polarity of pulse and ramp output by changing the polarity of the 1N914 diode. The result is a -2V to +2V adjustable VCO with positive ramp and pulse outputs in the low switch position. In the high position, negative ramp and pulses are generated with a 2.6 V to 7 V control voltage. In both switch positions, the frequency range is 15 kHz to 180 kHz.

The VCO circuits of Figs. 20(c) and 20(d) are simpler, higher-frequency-range circuits with oscillator capability up to 25 MHz. The circuit of Fig. 20(d) shows a method of compensating effects of power-supply frequency change by adding some of the VCO change into the VCO input. At center frequency of 5 MHz, for  $V_{in}$  = 0 V, the power-supply change is effectively cancelled for changes of  $\pm 10\%$  V_{cc}.

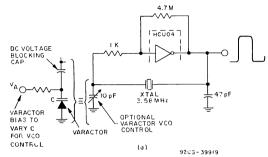
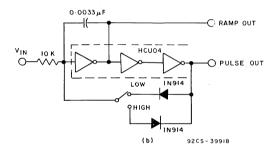


Fig. 20 - (a) 3.58-MHz clock or VCO circuit. Note: For all Fig. 20 circuits, +V_{CC} = 5 V, -V_{CC} = ground.



POSITIVE RAMP AND PULSE LOW ADJ RANGE 110 KHz AT 0 V VIN: -2 TO 2 V FREO: 180 KHz TO 15 KHz

NEGATIVE RAMP AND PULSE HIGH ADJ RANGE 100 KHz AT 5 V VIN: 2.6 V TO 7 V FREO: 15 KHz TO 180 KHz

Fig. 20 - (b) VCO pulse and ramp generator.

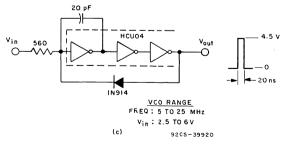


Fig. 20 - (c) High-frequency VCO pulse generator.

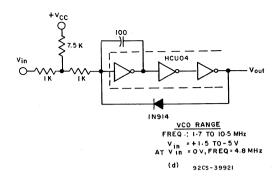


Fig. 20 - (d) Vcc -compensated VCO.

### SUMMARY

The characterization and applications of the HCU04 shown illustrate how simple, high-speed CMOS device can be more-widely used in both linear and digital circuits. Many applications require linear interface for buffer amplifiers, sensors, gain amplifiers, and multiple-line inverter circuits.

The power gain of the HCU04 is very high, although the voltage gain is typically less than 20. This feature makes the HCU04 an excellent driver for bipolar transistors driving lamps, relays, and solenoids.

#### REFERENCES

1. CD54/74HCU04, Hex Inverter Data Sheet; RCA Solid

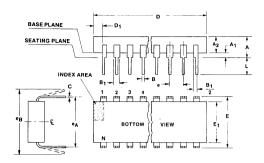
State File No. 1655. The notation CD54/74HCU04 denotes two devices, the CD54HCU04F, the Hex Inverter in a ceramic package, and the CD74HCU04E, the Hex Inverter in a plastic package. Both devices are electrically identical. The notation HCU04 used in this Note refers to either device.

#### **ACKNOWLEDGMENTS**

Substantial portions of the gain-bandwidth technical characterization and related circuits in this Note were provided by J. Nadolski; HCU04 device-parameter information was provided by B. Petryna and R. Funk.

	Dimensional	Outlines

# **Dual-In-Line Plastic Packages**



# (E) Suffix (JEDEC MS-001-AC) 14-Lead Dual-In-Line Plastic Package

SYMBOL	IN	CHES	MILLIMI	NOTES	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α		0.210	_	5.33	9
A ₁	0.015	_	0.39	_	9
A ₂	0.115	0.195	2.93	4.95	
В	0.014	0.022	0.356	0.558	
В ₁	0.045	0.070	1.15	1.77	3
С	0.008	0.015	0.204	0.381	
D	0.725	0.795	18.42	20.19	4
D ₁	0.005	_	0.13	_	12
E	0.300	0.325	7.62	8.25	5
E ₁	0.240	0.280	6.10	7.11	6, 7
e	0.10	00 BSC	2.54 E	BSC	8
e _A	0.30	00 BSC	7.62	BSC	9
e _B	_	0.430	_	10.92	10
L	0.115	0.160	2.93	4.06	9
N		14	14	ļ	11

92CS-39901

#### Notes:

- Refer to JEDEC Publication No. 95 JEDEC Registered and Standard Outlines for Solid State Products, for rules and general Information concerning registered and standard outlines. In Section 2.2.
- Protrusions (flash) on the base plane surface shall not exceed 0.010 in. (0.25 mm).
- 3. The dimension shown is for full leads. "Half" leads are optional at lead positions

1, N, 
$$\frac{N}{2}$$
  $\frac{N}{2}$  +1.

- Dimension D does not include mold flash or protrusions.
   Mold flash or protrusions shall not exceed 0.010 in. (0.25 mm).
- E is the dimension to the outside of the leads and is measured with the leads perpendicular to the base plane (zero lead spread).
- 6. Dimension E₁ does not include mold flash or protrusions.
- Package body and leads shall be symmetrical around center line shown in end view.
- Lead spacing e shall be non-cumulative and shall be measured at the lead tip. This measurement shall be made before insertion into gauges, boards or sockets.
- This is a basic installed dimension. Measurement shall be made with the device installed in the seating plane gauge (JEDEC Outline No. GS-3, seating plane gauge). Leads shall be in true position within 0.010 in. (0.25 mm) diameter for dimension eg.
- e_B is the dimension to the outside of the leads and is measured at the lead tips before the device is installed.
   Negative lead spread is not permitted.
- 11. N is the maximum number of lead positions.
- Dimension D₁ at the left end of the package must equal dimension D₁ at the right end of the package within 0.030 in. (0.76 mm).
- 13. Pointed or rounded lead tips are preferred to ease insertion.
- 14. For automatic insertion, any raised irregularity on the top surface (step, mesa, etc.) shall be symmetrical about the lateral and longitudinal package centerlines.

# (E) Suffix (JEDEC MS-001-AA) 16-Lead Dual-In-Line Plastic Package

SYMBOL	IN	CHES	MILLIME	ETERS	NOTES
STMIBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	1	0.210	_	5.33	9
A ₁	0.015	_	0.39	_	9
A ₂	0.115	0.195	2.93	4.95	
В	0.014	0.022	0.356	0.558	
B ₁	0.045	0.070	1.15	1.77	3
c	0.008	0.015	0.204	0.381	
D	0.745	0.840	18.93	21.33	4
D ₁	0.005	_	0.13	–	12
E	0.300	0.325	7.62	8.25	5
E ₁	0.240	0.280	6.10	7.11	6, 7
e	0.10	00 BSC	2.54 1	BSC	, 8
e _A	0.30	00 BSC	7.62 1	BSC	9
eв	_	0.430	-	10.92	10
L	0.115	0.160	2.93	4.06	9
N		16	10	5	11

# (E) Suffix (JEDEC MS-001-AE) 20-Lead Dual-In-Line Plastic Package

	IN	CHES	MILLIMETERS		NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	-	0.210	_	5.33	9
A ₁	0.015	_	0.39	_	9
A ₂	0.115	0.195	2.93	4.95	
В	0.014	0.022	0.356	0.558	
B ₁	0.045	0.070	1.15	1.77	3
c :	0.008	0.015	0.204	0.381	
D	0.925	1.060	23.5	26.9	4
D ₁	0.005	_	0.13	_	12
E	0.300	0.325	7.62	8.25	5
E ₁	0.240	0.280	6.10	7.11	6, 7
e	0.10	0 BSC	2.54 1	BSC	8
e _A	0.30	0 BSC	7.62 1	BSC	9
eв	_	0.430	_	10.92	10
L	0.115	0.160	2.93	4.06	9
N	<u></u>	20	20	)	

92CS-39900

92CS-39997

# 

# (EN) Suffix (JEDEC MS-001-AF) 24-Lead Dual-In-Line Plastic Package

DV44DQ1	IN	CHES	MILLIMETERS		NOTES
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	_	0.210	_	5.33	9
A ₁	0.015	_	0.39	_	9
A ₂	0.115	0.195	2.93	4.95	
В	0.014	0.022	0.356	0.558	
B ₁	0.045	0.070	1.15	1.77	3
С	0.008	0.015	0.204	0.381	
D	1.125	1.275	28.6	32.3	4
D ₁	0.005	_	0.13	_	12
E	0.300	0.325	7.62	8.25	5
E ₁	0.240	0.280	6.10	7.11	6, 7
e	0.10	00 BSC	2.54 [	BSC	8
e _A	0.30	00 BSC	7.62	BSC	9
e _B	_	0.430	_	10.92	10
L	0.115	0.160	2.93	4.06	9
N		24	24	<u>.</u>	11

92CS-39943

### (E) Suffix (JEDEC MS-011-AA) 24-Lead Dual-In-Line Plastic Package

SYMBOL	IN	CHES	MILLIMI	NOTES	
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	-	0.250	_	6.35	9
A ₁	0.015		0.39	-	9
A ₂	0.125	0.195	3.18	4.95	
В	0.014	0.022	0.356	0.558	1
В ₁	0.030	0.070	0.77	1.77	3
c	0.008	0.015	0.204	0.381	Į.
D	1.150	1.290	29.3	32.7	4
D ₁	0.005	_	0.13	_	12
E	0.600	0.625	15.24	15.87	5
E ₁	0.485	0.580	12.32	14.73	6, 7
e	0.10	00 BSC	2.54 [	2.54 BSC	
e _A	0.60	00 BSC	15.24	BSC	9
eВ	_	0.700	İ –	17.78	10
Ĺ	0.115	0.200	2.93	5.08	9
N	'	24	24		11

# **Dual-In-Line Plastic Packages**

#### Notes:

- Refer to JEDEC Publication No. 95 JEDEC Registered and Standard Outlines for Solid State Products, for rules and general information concerning registered and standard outlines, in Section 2.2.
- 2. Protrusions (flash) on the base plane surface shall not exceed 0.010 in. (0.25 mm).
- The dimension shown is for full leads. "Half" leads are optional at lead positions

1, N, 
$$\frac{N}{2}$$
  $\frac{N}{2}$  +1.

- Dimension D does not include mold flash or protrusions.
   Mold flash or protrusions shall not exceed 0.010 in. (0.25 mm).
- E is the dimension to the outside of the leads and is measured with the leads perpendicular to the base plane (zero lead spread).
- 6. Dimension E₁ does not include mold flash or protrusions.
- Package body and leads shall be symmetrical around center line shown in end view.
- Lead spacing e shall be non-cumulative and shall be measured at the lead tip. This measurement shall be made before insertion into gauges, boards or sockets.
- This is a basic installed dimension. Measurement shall be made with the device installed in the seating plane gauge (JEDEC Outline No. GS-3, seating plane gauge). Leads shall be in true position within 0.010 in. (0.25 mm) diameter for dimension eg.
- e_B is the dimension to the outside of the leads and is measured at the lead tips before the device is installed.
   Negative lead spread is not permitted.
- 11. N is the maximum number of lead positions.
- Dimension D₁ at the left end of the package must equal dimension D₁ at the right end of the package within 0.030 in. (0.76 mm).
- 13. Pointed or rounded lead tips are preferred to ease insertion.
- 14. For automatic insertion, any raised irregularity on the top surface (step, mesa, etc.) shall be symmetrical about the lateral and longitudinal package centerlines.

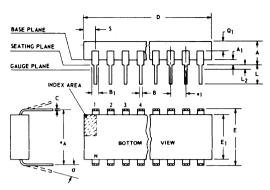
# (E) Suffix (JEDEC MS-011-AB) 28-Lead Dual-In-Line Plastic Package

SYMBOL	INCHES		MILLIMI	NOTES	
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	-	0.250	_	6.35	9
A ₁	0.015	_	0.39		9
A ₂	0.125	0.195	3.18	4.95	
В	0.014	0.022	0.356	0.558	
B ₁	0.030	0.070	0.77	1.77	3
C	0.008	0.015	0.204	0.381	
D	1.380	1.565	35.1	39.7	4
D ₁	0.005	_	0.13	_	12
E	0.600	0.625	15.24	15.87	5
E ₁	0.485	0.580	12.32	14.73	6, 7
e	0.10	0 BSC	2.54 E	BSC	8
e _A	0.60	0 BSC	15.24	BSC	9
e _B	_	0.700	_	17.78	10
L	0.115	0.200	2.93	5.08	9
N	l	28	28	<u> </u>	11

92CS-40000

92CS-40001

# **Dual-In-Line Frit-Seal Ceramic (CERDIP) Packages**



# (F) Suffix (JEDEC MO-001-AB) 14-Lead Dual-In-Line Frit-Seal Ceramic Package

SYMBOL	IN	CHES	MILLIM	MILLIMETERS	
SIMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	0.155	0.200	3.94	5.08	
A ₁	0.020	0.050	0.51	1.27	
В	0.014	0.020	0.356	0.508	
B ₁	0.050	0.065	1.27	1.65	
С	0.008	0.012	0.204	0.304	1
D	0.745	0.770	18.93	19.55	
E	0.300	0.325	7.62	8.25	
E ₁	0.240	0.260	6.10	6.60	
e ₁	0.1	00 TP	2.54	2	
e _A	0.3	00 TP	7.62 TP		2, 3
Ľ	0.125	0.150	3.18	3.81	
L ₂	0.000	0.030	0.00	0.76	
а	0°	15°	0°	15°	4
N		14	14		5
N ₁		0	0		6
Q ₁	0.040	0.075	1.02	1.90	
S	0.065	0.090	1.66	2.28	

92SS-4296R3

# (F) Suffix 20-Lead Dual-In-Line Frit-Seal Ceramic Package

SYMBOL	INC	CHES	MILLIM	ETERS	NOTES
SIMBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	0.120	0.250	3.10	6.30	
A ₁	0.020	0.070	0.51	1.77	
В	0.016	0.020	0.407	0.508	
В1	0.028	0.070	0.72	1.77	
C	0.008	0.012	0.204	0.304	1
D	0.942	0.990	23.93	25.15	
E	0.300	0.325	7.62	8.25	
E ₁	0.240	0.280	6.10	7.11	
e ₁	0.1	00 TP	2.54	2	
e _A	0.3	00 TP	7.62 TP		2, 3
Ĺ	0.100	0.200	2.54	5.00	
L ₂	0.000	0.030	0.00	0.76	
α	0°C	15°C	0°C	15° C	4
N		20	2	20	
N ₁	o		0		6
Q ₁	0.040	0.075	1.02	1.90	
s	0.040	0.100	1.02	2.54	

92CM-35137R1

#### NOTES:

Refer to JEDEC Publication No. 95 for Rules for Dimensioning Axial Lead Product Outlines.

- When this device is supplied solder-dipped, the maximum lead thickness (narrow portion) will not exceed 0.013 in. (0.33 mm).
- Leads within 0.005 in. (0.127 mm) radius of True Position (TP) at gauge plane with maximum material condition.
- 3. eA applies in zone Lo when unit is installed.
- 4. Applies to spread leads prior to installation.
- 5. N is the maximum quantity of lead positions.
- 6. N₁ is the quantity of allowable missing leads.

# (F) Suffix (JEDEC MO-001-AC) 16-Lead Dual-In-Line Frit-Seal Ceramic Package

SYMBOL	IN	CHES	MILLIMI	ETERS	NOTES
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	0.155	0.200	3.94	5.08	
A ₁	0.020	0.050	0.51	1.27	
В	0.014	0.020	0.356	0.508	
B ₁	0.035	0.065	0.89	1.65	
C	0.008	0.012	0.204	0.304	1
D	0.745	0.785	18.93	19.93	
E	0.300	0.325	7.62	8.25	
E ₁	0.240	0.260	6.10	6.60	
e ₁	0.1	00 TP	2.54	2	
e _A	0.3	00 TP	7.62 TP		2, 3
L.	0.125	0.150	3.18	3.81	
L ₂	0.000	0.030	0.00	0.76	
а	0°	15°	0°	15°	4
N		16	16	3	5
N ₁	0		0		6
Q ₁	0.040	0.075	1.02	1.90	
S	0.015	0.060	0.39	1.52	

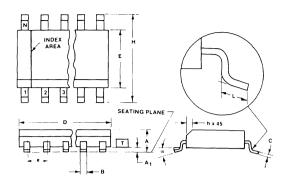
92CM-15967R4

# (F) Suffix (JEDEC MO-015-AA) 24-Lead Dual-In-Line Frit-Seal Ceramic Package

	IN	CHES	MILLIM	ETERS	
SYMBOL	MIN.	MAX.	MIN.	MAX.	NOTES
Α	0.120	0.250	3.10	6.30	
A ₁	0.020	0.070	0.51	1.77	
В	0.016	0.020	0.407	0.508	
B ₁	0.028	0.070	0.72	1.77	
С	0.008	0.012	0.204	0.304	1
D	1.200	1.290	30.48	32.76	
E	0.600	0.625	15.24	15.87	
E ₁	0.515	0.580	13.09	14.73	
e ₁	0.1	00 TP	2.54	TP	2
e _A	0.6	00 TP	15.24	TP	2,3
L	0.100	0.200	2.54	5.00	
L ₂	0.000	0.030	0.00	0.76	
α	0°C	15° C	0°C	15° C	4
N		24	24		5
N ₁	0		0		6
Q ₁	0.040	0.075	1.02	1.90	
S	0.040	0.100	1.02	2.54	2.0000000

92CS-26938R3

# **Dual-In-Line Surface Mount Plastic Packages**



#### NOTES:

- 1. Refer to applicable symbol list.
- 2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
- 3. "T" is a reference datum.
- "D" and "E" are reference datums and do not include mold flash or protrusions. Mold flash or protrusions shall not exceed .15mm (.006 in.).
- The chamfer on the body is optional. If it is not present, a visual index feature must be located within the cross hatched area.
- "L" is the length of terminal for soldering to a substrate.
- 7. "N" is the number of terminal positions.
- 8. Terminal numbers are shown for reference only.
- 9. Controlling dimensions: MILLIMETERS.

# (M) Suffix (JEDEC MS-012-AB) 14-Lead Dual-In-Line Surface-Mount Plastic Package

SYMBOL	IN	CHES	MILLIME	TERS	NOTES
STMBUL	MIN.	MAX.	MIN.	MAX.	NOTES
A	0.0532	0.0688	1.35	1.75	
A ₁	0.0040	0.0098	0.10	0.25	
В	0.0138	0.0192	0.35	0.49	
С	0.0075	0.0098	0.19	0.25	
D	0.3367	0.3444	8.55	8.75	4
E	0.1497	0.1574	3.80	4.00	4
e	0.05	0 BSC	1.27 BSC		
н	0.2284	0.2440	5.80	6.20	
h	0.0099	0.0196	0.25	0.50	5
L	0.016	0.050	0.40	1.27	6
N		14	14	4	7
α	0°	8°	0°	8°	

Notes: 1, 2, 3, 8, 9

92CS-38924R1

# (M) Suffix (JEDEC-MS-012-AC) 16-Lead Dual-In-Line Surface-Mount Plastic Package

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	NUTES
A	0.0532	0.0688	1.35	1.75	
A ₁	0.0040	0.0098	0.10	0.25	
В	0.0138	0.0192	0.35	0.49	
С	0.0075	0.0098	0.19	0.25	
D	0.3859	0.3937	9.80	10.00	4
E	0.1497	0.1574	3.80	4.00	4
e	0.050 BSC		1.27 BSC		
н	0.2284	0.2440	5.80	6.20	
h	0.0099	0.0196	0.25	0.50	5
L	0.016	0.050	0:40	1.27	6
N	,16		16		7
α	0°	8°	0°	8°	

Notes: 1, 2, 3, 8, 9

92CS-38925R1

# (M) Suffix (JEDEC-MS-013-AC) 20-Lead Dual-In-Line Surface-Mount Plastic Package

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
Α	0.0926	0.1043	2.35	2.65	
A ₁	0.0040	0.0118	0.10	0.30	
В	0.0138	0.0192	0.35	0.49	1
С	0.0091	0.0125	0.23	0.32	
D	0.4961	0.5118	12.60	13.00	4
E	0.2914	0.2992	7.40	7.60	4
е	0.050 BSC		1.27 BSC		
н	0.394	0.419	10.00	10.65	
h	0.010	0.029	0.25	0.75	5
L	0.016	0.050	0.40	1.27	6
N	20		20		7
α	0°	8°	l o°	8°	ł

Notes: 1, 2, 3, 8, 9

92CS-38926R1

# (M) Suffix (JEDEC MS-013-AD) 24-Lead Dual-In-Line Surface-Mount Plastic Package

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN.	MAX.	MIN.	MAX.	NOTES
Α	0.0926	0.1043	2.35	2.65	
A ₁	0.0040	0.0118	0.10	0.30	l
В	0.0138	0.0192	0.35	0.49	
С	0.0091	0.0125	0.23	0.32	1
D	0.5985	0.6141	15.20	15.60	4
Ε	0.2914	0.2992	7.40	7.60	4
е	0.050 BSC		1.27 BSC		
н	0.394	0.419	10.00	10.65	į
h	0.010	0.029	0.25	0.75	5
L	0.016	0.050	0.40	1.27	6
N	24		24		7
α	0°	8°	0°	8°	

Notes: 1, 2, 3, 8, 9

92CS-39037R1

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